

Memory Interface Solutions

User Guide

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Revision History

The following table shows the revision history for this document.

Date	Version	Revision
10/01/04	1.0	Initial MIG 1.0 release.
01/01/05	1.1	MIG 1.1 release.
05/01/05	1.2	MIG 1.2 release.
08/18/05	1.3	MIG 1.3 release.
11/04/05	1.4	MIG 1.4 release.
02/15/06	1.5	MIG 1.5 release.
03/28/06	1.5.1	Updated Table 3-10 and added Table 3-11 .
07/28/06	1.6	MIG 1.6 release.
03/21/07	1.7	MIG 1.7 release.

Date	Version	Revision
04/30/07	1.7.2	MIG 1.72 release. Added support for Spartan-3AN FPGAs.
07/05/07	1.7.3	MIG 1.73 release. Added support for Spartan-3A DSP FPGAs. Corrected minor typographical errors.
09/18/07	2.0	MAJOR REVISION. MIG Wizard guide added to Chapter 1. Design Frequency Range and Hardware Tested Configuration tables added in most chapters. Diagram and table updates throughout.
01/09/08	2.1	MIG 2.1 release. Revisions and added material throughout, including new Chapter 12, Appendix B, and Appendix D.
03/03/08	2.2	MIG 2.2 release. Added Qimonda support. Updated screen captures in Chapter 1. Added Spartan-3E FPGA support to Chapters 7 and 8. Added footnote to Table 9-1, page 356 . Added “Timing Analysis” in Appendix A . Added information on loading of address, command, and control signals to “Pin Assignments” in Appendix A . Replaced Appendix D.
09/19/08	2.3	MIG 2.3 release. Added Chapter 12, “Implementing DDRII SRAM Controllers.” Updated screen captures in Chapter 1. Added Appendix E, “Debug Port.” Added support for Virtex®-5 TXT devices. Minor updates throughout.
10/02/08	2.3.1	MIG 2.3 release. Added Appendix G, “Low Power Options.” Additional miscellaneous typographical edits throughout.
04/24/09	3.0	MIG 3.0 release. Updated screen captures in Chapter 1, “Using MIG.” Added Chapter 13, “Simulating MIG Designs.” Updated Appendix B, “Pinout-Related UCF Constraints for Virtex-5 FPGA DDR2 SDRAMs.” Added Appendix D, “SSO for Spartan FPGA Designs.” Updated content throughout.
06/24/09	3.1	MIG 3.1 release. Updated description and screen captures in Chapter 1, “Using MIG.” Updated Chapter 13, “Simulating MIG Designs,” and Appendix A, “Memory Implementation Guidelines.” Minor updates throughout.
09/16/09	3.2	MIG 3.2 release. Updated screen captures in Chapter 1, “Using MIG.” Combined Verify UCF and Update UCF sections into “Verify UCF and Update Design and UCF” in Chapter 1 . Updated Table 6-2, page 254 . Added Table 10-8, page 420 . Replaced “Signals of Interest” section with “Debugging Calibration Failures,” page 538 . Updated “Enabling the Debug Port,” page 571 . Minor updates throughout.
12/02/09	3.3	MIG 3.3 release. Fixed Pin Out feature description, and updated screen captures in Chapter 1, “Using MIG.” Removed references to <code>sim.exe</code> in Chapter 13, “Simulating MIG Designs.” Added Appendix F, “Analyzing MIG Designs in the ChipScope Analyzer with CDC.” Minor updates throughout.
04/19/10	3.4	MIG 3.4 release. Updated screen captures, removed “Using MIG in Batch Mode,” and updated “Implementing MIG Designs in ISE GUI Mode” in Chapter 1 . Updated Figure 8-8 .
07/23/10	3.5	MIG 3.5 release. Removed <code>wdf_almost_full</code> signal from Figure 2-13 . Updated Table 6-13 . Updated “Simulating the RLDRAM II Design” in Chapter 6 . Added “Changing the Refresh Rate” in Chapter 9 . Added “Burst Length of Two Design without FIFO Interface” in Chapter 10 . Updated “User Interface Accesses,” “Write Interface,” and “Read Interface” in Chapter 10 . Added “Changing the Refresh Rate” in Chapter 11 . Updated “Design Notes” in Chapter 13 . Updated “Memory-Specific Guidelines” in Appendix A .

Date	Version	Revision
09/21/10	3.6	MIG 3.6 release. Updated ISE® Design Suite version to 12.3 throughout. Updated “I/O Standards,” page 553.

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About This Guide

The Memory Interface Generator (MIG) generates DDRII SRAM, DDR SDRAM, DDR2 SDRAM, QDRII SRAM, and RLDRAM II interfaces for Virtex®-4 FPGAs and generates DDR SDRAM, DDR2 SDRAM, QDRII SRAM, and DDRII SRAM interfaces for Virtex-5 FPGAs. It also generates DDR and DDR2 SDRAM interfaces for Spartan®-3, Spartan-3A, Spartan-3E, and Spartan-3A DSP FPGAs. The tool takes inputs such as the memory interface type, FPGA family, FPGA devices, frequencies, data width, memory mode register values, and so forth, from the user through a graphical user interface (GUI). The tool generates RTL, SDC, UCF, and document files as output. RTL or EDIF (EDIF is created after running a script file, where the script file is a tool output) files can be integrated with other design files.

Refer to the [Xilinx website](http://www.xilinx.com) for the latest updates to this user guide.

Guide Contents

This manual contains the following chapters:

- [Section I: “Introduction”](#)
 - [Chapter 1, “Using MIG,”](#) shows how to install and use the MIG design tool.
- [Section II: “Virtex-4 FPGA to Memory Interfaces”](#)
 - [Chapter 2, “Implementing DDR SDRAM Controllers,”](#) describes how to implement DDR SDRAM interfaces that MIG creates for Virtex-4 FPGAs.
 - [Chapter 3, “Implementing DDR2 SDRAM Controllers,”](#) describes how to implement DDR2 SDRAM interfaces that MIG creates for Virtex-4 FPGAs.
 - [Chapter 4, “Implementing QDRII SRAM Controllers,”](#) describes how to implement QDRII SRAM interfaces that MIG creates for Virtex-4 FPGAs.
 - [Chapter 5, “Implementing DDRII SRAM Controllers,”](#) describes how to implement DDRII SRAM interfaces that MIG creates for Virtex-4 FPGAs.
 - [Chapter 6, “Implementing RLDRAM II Controllers,”](#) describes how to implement RLDRAM II interfaces that MIG creates for Virtex-4 FPGAs.
- [Section III: “Spartan-3/3E/3A/3AN/3A DSP FPGA to Memory Interfaces”](#)
 - [Chapter 7, “Implementing DDR SDRAM Controllers,”](#) describes how to implement DDR SDRAM interfaces that MIG creates for Spartan-3 FPGAs.
 - [Chapter 8, “Implementing DDR2 SDRAM Controllers,”](#) describes how to implement DDR2 SDRAM interfaces that MIG creates for Spartan-3 FPGAs.
- [Section IV: “Virtex-5 FPGA to Memory Interfaces”](#)
 - [Chapter 9, “Implementing DDR2 SDRAM Controllers,”](#) describes how to implement DDR2 SDRAM interfaces that MIG creates for Virtex-5 FPGAs.

- Chapter 10, “Implementing QDR II SRAM Controllers,” describes how to implement QDR II SRAM interfaces that MIG creates for Virtex-5 FPGAs.
- Chapter 11, “Implementing DDR SDRAM Controllers,” describes how to implement DDR SDRAM interfaces that MIG creates for Virtex-5 FPGAs.
- Chapter 12, “Implementing DDR II SRAM Controllers,” describes how to implement DDR II SRAM interfaces that MIG creates for Virtex-5 FPGAs.
- Section V: “Simulation Guide”
 - Chapter 13, “Simulating MIG Designs,” provides detailed information about simulating MIG designs for Virtex-5, Virtex-4, and Spartan-3 FPGAs.
- Section VI: “Debug Guide”
 - Chapter 14, “Debugging MIG DDR2 Designs” provides a step-by-step process for debugging designs that use MIG-generated memory interfaces.
- Section VII: “Appendices”
 - Appendix A, “Memory Implementation Guidelines,” provides helpful rules for reference designs.
 - Appendix B, “Pinout-Related UCF Constraints for Virtex-5 FPGA DDR2 SDRAMs,” provides detailed information about modifying pinout-dependent UCF constraints for Virtex-5 FPGA DDR2 SDRAMs.
 - Appendix C, “WASSO Limit Implementation Guidelines,” gives references to data and tools necessary for ensuring compliance with Simultaneous Switching Output (SSO) limitations.
 - Appendix D, “SSO for Spartan FPGA Designs,” describes SSO requirements for Spartan FPGA designs.
 - Appendix E, “Debug Port” provides information on the Debug port added to all memory interface designs for MIG 2.2 and later.
 - Appendix G, “Low Power Options,” provides information about the low power option implementation and IODELAY performance modes.
 - Appendix G, “Low Power Options,” provides an example of pin mapping for x4 DDR2 RDIMMs between the memory data sheet and the user constraints file.

References

The following documents provide supplementary material useful with this user guide:

1. Samsung Data Sheet k7i321884m_R04
http://www.samsung.com/Products/Semiconductor/SRAM/SyncSRAM/DDR II_CIO_SIO/36Mbit/K7I321884M/K7I321884M.htm
2. Micron Data Sheet MT47H16M16FG-37E
<http://www.micron.com/products/dram/ddr2sdram/partlist.aspx>
3. Samsung Data Sheet k7r323684m
http://www.samsung.com/Products/Semiconductor/common/product_list.aspx?family_cd=SRM020302
4. Micron Data Sheet MT49H16M18FM-25
<http://www.micron.com/products/dram/rldram/part.aspx?part=MT49H16M18FM-25>
5. Micron Data Sheet MT46V16M16FG-5B
<http://www.micron.com/products/dram/ddrdsram/partlist.aspx>
6. Xilinx® ChipScope™ Pro analyzer documentation
<http://www.xilinx.com/literature/literature-chipscope.htm>

7. [UG070](#), *Virtex-4 FPGA User Guide*
8. [UG072](#), *Virtex-4 FPGA PCB Designer's Guide*
9. [UG079](#), *Virtex-4 ML461 Memory Interfaces Development Board User Guide*
10. [UG190](#), *Virtex-5 FPGA User Guide*
11. [DS202](#), *Virtex-5 FPGA Data Sheet: DC and Switching Characteristics*
12. [UG203](#), *Virtex-5 FPGA PCB Designer's Guide*
13. [UG195](#), *Virtex-5 FPGA Packaging and Pinout Specification*
14. [UG199](#), *Virtex-5 FPGA ML561 Memory Interfaces Development Board User Guide*
15. [XAPP454](#), *DDR2 SDRAM Memory Interface for Spartan-3 FPGAs*
16. [XAPP458](#), *Implementing DDR2-400 Memory Interfaces in Spartan-3A FPGAs*
17. [XAPP645](#), *Single Error Correction and Double Error Detection*
18. [XAPP701](#), *Memory Interfaces Data Capture Using Direct Clocking Technique*
19. [XAPP702](#), *DDR-2 Controller Using Virtex-4 Devices*
20. [XAPP703](#), *QDR II SRAM Interface*
21. [XAPP709](#), *DDR SDRAM Controller Using Virtex-4 FPGA Devices*
22. [XAPP710](#), *Synthesizable CIO DDR RLD RAM II Controller for Virtex-4 FPGAs*
23. [XAPP721](#), *High-Performance DDR2 SDRAM Memory Interface Data Capture Using ISERDES and OSERDES*
24. [XAPP768c](#), *Interfacing Spartan-3 Devices With 166 MHz or 333 Mb/s DDR SDRAM Memories (available under click license)*
25. [XAPP851](#), *DDR SDRAM Controller Using Virtex-5 FPGA Devices*
26. [XAPP853](#), *QDR II SRAM Interface for Virtex-5 Devices*
27. [XAPP858](#), *High-Performance DDR2 SDRAM Interface In Virtex-5 Devices*
28. [DS099](#), *Spartan-3 FPGA Family: Complete Data Sheet*
29. [DS312](#), *Spartan-3E FPGA Family: Complete Data Sheet*
30. [DS529](#), *Spartan-3A FPGA Family Data Sheet*
31. [DS557](#), *Spartan-3AN FPGA Family Data Sheet*
32. [DS610](#), *Spartan-3A DSP FPGA Family Data Sheet*
33. [Chapter 6: PARTGen](#), *Development System Reference Guide*
34. WASSO Calculator for Virtex-4 devices
<https://secure.xilinx.com/webreg/clickthrough.do?cid=30163>
35. WASSO Calculator for Virtex-5 devices
<https://secure.xilinx.com/webreg/clickthrough.do?cid=30154>
36. Micron Technical Note TN-47-01, *DDR2-533 Memory Design Guide for Two-DIMM Unbuffered Systems*
http://download.micron.com/pdf/technotes/ddr2/tn_47_01.pdf
37. [DS317](#), *FIFO Generator v4.4 Data Sheet*

Additional Resources

To search the database of silicon and software questions and answers, or to create a technical support case in WebCase, see the Xilinx website at:
<http://www.xilinx.com/support>.

Typographical Conventions

This document uses the following typographical conventions. An example illustrates each convention.

Convention	Meaning or Use	Example
<i>Italic font</i>	References to other documents	See the <i>Virtex-4 Configuration Guide</i> for more information.
	Emphasis in text	The address (F) is asserted <i>after</i> clock event 2.
<u>Underlined Text</u>	Indicates a link to a web page.	http://www.xilinx.com/virtex4

Type Case of Port and Signal Names

Some port and signal names given in the figures and tables in this document might appear in uppercase type, even though those same names are in lowercase type in the designs themselves. This is strictly a typographical issue in the User Guide, and does not imply that the port and signal names in the designs need to be changed.



Section I: Introduction

Chapter 1, "Using MIG"

Using MIG

MIG is a tool used to generate memory interfaces for Xilinx® FPGAs. MIG generates Verilog or VHDL RTL design files, user constraints files (UCF), and script files. The script files are used to run simulations, synthesis, map, and par for the selected configuration.

This chapter describes the user interface details of all memory interfaces supported in MIG. It provides MIG features, usage, and installation details and describes the output files. This chapter also summarizes the changes and enhancements made from earlier versions of MIG.

MIG 3.6 Changes from MIG 3.5

The new features of MIG 3.6 are summarized in this section:

- ISE® Design Suite 12.3 software support

MIG 3.5 Changes from MIG 3.4

The new features of MIG 3.5 are summarized in this section:

- ISE Design Suite 12.2 software support

MIG 3.4 Changes from MIG 3.3

The new features of MIG 3.4 are summarized in this section:

- ISE Design Suite 12.1 software support

MIG 3.3 Changes from MIG 3.2

The new features of MIG 3.3 are summarized in this section:

- ISE Design Suite 11.4 software support
- Support of different frequencies for Virtex-5 FPGA multicontroller and multiple-interface designs
- Frequency selection in GUI changed to Clock Period
- Fixed Pin Out selection feature for Virtex-5 FPGAs in DDR SDRAM, DDR2 SDRAM, and QDRII SRAM designs.
- CDC support for all MIG-generated Debug enable designs

MIG 3.2 Changes from MIG 3.1

The new features of MIG 3.2 are summarized in this section:

- ISE Design Suite 11.3 software support
- DDR2 SDRAM twin-die component (4 GB) support for Virtex-5 FPGA designs
- Verify UCF and Update Design options are combined into Verify UCF and Update Design and UCF

MIG 3.1 Changes from MIG 3.0

The new features of MIG 3.1 are summarized in this section:

- ISE Design Suite 11.2 software support
- DDR2 SDRAM 4 GB memory part support for Virtex®-4 and Virtex-5 FPGA designs

MIG 3.0 Changes from MIG 2.3

The new features of MIG 3.0 are summarized in this section:

- ISE Design Suite 11.1 IP update 1 software support
- 64-bit/32-bit Linux Red Hat Enterprise 5.0 support
- 64-bit Windows Vista support
- 32-bit SUSE 10 support
- Verify UCF and Update Design support for Virtex-5 FPGA multicontroller designs
- Batch mode support for Create Custom Memory Part
- Weighted Average Simultaneously Switching Output (WASSO) support for Spartan® FPGA designs
- Removed the Preset Configurations option from the GUI

MIG 2.3 Changes from MIG 2.2

The new features of MIG 2.3 are summarized in this section:

- Support for DDRII SRAM for Virtex-5 FPGAs
- Power PC 440 (PPC440) processor compatible pinout support for Virtex-5 FPGA DDR2 SDRAM
- Support for single-ended versus differential system clock selection in the GUI
- Support for two bytes per bank for data group signals for Virtex-5 FPGA DDR2 SDRAM designs
- Support for high performance mode for IODELAY in the GUI
- FPGA floor plan changed to an architectural view from package view
- Support for multiple interface simulation testbench for Virtex-5 FPGAs
- Separate options for Verify UCF and Update Design in GUI
- Support for Verify UCF and Update Design for Spartan FPGA designs in the GUI
- Support for Virtex-5 TXT FPGA designs
- Support for Debug Port for Virtex-4 FPGA DDR2 SDRAM direct-clocking design

MIG 2.2 Changes from MIG 2.1

The new features of MIG 2.2 are summarized in this section:

- Support of Qimonda memory parts for the DDR2 SDRAM interface of all FPGA families.
- Multiple interface support in Virtex-5 FPGAs for DDR2 SDRAM and QDRII SRAM designs:
 - Provides an option to select DDR2 SDRAM and QDRII SRAM interfaces for multicontroller designs
 - Supports different frequencies for different memory interfaces.
 - Provides controller-wise DCI Cascade support
- Creates different UCF files for all the selected compatible FPGAs
- Enhanced support for the Debug port option using VIO
- Updates to Virtex-5 and Virtex-4 FPGA designs:
 - Supports updated designs
 - Provides an option to browse the old project file (.prj) in the Verify UCF page
 - Provides IDELAYCTRL location constraints in the UCF
- Added Debug port to all memory interface designs

MIG 2.1 Changes from MIG 2.0

The new features of MIG 2.1 are summarized in this section:

- Support for 64-bit/32-bit Linux Red Hat Enterprise 4.0
- Support for 64-bit Microsoft Windows XP Professional
- Support for 32-bit Microsoft Vista Business
- Support for 64-bit SUSE 10 Enterprise
- Data mask enable/disable option for DDR and DDR2 SDRAM designs
- Debug signals support
- Real-time pin allocation implemented in the GUI. As the user selects the banks, the GUI displays the information as the total number of required pin count and the number of pins allocated for each group of signals.
- Implements the priority bank selection for the data. Priority is given for exclusive Data banks first, then Data banks with the combination of other groups.
- Creates the RLOC and DQS gate constraints to older versions of UCF files that use the design from MIG 2.0 or following versions for Virtex-5 FPGA DDR2 SDRAMs. An option is provided to add or not add the constraints while verifying the UCF.
- Simulations support for custom memory parts
- Reserve Pin banks are changed from list view to hierarchical view
- Implemented the DCI Cascade and Master Bank selection option for QDRII SRAM Virtex-5 FPGA designs
- Support for Spartan-3A FPGA DDR2 SDRAM 200 MHz design
- 166 MHz frequency support for all possible data widths for Spartan-3E, Spartan-3A, and Spartan-3A DSP families

- Uncommon banks are faded out in the Bank Selection page when the user selects compatible FPGAs, allowing only the common banks for pin allocation
- Attributes X_CORE_INFO and CORE_GENERATION_INFO support for all designs
- Updates to Virtex-5 FPGA designs:
 - DDR2 SDRAM
 - Changing the MIG 1.73 or prior versions of UCF files compatible to MIG 2.0 or following versions of designs using Verify UCF feature
 - QDRII SRAM
 - BL2 support
 - DCI cascade support
- Updates to Virtex-4 FPGA designs:
 - DDR2 SDRAM Direct Clocking
 - CAS latency 5 support
 - Linear addressing support from the user interface
 - Calibration algorithm modified to fix the low-frequency issues
 - DDR2 SDRAM SerDes
 - Linear addressing support from the user interface
 - DDR SDRAM
 - Linear addressing support from the user interface
 - DDRII SRAM
 - Two address FIFOs replaced by a common address FIFO for both write and read commands
- Updates to Spartan FPGA designs:
 - DDR2 SDRAM and DDR SDRAM
 - Linear addressing support from the user interface

For MIG 2.1 release notes and a list of specific issues addressed in this release, consult Xilinx Answer Record [29767](#).

MIG 2.0 Changes from MIG 1.73

The new features of MIG 2.0 are summarized in this section:

- MIG GUI is changed to WIZARD implementation
- Supports 32-bit Linux Red Hat Enterprise 4.0
- Generates a compatible simulation testbench for the generated design
- Supports Preset Configuration
- Updates to Virtex-5 FPGA designs:
 - DDR SDRAM
 - Support for DIMMs
 - DDR2 SDRAM
 - Major physical layer changes: Read capture architecture modified, support added for read postamble DQS glitch gating, operation of PHY logic at half clock speed. See [XAPP858](#) for details.

- Support for unbuffered DIMMs. Implemented 2T timing to support unbuffered DIMMs
- 72-bit ECC support
- QDRII SRAM
 - Partial support for DCI Cascade
 - Allocating CQ, CQ# pins
 - Allocating K, K# to P and N pairs
 - Read data FIFOs removed from the user interface
- Unsupported features:
 - Edit signal names

For MIG 2.0 release notes and a list of specific issues addressed in this release, consult Xilinx Answer Record [29312](#).

MIG 1.73 Changes from MIG 1.72

The new features of MIG 1.73 are summarized in this section:

- Spartan-3A DSP FPGAs are supported

MIG 1.72 Changes from MIG 1.7

There are no new features added to this release from MIG 1.7.

For MIG 1.72 release notes and a list of specific issues addressed in this release, consult Xilinx Answer Record [25056](#).

MIG 1.7 Changes from MIG 1.6

The new features of MIG 1.7 are summarized in this section:

- Supports creating a new memory part by modifying an existing part
- Generates a script file to create an ISE software project
- Updates to Virtex-5 FPGA designs:
 - Supports DDR SDRAM Verilog and VHDL
 - Supports QDRII SRAM and DDR2 SDRAM VHDL
- Updates to Virtex-4 FPGA designs:
 - DDR2 SDRAM
 - ECC supported in Pipelined or Unpipelined modes
 - Add per-bit skew for DDR2 direct clocking
 - Change SerDes clock scheme
 - QDRII SRAM
 - No digital clock manager (DCM) support
 - DDRII SRAM
 - No DCM support
- Updates to Spartan-3 FPGA designs:
 - Spartan-3A FPGA support for DDR and DDR2 SDRAMs

- Pinout compatibility with MIG 1.6 and MIG 1.5 versions for Spartan-3 and Spartan-3E devices. There are several limitations to this feature. Contact Xilinx support for more details.

For MIG 1.7 release notes and a list of specific issues addressed in this release, consult Xilinx Answer Record [25406](#).

MIG 1.6 Changes from MIG 1.5

The new features of MIG 1.6 are summarized in this section:

- Supports Virtex-5 FPGA interfaces
- Outputs two different folders with and without a testbench for the selected memory interface. This feature is supported for all interfaces.
- Supports batch mode
- Virtex-4 FPGA GUI changes
 - DDR SDRAM
 - No DCM support
 - RLDRAM II
 - No DCM support
 - DCI for data
 - DCL for address and control
- Spartan-3 FPGA GUI changes
 - DDR2 SDRAM
 - No DCM support
- Removed Add Testbench button. The tool by default outputs with and without testbench designs, hence it is not required to have the Add Testbench button.

MIG 1.5 Changes from MIG 1.4

The new features of MIG 1.5 are summarized in this section:

- GUI changes:
 - Clock-capable I/Os for strobes and read clocks for direct-clocking method
 - Programmable Mode Register options
 - Verify my UCF feature
 - Programmable pin allocation limit for selected banks
 - Reserved Pin list
 - Save option to a file
- DDR2 SDRAM direct-clocking (Virtex-4 FPGA interfaces) support:
 - Synplicity Synplify 8.2 support
 - SODIMM support
 - Modified Read Enable implementation
- ISE 8.1.01i tool support (all MIG 1.5 designs support this ISE tool version)
- DDR2 SDRAM SerDes clocking (Virtex-4 FPGA interfaces) support
- DDR SDRAM for Virtex-4 FPGA interfaces:

- Synplicity Synplify 8.2 support
- CL = 2, 2.5, and 4
- BL = 2 and 8
- SODIMMs
- Support for more memory devices
- Modified Read Enable implementation
- DDR SDRAM for Spartan-3/Spartan-3E devices:
 - CL = 2 and 2.5
 - BL = 2 and 8
 - Synplicity Synplify 8.2
 - Registered DIMMs
 - Support for more memory devices
- DDR2 SDRAM for Spartan-3 devices:
 - Synplicity Synplify 8.2
 - BL = 8
 - Registered DIMMs
- RLDRAM II:
 - Synplicity Synplify 8.2 support
- QDRII and DDRII SRAMs:
 - Synplicity Synplify 8.2 support
- Supports skip wait 200 μ s delay for Verilog simulations. This feature is not supported for VHDL cases.
 - To skip 200 μ s initial delay, users should use the following run-time options for Verilog in ModelSim.
 - For DDR SDRAM for Virtex-4 FPGA interfaces:


```
vlog +define+simulation modulename_ddr_controller_0.v
```

 Where:
 - simulation is the parameter.
 - modulename_ddr_controller.v is the file with the parameter 'simulation'. The file modulename_ddr_controller.v must be present in the sim folder.
 - For DDR2 SDRAM for Virtex-4 FPGA interfaces:


```
vlog +define+simulation modulename_ddr2_controller_0.v
```
 - For Spartan-3 FPGA interfaces:


```
vlog +define+simulation modulename_ddr_infrastructure_top.v
```

Tool Features

The key features of MIG are listed below:

- Supported memory types for Virtex-5 FPGA interfaces:
 - DDR2 SDRAM components and single-rank DIMMs
See [“Supported Devices” in Chapter 9](#) for a complete listing of supported devices.
 - QDRII SRAM and DDRII SRAM
See [“Supported Devices” in Chapter 10](#) for a complete listing of supported QDRII devices. See [“Supported Devices” in Chapter 12](#) for a complete listing of supported DDRII devices.
 - DDR SDRAM components and single-rank DIMMs
See [“Supported Devices” in Chapter 11](#) for a complete listing of supported devices.

Both Verilog and VHDL RTL are generated. Additional devices can be created using the “Create Custom Part” feature.

- Supported memory types for Virtex-4 FPGA interfaces:
 - DDR SDRAM components, registered DIMMs, unbuffered DIMMs, and SODIMMs.
See [“Supported Devices” in Chapter 2](#) for a complete listing of supported devices.
 - DDR2 SDRAM components and single-rank DIMMs. The DDR2 controller supports deep memory depths from one to four.
See [“Supported Devices” in Chapter 3](#) for a complete listing of supported devices.
 - QDRII and DDRII SRAMs
See [“Supported Devices” in Chapter 4](#) for a complete listing of supported QDRII devices.
See [“Supported Devices” in Chapter 5](#) for a complete listing of supported DDRII devices.
 - RLDRAM II CIO and SIO memories
See [“Supported RLDRAM II Devices” in Chapter 6](#) for a complete listing of supported devices.

Additional devices can be created using the “Create Custom Part” feature.

- Supported memory types for Spartan-3 FPGA interfaces:
 - DDR SDRAM components, registered DIMMs, unbuffered DIMMs, and SODIMMs.
See [“Supported Devices” in Chapter 7](#) for a complete listing of supported devices.
 - DDR2 SDRAM components, registered DIMMs, unbuffered DIMMs, and SODIMMs.
See [“Supported Devices” in Chapter 8](#) for a complete listing of supported devices.

Additional devices can be created using the “Create New Memory Part” feature.

- Supported memory types for Spartan-3E FPGA interfaces:
 - DDR SDRAM components
See [“Supported Devices” in Chapter 7](#) for a complete listing of supported devices.

Additional devices can be created using the “Create New Memory Part” feature.

- Supported memory types for Spartan-3A/3AN FPGA interfaces:
 - DDR SDRAM components, registered DIMMs, unbuffered DIMMs, and SODIMMs.
See [“Supported Devices” in Chapter 7](#) for a complete listing of supported devices.
 - DDR2 SDRAM components, registered DIMMs, unbuffered DIMMs, and SODIMMs.
See [“Supported Devices” in Chapter 8](#) for a complete listing of supported devices.

Additional devices can be created using the “Create New Memory Part” feature.

- Supported memory types for Spartan-3A DSP FPGA interfaces:
 - DDR SDRAM components, unbuffered DIMMs, and SODIMMs.
See [“Supported Devices” in Chapter 7](#) for a complete listing of supported devices.
 - DDR2 SDRAM components, unbuffered DIMMs, and SODIMMs.
See [“Supported Devices” in Chapter 8](#) for a complete listing of supported devices.

Additional devices can be created using the “Create New Memory Part” feature.

- Supported synthesis and place-and-route tools:
 - XST (Xilinx ISE Design Suite 10.1) and Synplify Pro Version 8.8.0.4 are supported for Virtex-5, Virtex-4, and Spartan-3/3E/3A/3AN/3A DSP FPGA interfaces
- All currently available Virtex-5, Virtex-4, Spartan-3A, Spartan-3AN, Spartan-3A DSP, Spartan-3E, and Spartan-3 FPGAs are supported.
- DDR2 designs can use either the SerDes or the direct-clocking technique. The individual bits are deskewed in the direct-clocking technique used in DDR2 designs. The direct-clocking technique for other memories does not deskew each bit. Details are explained in the appropriate application notes referenced in this document.
- Direct and SerDes clocking techniques for data capture for Virtex-4 FPGA interfaces.
Direct clocking using per-bit deskew is explained in XAPP701 [\[Ref 18\]](#). With this technique, it is not necessary to use clock-capable I/Os for strobes or read clocks. SerDes clocking is explained in XAPP721 [\[Ref 23\]](#). The use of clock-capable I/Os for strobes and read clocks is recommended for maximum flexibility with higher frequency designs (200 MHz and above).

- Local clocking technique for data capture for all Spartan-3, Spartan-3A/3AN/3A DSP, and Spartan-3E FPGA interfaces.

The data capture technique using Spartan-3 FPGAs is explained in XAPP768c [\[Ref 24\]](#).

- VHDL and Verilog RTLs are supported for all designs.
- Variable data widths in multiples of 8 up to 144 bits.

The actual width depends upon the selected component. For a 9-bit wide component, data widths of 9, 18, 36, and 72 are supported.

For DDR2 SDRAM, most of the components support up to a 144-bit data width. 16-bit or 8-bit wide components can be used to create designs of any data width that is a multiple of 8.

- User-selectable banks for address, data, system control, and system clock signals.
For QDRII SRAM and RLDRAM II (SIO) memories, the user selects the data banks for reads and writes separately.

- Different banks are supported with different I/O standards.
MIG uses different banks for groups of signals whose I/O standards are different. If the I/O voltages for different groups (such as address, data, and system control) are different, the user must ensure enough banks are selected for MIG to use. If insufficient banks are selected, MIG cannot allocate pins.
- Various configurations are supported through changing bits in the Mode and Extended Mode registers.
- All fields not highlighted in the GUI either are not supported or are not relevant for that type of memory.
- Only one type of component is supported per interface.
Users cannot mix different components to create an interface.
- Multiple DDR2 interfaces for Virtex-4 FPGA designs.
Users can create up to eight controllers.
- Multiple DDR2 and QDRII interfaces for Virtex-5 FPGA designs and the combination of both interfaces can be selected.
- Different frequencies can be set for different memory interfaces in Virtex-5 FPGA designs.
- Pin compatibility.
Users can select multiple devices with the same package to generate compatible pinouts.
- Update design.
Users can update the old UCF files to be compatible with the latest MIG designs.

Design Tools

All MIG designs have been tested with ISE Design Suite 10.1 and Synplify Pro. MIG is currently supported on the following operating systems: 64-bit/32-bit Microsoft Windows XP, 64-bit/32-bit Linux Red Hat Enterprise 4.0, 32-bit Vista Business, and 64-bit SUSE 10 Enterprise.

Installation

MIG provides Xilinx CORE Generator™ tool reference designs and is included in the latest IP update. IP updates are available through the Xilinx Download Center or WebUpdate. Visit the Xilinx Download Center for the latest IP update and full documentation on both installation methods at <http://www.xilinx.com/download>.

Getting Started

MIG is a self-explanatory tool. This section is intended to help with understanding the various steps involved in using it.

The following steps launch MIG:

1. The CORE Generator system is launched by selecting **Start** → **Xilinx ISE Design Suite 12.3** → **ISE** → **Accessories** → **CORE Generator**.
2. Create a CORE Generator project.

3. The Xilinx part must be correctly set because it cannot be changed inside MIG. Virtex-5, Virtex-4, and Spartan-3/Spartan-3E/Spartan-3A/3AN/3A DSP devices are supported. Select the part via the part's Project Options menu in the CORE Generator system. The Generation tab is used to select between Verilog or VHDL by "design entry" under "flow". The "flow settings" and "vendor" must be chosen appropriately. The vendor choices are "Synplify" for Synplify and "ISE" for XST.
4. Remember the location of the CORE Generator project directory. The "View by Function" tab to the left shows the available cores organized into folders.
5. MIG is launched by selecting **Memories & Storage Elements** → **Memory Interface Generator** → **MIG**.
6. The name of the module to be generated is entered in the Component Name text box. After entering all the parameters in the GUI, click **Generate** to generate the module files in a directory with the same name as the component name in the CORE Generator project directory. After successful generation of the module files, the GUI is closed automatically.

The "Generated IP" tab to the left lists the generated modules.

MIG User Interface

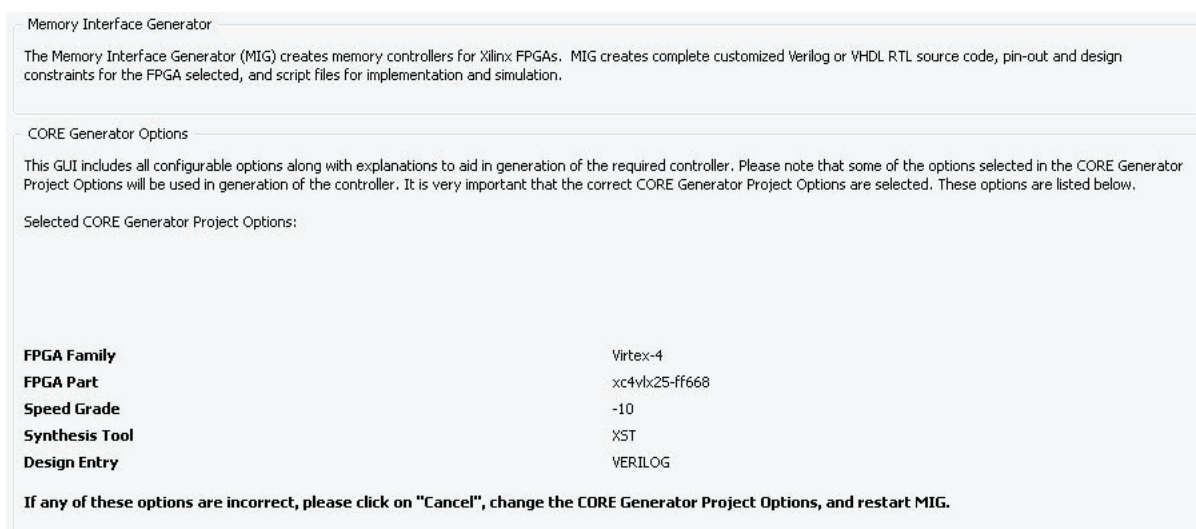
Getting Help

At any point in time, the MIG user manual can be accessed by clicking the **User Guide** button.

Version Information

The **Version Info** Button gives the information on new features added and the bugs fixed in the current version. It opens the web browser to display the contents.

CORE Generator Options



UG086_c1_04_072008

Figure 1-1: CORE Generator Options

The CORE Generator Options screen displays the details of the selected CORE Generator options that are selected before invoking MIG.

Note: CORE Generator project options are used in the generation of the memory controller. Correct CORE Generator project options must be selected.

If the displayed CORE Generator Project Options are inaccurate, click the **Cancel** button and reselect the CORE Generator Project Options.

Click **Next** to continue. A new window shows the MIG Output Options page.

MIG Output Options

MIG can have four different output options. They are:

1. [Create Design](#)
2. [Create Design for Xilinx Reference Boards](#)
3. [Verify UCF and Update Design and UCF](#)
4. [Spartan-3A FPGA DDR2 SDRAM 200 MHz Design](#)

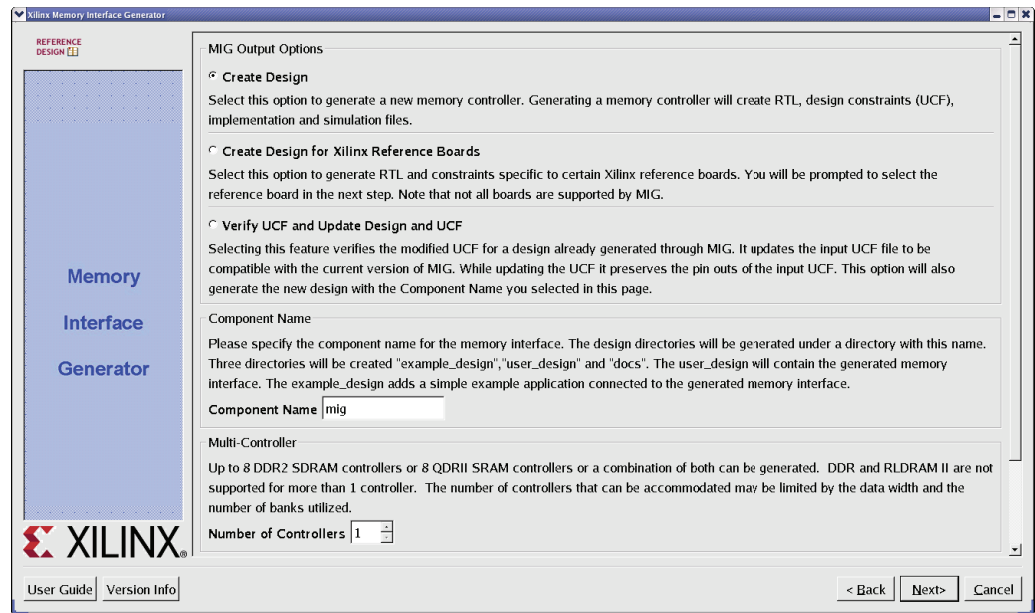
MIG outputs are generated with the folder name *<Component Name>*. For Virtex-4 FPGA and Spartan-3 FPGA designs, the top file (*<top_module>*) name is same as the *<Component Name>* entered in the GUI; all other RTL file names are prepended with *<Component Name>*. For example, for a Virtex-4 FPGA DDR2 SDRAM direct-clocking design with a component name of *mig* that is entered in the GUI, *<design_top>* file name becomes *mig.v* or *mig.vhd*, based on the HDL type selected. All other RTL files are prepended with *mig* (for example, *mig_ddr2_controller*). Whereas for Virtex-5 FPGA designs, the top file (*<top_module>*) name is the same as *<Component Name>* entered in the GUI; all other RTL file names are prepended with the memory interface name. For example, for a Virtex-5 FPGA DDR2 SDRAM design with a component name of *mig* that is entered in the GUI, *<design_top>* file name becomes *mig.v* or *mig.vhd*, based on the HDL type selected. All other RTL file names are prepended with *ddr2_* (such as, *ddr2_ctrl*).

Note: *<Component Name>* does not accept special characters. Only alphanumeric characters can be used to specify a component name. The component name should always start with an alphabetic character, but can end with an alphanumeric character. If the *<Component Name>* entered in the GUI matches with any of the design file names, a pop-up message appears asking the user to change the *<Component Name>* to proceed. If the *<Component Name>* entered in the GUI matches with the already existing *<Component Name>* in the project path, MIG prompts the user to confirm whether to overwrite the files. Upon clicking **Yes**, MIG overwrites only the duplicate files.

For multicontroller applications, the number of controllers should be selected at the **Number of Controllers** spin box. More than one controller can be selected for DDR2 SDRAM direct-clocking interface for Virtex-4 FPGA designs and for DDR2 SDRAM and QDRII SRAM designs in Virtex-5 FPGA designs. If more than one controller is selected, MIG limits the design generation to DDR2 SDRAM for Virtex-4 FPGA designs, and MIG limits the design generation to DDR2 SDRAM and QDRII SRAM for Virtex-5 FPGA designs. Select the appropriate number (1-8) in the pull-down menu. The **Number of Controllers** selection is enabled only for Virtex-5 and Virtex-4 FPGA families.

Note: The Create Design option can use a multiple number of controllers. For the Create Design for Xilinx Reference Boards, Verify UCF and Update Design and UCF options, the number of controllers is limited to one.

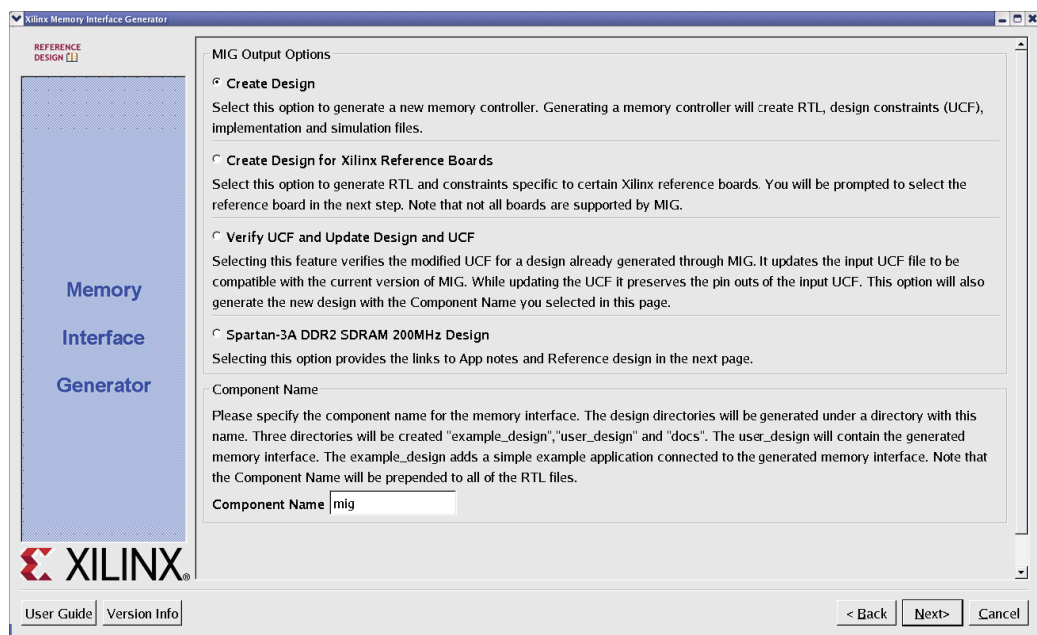
Click **Back** to return to previous page. Click **Cancel** to quit from the tool. Click **Next** to continue. The next page display depends upon the options selected in the current page.



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Figure 1-2: MIG Output Options / Component Name / Number of Controllers

The Spartan-3A DDR2 SDRAM 200 MHz Design option appears only for Spartan-3A FPGA designs (see [Figure 1-3](#)).



UG086_c1_55_030510

Figure 1-3: MIG Output Options Page of Spartan-3A FPGA Design

Create Design

Using the Create Design option, designs can be generated that are supported for that FPGA family. For example, the Virtex-4 FPGA family supports DDR2 SDRAM, DDR

SDRAM, QDRII SRAM, DDRII SRAM, and RDRAM II. Here is the flow for creating a design:

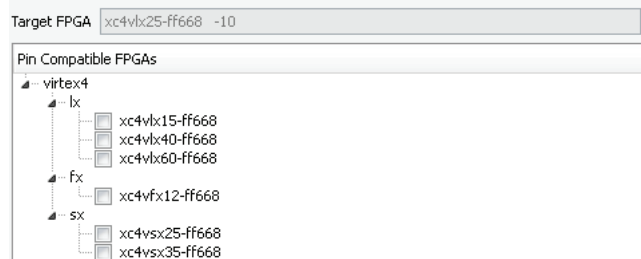
1. [Pin Compatible FPGAs](#)
2. [Memory Selection](#)
3. [Controller Options](#)
4. [Memory Options](#)
5. [FPGA Options](#)
6. [Extended FPGA Options](#)
7. [Reserve Pins](#)
8. [Bank Selection](#)
9. [Summary](#)
10. [Memory Model License](#)
11. [PCB Information](#)
12. [Design Notes](#)

All the options are described in this section.

Pin Compatible FPGAs

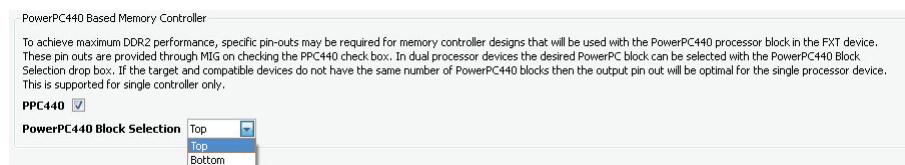
FPGAs in the selected family with the same package are listed here. If the generated pinout from MIG needs to be reusable with any of these other FPGAs, use this option to select the FPGAs with which the pinout has to be compatible. MIG supports Power PC440 compatible pinout for Virtex-5 FXT devices only for DDR2 SDRAM designs.

Note: The SerDes design is only supported for FPGAs with phase-matched clock drivers (PMCDs). If the target FPGA or the selected compatible FPGA has no PMCD, the capture method for DDR2 SDRAM is restricted to direct clocking.



UG086_c1_06_021109

Figure 1-4: Pin Compatible FPGAs



UG086_c1_66_072008

Figure 1-5: PPC440 Selection

Select any number of compatible FPGAs out of the listed ones. Only the common pins between target and selected FPGAs are used by MIG. The name in the text box signifies the

Target FPGA selected. When a Virtex-5 FXT device is selected as either compatible or target, the PPC440 checkbox is enabled. The PPC440 checkbox is enabled only when the Number of Controllers is selected as 1 in the MIG Output Options page. If the Number of Controllers is more than 1, then the PPC440 checkbox is disabled and masked, and user can no longer select this option. Click **Next** to continue. The Memory Selection is displayed.

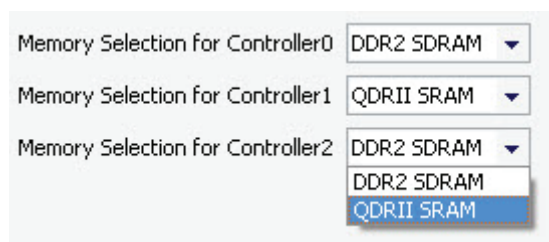
Memory Selection

This page displays all memory types that are supported by the selected FPGA family. An example is shown in Figure 1-6 for Virtex-4 FPGA designs and in Figure 1-7 for Virtex-5 FPGA designs. In Virtex-5 FPGA designs, the user can select the combination of both DDR2 SDRAM and QDRII SRAM interfaces for a multicontroller design.



UG086_c1_07_072008

Figure 1-6: Memory Selection for Virtex-4 FPGA Designs



UG086_c1_56_072008

Figure 1-7: Memory Selection for Virtex-5 FPGA Designs

For Virtex-5 FPGA designs, only the DDR2 SDRAM controller is shown when the PPC440 checkbox is enabled in the Pin Compatible FPGAs page. Select the appropriate option, and then click **Next** to continue. The Controller Options window is displayed.

Controller Options

This page shows the various controller options that can be selected. If the design has multiple controllers, this page is repeated for each of the controllers. The page is partitioned into a maximum of nine sections. The number of partitions depends on the type of selected memory.

- **Capture Method.** This feature deals with the data capture method. The DDR2 SDRAM controller for Virtex-4 devices supports two types of capture method. For other designs, the capture method is displayed, but it cannot be changed.

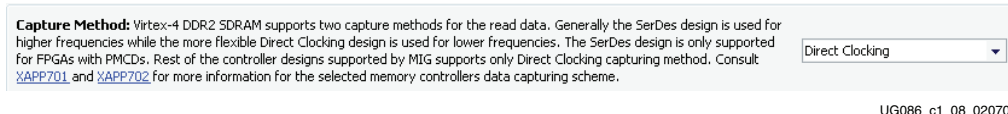


Figure 1-8: Capture Method

Click the pull-down menu button and select an option. Certain other options such as frequency and ECC are restricted based on this selection.

- **Frequency.** This feature indicates the desired frequency for all the controllers. This frequency block is limited by factors such as the selected FPGA, device speed grade, and clocking type.

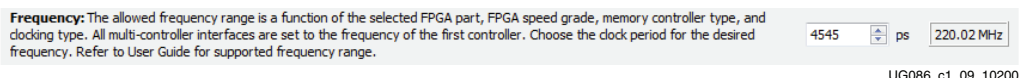


Figure 1-9: Frequency

Vary the clock period as required. Either use the spin box or enter a valid value through the keyboard. Values entered are restricted based on the minimum and maximum clock periods supported. The maximum frequency of deep designs is 150 MHz (6,666 ps).

Note: For Virtex-4 FPGA multicontroller designs, the frequency selected for the first controller is used for all other controllers. For Virtex-5 FPGA multicontroller and multiple-interface designs, every controller can have a different frequency. The number of controllers that can have different frequencies is limited by the number of PLLs available in the selected FPGA. Memory parts and data width are restricted based on the frequency selection.

- **Memory Type.** For DDR2 SDRAM, MIG categorizes different memory components and modules available into components, UDIMMs, SODIMMs, and RDIMMs. This can vary according to the memory selected. Virtex-5 FPGA DDR2 SDRAM controller supports deep designs only for dual-rank DIMMs.

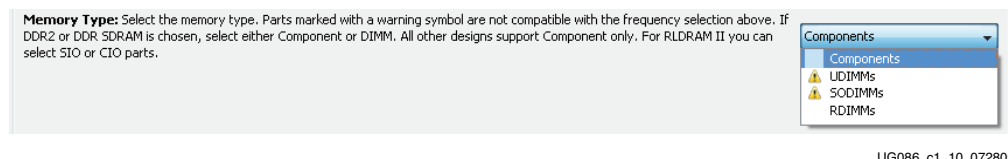
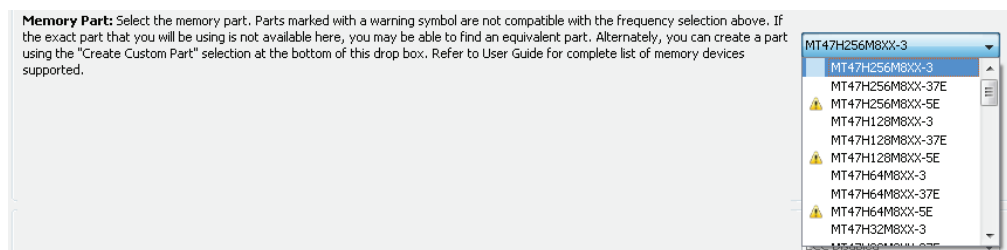


Figure 1-10: Memory Type

Click the pull-down menu combo box and select the memory type. Memory type options marked with a warning symbol are not compatible with the selected frequency.

- **Memory Part.** This feature helps the selection of a memory part for the design. Selection can be made from an existing list, or a new part can be created.



UG086_c1_11_072809

Figure 1-11: Memory Part

Select the appropriate memory part from the list. Select the larger memory parts to get all address lines in UCF. If the required part or its equivalent is unavailable, a new memory part can be created. Parts marked with a warning symbol are not compatible with the selected frequency. To create a custom part, select the Create Custom Part from the drop down combo box. A new window appears as shown in [Figure 1-12](#).

The window called Create Custom Part includes all the details of the memory component selected in Select Base Part. Enter the appropriate memory part name in the text box. Select the suitable base part from the Select base part list. Edit the Value column as needed. Select the suitable values from the Row, Column, and Bank options as per the requirements. After editing the required fields, click the **Save** button. The new part can be saved with the selected name. This new part is added in the Memory Parts list as shown in [Figure 1-13](#) and saved into the database for reuse and to produce the design.

Note: The rank and speed grade of the Create Custom Part is the same as the base part selected in the GUI. For example, if the base part selected in the GUI is dual-rank, the new part created is also a dual-rank part.

Create Custom Part

Custom Memory Part

This option creates a new memory part. Note that the new part will be a modification of the "Base Part" you select below. The timing parameters and the density can be changed.

Select Base Part: MT47H256M8XX-3

Enter New Memory Part Name:

Change the required Timing Parameters. "Value" is the only field that can be edited.

Parameter	Value	Range	Units	Descriptions
tdha	300	175-400	ps	DQ and DM input hold time relative to DQS ...
tdhb	175	25-275	ps	DQ and DM input hold time relative to DQS ...
trfc	197.5	75-327.5	ns	Refresh to Active or Refresh to Refresh
twtr	7.5	7.5-10	ns	Read following a Write to the same device
tis	400	200-600	ps	Address and control input setup time
twr	15	15-15	ns	Write recovery time
tac	450	400-600	ps	DQ output access time from CK/CK#
tras	40	40-45	ns	Active to Precharge command
tjit	125	100-125	ps	Clock Jitter
trtp	7.5	7.5-7.5	ns	Internal Read to Precharge command delay

Row Address: 15

Column Address: 10

Bank Address: 3

Buttons: Help, Save, Delete, Cancel

UG086_c1_12_072809

Figure 1-12: Create Custom Part

Memory Part: Select the memory part. Parts marked with a warning symbol are not compatible with the frequency selection above. If the exact part that you will be using is not available here, you may be able to find an equivalent part. Alternately, you can create a part using the "Create Custom Part" selection at the bottom of this drop box. Refer to User Guide for complete list of memory devices supported.

cust_part_mig

UG086_c1_13_072809

Figure 1-13: Memory Part

Note: In order to use the MIG-generated design UCF for different densities of the same memory type, select the highest memory part from Memory Selection page. For different density parts, only the number of address bits differ. Hence, if a design is generated selecting the highest density memory part, the same UCF can be used for the lower density memory part of the same memory type. For example, if a 128 x 16 DDR2 SDRAM design is generated, its UCF can be used for 64 x 16 DDR2 SDRAM design by connecting the most-significant address bit to ground. This scenario works only if the different density memory parts have the same design parameters (such as data width and other memory parameters).

- **Data Width.** The data width value can be selected here based on the memory type selected earlier. The list shows all supported data widths for the selected part. Choose one of them. These values are generally multiples of the individual device data

widths. In some cases, the width might not be an exact multiple. For example, though 16 bits is the default data width for x16 components, 8 bits is also a valid value.

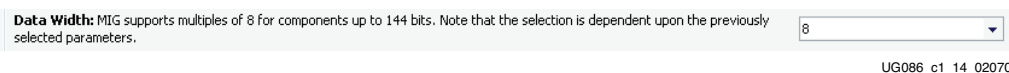


Figure 1-14: Data Width

- Memory Depth.** The DDR2 SDRAM Virtex-4 FPGA controller with the direct-clocking capture method supports a memory depth of one to four. DDR2 SDRAM Virtex-5 FPGA controller supports a memory depth of two only for dual-rank DIMMs. The maximum frequency supported for deep designs is less than or equal to 150 MHz. For other designs, this option is unavailable.

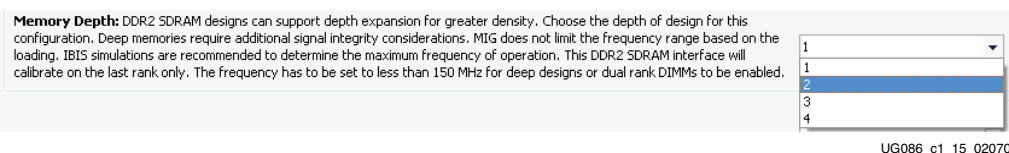


Figure 1-15: Memory Depth

Select the appropriate option from the Memory Depth option.

- ECC.** ECC stands for Error Correction Code. This feature enables the generation of ECC along with the code. This section is enabled based on selected data width. This option is available only for DDR2 SDRAM Virtex-4 and Virtex-5 FPGA designs.



Figure 1-16: ECC (a)

Note that ECC selection is enabled only when the appropriate data width is selected. DDR2 SDRAM Virtex-4 FPGA design supports three modes: ECC Disabled, Unpipeline Mode, and Pipeline Mode, as shown in Figure 1-16. Select the appropriate mode. The Pipeline mode improves frequency performance at the cost of an extra pipeline stage.



Figure 1-17: ECC (b)

For other Virtex-4 FPGA designs, this window is disabled as shown in Figure 1-17. For Virtex-5 FPGA DDR2 SDRAM designs, the two options are ECC Enabled and ECC Disabled.

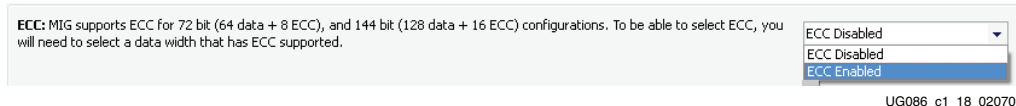


Figure 1-18: ECC (c)

Figure 1-18 shows the ECC option section for the Virtex-5 FPGA design GUI. For Virtex-5 devices, ECC is supported for 72-bit or 144-bit DDR2 SDRAM designs.

- **Data Mask.** When this Data Mask checkbox is marked, the data mask pins are allocated. When this Data Mask checkbox is not checked, the data mask pins are not allocated, which increases the pin efficiency. This option is disabled and cannot be changed for memory parts that do not support data masks. Similarly, this option is disabled for ECC enabled designs. This option is available only for DDR2 and DDR SDRAMs.

Data Mask: You will be able to enable/disable the generation of Data Mask (DM) pins using this check box. You will be able to change this option only if the memory part you have selected has DM pins. Uncheck this box to not use data masks and save FPGA I/Os that are used for DM signals. ☒

UG086_c1_43_021009

Figure 1-19: Data Mask

Select the option as per the requirement.

- **Clock Capable I/O.** Checking the Clock Capable I/O box makes use of the CC pins available in Virtex-4 FPGAs for strobes or read clocks. This option is enabled and cannot be changed for DDR2 SDRAM SerDes designs, but is editable for other designs.

Clock Capable I/O: Select clock capable I/Os to enable compatibility between the two Virtex-4 capture techniques, Direct Clocking and SerDes. If only Direct Clocking will be used, this can be unselected for greater pin efficiency. ☒

UG086_c1_19_021009

Figure 1-20: Clock Capable I/O

Select the option as per the requirement.

- **Write Pipe Stages.** The Write Pipe Stages is supported only for Spartan FPGA designs. This option allows users to implement the write data pipelines in the user interface.

Write Pipe Stages: MIG supports 0 to 4 pipelines for write data. The default is 4 pipelines. When the user selects 0 to 3 pipelines, the remaining pipe stages are included in the user interface. For example if the user selects 0 pipelines, write data should be passed through a 4 stage pipeline in the user interface.

UG086_c1_57_021009

Figure 1-21: Write Pipe Stages

- **Memory Details.** This section displays details about the selected memory. For DIMMs, x4/x8/x16 indicates the memory width of the base device.

Memory Details: 2Gb, x8, row:15, col:10, bank:3, data bits per strobe:8, with data mask, single rank

UG086_c1_20_021009

Figure 1-22: Memory Details

The memory details change based on the selected Memory part.

Click **Next** to continue. The Memory Options window is displayed for RLDRAM II, DDR, and DDR2 SDRAM devices. For other memories, the next window displayed is FPGA Options.

Memory Options

This feature allows selection of various memory options as supported by the controller type.

Memory Options for Controller 0 - DDR2 SDRAM

Choose the Memory Options settings for the memory device. Settings are restricted to those supported by the controller. Consult the memory vendor data sheet for more information.

Burst Length
Determines the maximum number of column locations that can be accessed for a given READ or WRITE command. 4(010)

Burst Type
The ordering of accesses with in a burst is determined based on the burst length, the burst type and the starting column address. sequential(0)

CAS Latency
CL is the delay, in clock cycles, between the registration of a READ command and the availability of the first output data. CAS Latency is dependent on the frequency specified in the prior Controller Options page. 3(011)

Output Drive Strength
Selecting reduced strength will reduce all outputs to approximately 60 percent of the drive strength. Fullstrength(0)

RTT (nominal) - ODT
This feature allows to apply internal termination resistance of the memory module for signals DQ, DQS/DQS#, LDQS/LDQS#, UDQS/UDQS# and LDM/UDM. This improves the signal integrity of the memory channel. RTT Disabled(00)

Additive Latency (AL)
This feature allows the READ/WRITE command to be issued prior to tRCD (minimum) by delaying the internal command to the DDR2 SDRAM by AL clocks. 0(000)

DQS# Enable
Crosstalk and simultaneous switching output impact on the strobe output driver can be reduced with this option ON. When Enabled DQS is differential and when disabled DQS is single-ended. Enable(0)

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Figure 1-23: Memory Options for Virtex-4 FPGA DDR2 Direct Clocking Design

Memory Options for Controller 0 - DDR2 SDRAM

Choose the Memory Options settings for the memory device. Settings are restricted to those supported by the controller. Consult the memory vendor data sheet for more information.

Burst Length
Determines the maximum number of column locations that can be accessed for a given READ or WRITE command. 4(010)

Burst Type
The ordering of accesses with in a burst is determined based on the burst length, the burst type and the starting column address. sequential(0)

CAS Latency
CL is the delay, in clock cycles, between the registration of a READ command and the availability of the first output data. CAS Latency is dependent on the frequency specified in the prior Controller Options page. 4(100)

Output Drive Strength
Selecting reduced strength will reduce all outputs to approximately 60 percent of the drive strength. Fullstrength(0)

RTT (nominal) - ODT
This feature allows to apply internal termination resistance of the memory module for signals DQ, DQS/DQS#, LDQS/LDQS#, UDQS/UDQS# and LDM/UDM. This improves the signal integrity of the memory channel. The Virtex-5 DDR2 interface requires that if parallel termination is used at the memory I/Os, then it must be ODT rather than external termination resistor(s). This is a requirement of the read capture scheme in use. 75ohms(01)

Additive Latency (AL)
This feature allows the READ/WRITE command to be issued prior to tRCD (minimum) by delaying the internal command to the DDR2 SDRAM by AL clocks. 0(000)

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Figure 1-24: Memory Options for Virtex-5 FPGA DDR2 Design

These values are programmed into memory during initialization.

Note: The memory options listed in this GUI are restricted by the frequency and the memory part selected on the prior page. The memory option value will not be shown in this page if it cannot be changed. For example, a CAS latency value of 5 is only supported in a frequency range of 267 MHz

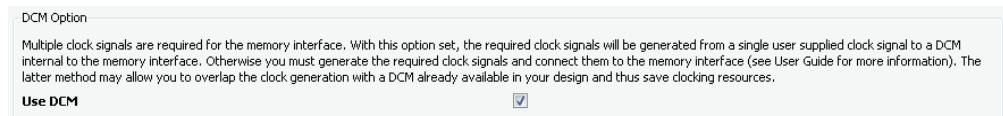
to 333 MHz. Thus, the CAS latency value is not shown in a frequency range of 267 MHz to 333 MHz, and the value selected for CAS latency is 5.

Click **Next** to continue. The FPGA Options window is displayed.

FPGA Options

This feature is partitioned into three or four sections based on the FPGA family selected: DCM, DCI, SSTL Class, and Debug Signals Control. For Virtex-5 FPGA designs, the DCI option appears in the Extended FPGA Options page.

- **DCM.** DCM allows design generation with or without a DCM in the design. This option appears only for Virtex-4 and Spartan FPGA designs. When a design is generated with DCM, all the required clocks for the design are generated out of the DCM using the system clock inputs. When the DCM is disabled, the user must implement a user clocking scheme to generate the required design clocks. Refer to the *Clocking Scheme* section of a design for details about the clocks that the user must generate when the DCM is not instantiated in the design.



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Figure 1-25: DCM Option

- **PLL.** PLL allows design generation with or without a phase-locked loop (PLL) in the design. This option appears only for Virtex-5 FPGA designs. In MIG 3.0 and later, DCM is replaced with PLL for all Virtex-5 FPGA designs. When a design is generated with PLL, all the required clocks for the design are generated out of the PLL using the system clock inputs. When the PLL is disabled, the user must implement a user clocking scheme to generate the required design clocks. Refer to the *Clocking Scheme* section of a design for details about the clocks that the user must generate when the PLL is not instantiated in the design.



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Figure 1-26: PLL Option

- **DCI.** This feature indicates whether the Digitally Controlled Impedance is Disabled or Enabled. This option appears only for Virtex-4 FPGA designs. DCI can be enabled or disabled for input, bidirectional, or output pins. This option can change according to the memory selected. They are listed as follows:

DDR2 SDRAM — DCI for DQ/DQS and DCI for Address/Control

DDR SDRAM — DCI for DQ/DQS and DCI for Address/Control

RLDRAM II — DCI for Data, Read Clocks, and Data Valid Signals and DCI for Address/Control

QDRII SRAM — DCI for Data and Read Clocks

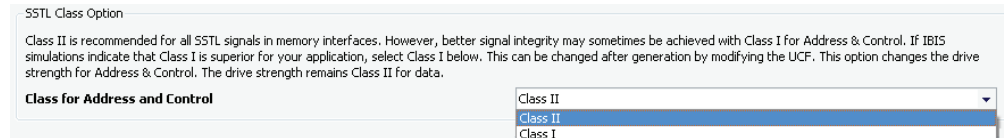
DDRII SRAM — DCI for Data and Read Clocks



UG086_c1_24_021009

Figure 1-27: DCI Options (a)

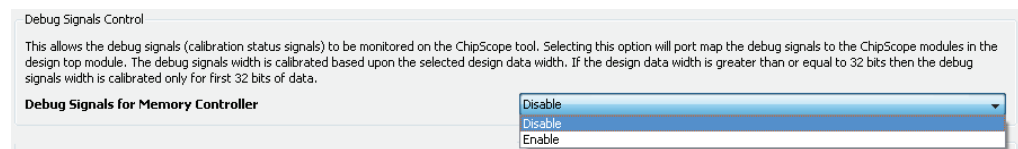
- **SSTL Class Option.** SSTL Class Option determines the I/O standard drive strength in the UCF of DDR and DDR2 SDRAM. These I/O standards can be changed based on their application.



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Figure 1-28: SSTL Class Options

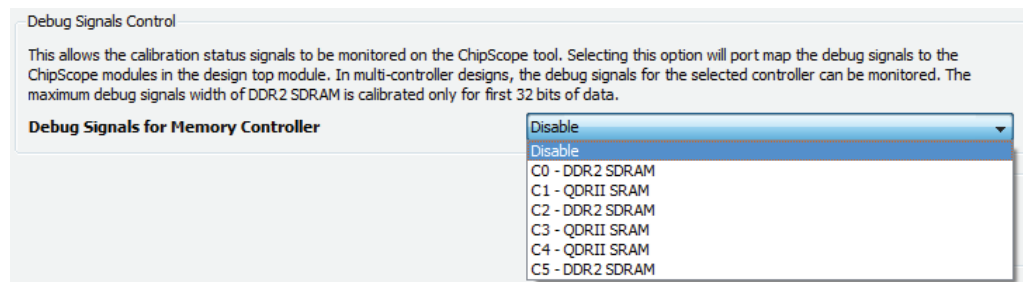
- **Debug Signals Control.** Selecting this option enables the debug signals to be port-mapped to the ChipScope™ analyzer modules in the design top module. This helps in monitoring the debug signals on the ChipScope tool. When the generated design is run in batch mode using `ise_flow.bat` in the design's par folder, the CORE Generator system is called to generate ChipScope analyzer modules (that is, EDIF files are generated). Deselecting this option leaves the debug signals unconnected in the design top module, with no ChipScope analyzer modules instantiated in the design top module or generated by the CORE Generator system. In Virtex-4 FPGA multicontroller designs, the Debug port is supported for the first controller.



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Figure 1-29: Debug Signals Control

In Virtex-5 FPGA multicontroller and multiple-interface designs, the Debug port is supported for the selected controller in the GUI.



UG086_c1_59_102009

Figure 1-30: Debug Signals in Virtex-5 FPGA Multiple Interface Designs

- System Clock.** This option enables users to select the system clock type for the design to be generated (Figure 1-31). This option is applied on both system clock as well as IDELAYCTRL clock (200 MHz clock). When Differential is selected, only differential clock pairs appear in the design top RTL file as well as in the design UCF. When Single-Ended is selected, only single-ended clock input pins appear in the design top RTL file as well as in the design UCF. This option is grayed out when PLL/DCM option is deselected and the clock type remains single-ended (Figure 1-32).

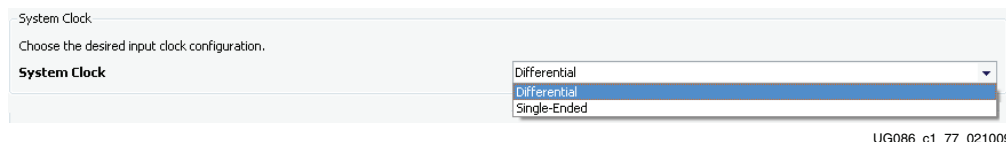


Figure 1-31: System Clock Type Selection when PLL/DCM Option is Selected

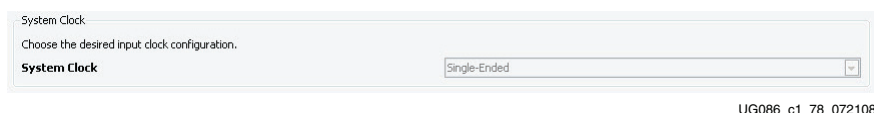


Figure 1-32: System Clock Type Selection when PLL/DCM Option is Deselected

- High Performance Mode.** This is the IDELAY element High Performance Mode selection type for Virtex-5 FPGA designs (Figure 1-33). This option sets the IDELAY in HIGH power or LOW power mode. This option is enabled for selection only when the design frequency is less than the false frequency mode. When the frequency set in the Controller options page is more than the specified false frequency range, then the High Performance Mode option is not available for selection and is grayed out with the default value set to TRUE (Figure 1-34).

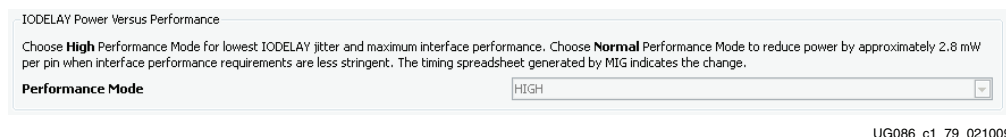


Figure 1-33: High Performance Mode Selection Type for Virtex-5 FPGA Interface Single Controller Designs

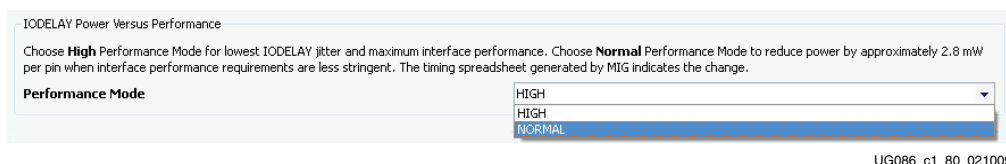
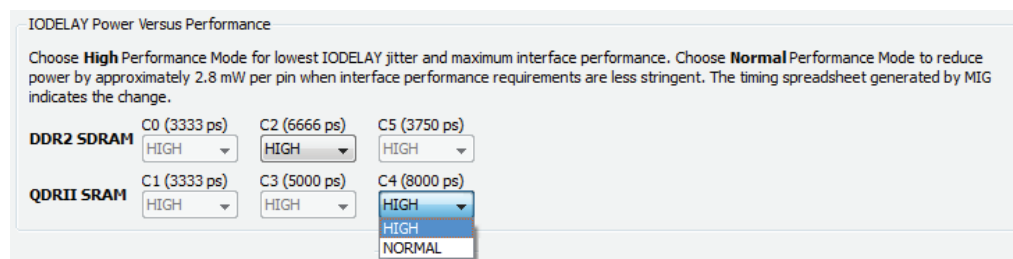


Figure 1-34: High Performance Mode Default: Design Freq > False Freq Range

In Virtex-5 FPGA multicontroller and multiple-interface designs, IDELAY performance mode can be selected for each controller independently (Figure 1-35).

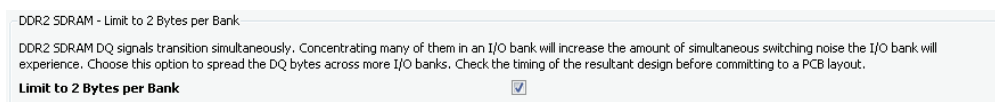


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Figure 1-35: High Performance Mode Selection Type for Virtex-5 FPGA Multiple Interface Designs

Refer to [Appendix E, “Debug Port”](#) for more information on False Mode frequency ranges for all Virtex-5 FPGA memory interface designs.

- **Limit to 2 Bytes per Bank.** Enabling this option allows only two bytes of data into a single bank ([Figure 1-36](#)). This option is available only for Virtex-5 FPGA DDR2 SDRAM memory interface designs.



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Figure 1-36: Limit to 2 Bytes per Bank in Virtex-5 FPGA DDR2 SDRAM Interface Designs

Click **Next** to continue. For Virtex-5 FPGA designs, the Extended FPGA Options window is displayed, and for other designs, the Reserve Pins window is displayed.

Extended FPGA Options

This feature is partitioned into three sections: DCI, DCI Cascading Information, and SSTL Class. This page will appear for Virtex-5 FPGA designs only.

- **DCI.** This feature indicates whether the Digitally Controlled Impedance is Disabled or Enabled. DCI can be enabled or disabled for input, bidirectional, or output pins. This option can change according to the memory selected. They are listed as follows:

DDR2 SDRAM — DCI for DQ/DQS and DCI for Address/Control

DDR SDRAM — DCI for DQ/DQS and DCI for Address/Control

QDR II SRAM — DCI for Data and Read Clocks

DDR II SRAM — DCI for Data and Read Clocks

The DCI selection window is shown in [Figure 1-27](#).

For multiple interfaces in Virtex-5 FPGA designs, DCI can be selected for each interface separately. The Extended FPGA Options page shows the DCI selections for each interface separately ([Figure 1-37](#)).

DDR2 SDRAM

Digitally Controlled Impedance (DCI)

Select the DCI (Digitally Controlled Impedance) I/O standard to enable the FPGA internal termination for DQ, DQS, address and control signals. Consult the User Guide for more information and use IBIS simulation to determine the best termination strategy. This can also be changed after generation by altering the UCF manually.

DCI for DQ/DQS ☒ **DCI for Address/Control** ☐

SSTL Class Option

Class II is recommended for all SSTL signals in memory interfaces. However, better signal integrity may sometimes be achieved with Class I for Address & Control. If IBIS simulations indicate that Class I is superior for your application, select Class I below. This can be changed after generation by modifying the UCF. This option changes the drive strength for Address & Control. The drive strength remains Class II for data.

Class for Address and Control Class II

QDR II SRAM

Digitally Controlled Impedance (DCI)

Select the DCI (Digitally Controlled Impedance) I/O standard to have the FPGA internally terminate the signals from the QDR II memory (read path). Consult the User Guide for more information and use IBIS simulation to determine the best termination strategy.

DCI for Data and Read Clocks ☒

DCI Cascading Information

Select the DCI Cascade for cascading the DCI reference pins in the banks to obtain pin efficiency. Master Banks must be selected in the Bank Selection page. Refer to the MIG User Guide to know the rules for selecting the Master-Slave banks. For 18-bit data width designs, DCI Cascade is not applicable. For X36 component designs, DCI Cascade is enabled when DCI is selected.

DCI Cascade Selection C1 ☒

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Figure 1-37: DCI Option for Multiple Interfaces Selected in Virtex-5 FPGA Designs

If DCI is enabled, the pins are characterized by the DCI I/O standards.

- **DCI Cascading Information.** This option appears only for QDR II Virtex-5 FPGA designs. This option is necessary for generating 36-bit component designs with DCI support.

QDR II SRAM

Digitally Controlled Impedance (DCI)

Select the DCI (Digitally Controlled Impedance) I/O standard to have the FPGA internally terminate the signals from the QDR II memory (read path). Consult the User Guide for more information and use IBIS simulation to determine the best termination strategy.

DCI for Data and Read Clocks ☒

DCI Cascading Information

Select the DCI Cascade for cascading the DCI reference pins in the banks to obtain pin efficiency. Master Banks must be selected in the Bank Selection page. Refer to the MIG User Guide to know the rules for selecting the Master-Slave banks. For 18-bit data width designs, DCI Cascade is not applicable. For X36 component designs, DCI Cascade is enabled when DCI is selected.

DCI Cascade Selection C0 ☒ C1 ☒

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Figure 1-38: DCI Cascading Information Option

Note: If the DCI Cascading Information option is checked, the Bank Selection window shows the Master Bank selection box. The user must not reserve VRN/VRP pins in the Reserve Pins window for the selected master banks.

- **SSTL Class Options.** SSTL Class Option determines the I/O standard drive strength in the UCF of DDR and DDR2 SDRAM. These I/O standards can be changed based on their application.

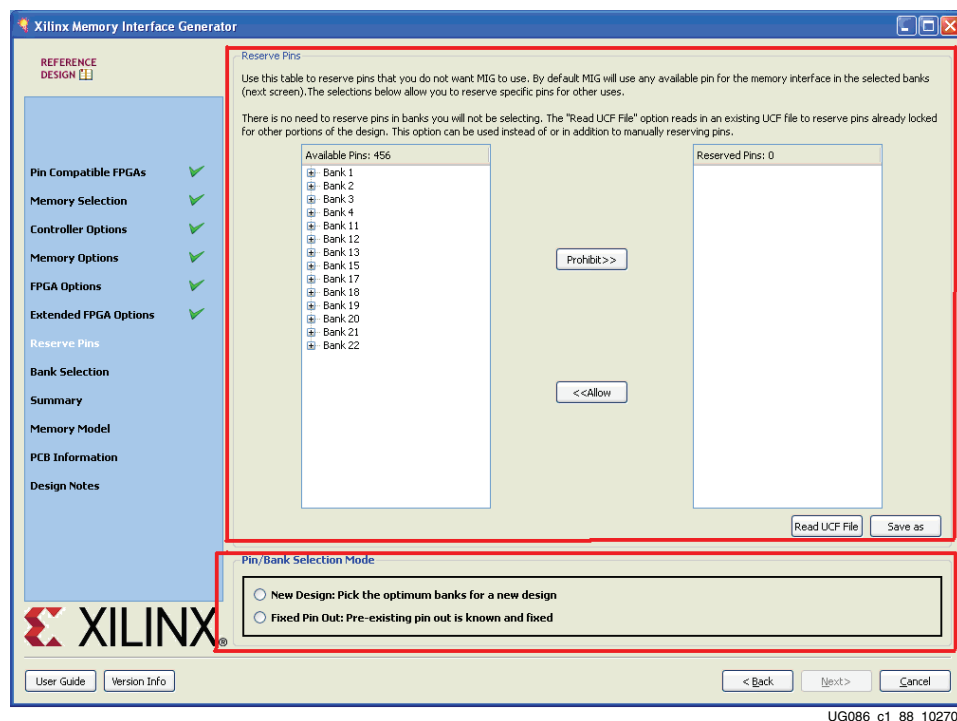
Click **Next** to continue. The Reserve Pins page is displayed.

This page is partitioned into two sections:

- Reserve Pins
- Pin/Bank Selection Mode

The Reserve Pins section allows the user to reserve the specific pins of the device. The Pin/Bank Selection Mode section lets the user select the Pin/Bank selection GUI mode, based on user requirements. By default, the **Next** button is disabled. This button is enabled

after the user chooses the Pin/Bank selection mode. The Pin Selection feature is only implemented for Virtex-5 FPGA devices in DDR and DDR2 SDRAMs, and QDR II SRAM.



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Figure 1-39: Reserve Pins Page

Reserve Pins

This feature allows specific pins to be reserved for other applications. After selecting suitable pins as necessary, the reserved pins are not used by the MIG tool while generating the pinout for that particular design.

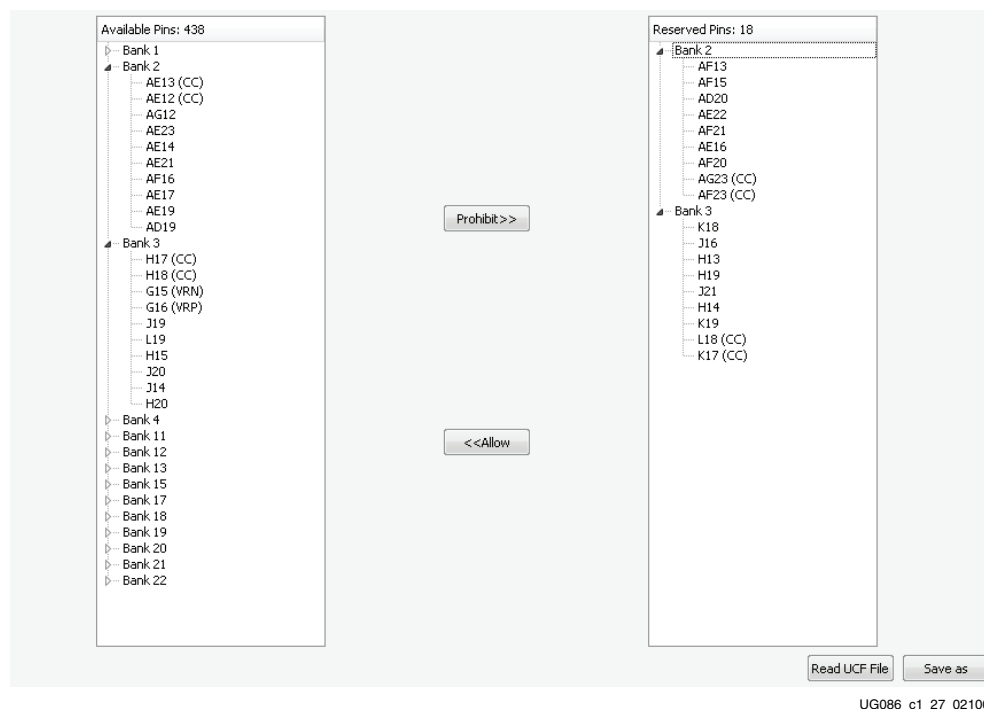


Figure 1-40: Reserve Pins Section

Select the pins from the Available Pins column, and click the **Prohibit** button. The particular pin is transferred to Reserve Pins column along with its bank information. This signifies that the selected pin has been reserved. To unreserve a reserved pin, click the appropriate pin that needs to be removed, and then click the **Allow** button. The number 408 in the Available Pins header signifies the number of pins available for pinout, whereas the number 16 in the Reserve Pins header signifies the number of pins selected to be reserved.

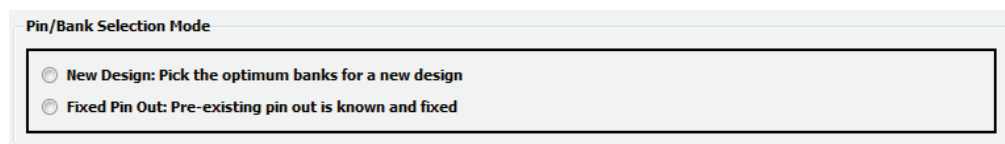
The reserved pins information can be saved in a user defined file using the **Save as** button. A browser window appears after clicking the **Save as** button. Set the file location here.

Use the **Read UCF File** button to read a reserve pins from a UCF. When the **Read UCF File** button is clicked, a new window pop ups. Select the UCF to be read. After reserving the pins, click **Next** to continue. The Bank Selection window is displayed.

Pin/Bank Selection Mode

This mode has two options based on whether or not a fixed board layout is available (Figure 1-41):

- **New Design:** In this option, the user picks the optimum banks for a new design. This option applies when the user does not already have a board. The pins for various signals can be automatically selected, based on the optimum bank selection.
- **Fixed Pin Out:** In this option, a preexisting pinout is known and fixed. This option applies when the user already has a board. In this case, signals have to be manually assigned to the pins.



Pin/Bank Selection Mode

☐ New Design: Pick the optimum banks for a new design
☐ Fixed Pin Out: Pre-existing pin out is known and fixed

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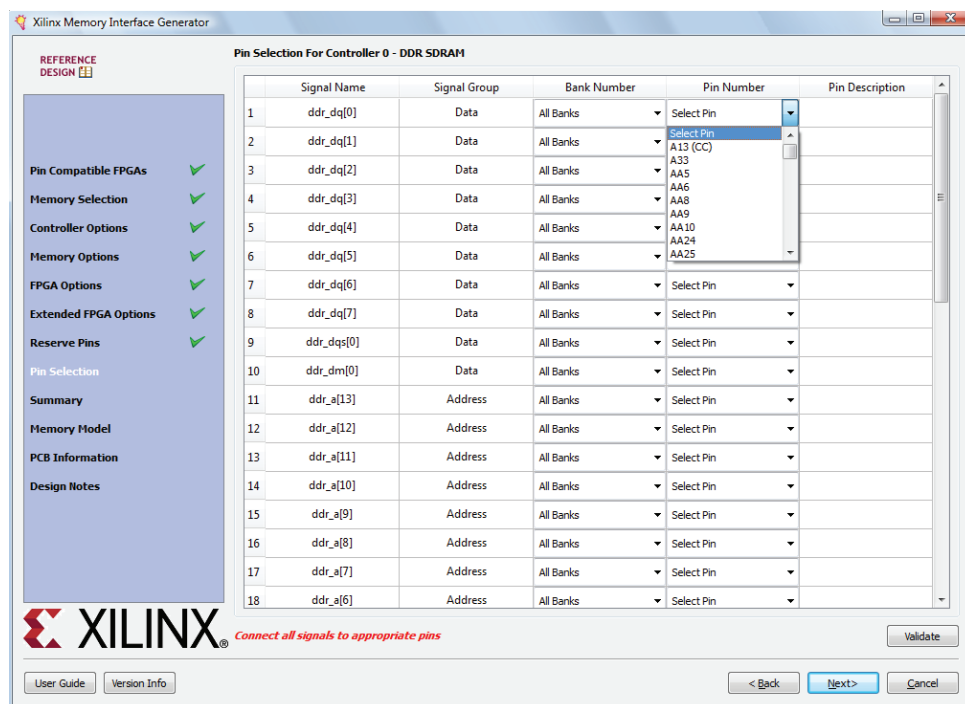
Figure 1-41: Pin/Bank Selection Mode

After selecting the appropriate option, click the **Next** button to continue. If the **Fixed Pin out: Pre-existing pin out is known and fixed** option is selected, the Pin Selection page is displayed ([“Pin Selection,”](#) page 53). If the **New Design: Pick the optimum banks for a new design** option is selected, the Bank Selection page is displayed ([“Bank Selection,”](#) page 54).

Pin Selection

This page allows for the selection of pins for the various signals on the memory interface. There are five columns in the pin selection table:

- Signal Name
- Signal Group
- Bank Number
- Pin Number
- Pin Name



Pin Selection For Controller 0 - DDR SDRAM

	Signal Name	Signal Group	Bank Number	Pin Number	Pin Description
1	ddr_dq[0]	Data	All Banks	Select Pin	
2	ddr_dq[1]	Data	All Banks	Select Pin	
3	ddr_dq[2]	Data	All Banks	A13 (CC)	
4	ddr_dq[3]	Data	All Banks	AA5	
5	ddr_dq[4]	Data	All Banks	AA6	
6	ddr_dq[5]	Data	All Banks	AA8	
7	ddr_dq[6]	Data	All Banks	AA9	
8	ddr_dq[7]	Data	All Banks	AA10	
9	ddr_dqs[0]	Data	All Banks	AA24	
10	ddr_dm[0]	Data	All Banks	AA25	
11	ddr_a[13]	Address	All Banks	Select Pin	
12	ddr_a[12]	Address	All Banks	Select Pin	
13	ddr_a[11]	Address	All Banks	Select Pin	
14	ddr_a[10]	Address	All Banks	Select Pin	
15	ddr_a[9]	Address	All Banks	Select Pin	
16	ddr_a[8]	Address	All Banks	Select Pin	
17	ddr_a[7]	Address	All Banks	Select Pin	
18	ddr_a[6]	Address	All Banks	Select Pin	

XILINX Connect all signals to appropriate pins

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Figure 1-42: Pin Selection Page

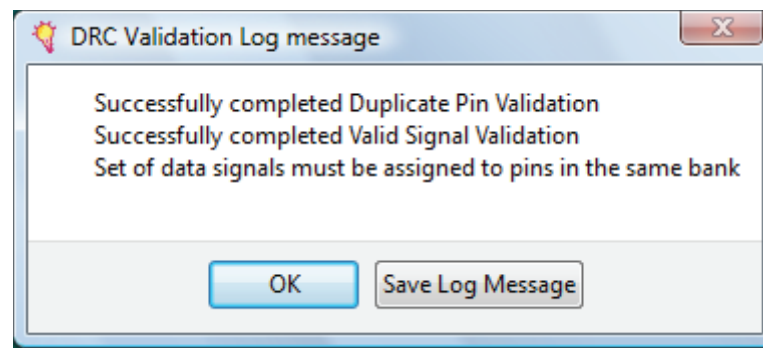
- **Signal Name.** This column displays all the required signals for the specific memory interface. The signal name cannot be edited or changed.

- **Signal Group.** This column displays the group name of the corresponding signal name. The signal name cannot be edited or changed.
- **Bank Number.** This column displays all the banks available in the FPGA. Each cell of this column contains a pull-down menu. The entries in the pull-down menu are the banks of the corresponding FPGA. Select the appropriate banks for specific memory signals. After the bank is selected in the bank number, the Pin Number pull-down menu is automatically populated with a list of pins from the corresponding bank.

Note: It is not mandatory to select a bank number. When the pin number is selected, the bank number pull-down menu is automatically updated with the corresponding bank number.

- **Pin Number.** This column displays all the pin numbers available in the FPGA. Each cell of this column contains a pull-down menu that lists all the pins in the FPGA. Select the appropriate pins for specific memory signals. After the pin number is selected in the Pin Number menu, the Bank Number menu automatically changes to the corresponding bank.
- **Pin Name.** This column displays the pin name (I/O type) of the user selected pin number. The pin name cannot be edited or changed.

Use the **Validate** button to verify the design rule of all the assigned pins to memory signals. After verifying the design rule, a DRC Validation Log message window is displayed with a list of success and failure messages. This window can be saved using the **Save Log Message** button.



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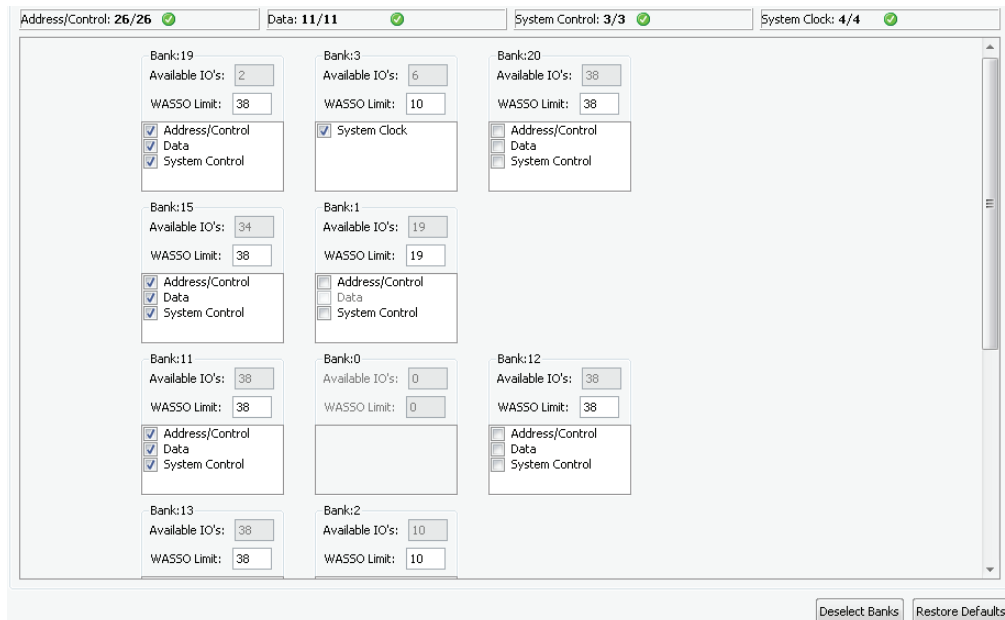
Figure 1-43: DRC Validation Log Message

After successfully assigning the memory interface signals to the appropriate pin, click the **Next** button to continue. If there are no errors, the Summary page is displayed ([“Summary,” page 75](#)).

Bank Selection

This feature allows selection of banks for the Memory interface. Banks can be selected for different groups of memory signals. The different groups are:

- Address and Control Signals
- Data Signals
- System Control Signals
- System Clock



Address/Control: 26/26 ✓ Data: 11/11 ✓ System Control: 3/3 ✓ System Clock: 4/4 ✓

Bank:19
Available IO's: 2
WASSO Limit: 38
☒ Address/Control
☒ Data
☒ System Control

Bank:15
Available IO's: 34
WASSO Limit: 38
☒ Address/Control
☒ Data
☒ System Control

Bank:11
Available IO's: 38
WASSO Limit: 38
☒ Address/Control
☒ Data
☒ System Control

Bank:13
Available IO's: 38
WASSO Limit: 38
☒ Address/Control
☒ Data
☒ System Control

Bank:3
Available IO's: 6
WASSO Limit: 10
☒ System Clock

Bank:1
Available IO's: 19
WASSO Limit: 19
☐ Address/Control
☐ Data
☐ System Control

Bank:0
Available IO's: 0
WASSO Limit: 0
☐ Address/Control
☐ Data
☐ System Control

Bank:2
Available IO's: 10
WASSO Limit: 10
☐ Address/Control
☐ Data
☐ System Control

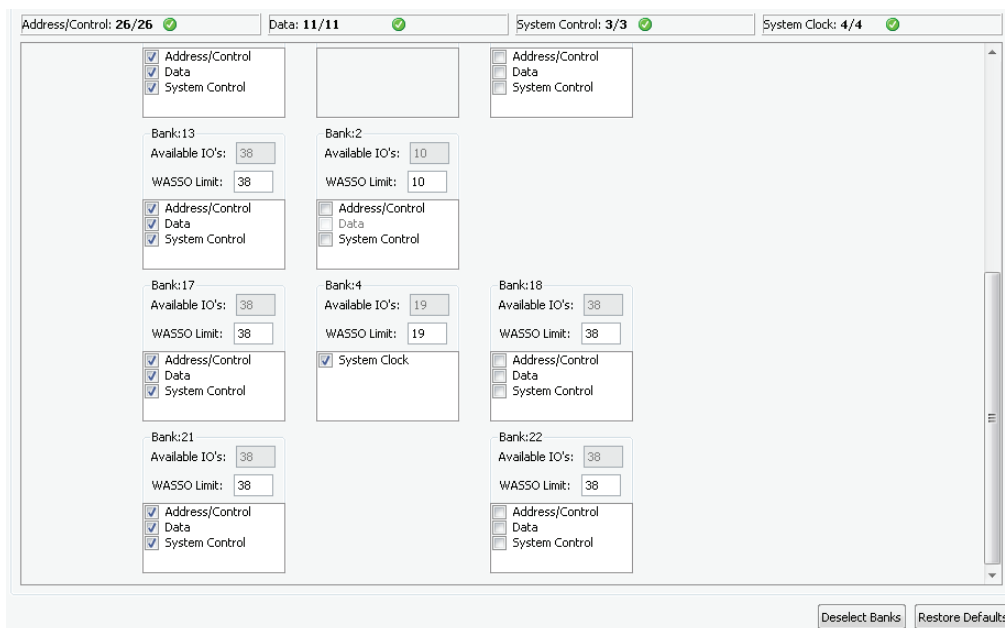
Bank:20
Available IO's: 38
WASSO Limit: 38
☐ Address/Control
☐ Data
☐ System Control

Bank:12
Available IO's: 38
WASSO Limit: 38
☐ Address/Control
☐ Data
☐ System Control

Deselect Banks Restore Defaults

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Figure 1-44: Bank Select (a)



Address/Control: 26/26 ✓ Data: 11/11 ✓ System Control: 3/3 ✓ System Clock: 4/4 ✓

☒ Address/Control
☒ Data
☒ System Control

Bank:13
Available IO's: 38
WASSO Limit: 38
☒ Address/Control
☒ Data
☒ System Control

Bank:17
Available IO's: 38
WASSO Limit: 38
☒ Address/Control
☒ Data
☒ System Control

Bank:21
Available IO's: 38
WASSO Limit: 38
☒ Address/Control
☒ Data
☒ System Control

Bank:2
Available IO's: 10
WASSO Limit: 10
☐ Address/Control
☐ Data
☐ System Control

Bank:4
Available IO's: 19
WASSO Limit: 19
☒ System Clock

Bank:18
Available IO's: 38
WASSO Limit: 38
☐ Address/Control
☐ Data
☐ System Control

Bank:22
Available IO's: 38
WASSO Limit: 38
☐ Address/Control
☐ Data
☐ System Control

Deselect Banks Restore Defaults

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Figure 1-45: Bank Select (b)

Select the appropriate bank and memory signals as required.

The WASSO limit in conjunction with the Reserve pins limits the number of available I/Os in a bank. For more information on the WASSO limit, refer [Appendix C, "WASSO Limit Implementation Guidelines."](#)

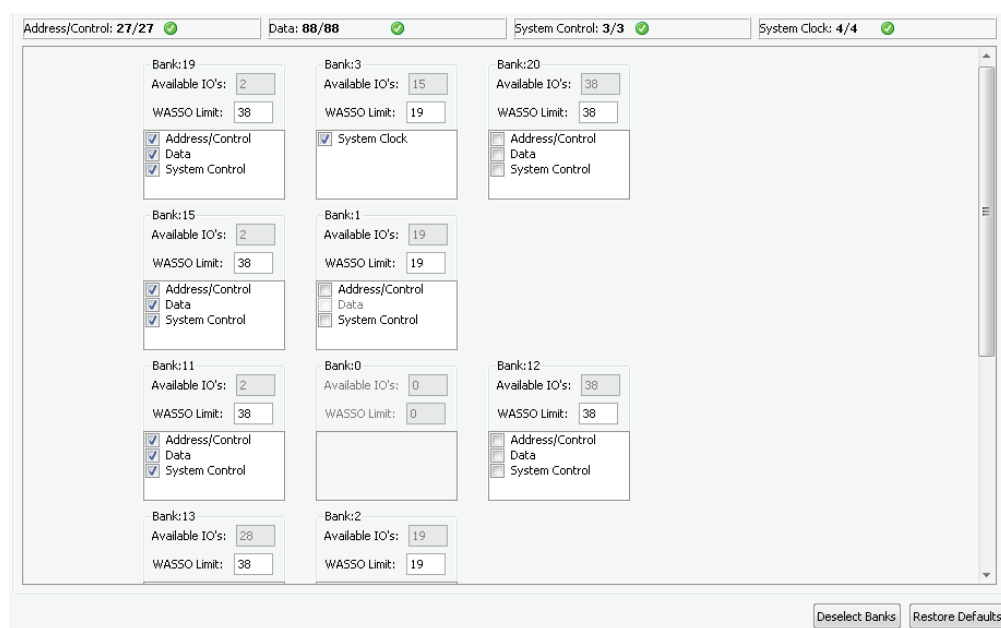
To unselect the banks that are selected, click the **Deselect Banks** button. To restore the defaults, click the **Restore Defaults** button.

In certain banks, global clock pins are not allowed for system clock. This is because system clock signals have different I/O standards as compared to those of any other signals in the design. In such banks, global clock pins are left unused.

- **Real-time pin allocation.** As the user selects the banks, pin allocation is done dynamically, and the number of pins required is updated for each group of signals.
 - The red circle with a cross mark at each group indicates that sufficient pins are not allocated, and additional pins are required for the selected configuration.
 - The green circle with a tick mark at each group indicates that sufficient pins are allocated for the selected configuration.
 - The denominator in each group indicates the total number of pins required for each group.

The user must select banks until the numerator equals the denominator. The user cannot move to the next page unless sufficient pins are allocated for each group.

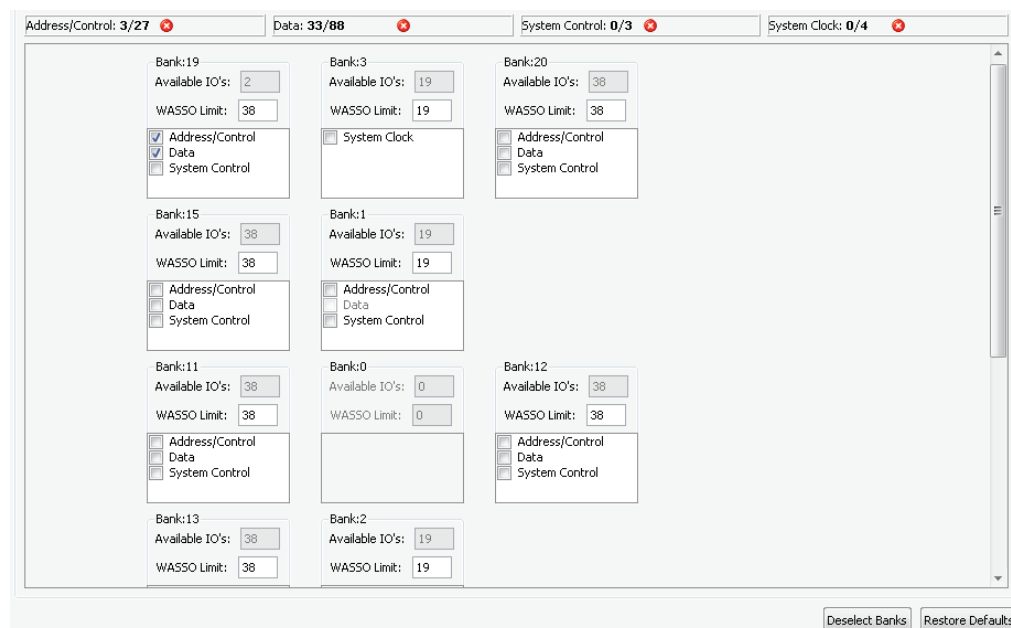
Figure 1-46 illustrates the conditions where sufficient banks are selected in order to successfully generate the design.



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Figure 1-46: Real-Time Pin Allocation: Sufficient Banks Selected

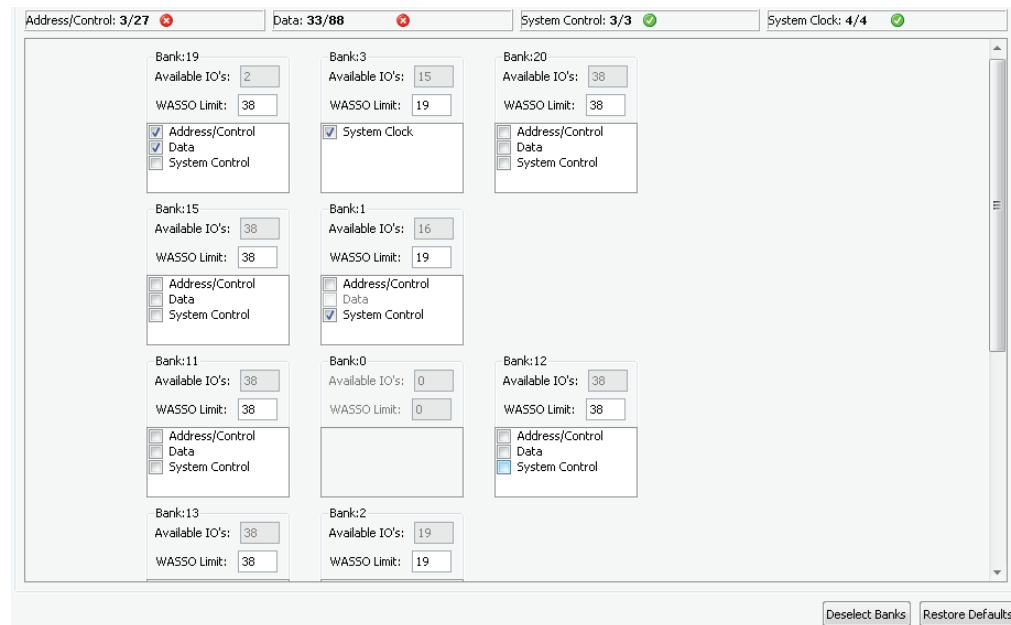
Figure 1-47 indicates when sufficient banks are *not* allocated for each signal group.



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Figure 1-47: Real-Time Pin Allocation: Sufficient Banks Not Selected

Figure 1-48 indicates sufficient pins are allocated for System Control and System Clock groups, but sufficient pins are *not* allocated for Data and Address groups.



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Figure 1-48: Real-Time Pin Allocation: Insufficient Pins for Data/Address Groups

- **Pin Allocation Priority.** MIG allocates the pins starting with exclusive data banks first, followed by data banks that combine with other groups.

Figure 1-49 indicates that data banks are selected in bank 11, bank 19, bank 20, and bank 12. In bank 11, bank 20 and bank 12, only data is selected; in bank 19, data, address, and system control are selected. Here, data is allocated first in bank 11, bank 20 and bank 12, and then in bank 19. This Pin Allocation Priority is applicable only for data group signals in Virtex-4 and Virtex-5 devices.

Note: Data group infers Data group pins in CIO designs and Data Read group pins in SIO designs.

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Figure 1-49: Pin Allocation Priority

- Master Bank selection.** This is applicable only for QDRII SRAM and DDRII SRAM Virtex-5 FPGA designs when the DCI Cascading Information option is selected. A Master bank should be selected in each column when a Data Read is selected in that particular column. *There is an exception for the middle column.* The middle column is divided into two parts: above zero bank and below zero bank. The middle column can have two Master banks, depending on where the Read Data banks are selected. If the Read Data bank is selected *either* above *or* below the Zero bank, only one Master Bank is required. If the Read Data banks are selected *both* above *and* below Zero bank, two Master banks are required.

Figure 1-50 shows that the Data Read is selected in both the columns and user needs to select the Master Banks in both the columns. Master bank selection box lists all the possible banks that can be selected as Master Bank. MIG does not show the Master Bank selection box for a column if that column does not have enough pins in the banks.

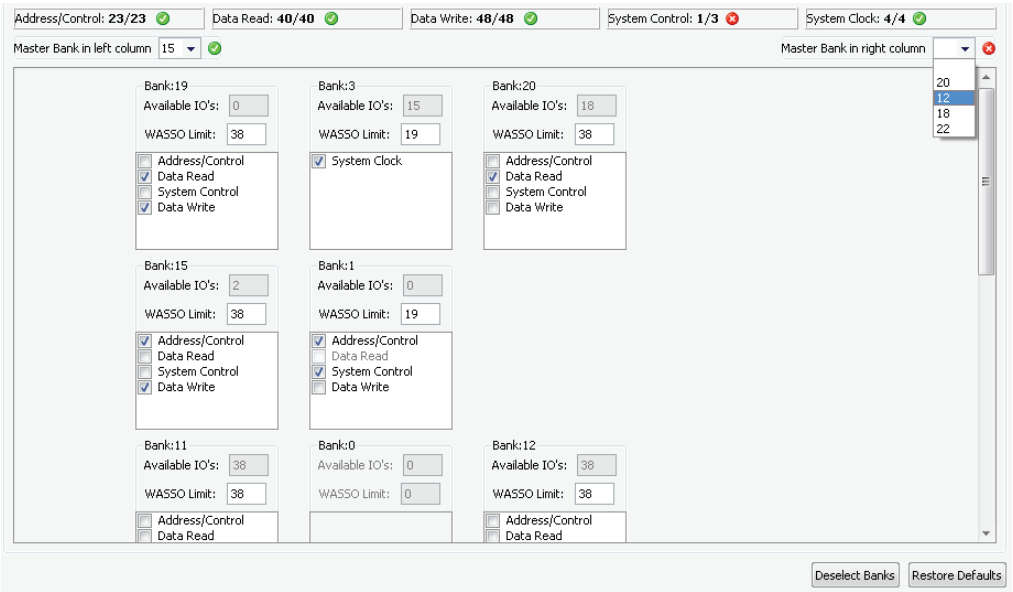


Figure 1-50: Master Bank Selection (a)

Figure 1-51 shows the Master Bank selection in the center column. It uses all the pins for Read Data from the center column.

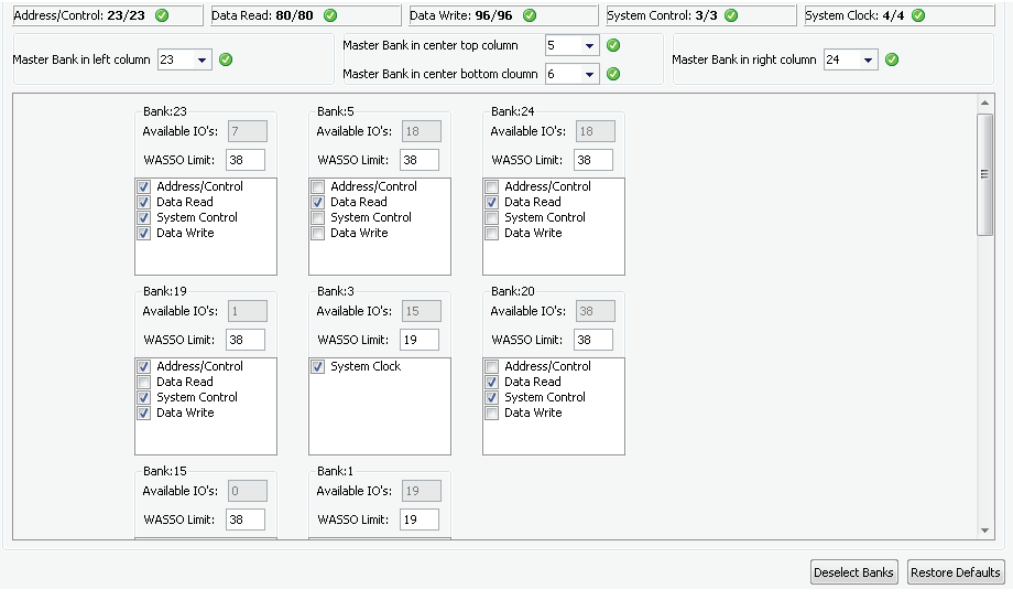


Figure 1-51: Master Bank Selection (b)

- Bank Selections for Multiple Memory Interfaces in Virtex-5 FPGA Designs.** For a multiple interface design, a particular group is allowed to select in a bank only for compatible I/O standards. For example (with the selected FPGA as XC5VLX220-FF1760), Controller 0 is DDR2 SDRAM (see Figure 1-52) and Controller 1 is QDRII SRAM (see Figure 1-53). In DDR2 SDRAM, bank 19 is selected for Data, bank 19 and bank 15 are selected for Address, and bank 1 is selected for System Control. In QDRII SRAM, neither bank 19 nor bank 15 are allowed to select Data Read, because the I/O standard for DDR2 SDRAM Data and Address is SSTL18_II_DCI, and the I/O standard for QDRII SRAM Data Read is HSTL_I_DCI_18. These two I/O standards are not compatible. Hence MIG does not allow bank selection for the group of signals that do not follow the I/O standard compatibility rules.

Bank Selection For Controller 0 - DDR2 SDRAM

Choose the banks for the memory interface from the architectural view below. Generally banks in a single column give the optimum internal timing. You can alter the pin selection manually in the generated UCF but you must update the design with the "Update Design" option in this tool after making changes. See the User Guide for more information.

- You can set the Weighted Average Simultaneous Switching Outputs (WASSO - see the selected FPGA's User Guide) to limit the number of pins used per bank.
- Optimal banks for the PPC440 are preset if the option was selected earlier.
- Banks 3 and 4 have global clock inputs and are used for System Clock pins which have an I/O voltage which is incompatible with the memory interface.
- Priority for pins in a selected bank is 1) Data, 2) Address/Control, 3) System Control.

Address/Control: 26/26 Data: 11/11 System Control: 3/3 System Clock: 4/4

Bank:23 Available IO's: 38 WASSO Limit: 38 <input type="checkbox"/> Address/Control <input type="checkbox"/> Data <input type="checkbox"/> System Control	Bank:5 Available IO's: 38 WASSO Limit: 38 <input type="checkbox"/> Address/Control <input type="checkbox"/> Data <input type="checkbox"/> System Control	Bank:24 Available IO's: 38 WASSO Limit: 38 <input type="checkbox"/> Address/Control <input type="checkbox"/> Data <input type="checkbox"/> System Control
Bank:19 Available IO's: 2 WASSO Limit: 38 <input checked="" type="checkbox"/> Address/Control <input type="checkbox"/> Data <input type="checkbox"/> System Control	Bank:3 Available IO's: 15 WASSO Limit: 19 <input checked="" type="checkbox"/> System Clock	Bank:20 Available IO's: 38 WASSO Limit: 38 <input type="checkbox"/> Address/Control <input type="checkbox"/> Data <input type="checkbox"/> System Control
Bank:15 Available IO's: 37 WASSO Limit: 38 <input checked="" type="checkbox"/> Address/Control <input type="checkbox"/> Data <input type="checkbox"/> System Control	Bank:1 Available IO's: 16 WASSO Limit: 19 <input type="checkbox"/> Address/Control <input type="checkbox"/> Data <input checked="" type="checkbox"/> System Control	Bank:16 Available IO's: 38 WASSO Limit: 38 <input type="checkbox"/> Address/Control <input type="checkbox"/> Data <input type="checkbox"/> System Control
Bank:11 Available IO's: 38 WASSO Limit: 38 <input type="checkbox"/> Address/Control <input type="checkbox"/> Data	Bank:0 Available IO's: 0 WASSO Limit: 0	Bank:12 Available IO's: 38 WASSO Limit: 38 <input type="checkbox"/> Address/Control <input type="checkbox"/> Data

Deselect Banks Restore Defaults

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Figure 1-52: DDR2 SDRAM Bank Selection in a Multiple Interface Design

Bank Selection For Controller 1 - QDRII SRAM

Choose the banks for the memory interface from the architectural view below. Generally banks in a single column give the optimum internal timing. You can alter the pin selection manually in the generated UCF but you must update the design with the "Update Design" option in this tool after making changes. See the User Guide for more information.

- You can set the Weighted Average Simultaneous Switching Outputs (WASSO - see the selected FPGA's User Guide) to limit the number of pins used per bank.
- Optimal banks for the PPC440 are preset if the option was selected earlier.
- Banks 3 and 4 have global clock inputs and are used for System Clock pins which have an I/O voltage which is incompatible with the memory interface.
- Priority for pins in a selected bank is 1) Data, 2) Address/Control, 3) System Control.

Master Bank check boxes below the signal groups indicate the selection of Master bank when DCI Cascade option is enabled. Right and left columns can have only one Master bank, and the center column may have two Master Banks.

Address/Control: 22/22 ☒ Data Read: 38/38 ☒ Data Write: 44/44 ☒ System Control: 2/2 ☒ System Clock: 2/2 ☒

Master Bank in left column Master Bank in center top column Master Bank in center bottom column Master Bank in right column 20 ☒

Bank	Available IO's	WASSO Limit	Address/Control	Data Read	Data Write	System Control	System Clock
Bank:23	38	38	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
Bank:5	5	38	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>
Bank:24	0	38	<input type="checkbox"/>	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
Bank:19	2	38	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
Bank:3	13	19	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>
Bank:20	2	38	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input checked="" type="checkbox"/>
Bank:15	37	38	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
Bank:1	16	19	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
Bank:16	38	38	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>

Deselect Banks Restore Defaults

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Figure 1-53: QDRII SRAM Bank Selection in a Multiple Interface Design

When PPC440 compatible pinouts are selected, MIG outputs the fixed pinout. The banks that are checked indicate the banks used for PPC440 pinouts; the user does not have an option to select the specific banks. For example, bank selection of a 16-bit design with a XC5VFX100T-FF1136 target device and the PowerPC440 Block Selection value in the Pin Compatible FPGAs page set to **Top** is shown in [Figure 1-54](#).

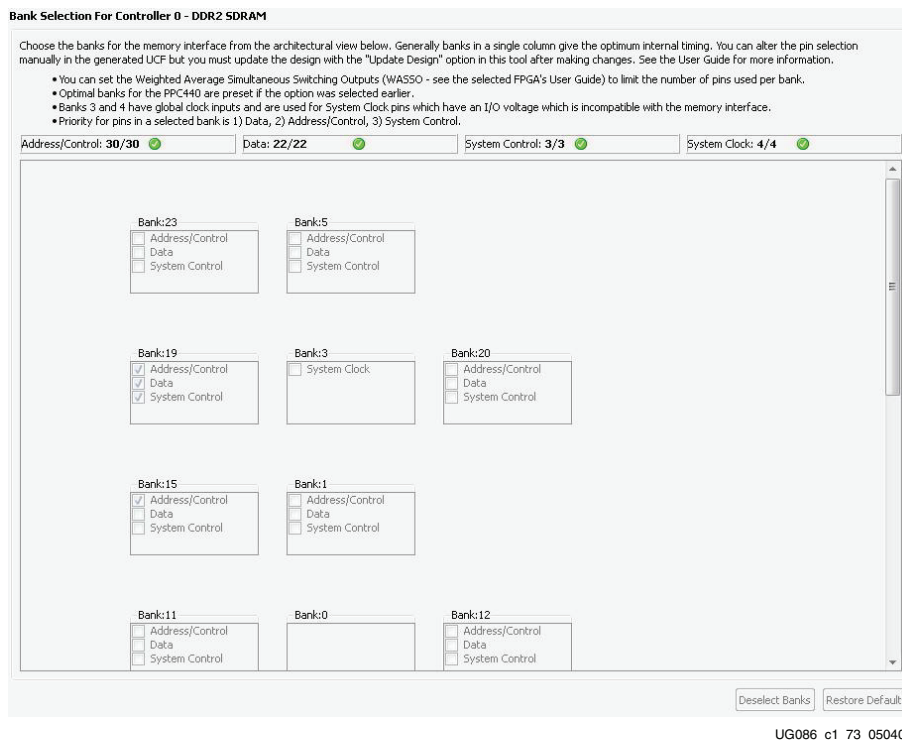
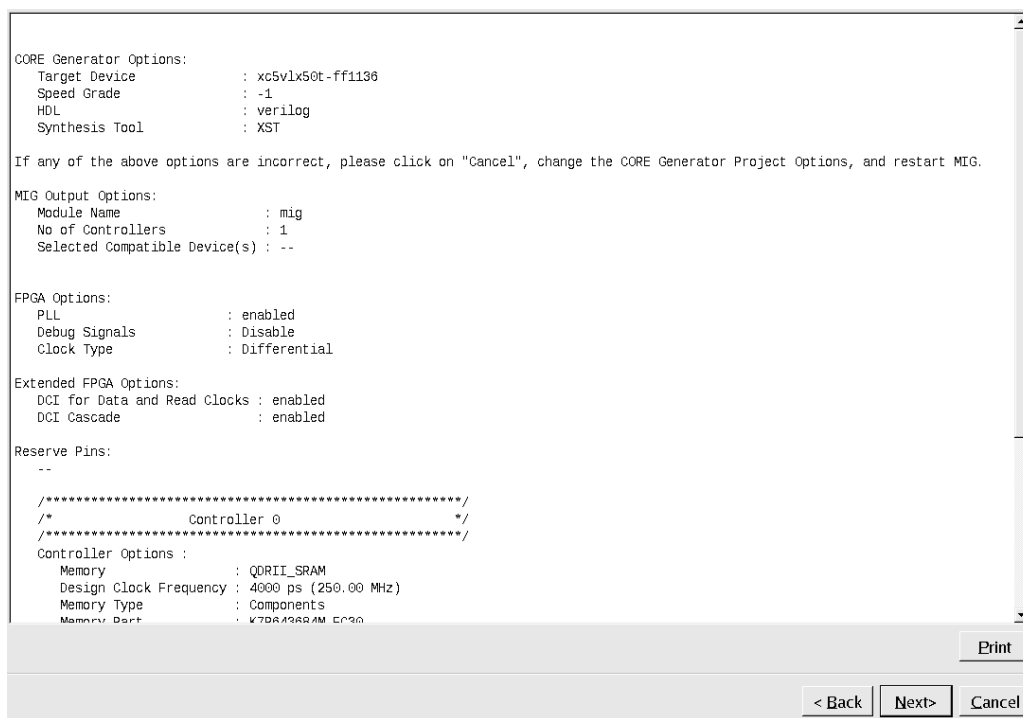


Figure 1-54: PPC Bank Selection Page

After selecting the banks, click **Next** to continue. The Summary page window is displayed.

Summary

This window provides complete details about the CORE Generator options, Interface parameters, FPGA options, and Bank selections of the active project (Figure 1-55).



```

CORE Generator Options:
  Target Device      : xc5vlx50t-ff1130
  Speed Grade       : -1
  HDL                : verilog
  Synthesis Tool    : XST

If any of the above options are incorrect, please click on "Cancel", change the CORE Generator Project Options, and restart MIG.

MIG Output Options:
  Module Name        : mig
  No. of Controllers : 1
  Selected Compatible Device(s) : --

FPGA Options:
  PLL                : enabled
  Debug Signals      : Disable
  Clock Type         : Differential

Extended FPGA Options:
  DCI for Data and Read Clocks : enabled
  DCI Cascade          : enabled

Reserve Pins:
  --

/*****
/*          Controller 0          */
*****/

Controller Options :
  Memory           : QDRII_SDRAM
  Design Clock Frequency : 4000 ps (250.00 MHz)
  Memory Type       : Components
  Memory Bank       : V70R432SRAM_C020
  
```

Print

< Back Next > Cancel

UG086_c1_31_030510

Figure 1-55: Summary

Click **Next** to move to the License Agreement page of the selected memory of the Micron/Qimonda memory model only for DDR2 SDRAM, DDR SDRAM, and RLDRAM II memory interface designs. For other memory interface designs, clicking the **Next** button will move to the PCB information page.

Memory Model License

MIG outputs a Micron memory model for simulation purposes for memories such as DDR SDRAM, DDR2 SDRAM, and RLDRAM II, as well as Qimonda memory model for DDR2 SDRAM. Read the license agreement carefully and select the **Accept** radio button to accept it (Figure 1-56). Selecting the **Accept** radio button also causes the models to be output in the output `sim` folder.

If the license agreement is not agreed to (i.e., the **Decline** radio button is selected), the memory model is not available. The user then needs to get the appropriate memory model by some other means to simulate the design.

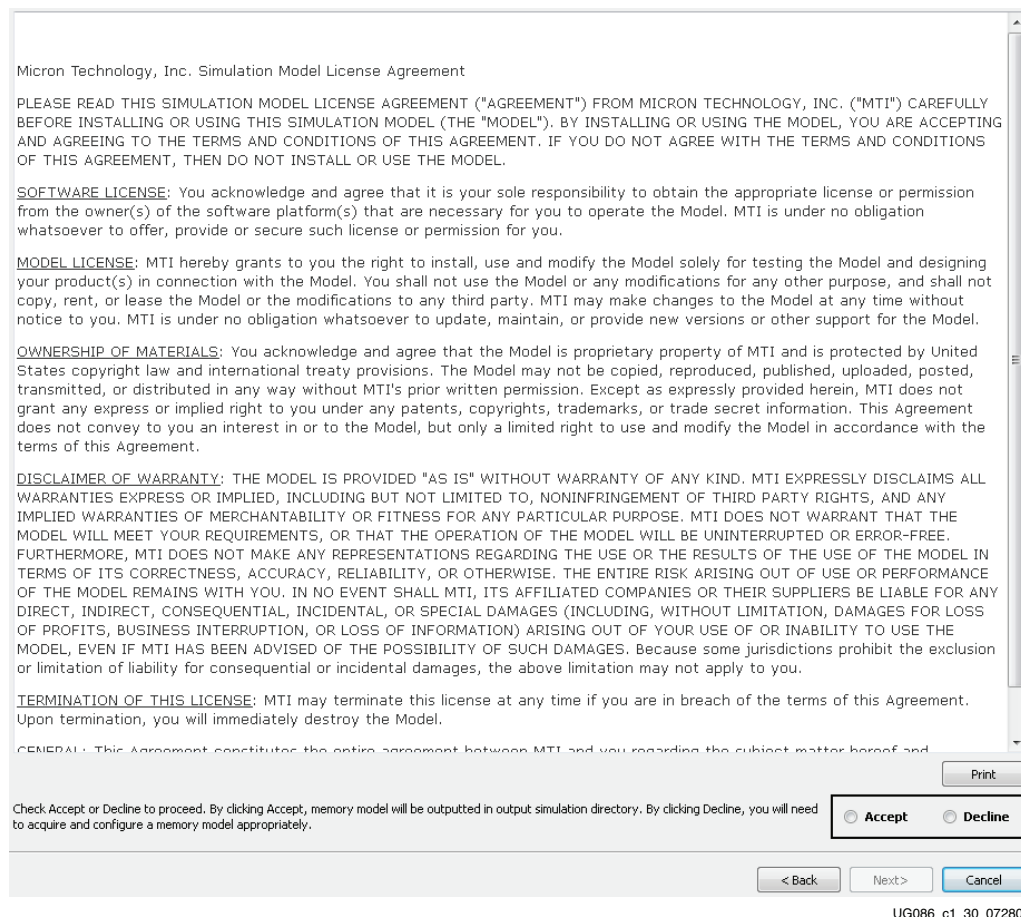


Figure 1-56: License Agreement

MIG outputs Micron and Qimonda memory models only. MIG does not output Samsung and Cypress memory models; these should be download from the vendor's respective websites (Figure 1-57).

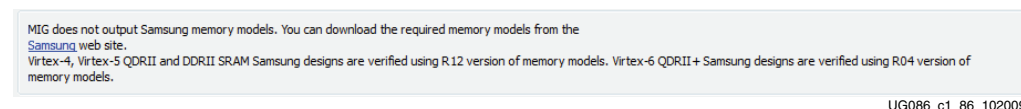
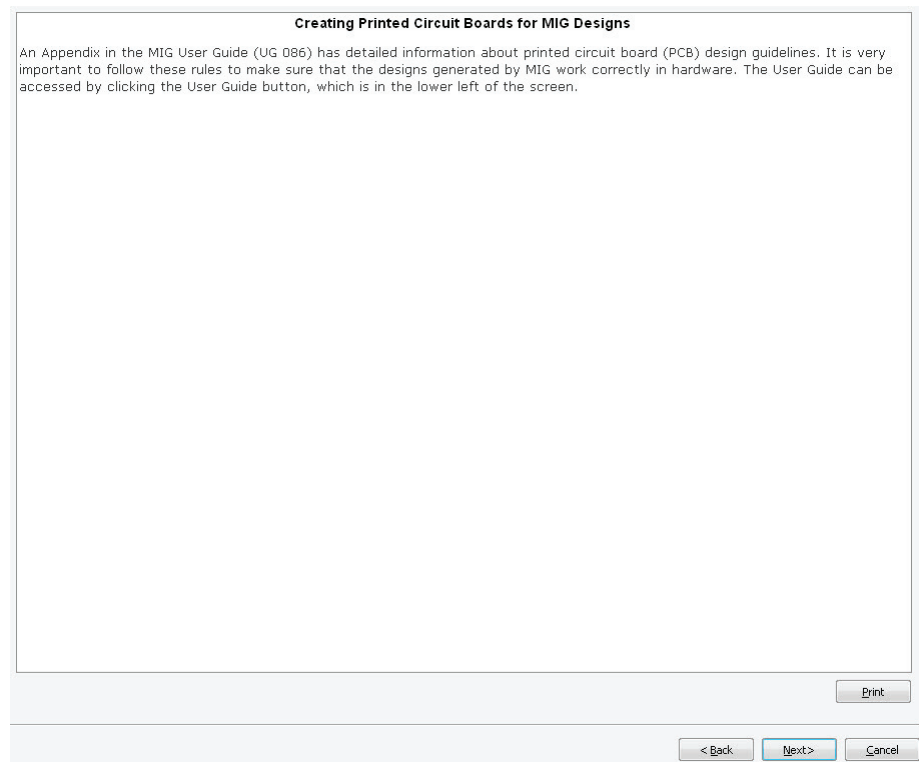


Figure 1-57: Samsung Memory Models Information

Click the **Next** button to move to the PCB information page.

PCB Information

This page displays the PCB related information to be considered while designing the board that uses MIG generated designs ([Figure 1-58](#)).



UG086_c1_42_072008

Figure 1-58: PCB Information

Click **Next** to go to the Design Notes page.

Design Notes

This page provides the design notes that should be taken into account while using MIG generated designs (Figure 1-59).

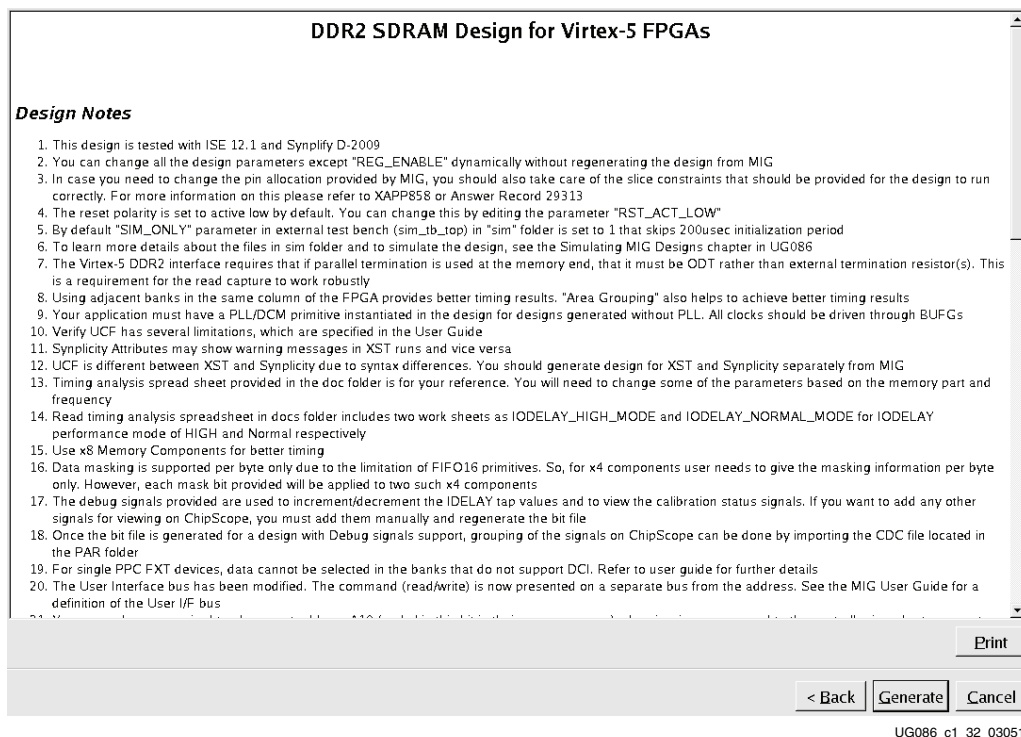


Figure 1-59: Design Notes

Click **Generate** to generate the design files. MIG generates three output directories: example_design, user_design, and docs. After generating the design, the MIG GUI closes.

Click **Cancel**. A Quit Confirmation window appears, as shown in Figure 1-60.

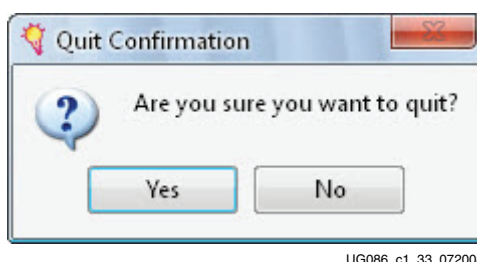


Figure 1-60: Quit Confirmation

Click **Yes** to exit or **No** to return to the current page.

Output Files

A MIG-generated design has the following output files and directory:

- A `<component name>_xmdf.tcl` file. This is the interface file between the ISE and CORE Generator software. The ISE software uses this file to determine the files output by the CORE Generator software for the core to be integrated into the ISE project.
- A `<component name>.vho` file, used for the core to be instantiated, created only when a VHDL design is generated.
- A `<component name>.veo` file, used for the core to be instantiated, created only when a Verilog design is generated.
- A `<component name>_readme.txt` file, includes information about the files generated and how they are used.
- A `<component name>` directory.

In the `<component name>` directory, three folders are created:

- docs
- example_design
- user_design

Any relevant documents, such as application notes, timing analysis spreadsheets, and user guide are in the docs directory.

The example_design and user_design folders contain several other folders and files. They are:

- rtl — Contains all the RTL files (either VHDL or Verilog design files). The RTL files generated for Virtex-5 FPGA designs do not have user design names (component names) prepended to the RTL file names. MIG generates the same code for both the XST and Synplicity tools. The generated RTL has separate XST and Synplicity attributes. While running XST designs, Synplicity attributes might cause warning messages to appear, and vice versa. The warning messages related to these attributes can be ignored.
- par — Contains the UCF with constraints for the design, including two scripts files that are generated (ise_flow.bat and create_ise.bat):
 - ise_flow.bat — The user double-clicks the ise_flow.bat script file to run the design through synthesis, build, map, and par. This script file sets all the required options. Users should refer to this file for the recommended build options for the design. This file takes all synthesis options from the xst_run.txt file located in the par folder. All map, place-and-route, and Timing Reporter and Circuit Evaluator (TRCE) options are set in the ise_flow.bat file. BITGEN options are taken from the UT file located in the par folder. The options that are not listed out in these files (such as Synthesis and others) are set to their default values. For more information about the allowed option values, refer to the Development System Reference Guide in the Xilinx ISE 12.3 Design Suite Software Manuals and Help – PDF Collection at <http://www.xilinx.com/support/documentation/index.htm>.
 - create_ise.bat — The generated MIG design includes a create_ise.bat script file in both the example_design/par and user_design/par directories. Running the create_ise.bat script generates an ISE tools project that incorporates the generated MIG design. If the file is run from the example_design/par directory, the ISE tools project includes the example_design. If the file is run from the user_design/par directory, the ISE

project includes the `user_design`. The `create_ise.bat` file calls the `set_ise_prop.tcl` file, which is also located in the selected `par` directory. The `set_ise_prop.tcl` file includes standard `xtclsh` commands that pull the MIG RTL source files (`example_design/rtl` or `user_design/rtl`) into an ISE tools project and set the required synthesis and implementation build options. After completion of the `create_ise.bat` script, a `test.ise` file is created that can be opened in the ISE tools. The synthesis and implementation build options set by `create_ise.bat` are recommended. No other build options have been tested and are not supported. For detailed information on the options set by `create_ise.bat`, refer to the Development System Reference Guide and the XST User Guide in the Xilinx ISE 12.3 Design Suite Software Manuals and Help – PDF Collection at <http://www.xilinx.com/support/documentation/index.htm>.

- `compatible_ucf` — This folder is created when the memory interface designs are generated with compatible FPGAs. This folder contains a compatible UCF of every compatible FPGA selected.
- CDC file — MIG provides the CDC for debug enable designs. For more information on how to use this file, refer to [Appendix F, “Analyzing MIG Designs in the ChipScope Analyzer with CDC.”](#)
- `synth` — Contains the SDC file which has design constraints for Synplify Pro synthesis tool. This folder also has the script files, which set various tool options. There is also a project file, through which the RTL files are passed for synthesis.
- `sim` — Contains the testbench files that are needed to simulate the design. It also has a `.do` file. For more information on simulating the design, refer to [“Simulation Guide,” page 499](#).

For the `user_design` folder, a synthesizable testbench module is also present in the `sim` folder.

Caution! Recommended Build Options. The `ise_flow.bat` file in the `par` folder of the component name directory contains the recommended build options for the design. Failure to follow the recommended build options could produce unexpected results.

Create Design for Xilinx Reference Boards

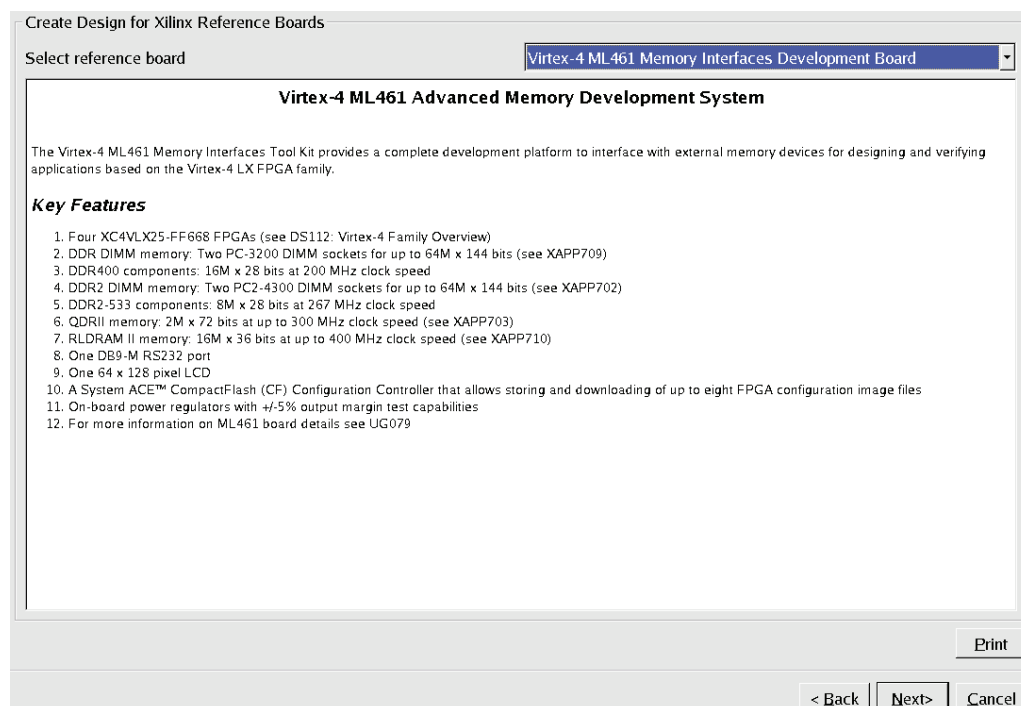
To create a design for the Xilinx Reference Boards, select **Create Design for Xilinx Reference Boards** from the MIG Output Options. It is intended to generate the board files for various Xilinx Reference Boards. Click **Next** to continue.

The flow is as follows:

1. [Reference Board Designs](#)
2. [Memory Model License](#)
3. [PCB Information](#)
4. [Design Notes](#)

Reference Board Designs

This section allows selection of the board for which the designs are to be generated (Figure 1-61).



UG086_c1_34_030510

Figure 1-61: Create Design for Xilinx Reference Boards

The pull-down menu includes a list of boards. Select the appropriate board. Details about the particular board are displayed in the pane below. After selecting the board, click **Next** to move to next page.

Memory Model License

MIG outputs a Micron memory model for simulation purpose for memories like DDR SDRAM, DDR2 SDRAM, and RLDRAM II. To generate the board files for the specified Xilinx Reference Board, read the license agreement carefully and select the **Accept License Agreement** radio button (Figure 1-62).

If the license agreement is not accepted, the user cannot generate board files. The **Next** button is disabled unless the license agreement is accepted.

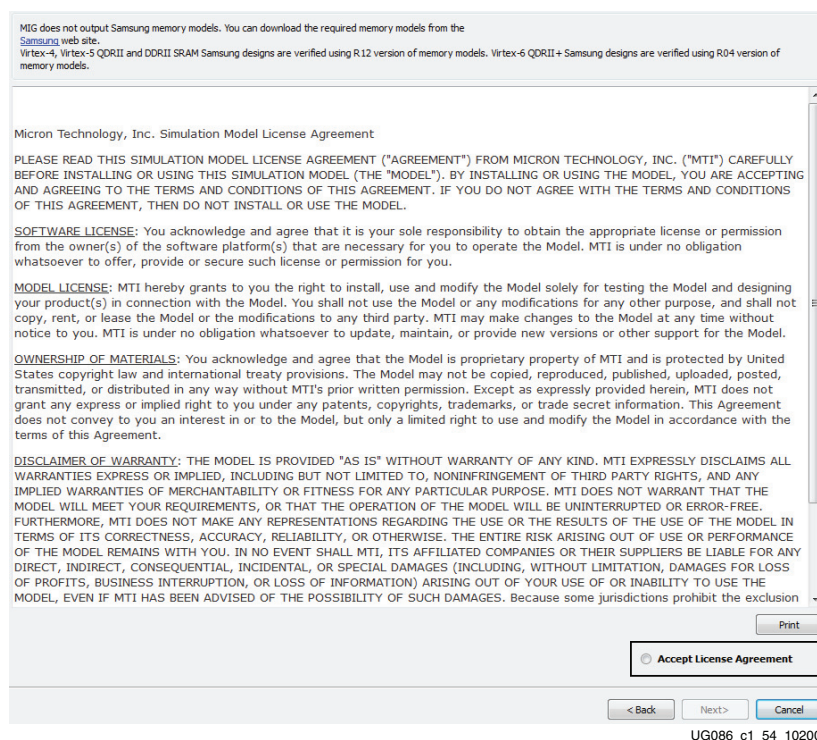


Figure 1-62: Memory Model License

Click **Next** to go to the PCB Information page.

PCB Information

This page displays the PCB-related information to be considered while designing the board that is to use a MIG generated design ([Figure 1-63](#)).

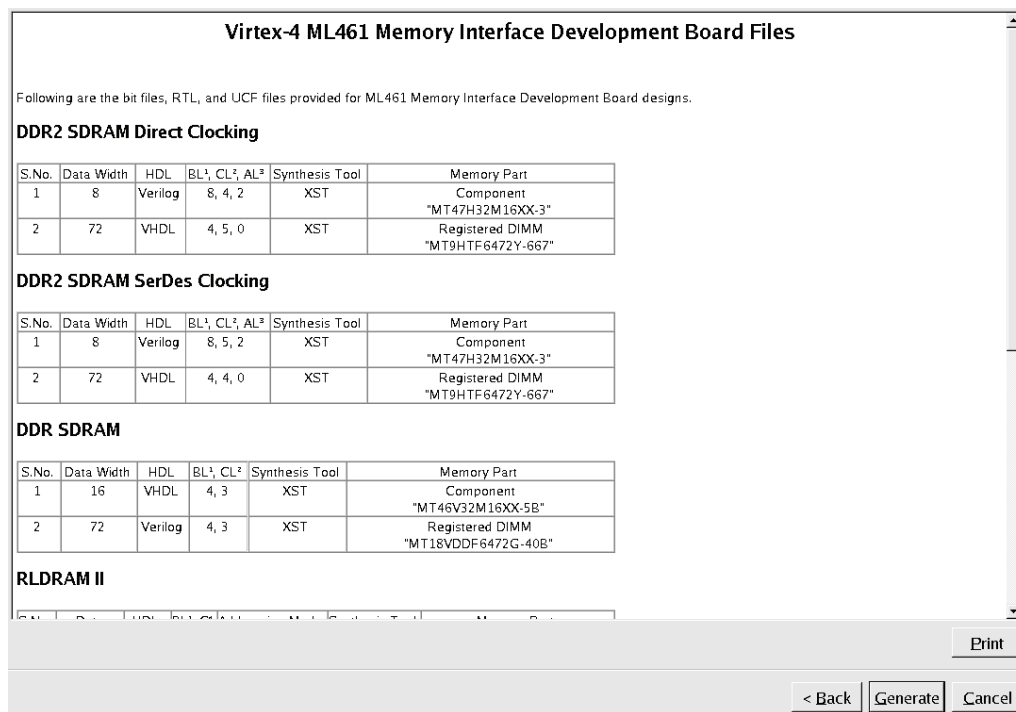


Figure 1-63: PCB Information

Click **Next** to go to the Design Notes page.

Design Notes

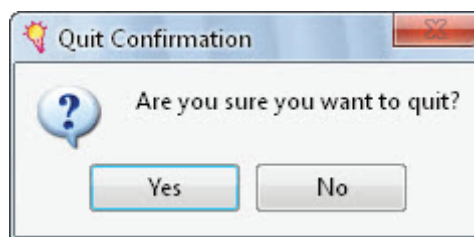
Click **Generate** to generate the board files for the specified Xilinx reference board (Figure 1-64). After successful generation of the board files, the MIG GUI closes.



UG086_ct_35_030510

Figure 1-64: Finish

Click **Cancel**. A Quit Confirmation window appears, as shown in Figure 1-65. Click **Yes** to exit or **No** to return to the current page.



UG086_ct_33_072008

Figure 1-65: Quit Confirmation

Verify UCF and Update Design and UCF

To verify the UCF and update design and UCF, select the third option (Verify UCF and Update Design and UCF) from the MIG Output Options page. This option verifies that the input UCF passed and can update the design and UCF for the current version of the MIG tool. Verify UCF is intended for verification of UCF files that were/are generated from the MIG tool and later modified. This feature ensures that the pinout still follows the rules required for the current version of MIG generated designs. For a list of rules associated with the Verify UCF feature, refer to [“Verify UCF and Update Design Rules,” page 80](#).

The Update Design feature updates the input UCF files to make them compatible with the current MIG design. The MIG tool verifies the input UCF for the pin allocation rules and allows the UCF to get updated only if it passes the pin allocation rules. The Update Design feature is required in the following scenarios:

- A pinout is generated using an older version of MIG and the design is to be revised to the current version of MIG. In MIG 2.0 and later, the pinout allocation algorithms have been changed for certain MIG designs.
- A pinout is generated independent of MIG or is modified after the design is generated. When a design is generated from MIG, the UCF file and HDL code are generated with the correct constraints.

Caution! This is not recommended. MIG should be used to generate the pinout. If an independently generated pinout must be used, a UCF should be generated using MIG and used as a baseline for constraint modifications.

After verification of the UCF is completed and if there are no issues with the input UCF, the user can update the RTL and UCF for the current version of the MIG tool by proceeding further. The Update Design feature ensures that the input UCF pinout remains the same. This option is not supported for Virtex-5 FPGA PPC440 DDR2 designs. Update Design works for Create Custom Part if the created custom parts exist in the output directory or project directory. If the created custom part does not exist, the MIG tool cannot update the design. For a list of rules associated with the Update Design feature, refer to [“Verify UCF and Update Design Rules,” page 80](#). For more details on Virtex-5 FPGA DDR2 design constraints, see [Appendix B, “Pinout-Related UCF Constraints for Virtex-5 FPGA DDR2 SDRAMs.”](#) For a list of rules associated with the Update UCF feature, refer to [“Verify UCF and Update Design Rules,” page 80](#).

The Update Design feature updates the UCF constraints and also the RTL design parameters. RTL design parameters are updated in the corresponding RTL file. For example, for a Virtex-4 FPGA single controller DDR2 direct-clocking design, the IDELAYCTRL_NUM parameter is updated in the idelay_ctrl module. These parameters are updated for both example_design and user_design. In MIG 3.0 and later, DCM is replaced with PLL for all Virtex-5 FPGA designs. If the Update Design option is used, the MIG tool uses PLL resources instead of DCM resources. The infrastructure module has both PLL and DCM codes and the CLK_GENERATOR parameter enables either a PLL or a DCM in the infrastructure module. The CLK_GENERATOR parameter is set to PLL by default. For use as a DCM, this parameter should be changed manually to DCM.

MIG generates mig.prj files in the output mig_x/example_design and mig_x/user_design directories. These files contain the project settings specific to a generated MIG project for both the example_design and user_design. A mig.prj file is required to perform the update. This mig.prj file can be from a previous version of MIG or from the current version.

If a MIG design has not been generated, use the current MIG version to generate the design. Select the appropriate banks of the desired pinout on the Bank Selection GUI page

to ensure that the update completes successfully. If a MIG design has already been generated, locate the `mig.prj` file in the generated MIG project. Ensure that the banks selected for this project match the banks of the desired pinout. This is required for the update to complete successfully.

Open MIG either by invoking a new MIG project or by reopening the previously generated MIG project. Verify the options displayed on screen one and click **Next**. On screen two, provide a component name and select **Verify UCF and Update Design and UCF**.

Note: Verify UCF and Update Design and UCF verifies that the pinout adheres to the required pinout rules outlined in [Appendix A, "Memory Implementation Guidelines."](#) The pinout must meet these guidelines for the tool to complete the Update Design option.

The flow is as follows:

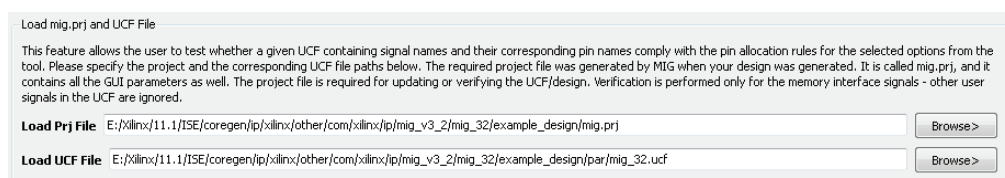
1. [Load mig.prj and UCF](#)
2. [Summary](#)
3. [Verification Report](#)
4. [Memory Model License](#)
5. [PCB Information](#)
6. [Design Notes](#)

Load mig.prj and UCF

Browse to the project file path (`mig.prj`). If the pinout is an `example_design` pinout (i.e., contains the additional `example_design` pins such as `ERROR`), select the `mig.prj` file located in the `example_design` directory. If the pinout does not include the additional `example_design` pins, select the `mig.prj` file located in the `user_design` directory.

If a MIG provided UCF is being updated from a pre-MIG release, browse to the MIG-generated UCF. If a UCF is being updated to a user-defined pinout, browse to this UCF. The UCF only needs to include the desired pin LOCs; however, the pin names must match the MIG syntax. Provide the input UCF path at the **Load UCF File** box and input the `mig.prj` at the **Load Prj File** Box, or click the **Browse** button to enter the UCF and Prj files through a browser window ([Figure 1-66](#)).

Note: Update Design is not supported for the UCF signal names that were modified using the Edit Signal Names option of MIG 1.73.



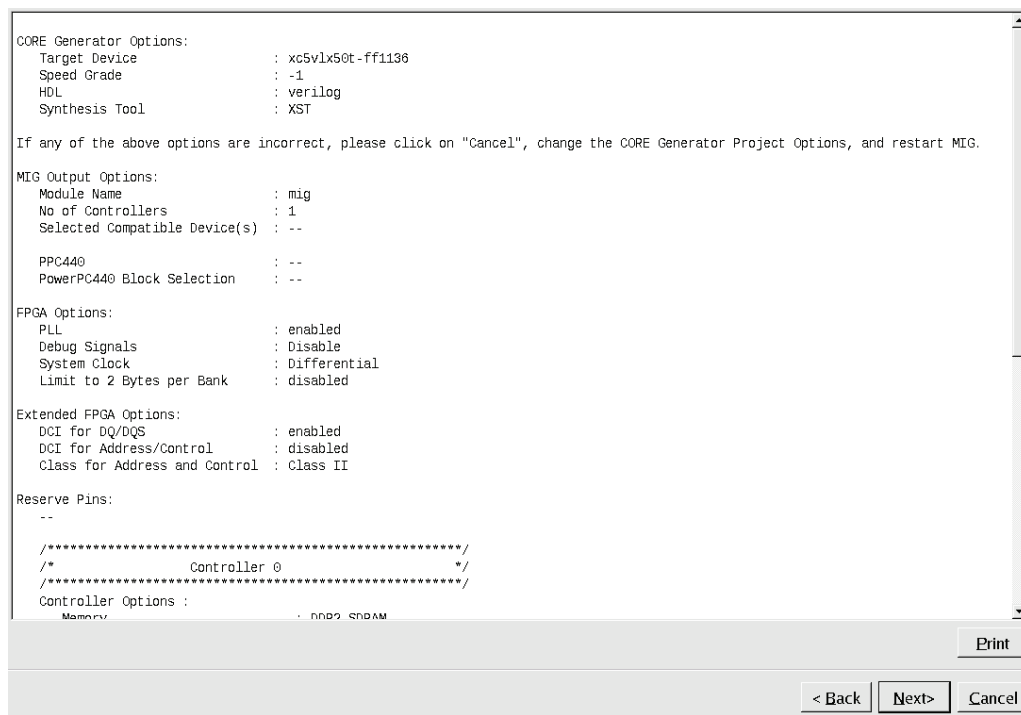
UG086_c1_37_072809

Figure 1-66: Prj and UCF Selection Window

Select the appropriate files. After selecting the files, click **Next** to continue.

Summary

This page provides complete details about the bank selection, Interface parameters, CORE Generator options and FPGA options of the project for which the UCF is to be verified.



```

CORE Generator Options:
  Target Device       : xc5vlx50t-ff1136
  Speed Grade        : -1
  HDL                 : verilog
  Synthesis Tool      : XST

If any of the above options are incorrect, please click on "Cancel", change the CORE Generator Project Options, and restart MIG.

MIG Output Options:
  Module Name         : mig
  No of Controllers    : 1
  Selected Compatible Device(s) : --

  PPC440              : --
  PowerPC440 Block Selection : --

FPGA Options:
  PLL                  : enabled
  Debug Signals        : Disable
  System Clock         : Differential
  Limit to 2 Bytes per Bank : disabled

Extended FPGA Options:
  DCI for DQ/DQS       : enabled
  DCI for Address/Control : disabled
  Class for Address and Control : Class II

Reserve Pins:
  --

/* ***** */
/*          Controller 0          */
/* ***** */

Controller Options :
  Memory           : nand2 sbram
  
```

Print

< Back Next > Cancel

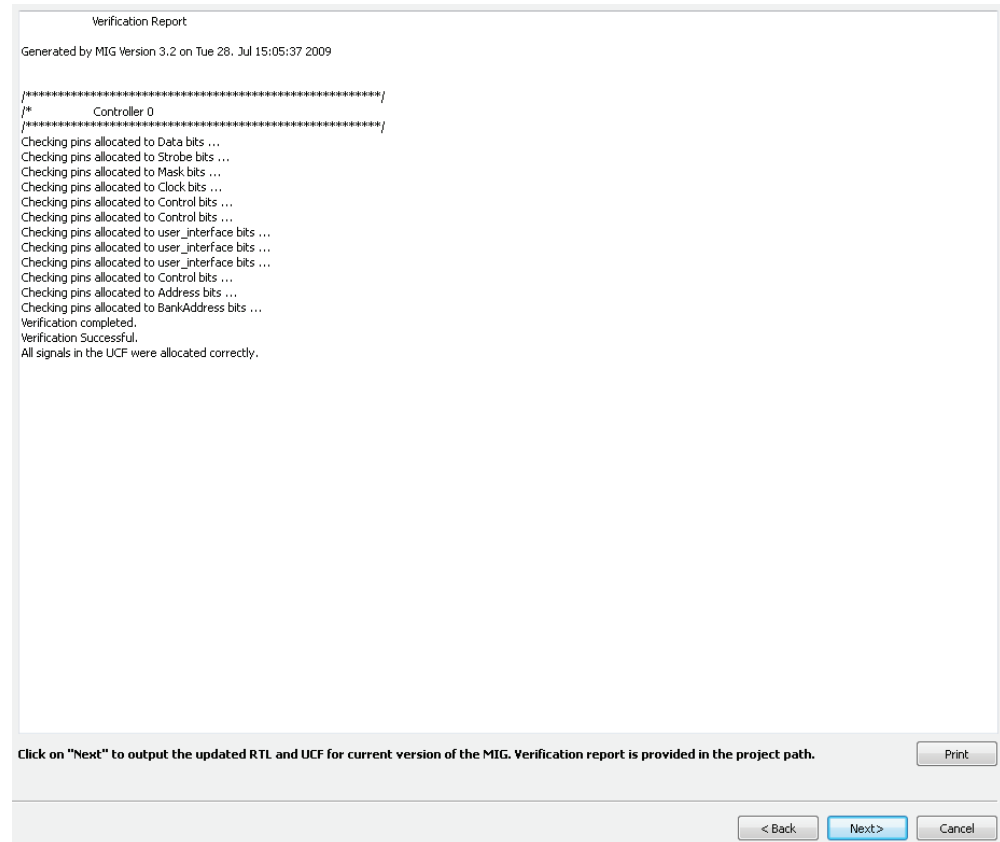
UG086_c1_38_030510

Figure 1-67: Summary Page

Click **Next** to move to the Verification Report page.

Verification Report

This window indicates if the input UCF has been verified and provides warning or error messages if the input UCF does not follow the pin allocation rules.



UG086_c1_69_072809

Figure 1-68: Verification Report Page after Successful Verification

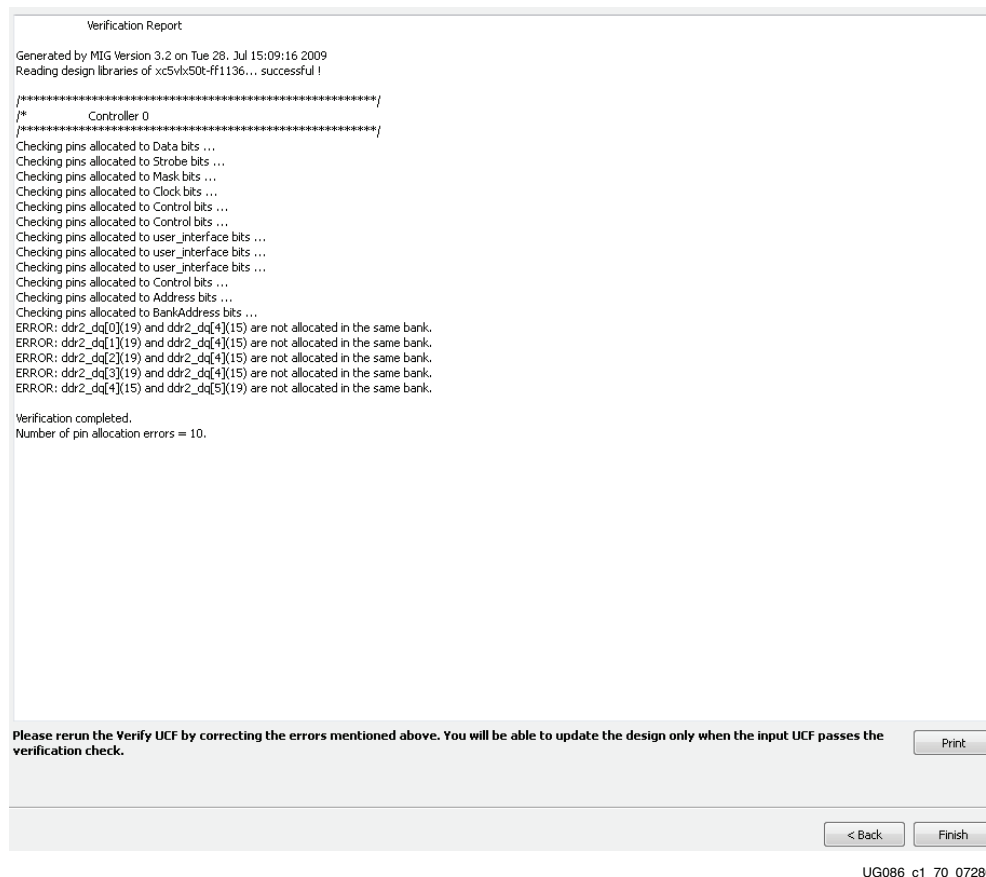


Figure 1-69: Verification Report Page after Unsuccessful Verification

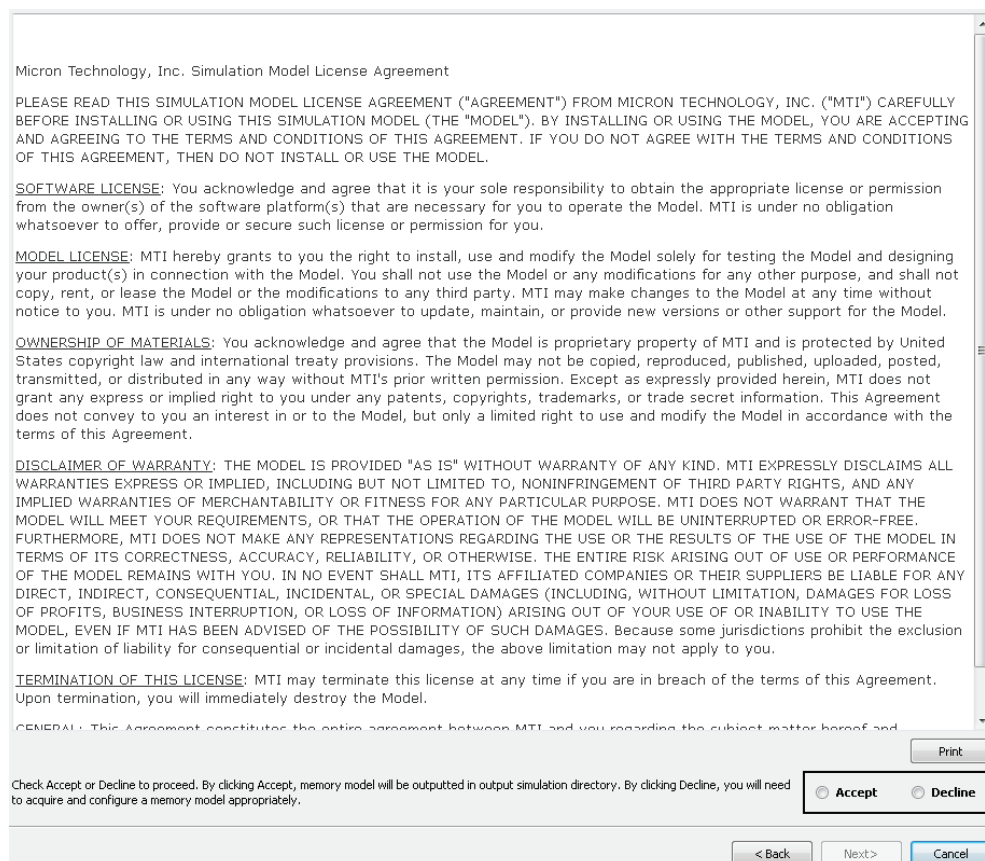
Click **Next** to move to Memory Model License agreement page. If the Verification Report file has a warning message(s), MIG proceeds with updating the design.

When the input UCF does not follow the MIG pin allocation rules, for example if the Verification Report file has an error message(s), MIG does not proceed with updating the design.

Memory Model License

MIG outputs Micron memory model for simulation purposes for memories such as DDR2 SDRAM, DDR SDRAM and RLDRAM II and Qimonda memory model for DDR2 SDRAM. To get the simulation model in the output folder, click the **Accept** radio button. Read the license agreement carefully and select the **Accept** radio button to accept it.

If the license agreement is not agreed to (i.e., the **Decline** radio button is selected), the simulation model is not output into the output folder.



Micron Technology, Inc. Simulation Model License Agreement

PLEASE READ THIS SIMULATION MODEL LICENSE AGREEMENT ("AGREEMENT") FROM MICRON TECHNOLOGY, INC. ("MTI") CAREFULLY BEFORE INSTALLING OR USING THIS SIMULATION MODEL (THE "MODEL"). BY INSTALLING OR USING THE MODEL, YOU ARE ACCEPTING AND AGREEING TO THE TERMS AND CONDITIONS OF THIS AGREEMENT. IF YOU DO NOT AGREE WITH THE TERMS AND CONDITIONS OF THIS AGREEMENT, THEN DO NOT INSTALL OR USE THE MODEL.

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TERMINATION OF THIS LICENSE: MTI may terminate this license at any time if you are in breach of the terms of this Agreement. Upon termination, you will immediately destroy the Model.

GENERAL: This Agreement constitutes the entire agreement between MTI and you regarding the subject matter hereof and

Check Accept or Decline to proceed. By clicking Accept, memory model will be outputted in output simulation directory. By clicking Decline, you will need to acquire and configure a memory model appropriately.

☒ Accept ☐ Decline

< Back Next > Cancel

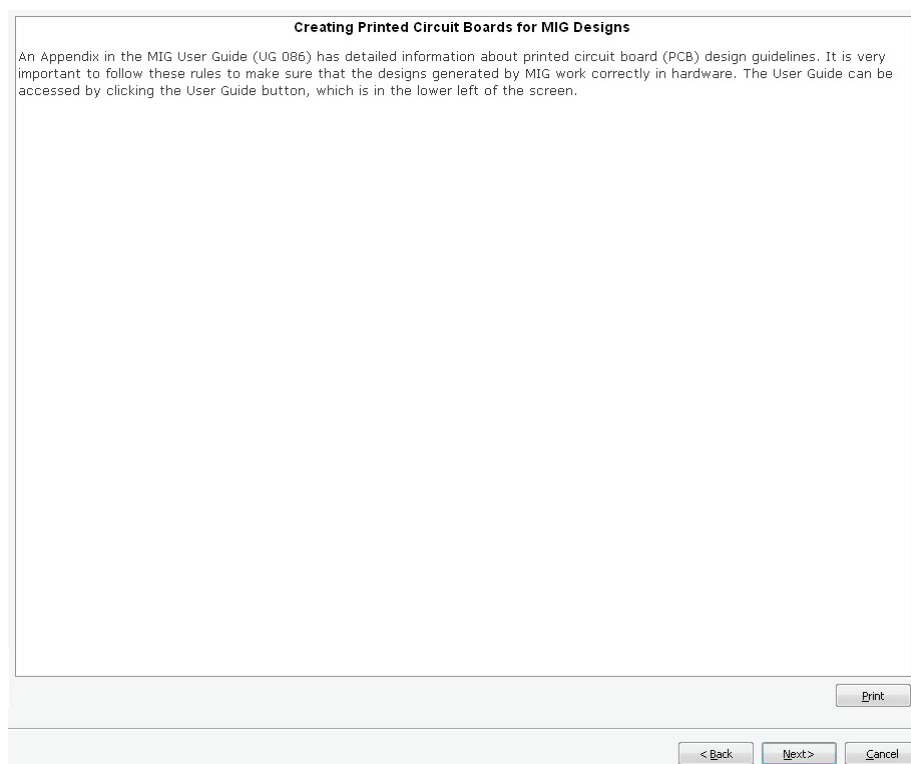
UG086_c1_71_072809

Figure 1-70: Memory Model License Agreement Page

Click **Next** to move to the PCB information page

PCB Information

This page displays the PCB related information to be considered while designing the board that uses MIG generated designs. Click **Next** to go to the Design Notes page.



UG086_c1_72_072208

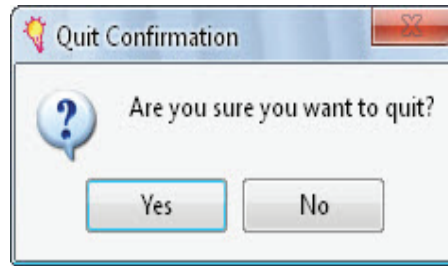
Figure 1-71: PCB Information

Design Notes

This page provides the design notes that should be taken into account while using the MIG generated designs.

Click the Generate button to generate the complete design with the loaded Prj settings and modified UCF (the UCF is updated without affecting the pin allocation constraints). MIG generates three output directories example_design, user_design and docs. The UCF files in the example_design and user_design folders are updated to the input UCF. After generating the design, the MIG GUI closes.

Click **Cancel**. A Quit Confirmation window appears, as shown in [Figure 1-72](#). Click **Yes** to exit or **No** to return to the Current page.



UG086_c1_84_092208

Figure 1-72: Quit Confirmation

Verify UCF and Update Design Rules

Verify UCF and Update Design and UCF verifies the input UCF file for pin allocation rules and generates warnings or error reports for any issues. It does not verify the input prj file. This feature is useful to verify any UCF pinout changes after the design is generated from the MIG tool. The user must pass the MIG generated prj file (the original prj file) without any modifications. The verification report will not be correct if any of the parameters in the original prj file are altered. In the CORE Generator tool, the recustomization option should be selected to reload the project.

The following UCF keywords and syntax elements are supported by Verify UCF and Update Design:

- KEYWORDS:
 - NET
 - Net
 - net
- NET names (can be lowercase, uppercase, or a mix of lower- and uppercase):
 - NET "ddr2_dq[0]"
 - NET ddr2_dq[0]
 - NET "DDR2_DQ[0]"
 - NET "Ddr2_dq[0]"

- Bus notations:
 - NET “ddr2_dq[0]”
 - NET “ddr2_dq<0>”
- LOC constraints (supports various syntaxes, such as LOC, PROHIBIT and INHIBIT):
 - LOC = “N33”
 - LOC = N33
- IOSTANDARD:
 - NET “ddr2_dq[*]” IOSTANDARD = SSTL18_II_DCI;
 - NET “ddr2_dq[*]” LOC=N33 | IOSTANDARD = SSTL18_II_DCI;
- The MIG output UCF has spaces between the various KEYWORDS. The input UCF need not have the same number of spaces, but each KEYWORD should be followed by at least one space:
 - NET “ddr2_dq[*]” IOSTANDARD = SSTL18_II_DCI;
 - NET “ddr2_dq[*]” IOSTANDARD = SSTL18_II_DCI;

All of the above elements of syntax are treated the same by the MIG tool.

The following rules are verified from the input UCF file.

DDR2 SDRAM/DDR SDRAM Spartan FPGA designs:

1. Verifies the slice location constraints for DQ, DQS delayed col, FIFO write enable and FIFO write address, and rst_dqs_div signals.
2. Verifies RLOC and BEL constraints for LUT delay calibration chain.
3. Verifies RLOC_ORIGIN constraints for LUT delay calibration chain.
4. Verifies AREA group constraint for calibration logic.
5. Verifies 5 Up/6 Down rule for DQ signals from DQS for left/right banks.
6. Verifies 5 Right rule for DQ signal from DQS for top/bottom banks
7. Verifies the DQ, DQS, DM, memory clocks, and rst_dqs_div (loop back) signals on the same side of the FPGA.
8. Verifies the rst_dqs_div signal (loopback) should be center of the DQS sets.
9. Verifies system clock signals, whether allocated to the global clock pair of the device.
10. Verifies memory clock signals and differential DQS to be allocated to the differential I/O pair of the device.
11. Verifies if reserved pins are used in the UCF.
12. Verifies VRN/VRP and VREF pins are not used in the UCF.
13. Verifies if the same tile is used for left/right banks for the following signals:
 - DQ and DQS
 - DQ and Address
 - DQ and rst_dqs_div_out
 - DM and DQS
 - DM and Address
 - DM and rst_dqs_div_out

The above signals cannot be used in the same tile because the two signals are in two different clock phases.

14. Verifies all the pins and slice allocation rules if user selects compatible UCF.

DDR2 SDRAM Virtex-4/Virtex-5 FPGA designs:

1. Updates the IDELAYCTRL LOCs and slice constraints in the updated UCF.
2. Verifies the UCF and Updates the design even with the compatible UCF.
3. Verifies the UCF and Updates the design even with the user design UCF.
4. Verifies the UCF for system clocks allocated to global clock pins.
5. Updates the design for Virtex-4 FPGA DDR2 SDRAM multicontroller user design UCF. If MIG does not find sufficient pins in a bank for allocating ERROR signal, then user has to manually allocate the LOCs for the ERROR signal in the updated UCF file.
6. In designs containing an x4 memory part, the MIG verifies the UCF only when the DM is associated with DQ higher nibble.
7. Verifies UCF for differential DQS signals allocated to differential pair pins in DDR2 SDRAM designs.

DDR SDRAM Virtex-4/Virtex-5 FPGA designs:

1. Updates the IDELAYCTRL LOCs and slice constraints in the updated UCF.
2. Verifies the UCF and Updates the design even with the compatible UCF.
3. Verifies the UCF and Updates the design even with the user design UCF.
4. Verifies the UCF for system clocks allocated to global clock pins.
5. Verifies the UCF for DQS to CC_P pin and corresponding DM to the CC_N for a CC pair in Virtex-5 FPGA designs.
6. For parts with no DM, verifies the UCF for DQS to CC_P pin and the CC_N to any of the output pins only in Virtex-5 FPGA designs.
7. In designs containing an x4 memory part, the MIG verifies the UCF only when the DM is associated with DQ higher nibble.

QDRII SRAM/DDRII SRAM Virtex-4/Virtex-5 FPGA designs:

1. Updates the IDELAYCTRL LOCs in the updated UCF.
2. Verifies the UCF and updates the design even with the compatible UCF.
3. Verifies the UCF and Updates the design even with the user design UCF.
4. Verifies the UCF for system clocks allocated to global clock pins.
5. Verifies the UCF for CQ and CQ_n allocation only to P-pins.
6. For DDRII SRAM CIO x36 Virtex-5 FPGA designs, MIG verifies the UCF only when the K/K_n and C/C_n are associated with the most significant 18 bits of data.

RLDRAMII Virtex-4 FPGA design:

1. Updates the IDELAYCTRL LOCs in the updated UCF.
2. Verifies the UCF and updates the design even with the compatible UCF.
3. Verifies the UCF and updates the design even with the user design UCF.
4. Verifies the UCF for system clocks allocated to global clock pins.

The following rules are *not* verified from the input UCF file.

DDR2 SDRAM/DDR SDRAM Spartan FPGA designs:

1. MIG does not verify if user changes vector notation of generate statement in the instance hierarchy path.

2. If two pins are allocated to the same signal, MIG is not giving any error or warning message.
3. MIG does not verify if DQS signal is not present in the UCF and does not report any message in the report.
4. MIG does not give any message if DIRT strings are missing in the UCF file for top/bottom banks of XC3S2000, XC3S4000 and XC3S5000 devices.

DDR2 SDRAM Virtex-4/Virtex-5 FPGA designs:

1. Verify UCF for IDELAYCTRL LOCs and slice constraints.
2. Update design for the PPC supported designs.
3. Verify UCF and Update design for Virtex-5 FPGA multicontroller designs.
4. Updated design using the updated UCF. It will result in unknown error messages.
5. Verify UCF for differential system clocks and differential memory signals allocated to differential pair.
6. Verify UCF for vacant VRN/VRP and VREF pins.
7. Verify UCF when a signal is allocated to two pins.
8. Verify UCF when reserved pins used for pin allocation.

DDR SDRAM Virtex-4/Virtex-5 FPGA designs:

1. Verify UCF for IDELAYCTRL LOCs and slice constraints.
2. Updated design using the updated UCF. It will result in unknown error messages.
3. Verify UCF for differential system clocks and differential memory signals allocated to differential pair.
4. Verify UCF for vacant VRN/VRP and VREF pins.
5. Verify UCF when a signal is allocated to two pins.
6. Verify UCF when reserved pins used for pin allocation.

QDRII SRAM/DDRII SRAM Virtex-4/Virtex-5 FPGA designs:

1. Verify UCF for IDELAYCTRL LOCs.
2. Updated design using the updated UCF. It will result in unknown error messages.
3. Verify UCF for differential system clocks and differential memory signals allocated to differential pair.
4. Verify UCF for vacant VRN/VRP and VREF pins.
5. Verify UCF for Master-Slave banks association.
6. Verify UCF when a signal is allocated to two pins.
7. Verify UCF when reserved pins used for pin allocation.

RLDRAMII Virtex-4 FPGA design:

1. Verify UCF for IDELAYCTRL LOCs.
2. Updated design using the updated UCF. It will result in unknown error messages.
3. Verify UCF for differential system clocks and differential memory signals allocated to differential pair.
4. Verify UCF for vacant VRN/VRP and VREF pins.
5. Verify UCF when a signal is allocated to two pins.
6. Verify UCF when reserved pins used for pin allocation.

Error Messages

This section describes the different error messages that can be generated when verifying the UCF.

The reference UCF must follow the MIG naming conventions (refer to the UCF generated by MIG). For example, the Virtex-4 FPGA DDR2 SDRAM controller 0 should have `cntrl0_ddr2_dq[0]` for data bits, and RLDRAM controller 0 should have `cntrl0_rld2_dq[0]` for data bits.

- **Uniqueness.** If two signals are allocated to the same pins in the reference UCF, an error message is listed in the directed file with a user-assigned name.

The error message format is "<signal_name1> and <I> are allocated to same pins."

For example, if `cntrl0_ddr2_dq[0]` and `cntrl0_ddr2_dqs[0]` are allocated to same pin, such as:

```
NET "cntrl0_ddr2_dq[0]" LOC = "D12" ;
NET "cntrl0_ddr2_dqs[0]" LOC = "D12" ;
```

Then the following error message is printed:

```
ERROR: cntrl0_ddr2_dq[0] and cntrl0_ddr2_dqs[0] are allocated to the
same pins. Pins are not unique.
```

- **Association.** Signals in the same group should be allocated in the same bank, otherwise MIG reports error messages. For CIO parts (such as DDR2 SDRAM, DDR SDRAM, RLDRAMII, and DDRII SRAM CIO), this rule is applied on data group pins. For SIO parts (such as QDRII SRAM, and DDRII SRAM SIO), this rule is applied only for data read group pins and not for data write group pins.

The error message format is "<signal_name1> and <signal_name2> are not allocated in the same banks."

For example, DDR2 SDRAM:

```
NET "cntrl0_ddr2_dq[0]" LOC = "D12" ; #bank 6
NET "cntrl0_ddr2_dq[1]" LOC = "C12" ; #bank 6
NET "cntrl0_ddr2_dq[2]" LOC = "B10" ; #bank 6
NET "cntrl0_ddr2_dq[3]" LOC = "C10" ; #bank 7
```

Assume `cntrl0_ddr2_dq[3]` and `cntrl0_ddr2_dq[2]` are allocated to pins of different banks, such as bank 7 and bank 6, respectively. The following error messages are printed:

```
ERROR: cntrl0_ddr2_dq[0] (6) and cntrl0_ddr2_dq[3] (7) are not
allocated in the same banks
ERROR: cntrl0_ddr2_dq[1] (6) and cntrl0_ddr2_dq[3] (7) are not
allocated in the same banks
ERROR: cntrl0_ddr2_dq[2] (6) and cntrl0_ddr2_dq[3] (7) are not
allocated in the same banks
```

For example, SIO part - QDRII SRAM:

```
NET "qdr_q[0]" LOC = "K24" ; #Bank 19
NET "qdr_q[1]" LOC = "L24" ; #Bank 19
NET "qdr_q[2]" LOC = "L25" ; #Bank 19
NET "qdr_q[3]" LOC = "E29" ; #Bank 15
```

Assume `qdr_q[3]` and `qdr_q[2]` are allocated to pins of different banks, such as bank 15 and bank 19, respectively. The following error messages are printed:


```

ERROR: qdr_q[0] (19) and qdr_q[3] (15) are not allocated in the same
banks
ERROR: qdr_q[1] (19) and qdr_q[3] (15) are not allocated in the same
banks
ERROR: qdr_q[2] (19) and qdr_q[3] (15) are not allocated in the same
banks

```

These types of error messages are reported for each pair of signals of the same group, but are allocated to different banks.

- **Strobes vs. Data allocation for Virtex-4 FPGA DDR2 SDRAM SerDes designs.** Data (DQ) should be allocated within the same or one clock region above or below the corresponding strobe (DQS) clock region. This rule applies for Virtex-4 FPGA DDR2 SDRAM SerDes designs only. If not, an error message is displayed.

For example, the XC4VLX100-FF1148 Virtex-4 FPGA DDR2 SDRAM SerDes design has this pinout:

```

NET "cntrl0_ddr2_dq[0]" LOC = "F20" ; #Bank 1
NET "cntrl0_ddr2_dq[1]" LOC = "A15" ; #Bank 1
NET "cntrl0_ddr2_dq[2]" LOC = "B15" ; #Bank 1
NET "cntrl0_ddr2_dq[3]" LOC = "N19" ; #Bank 1
NET "cntrl0_ddr2_dqs[0]" LOC = "F13" ; #Bank 1

```

The clock region of cntrl0_ddr2_dq[0], cntrl0_ddr2_dq[1], and cntrl0_ddr2_dq[2] is CLOCKREGION_X1Y8. The clock region of cntrl0_ddr2_dq[3] is CLOCKREGION_X1Y5, while the clock region of cntrl0_ddr2_dqs[0] is CLOCKREGION_X1Y6. The allowed clock regions for dq[0] to dq[7] are X1Y5, X1Y6, and X1Y7. In this example, the data signals cntrl0_ddr2_dq[0], cntrl0_ddr2_dq[1], and cntrl0_ddr2_dq[2] violate the rule. The MIG tool outputs the following error messages for each signal that violates the clock region rule:

```

ERROR: cntrl0_ddr2_dq[0] (1) is not allocated within the clock region
boundary of cntrl0_ddr2_dqs[0] (1). (DQ should be in the same or one
above/below clock region of the corresponding DQS clock region).
ERROR: cntrl0_ddr2_dq[1] (1) is not allocated within the clock region
boundary of cntrl0_ddr2_dqs[0] (1). (DQ should be in the same or one
above/below clock region of the corresponding DQS clock region).
ERROR: cntrl0_ddr2_dq[2] (1) is not allocated within the clock region
boundary of cntrl0_ddr2_dqs[0] (1). (DQ should be in the same or one
above/below clock region of the corresponding DQS clock region).

```

- **Clock Capable I/Os for strobes/read clock.** Check for CC pins if Use CC for direct clocking is clicked. In this case, the strobe/read_clock signals should be allocated to the CC pins only. If not, an error message is displayed.

The error message format is "<signal_name> should be allocated to the CC Pins." For example, cntrl0_ddr2_dqs[0] is a strobe. Assume it is allocated to the K12 pin, which is not a clock capable I/O pin. The following error message is printed:

```

ERROR: cntrl0_ddr2_dqs[0] should be allocated to the CC Pins.

```

- **Absence of signals.** If one or more signal-pin pair is missing and/or commented in the given UCF against the selected inputs, the verification result indicates the absence of those signal-pin pairs as a warning.

The warning message format is "<signal_name> is forbidden in the given UCF against the selected inputs."

For example, assume the reference UCF has 8 bits (dq[0:7]), and the data width passed through PRJ is 16 bits. While checking, MIG verifies only 8 bits and reports the other expected bits as follows:

```
WARNING : cntrl0_ddr2_dq[8] is expected, but not present in the UCF.
WARNING : cntrl0_ddr2_dq[9] is expected, but not present in the UCF.
WARNING : cntrl0_ddr2_dq[10] is expected, but not present in the
UCF.
WARNING : cntrl0_ddr2_dq[11] is expected, but not present in the
UCF.
WARNING : cntrl0_ddr2_dq[12] is expected, but not present in the
UCF.
WARNING : cntrl0_ddr2_dq[13] is expected, but not present in the
UCF.
WARNING : cntrl0_ddr2_dq[14] is expected, but not present in the
UCF.
WARNING : cntrl0_ddr2_dq[15] is expected, but not present in the
UCF.
```

- **Bank selection.** If one or more banks are not selected and one or more pins from that (those) bank(s) is (are) used for some purpose, an error message is printed.

The error message format is "<signal_name> (<signal_group>) should not be allocated to bank <bank_number>. The rule is, it can only be moved within the bank(s) "<bank_numbers>" specified in the input mig.prj file for the <signal_group> group."

For example:

```
NET "cntrl0_ddr2_dqs[0]" LOC = "D12" ;#bank 6
```

Bank 6 is not selected for Data (as cntrl0_ddr2_dqs[0] from Data). Assume that cntrl0_ddr2_dqs[0], which belongs to the strobe group, is allocated to a pin belonging to bank 6. The following error message is printed:

```
ERROR: cntrl0_ddr2_dqs[0] (Strobe) should not be allocated to bank 6.
The rule is, it can only be moved within the bank(s)
"11,13,15,17,19,21" specified in the input mig.prj file for "Data"
group.
```

Spartan-3A FPGA DDR2 SDRAM 200 MHz Design

This page is displayed only for Spartan-3A FPGA designs. It provides links to XAPP458 [Ref 16] and the Spartan-3A FPGA DDR2 SDRAM 200 MHz reference design.

200 MHz Design Support

Implementing DDR2-400 Memory Interfaces in Spartan-3A FPGA's:

- DDR2-400 has been validated in hardware
- Documented in application notes with reference designs
- Additional bandwidth enables new applications and lower cost implementations of existing applications

Interface Details:

- 16-bit data width
- Spartan-3A FPGA - XC3S700A-SFG484C
- Memory Part - MT47H32M16BN-3 (CL=3)
- Uses MIG Controller with minor modifications
- All five timing budgets documented and pass

Please refer to the links below for application notes and reference design

- http://www.xilinx.com/prs_rls/2007/silicon_spart/0795_ddr2.htm
- http://www.xilinx.com/support/documentation/application_notes/xapp458.pdf
- http://www.xilinx.com/support/documentation/application_notes/xapp458.zip

UG086_c1_53_072108

Figure 1-73: Spartan-3A FPGA 200 MHz Design Support

Implementing MIG Designs in ISE GUI Mode

The MIG tool can be invoked from the project navigator of the ISE software as follows:

1. Launch the ISE software by selecting **Start → Xilinx ISE Design Suite 12.3 → ISE → Project Navigator**.
2. Create an ISE project:
 - a. Select **File → New Project**. The New Project Wizard appears.
 - b. Type the appropriate name in the Project Name field. Enter a directory path or browse to a location for the new project. A subdirectory is created with the Project Name entered automatically.
 - c. Select **HDL** for the Top-level Source Type and click **Next** to move to the device properties page.
 - d. The Xilinx part must be correctly set because it cannot be changed inside the MIG tool. Virtex-5, Virtex-4, and Spartan-3/Spartan-3E/Spartan-3A/3AN/3A DSP devices are supported. Select the part using **Device**, **Package**, and **Speed** in the Device Properties menu. Select the HDL using **Simulator** and **Preferred Language** in the Device Properties menu. Leave the default values in the remaining fields.
 - e. Click **Next** to proceed to the Create New Source window in the New Project Wizard.
 - f. Create new source as follows:
 - Click **New Source**, select the Source Type as **IP (CORE Generator & Architecture Wizard)**, and enter the appropriate File Name and Location in the Select Source Type menu. Click **Next**.
 - The Select IP menu lists out the various IPs that are supported. The View by Function tab to the left shows the available cores organized into folders. Choose the MIG tool by selecting **Memories & Storage Elements → Memory Interface Generator → MIG**. Click **Next**.
 - In the Summary menu, click **Finish**. The software returns to the Create New Source menu.
 - Click **Finish** in the New Project Wizard. The XCO file is created and added to the project.

Note: New Source can be created in step f) or by creating the project by selecting **Project → New Source**.
 - g. Click **Next**. Optionally, add existing source files to the project in the Add Existing Sources page.
 - h. Click **Next** to display the Project Summary page.
 - i. Click **Finish** to create the project.
 - j. Upon creating the project, the ISE software invokes the MIG tool. Enter the name of the module to be generated in the Component Name text box. The component name provided in the MIG tool should be the same as that used in the Project Navigation New Source menu. After entering all the parameters in the GUI, click **Generate**. This generates the module files in a directory with the same name as the component name in the ISE project directory.
 - k. After generating the design, click the **Finish** button. This closes the MIG tool.

1. The MIG tool generates the `example_design` and `user_design`. The `example_design` includes the synthesizable test bench, while `user_design` does not include any test bench modules.
3. If New Source is not created in the Create New Source menu in step f), new source can be created by selecting **Project** → **New Source**. The steps required to create a new source are the same as those listed in step f).
4. Upon closing the MIG tool, the XCO file is added to the ISE project. Create a top-level HDL file (`.v` or `.vhd`) that includes the instance of `<top_module>` of the MIG-generated user design. After creating the top-level HDL file, add it to an ISE project by selecting **Project** → **Add Source**. Upon adding the top-level HDL file to the ISE project, the MIG RTL source files (`user_design/rtl`) are added to the ISE project. Only `user_design` files are added to an ISE project.

For example, if a MIG design is generated with the module name entered in the GUI (such as “`test_case`”), create a top-level HDL file by including the `<top_module>` HDL module (i.e., `test_case.v/vhd`) instance of `user_design`. If the top-level HDL file is called `inst_test_case.v/.vhd`, add the `inst_test_case.v/.vhd` module to the ISE project by selecting **Project** → **Add Source**.
5. The UCF file (`user_design/par`) is also added to the ISE project. The RTL source files and the UCF file that are added to the project are not shown in the Files Tab window.
6. Default synthesis and implementation build options are used. These options can be set as required.
7. Click **Process** → **Implement Top Module**. The software runs through synthesis, MAP, PAR, and TRCE.

If the design is generated using the CORE Generator tool or batch mode, the design can be run in the ISE software GUI using `create_ise.bat`. This script file is included in both the `example_design/par` and `user_design/par` directories of the generated MIG design. Running the `create_ise.bat` script generates an ISE project that incorporates the generated MIG design. If the script is run from the `example_design/par` directory, the ISE project includes the `example_design`. If the script is run from the `user_design/par` directory, the ISE project includes the `user_design`. The `create_ise.bat` file calls the `set_ise_prop.txt` file. This file is also located in the selected `par` directory. The file includes standard `xtclsh` commands that pull the MIG RTL source files (`example_design/rtl` or `user_design/rtl`) into an ISE project and set the required synthesis and implementation build options. After completion of the `create_ise.bat` script, a `test_ise` file is created that can be opened in the ISE software. The synthesis and implementation build options set by `create_ise.bat` are recommended. No other build options have been tested and cannot be supported. For detailed information on the options set, refer to the Development System Reference Guide and the XST User Guide in the Xilinx ISE 12.3 Design Suite Software Manuals and Help – PDF Collection at <http://www.xilinx.com/support/documentation/index.htm>.

Section II: Virtex-4 FPGA to Memory Interfaces

Chapter 2, “Implementing DDR SDRAM Controllers”

Chapter 3, “Implementing DDR2 SDRAM Controllers”

Chapter 4, “Implementing QDR II SRAM Controllers”

Chapter 5, “Implementing DDR II SRAM Controllers”

Chapter 6, “Implementing RDRAM II Controllers”

Implementing DDR SDRAM Controllers

This chapter describes how to implement DDR SDRAM interfaces for Virtex®-4 FPGAs generated by MIG. This design is based on XAPP709 [\[Ref 21\]](#).

Feature Summary

Supported Features

The DDR SDRAM controller design supports the following:

- Burst lengths of two, four, and eight
- Sequential and interleaved burst types
- CAS latencies of 2, 2.5, and 3
- Precharge based on the row to be accessed or the precharge command given by the user
- Registered DIMMs, unbuffered DIMMs, and SODIMMs
- Different memories (density/speed)
- Auto refresh
- Linear addressing
- VHDL and Verilog
- With and without a testbench
- With and without a DCM
- Data mask
- System clock, differential and single-ended

The supported features are described in more detail in [“Architecture.”](#)

Design Frequency Ranges

Table 2-1: Design Frequency Range in MHz

Memory	FPGA Speed Grade					
	-10		-11		-12	
	Min	Max	Min	Max	Min	Max
Component	77	165	77	170	77	175
DIMM	77	165	77	170	77	175

Unsupported Features

- Dual Rank DIMMs
- Deep Memory
- Auto Precharge
- Bank Management
- Multi Controller

Architecture

Interface Model

DDR SDRAM interfaces are source-synchronous and double data rate. They transfer data on both edges of the clock cycle. A memory interface can be modularly represented as shown in Figure 2-1. A modular interface has many advantages. It allows designs to be ported easily and also makes it possible to share parts of the design across different types of memory interfaces.

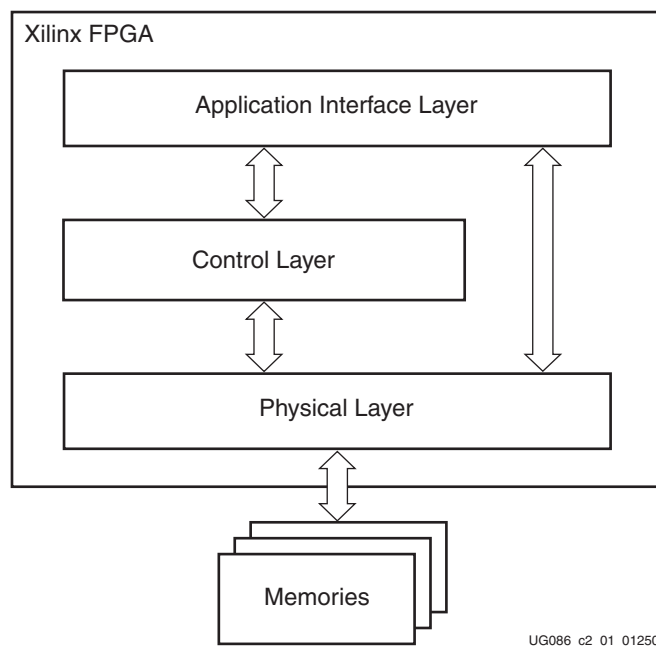


Figure 2-1: Modular Memory Interface Representation

Implemented Features

This section provides details on the supported features of the DDR SDRAM controller. Based on user selection, the tool generates a parameter file, which is used to set various features of the memory and to generate the control signals accordingly.

The parameter file provides the settings for burst length, CAS latency, sequential or interleaved addressing, number of row address bits, number of column address bits, bank address, and the timing parameters based on the frequency and the speed grade selected from the GUI. The DDR SDRAM controller uses these parameters directly.

The user issues a command through the FIFOs (user_interface). The user address (i.e., APP_AF_ADDR that is written into the FIFO as shown in [Figure 2-11](#) or [Figure 2-13](#)) is decoded in a sequence. The total width of the Read/Write Address FIFO (rd_wr_addr_fifo) is 36 bits. The user writes the column address (least-significant bits), row address, bank address, chip address [31:0], and the command to be issued [34:32]. The 36th bit (APP_AF_ADDR[35]) is reserved by the design to manipulate whether or not the row to be accessed is same as that of the previous row. The APP_AF_ADDR[35] input is a don't care for the design. The controller takes the row and column address bits based on the selected component. The [“Write Interface”](#) and [“Read Interface”](#) sections provide further details on how to issue the write and read commands, respectively.

[Table 2-2](#) lists the commands that the user can issue through the User interface. If the user issues an invalid command, the state of the controller is undefined. The functionality is not guaranteed when an invalid command is issued.

Table 2-2: User Commands

Command	APP_AF_ADDR[34:32]
READ	101
WRITE	100
REFRESH	001
PRECHARGE	010

Burst Length

Bits M0:M3 of the Mode Register define the burst length and burst type. Read and write accesses to the DDR SDRAM are burst-oriented. The burst length is programmable to either 2, 4, or 8 from the GUI. It determines the maximum number of column locations accessed for a given READ or WRITE command.

The DDR SDRAM ddr_controller module implements the user-selected burst length from MIG.

CAS Latency

Bits M4:M6 of the Mode Register define the CAS latency (CL). CL is the delay in clock cycles between the registration of a READ command and the availability of the first bit of output data. CL can be set to 2, 2.5, or 3 clocks from the GUI.

The controller supports CAS latencies of 2, 2.5, and 3.

During read data operations, the generation of the read_en signal varies according to the CL in the ddr_controller module.

Registered DIMMs

DDR SDRAM supports registered DIMMs. This feature is implemented in the ddr_controller module. For registered DIMMs, the READ and WRITE commands and address have one additional clock latency than unbuffered DIMMs. Also for registered DIMMs, the controller delays the data and the strobe by one clock because the command has one clock latency due to the register in the DIMM.

Unbuffered DIMMs and SODIMMs

DDR SDRAM design supports unbuffered DIMMs and SODIMMs. Unbuffered DIMMs are normal DIMMs where a set of components are used to get a particular configuration. SODIMMs vary from the unbuffered DIMMs only by package type. They are functionally the same.

Precharge

The PRECHARGE command is issued before the next read or write is issued for a different row, but not if the read or write is in the same row. The PRECHARGE command checks the row address, bank address, and chip selects. The DDR Virtex-4 FPGA controller issues a PRECHARGE command if there is a change in any address where a read or write command is to be issued. The AUTO PRECHARGE command via the A10 column bit is not supported.

Auto Refresh

The DDR SDRAM controller issues AUTO REFRESH commands at specified intervals for the memory to refresh the charge required to retain the data in the memory. The user can also issue a REFRESH command through the user interface by setting bits 34, 33, and 32 of the `app_af_addr` signal in the `user_interface` module to `3'b001`. If there is a refresh request while during an ongoing read or write burst, the controller issues a REFRESH command after completing the current read or write burst command.

Linear Addressing

The DDR SDRAM controller supports linear addressing. Linear addressing refers to the way the user provides the address of the memory to be accessed. For Virtex-4 FPGA DDR SDRAM controllers, the user provides the address information through the `app_af_addr` signal. As the densities of the memory devices vary, the number of column address bits and row address bits also changes. In any case, the row address bits in the `app_af_addr` signal always start from the next-higher bit, where the column address ends. This feature increases the number of devices that can be supported with the design.

Different Memories (Density/Speed)

This feature supports different memory components and DIMMs. The component densities can vary from 128 Mb to 1 Gb, and the DIMM densities can vary from 128 MB to 1 GB. Higher densities can be created using the "Create new memory part" feature of MIG. The maximum supported column address is 13 bits, the maximum row address is 15 bits, and the maximum bank address is 2 bits. To support this feature, the design can decode write and read addresses from the user in the DDR SDRAM controller module. The user address consists of row, column, bank, and chip addresses, and the user command. Apart from the address decoding, timing parameters vary according to the density and speed grade.

Data Mask

MIG supports a data mask option. If this option is checked in the GUI, MIG generates a design with data mask pins. This option can be chosen if the selected part has data masking.

System Clock

MIG supports a differential or single-ended system clock option. Based on the selection in the GUI, input system clocks and IDELAY clocks are differential or single-ended.

Table 2-3 lists the timing parameters for components, and Table 2-4 lists the timing parameters for DIMMs.

Table 2-3: Timing Parameters for Components

Parameter	Description		Micron 128 Mb		Micron 256 Mb		Micron 512 Mb		Micron 1 Gb	
			-5	-75	-5	-75	-5	-75	-5	-75
T _{CK}	Clock Cycle Time	CL = 3	5 ns	NA	5 ns	NA	5 ns	NA	5 ns	NA
		CL = 2.5	6 ns	7.5 ns	6 ns	7.5 ns	6 ns	7.5 ns	6 ns	7.5 ns
		CL = 2	7.5 ns	10 ns	7.5 ns	10 ns	7.5 ns	10 ns	7.5 ns	10 ns
T _{MRD}	LOAD MODE Command Cycle Time		10 ns	15 ns	10 ns	15 ns	10 ns	15 ns	10 ns	15 ns
T _{RP}	PRECHARGE Command Period		15 ns	20 ns	15 ns	20 ns	15 ns	20 ns	15 ns	20 ns
T _{RFC}	REFRESH Time		70 ns	75 ns	70 ns	75 ns	70 ns	75 ns	120 ns	120 ns
T _{RCD}	ACTIVE to READ or WRITE Delay		15 ns	20 ns	15 ns	20 ns	15 ns	20 ns	15 ns	20 ns
T _{RAS}	ACTIVE to PRECHARGE Command		40 ns	40 ns	40 ns	40 ns	40 ns	40 ns	40 ns	40 ns
T _{RC}	ACTIVE to ACTIVE (Same Bank) Command		55 ns	65 ns	55 ns	65 ns	55 ns	65 ns	55 ns	65 ns
T _{WTR}	WRITE to READ Command Delay		2 * T _{CK}	1 * T _{CK}	2 * T _{CK}	1 * T _{CK}	2 * T _{CK}	1 * T _{CK}	2 * T _{CK}	1 * T _{CK}
T _{WR}	WRITE Recovery Time		15 ns	15 ns	15 ns	15 ns	15 ns	15 ns	15 ns	15 ns

Table 2-4: Timing Parameters for DIMMs (Unbuffered and Registered)

Parameter	Description		Micron 128 MB	Micron 256 MB	Micron 512 MB	Micron 1 GB
			-40	-40	-40	-40
T _{CK}	Clock Cycle Time	CL = 3	5 ns	5 ns	5 ns	5 ns
		CL = 2.5	6 ns	6 ns	6 ns	6 ns
		CL = 2	7.5 ns	7.5 ns	7.5 ns	7.5 ns
T _{MRD}	LOAD MODE Command Cycle Time		10 ns	10 ns	10 ns	10 ns
T _{RP}	PRECHARGE Command Period		15 ns	15 ns	15 ns	15 ns
T _{RFC}	REFRESH Time		70 ns	70 ns	70 ns	70 ns

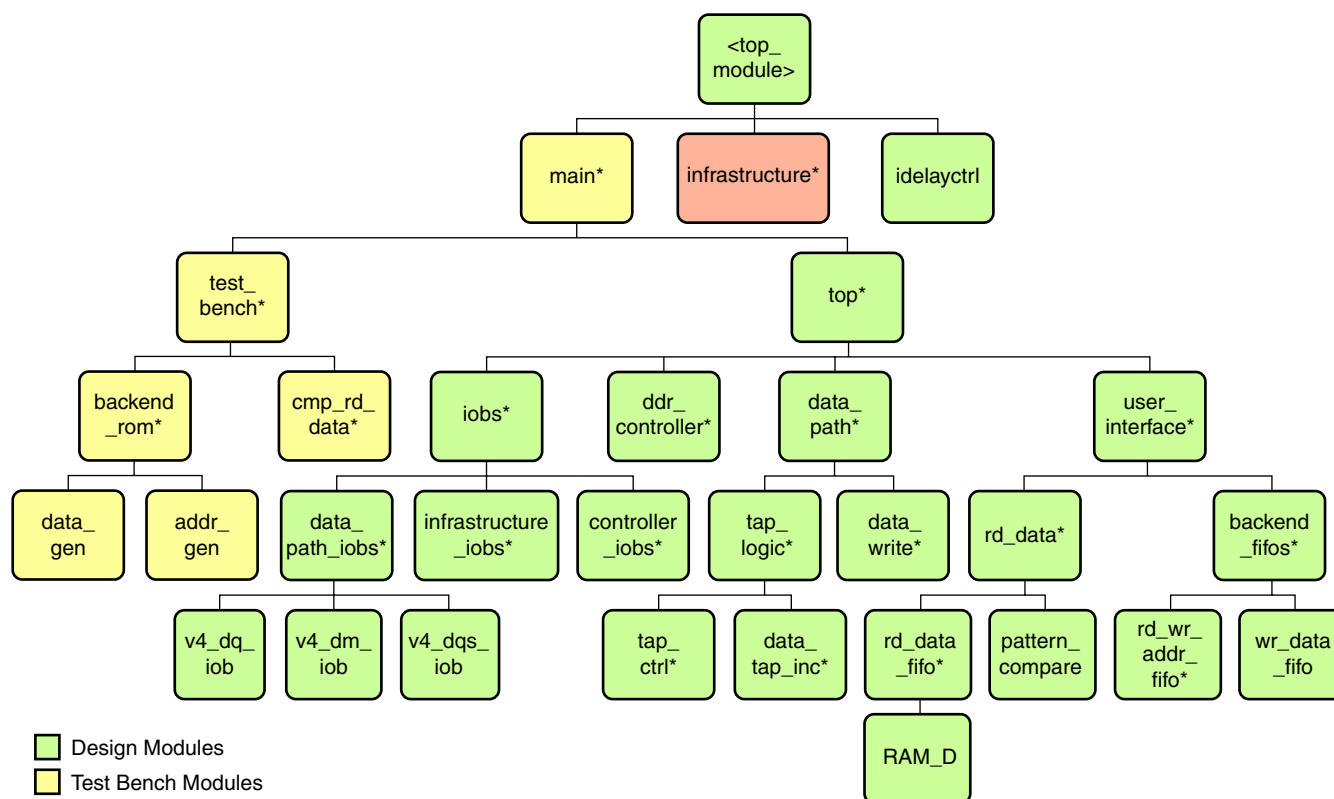
Table 2-4: Timing Parameters for DIMMs (Unbuffered and Registered) (Cont'd)

Parameter	Description	Micron 128 MB	Micron 256 MB	Micron 512 MB	Micron 1 GB
		-40	-40	-40	-40
T_{RCD}	ACTIVE to READ or WRITE Delay	15 ns	15 ns	15 ns	15 ns
T_{RAS}	ACTIVE to PRECHARGE Command	40 ns	40 ns	40 ns	40 ns
T_{RC}	ACTIVE to ACTIVE (Same Bank) Command	55 ns	55 ns	55 ns	55 ns
T_{WTR}	WRITE to READ Command Delay	$2 * T_{CK}$	$2 * T_{CK}$	$2 * T_{CK}$	$2 * T_{CK}$
T_{WR}	WRITE Recovery Time	15 ns	15 ns	15 ns	15 ns

Note: For the latest timing information, refer to the vendor memory data sheets.

Hierarchy

Figure 2-2 shows the hierarchical structure of the DDR SDRAM design generated by MIG with a testbench and a DCM. The physical and control layers are clearly separated in this figure. MIG generates the entire DDR SDRAM controller as shown in this hierarchy, including the testbench. MIG also generates a parameter file where all user input parameters or some parameters used internally by the design are defined.



Note: A block with a * has a parameter file included.

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Figure 2-2: Hierarchical Structure of the Virtex-4 FPGA DDR SDRAM Design

The modules are classified as follows:

- Design modules
- Testbench modules
- Clocks and reset generation modules

There is a parameter file generated with the design that has all the user input and design parameters selected from MIG.

MIG can generate four different DDR SDRAM designs:

- With a testbench and a DCM
- Without a testbench and with a DCM
- With a testbench and without a DCM
- Without a testbench and without a DCM

When the testbench is not generated by MIG, the top-level module has the user interface signals. The list of user interface signals is provided in Table 2-8.

Design clocks and resets are generated in the infrastructure module. The DCM clock is instantiated in the infrastructure module for designs with a DCM. The inputs to this module are the differential design clock and a 200 MHz differential clock for the IDELAYCTRL module. A user reset is also input to this module. Using the input clocks and reset signals, the system clocks and the system reset are generated in this module, which is used in the design.

The DCM primitive is not instantiated in this module if the **Use DCM** option is unchecked. So, the system operates on the user-provided clocks. The system reset is generated in the infrastructure module using the dcm_lock input signal.

MIG Tool Design Options

MIG provides various options to generate the design with or without a testbench or with or without a DCM. This section provides detailed descriptions of the type of design generated by the user using various options. [Figure 2-3, page 101](#) and [Figure 2-4, page 102](#) represent the system clock of differential. For more information on clocking structure refer to [“Clocking Scheme,” page 110](#).

MIG outputs both an example_design and a user_design. The MIG-generated example_design includes the entire memory controller design along with a synthesized testbench (example user application). This testbench generates sample writes and reads and then uses comparison logic to verify that the data patterns written are the same as those received. This example_design can be used to test functionality both in simulation and in hardware. The user_design includes the memory controller design only. This design allows users to connect the MIG memory controller design to a user developed testbench (user application). Refer to [Table 2-8, page 112](#) for user interface signals, the [“User Interface Accesses,” page 114](#) for timing restriction on user interface signals, and [Figure 2-11, page 116](#) for write interface timing.

[Figure 2-3](#) shows a DDR SDRAM controller block diagram representation of the top-level module for a design with a DCM and a testbench. The sys_clk_p and sys_clk_n signals are differential input system clocks. The DCM clock is instantiated in the infrastructure module that generates the required design clocks. The differential clk200_p and clk200_n pair are used for the idelay_ctrl element. The active-Low system reset signal is sys_reset_in_n. All design resets are gated by the dcm_lock signal. Memory device signals are prepended with the controller number. For example, ddr_ras_n appears as cntrl0_ddr_ras_n.

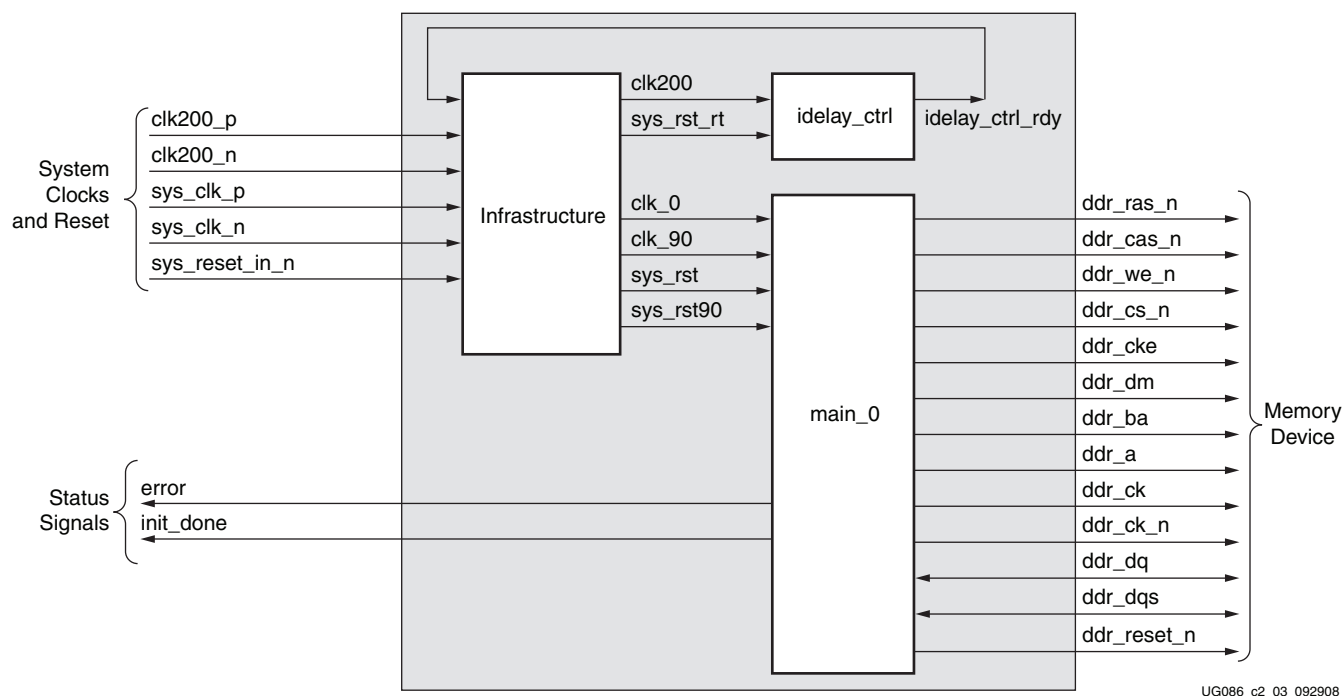


Figure 2-3: Top-Level Block Diagram of the DDR SDRAM Design with a DCM and a Testbench

The error output signal indicates whether the case passes or fails. The testbench module does writes and reads, and also compares the read data with the written data. The error signal is driven High on data mismatches.

The init_done signal indicates the completion of initialization and calibration of the design.

All the signals listed under the Memory Device category do not necessarily appear in the top-level block port list. The port list varies according to the memory type selected, such as a component or a registered DIMM. For example, a component does not have the ddr_reset_n signal.

[Figure 2-4](#) shows a block diagram representation of the top-level module for a design with a DCM but without a testbench.

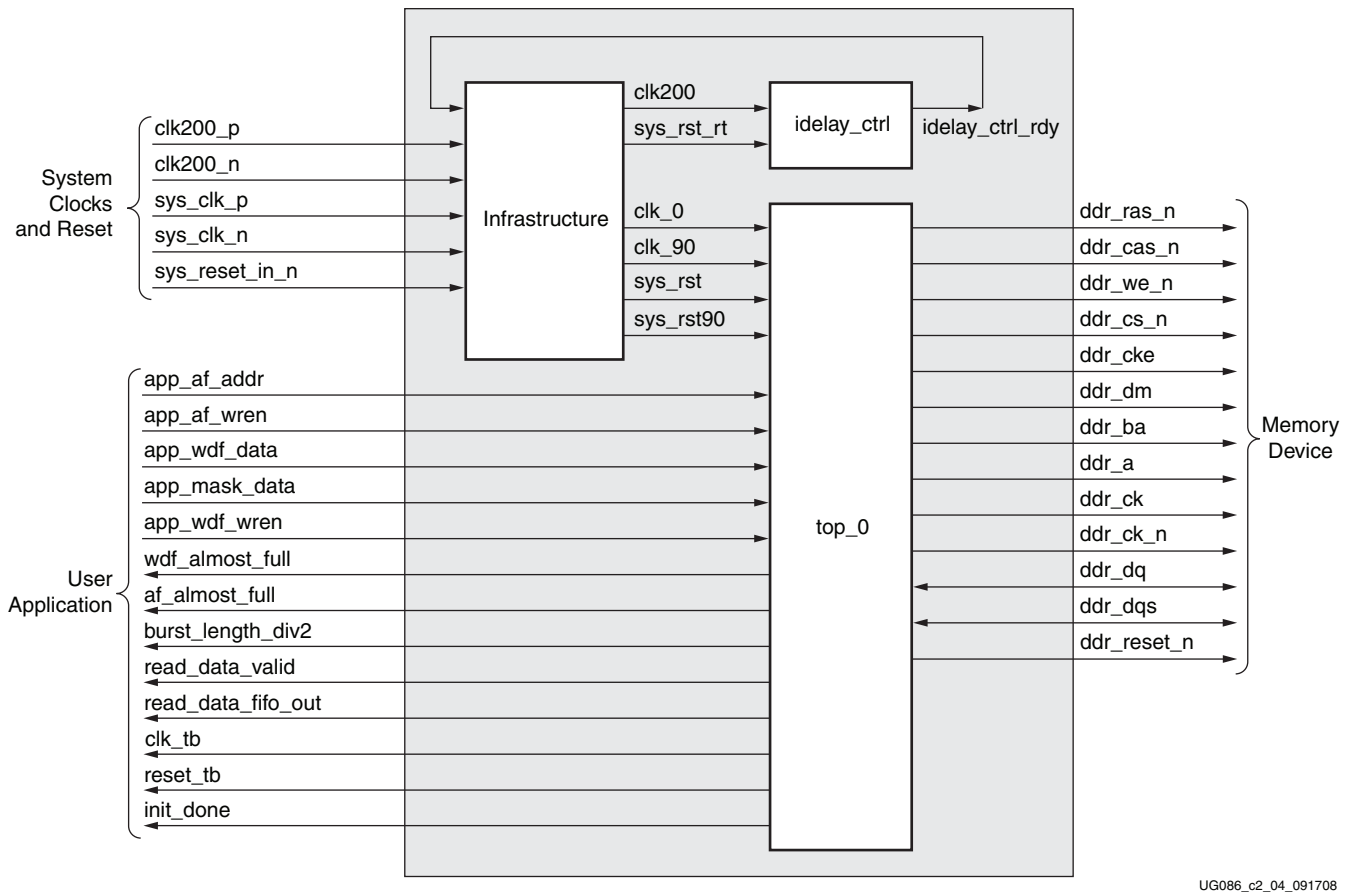


Figure 2-4: Top-Level Block Diagram of the DDR SDRAM Design with a DCM but without a Testbench

The DCM clock module is instantiated in the infrastructure module. Using the differential `sys_clk_p` and `sys_clk_n` signals, the internal DCM generates all the required clocks for the design. The differential `clk200_p` and `clk200_n` are used by the `idelay_ctrl` element. The active-Low system reset signal is `sys_reset_in_n`. All design resets are generated using the input reset signal gated by the `dcm_lock` signal.

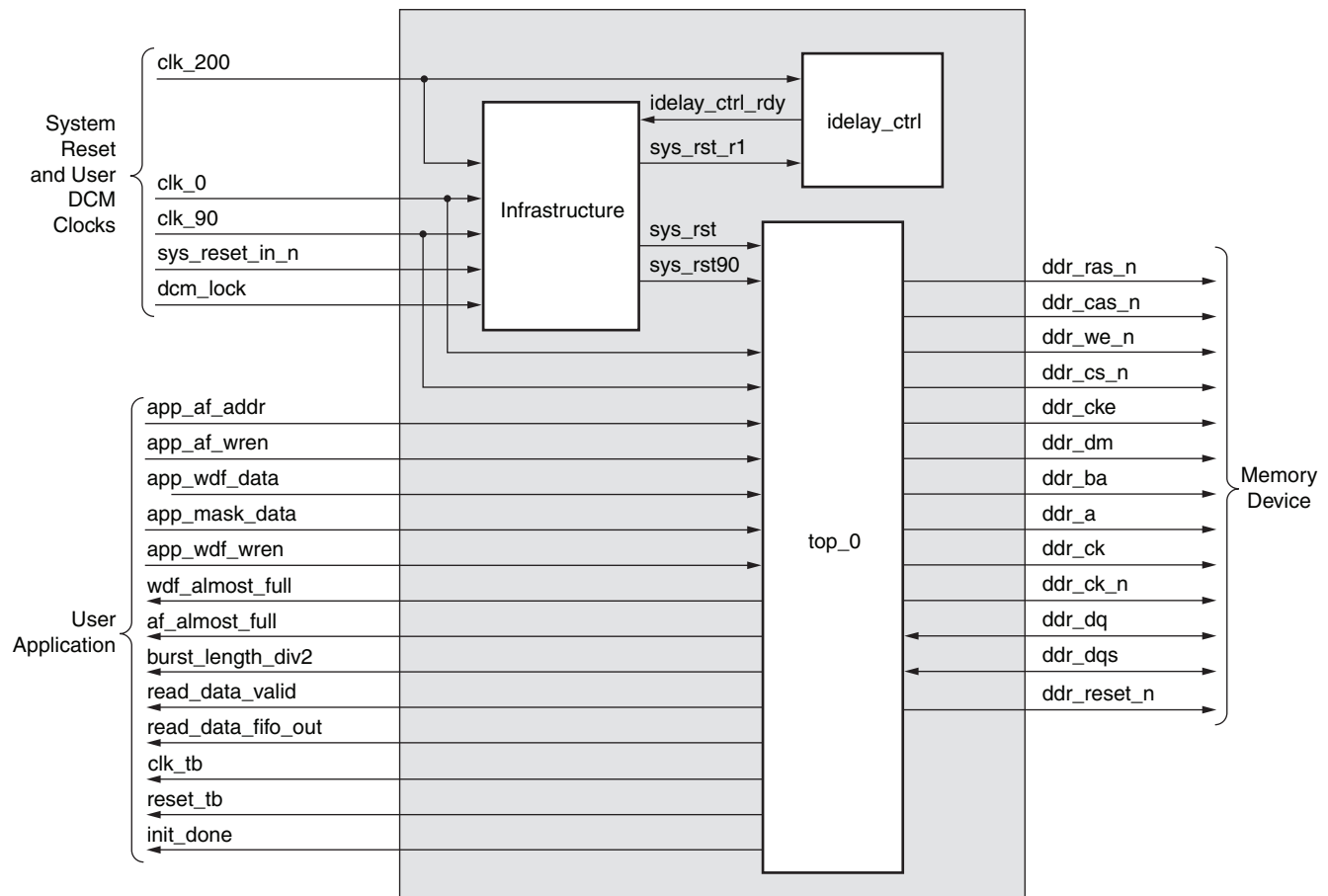
The `init_done` signal indicates the completion of initialization and calibration of the design.

The application's user interface signals are listed in Figure 2-4. The design provides the `clk_tb` and `reset_tb` signals to the user to synchronize with the design.

Figure 2-5 shows a block diagram representation of the top-level module for a design without a DCM or a testbench. There is no DCM instantiated in the infrastructure module. All the clocks and dcm_lock should be given as inputs from the user interface. Resets are generated using the sys_reset_in_n signal gated by the dcm_lock signal in the infrastructure module. Clk200 is used by the idelay_ctrl element. All the clocks should be single-ended. The user application must have a DCM primitive instantiated in the design.

The init_done signal indicates the completion of initialization and calibration of the design.

The user interface signals are also listed in the <top_module> module. The design provides the clk_tb and reset_tb signals to the user to synchronize with the design.



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Figure 2-5: Top-Level Block Diagram of the DDR SDRAM Design without a DCM or a Testbench

Figure 2-6 shows a block diagram representation of the top-level module for a design with a testbench but without a DCM. The user should provide all the clocks and the dcm_lock signal. These clocks should be single-ended. The active-Low system reset signal is sys_reset_in_n. All design resets are gated by the dcm_lock signal.

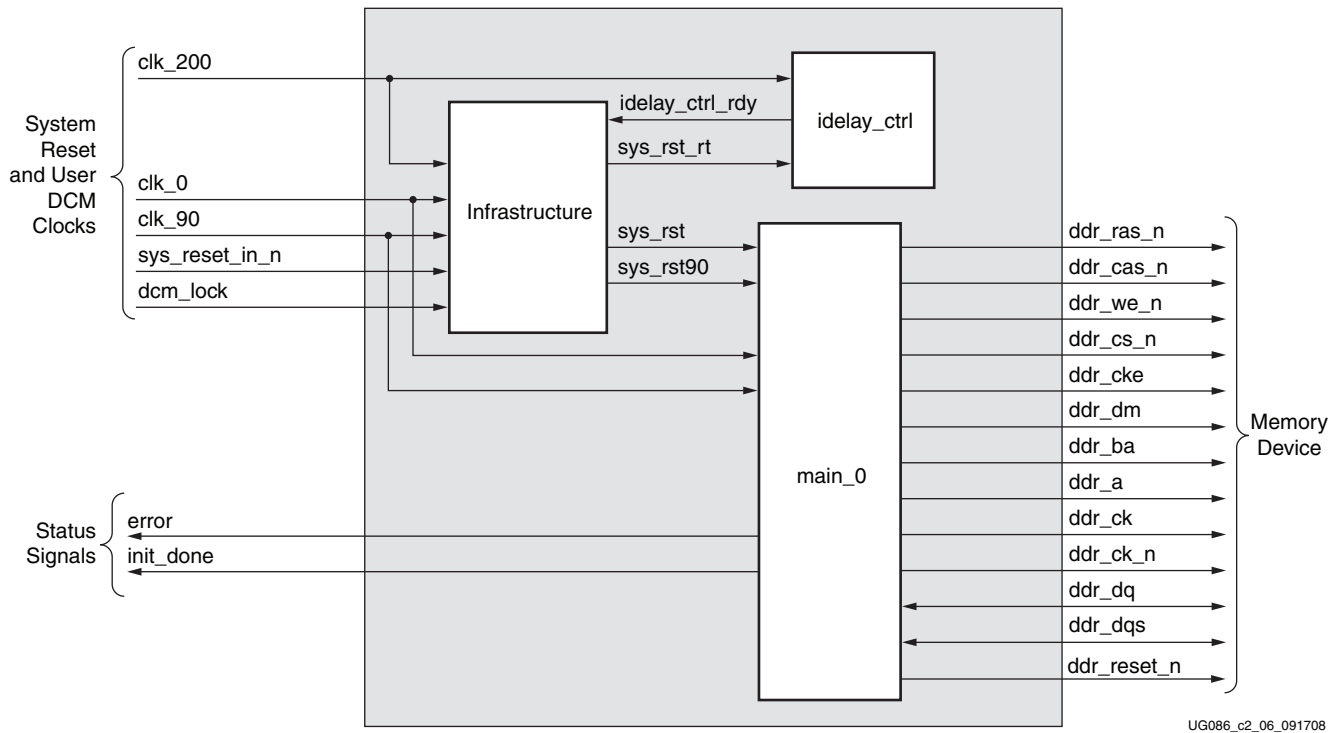


Figure 2-6: Top-Level Block Diagram of the DDR SDRAM Design with a Testbench but without a DCM

The error output signal indicates whether the case passes or fails. The testbench module does writes and reads, and also compares the read data with the written data. The ERROR signal is driven High on data mismatches. The init_done signal indicates the completion of initialization and calibration of the design.

Figure 2-7 shows the expanded block diagram of the design. The top module is expanded to show various internal blocks. The functions of these blocks are explained in the subsections following the figure.

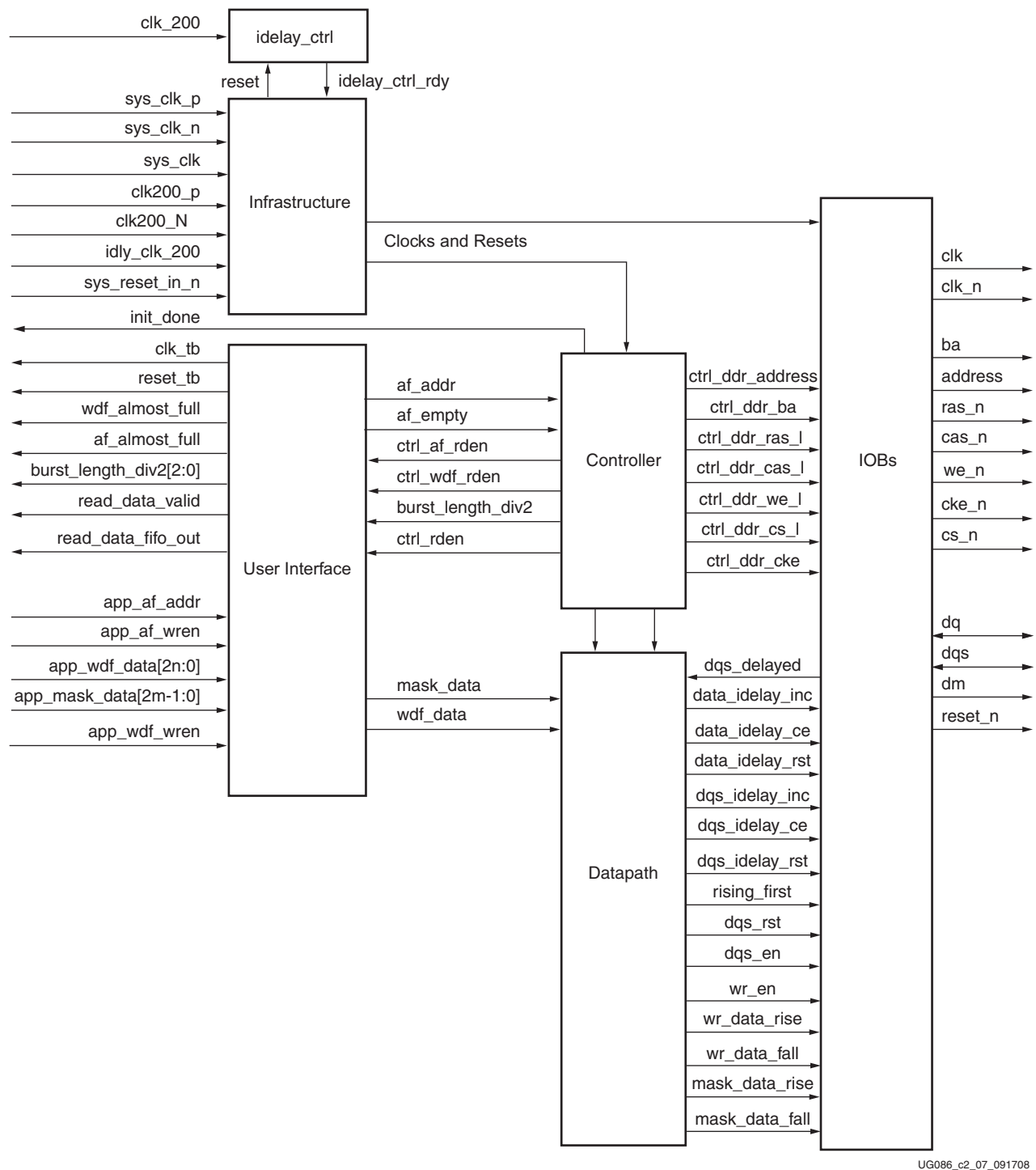


Figure 2-7: Expanded DDR SDRAM Controller Block Diagram

Controller

The DDR SDRAM controller initializes the memory, accepts and decodes user commands, and generates READ, WRITE, and REFRESH commands. The DDR SDRAM controller also generates signals for other modules. The memory is initialized and powered-up using a defined process. The controller state machine handles the initialization process upon power-up. If the AUTO REFRESH command is to be issued between any user read or write commands, then the read or write command is suspended until the `ref_done` flag is deasserted.

Datapath

This module transmits data to the memories. Its major functions include storing the write data and calculating the tap value for the read datapath. The `data_write` and `data_path_IOBs` modules do the actual write functions. The `Idelay_ctrl`, `tap_ctrl` and `data_tap_inc` modules do the calibration.

User Interface

This module stores write data in its Write Data FIFO (`wr_data_fifo`), stores write and read addresses in its Read/Write Address FIFO (`rd_wr_addr_fifo`), and stores received read data from memory in its Read Data FIFO (`rd_data_fifo`). The width of the Write Data FIFO is twice the data width and mask width of the memory. For example, for a 16-bit width, the width of the FIFO is 36 because the data width is 32 and the mask width is 4. The `rd_wr_addr_fifo` and `wr_data_fifo` modules store the data and address in block RAMs. The `rd_data_fifo` module captures the data in the LUT-based RAMs.

The FIFOs are built using FIFO16 primitives in the `rd_wr_addr_fifo`, `wr_data_fifo_16`, and `wr_data_fifo_8` modules. FIFO16 has two FIFO threshold attributes, `ALMOST_EMPTY_OFFSET` and `ALMOST_FULL_OFFSET`, that are set to 7 and F, respectively, in the RTL by default. These values can be altered to match the application. For valid FIFO threshold offset values, refer to UG070 [Ref 7].

The controller also generates user commands, such as READ and WRITE.

The `pattern_compare` module registers the delay between the command and the data received from the IOBs. This delay is then applied to the `Rden` signal generated from the `ddr_controller` module during the actual read to register the valid data in the internal FIFOs.

Test Bench

The MIG tool generates two RTL folders, `example_design` and `user_design`. The `example_design` folder includes the synthesizable test bench, while `user_design` does not include the test bench modules. The MIG test bench performs eight write commands and eight read commands in an alternating fashion. The number of words in a write command depends on the burst length. For a burst length of 4, the test bench writes a total of 32 data words for all eight write commands (16 rise data words and 16 fall data words). For a burst length of 8, the test bench writes a total of 64 data words. It writes the data pattern of FF, 00, AA, 55, 55 AA, 99, 66 in a sequence of which FF, AA, 55, and 99 are rise data words and 00, 55, AA, and 66 are fall data words for an 8-bit design. The falling edge data is the complement of the rising edge data. For a burst length of 4, the data sequence for the first write command is FF, 00, AA, 55, and the data sequence for the second write command is 55, AA, 99, 66. For a burst length of 8, the data pattern for the first write command is FF, 00, AA, 55, 55 AA, 99, 66 and the same pattern is repeated for all the remaining write commands. This data pattern is repeated in the same order based on the number of data

words written. For data widths greater than 8, the same data pattern is concatenated for the other bits. For a 32-bit design and a burst length of 8, the data pattern for the first write command is FFFFFFFF, 00000000, AAAAAAAAAA, 55555555, 55555555, AAAAAAAAAA, 99999999, 66666666.

Address generation logic generates eight different addresses for eight write commands. The same eight address locations are repeated for the following eight read commands. The read commands are performed at the same locations where the data is written. There are total of 32 different address locations for 32 write commands, and the same address locations are generated for 32 read commands. Upon completion of a total of 64 commands, including both writes and reads (eight writes and eight reads repeated four times), address generation rolls back to the first address of the first write command and the same address locations are repeated. The MIG test bench exercises only a certain memory area. The address is formed such that all address bits are exercised. During writes, a new address is generated for every burst operation on the column boundary.

During reads, comparison logic compares the read pattern with the pattern written, i.e., the FF, 00, AA, 55, 55 AA, 99, 66 pattern. For example, for an 8-bit design of burst length 4, the data written for a single write command is FF, 00, AA, 55. During reads, the read pattern is compared with the FF, 00, AA, 55 pattern. Based on a comparison of the data, a status signal error is generated. If the data read back is the same as the data written, the error signal is 0, otherwise it is 1.

Infrastructure

The infrastructure module generates the FPGA clock and reset signals. When differential clocking is used, sys_clk_p, sys_clk_n, clk_200_p, and clk_200_n signals appear. When single-ended clocking is used, sys_clk and idly_clk_200 signals appear. In addition, clocks are available for design use and a 200 MHz clock is provided for the idelayctrl primitive. Differential and single-ended clocks are passed through buffers before connecting to a DCM. For differential clocking, the output of the sys_clk_p/sys_clk_n buffer is single-ended and is provided to the DCM input. Likewise, for single-ended clocking, sys_clk is passed through a buffer and its output is provided to the DCM input. The clock outputs of the DCM are clk_0 and clk_90. After the DCM is locked, the design is in the reset state for at least 25 clocks. The infrastructure module also generates all of the reset signals required for the design.

Idelay_ctrl

This module instantiates the IDELAYCTRL primitive of the Virtex-4 FPGA. The IDELAYCTRL primitive is used to continuously calibrate the individual delay elements in its region to reduce the effect of process, temperature, and voltage variations. A 200 MHz clock has to be fed to this primitive.

The MIG tool instantiates the required number of IDELAYCTRLs in the RTL and uses the LOC constraints in the UCF file to fix their locations. The number of IDELAYCTRLs is defined by the IDELAYCTRL_NUM parameter in the idelay_ctrl module. In the RTL, IDELAY_CTRL_RDY is generated by doing a logical AND of the RDY signals of every IDELAYCTRL block.

IDELAYCTRL LOC constraints should be checked in the following cases:

- The MIG design is used with other IP cores or user designs that also require the use of IDELAYCTRL and IDELAYs.

- Previous ISE® software releases 8.2.03i and 9.1i had an issue with IDELAYCTRL block replication or trimming. When using these revisions of the ISE software, the user must instantiate and constrain the location of each IDELAYCTRL individually.

See UG070 [Ref 7] for more information on the requirements of IDELAYCTRL placement.

IOBS Module

All DDR SDRAM address, control, and data signals are transmitted and received in the through the input and output buffers.

DDR SDRAM Initialization and Calibration

DDR memory is initialized through a specified sequence as shown in [Figure 2-8](#). The controller starts the memory initialization at power up itself. Following the initialization, the relationship between the data and the FPGA clock is calculated using the tap_logic. The controller issues a dummy write command and a dummy read command to the memory and compares read data with the fixed pattern. During dummy reads, the tap_logic module calibrates and delays the data to center-align with the FPGA clock. The sel_done port in the tap_logic module indicates the completion of the per-bit calibration. XAPP701 [Ref 18] provides more information about the calibration architecture.

After the per-bit calibration is done, the controller does a read enable calibration. This calibration is used to determine the delay from read command to read data at rd_data_fifo. The delay between read command and read data is affected by the CAS latency parameters, the PCB traces, and the I/O buffer delays. Read enable calibration is used to generate a write enable to rd_data_fifo so that valid data is registered. Controller writes a known fixed pattern and reads back the data from memory. The read data is compared against the known fixed pattern. The comp_done port in rd_data module indicates the completion of the read enable calibration.

The init_done port indicates the completion of both per-bit calibration and read enable calibration. After initialization and calibration is done, the controller can start issuing user commands to the memory.

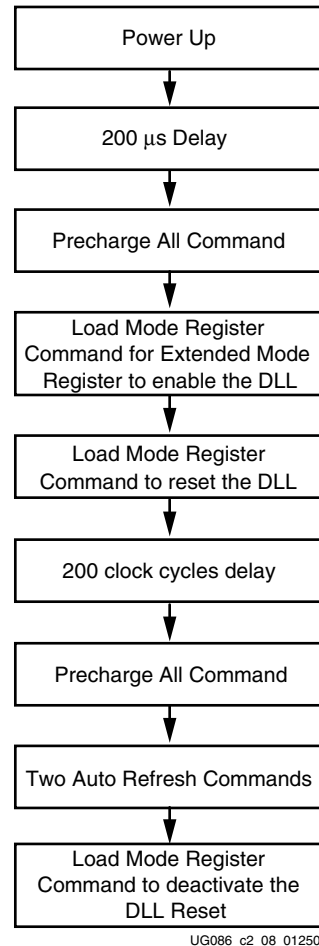


Figure 2-8: DDR Memory Initialization Sequence

Clocking Scheme

Figure 2-9, page 111 shows the clocking scheme for this design. Global and local clock resources are used.

The global clock resources consist of a DCM, two global clock buffers (BUFG) on DCM output clocks, and one BUFG for clk_200. The local clock resources consist of regional I/O clock networks (BUFIO). The global clock architecture is discussed in this section.

The MIG tool allows the user to customize the design such that the DCM is not included. In this case, clk_0, clk_90 and IDELAYCTRL clock clk_200 must be supplied by the user.

Global Clock Architecture

The user must supply two input clocks to the design:

- A system clock running at the target frequency for the memory
- A 200 MHz clock for the IDELAYCTRL blocks.

These clocks can be either single-ended or differential. Users can select the single-ended or differential clock input option from the MIG GUI. Differential clocks are connected to the IBUFGDS and the single-ended clock is connected to IBUFG.

The system clock from the output of the IBUFGDS or the IBUFG is connected to the DCM to generate the various clocks used by the memory interface logic.

The clk200 output of the IBUFGDS or the IBUFG is connected to the BUFG. The output of the BUFG is used for IDELAY IOB delay blocks for aligning read capture data.

The DCM generates two separate synchronous clocks for use in the design. This is shown in Table 2-5 and Figure 2-9, page 111. The clock structure is same for both the example design and the user design. For designs without DCM instantiation, the DCM and the BUFs should be instantiated at the user end to generate the required clocks.

Table 2-5: DDR Interface Design Clocks

Clock	Description	Logic Domain
clk_0	Skew compensated replica of the input system clock.	The clock for the controller and the user interface logic, most of the DDR bus-related I/O flip-flops (e.g., memory clock, control/address, output DQS strobe, and DQ input capture). This is used to register the data, address, and command signals, and the address and data enables for the user interface logic ⁽¹⁾ . This clock is also used to generate read data, read data valid, and FIFO status signals.
clk_90	90° phase-shifted version of clk_0	Used in the write data path section of physical layer. Clocks write path control logic, DDR side of the Write Data FIFO, and output flip-flops for DQ.

Notes:

1. See "User Interface Accesses," page 114 for timing requirements and restrictions on the user interface signals.

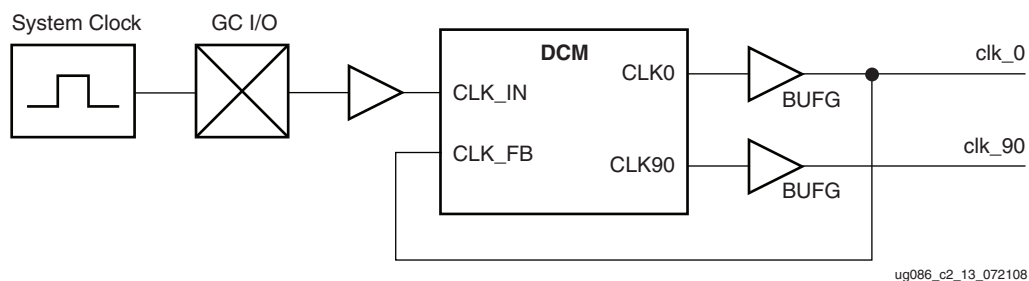


Figure 2-9: Clocking Scheme for DDR Interface Logic

DDR SDRAM System and User Interface Signals

Table 2-6 describes the DDR SDRAM system interface signals for designs with the DCM. The system interface signals are the clocks and the reset signals provided by the user to the FPGA. The differential clock signals, `sys_clk_p` and `sys_clk_n`, are the two clocks to be provided to the design. These two clocks must have a phase difference of 180 degrees with respect to each other. The `sys_reset_in_n` signal resets all the logic.

Table 2-6: DDR SDRAM System Interface Signals for Designs with DCM

Signal Name	Direction	Description
<code>sys_clk_p</code> , <code>sys_clk_n</code>	Input	Differential input clock to the DCM. The DDR SDRAM controller and memory operate on this frequency.
<code>sys_reset_in_n</code>	Input	Active-Low reset to the DDR SDRAM controller.
<code>clk200_p</code> , <code>clk200_n</code>	Input	Differential clock used in the <code>idelay_ctrl</code> logic.

Table 2-7 shows the system interface signals for designs without the DCM. The `clk_0`, `clk_90`, and `clk_200` signals are the single-ended input clocks. The `clk_90` signal must have a phase difference of 90° with respect to `clk_0`. The `clk_200` signal is the clock used for the `IDELAYCTRL` primitives in Virtex-4 FPGAs.

Table 2-7: System Interface Signals for Designs without the DCM

Signal	Direction	Description
<code>clk_0</code>	Input	The DDR SDRAM controller and memory operate on this clock.
<code>sys_reset_in_n</code>	Input	Active-Low reset to the DDR SDRAM controller. This signal is used to generate a synchronous system reset.
<code>clk_90</code>	Input	90° phase-shifted clock with the same frequency as <code>clk_0</code> .
<code>clk_200</code>	Input	200 MHz differential input clock for the <code>IDELAYCTRL</code> primitive of the Virtex-4 FPGA.
<code>dcm_lock</code>	Input	The status signal indicating whether the DCM is locked or not. It is used to generate the synchronous system reset.

Table 2-8 describes the DDR SDRAM user interface signals for designs without the testbench.

Table 2-8: DDR SDRAM User Interface Signals for Designs without the Testbench Case

Signal Name ⁽¹⁾	Direction	Description
<code>clk_tb</code>	Output	All user interface signals must be synchronized with respect to <code>clk_tb</code> .
<code>reset_tb</code>	Output	Active-High system reset for the user interface.
<code>burst_length_div2[2:0]</code>	Output	Indicates the number of bursts that can be written to or read from the memory. 001: burst length = 2 010: burst length = 4 100: burst length = 8

Table 2-8: DDR SDRAM User Interface Signals for Designs without the Testbench Case (Cont'd)

Signal Name ⁽¹⁾	Direction	Description
read_data_valid	Output	Status of the Read Data FIFO. This signal is asserted when read data is available in the Read Data FIFO.
read_data_fifo_out [2n-1:0]	Output	Read data from memory, where n is the data width of the interface. The read data is stored into the Read Data FIFO. This data can be read from the FIFO depending upon the status of the FIFO.
wdf_almost_full	Output	ALMOST FULL status of the Write Data FIFO. When this signal is asserted, the user can write 5 more locations into the FIFO in designs generated with a testbench and 14 more locations in designs without a testbench.
af_almost_full	Output	ALMOST FULL status of the Read Address FIFO. The user can issue eight more locations into the FIFO after AF_ALMOST_FULL is asserted.
app_af_addr[35:0] ⁽²⁾	Input	Memory address and command. Bit 35 is used internally by the controller. The controller ignores this bit from the user interface. Bits [34:32] are used for dynamic commands as follows: 001: Auto Refresh 010: Precharge 100: Write 101: Read Bits [31:0] form the memory chip select, bank address, row address, and column address. The positioning of the chip, bank, row, and column addresses changes based on the memory configuration.
app_af_wren	Input	Write-enable signal to the Write Address FIFO. This signal is synchronized with the write address. The write address is written to the Write Address FIFO only when this signal is asserted High.
app_mask_data[2m-1:0]	Input	User mask data, where m indicates the data mask width of the interface. The mask data is twice the mask width of the interface. The mask data is written into the Write Data FIFO along with the write data.
app_wdf_data[2n-1:0]	Input	User write data to the memory, where n indicates the data width of the interface. The user write data is twice the data width of the interface. The most-significant bits contain the rising-edge data, and the least-significant bits contain the falling-edge data. Memory write data is written into the Write Data FIFO, and the write address is written into the Write Address FIFO from the user interface. The DDR SDRAM controller reads the Write Address FIFO and Write Data FIFO.

Table 2-8: DDR SDRAM User Interface Signals for Designs without the Testbench Case (Cont'd)

Signal Name ⁽¹⁾	Direction	Description
app_wdf_wren	Input	Write-enable signal to the Write Data FIFO. This signal is synchronized with the write data. The write data is written to the Write Data FIFO only when this signal is asserted High.

Notes:

1. All user interface signal names are prepended with a controller number, for example, cntrl0_APP_WDF_DATA. DDR SDRAM devices currently support only one controller. See “User Interface Accesses,” page 114 for timing requirements and restrictions on the user interface signals.
2. Linear addressing is used, i.e., the row address immediately follows the column address bits, and the bank address follows the row address bits, thus supporting more devices. The number of address bits used depends on the density of the memory part. The controller ignores the unused bits, which can all be tied High.

Table 2-9 describes the status signals that are available to the user.

Table 2-9: DDR SDRAM Design Status Signals

Signal Name	Direction	Description
init_done	Output	This signal indicates the completion of initialization and calibration of the design.

User Interface Accesses

The user backend logic communicates with the memory controller through a FIFO-based user interface. This interface consists of three related buses:

- A Command/Address FIFO bus, which accepts write/read commands as well as the corresponding memory address from the user
- A Write Data FIFO bus, which accepts the corresponding write data when the user issues a write command on the Command/Address bus
- A Read bus on which the corresponding read data for an issued read command is returned

The user interface has the following timing and signaling restriction:

- Commands and write data cannot be written by the user until calibration is complete (as indicated by init_done). In addition, the following interface signals need to be held Low until calibration is complete: app_af_wren, app_wdf_wren, app_wdf_data, and app_mask_data. Failure to hold these signals Low causes errors during calibration. This restriction arises from the fact that the Write Data FIFO is used during calibration to hold the training patterns for the various stages of calibration.
- When issuing a write command, the first write data word must be written to the Write Data FIFO no more than one clock cycle after the write command is issued. This restriction arises from the fact that the controller assumes write data is available when it receives the write command from the user.
- clk_tb is connected to clk_0 in the controller. In case that user clock domain is different from clk_0 / clk_tb of MIG, the user should add FIFOs for all data inputs and outputs of the controller, in order to synchronize them to the clk_tb.

Write Interface

Figure 2-10 shows the user interface block diagram for write operations.

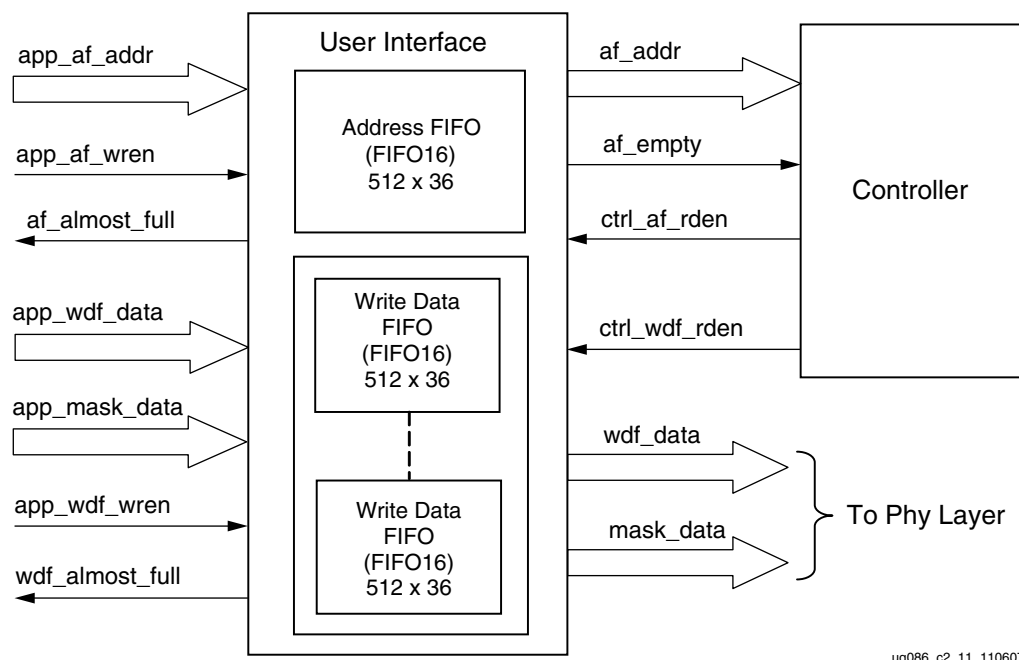


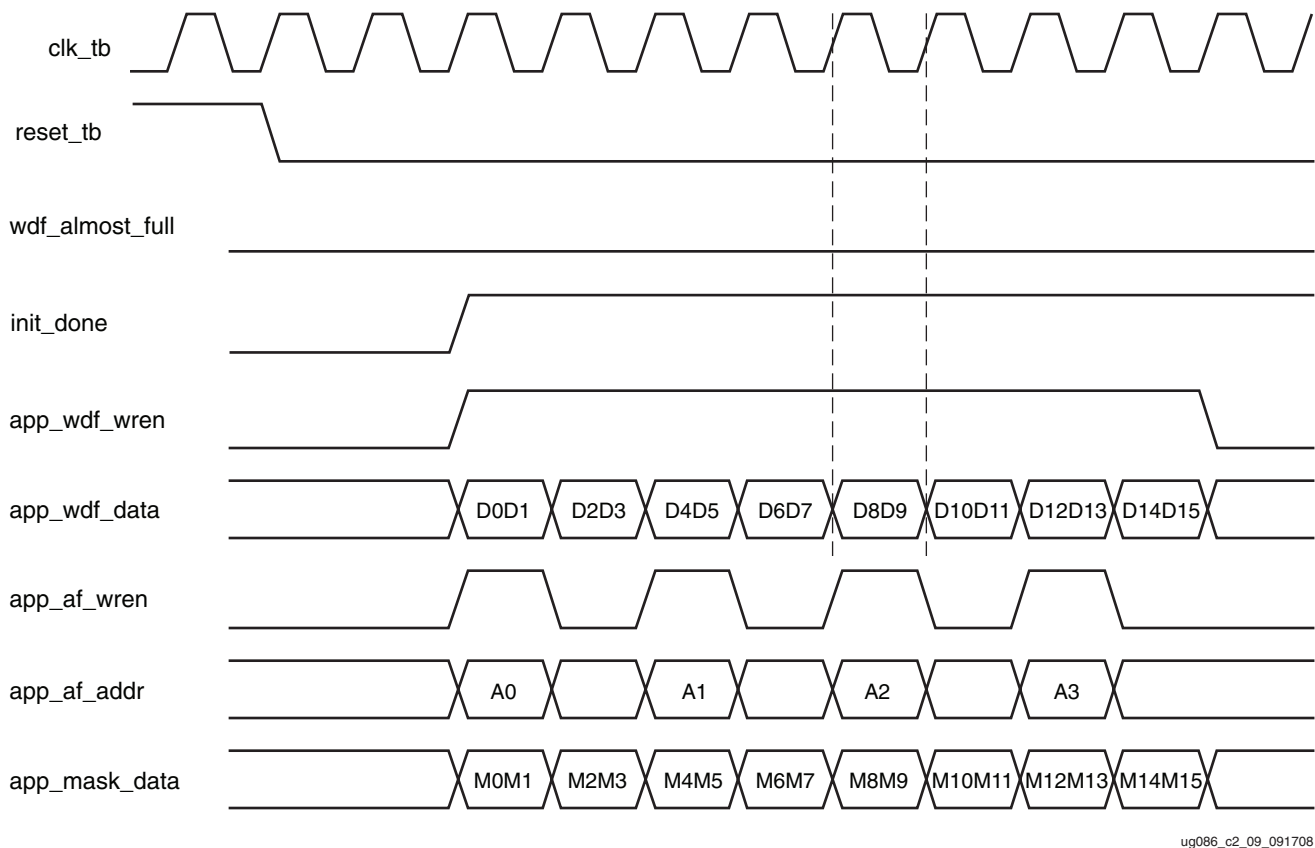
Figure 2-10: User Interface Block Diagram for Write Operations

The following steps describe the architecture of the Address and Write Data FIFOs and show how to perform a write burst operation to DDR SDRAM from the user interface.

1. The user interface consists of an Address FIFO and a Write Data FIFO. These FIFOs are constructed using Virtex-4 FPGA FIFO16 primitives with a 512 x 36 configuration. The 36-bit architecture comprises one 32-bit port and one 4-bit port. For Write Data FIFOs, the 32-bit port is used for data bits and the 4-bit port is used for mask bits.
2. The Common Address FIFO is used for both write and read commands, and comprises a command part and an address part. Command bits discriminate between write and read commands.
3. User interface data width `app_wdf_data` is twice that of the memory data width. For an 8-bit memory width, the user interface is 16 bits consisting of rise data and fall data. For every 8 bits of data, there is a mask bit. For 72-bit memory data, the user interface data width `app_wdf_data` is 144 bits, and the mask data `app_mask_data` is 18 bits.
4. The minimum configuration of the Write Data FIFO is 512 x 36 for a memory data width of 8 bits. For an 8-bit memory data width, the least significant 16 bits of the data port is used for write data. The controller internally pads all zeros for the most-significant 16 bits.
5. Depending on the memory data width, MIG instantiates multiple FIFO16s to gain the required width. For designs using 8-bit data width, one FIFO16 is instantiated; for 72-bit data width, a total of five FIFO16s are instantiated. The bit architecture comprises 16 bits of rising-edge data, 2 bits of rising-edge mask, 16 bits of falling-edge data, and 2 bits of falling-edge mask, which are all stored in a FIFO16. MIG routes the `app_wdf_data` and `app_mask_data` to FIFO16s accordingly.
6. The user can initiate a write to memory by writing to the Address FIFO and the Write Data FIFO when the FIFO Full flags are deasserted. Status signal `af_almost_full` is

asserted when Address FIFO is full, and similarly wdf_almost_full is asserted when Write Data FIFO is full.

7. Both the Address FIFO and Write Data FIFO Full flags are deasserted with power-on.
8. The user should assert the Address FIFO write-enable signal app_af_wren along with address app_af_addr to store the write address and write command into the Address FIFO.
9. The user should assert the Data FIFO write-enable signal app_wdf_wren along with write data app_wdf_data and mask data app_mask_data to store the write data and mask data into the Write Data FIFO. The user should provide both rise and fall data together for each write to the Data FIFO.
10. The controller reads the Address FIFO by issuing the ctrl_af_rden signal. The controller reads the Write Data FIFO by issuing the ctrl_wdf_rden signal after the Address FIFO is read. It decodes the command part after the Address FIFO is read.
11. The write command timing diagram in Figure 2-11 is derived from the MIG-generated testbench. As shown (burst length of 4), each write to the Address FIFO must be coupled with *two* writes to the Data FIFO. Similarly, for a burst length of 8, every write to the Address FIFO must be coupled with *four* writes to the Data FIFO. Failure to follow this rule can cause unpredictable behavior.



ug086_c2_09_091708

Figure 2-11: DDR SDRAM Write Burst for Four Bursts (BL = 4)

Correlation between the Address and Data FIFOs

There is a worst case two-cycle latency from the time the address is loaded into the address FIFO on `app_af_addr[35:0]` to the time the controller decodes the address. Because of this latency, it is not necessary to provide the address on the last clock where data is entered into the data FIFO. If the address is written before the last data phase, the overall efficiency and performance increases because it eliminates or reduces the two-cycle latency. However, if the address is written before data is input into the data FIFO, a FIFO empty condition might result because the Data FIFO does not contain valid data.

Based on these considerations, Xilinx recommends entering the address into the address FIFO between the first data phase and the next-to-last data phase. For a burst of four or eight, this means the address can be asserted one clock before the first data phase. This implementation increases efficiency by reducing the one clock latency and guarantees that valid data is available in the Data FIFO.

Read Interface

Figure 2-12 shows a block diagram of the read interface.

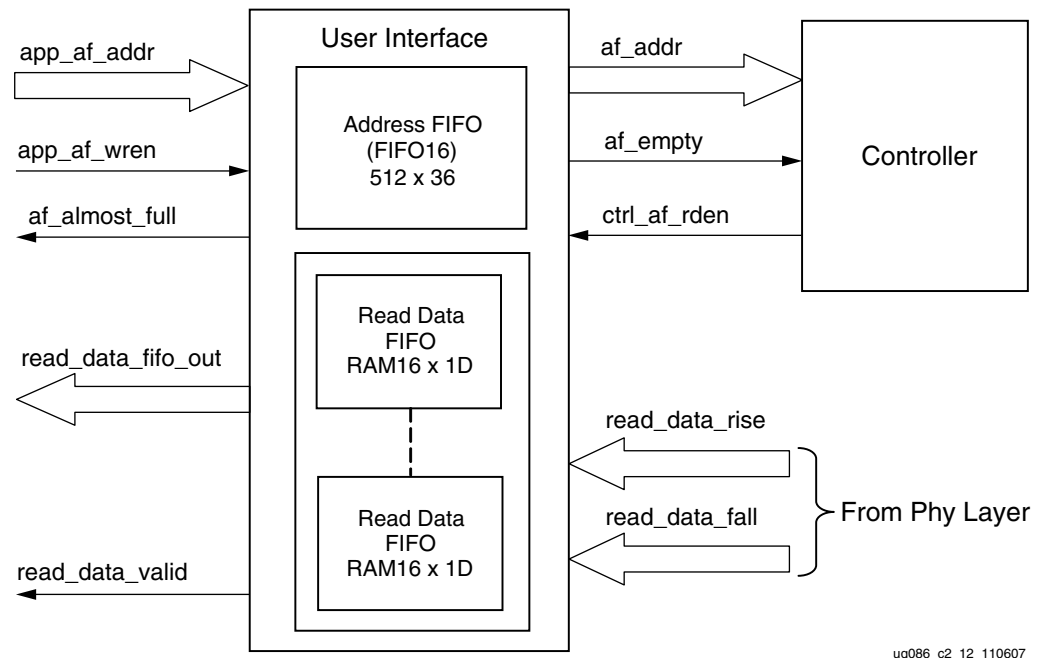


Figure 2-12: User Interface Block Diagram for Read Operation

The following steps describe the architecture of the Read Data FIFOs and show how to perform a burst read operation from DDR SDRAM from the user interface.

1. The read user interface consists of an Address FIFO and a Read Data FIFO. The Address FIFO is common to both read and write operations. These FIFOs are constructed using Virtex-4 FPGA Distributed RAMs with a 16 x 1 configuration. MIG instantiates a number of RAM16Ds depending on the data width. For example, for 8-bit data width, MIG instantiates a total of 16 RAM16Ds, 8 for rising-edge data and 8 for falling-edge data. Similarly, for 72-bit data width, MIG instantiates a total of 144 RAM16Ds, 72 for rising-edge data and 72 for falling-edge data.
2. The user can initiate a read to memory by writing to the Address FIFO when the FIFO Full flag `af_almost_full` is deasserted.

3. To write the read address and read command into the Address FIFO, the user should issue the Address FIFO write-enable signal `app_af_wren` along with read address `app_af_addr`.
4. The controller reads the Address FIFO containing the address and command. After decoding the command, the controller generates the appropriate control signals to memory.
5. Prior to the actual read and write commands, the design calibrates the latency (number of clock cycles) from the time the read command is issued to the time data is received. Using this pre-calibrated delay information, the controller generates the write-enable signals to the Read Data FIFOs.
6. The `read_data_valid` signal is asserted when data is available in the Read Data FIFOs.
7. Figure 2-13 shows a user interface timing diagram for a burst length of 4, CAS latency of 3 at 175 MHz, and a `Trcd` value of the memory part at 20 ns. The read latency is calculated from the point when the Read command is given by the user to the point when the data is available with the `read_data_valid` signal. The minimum latency in this case is 26 clocks, where no precharge is required, no auto-refresh request is pending, the user commands are issued after initialization is completed, and the first command issued is a Read command. The controller executes the commands only after initialization is done as indicated by the `init_done` signal.

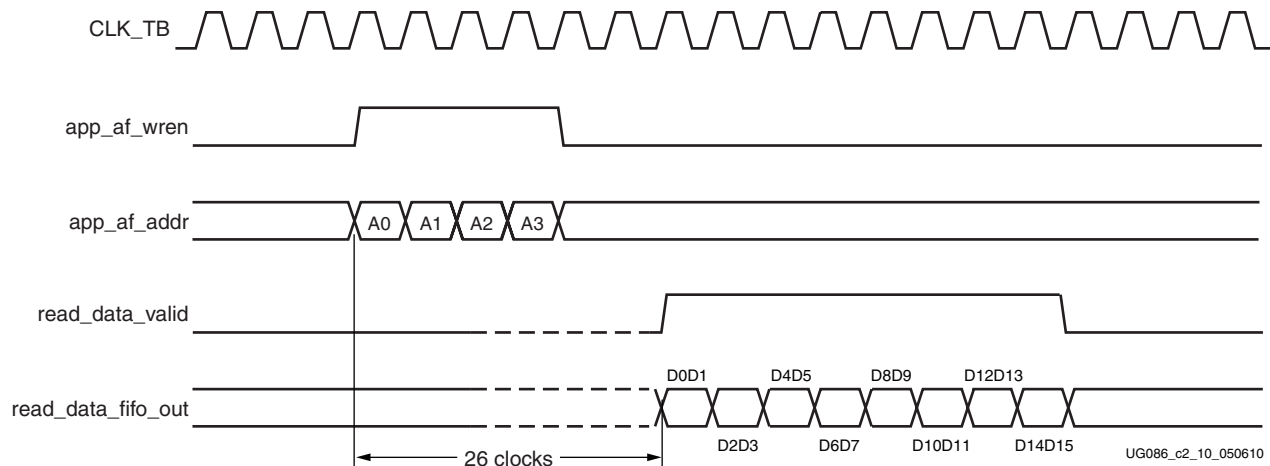


Figure 2-13: DDR SDRAM Read Burst for Four Bursts (BL = 4)

8. After the address and command are loaded into the Address FIFO, it takes 26 clock cycles minimum for CL = 3 at a frequency of 175 MHz for the controller to assert the `read_data_valid` signal.
9. Read data is available only when the `read_data_valid` signal is asserted. The user should access the read data on every positive edge of the `read_data_valid` signal.

The read latency for the case where (1) CL = 3, (2) the read is written to an empty address/command FIFO, (3) the read targets an unopened bank/row, and (4) the frequency is 175 MHz, is broken down as indicated in Table 2-10.

Table 2-10: Read Command to Read Data Clock Cycles

Parameter	Number of Clock Cycles
Read Command to Empty Signal Deassertion	7 clocks
Empty to Active Command	5.5 clocks
Active to Read Command	4 clocks
Memory Read to Valid	9.5 clocks
Total:	26 clocks

In general, read latency varies based on the following parameters:

- Number of commands already in the FIFO pipeline before the read command is issued
- Whether an ACTIVATE command needs to be issued to open the new bank/row
- Whether a PRECHARGE command needs to be issued to close a previously opened bank
- Specific timing parameters for the memory, such as T_{RAS} and T_{RCD} in conjunction with the bus clock frequency
- Commands can be interrupted, and banks/rows can forcibly be closed when the periodic AUTO REFRESH command is issued
- CAS latency
- If the user issues the commands before initialization is complete, the latency cannot be determined.
- Board-level and chip-level (for both memory and FPGA) propagation delays

DDR SDRAM Signal Allocations

The MIG tool allows selection of banks for different classes of memory signals. [Table 2-11](#) shows the list of signals allocated in a group from bank selection checkboxes.

Table 2-11: DDR SDRAM Signal Allocations

Bank Selected	Signals Allocated in the Group
Address	Memory address, memory control, and memory clock signals
Data	Data, data mask, and data strobes
System Control	System reset from the user interface and status signals
System Clock	System clocks from the user interface

Note: Timing has been verified for most of the MIG generated configurations. For the best timing results, adjacent banks in the same column of the FPGA should be used. Banks that are separated by unbonded banks should be avoided because these can cause timing violations.

Simulating the DDR SDRAM Design

After generating the design, MIG creates a `sim` folder in the specified path. This folder contains simulation files for a particular design. The `sim` folder contains the external testbench, memory model, and do file to simulate the generated design. The memory model files are currently generated in Verilog only. To learn more about the files in the `sim` folder and to simulate the design, refer to “Simulation Guide,” page 499.

For single-rank DIMMs, MIG outputs only the base part memory model. In the simulation testbench (`sim_tb_top` in the `sim` folder), MIG instantiates the required number of memory models. For example, a 1 GB single-rank DIMM with the base part is 1 Gb, and MIG instantiates the base model eight times. If the MIG generated memory model is to be used with the user’s test bench, multiple instances that are based on the selected configuration should be used.

The MIG output memory model considers the `part_mem_bits` parameter by default for memory range allocation. This covers only a partial memory range, i.e., $2^{\text{part_mem_bits}}$. To allocate the full memory range, the `FULL_MEM` parameter should be set in the memory model, which in turn sets the `full_mem_bits` parameter for memory allocation. Allocating the full memory range might exceed the memory of the operating system, thus causing memory allocation failure in simulations.

Simulation Violations

There might be simulation violations for frequencies such as 150 MHz where the clock period is not an integer value. At 150 MHz, the clock period value in the simulation testbench is 6.66 ns and the MIG tool rounds it to 6.67 ns. Consider a memory T_{RCD} value of 20 ns. MIG calculates the T_{RCD} count value based on the clock period, $\text{RCD_COUNT_VALUE} = 20 / 6.67 = 2.998 = 3$ (after rounding off) in the design parameter file. The T_{RCD} value for 3 clock cycles is $3 \times 6.66 = 19.98$, which causes timing violations by 20 ps. The difference between the clock period in the external simulation testbench versus the MIG tool causes timing violations. This is only one example case. There might be more such scenarios. These are only simulation warnings. Functionally, there should be no issues. To remove these warnings, the related count value can be increased by one.

Changing the Refresh Rate

Change the global ``define` (for Verilog) or constant (for VHDL) variable `MAX_REF_CNT` in `mymodule_parameters_0.v` (or `.vhd`) so that $\text{MAX_REF_CNT} = (\text{refresh interval in clock periods}) = (\text{refresh interval}) / (\text{clock period})$. For example, for a refresh rate of 3.9 μs with a memory bus running at 200 MHz:

$$\text{MAX_REF_CNT} = 3.9 \mu\text{s} / (\text{clock period}) = 3.9 \mu\text{s} / 5 \text{ ns} = 780 \text{ (decimal)} = 0x30C$$

If the above value exceeds $2^{\text{MAX_REF_WIDTH}} - 1$, the value of `MAX_REF_WIDTH` must be increased accordingly in `parameters_0.v` (or `.vhd`) to increase the width of the counter used to track the refresh interval.

Supported Devices

The design generated out of MIG is independent of the memory package, hence the package part of the memory component is replaced with XX or XXX, where XX or XXX to indicate a don't care condition. The tables below list the components (Table 2-12) and DIMMs (Table 2-13 through Table 2-15) supported by MIG for DDR SDRAM. In supported devices, XX in the memory component column denotes either single or two alphanumeric characters. For example, MT46V32M4XX-75 can be either MT46V32M4P-75 or MT46V32M4BN-75. An X in the DIMM columns (for Unbuffered, Registered, and SO DIMMs) denotes a single alphanumeric character. For example, MT9VDDF3272X-40B can be either MT9VDDF3272G-40B or MT9VDDF3272Y-40B. Similarly MT4VDDT1664AX-40B can be either MT4VDDT1664AG-40B or MT4VDDT1664AY-40B. Pin mapping for x4 RDIMMs is provided in Appendix G, "Low Power Options."

Table 2-12: Supported Components for DDR SDRAM

Components	Packages (XX)	Components	Packages (XX)
MT46V32M4XX-75	P,TG	MT46V32M4XX-5B	-
MT46V64M4XX-75	FG,P,TG	MT46V64M4XX-5B	BG,FG,P,TG
MT46V128M4XX-75	BN,FN,P,TG	MT46V128M4XX-5B	BN,FN,P,TG
MT46V256M4XX-75	P,TG	MT46V256M4XX-5B	P,TG
MT46V16M8XX-75	P,TG	MT46V16M8XX-5B	TG,P
MT46V32M8XX-75	FG,P,TG	MT46V32M8XX-5B	BG,FG,P,TG
MT46V64M8XX-75	BN,FN,P,TG	MT46V64M8XX-5B	BN,FN,P,TG
MT46V128M8XX-75	P,TG	MT46V128M8XX-5B	-
MT46V8M16XX-75	P,TG	MT46V8M16XX-5B	TG,P
MT46V16M16XX-75	BG,FG,P,TG	MT46V16M16XX-5B	BG,FG,P,TG
MT46V32M16XX-75	-	MT46V32M16XX-5B	BN,FN,P,TG
MT46V64M16XX-75	P,TG	MT46V64M16XX-5B	-

Table 2-13: Supported Unbuffered DIMMs for DDR SDRAM

Unbuffered DIMMs	Packages (X)	Unbuffered DIMMs	Packages (X)
MT4VDDT1664AX-40B	G,Y	MT8VDDT3264AX-40B	G,Y
MT4VDDT3264AX-40B	G,Y	MT9VDDT3272AX-40B	Y

Table 2-14: Supported Registered DIMMs for DDR SDRAM

Registered DIMMs	Packages (X)	Registered DIMMs	Packages (X)
MT9VDDF3272X-40B	G,Y	MT18VDDF6472X-40B	G,Y
MT9VDDF6472X-40B	G,Y	MT18VDDF12872X-40B	G,Y

Table 2-15: Supported SODIMMs for DDR SDRAM

SODIMMs	Packages (X)	SODIMMs	Packages (X)
MT4VDDT3264HX-40B	G,Y	MT9VDDT3272HX-40B	-
MT4VDDT1664HX-40B	Y	MT9VDDT6472HX-40B	G,Y

Table 2-15: Supported SODIMMs for DDR SDRAM (Cont'd)

SODIMMs	Packages (X)	SODIMMs	Packages (X)
MT8VDDT3264HX-40B	-	MT9VDDT12872HX-40B	-
MT8VDDT6464HX-40B	G,Y		

Hardware Tested Configurations

The frequencies shown in Table 2-16 were achieved on the Virtex-4 FPGA ML461 Memory Interfaces Development Board under nominal conditions. This frequency should not be used to determine the maximum design frequency. The maximum design frequency supported in the MIG wizard is based on a combination of the TRCE results for fabric timing on multiple device/package combinations and I/O timing analysis using FPGA and memory timing parameters for a 64-bit wide interface.

Table 2-16: Hardware Tested Configurations

Synthesis Tools		XST and Synplicity
HDL		Verilog and VHDL
FPGA Device		XC4VLX25-FF668-11
Burst Lengths		2, 4, 8
CAS Latency (CL)		2, 2.5, 3
16-bit Design		Tested on 16-bit Component "MT46V32M16XX-5B"
72-bit Design		Tested on 72-bit RDIMM "MT18VDDF6472G-40B"
CL = 2	Achieved Frequency Range for Component	110 MHz to 180 MHz
	Achieved Frequency Range for DIMM	110 MHz to 160 MHz
CL = 2.5	Achieved Frequency Range for Component	110 MHz to 220 MHz
	Achieved Frequency Range for DIMM	110 MHz to 200 MHz
CL = 3	Achieved Frequency Range for Component	110 MHz to 240 MHz
	Achieved Frequency Range for DIMM	110 MHz to 240 MHz

Implementing DDR2 SDRAM Controllers

This chapter describes how to implement DDR2 SDRAM interfaces for Virtex®-4 FPGAs generated by MIG. MIG supports two implementations of DDR2 SDRAM interfaces: direct clocking and SerDes clocking. The direct-clocking interface supports frequencies up to 240 MHz. This design is based on XAPP702 [Ref 19]. The SerDes clocking design supports frequencies up to 300 MHz and is based on XAPP721 [Ref 23].

Interface Model

DDR2 SDRAM interfaces are source-synchronous and double data rate. They transfer data on both edges of the clock cycle. A memory interface can be modularly represented as shown in Figure 3-1. A modular interface has many advantages. It allows designs to be ported easily and also makes it possible to share parts of the design across different types of memory interfaces.

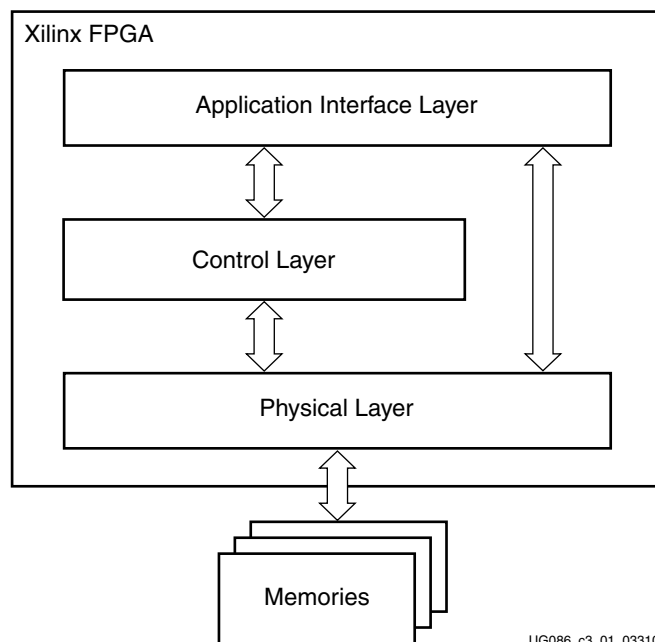


Figure 3-1: Modular Memory Interface Representation

Direct-Clocking Interface

Feature Summary

This section summarizes the supported and unsupported features of the direct-clocking DDR2 SDRAM controller design.

Supported Features

The DDR2 SDRAM controller design supports the following:

- Burst lengths of four and eight
- Sequential and interleaved burst types
- CAS latencies of 3, 4, and 5
- Additive latencies of 0, 1, and 2
- Differential and single-ended DQS
- On-Die Termination (ODT)
- Up to four deep memories
- Memory components
- Registered DIMMs (up to 240 MHz)
- Unbuffered DIMMs (up to 200 MHz)
- Unbuffered SODIMMs (up to 200 MHz)
- Different memories (density/speed)
- Byte-wise data masking
- Precharge and auto refresh
- Linear addressing
- ECC support
- Verilog and VHDL
- With and without a testbench
- With and without a DCM
- Multicontrollers (up to eight)
- Data Mask
- System clock, differential and single-ended

The supported features are described in more detail in [“Architecture.”](#)

Design Frequency Ranges

Table 3-1: Design Frequency Range in MHz

Memory	FPGA Speed Grade					
	-10		-11		-12	
	Min	Max	Min	Max	Min	Max
Component	125	220	125	230	125	240
UDIMM/SODIMM	125	200	125	200	125	200

Table 3-1: Design Frequency Range in MHz

Memory	FPGA Speed Grade					
	-10		-11		-12	
	Min	Max	Min	Max	Min	Max
RDIMM	125	220	125	230	125	240
Deep Memory / Dual Rank DIMM	125	150	125	150	125	150

Unsupported Features

The DDR2 SDRAM controller design does not support:

- Additive latencies of 3 and 4
- Redundant DQS (RDQS)
- Unbuffered DIMMs (greater than 200 MHz)
- Unbuffered SODIMMs (greater than 200 MHz)

Architecture

Implemented Features

This section provides details on the supported features of the DDR2 SDRAM controller.

Burst Length

The DDR2 SDRAM controller supports burst lengths of four and eight. The burst length can be selected through the **Set mode register(s)** option from the GUI. For a design without a testbench (user design), the user has to provide bursts of the input data based on the chosen burst length. Bits M2:M0 of the Mode Register define the burst length, and bit M3 indicates the burst type (see the Micron data sheet). Read and write accesses to the DDR2 SDRAM are burst-oriented. It determines the maximum number of column locations accessed for a given READ or WRITE command.

CAS Latency

The DDR2 SDRAM controller supports CAS latencies (CLs) of three and four. CL can be selected in the **Set mode register(s)** option from the GUI. The CAS latency is implemented in the ddr2_controller module. During data write operations, the generation of the ctrl_Dqs_En and ctrl_Dqs_Rst signals varies according to the CL in the ddr2_controller module. During data read operations, the generation of the ctrl_RdEn signal varies according to the CL in the ddr2_controller module. Bits M4:M6 of the Mode Register define the CL (see the Micron data sheet). CL is the delay in clock cycles between the registration of a READ command and the availability of the first bit of output data.

Additive Latency

DDR2 SDRAM devices support a feature called posted CAS additive latency (AL). The DDR2 SDRAM supports additive latencies of 0, 1, and 2. AL can be selected in the **Set mode register(s)** option from the GUI. Additive latency is implemented in the ddr2_controller module. The ddr2_controller module issues READ/WRITE commands prior to t_{RCD} (minimum) depending on the user-selected AL value in the Extended Mode Register. This feature allows the READ command to be issued prior to t_{RCD} (minimum) by delaying the internal command to the DDR2 SDRAM by AL clocks. Posted CAS AL makes

the command and data bus efficient for sustainable bandwidths in DDR2 SDRAM. Bits E3:E5 of the Extended Mode Register define the value of AL (see the Micron data sheet).

Registered DIMMs

DDR2 SDRAM supports registered DIMMs. This feature is implemented in the `ddr2_controller` module. For registered DIMMs, the READ and WRITE commands and address have one additional clock latency than unbuffered DIMMs.

Unbuffered DIMMs and SODIMMs

The DDR2 SDRAM design supports unbuffered DIMMs and SODIMMs. Unbuffered DIMMs are normal DIMMs, where a set of components are used to get a particular configuration. SODIMMs differ from the unbuffered DIMMs only by the package type. Otherwise they are functionally the same.

Multicontrollers

MIG supports multicontrollers for DDR2 SDRAMs. A maximum of eight controllers can be selected by the user from the tool. In multicontroller designs, MIG supports the same frequency for all the controllers.

Different Memories (Density/Speed)

The DDR2 SDRAM controller supports different densities. For DDR2 components shown in MIG, densities vary from 256 Mb to 2 Gb, and DIMM densities vary from 128 Mb to 4 Gb. Higher densities can be created using the “Create new memory part” feature of MIG. The supported maximum column address is 13, the maximum row address is 15, and the maximum bank address is 3. The design can decode write and read addresses from the user in the DDR2 SDRAM controller module. The user address consists of column, row, bank, chip address, and user command.

Table 3-2 and Table 3-3 list sample timing sheets for Micron components and DIMMs, respectively.

Table 3-2: Timing Parameters for Components

Parameter	Description	Micron 256 Mb		Micron 512 Mb		Micron 1 Gb	
		-37E	-5E	-37E	-5E	-37E	-5E
T_{MRD}	LOAD MODE command cycle time	2	2	2	2	2	2
T_{RP}	PRECHARGE command period	15	15	15	15	15	15
T_{RFC}	REFRESH to ACTIVE or REFRESH to REFRESH command interval	75	75	105	105	127.5	127.5
T_{RCD}	ACTIVE to READ or WRITE delay	15	15	15	15	15	15
T_{RAS}	ACTIVE to PRECHARGE command	40	40	40	40	40	40
T_{RC}	ACTIVE to ACTIVE (same bank) command	55	55	55	55	55	55
T_{RTP}	READ to PRECHARGE command delay	7.5	7.5	7.5	7.5	7.5	7.5
T_{WTR}	WRITE to READ command delay	7.5	10	7.5	10	7.5	10
T_{WR}	WRITE Recovery time	15	15	15	15	15	15

Table 3-3: Timing Parameters for DIMMs

Parameter	Description	MT4HTF		MT8HTF		MT16HTF		MT9HTF		MT18HTF	
		-53E	-40E	-53E	-40E	-53E	-40E	-53E	-40E	-53E	-40E
T_{MRD}	LOAD MODE command cycle time	2	2	2	2	2	2	2	2	2	2
T_{RP}	PRECHARGE command period	15	15	15	15	15	15	15	15	15	15
T_{RFC}	REFRESH to ACTIVE or REFRESH to REFRESH command interval	128 MB 75	75	256 MB 75	75	512 MB 75	75	256 MB 75	75	512 MB 75	75
		256 MB 105	105	512 MB 105	105	1 GB 105	105	512 MB 105	105	1 GB 105	105
		512 MB 127.5	127.5	1 GB 127.5	127.5	2 GB 127.5	127.5	1 GB 127.5	127.5	2 GB 127.5	127.5
T_{RCD}	ACTIVE to READ or WRITE delay	15	15	15	15	15	15	15	15	15	15
T_{RAS}	ACTIVE to PRECHARGE command	40	40	40	40	40	40	40	40	40	40
T_{RC}	ACTIVE to ACTIVE (same bank) command	55	55	55	55	55	55	55	55	55	55
T_{RTP}	READ to PRECHARGE command delay	7.5	7.5	7.5	7.5	7.5	7.5	7.5	7.5	7.5	7.5
T_{WTR}	WRITE to READ command delay	7.5	10	7.5	10	7.5	10	7.5	10	7.5	10
T_{WR}	WRITE recovery time	15	15	15	15	15	15	15	15	15	15

Note: For the latest timing information, refer to the vendor memory data sheets.

Data Masking

The DDR2 SDRAM design supports data masking per byte. Masking per nibble is not supported due to the limitation of the internal block RAM based FIFOs. So, the masking of data can be done on a per byte basis. The mask data is stored in the Data FIFO along with the actual data.

MIG supports a data mask option. If this option is checked in the GUI, MIG generates a design with data mask pins. This option can be chosen if the selected part has data masking. DDR2 SDRAM designs do not support read-modify-write operations in ECC mode. The mask bits to the SDRAM should never be asserted while in the ECC mode. Thus, when ECC is selected, the data masking selection is disabled in the GUI.

Precharge

The PRECHARGE command is used to close the open row in a bank if there is a command to be issued in the same bank. The PRECHARGE command checks the row address, bank address, and chip address, and the Virtex-4 FPGA DDR2 controller issues a PRECHARGE command if there is a change in any of the addresses where a read or write command is to be issued. The auto precharge function is not supported.

Auto Refresh

The DDR2 SDRAM controller issues AUTO REFRESH commands at specified intervals for the memory to refresh the charge required to retain the data in the memory. The user can

also issue a REFRESH command through the user interface by setting bits 34, 33, and 32 of the `app_af_addr` signal in the `user_interface` module to `3'b001`. If there is a refresh request while there is an ongoing read or write burst, the controller issues a refresh command after completing the current read or write burst command.

Linear Addressing

The DDR2 SDRAM controller supports linear addressing. Linear addressing refers to the way the user provides the address of the memory to be accessed. For Virtex-4 FPGA DDR2 SDRAM controllers, the user provides address information through the `app_af_addr` bus. As the densities of the memory devices vary, the number of column address bits and row address bits also change. In any case, the row address bits in the `app_af_addr` bus always start from the next higher bit, where the column address ends. This feature increases the number of devices that can be supported with the design.

On-Die Termination

The DDR2 SDRAM controller supports on-die termination (ODT). Through the **Set mode register(s)** option from the GUI, the user can disable ODT or can choose 75, 150, or 50. ODT can turn the termination on and off as needed to improve signal integrity in the system. Because DDR2 supports the deep memory maximum of four, a maximum of four ODTs is supported. Several examples follow:

1. *Four single-rank DIMMs or components populated in four different slots.* If the user selects **deep memory = 4**, the memory component sequence is 0, 1, 2, and 3. During write operations, the ODT is enabled for component 3 when writing into 0, 1, or 2, otherwise it is enabled for component 2 when writing into component 3. During read operations, the ODT is enabled for component 3 when reading from 0, 1, or 2, otherwise it is enabled for component 2 for reading from component 3.

Two dual-rank DIMMs populated in two different slots. Rank 1 and rank 2 of slot 1 are referred to as CS0 and CS1. Rank 1 and rank 2 of slot 2 are referred to as CS2 and CS3. ODT is enabled for CS0 when writing into CS2 or CS3 and enabled for CS2 when writing into CS0 or CS1. ODT is enabled for CS0 when reading from CS2 or CS3 and enabled for CS2 when reading from CS0 or CS1. ODT0, ODT1, ODT2, and ODT3 should be connected to the ODT signals of CS0, CS1, CS2, and CS3, respectively.

2. *Three single-rank DIMMs or components populated in three different slots.* If the user selects **deep memory = 3**, the memory component sequence is 0, 1, and 2. During write operations, the ODT is enabled for component 2 when writing into 0 or 1, otherwise it is enabled for component 1 when writing into component 2. During read operations, the ODT is enabled for component 2 when reading from 0 or 1, otherwise it is enabled for component 1 for reading from component 2. ODT0, ODT1, and ODT2 should be connected to the ODT signals of CS0, CS1, and CS2, respectively.

3. *Two single-rank DIMMs or components populated in two different slots.* If the user selects **deep memory = 2**, the memory component sequence is 0 and 1. During write operations, the ODT is enabled for component 1 when writing into 0, otherwise it is enabled for component 0 when writing into component 1. During read operations, the ODT is enabled for component 1 when reading from 0, otherwise it is enabled for component 0 for reading from component 1.

One single dual-rank DIMM is populated in single slot. Rank 1 and rank 2 of slot 1 are referred as CS0 and CS1. ODT is enabled for CS0 when writing into CS0 or CS1. During read operations, the ODT is disabled. ODT0 and ODT1 should be connected to the ODT signals of CS0 and CS1, respectively.

4. If the user selects **deep memory = 1**, the memory component sequence is 0. During write operations, the ODT is enabled for component 0 when writing into 0. During read operations, the ODT is disabled. ODT0 should be connected to the ODT signal of CS0.

Table 3-4 shows ODT control during write operations.

Table 3-4: ODT Control During Writes

Configuration		Write To	DRAM at Slot 1 (ODT On/Off)		DRAM at Slot 1 (ODT On/Off)	
Slot 1	Slot 2		Rank 1	Rank 2	Rank 1	Rank 2
DR ⁽¹⁾	DR	Slot 1	Off	Off	On	Off
		Slot 2	On	Off	Off	Off
DR	Empty	Slot 1	On	Off	N/A	N/A
Empty	DR	Slot 2	N/A	N/A	On	Off
SR ⁽²⁾	SR	Slot 1	Off	N/A	On	N/A
		Slot 2	On	N/A	Off	N/A
SR	Empty	Slot 1	On	N/A	N/A	N/A
Empty	SR	Slot 2	N/A	N/A	On	N/A

Notes:

1. Dual rank.
2. Single rank.

Table 3-5 shows ODT control during read operations.

Table 3-5: ODT Control During Reads

Configuration		Read From	DRAM at Slot 1 (ODT On/Off)		DRAM at Slot 1 (ODT On/Off)	
Slot 1	Slot 2		Rank 1	Rank 2	Rank 1	Rank 2
DR ⁽¹⁾	DR	Slot 1	Off	Off	On	Off
		Slot 2	On	Off	Off	Off
DR	Empty	Slot 1	Off	Off	N/A	N/A
Empty	DR	Slot 2	N/A	N/A	Off	Off
SR ⁽²⁾	SR	Slot 1	Off	N/A	On	N/A
		Slot 2	On	N/A	Off	N/A
SR	Empty	Slot 1	Off	N/A	N/A	N/A
Empty	SR	Slot 2	N/A	N/A	Off	N/A

Notes:

1. Dual rank.
2. Single rank.

Deep Memories

The MIG DDR2 SDRAM controller supports depths up to 4. Through the **Depth** option, the user can select various deep values. For deep memory implementations, MIG generates chip selects, CKE signals, and ODT signals for each memory. The clock widths (ck and ck_n) are a multiple factor of the deep configuration chosen in MIG. This feature increases the depth of the memory. For example, if the user selects a 256 Mb component and deep memory = 4 from MIG, the tool generates a memory interface for a 1 Gb design.

Deep memory logic is implemented in the ddr2_ controller module. With deep memories, DDR2 SDRAMs are initialized one after the other to avoid loading the address and control buses, and the calibration is done on the last memory. Apart from initialization, the DDR2 SDRAM controller module also demultiplexes the column, row, and bank addresses from the user address. The module also decodes the chip selects and rank addresses for components and DIMMs.

The formats of user read/write addresses for a 256 Mb component and 2 GB and 4 GB DIMMs are given in “[Deep Memory Configurations](#).”

ECC Support

The DDR2 SDRAM controller supports ECC. ECC is supported for the following data widths:

- 40-bit (32-bit data and a 0 prepended to 7-bit parity)
- 72-bit (64-bit data and 8-bit parity)
- 144-bit (128-bit data and 16-bit parity)

The user can completely disable the ECC or can generate the design for the above data widths by choosing either the Unpipeline mode or the Pipeline mode from the GUI.

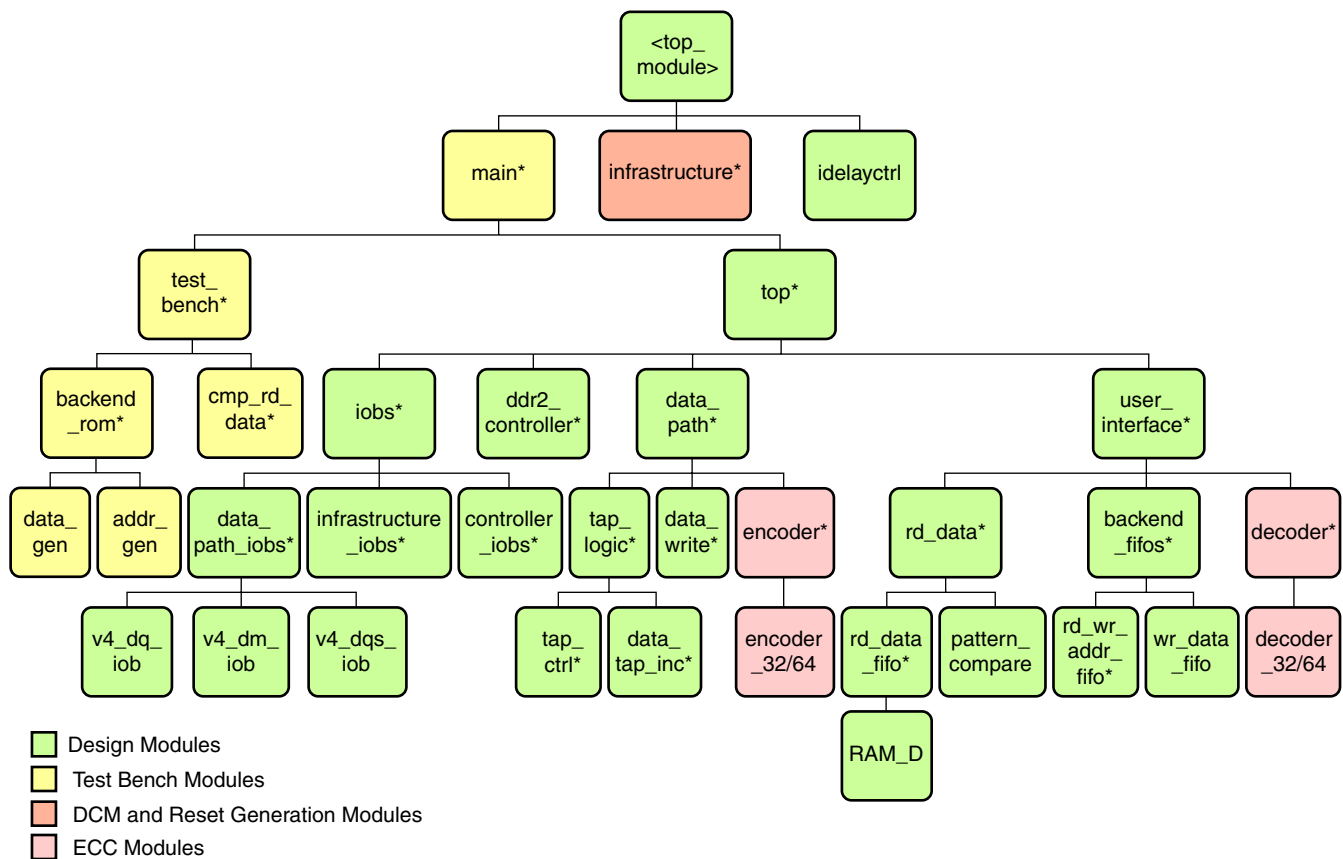
ECC is based on XAPP645 [Ref 17]. The design can detect and correct all single bit errors, and it can detect double bit errors in the data. This design utilizes Hamming code for the ECC operations. The Pipeline mode improves the frequency performance at the cost of an extra pipeline stage.

System Clock

MIG supports differential and single-ended system clocks. Based on the selection in the GUI, input system clocks and IDELAY clocks are differential or single-ended.

Hierarchy

Figure 3-2 shows the hierarchical structure of the DDR2 SDRAM controller.



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Figure 3-2: Hierarchical Structure of the DDR2 Design (Direct Clocking)

Figure 3-2 shows the hierarchical structure of the DDR2 SDRAM design generated by MIG with a testbench and a DCM. The modules are classified as follows:

- Design modules
- Testbench modules
- Clocks and reset generation modules

There is a parameter file generated with the design that has all the user input and design parameters selected from MIG.

MIG can generate four different DDR2 SDRAM designs:

- With a testbench and a DCM
- Without a testbench and with a DCM
- With a testbench and without a DCM
- Without a testbench and without a DCM

A design without a testbench (user_design) does not have testbench modules. The <top_module> module has the user interface signals for designs without a testbench. The list of user interface signals is provided in [Table 3-9, page 142](#).

Design clocks and resets are generated in the infrastructure module. The DCM clock is instantiated in the infrastructure module for designs with a DCM. The inputs to this module are the differential design clock and a 200 MHz differential clock for the IDELAYCTRL module. A user reset is also input to this module. Using the input clocks and reset signals, the system clocks and the system reset are generated in this module, which is used in the design.

The DCM primitive is not instantiated in this module if the **Use DCM** option is unchecked. So, the system operates on the user-provided clocks. The system reset is generated in the infrastructure module using the dcm_lock input signal.

For ECC enabled designs, the corresponding pink shaded modules are present in the design. ECC data is generated from these modules.

MIG Tool Design Options for Direct-Clocking Interface

MIG provides various options to generate the design with or without a testbench or with or without a DCM. This section provides detailed descriptions of the type of design generated by the user using various options. [Figure 3-3, page 133](#) and [Figure 3-4, page 134](#) show the differential system clock. For more information on the clocking structure, refer to “Direct-Clocking Interface Clocking Scheme,” [page 140](#).

MIG outputs both an example_design and a user_design. The MIG-generated example_design includes the entire memory controller design along with a synthesized testbench (example user application). This testbench generates sample writes and reads and then uses comparison logic to verify that the data patterns written are the same as those received. This example_design can be used to test functionality both in simulation and in hardware. The user_design includes the memory controller design only. This design allows users to connect the MIG memory controller design to a user developed testbench (user application). Refer to [Table 3-9, page 142](#) for user interface signals, the “User Interface Accesses,” [page 143](#) for timing restriction on user interface signals, and [Figure 3-10, page 146](#) and [Figure 3-11, page 147](#) for write interface timing.

[Figure 3-3, page 133](#) shows a top-level block diagram of a DDR2 SDRAM design with a DCM and a testbench. The sys_clk_p and sys_clk_n signals are differential input system clocks. The DCM is instantiated in the infrastructure module that generates the required design clocks. The differential clk200_p and clk200_n signals are used for the idelay_ctrl element. The sys_reset_in_n is the active-Low system reset signal. All design resets are gated by the dcm_lock signal. The error output signal indicates whether the case passes or fails. The testbench module does writes and reads, and also compares the read data with the written data. The error signal is driven High on data mismatches. The init_done signal indicates the completion of initialization and calibration of the design. Memory device signals are prepended with the controller number. For example, for a single controller design, the ddr2_ras_n signal appears as cntrl0_ddr2_ras_n. Similarly, for a four-controller design with controllers 0, 1, 2, and 3, the controller 3 ddr2_ras_n signal appears as cntrl3_ddr2_ras_n.

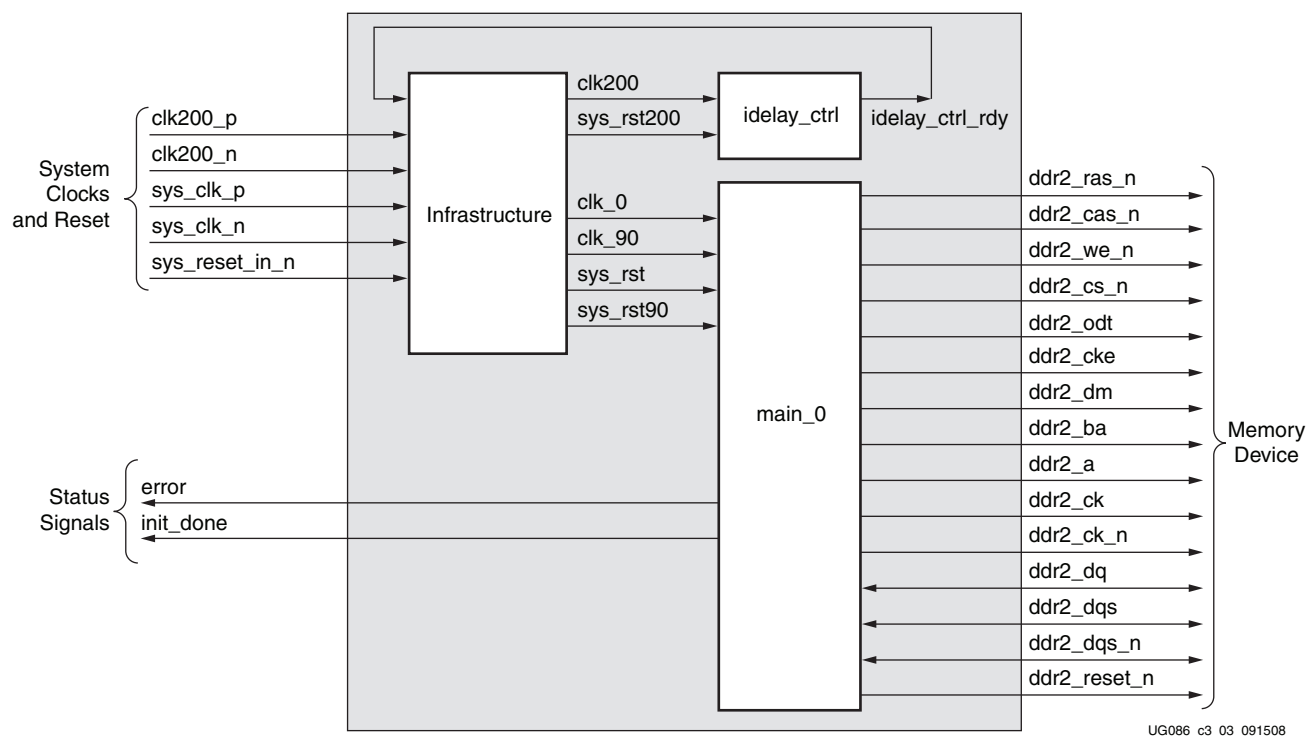
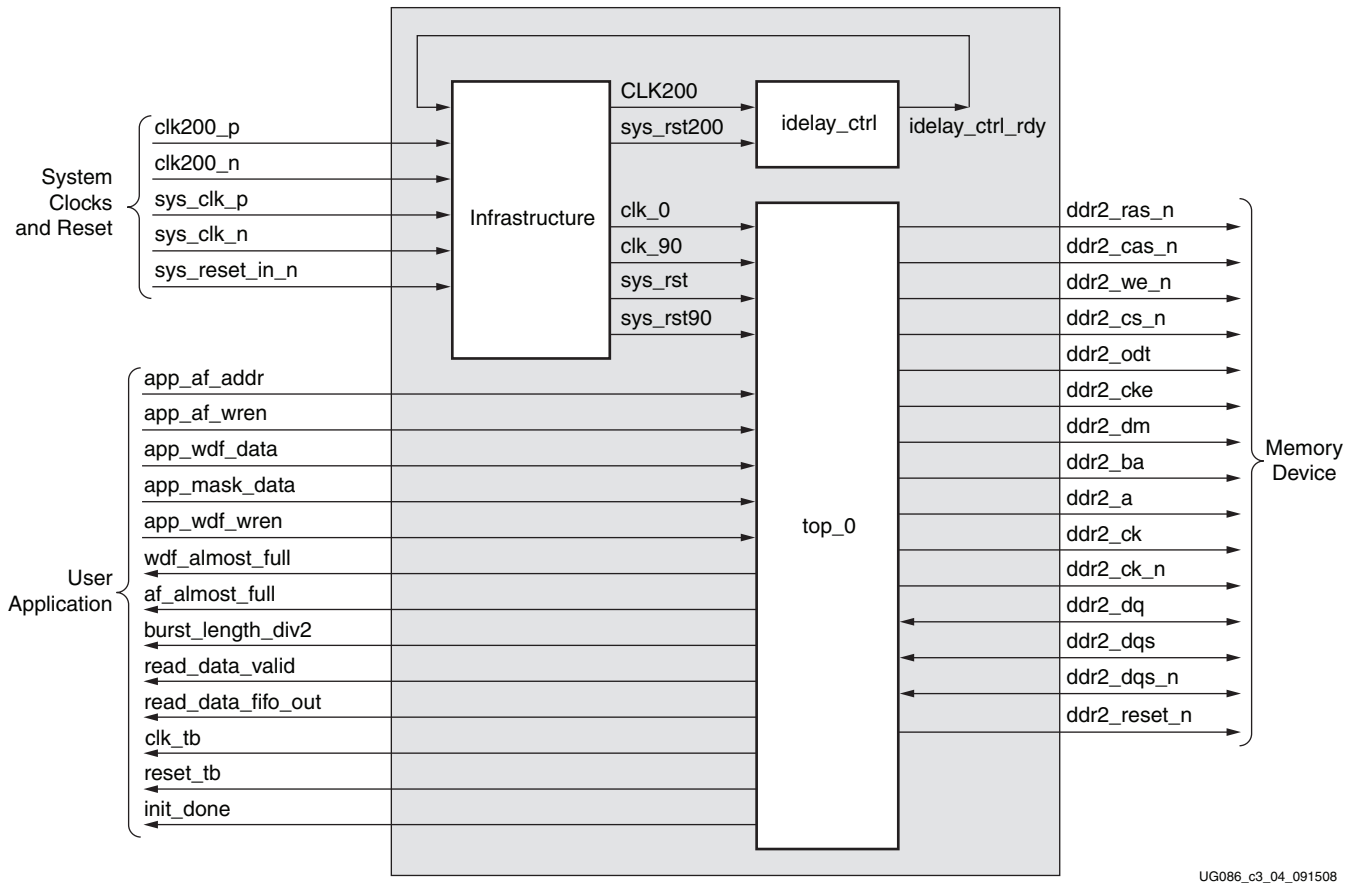


Figure 3-3: Top-Level Block Diagram of the DDR2 SDRAM Design with a DCM and a Testbench

All Memory Device ports do not necessarily appear for all MIG-generated designs. For example, port `ddr2_reset_n` appears in the port list for Registered DIMM designs only. Similarly, `ddr2_dqs_n` does not appear for single-ended DQS designs. Port `DDR2_DM` appears only for parts that contain a data mask; a few RDIMMs have no data mask, and `DDR2_DM` does not appear in the port list for them.

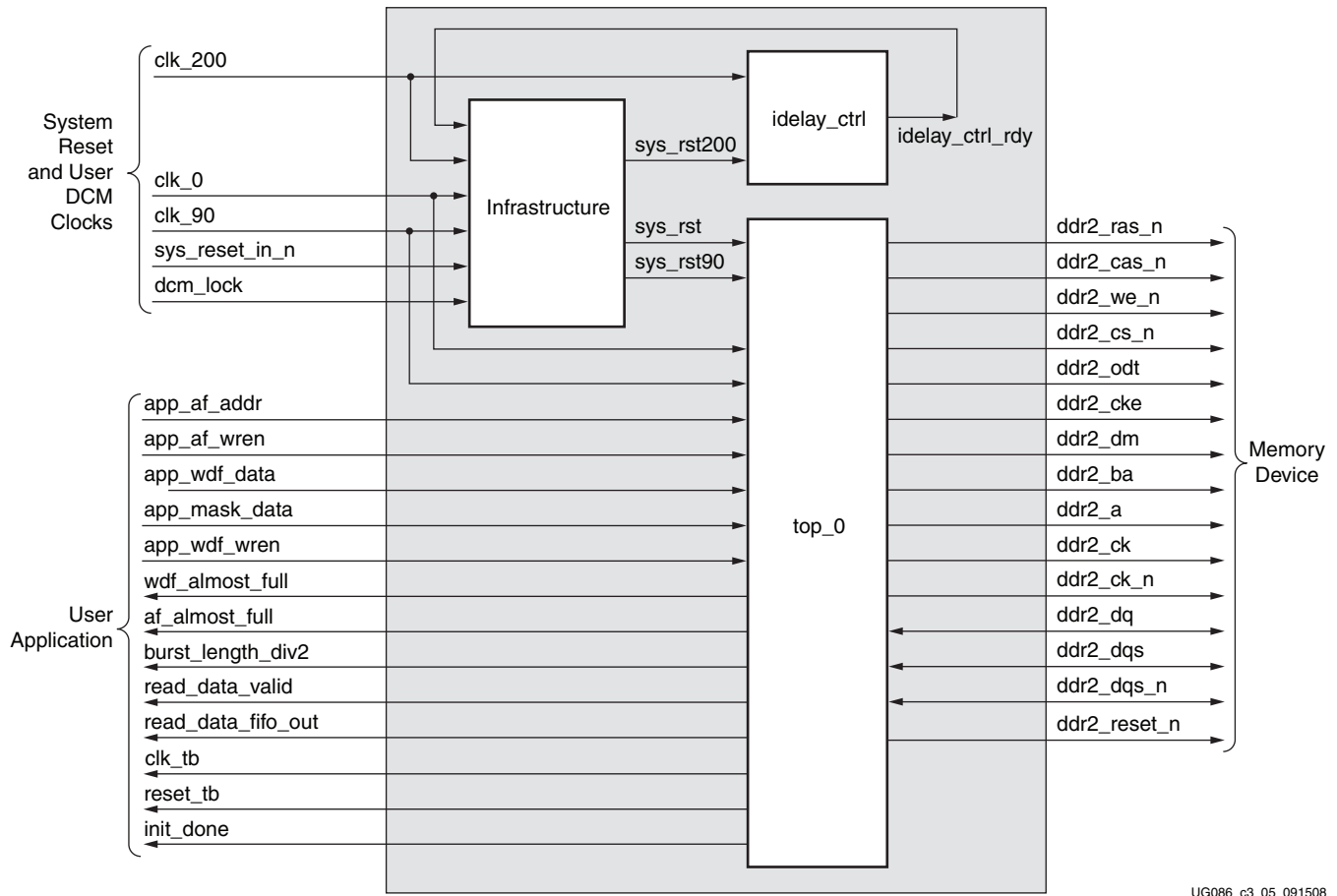
Figure 3-4 shows a top-level block diagram of a DDR2 SDRAM design with a DCM but without a testbench. The `sys_clk_p` and `sys_clk_n` pair are differential input system clocks. A DCM is instantiated in the infrastructure module that generates the required design clocks. The differential `clk200_p` and `clk200_n` are used for the `idelay_ctrl` element. The active-Low system reset signal is `sys_reset_in_n`. All design resets are gated by the `dcm_lock` signal. The user has to drive the user application signals. The design provides the `CLK_TB` and `RESET_TB` signals to the user to synchronize with the design. The `INIT_DONE` signal indicates the completion of initialization and calibration of the design.



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Figure 3-4: Top-Level Block Diagram of the DDR2 SDRAM Design with a DCM but without a Testbench

Figure 3-5 shows a top-level block diagram of a DDR2 SDRAM design without a DCM or a testbench. The user should provide all the clocks and the dcm_lock signal. These clocks should be single-ended. The active-Low system reset signal is sys_reset_in_n. All design resets are gated by the dcm_lock signal. The user application must have a DCM primitive instantiated in the design. All user clocks should be driven through BUFs. The user has to drive the user application signals. The design provides the CLK_TB and RESET_TB signals to the user to synchronize with the design. The INIT_DONE signal indicates the completion of initialization and calibration of the design.



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Figure 3-5: Top-Level Block Diagram of the DDR2 SDRAM Design without a DCM or a Testbench

Figure 3-6 shows a top-level block diagram of a DDR2 SDRAM design with a testbench but without a DCM. The user should provide all the clocks and the dcm_lock signal. These clocks should be single-ended. The active-Low system reset signal is sys_reset_in_n. All design resets are gated by the dcm_lock signal. The user application must have a DCM primitive instantiated in the design. All user clocks should be driven through BUFs. The ERROR output signal indicates whether the case passes or fails. The testbench module does writes and reads, and also compares the read data with the written data. The ERROR signal is driven High on data mismatches. The INIT_DONE signal indicates the completion of initialization and calibration of the design.

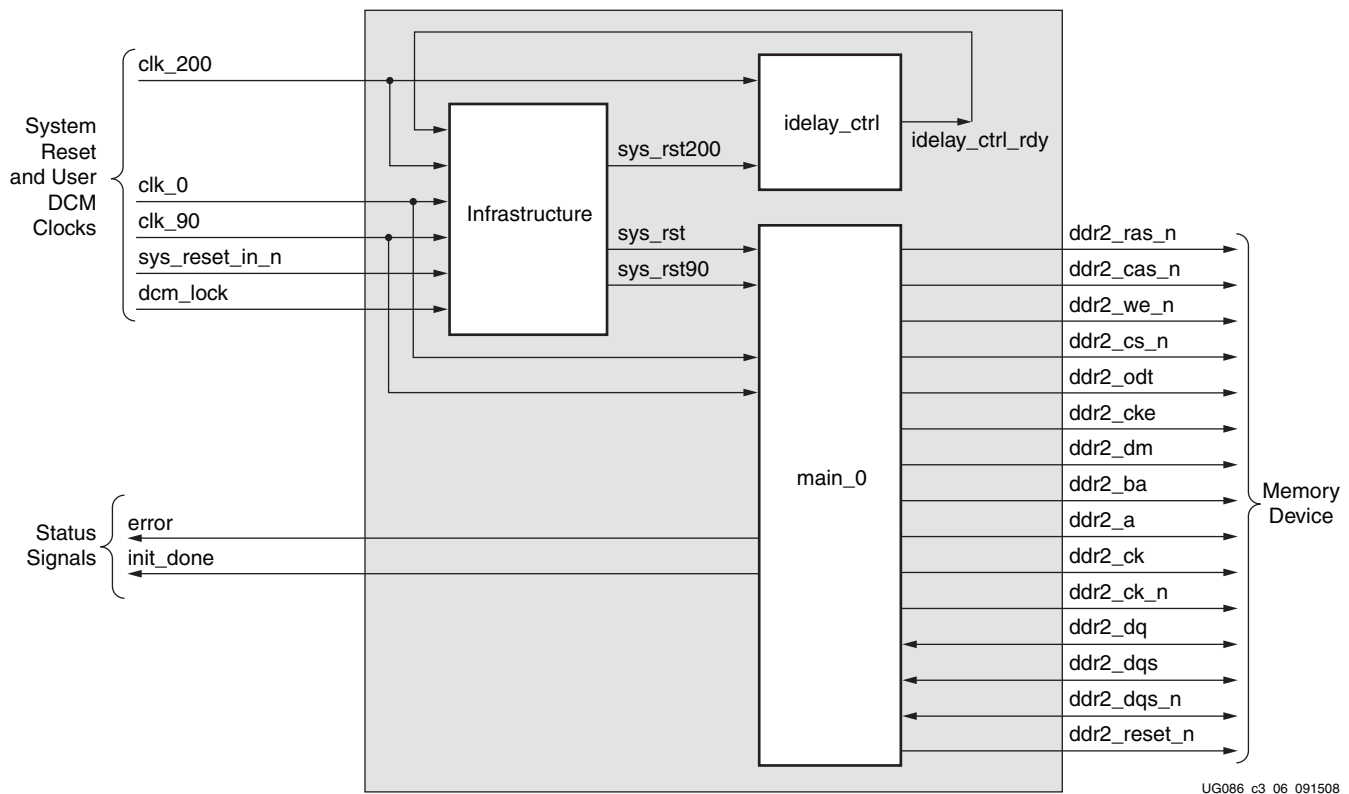


Figure 3-6: Top-Level Block Diagram of the DDR2 SDRAM Design with a Testbench but without a DCM

DDR2 Controller Submodules

Infrastructure

The infrastructure module generates the FPGA clock and reset signals. When differential clocking is used, `sys_clk_p`, `sys_clk_n`, `clk_200_p`, and `clk_200_n` signals appear. When single-ended clocking is used, `sys_clk` and `idly_clk_200` signals appear. In addition, clocks are available for design use and a 200 MHz clock is provided for the `IDELAYCTRL` primitive. Differential and single-ended clocks are passed through global clock buffers before connecting to a DCM. For differential clocking, the output of the `sys_clk_p/sys_clk_n` buffer is single-ended and is provided to the DCM input. Likewise, for single-ended clocking, `sys_clk` is passed through a buffer and its output is provided to the DCM input. The outputs of the DCM are `clk_0` (0° phase-shifted version of the input clock) and `clk_90` (90° phase-shifted version of the input clock). After the DCM is locked, the design is in the reset state for at least 25 clocks. The infrastructure module also generates all of the reset signals required for the design.

Figure 3-7 is a detailed block diagram of the DDR2 SDRAM controller. The five blocks shown are the subblocks of the top module. User backend signals are provided by the tool for designs with a testbench. The user has to drive these signals for designs without a testbench. The functions of these blocks are explained in the subsections following the figure.

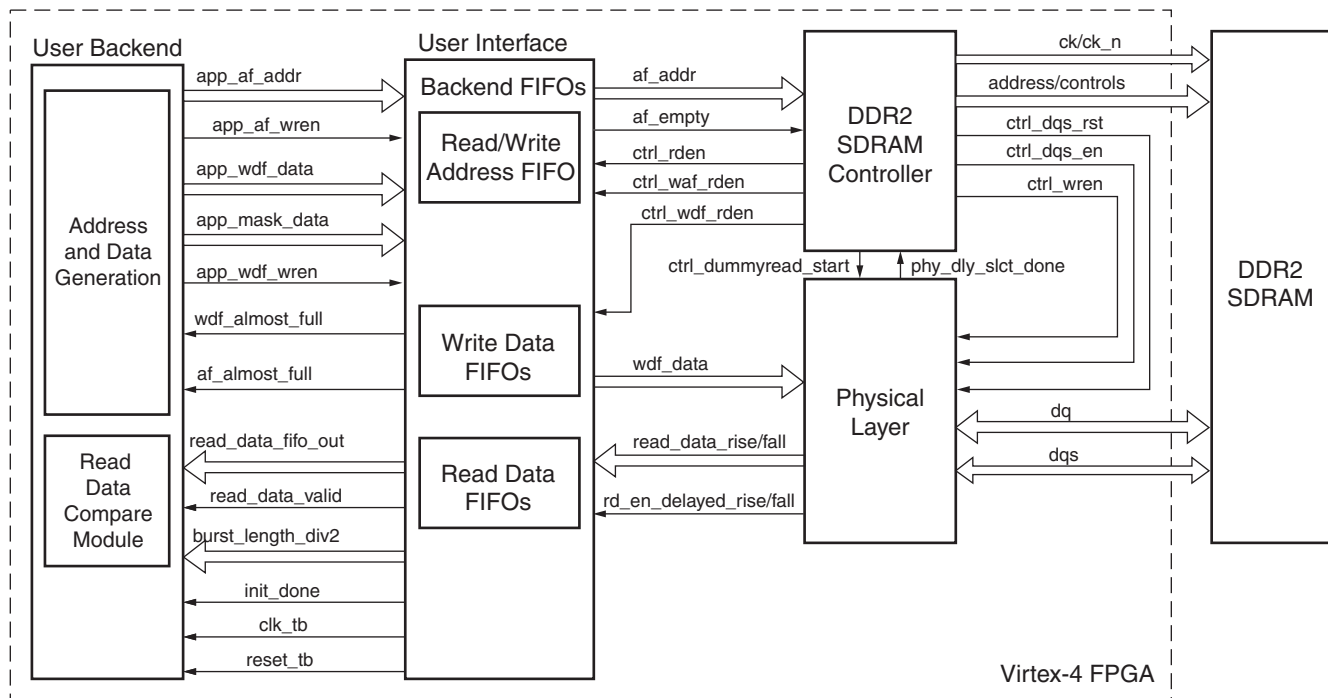


Figure 3-7: DDR2 Memory Controller Block Diagram

Controller

The DDR2 SDRAM `ddr2_controller` accepts and decodes user commands and generates read, write, and refresh commands. The DDR2 SDRAM controller also generates signals for other modules. The memory is initialized and powered-up using a defined process. The controller state machine handles the initialization process upon power-up. After memory initialization, the controller issues dummy read commands. During dummy reads, the

tap_logic module calibrates and delays the data to center-align with the FPGA clock. After the calibration is done, the controller issues a dummy write and pattern read commands to get the delay between the read command and IOB output data.

The delay, calculated in number of clocks, is used as a write-enable signal to the read data FIFOs. For deep designs, the DQ calibration and pattern calibration are done only on the last memory. For example, for four deep designs, the fourth memory is used for calibration. There is no reason to use the fourth memory because the controller retains the last chip select during initialization of memory. Thus the same chip select is used for calibration. XAPP701 [Ref 18] provides more details about the calibration architecture.

User Interface

This module stores write data, write addresses, and read addresses in FIFOs and receives read data from the memory. The rd_data and rd_data_fifos modules capture the data in the LUT-based RAMs. The rd_wr_addr_fifo and wr_data_fifo modules store the data and address in block RAMs. The FIFOs are built using FIFO16 primitives in rd_wr_addr_fifo, wr_data_fifo_16, and wr_data_fifo_8 modules. Each FIFO has two FIFO threshold attributes, ALMOST_EMPTY_OFFSET and ALMOST_FULL_OFFSET, that are set to 7 and F, respectively, in the RTL by default. These values can be changed as needed. For valid FIFO threshold offset values, refer to UG070 [Ref 7].

Once the calibration is done, the controller issues a pattern_write command with a known pattern (0xAA559966) to the memory. Then the controller issues a pattern_read command from the same location and compares the read data with the known pattern in the pattern_compare8 or the pattern_compare4 module. During the pattern_read command, the controller generates the ctrl_rden signal, which is delayed in the pattern_compare module to synchronize with the read data. This delay is applied to the ctrl_rden signal generated from the ddr2_controller module during a normal read to register the valid data in the internal FIFOs.

The FIRST_RISING logic is implemented in the pattern_compare module. FIRST_RISING is asserted when the first data is captured with respect to the falling edge of FPGA clock. This signal is used in rd_data_fifo to swap rise and fall data. In addition to the ODDR used to register output data (DQ) in each I/O, a second ODDR in the IOB controls the 3-state enable for the I/O. This is used to enable the write data output one-half clock cycle before the first data word and disable the write data one-half clock cycle after the last data word.

Test Bench

The MIG tool generates two RTL folders, example_design and user_design. The example_design folder includes the synthesizable test bench, while user_design does not include the test bench modules. The MIG test bench performs eight write commands and eight read commands in an alternating fashion. The number of words in a write command depends on the burst length. For a burst length of 4, the test bench writes a total of 32 data words for all eight write commands (16 rise data words and 16 fall data words). For a burst length of 8, the test bench writes a total of 64 data words. It writes the data pattern of FF, 00, AA, 55, 55 AA, 99, 66 in a sequence of which FF, AA, 55, and 99 are rise data words and 00, 55, AA, and 66 are fall data words for an 8-bit design. The falling edge data is the complement of the rising edge data. For a burst length of 4, the data sequence for the first write command is FF, 00, AA, 55, and the data sequence for the second write command is 55, AA, 99, 66. For a burst length of 8, the data pattern for the first write command is FF, 00, AA, 55, 55 AA, 99, 66 and the same pattern is repeated for all the remaining write commands. This data pattern is repeated in the same order based on the number of data words written. For data widths greater than 8, the same data pattern is concatenated for the other bits. For a 32-bit design and a burst length of 8, the data pattern for the first write

command is FFFFFFFF, 00000000, AAAAAAAA, 55555555, 55555555, AAAAAAAA, 99999999, 66666666.

Address generation logic generates eight different addresses for eight write commands. The same eight address locations are repeated for the following eight read commands. The read commands are performed at the same locations where the data is written. There are total of 32 different address locations for 32 write commands, and the same address locations are generated for 32 read commands. Upon completion of a total of 64 commands, including both writes and reads (eight writes and eight reads repeated four times), address generation rolls back to the first address of the first write command and the same address locations are repeated. The MIG test bench exercises only a certain memory area. The address is formed such that all address bits are exercised. During writes, a new address is generated for every burst operation on the column boundary.

During reads, comparison logic compares the read pattern with the pattern written, i.e., the FF, 00, AA, 55, 55 AA, 99, 66 pattern. For example, for an 8-bit design of burst length 4, the data written for a single write command is FF, 00, AA, 55. During reads, the read pattern is compared with the FF, 00, AA, 55 pattern. Based on a comparison of the data, a status signal error is generated. If the data read back is the same as the data written, the error signal is 0, otherwise it is 1. Comparison logic only compares the data bits and not the ECC data pattern. For example, for a 72-bit ECC design, comparison logic only compares 64 bits. The 8 MSBs (ECC bits) are not compared.

Infrastructure

The infrastructure module generates the FPGA clock and reset signals. When differential clocking is used, sys_clk_p, sys_clk_n, clk_200_p, and clk_200_n signals appear. When single-ended clocking is used, sys_clk and idly_clk_200 signals appear. In addition, clocks are available for design use and a 200 MHz clock is provided for the IDELAYCTRL primitive. Differential and single-ended clocks are passed through global clock buffers before connecting to a DCM. For differential clocking, the output of the sys_clk_p/sys_clk_n buffer is single-ended and is provided to the DCM input. Likewise, for single-ended clocking, sys_clk is passed through a buffer and its output is provided to the DCM input. The outputs of the DCM are clk_0 (0° phase-shifted version of the input clock) and clk_90 (90° phase-shifted version of the input clock). After the DCM is locked, the design is in the reset state for at least 25 clocks. The infrastructure module also generates all of the reset signals required for the design.

Idelay_ctrl

This module instantiates the IDELAYCTRL primitive of the Virtex-4 FPGA. The IDELAYCTRL primitive is used to continuously calibrate the individual delay elements in its region to reduce the effect of process, temperature, and voltage variations. A 200 MHz clock has to be fed to this primitive. For more information on IDELAYCTRLs, refer to [“Verify IDELAYCTRL Instantiation for Virtex-4 and Virtex-5 FPGA Designs” in Chapter 14](#).

DDR2 SDRAM Initialization and Calibration

DDR2 memory is initialized through a specified sequence as per both Micron and JEDEC specifications. The controller starts the memory initialization at power-up. Following the initialization, the relationship between the data and the FPGA clock is calculated using the tap_logic. The controller issues a dummy write command and a dummy read command to the memory and compares read data with the fixed pattern. During dummy reads, the tap_logic module calibrates and delays the data to center-align with the FPGA clock. XAPP701 [\[Ref 18\]](#) provides more details about the calibration architecture.

The sel_done port in the tap_logic module indicates the completion of the per-bit calibration. After the per-bit calibration is done, the controller does a read enable calibration. This calibration is used to determine the delay from read command to read data at rd_data_fifo. The delay between read command and read data is affected by the CAS latency and additive latency parameters, the PCB traces, and the I/O buffer delays. This in turn is used to generate a write enable to rd_data_fifo so that valid data is registered. The controller writes a known fixed pattern and reads back the data. The read data is compared against the known fixed pattern. The comp_done port in the rd_data module indicates the completion of the read enable calibration.

The init_done port indicates the completion of both per-bit calibration and read enable calibration. After initialization and calibration is done, the controller can start issuing user commands to the memory.

Direct-Clocking Interface Clocking Scheme

Figure 3-8, page 141 shows the clocking scheme for this design. Global and local clock resources are used.

The global clock resources consist of a DCM, two BUFGs on DCM output clocks, and one BUFG for clk_200. The local clock resources consist of regional I/O clock networks (IBUFIO). The global clock architecture is discussed in this section.

The MIG tool allows the user to customize the design such that the DCM is not included. In this case clk_0, clk_90 and IDELAYCTRL clock clk_200 must be supplied by the user.

Global Clock Architecture

The user must supply two input clocks to the design:

- A system clock running at the target frequency for the memory
- A 200 MHz clock for the IDELAYCTRL blocks

These clocks can be either single ended or differential. User can select single-ended or differential clock input option from MIG GUI. Differential clocks are connected to the IBUFGDS and single ended clock is connected to IBUFG.

The system clock from the output of the IBUFGDS or the IBUFG is connected to the DCM to generate the various clocks used by the memory interface logic.

The clk_200 output of the IBUFGDS or the IBUFG is connected to the BUFG. The output of the BUFG is used for IDELAY IOB delay blocks for aligning read capture data.

The DCM generates two separate synchronous clocks for use in the design. This is shown in Table 3-6, page 141 and Figure 3-8, page 141. The clock structure is same for both example design and user design. For designs with out DCM instantiation, DCM and the BUFGs should be instantiated at user end to generate the required clocks.

Table 3-6: DDR2 Interface Design Clocks

Clock	Description	Logic Domain
clk_0	Skew compensated replica of the input system clock.	The clock for the controller and the user interface logic, most of the DDR2 bus-related I/O flip-flops (e.g., memory clock, control/address, output DQS strobe, and DQ input capture). This is used to register the data, address, and command signals, and the address and data enables for the user interface logic ⁽¹⁾ . This clock is also used to generate read data, read data valid, and FIFO status signals.
clk90_0	90° phase-shifted version of CLK0.	Used in the write data path section of physical layer. Controls write path control logic, DDR2 side of the Write Data FIFO, and output flip-flops for DQ.

Notes:

1. See "User Interface Accesses," page 143 for timing requirements and restrictions on the user interface signals.

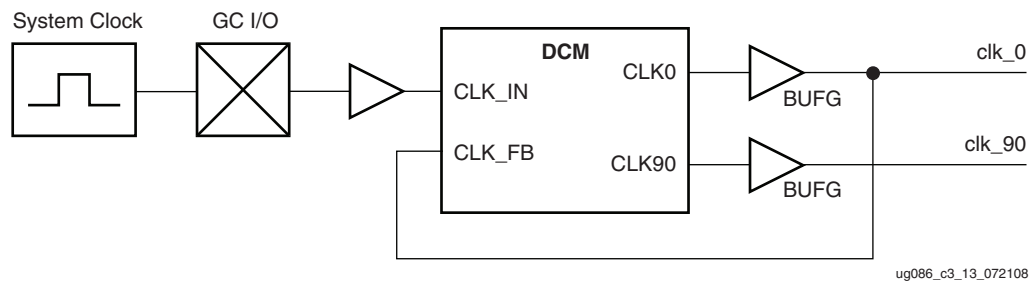


Figure 3-8: Clocking Scheme for DDR2 Interface Logic

DDR2 SDRAM System and User Interface Signals

Table 3-7 describes the DDR2 SDRAM system interface signals. The system interface signals are the clocks and the reset signals given by the user to the FPGA. The sys_clk_p and sys_clk_n pair are the two clocks provided to the design. They must have a phase difference of 180° with respect to each other. Similarly, clk200_p and clk_200N are 200 MHz differential clocks for the IDELAYCTRL module. The sys_reset_in_n signal resets all the logic.

Table 3-7: DDR2 SDRAM Controller System Interface Signals (with a DCM)

Signal Name	Direction	Description
sys_clk_p, sys_clk_n	Input	Differential input clock to the DCM. The DDR2 controller and memory operate at this frequency.
clk200_p, clk200_n	Input	Differential clock used in the idelay_ctrl logic.
sys_reset_in_n	Input	Active-Low reset to the DDR2 controller.

Table 3-8 shows the system interface signals for designs without a DCM. clk_0, clk_90, and clk_200 are single-ended input clocks. The clk_90 signal must have a phase difference of 90° with respect to clk_0. The clk_200 signal is the clock used for the IDELAYCTRL primitives in Virtex-4 FPGAs.

Table 3-8: DDR2 SDRAM Controller System Interface Signals (without a DCM)

Signal	Direction	Description
clk_0	Input	The DDR2 SDRAM controller and memory operates on this clock.
sys_reset_in_n	Input	Active-Low reset to the DDR2 SDRAM controller. This signal is used to generate the synchronous system reset.
clk_90	Input	90° phase-shifted clock with the same frequency as clk_0.
clk_200	Input	200 MHz differential input clock for the IDELAYCTRL primitive of Virtex-4 FPGAs.
dcm_lock	Input	This status signal indicates whether the DCM is locked or not. It is used to generate the synchronous system reset.

Table 3-9 describes the DDR2 SDRAM user interface signals.

Table 3-9: DDR2 SDRAM Controller User Interface Signals

Signal Name ⁽¹⁾	Direction	Description
CLK_TB	Output	All user interface signals must be synchronized with respect to CLK_TB.
RESET_TB	Output	Reset signal for the User Interface.
BURST_LENGTH_DIV2[2:0]	Output	This signal determines the data burst length for each write address. 010: burst length = 4 100: burst length = 8
WDF_ALMOST_FULL	Output	This signal indicates the ALMOST_FULL status of the Write Data FIFO. When this signal is asserted, the user can write 5 more locations into the FIFO in designs generated with a testbench and 14 more locations in designs without a testbench.
APP_WDF_DATA[2n-1:0]	Input	User write data to the memory, where <i>n</i> indicates the data width of the interface. The user data is twice the data width of the interface. The most-significant bits contain the rising-edge data and the least-significant bits contain the falling-edge data.
APP_MASK_DATA[2m-1:0]	Input	User mask data to the memory, where <i>m</i> indicates the data mask width of the interface. The mask data is twice the mask width of the interface. The most-significant bits contain the rising-edge mask data and the least-significant bits contain the falling-edge mask data. These signals are not present when the memory part does not have mask support (for example, certain Registered DIMMs) or when the data mask option is not selected in the MIG GUI.
APP_WDF_WREN	Input	Write Enable signal to the Write Data FIFO.
AF_ALMOST_FULL	Output	This signal indicates the ALMOST_FULL status of the Address FIFO. The user can issue eight more locations into the FIFO after AF_ALMOST_FULL is asserted.

Table 3-9: DDR2 SDRAM Controller User Interface Signals (Cont'd)

Signal Name ⁽¹⁾	Direction	Description
APP_AF_ADDR[35:0] ⁽²⁾	Input	<p>The user address consists of a memory address and dynamic commands. Bits [31:0] are the memory read/write address. Bits [31:0] form the memory chip select, bank address, row address, and column address.</p> <p>Bit 35 is reserved for internal use of the controller. Bits [34:32] represent the following dynamic commands:</p> <p>001: Auto Refresh 010: Precharge 100: Write 101: Read</p> <p>Other combinations are invalid. Functionality of the controller is unpredictable for unimplemented commands.</p>
APP_AF_WREN	Input	Write Enable signal to the Address FIFO.
READ_DATA_FIFO_OUT[2n-1:0]	Output	Read data from the memory, where <i>n</i> indicates the data width of the interface. The most-significant bits of the read data consist of the rising-edge data and the least-significant bits consist of the falling-edge data.
READ_DATA_VALID	Output	This signal is asserted to indicate the read data is available to the user.
INIT_DONE	Output	This signal indicates the completion of initialization and calibration of the design.

Notes:

1. All user interface signal names are prepended with a controller number. DDR2 SDRAM devices support multicontroller operation, where a maximum of eight controllers can be selected by the user from MIG. For example, when the user selects eight controllers, the signal names have the following format: cntrl0_user_signal, cntrl1_user_signal, cntrl2_user_signal, cntrl3_user_signal, cntrl4_user_signal, cntrl5_user_signal, cntrl6_user_signal, and cntrl7_user_signal. See “User Interface Accesses” for timing requirements and restrictions on the user interface signals.
2. Linear addressing is used, i.e., the row address immediately follows the column address bits, and the bank address follows the row address bits, thus supporting more devices. The number of address bits used depends on the density of the memory part. The controller ignores the unused bits, which can all be tied High.

User Interface Accesses

The user backend logic communicates with the memory controller through a FIFO-based user interface. This interface consists of three related buses:

- A Command/Address FIFO bus, which accepts write/read commands as well as the corresponding memory address from the user
- A Write Data FIFO bus, which accepts the corresponding write data when the user issues a write command on the Command/Address bus
- A Read bus on which the corresponding read data for an issued read command is returned

The user interface has the following timing and signaling restrictions:

- Commands and write data cannot be written by the user until calibration is complete (as indicated by INIT_DONE). In addition, the following interface signals need to be held Low until calibration is complete: APP_AF_WREN, APP_WDF_WREN, APP_WDF_DATA, and APP_MASK_DATA. Failure to hold these signals Low causes errors during calibration. This restriction arises from the fact that the Write Data FIFO

is used during calibration to hold the training patterns for the various stages of calibration.

- When issuing a write command, the first write data word must be written to the Write Data FIFO no more than two clock cycles after the write command is issued. This restriction arises from the fact that the controller assumes write data is available when it receives the write command from the user.
- The `clk_tb` signal is connected to `clk_0` in the controller. If the user clock domain is different from `clk_0` / `clk_tb` of the MIG, the user should add FIFOs for all data inputs and outputs of the controller in order to synchronize them to the `clk_tb`.

Write Interface

Figure 3-9 shows the user interface block diagram for write operations.

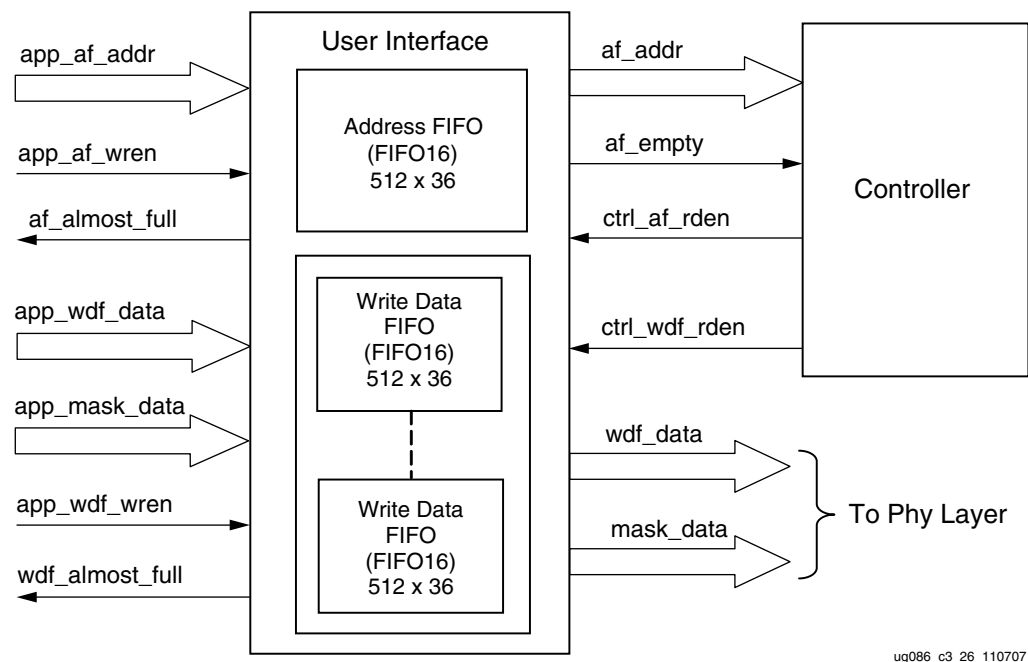


Figure 3-9: User Interface Block Diagram for Write Operations

The following steps describe the architecture of the Address and Write Data FIFOs and show how to perform a write burst operation to DDR2 SDRAM from the user interface.

1. The user interface consists of an Address FIFO and a Write Data FIFO. These FIFOs are constructed using Virtex-4 FPGA FIFO16 primitives with a 512 x 36 configuration. The 36-bit architecture comprises one 32-bit port and one 4-bit port. For Write Data FIFOs, the 32-bit port is used for data bits and the 4-bit port is used for mask bits. Mask bits are available only when supported by the memory part *and* when data mask is enabled in the MIG GUI. Some memory parts, such as Registered DIMMs of x4 parts, do not support mask bits.
2. The Common Address FIFO is used for both write and read commands, and comprises a command part and an address part. Command bits discriminate between write and read commands.
3. User interface data width `app_wdf_data` is twice that of the memory data width. For an 8-bit memory width, the user interface is 16 bits consisting of rise data and fall data.

For every 8 bits of data, there is a mask bit. For 72-bit memory data, the user interface data width `app_wdf_data` is 144 bits, and the mask data `app_mask_data` is 18 bits.

4. The minimum configuration of the Write Data FIFO is 512 x 36 for a memory data width of 8 bits. For an 8-bit memory data width, the least-significant 16 bits of the data port are used for write data and the least-significant two bits of the 4-bit port are used for mask bits. The controller internally pads all zeros for the most-significant 16 bits of the 32-bit port and the most-significant two bits of the 4-bit port.
5. Depending on the memory data width, MIG instantiates multiple FIFO16s to gain the required width. For designs using 8-bit data width, one FIFO16 is instantiated; for 72-bit data width, a total of five FIFO16s are instantiated. The bit architecture comprises 16 bits of rising-edge data, 2 bits of rising-edge mask, 16 bits of falling-edge data, and 2 bits of falling-edge mask, which are all stored in a FIFO16. MIG routes the `app_wdf_data` and `app_mask_data` to FIFO16s accordingly.
6. The user can initiate a write to memory by writing to the Address FIFO and the Write Data FIFO when the FIFO Full flags are deasserted and after the `init_done` signal is asserted. Status signal `af_almost_full` is asserted when Address FIFO is full, and similarly `wdf_almost_full` is asserted when Write Data FIFO is full.
7. Both the Address FIFO and Write Data FIFO Full flags are deasserted with power-on.
8. The user should assert the Address FIFO write-enable signal `app_af_wren` along with address `app_af_addr` to store the write address and write command into the Address FIFO.
9. The user should assert the Data FIFO write-enable signal `app_wdf_wren` along with write data `app_wdf_data` and mask data `app_mask_data` to store the write data and mask data into the Write Data FIFO. The user should provide both rise and fall data together for each write to the Data FIFO.
10. The controller reads the Address FIFO by issuing the `ctrl_af_rden` signal. The controller reads the Write Data FIFO by issuing the `ctrl_wdf_rden` signal after the Address FIFO is read. It decodes the command part after the Address FIFO is read.

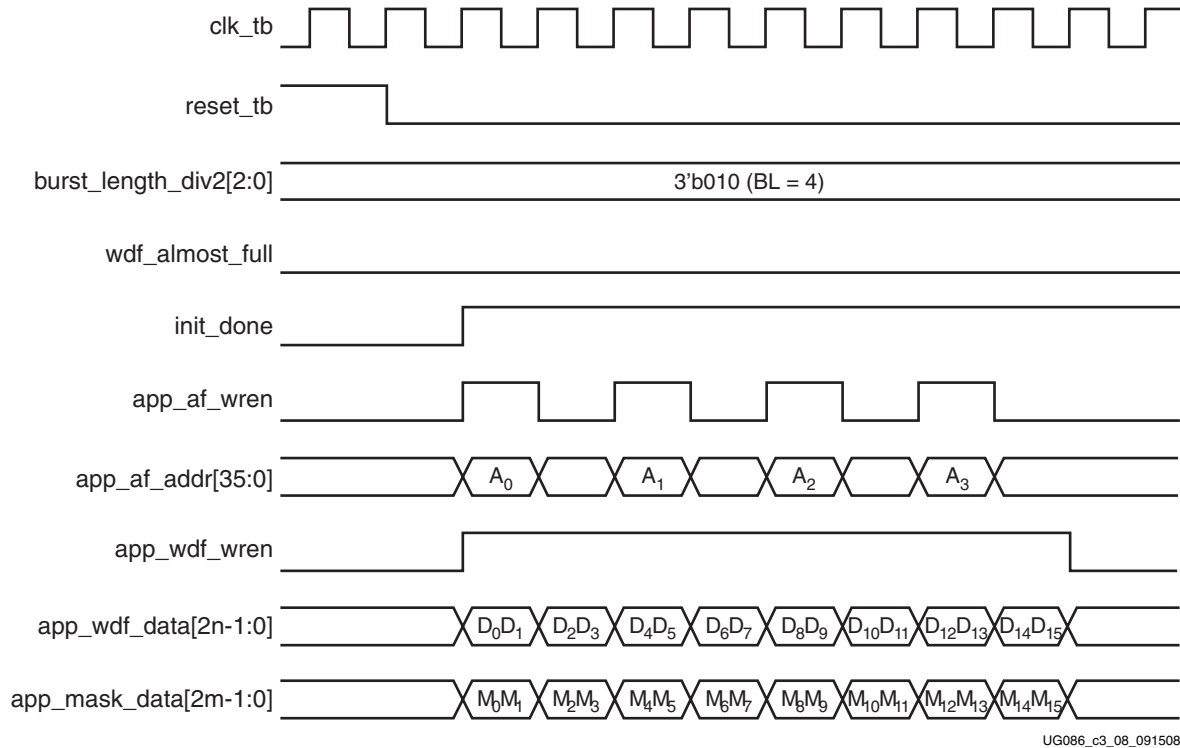


Figure 3-10: DDR2 SDRAM Write Burst (BL = 4) for Four Bursts

11. The write command timing diagram in Figure 3-10 is derived from the MIG-generated testbench. As shown (burst length of 4), each write to the Address FIFO must be coupled with *two* writes to the Data FIFO. Similarly, for a burst length of 8, every write to the Address FIFO must be coupled with *four* writes to the Data FIFO. Failure to follow this rule can cause unpredictable behavior.

Note: The user can start filling the Write Data FIFO two clocks after the Address FIFO is written, because there is a two-clock latency between the command fetch and reading the Data FIFO. Using the terms shown in Figure 3-11, therefore, the user can assert the A0 address two clocks before D0D1.

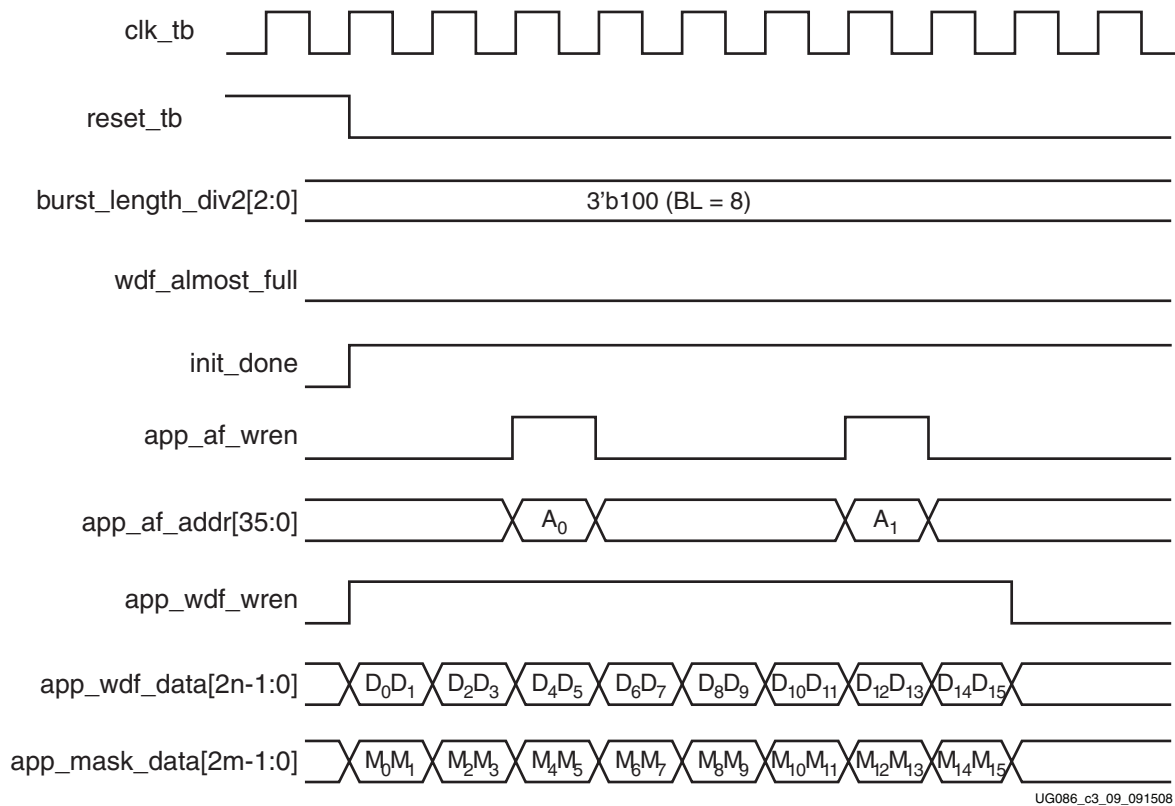


Figure 3-11: DDR2 SDRAM Write Burst (BL = 8) for Two Bursts

12. The write command timing diagram in Figure 3-11 is derived from the MIG-generated testbench. As shown (burst length of 8), each write to the Address FIFO must be coupled with *four* writes to the Data FIFO. Because the controller first reads the address and command together, the address need not coincide with the last data. After the command is analyzed (nearly two clocks later for a worst-case timing scenario), the controller sequentially reads the data in four clocks. Thus, there are six clocks from the time the address is read to the time the last data is read.

Correlation between the Address and Data FIFOs

There is a worst-case two-cycle latency from the time the address is loaded into the address FIFO on APP_AF_ADDR[35:0] to the time the controller decodes the address. Because of this latency, it is not necessary to provide the address on the last clock where data is entered into the data FIFO. If the address is written before the last data phase, the overall efficiency and performance increases because it eliminates or reduces the two-cycle latency. However, if the address is written before data is input into the data FIFO, a FIFO empty condition might result because the Data FIFO does not contain valid data.

Based on these considerations, Xilinx recommends entering the address into the address FIFO between the first data phase and the next-to-last data phase. For a burst of four or eight, this means the Address can be asserted two clocks before the first data phase. This implementation increases efficiency by reducing the two clock latency and guarantees that valid data is available in the Data FIFO.

Read Interface

Figure 3-12 shows a block diagram of the read interface.

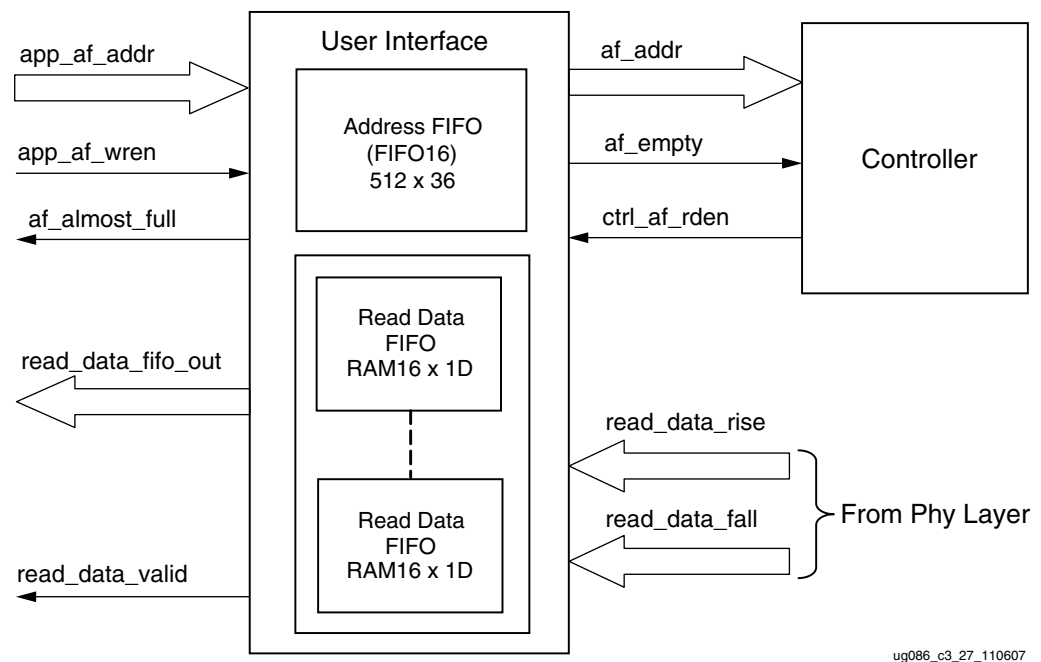


Figure 3-12: User Interface Block Diagram for Read Operation

The following steps describe the architecture of the Read Data FIFOs and show how to perform a burst read operation from DDR SDRAM from the user interface.

1. The read user interface consists of an Address FIFO and a Read Data FIFO. The Address FIFO is common to both read and write operations. The Read Data FIFOs are constructed using Virtex-4 FPGA Distributed RAMs with a 16 x 1 configuration. MIG instantiates a number of RAM16Ds depending on the data width. For example, for 8-bit data width, MIG instantiates a total of 16 RAM16Ds, 8 for rising-edge data and 8 for falling-edge data. Similarly, for 72-bit data width, MIG instantiates a total of 144 RAM16Ds, 72 for rising-edge data and 72 for falling-edge data.
2. The user can initiate a read to memory by writing to the Address FIFO when the FIFO Full flag `af_almost_full` is deasserted and after `init_done` is asserted.
3. To write the read address and read command into the Address FIFO, the user should issue the Address FIFO write-enable signal `app_af_wren` along with read address `app_af_addr`.
4. The controller reads the Address FIFO containing the address and command. After decoding the command, the controller generates the appropriate control signals to memory.
5. Prior to the actual read and write commands, the design calibrates the latency (number of clock cycles) from the time the read command is issued to the time data is received. Using this pre-calibrated delay information, the controller generates the write-enable signals to the Read Data FIFOs.
6. The `read_data_valid` signal is asserted when data is available in the Read Data FIFOs.

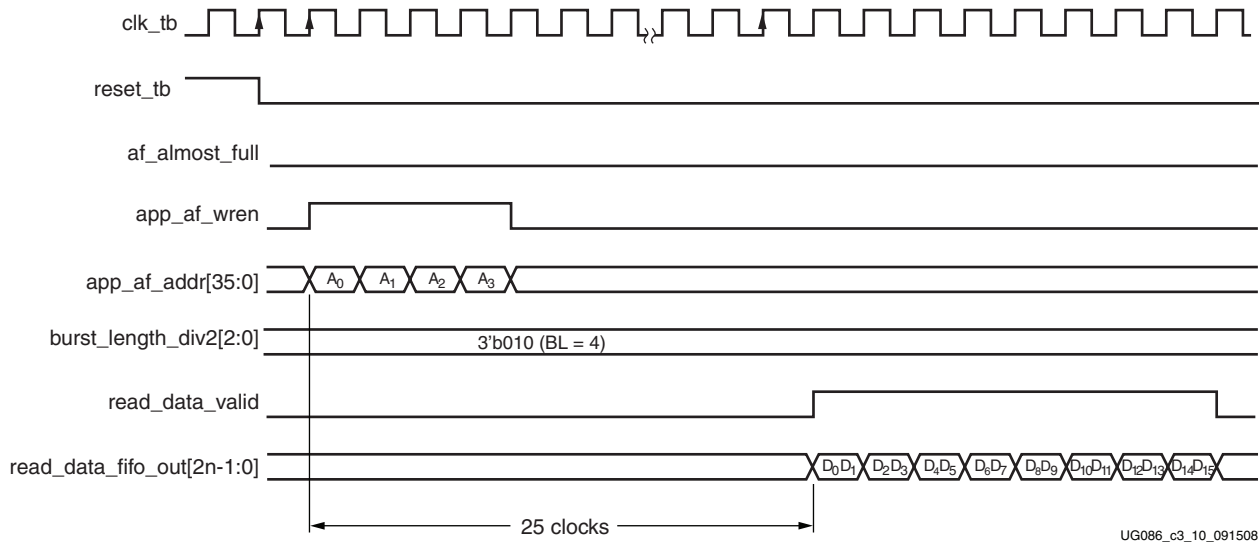


Figure 3-13: DDR2 SDRAM Read Burst (BL = 4) for Four Bursts

7. [Figure 3-13](#) shows the user interface timing diagram for a burst length of 4, and [Figure 3-14](#) shows the user interface timing diagram for a burst length of 8. Both the cases shown here are for a CAS latency of 3 at 200 MHz. The read latency is calculated from the point when the read command is given by the user to the point when the data is available with the read_data_valid signal. The minimum latency in this case is 25 clocks, where no precharge is required, no auto-refresh request is pending, the user commands are issued after initialization is completed, and the first command issued is a Read command. Controller executes the commands only after initialization is done as indicated by the init_done signal.
8. After the address and command are loaded into the Address FIFO, it takes 25 clock cycles minimum for the controller to assert the read_data_valid signal.
9. Read data is available only when the read_data_valid signal is asserted. The user should access the read data on every positive edge of the read_data_valid signal.

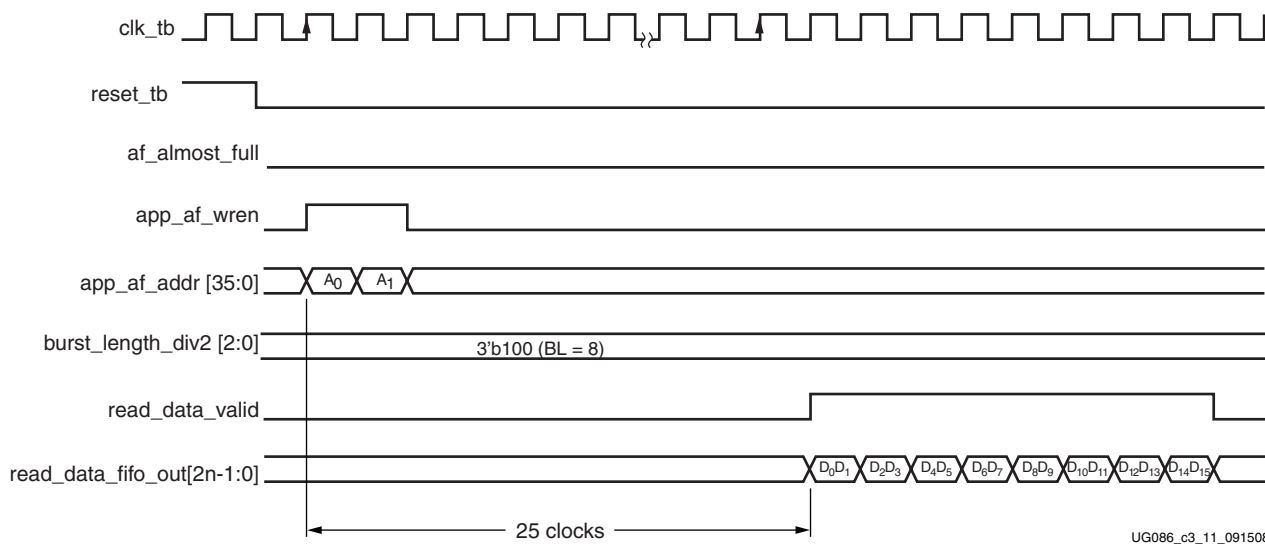


Figure 3-14: DDR2 SDRAM Read Burst (BL = 8) for Two Bursts

The 25 clocks from the read command to the read data, as shown in Figure 3-13 and Figure 3-14, are broken up as indicated in Table 3-10.

Table 3-10: Read Command to Read Data Clock Cycles

Parameter	Number of Clocks
Read Address to Empty Deassert	7 clocks
Empty to Active Command	5.5 clocks
Active to Read Command	3 clocks
Memory Read Command to Read Data Valid	9.5 clocks
Total:	25 clocks

In general, read latency varies based on the following parameters:

- CAS latency (CL) and additive latency (AL)
- The number of commands already in the FIFO pipeline before the read command is issued
- Whether an ACTIVATE command needs to be issued to open the new bank/row
- Whether a PRECHARGE command needs to be issued to close a previously opened bank
- Specific timing parameters for the memory, such as T_{RAS} and T_{RCD} in conjunction with the bus clock frequency
- Commands might be interrupted, and banks/rows might be forcibly closed when the periodic AUTO REFRESH command is issued
- If the user issues the commands before initialization is complete, the latency cannot be determined
- Board-level and chip-level (for both memory and FPGA) propagation delays

User to Controller Interface

Table 3-11 lists the signals between the User interface and the controller.

Table 3-11: Signals between User Interface and Controller

Port Name	Port Width	Port Description	Notes
af_addr	36	Output of the Address FIFO in the user interface. The mapping of these address bits is: [31:0]: Memory Address (CS, Bank, Row, Column) [34:32]: Dynamic Command Request [35]: Reserved	Monitor FIFO-full status flag to write address into the Address FIFO
af_empty	1	The user interface Address FIFO empty status flag output. The user application can write to the Address FIFO when this signal is asserted until the write data FIFO-full status flag is asserted.	FIFO16 Almost Empty flag

Table 3-11: Signals between User Interface and Controller (Cont'd)

Port Name	Port Width	Port Description	Notes
ctrl_af_RdEn	1	Read Enable input to Address FIFO in the user interface.	This signal is asserted for one clock cycle when the controller state is write, read, Precharge All, or Auto Refresh resulting from dynamic command requests. Figure 3-16 shows the timing waveform for burst length of eight with four back-to-back writes followed by four back-to-back reads.
ctrl_Wdf_RdEn	1	Read Enable input to Write Data FIFO in the user interface.	The controller asserts this signal two clock cycles after the first write state. This signal remains asserted for two clock cycles for a burst length of four and four clock cycles for a burst length of eight. Figure 3-16 shows the timing waveform. Sufficient data must be available in Write Data FIFO associated with a write address for the required burst length before issuing a write command. For example, for a 64-bit data bus and a burst length of four, the user should input two 128-bit data words in the Write Data FIFO for every write address before issuing the write command.

The memory address (af_addr) includes the column address, row address, bank address, and chip-select width for deep memory interfaces.

Column Address

```
[column_address - 1:0]
```

Row Address

```
[column_address + row_address - 1:column_address]
```

Bank Address

```
[column_address + row_address + bank_address - 1:column_address + row_address]
```

Chip Select

```
[column_address + row_address + bank_address + chip_address - 1:column_address + row_address + bank_address]
```

Dynamic Command Request

Table 3-12 lists commands not required for normal operation of the controller. The user has the option of requesting these commands if the commands are required by their application.

Table 3-12: Optional Commands

Command	Description
001	Auto Refresh
010	Precharge

Table 3-12: Optional Commands (Cont'd)

Command	Description
100	Write
101	Read

Figure 3-15 describes four consecutive writes followed by four consecutive reads with a burst length of 8.

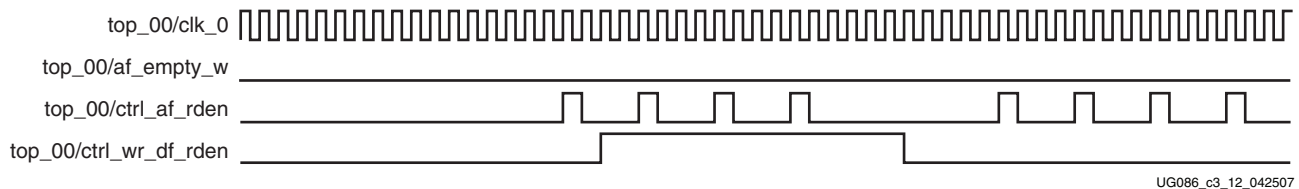


Figure 3-15: Consecutive Writes Followed by Consecutive Reads with Burst Length of 8

Controller to Physical Layer Interface

Table 3-13 lists the signals between the controller and the physical layer.

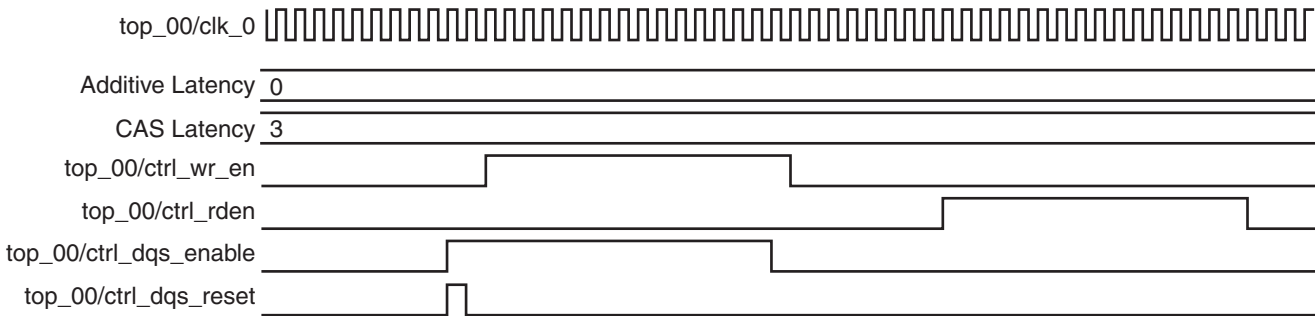
Table 3-13: Signals between the Controller and Physical Layer

Port Name	Port Width	Port Description	Notes
ctrl_Dummyread_Start	1	Output from the controller to the physical layer. When asserted, the physical layer begins strobe and data calibration after memory initialization.	This signal is asserted after read strobe begins to toggle in the dummy read state. This signal is deasserted when the phy_Dly_Slct_Done signal is asserted.
phy_Dly_Slct_Done	1	Output from the physical layer to the controller indicating calibration is complete.	This signal is asserted after data bits have been delayed to center align with respect to the FPGA global clock. The ctrl_Dummyread_Start signal is deasserted when the phy_Dly_Slct_Done signal is asserted. Normal operation begins after this signal is asserted.
ctrl_Dqs_Rst	1	Output from the controller to the physical layer for the write strobe preamble.	This signal is asserted for one clock cycle during a write. The CAS latency and AL values determine how many clock cycles after the first write state this signal is asserted. Figure 3-16 shows the timing waveform for this signal with CAS latency of 3 and AL of 0 for four back-to-back writes with a burst length of 8.

Table 3-13: Signals between the Controller and Physical Layer (Cont'd)

Port Name	Port Width	Port Description	Notes
ctrl_Dqs_En	1	Output from the controller to the physical layer for a write strobe.	This signal is asserted for three clock cycles during a write with a burst length of four and five clock cycles with a burst length of 8. The CAS latency and AL values determine how many clock cycles after the first write or burst write state this signal is asserted. Figure 3-16 shows the timing waveform for this signal with CAS latency of 3 and AL of 0 for four back-to-back writes with a burst length of 8.
ctrl_WrEn	1	Output from the controller to the physical layer for write data three-state control.	This signal is asserted for two clock cycles during a write with a burst length of 4 and for four clock cycles with a burst length of 8. The CAS latency and AL values determine how many clock cycles after the first write or burst write state this signal is asserted. Figure 3-16 shows the timing waveform for this signal with CAS latency of 3 and AL of 0 for four back-to-back writes with a burst length of 8.

Figure 3-16 describes the timing waveform for control signals from the controller to the physical layer.



UG086_c3_13_042507

Figure 3-16: Timing Waveform for Control Signals from the Controller to the Physical Layer

The following examples provide user address formats for different densities of components and DIMMs in deep memory designs. These are examples only, not associated with any specific memory part number from memory data sheets.

Case 1: 256 Mb (x4 component)

Density	256 Mb (256 Mb x 4 = 1 Gb)
Depth	4
Row address	13
Column address	11
Bank address	2
Rank/chip + deep address	2

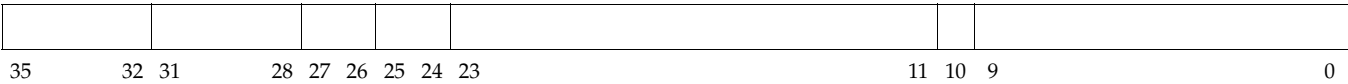
[illegible]

A10-A0	Column address
A23-A11	Row address
A25-A24	Bank address
A27 -A26	Rank + deep address
A31-A28	Assigned to all zeros
A34-A32	Dynamic commands
A35	Reserved for internal use

Case 2: 256 Mb (x8 component)

Density	256 Mb (256 Mb x 3 = 768 Mb)
Depth	3
Row address	13
Column address	10
Bank address	2
Rank/chip + deep address	2

Write Address/Read Address:

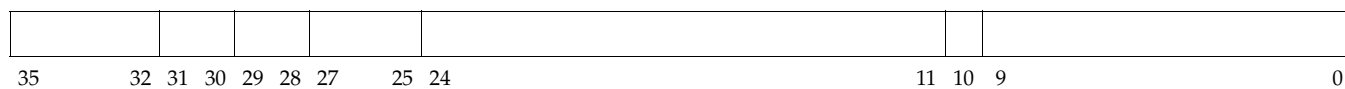


A9-A0	Column address
A22-A10	Row address
A24-A23	Bank address
A26-A25	Rank + deep address
A31-A27	Assigned to all zeros
A34-A32	Dynamic commands
A35	Reserved for internal use

Case 3: 256 Mb (x16 component)

Density	256 Mb (256 Mb x 2 = 512 Mb)
Depth	2
Row address	13
Column address	9
Bank address	2
Rank/chip + deep address	1

Write Address/Read Address:



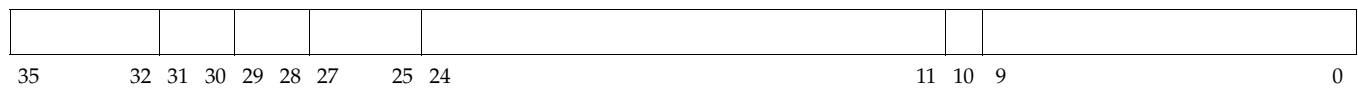
A8-A0	Column address
A21-A9	Row address
A23-A22	Bank address
A24	Rank + deep address
A31-A25	Assigned to all zeros
A34-A32	Dynamic commands
A35	Reserved for internal use

DIMMs

Case 1: 2 GB

Density	1 GB (1 x 2 = 2 GB)
Depth	2
Row address	14
Column address	10
Bank address	3
Rank/chip + deep address	2

Write Address/Read Address:

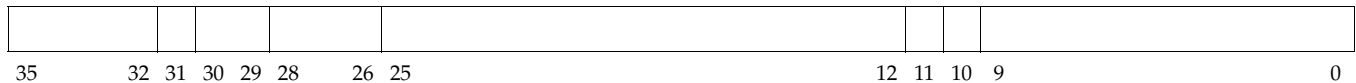


A9-A0	Column address
A23-A10	Row address
A26-A24	Bank address
A28-A27	Rank + deep address
A31-A29	Assigned to all zeros
A34-A32	Dynamic commands
A35	Reserved for internal use

Case 2: (8 GB)

Density	4 GB (4 x 2 = 8 GB)
Depth	2
Row address	14
Column address	11
Bank address	3
Rank/chip + deep address	2

Write Address/Read Address:



A10-A0	Column address
A24-A11	Row address
A27-A25	Bank address
A29-A28	Rank + deep address
A31-A30	Assigned to zeros
A34 - A32	Dynamic commands
A35	Reserved for internal use

Direct-Clocking DDR2 SDRAM Signal Allocations

MIG allows banks to be selected for different classes of memory signals.

Table 3-14 shows the list of signals allocated in a group from bank selection checkboxes.

Table 3-14: Direct-Clocking DDR2 SDRAM Signal Allocations

Bank Selected	Signals Allocated in the Group
Address	Memory address, memory control, and memory clock signals
Data	Data, data mask, and data strobes
System Control	System reset from user interface and status signals
System Clock	System clocks from the user interface

Note: Timing has been verified for most of the MIG generated configurations. For the best timing results, adjacent banks in the same column of the FPGA should be used. Banks that are separated by unbonded banks should be avoided because these can cause timing violations.

Simulating the DDR2 SDRAM Design

After generating the design, MIG creates a `sim` folder in the specified path. This folder contains simulation files for a particular design. The `sim` folder contains the external testbench, memory model, and `.do` file to simulate the generated design. The memory model files are currently generated in Verilog only. To learn more details about the files in the `sim` folder and to simulate the design, refer to “[Simulation Guide](#),” page 499.

For both single- and dual-rank DIMMs, MIG outputs only the base part memory model. In the simulation testbench (`sim_tb_top` in the `sim` folder), MIG instantiates the required number of memory models. For example, a 1 GB single-rank DIMM with the base part is 1 Gb, and MIG instantiates the base model eight times. A dual-rank part (2 GB capacity) with the base part is 1 Gb. MIG instantiates a 1 Gb model 16 times (the first 8 instances correspond to CS0, and the remaining 8 instances correspond to CS1). If the MIG generated memory model is to be used with the user’s test bench, multiple instances that are based on the selected configuration should be used.

The MIG output memory model considers the `MEM_BITS` parameter by default for memory range allocation. This covers only a partial memory range, i.e., $2^{\text{MEM_BITS}}$. To allocate the full memory range, the `MAX_MEM` parameter should be set in the memory model. Allocating the full memory range might exceed the memory of the operating system, thus causing memory allocation failure in simulations.

Deep-Design Violations

Simulation violations occur for a depth of 4 at frequencies less than and equal to 127 MHz. An auto-refresh command is issued during memory initialization. The next auto-refresh command is issued upon the auto-refresh request after completing calibration (`INIT_DONE` asserted). Because the controller issues the refresh command to the memory only after calibration is completed, even though there is a pending auto-refresh request, a `MAX TREFC` violation occurs for CS0 for a depth of 4 and at frequencies between 125 MHz to 127 MHz. These violations can be ignored because there are no read and write commands issued to the memory, i.e., CS0.

Simulation Violations

There might be simulation violations for frequencies such as 150 MHz where the clock period is not an integer value. At 150 MHz, the clock period value in the simulation testbench is 6.66 ns and the MIG tool rounds it to 6.67 ns. Consider a memory `TRCD` value of 20 ns. MIG calculates the `TRCD` count value based on the clock period, $\text{RCD_COUNT_VALUE} = 20 / 6.67 = 2.998 = 3$ (after rounding off) in the design parameter file. The `TRCD` value for 3 clock cycles is $3 \times 6.66 = 19.98$, which causes timing violations by 20 ps. The difference between the clock period in the external simulation testbench versus the MIG tool causes timing violations. This is only one example case. There might be more such scenarios. These are only simulation warnings. Functionally, there should be no issues. To remove these warnings, the related count value can be increased by one.

Changing the Refresh Rate

Change the global ``define` (for Verilog) or constant (for VHDL) variable `MAX_REF_CNT` in `mymodule_parameters_0.v` (or `.vhd`) so that $\text{MAX_REF_CNT} = (\text{refresh interval in clock periods}) = (\text{refresh interval}) / (\text{clock period})$. For example, for a refresh rate of 3.9 μs with a memory bus running at 200 MHz:

$$\text{MAX_REF_CNT} = 3.9 \mu\text{s} / (\text{clock period}) = 3.9 \mu\text{s} / 5 \text{ ns} = 780 (\text{decimal}) = 0\text{x}30\text{C}$$

If the above value exceeds $2^{\text{MAX_REF_WIDTH}} - 1$, the value of MAX_REF_WIDTH must be increased accordingly in parameters_0.v (or .vhd) to increase the width of the counter used to track the refresh interval.

Supported Devices

The design generated out of MIG is independent of memory package, hence the package part of the memory component is replaced with XX or XXX, where XX or XXX indicates a don't care condition. The tables below list the components (Table 3-15) and DIMMs (Table 3-16 through Table 3-18) supported by the tool for DDR2 direct-clocking designs. In supported devices, an X in the components column (for Components and Unbuffered DIMMs) denotes a single alphanumeric character. For example MT47H128M4XX-3 can be either MT47H128M4BP-3 or MT47H128M4B6-3. Similarly MT16HTF25664AX-40E can be either MT16HTF25664AY-40E or MT16HTF25664AG-40E. An XX for Registered DIMMs denotes a single or two alphanumeric characters. For example, MT9HTF3272XX-667 can be either MT9HTF3272Y-667 or MT9HTF3272DY-667. An XXX for Registered DIMMs denotes two or three alphanumeric characters. For example, MT18HTF12872XXX-667 can be either MT18HTF12872DY-667 or MT18HTF12872PDY-667. Pin mapping for x4 RDIMMs is provided in Appendix G, "Low Power Options."

Table 3-15: Supported Components for DDR2 SDRAM

Components	Packages (XX)	Components	Packages (XX)
MT47H64M4XX-3	BP	MT47H16M16XX-3	BG
MT47H64M4XX-37E	BP	MT47H16M16XX-37E	BG
MT47H64M4XX-5E	BP	MT47H16M16XX-5E	BG
MT47H128M4XX-3	B6,CB,GB	MT47H32M16XX-3	BN,CC,FN,GC
MT47H128M4XX-37E	B6,CB,GB	MT47H32M16XX-37E	BN,CC,FN,GC
MT47H128M4XX-5E	B6,CB,GB	MT47H32M16XX-5E	BN,CC,FN,GC
MT47H256M4XX-3	BT,HQ	MT47H64M16XX-3	BT,HR
MT47H256M4XX-37E	BT,HQ	MT47H64M16XX-37E	BT,HR
MT47H256M4XX-5E	BT,HQ	MT47H64M16XX-5E	BT,HR
MT47H512M4XX-3	HG	MT47H128M16XX-3	HG
MT47H512M4XX-37E	HG	MT47H128M16XX-37E	HG
MT47H512M4XX-5E	HG	MT47H128M16XX-5E	--
MT47H32M8XX-3	BP	HYB18T1G800XXXX-3S	C2F,C2FL
MT47H32M8XX-37E	BP	HYB18T1G800XXXX-37	C2F,C2FL
MT47H32M8XX-5E	BP	HYB18T1G160XXXX-3S	C2F,C2FL
MT47H64M8XX-3	B6,CB,F6,GB	HYB18T1G160XXXX-37	C2F,C2FL
MT47H64M8XX-37E	B6,CB,F6,GB	HYB18T1G400XXXX-3S	C2F,C2FL
MT47H64M8XX-5E	B6,CB,F6,GB	HYB18T1G400XXXX-37	C2F,C2FL
MT47H128M8XX-3	BT,HQ	HYB18T512800XXXX-3S	B2F,B2FL
MT47H128M8XX-37E	BT,HQ	HYB18T512800XXXX-37	B2F,B2FL
MT47H128M8XX-5E	BT,HQ	HYB18T512160XXXX-3S	B2F,B2FL
MT47H256M8XX-3	HG	HYB18T512160XXXX-37	B2F,B2FL

Table 3-15: Supported Components for DDR2 SDRAM (Cont'd)

Components	Packages (XX)	Components	Packages (XX)
MT47H256M8XX-37E	HG	HYB18T512400XXXX-3S	B2F,B2FL
MT47H256M8XX-5E	HG	HYB18T512400XXXX-37	B2F,B2FL

Table 3-16: Supported Registered DIMMs for DDR2 SDRAM

Registered DIMMs	Registered DIMMs
MT9HTF3272Y-667	MT18HTF12872Y-40E
MT9HTF3272PY-667	MT18HTF12872PY-40E
MT9HTF3272Y-53E	MT18HTF25672Y-667
MT9HTF3272PY-53E	MT18HTF25672PY-667
MT9HTF3272Y-40E	MT18HTF25672Y-53E
MT9HTF3272PY-40E	MT18HTF25672PY-53E
MT9HTF6472Y-667	MT18HTF25672Y-40E
MT9HTF6472PY-667	MT18HTF25672PY-40E
MT9HTF6472Y-53E	MT18HTF6472DY-667
MT9HTF6472PY-53E	MT18HTF6472PDY-667
MT9HTF6472Y-40E	MT18HTF6472DY-53E
MT9HTF6472PY-40E	MT18HTF6472PDY-53E
MT9HTF12872Y-667	MT18HTF6472DY-40E
MT9HTF12872PY-667	MT18HTF6472PDY-40E
MT9HTF12872Y-53E	MT18HTF12872DY-667
MT9HTF12872PY-53E	MT18HTF12872PDY-667
MT9HTF12872Y-40E	MT18HTF12872DY-53E
MT9HTF12872PY-40E	MT18HTF12872PDY-53E
MT18HTF6472G-53E	MT18HTF12872DY-40E
MT18HTF6472Y-667	MT18HTF12872PDY-40E
MT18HTF6472PY-667	MT18HTF25672DY-667
MT18HTF6472Y-53E	MT18HTF25672PDY-667
MT18HTF6472PY-53E	MT18HTF25672DY-53E
MT18HTF6472Y-40E	MT18HTF25672PDY-53E
MT18HTF6472PY-40E	MT18HTF25672DY-40E
MT18HTF12872Y-667	MT18HTF25672PDY-40E
MT18HTF12872PY-667	MT36HTJ51272Y-667
MT18HTF12872Y-53E	MT36HTJ51272Y-53E

Table 3-16: Supported Registered DIMMs for DDR2 SDRAM (Cont'd)

Registered DIMMs	Registered DIMMs
MT18HTF12872PY-53E	MT36HTJ51272Y-40E
MT36HTF51272Y-667	MT36HTF51272Y-53E
MT36HTF51272Y-40E	--

Table 3-17: Supported Unbuffered DIMMs for DDR2 SDRAM

Unbuffered DIMMs	Unbuffered DIMMs
MT4HTF1664AY-667	MT9HTF3272AY-40E
MT4HTF1664AY-53E	MT9HTF6472AY-667
MT4HTF1664AY-40E	MT9HTF6472AY-53E
MT4HTF3264AY-53E	MT9HTF6472AY-40E
MT4HTF3264AY-667	MT16HTF25664AX-667
MT4HTF3264AY-40E	MT16HTF25664AX-53E
MT4HTF6464AY-667	MT16HTF25664AX-40E
MT16HTF51264AY-667	MT16HTF51264AY-53E
MT4HTF6464AY-53E	MT18HTF6472AY-667
MT4HTF6464AY-40E	MT18HTF6472AY-53E
MT8HTF6464AY-667	MT18HTF6472AY-40E
MT8HTF6464AY-53E	MT18HTF12872AY-667
MT8HTF6464AY-40E	MT18HTF12872AY-53E
MT8HTF12864AY-667	MT18HTF12872AY-40E
MT8HTF12864AY-53E	MT18HTF25672AY-667
MT8HTF12864AY-40E	MT18HTF25672AY-53E
MT9HTF3272AY-53E	MT18HTF25672AY-40E
MT9HTF3272AY-667	MT18HTF51272AY-53E
MT18HTF51272AY-667	MT18HTF51272AY-40E

Table 3-18: Supported SODIMMs for DDR2 SDRAM

SODIMMs	SODIMMs
MT4HTF1664HY-667	MT8HTF6464HY-40E
MT4HTF1664HY-53E	MT8HTF3264HDY-667
MT4HTF1664HY-40E	MT8HTF3264HDY-53E
MT4HTF3264HY-667	MT8HTF3264HDY-40E
MT4HTF3264HY-53E	MT8HTF6464HDY-667
MT4HTF3264HY-40E	MT8HTF6464HDY-53E
MT8HTF3264HY-667	MT8HTF6464HDY-40E
MT8HTF3264HY-53E	MT16HTF25664HY-667
MT8HTF3264HY-40E	MT16HTF25664HY-53E

Table 3-18: Supported SODIMMs for DDR2 SDRAM (Cont'd)

SODIMMs	SODIMMs
MT8HTF6464HY-667	MT16HTF25664HY-40E
MT8HTF6464HY-53E	MT16HTS51264HY-667
MT16HTS51264HY-53E	--

Hardware Tested Configurations

The frequencies shown in Table 3-19 were achieved on the Virtex-4 FPGA ML461 Memory Interfaces Development Board under nominal conditions. This frequency should not be used to determine the maximum design frequency. The maximum design frequency supported in the MIG wizard is based on a combination of the TRCE results for fabric timing on multiple device/package combinations and I/O timing analysis using FPGA and memory timing parameters for a 64-bit wide interface.

Table 3-19: Hardware Tested Configurations

Synthesis Tools	XST and Synplicity
HDL	Verilog and VHDL
FPGA Device	XC4VLX25-FF668-11
Burst Lengths	4, 8
CAS Latency (CL)	3, 4
Additive Latency	0, 1, 2
8-bit Design	Tested on 16-bit Component "MT47H32M16XX-3"
72-bit Design	Tested on 72-bit RDIMM "MT9HTF6472Y-667"
ECC with Pipelined Mode	72-bit Registered DIMM design
Frequency Range	110 MHz to 270 MHz for CL = 3
	110 MHz to 300 MHz for CL = 4 or 5

SerDes Clocking Interface

This technique uses the Input Serializer/Deserializer (ISERDES) and Output Serializer/Deserializer (OSERDES) features available in every Virtex-4 FPGA I/O. A DDR2 SDRAM interface is source-synchronous, where the read data and read data strobe are transmitted edge-aligned. To capture this transmitted data using Virtex-4 FPGAs, either the strobe or the data can be delayed. In this design, the read data is captured in the delayed strobe domain and recaptured in the FPGA clock domain in the ISERDES. The received signal, double data rate (DDR) read data, is converted to 4-bit parallel single data rate (SDR) data at the frequency of the interface using the ISERDES. The write data and strobe transmitted by the FPGA use the OSERDES. The OSERDES converts 4-bit parallel data at half the frequency of the interface to DDR data at the interface frequency.

Feature Summary

This section summarizes the supported and unsupported features of the SerDes clocking DDR2 SDRAM controller design.

Supported Features

The DDR2 SDRAM controller design supports:

- Burst lengths of four and eight
- Sequential and Interleaved burst types
- CAS latencies of 4 and 5
- Different memories (density/speed)
- Components
- Additive latencies 0, 1, and 2
- Verilog and VHDL
- Differential and single-ended DQS
- Linear addressing
- Without a testbench
- On Die Termination (ODT)
- DIMMs (registered DIMMs up to 300 MHz and unbuffered DIMMs up to 266 MHz)
- Data mask
- System clock, differential and single-ended

The supported features are described in more detail in [“Architecture.”](#)

Design Frequency Ranges

Table 3-20: Design Frequency Range in MHz

Memory	FPGA Speed Grade					
	-10		-11		-12	
	Min	Max	Min	Max	Min	Max
Component	200	230	200	266	200	300
Registered DIMM	200	230	200	266	200	300
UDIMM/SODIMM	200	230	200	266	200	266

Unsupported Features

The DDR2 SDRAM controller design does not support:

- CAS latency of 3
- Additive latencies of 3 and 4
- Redundant DQS (RDQS)
- Auto precharge
- Deep memories
- ECC support
- Without a DCM
- Multicontroller

Architecture

Implemented Features

This section provides details on the supported features of the DDR2 SDRAM controller.

Burst Length

The DDR2 SDRAM controller supports burst lengths of four and eight. The burst length can be selected through the **Set mode register(s)** option in MIG. For a design without a testbench (user design), the user has to provide bursts of the input data based on the chosen burst length. Bits M2:M0 of the Mode Register define the burst length, and bit M3 indicates the burst type (see the Micron data sheet). Read and write accesses to the DDR2 SDRAM are burst-oriented. It determines the maximum number of column locations accessed for a given READ or WRITE command.

CAS Latency

The DDR2 SDRAM controller supports CAS latencies (CLs) of four and five. CL can be selected in the **Set mode register(s)** option from the GUI. The CAS latency is implemented in the `ddr2_controller` module. During data write operations, the generation of the `ctrl_WrEn`, `ctrl_WrEn_Dis`, and `ctrl_Odd_Latency` signals varies according to the CL in the `ddr2_controller` module. During data read operations, the generation of the `ctrl_RdEn_div0` signal varies according to the CL in the `ddr2_controller` module. Bits M4:M6 of the Mode Register define the CL (see the Micron data sheet). CL is the delay in clock cycles between the registration of a READ command and the availability of the first bit of output data.

Additive Latency

DDR2 SDRAM devices support a feature called posted CAS additive latency (AL). The DDR2 SDRAM supports additive latencies of 0, 1, and 2. AL can be selected in the **Set mode register(s)** option. Additive latency is implemented in the `ddr2_controller` module. The `ddr2_controller` module issues READ/WRITE commands prior to t_{RCD} (minimum) depending on the user-selected AL value in the Extended Mode Register. This feature allows the READ command to be issued prior to t_{RCD} (minimum) by delaying the internal command to the DDR2 SDRAM by AL clocks. Posted CAS AL makes the command and data bus efficient for sustainable bandwidths in DDR2 SDRAM. Bits E3:E5 of the Extended Mode Register define the value of AL (see the Micron data sheet).

Registered DIMMs

DDR2 SDRAM supports registered DIMMs. This feature is implemented in the `ddr2_controller` module. For registered DIMMs, the address and command signals are registered at the DIMM and therefore have one additional clock latency than unbuffered DIMMs.

Unbuffered DIMMs and SODIMMs

The DDR2 SDRAM design supports unbuffered DIMMs and SODIMMs. Unbuffered DIMMs do not have registers at the DIMM for address and command signals. SODIMMs differ from the unbuffered DIMMs only by the package type; otherwise they are functionally the same.

Different Memories (Density/Speed)

The DDR2 SDRAM controller supports different densities. For DDR2 components shown in MIG, densities vary from 256 Mb to 2 Gb, and DIMM densities vary from 128 Mb to 4 Gb. The user can select various configurations using the “Create new memory part” feature of MIG. The supported maximum column address is 13, the maximum row address is 15, and the maximum bank address is 3. The design can decode write and read addresses from the user in the DDR2 SDRAM controller module. The user address consists of column, row, bank, chip address, and user command.

Table 3-21 and Table 3-22 list sample timing sheets for Micron components and DIMMs, respectively.

Table 3-21: Timing Parameters for Components

Parameter	Description	Micron 256 Mb		Micron 512 Mb		Micron 1 Gb		Units
		-37E	-3	-37E	-3	-37E	-3	
T _{MRD}	LOAD MODE command cycle time	2	2	2	2	2	2	T _{CK}
T _{RP}	PRECHARGE command period	15	15	15	15	15	15	ns
T _{RFC}	REFRESH to ACTIVE or REFRESH to REFRESH command interval	75	75	105	105	127.5	127.5	ns
T _{RCD}	ACTIVE to READ or WRITE delay	15	15	15	15	15	15	ns
T _{RAS}	ACTIVE to PRECHARGE command	40	40	40	40	40	40	ns
T _{RC}	ACTIVE to ACTIVE (same bank) command	55	55	55	55	55	55	ns
T _{RTP}	READ to PRECHARGE command delay	7.5	7.5	7.5	7.5	7.5	7.5	ns
T _{WTR}	WRITE to READ command delay	7.5	7.5	7.5	7.5	7.5	7.5	ns
T _{WR}	WRITE recovery time	15	15	15	15	15	15	ns

Table 3-22: Timing Parameters for DIMMs

Parameter	Description	MT4HTF		MT8HTF		MT16HTF		MT9HTF		MT18HTF	
		-53E	-40E	-53E	-40E	-53E	-40E	-53E	-40E	-53E	-40E
T _{MRD}	LOAD MODE command cycle time	2 ns	2 ns	2 ns	2 ns	2 ns	2 ns	2 ns	2 ns	2 ns	2 ns
T _{RP}	PRECHARGE command period	15 ns	15 ns	15 ns	15 ns	15 ns	15 ns	15 ns	15 ns	15 ns	15 ns
T _{RFC}	REFRESH time	128 MB 75 ns	75 ns	256 MB 75 ns	75 ns	512 MB 75 ns	75 ns	256 MB 75 ns	75 ns	512 MB 75 ns	75 ns
		256 MB 105 ns	105 ns	512 MB 105 ns	105 ns	1 GB 105 ns	105 ns	512 MB 105 ns	105 ns	1 GB 105 ns	105 ns
		512 MB 127.5 ns	127.5 ns	1 GB 127.5 ns	127.5 ns	2 GB 127.5 ns	127.5 ns	1 GB 127.5 ns	127.5 ns	2 GB 127.5 ns	127.5 ns
T _{RCD}	ACTIVE to READ or WRITE delay	15 ns	15 ns	15 ns	15 ns	15 ns	15 ns	15 ns	15 ns	15 ns	15 ns
T _{RAS}	ACTIVE to PRECHARGE command	40 ns	40 ns	40 ns	40 ns	40 ns	40 ns	40 ns	40 ns	40 ns	40 ns

Table 3-22: Timing Parameters for DIMMs (Cont'd)

Parameter	Description	MT4HTF		MT8HTF		MT16HTF		MT9HTF		MT18HTF	
		-53E	-40E	-53E	-40E	-53E	-40E	-53E	-40E	-53E	-40E
T_{RC}	ACTIVE to ACTIVE command (same bank)	55 ns	55 ns	55 ns	55 ns	55 ns	55 ns	55 ns	55 ns	55 ns	55 ns
T_{RTP}	READ to PRECHARGE command delay	7.5 ns	7.5 ns	7.5 ns	7.5 ns	7.5 ns	7.5 ns	7.5 ns	7.5 ns	7.5 ns	7.5 ns
T_{WTR}	WRITE to READ command delay	7.5 ns	10 ns	7.5 ns	10 ns	7.5 ns	10 ns	7.5 ns	10 ns	7.5 ns	10 ns
T_{WR}	WRITE recovery time	15 ns	15 ns	15 ns	15 ns	15 ns	15 ns	15 ns	15 ns	15 ns	15 ns

Notes:

1. For the latest timing information, refer to the vendor memory data sheets.

Data Masking

The DDR2 SDRAM design supports data masking per byte. Masking per nibble is not supported due to the limitation of the internal block RAM based FIFOs. So, the masking of data can be done on per byte basis. The mask data is stored in the Data FIFO along with the actual data.

MIG supports a data mask option. If this option is checked in the GUI, MIG generates design with data mask pins. This option can be chosen if the selected part has data masking.

Precharge

The PRECHARGE command is used to close the open row in a bank if there is a command to be issued to a different row in the same bank. The PRECHARGE command checks the row address, bank address, and chip address, and the Virtex-4 FPGA DDR2 controller issues a PRECHARGE command if there is a change in any address where a read or write command is to be issued. The auto-precharge function is not supported.

Auto Refresh

The DDR2 SDRAM controller issues AUTO REFRESH commands at specified intervals for the memory to refresh the charge required to retain the data in the memory. The user can also issue a REFRESH command through the user interface by setting bits 34, 33, and 32 of the app_af_addr signal in the user_interface module to 3'b001. If there is a refresh request while there is an ongoing read or write burst, the controller issues a REFRESH command after completing the current read or write burst command.

Linear Addressing

The DDR2 SDRAM controller supports linear addressing. Linear addressing refers to the way the user provides the address of the memory to be accessed. For Virtex-4 FPGA DDR2 SDRAM controllers, the user provides the address information through the app_af_addr signal. As the densities of the memory devices vary, the number of column address bits and row address bits also change. In any case, the row address bits in the app_af_addr signal always start from the next higher bit, where the column address ends. This feature increases the number of devices that can be supported with the design.

On-Die Termination

The DDR2 SDRAM controller supports on-die termination (ODT). Through the **Set mode register(s)** option from the GUI, the user can disable ODT or can choose 75, 150, or 50.

ODT can turn the termination on and off as needed to improve the signal integrity in the system. ODT is only enabled on writes to DDR2 memory. It is disabled on read operations.

System Clock

MIG supports differential and single-ended system clocks. Based on the selection in the GUI, input system clocks and IDELAY clocks are differential or single-ended.

Hierarchy

Figure 3-17 shows the hierarchical structure of the DDR2 SDRAM controller.

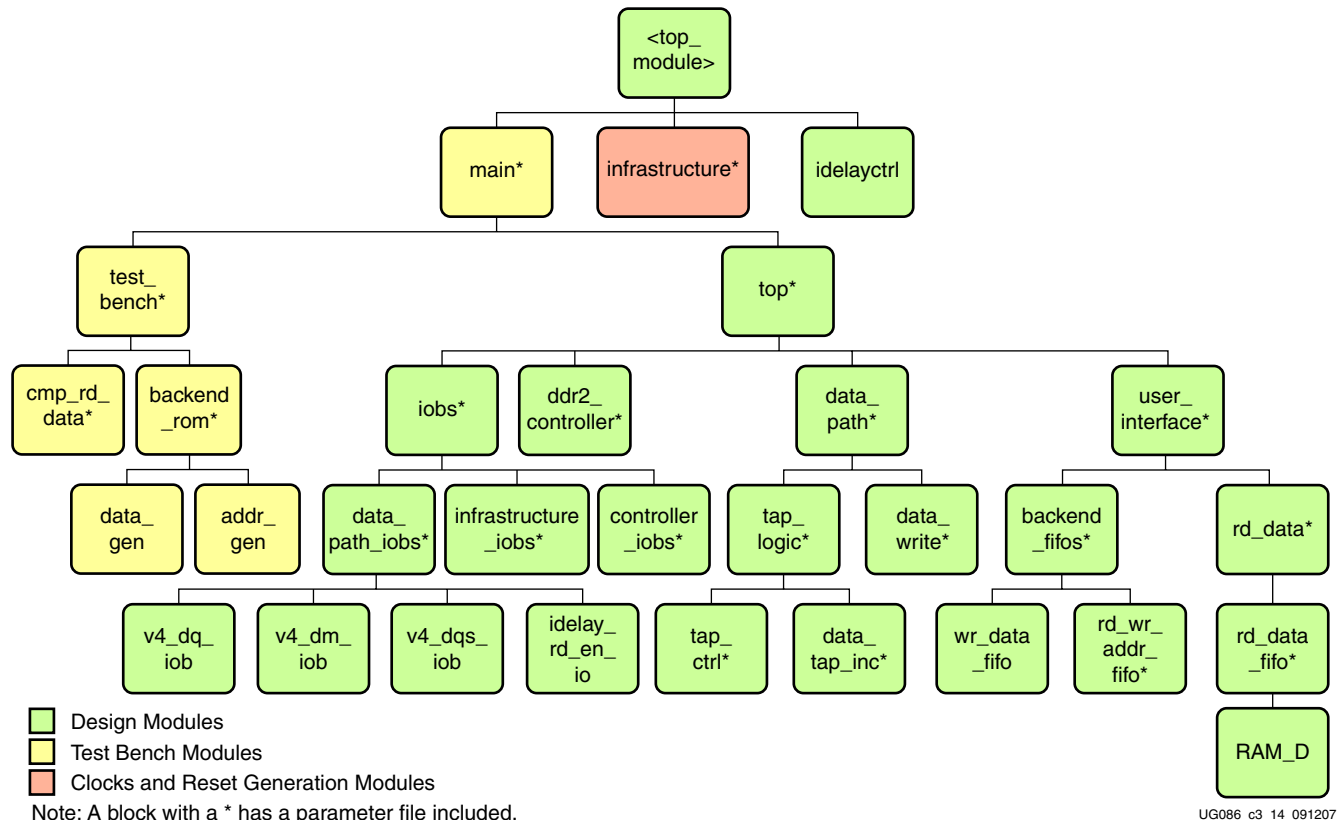


Figure 3-17: Hierarchical Structure of the DDR2 SDRAM Design (SerDes Clocking)

Figure 3-17 shows the hierarchical structure of the DDR2 SDRAM design generated by MIG with a testbench and a DCM. The modules are classified as follows:

- Design modules
- Testbench modules
- Clocks and reset generation modules

There is a parameter file generated with the design that has all the user input and design parameters selected from MIG.

MIG can generate two different DDR2 SDRAM designs:

- With a testbench and a DCM
- Without a testbench and with a DCM

A design without a testbench (user_design) does not have testbench modules. The <top_module> module has the user interface signals for designs without a testbench. The list of user interface signals is provided in [Table 3-24](#).

Design clocks and resets are generated by using the DCM in the infrastructure module. The inputs to this module are the differential design clock and a 200 MHz differential clock for the IDELAYCTRL module. A user reset is also input to this module. Using the input clocks and reset signals, the system clocks and the system reset are generated in this module, which is used in the design.

MIG Tool Design Options for SerDes Clocking Interface

MIG provides various options to generate the design with or without a testbench or with or without a DCM. This section provides detailed descriptions of the type of design generated by the user using various options. [Figure 3-18](#) and [Figure 3-19, page 171](#) show the differential system clock.

MIG outputs both an example_design and a user_design. The MIG-generated example_design includes the entire memory controller design along with a synthesized testbench (example user application). This testbench generates sample writes and reads and then uses comparison logic to verify that the data patterns written are the same as those received. This example_design can be used to test functionality both in simulation and in hardware. The user_design includes the memory controller design only. This design allows users to connect the MIG memory controller design to a user developed testbench (user application). Refer to [Table 3-24, page 176](#) for user interface signals, the “[User Interface Accesses](#),” [page 178](#) for timing restriction on user interface signals, and [Figure 3-24, page 180](#) and [Figure 3-25, page 181](#) for write interface timing.

[Figure 3-18](#) shows a top-level block diagram of a DDR2 SDRAM design with a DCM and a testbench. The sys_clk_p and sys_clk_n signals are differential input system clocks. The DCM is instantiated in the infrastructure module that generates the required design clocks. The differential clk200_p and clk200_n signals are used for the idelay_ctrl element. The sys_reset_in_n is an active-Low system reset signal. All design resets are gated by the dcm_lock signal. The error output signal indicates whether a read passes or fails. The testbench module issues writes and reads, and also compares the read data with the written data. The error signal is driven High on data mismatches. The init_complete signal indicates the completion of initialization and calibration of the design. Memory device signals are prepended with the controller number. For example, the ddr2_ras_n signal appears as cntrl0_ddr2_ras_n.

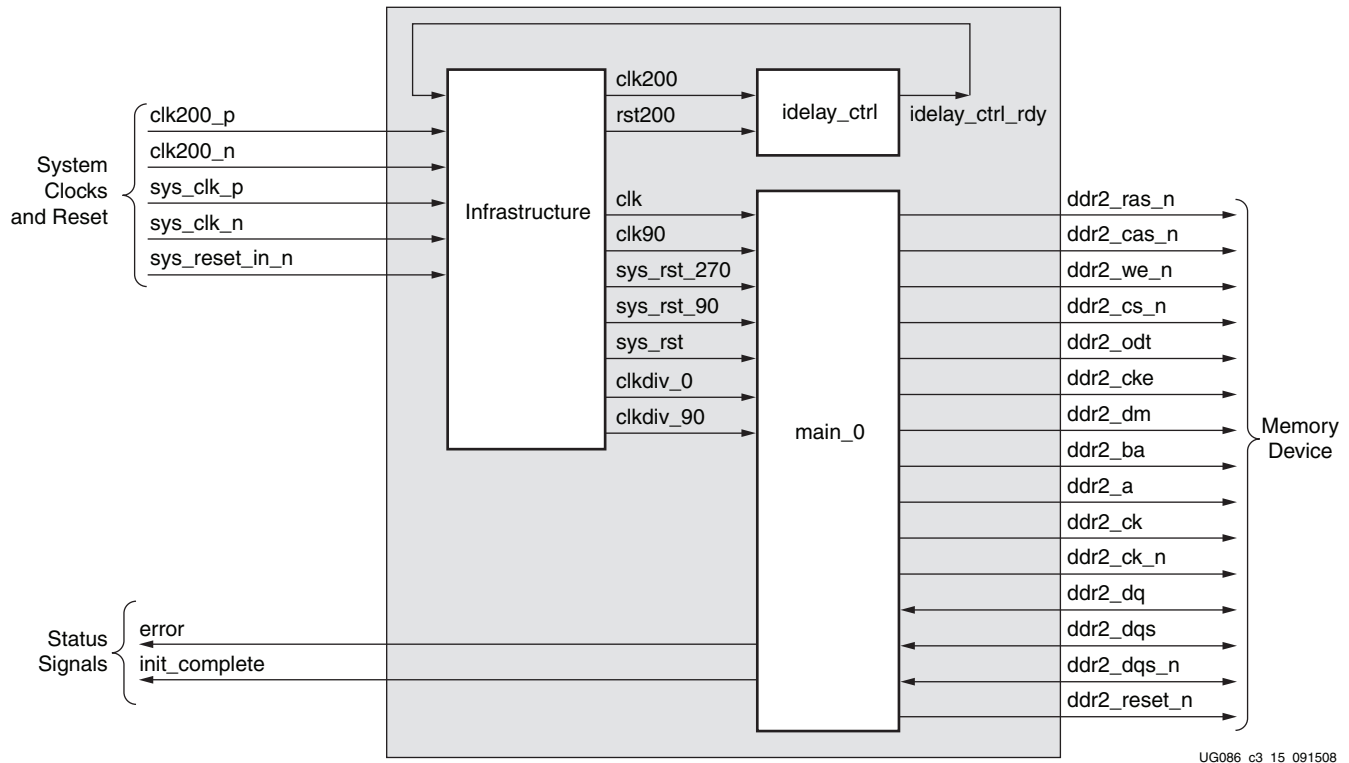


Figure 3-18: Top-Level Block Diagram of the DDR2 SDRAM Design with a DCM and a Testbench

All Memory Device ports do not necessarily appear for all MIG-generated designs. For example, port `ddr2_reset_n` appears in the port list for registered DIMM designs only. Similarly, `ddr2_dqs_n` does not appear for single-ended DQS designs. Port `DDR2_DM` appears only for parts that contain a data mask; a few RDIMMs have no data mask, and `DDR2_DM` does not appear in the port list for them.

Figure 3-19 shows a top-level block diagram of a DDR2 SDRAM design with a DCM but without a testbench. The `sys_clk_p` and `sys_clk_n` pair are differential input system clocks. The DCM is instantiated in the `infrastructure` module that generates the required design clocks. The differential `clk200_p` and `clk200_n` pair are used for the `idelay_ctrl` element. The active-Low system reset signal is `sys_reset_in_n`. All design resets are gated by the `dcm_lock` signal. The user has to drive the user application signals. The design provides the `clk_tb` and `reset_tb` signals to the user to synchronize with the design. The `init_complete` signal indicates the completion of initialization and calibration of the design.

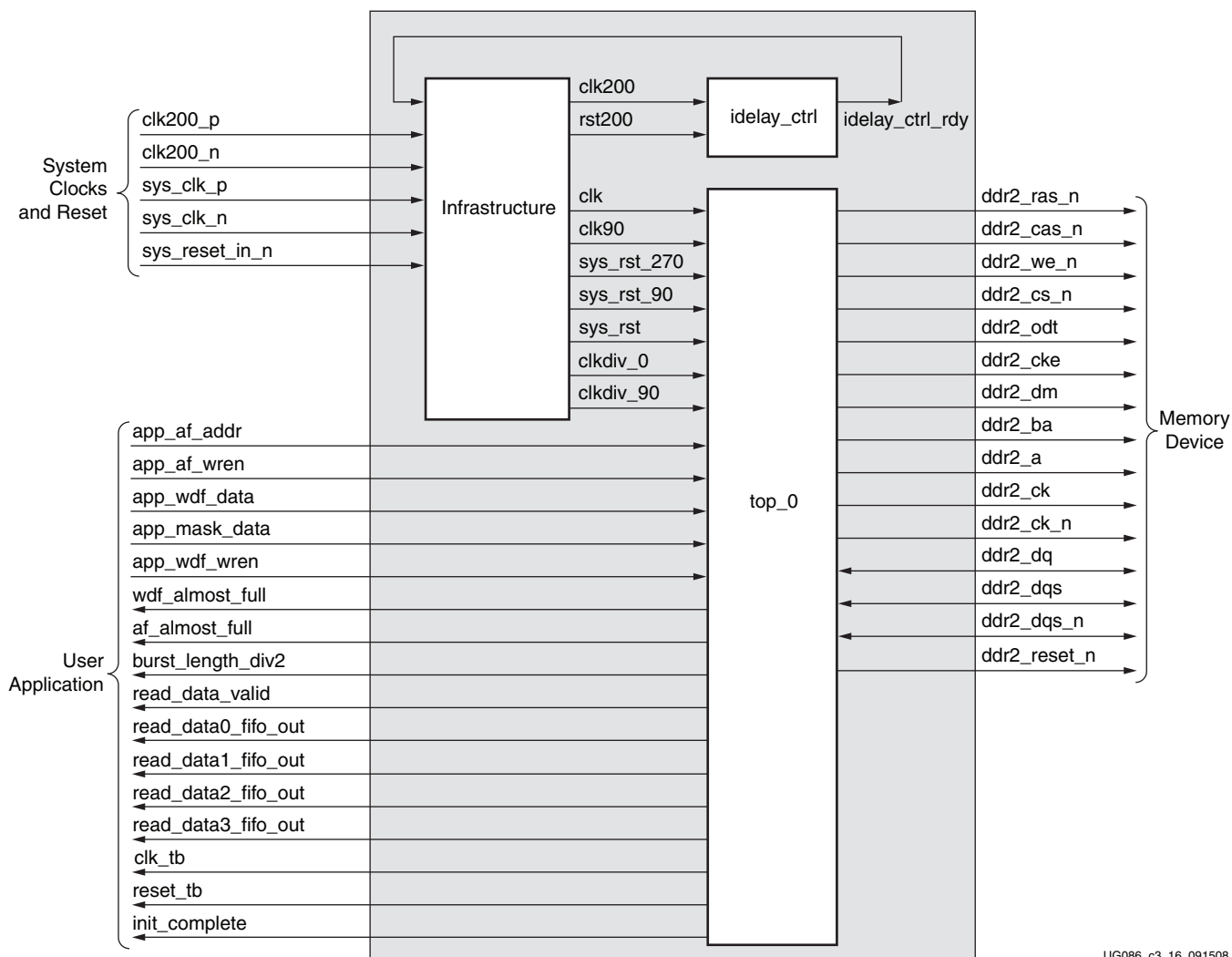


Figure 3-19: Top-Level Block Diagram of the DDR2 SDRAM Design with a DCM but without a Testbench

DDR2 Controller Submodules

Figure 3-20 is a detailed block diagram of the DDR2 SDRAM controller. The five blocks shown are the subblocks of the top module. The user backend signals are provided by the tool for designs with a testbench. The user has to drive these signals for designs without a testbench. The functions of these blocks are explained in the subsections following Figure 3-20.

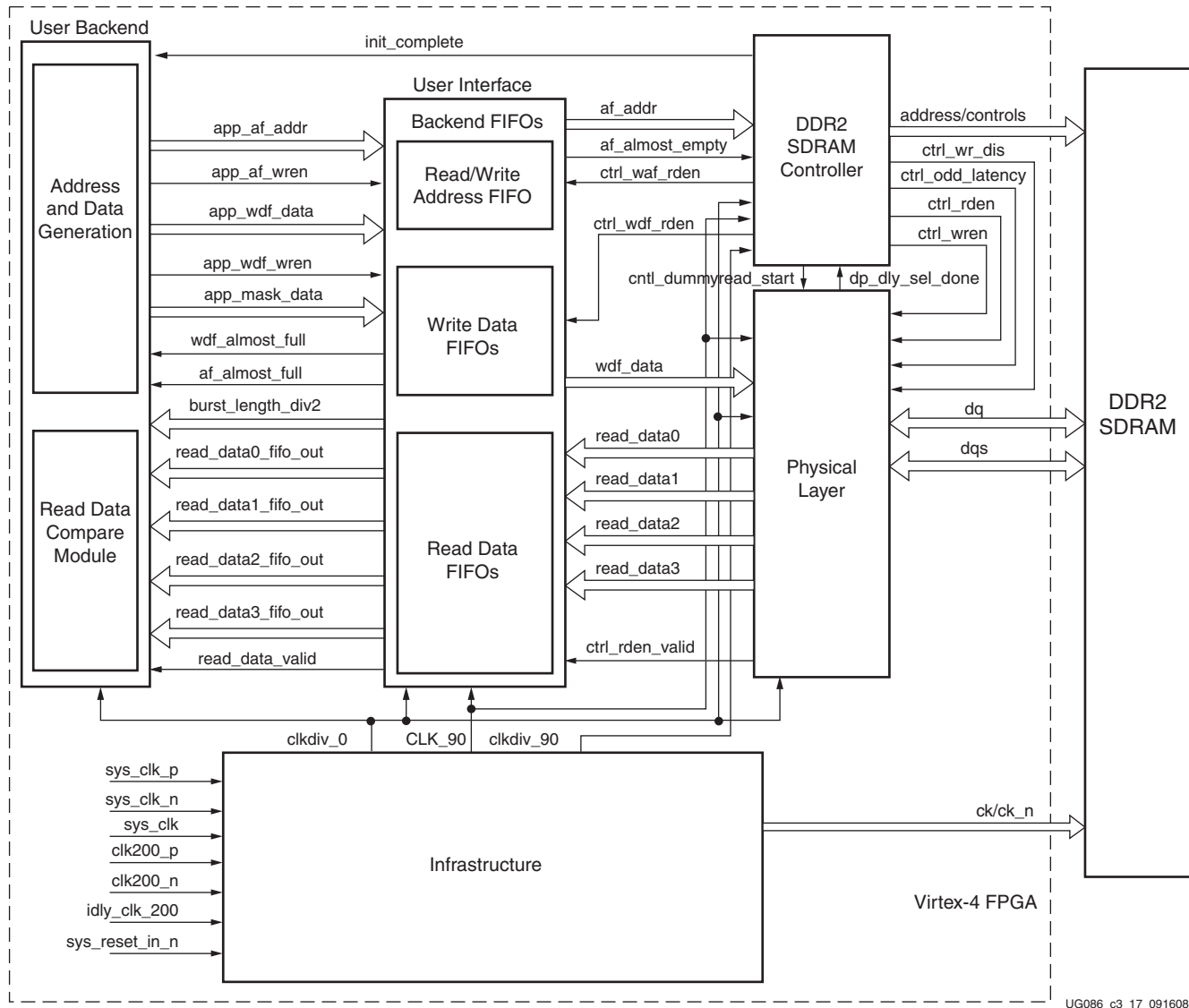


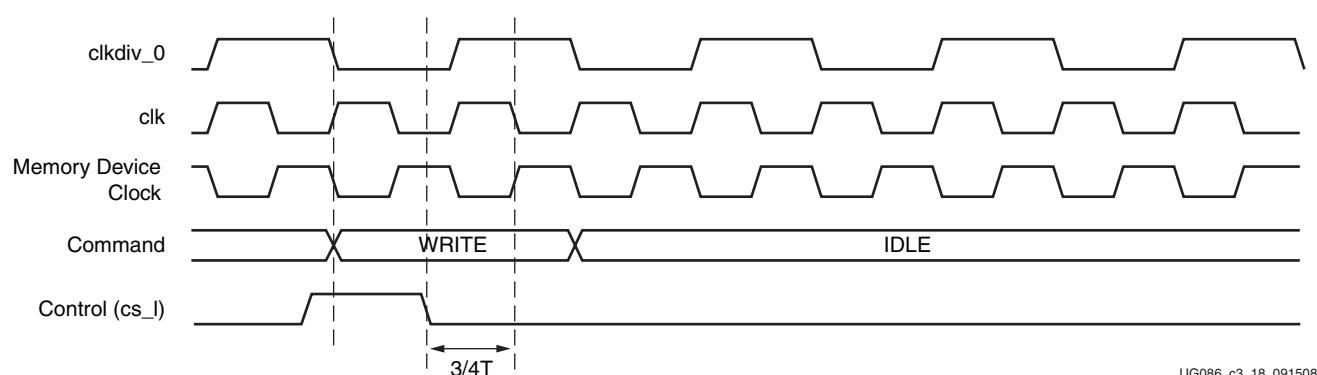
Figure 3-20: DDR2 Memory Controller Block Diagram (SerDes Clocking)

Controller

The DDR2 SDRAM ddr2_controller accepts and decodes user commands and generates read, write, and refresh commands. The DDR2 SDRAM controller also generates signals for other modules. The memory is initialized and powered up using a defined process. The controller state machine handles the initialization process upon power-up. When the initialization is over, the controller starts doing a dummy write and continuous dummy reads. During these dummy reads, the tap_logic module calibrates DQ and DQS by

varying the delay to center-align the data with the FPGA clock. Then the `tap_logic` module asserts the `dp_dqs_dq_calib_done` signal. After this assertion, the controller does one more write and read to the memory for read-enable calibration to determine the delay between the read command and data. Then `dp_dly_slct_done` is asserted to start writing to and reading from the memory.

The `ddr2_controller` is clocked at half the frequency of the interface using `CLKDIV_0` and `CLKDIV_90` and `CLK_90`. Therefore the address and bank address are driven and the command signals (`RAS_L`, `CAS_L`, and `WE_L`) are asserted for two clock cycles of the fast memory interface clock. The control signals (`CS_L`, `CKE`, and `ODT`) are DDR of the half frequency clock `CLKDIV_0`, ensuring that the control signals are asserted for just one clock cycle of the fast memory interface clock. Figure 3-21 shows the command and control timing diagram for unbuffered DIMMs and components in which `CS_L` is deasserted 3/4T earlier when the write command is at the positive edge of the device clock to the memory. For registered DIMMs, `CS_L` is deasserted T/2 earlier only.



UG086_c3_18_091508

Figure 3-21: Command and Control Timing from Controller to DDR2 Memory

Physical Layer

This module transmits data to and receives data from the memories. Its major functions include processing the data in the write datapath, and calibrating the data in the read datapath. The write datapath function is implemented in the `data_write` module and the read datapath function is implemented in the `tap_ctrl`, `data_tap_inc`, and `idelay_rd_en_io` modules.

To start calibration in the read datapath, the write datapath first generates the training pattern (known data) and writes it to the memory during dummy writes. Calibration is done during the dummy reads. The read datapath expects the training pattern. When the received training pattern is correct, then DQ and DQS are aligned with the FPGA clock to capture the data without errors during actual writes and reads. After this calibration is finished, `dp_dqs_dq_calib_done` is asserted to start read-enable calibration to find the delay between the read command and data at the input of the Read Data FIFO. So the read enable generated from the controller with the read command is delayed by the same amount and is used as the write enable to the Read Data FIFO for normal reads. Once this read-enable calibration is complete, `dp_dly_slct_done` is asserted, which initiates writes and reads to the memory.

User Interface

This module stores write data and write addresses, writes the data into a location specified by the write address, stores read addresses used to read from a specific location, and also stores data read from the memory in FIFOs. The `rd_data` and `rd_data_fifos` modules store

the data in LUT-based RAMs. The `rd_wr_addr_fifo` and `wr_data_fifo` modules store the data and address in block RAMs.

The FIFOs are built using FIFO16 primitives in the `rd_wr_addr_fifo` and `wr_data_fifo_16` modules. Each FIFO has a threshold attribute called `ALMOST_FULL_OFFSET`, whose value is set to 7, by default, in the RTL. This value can be changed as needed. For valid FIFO threshold offset values, refer to UG070 [Ref 7].

The width of the data stored by the `wr_data_fifo` module is four times the interface data width, because the data corresponding to four edges is given in one clock cycle.

Test Bench

The MIG tool generates two RTL folders, `example_design` and `user_design`. The `example_design` folder includes the synthesizable test bench, while `user_design` does not include the test bench modules. The MIG test bench performs eight write commands and eight read commands in an alternating fashion. The number of words in a write command depends on the burst length. For a burst length of 4, the test bench writes a total of 32 data words for all eight write commands (16 rise data words and 16 fall data words). For a burst length of 8, the test bench writes a total of 64 data words. It writes the data pattern of FF, 00, AA, 55, 55 AA, 99, 66 in a sequence of which FF, AA, 55, and 99 are rise data words and 00, 55, AA, and 66 are fall data words for an 8-bit design. The falling edge data is the complement of the rising edge data. For a burst length of 4, the data sequence for the first write command is FF, 00, AA, 55, and the data sequence for the second write command is 55, AA, 99, 66. For a burst length of 8, the data pattern for the first write command is FF, 00, AA, 55, 55 AA, 99, 66 and the same pattern is repeated for all the remaining write commands. This data pattern is repeated in the same order based on the number of data words written. For data widths greater than 8, the same data pattern is concatenated for the other bits. For a 32-bit design and a burst length of 8, the data pattern for the first write command is FFFFFFFF, 00000000, AAAAAAAAAA, 55555555, 55555555, AAAAAAAAAA, 99999999, 66666666.

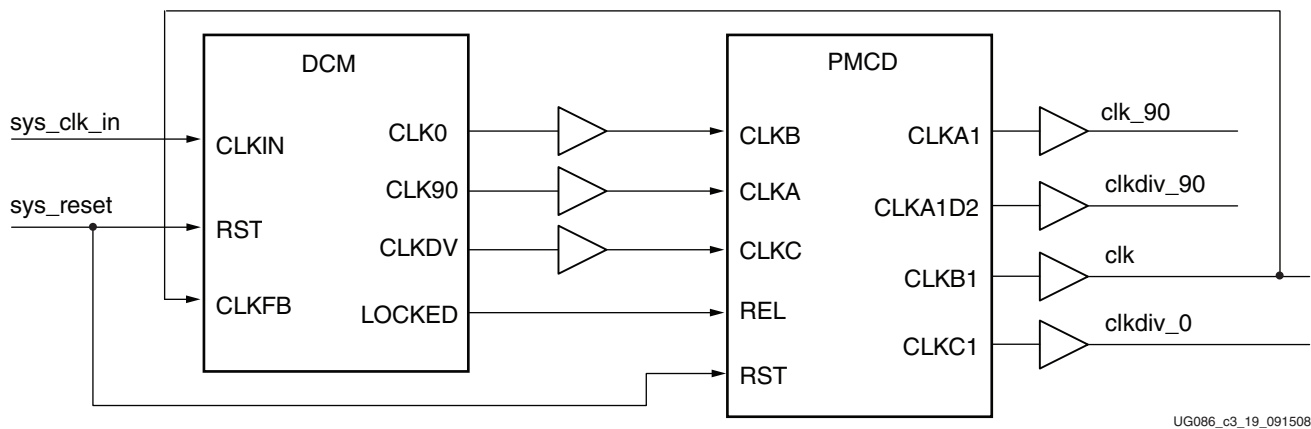
Address generation logic generates eight different addresses for eight write commands. The same eight address locations are repeated for the following eight read commands. The read commands are performed at the same locations where the data is written. There are total of 32 different address locations for 32 write commands, and the same address locations are generated for 32 read commands. Upon completion of a total of 64 commands, including both writes and reads (eight writes and eight reads repeated four times), address generation rolls back to the first address of the first write command and the same address locations are repeated. The MIG test bench exercises only a certain memory area. The address is formed such that all address bits are exercised. During writes, a new address is generated for every burst operation on the column boundary.

During reads, comparison logic compares the read pattern with the pattern written, i.e., the FF, 00, AA, 55, 55 AA, 99, 66 pattern. For example, for an 8-bit design of burst length 4, the data written for a single write command is FF, 00, AA, 55. During reads, the read pattern is compared with the FF, 00, AA, 55 pattern. Based on a comparison of the data, a status signal error is generated. If the data read back is the same as the data written, the error signal is 0, otherwise it is 1.

Infrastructure Module

The infrastructure module generates the necessary FPGA clock and reset signals. The clocking scheme used for this design includes one DCM and one PMCD, as shown in Figure 3-22. When differential clocking is used, `sys_clk_p`, `sys_clk_n`, `clk_200_p`, and `clk_200_n` signals appear. When single-ended clocking is used, `sys_clk` and `idly_clk_200` signals appear. In addition, clocks are available for design use and a 200 MHz clock is

provided for the IDELAYCTRL primitive. Differential and single-ended clocks are passed through global clock buffers before connecting to a DCM. For differential clocking, the output of the sys_clk_p/sys_clk_n buffer is single-ended and is provided to the DCM input. Likewise, for single-ended clocking, sys_clk is passed through a buffer and its output is provided to the DCM input. The clock outputs of the DCM are passed through the PMCD. The outputs of the PMCD are clk (0° phase-shifted version of the input clock), clk_90 (90° phase-shifted version of the input clock), clkdiv_0 (half the frequency of the input clock and phase-aligned with clk), and clkdiv_90 (half the frequency of the input clock and phase-aligned with clk_90). The clock outputs of the DCM are passed through PMCD. After the DCM is locked, the design is in the reset state for at least 25 clocks. The infrastructure module also generates all of the reset signals required for the design.



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Figure 3-22: Clocking Scheme for the High-Performance Memory Interface Design

Note: SerDes design is not supported for FPGAs that do not have PMCDs. Unsupported FPGAs for SerDes design are:

XC4VLX15-FF668	XC4VFX12-FF668	XC4VSX25-FF668
XC4VLX15-FF676	XC4VFX12-SF363	XC4VSX25-FF676
XC4VLX15-SF363	XC4VFX20-FF672	

Idelay_ctrl

This module instantiates the IDELAYCTRL primitive of the Virtex-4 FPGA. The IDELAYCTRL primitive is used to continuously calibrate the individual delay elements in its region to reduce the effect of process, temperature, and voltage variations. A 200 MHz clock has to be fed to this primitive. For more information on IDELAYCTRLs, refer to “Verify IDELAYCTRL Instantiation for Virtex-4 and Virtex-5 FPGA Designs” in Chapter 14.

DDR2 SDRAM Initialization and Calibration

DDR2 memory is initialized through a specified sequence as per both Micron and JEDEC specifications. The controller starts the memory initialization at power-up. Following the initialization, the relationship between the data and the FPGA clock is calculated using the tap_logic. The controller issues a dummy write command and dummy read command to the memory and compares read data with the fixed pattern. During dummy reads, the tap_logic module calibrates and delays the DQ and DQS to center-align with the FPGA clock. The dqs_dq_calib_done port in the tap_logic module indicates the completion of DQS to FPGA clock calibration and per bit calibration.

After the per-bit calibration is done, the controller does a read enable calibration. This calibration is used to determine the delay from read command to read data at `rd_data_fifo`. The delay between read command and read data is affected by the CAS latency and additive latency parameters, the PCB traces, and the I/O buffer delays. This in turn is used to generate a write enable to `rd_data_fifo` so that valid data is registered. The controller issues a dummy read command and compares the read data with a fixed known pattern. The `training_done` port in the `tap_logic` module indicates the completion of the read enable calibration.

The `init_complete` port indicates the completion of DQS to FPGA clock calibration, per-bit calibration, and read enable calibration. After initialization and calibration are done, the controller can start issuing user commands to the memory.

DDR2 SDRAM System and User Interface Signals

Table 3-23 lists the system signals that are required for the design. The system interface signals are the clocks and the reset signals given by the user to the FPGA. The `sys_clk_p` and `sys_clk_n` signals comprise the differential clock pair provided to the design. Similarly, `clk200_p` and `clk_200N` comprise the 200 MHz differential clock pair for the `IDELAYCTRL` module. The `sys_reset_in_n` signal resets all the logic.

Table 3-23: DDR2 SDRAM System Signals

Signal Name	Direction	Description
<code>sys_clk_p</code> , <code>sys_clk_n</code>	Input	This differential clock pair generates the single-ended clock to the input of the DCM. Memory operates at this frequency, but the <code>ddr2_controller</code> , <code>data_path</code> , and <code>user_interface</code> modules, and all other FPGA slice logic are clocked at half of this frequency.
<code>clk200_p</code> , <code>clk200_n</code>	Input	Differential clock used in the <code>idelay_ctrl</code> logic.
<code>sys_reset_in_n</code>	Input	Active-Low reset to the design.

Table 3-24 describes the DDR2 SDRAM user interface signals.

Table 3-24: DDR2 SDRAM Controller User Interface Signals

Signal Name ⁽¹⁾	Direction	Description
<code>clk_tb</code>	Output	All user interface signals must be synchronized with respect to the negative edge of <code>CLKDIV_0</code> .
<code>reset_tb</code>	Output	Reset signal for the User Interface.
<code>burst_length_div2[2:0]</code>	Output	This signal determines the data burst length for each write address. 010: burst length = 4 100: burst length = 8
<code>wdf_almost_full</code>	Output	This signal indicates the <code>ALMOST_FULL</code> status of the Write Data FIFO. When this signal is asserted, the user can write 5 more data words into the FIFO for the with testbench case and 14 more data words for the without testbench case.
<code>app_wdf_data[4n-1:0]</code>	Input	User write data to the memory, where <i>n</i> indicates the data width of the interface. The user data width is four times the data width of the interface. This bus has the data for two rising edges and two falling edges. The most-significant bits contain the second falling-edge data, and the least-significant bits contain the first rising-edge data.

Table 3-24: DDR2 SDRAM Controller User Interface Signals (Cont'd)

Signal Name ⁽¹⁾	Direction	Description
app_mask_data[4m-1:0]	Input	User mask data to the memory, where m indicates the data mask width of the interface. The mask data width is four times the mask width of the interface. This bus also has the mask data for four edges. The most-significant bits contain the mask data for the second falling edge, and the least-significant bits contain the mask data for the first rising edge. These signals are not present when the memory part does not have mask support (for example, certain Registered DIMMs) or when the data mask option is not selected in the MIG GUI.
app_wdf_wren	Input	Write Enable signal to the Write Data FIFO.
af_almost_full	Output	This signal indicates the ALMOST_FULL status of the Address FIFO. When this signal is asserted, the user can issue eight more commands/addresses to the FIFO.
app_af_addr[35:0] ⁽²⁾	Input	The user address consists of a memory address and dynamic commands. The address width [31:0] is the memory read/write address, which includes the column, row, bank, and chip address. The address width [35:32] represents dynamic commands. 001: Auto Refresh 010: Precharge All 100: Write 101: Read
app_af_wren	Input	Write Enable signal to the Address FIFO.
read_data0_fifo_out[n-1:0] read_data1_fifo_out[n-1:0] read_data2_fifo_out[n-1:0] read_data3_fifo_out[n-1:0]	Output	The read data captured from the memory is four parallel <i>n</i> -bit data buses, each at half the frequency of the interface, where <i>n</i> indicates the data width of the interface. READ_DATA0_FIFO_OUT is the first rising-edge data, READ_DATA1_FIFO_OUT is the second rising-edge data, READ_DATA2_FIFO_OUT is the first falling-edge data, and READ_DATA3_FIFO_OUT is the second falling-edge data.
read_data_valid	Output	This signal is asserted to indicate the read data is available to the user.
init_complete	Output	This signal indicates the completion of initialization to the memory and calibration in the design.

Notes:

1. All user interface signal names are prepended with a controller number for the without testbench case, because SerDes clocking supports only a single controller. See [“User Interface Accesses,” page 143](#) for timing requirements and restrictions on the user interface signals.
2. Linear addressing is used, i.e., the row address immediately follows the column address bits, and the bank address follows the row address bits, thus supporting more devices. The number of address bits used depends on the density of the memory part. The controller ignores the unused bits, which can all be tied High.

User Interface Accesses

The user backend logic communicates with the memory controller through a FIFO-based user interface. This interface consists of three related buses:

- A Command/ Address FIFO bus, which accepts write/read commands as well as the corresponding memory address from the user
- A Write Data FIFO bus, which accepts the corresponding write data when the user issues a write command on the Command/ Address bus
- A Read bus on which the corresponding read data for an issued read command is returned

The user interface has the following timing and signaling restriction: When issuing a write command, the first write data word must be written to the Write Data FIFO no more than two clock cycles after the write command is issued. This restriction arises from the fact that the controller assumes write data is available when it receives the write command from the user.

The `clk_tb` signal is connected to `clkdiv_0` in the controller. If the user clock domain is different from `clkdiv_0` / `clk_tb` of the MIG, the user should add FIFOs for all data inputs and outputs of the controller in order to synchronize them to the `clk_tb`.

Write Interface

Figure 3-23 shows the user interface block diagram for write operations.

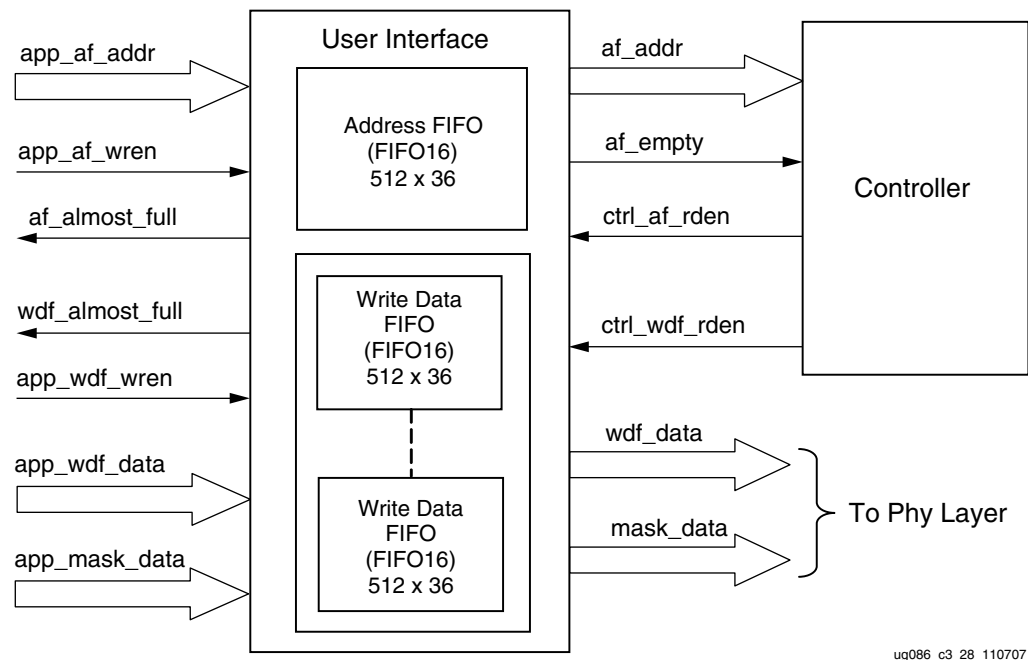


Figure 3-23: User Interface Block Diagram for Write Operations

The following steps describe the architecture of the Address and Write Data FIFOs and show how to perform a write burst operation to DDR2 SDRAM from the user interface.

1. The user interface consists of an Address FIFO and a Write Data FIFO. These FIFOs are constructed using Virtex-4 FPGA FIFO16 primitives with a 512 x 36 configuration. The 36-bit architecture comprises one 32-bit port and one 4-bit port. For Write Data FIFOs, the 32-bit port is used for data bits and the 4-bit port is used for mask bits. Mask bits

are available only when supported by the memory part *and* when the **data mask** option is enabled in the MIG GUI. Some memory parts, such as Registered DIMMs of x4 parts, do not support mask bits.

2. The Common Address FIFO is used for both write and read commands, and comprises a command part and an address part. Command bits discriminate between write and read commands.
3. User interface data width `app_wdf_data` is four times that of the memory data width. For an 8-bit memory width, the user interface is 32 bits consisting of two rising-edge data and two falling-edge data. For every 8 bits of data, there is a mask bit. For 72-bit memory data, the user interface data width `app_wdf_data` is 288 bits, and the mask data `app_mask_data` is 36 bits.
4. The minimum configuration of the Write Data FIFO is 512 x 36 for a memory data width of 8 bits.
5. Depending on the memory data width, MIG instantiates multiple FIFO16s to gain the required width. For designs using 8-bit data width, one FIFO16 is instantiated; for 72-bit data width, a total of nine FIFO16s are instantiated. The bit architecture comprises 16 bits of rising-edge data, 2 bits of rising-edge mask, 16 bits of falling-edge data, and 2 bits of falling-edge mask, which are all stored in a FIFO16. MIG routes the `app_wdf_data` and `app_mask_data` to FIFO16s accordingly.
6. The user can initiate a write to memory by writing to the Address FIFO and the Write Data FIFO when the FIFO Full flags are deasserted. Status signal `af_almost_full` is asserted when Address FIFO is full, and similarly `wdf_almost_full` is asserted when Write Data FIFO is full.
7. Both the Address FIFO and Write Data FIFO Full flags are deasserted with power-on.
8. The user should assert the Address FIFO write-enable signal `app_af_wren` along with address `app_af_addr` to store the write address and write command into the Address FIFO.
9. The user should assert the Data FIFO write-enable signal `app_wdf_wren` along with write data `app_wdf_data` and mask data `app_mask_data` to store the write data and mask data into the Write Data FIFO. The user should provide two rising-edge and two falling-edge data together for each write to the Data FIFO.
10. The controller reads the Address FIFO by issuing the `ctrl_af_rden` signal. The controller reads the Write Data FIFO by issuing the `ctrl_wdf_rden` signal after the Address FIFO is read. It decodes the command part after the Address FIFO is read.

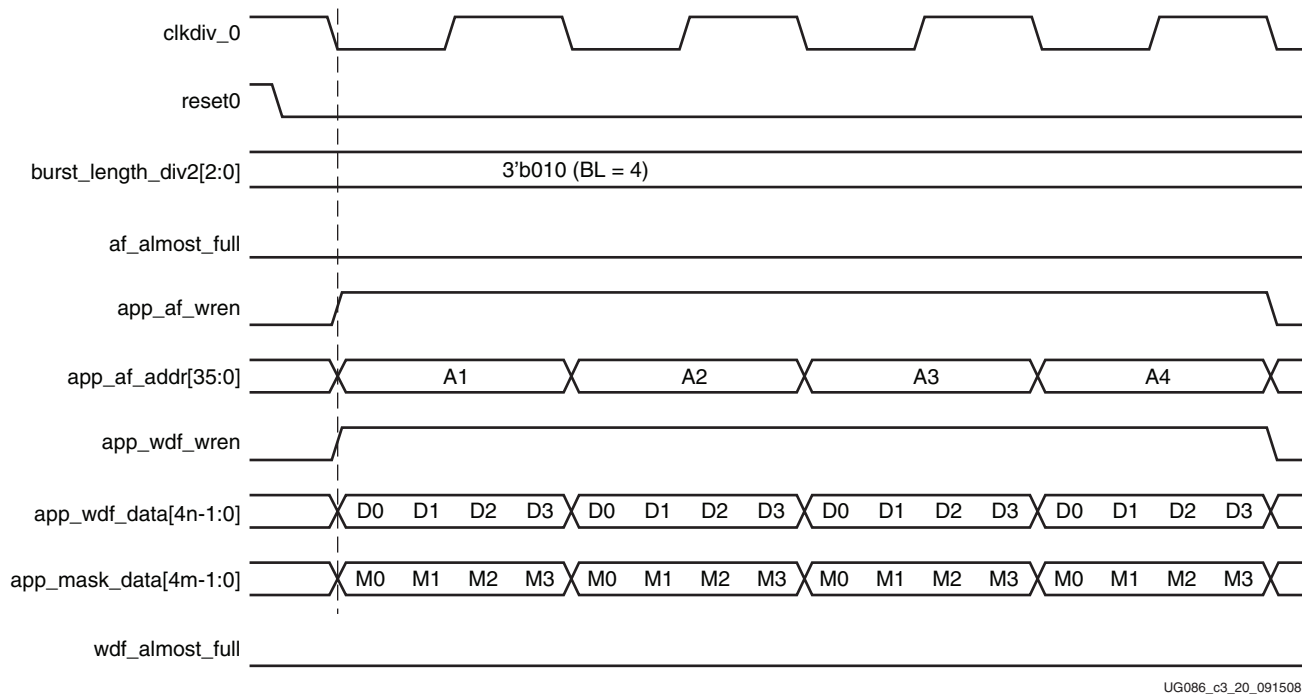
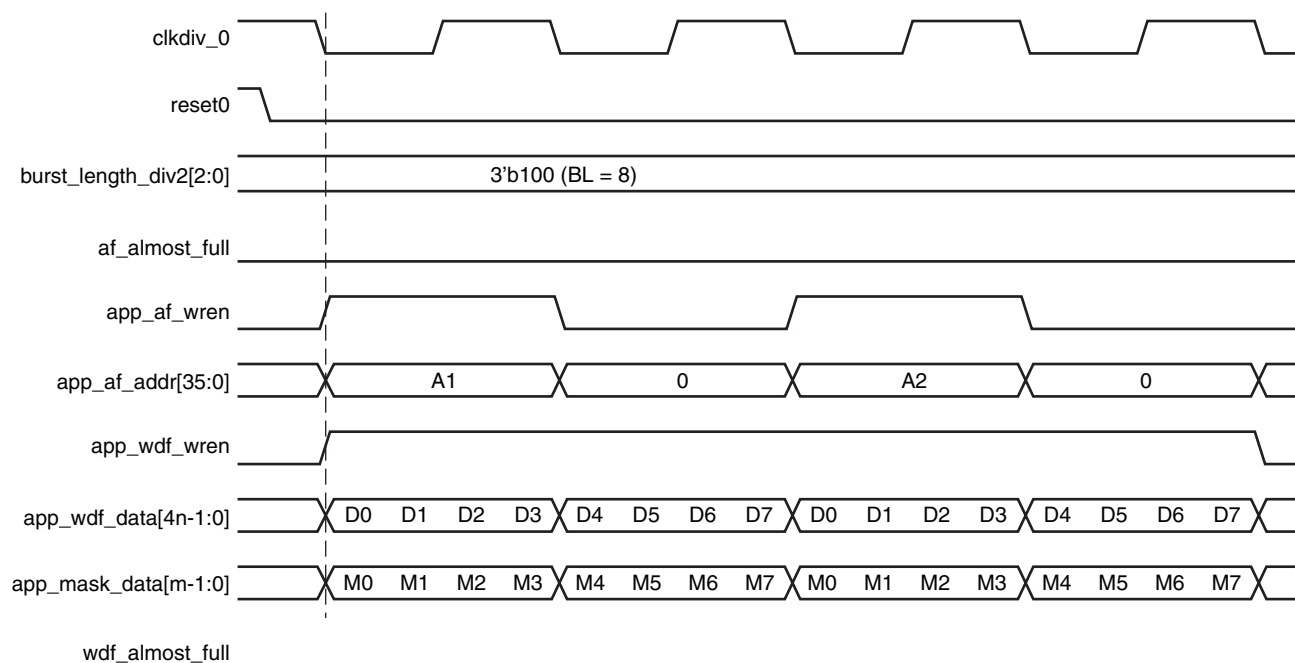


Figure 3-24: DDR2 SDRAM Write Burst (BL = 4) for Four Bursts

- The write command timing diagram in Figure 3-24 is derived from the MIG-generated testbench. As shown (burst length of 4), each write to the Address FIFO must be coupled with *one* write to the Data FIFO.

Note: The user can start filling the Write Data FIFO two clocks after the Address FIFO is written, because there is a two-clock latency between the command fetch and reading the Data FIFO. Using the terms shown in Figure 3-24 and Figure 3-25, therefore, the user can assert the A1 address two clocks before D0D1D2D3. Similarly, A2, A3, and A4 can be advanced by two clocks.



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Figure 3-25: DDR2 SDRAM Write Burst (BL = 8) for Two Bursts

12. The write command timing diagram in [Figure 3-25](#) is derived from the MIG-generated testbench. As shown (burst length of 8), each write to the Address FIFO must be coupled with *two* writes to the Data FIFO. Because the controller first reads the address and command together, the address need not coincide with the last data. After the command is analyzed (nearly two clocks later for a worst-case timing scenario), the controller sequentially reads the data in four clocks. Thus, there are six clocks from the time the address is read to the time the last data is read.

Correlation between the Address and Data FIFOs

There is a worst case two-cycle latency from the time the address is loaded into the address FIFO on APP_AF_ADDR[35:0] to the time the controller decodes the address. Because of this latency, it is not necessary to provide the address on the last clock where data is entered into the data FIFO. If the address is written before the last data phase, the overall efficiency and performance increases because it eliminates or reduces the two-cycle latency. However, if the address is written before data is input into the data FIFO, a FIFO empty condition might result because the Data FIFO does not contain valid data.

Based on these considerations, Xilinx recommends entering the address into the address FIFO between the first data phase and the next-to-last data phase. For a burst of four or eight, this means the Address can be asserted two clocks before the first data phase. This implementation increases efficiency by reducing the two clock latency and guarantees that valid data is available in the Data FIFO.

Read Interface

Figure 3-26 shows a block diagram of the read interface.

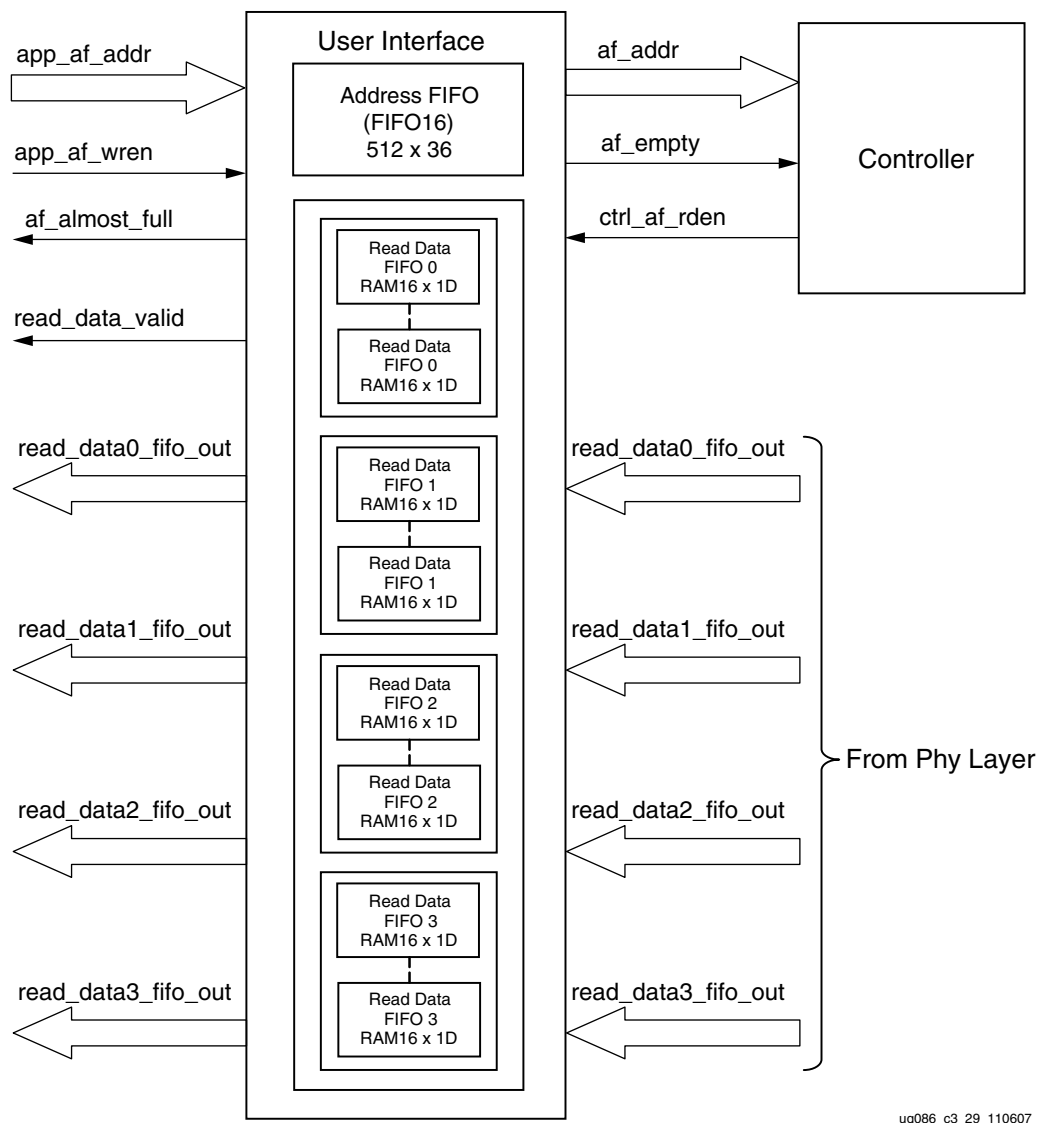


Figure 3-26: User Interface Block Diagram for Read Operation

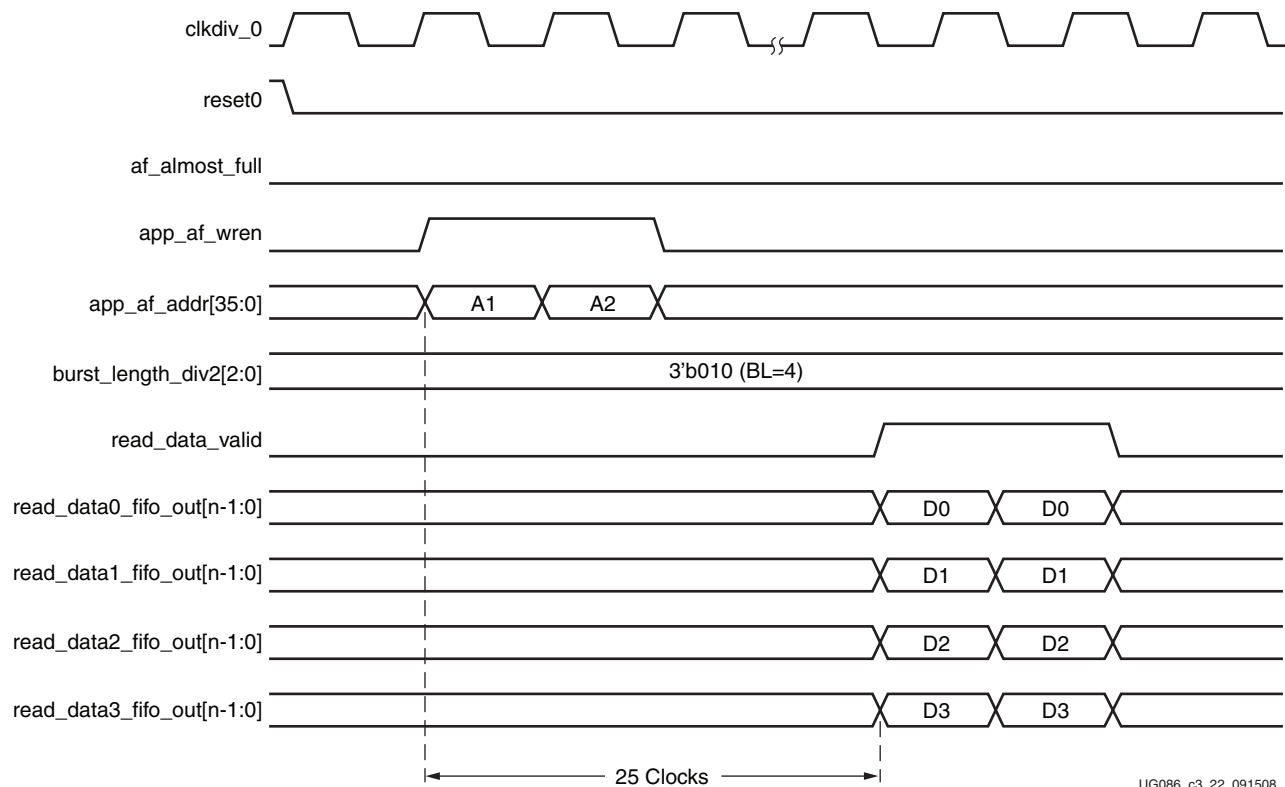
The following steps describe the architecture of the Read Data FIFOs and show how to perform a burst read operation from DDR SDRAM from the user interface.

1. The read user interface consists of an Address FIFO and a Read Data FIFO. The Address FIFO is common to both read and write operations. These FIFOs are constructed using Virtex-4 FPGA Distributed RAMs with a 16 x 1 configuration. MIG instantiates a number of RAM16Ds depending on the data width. For example, for 8-bit data width, MIG instantiates a total of 32 RAM16Ds, 16 for first and second rising-edge data and 16 for first and second falling-edge data. Similarly, for 72-bit data width, MIG instantiates a total of 288 RAM16Ds, 144 for first and second rising-edge data and 144 for first and second falling-edge data.

2. The user can initiate a read to memory by writing to the Address FIFO when the FIFO Full flag `af_almost_full` is deasserted.
3. To write the read address and read command into the Address FIFO, the user should issue the Address FIFO write-enable signal `app_af_wren` along with read address `app_af_addr`.
4. The controller reads the Address FIFO containing the address and command. After decoding the command, the controller generates the appropriate control signals to memory.
5. Prior to the actual read and write commands, the design calibrates the latency (number of clock cycles) from the time the read command is issued to the time data is received. Using this pre-calibrated delay information, the controller generates the write-enable signals to the Read Data FIFOs.

After the power-up calibration is done, dummy reads are executed to set up the delay between the read command and read data from the memory. During the time these dummy reads are in progress, the read enable is generated with each read command and is delayed until the read data matches the write data. This delay includes CAS latency, trace delay, and path delay. This precalculated delay is used for asserting the read-enable signals that latch the data into the Read Data FIFOs. The delays are calculated on a per-DQS basis. For example, if a bank has two DQS signals, there are two read enables used to latch the read data to the FIFOs. The strobe (DQS), data (DQ), and clock (CK/CK) signals should be matched in trace length from the FPGA to the memory device. MIG ensures that a DQS and its corresponding DQ signals do not cross a bank boundary.

6. The `read_data_valid` signal is asserted when data is available in the Read Data FIFOs.



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Figure 3-27: DDR2 SDRAM Read Burst (BL = 4) for Two Bursts

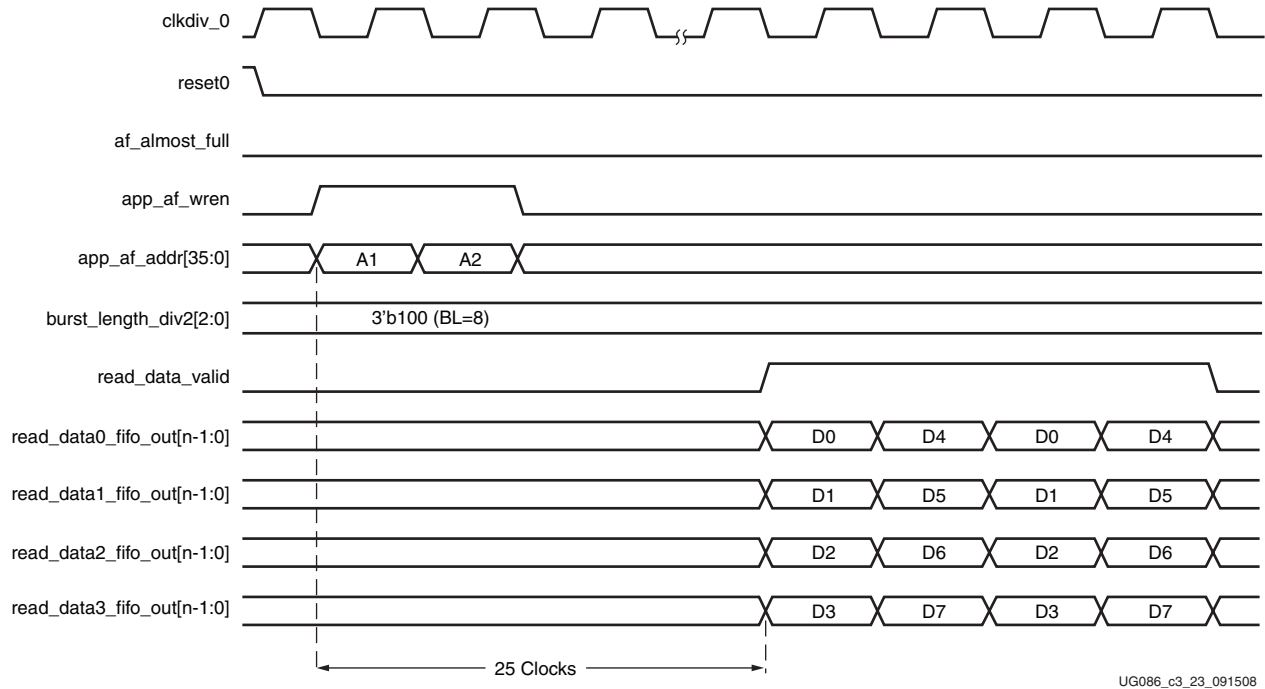


Figure 3-28: DDR2 SDRAM Read Burst (BL = 8) for Two Bursts

7. Figure 3-27 shows the user interface timing diagram for a burst length of 4, and Figure 3-28 shows user interface timing diagram for a burst length of 8. Both the cases shown here are for a CAS latency of 4 at 200 MHz. The read latency is calculated from the point when the read command is given by the user to the point when the data is available with the `read_data_valid` signal. The minimum latency in this case is 25 clocks, where no precharge is required, no auto-refresh request is pending, the user commands are issued after initialization is completed, and the first command issued is a Read command. Controller executes the commands only after initialization is done as indicated by the `init_done` signal.
8. After the address and command are loaded into the Address FIFO, it takes 25 clock cycles minimum for the controller to assert the `read_data_valid` signal.
9. Read data is available only when the `read_data_valid` signal is asserted. The user should access the read data on every positive edge of the `read_data_valid` signal.

Table 3-25 shows how the 25 clocks from the read command to the read data are broken up.

Table 3-25: Read Command to Read Data Clock Cycles

Parameter	Number of Clocks (CLKDIV_0)
Read Command to Empty Signal Deassertion	7 Clocks
Empty to Active Command	5.5 Clocks
Active to Read Command	3 Clocks
Memory Read Command to Read Data Valid	9.5 Clocks
Total:	25 Clocks

In general, read latency varies based on the following parameters:

- CAS latency (CL) and additive latency (AL)
- The number of commands already in the FIFO pipeline before the read command is issued
- Whether an ACTIVATE command needs to be issued to open the new bank/row
- Whether a PRECHARGE command needs to be issued to close a previously opened bank
- Specific timing parameters for the memory, such as TRAS, and TRCD in conjunction with the bus clock frequency
- Possible interruption of commands and/or forced closure of banks/rows when the periodic AUTO REFRESH command is issued
- Commands issued by the user before initialization is complete, causing latency to be indeterminate
- Board-level and chip-level (for both memory and FPGA) propagation delays

User to Controller Interface

[Table 3-26](#) lists the signals between the user interface and the controller.

Table 3-26: Signals between User Interface and Controller

Port Name	Port Width	Port Description	Notes
waf_addr	36	Output of the Address FIFO in the user interface. Mapping of these address bits: Memory Address (CS, Bank, Row, Column): [31:0] Dynamic Command Request: [34:32] Reserved: [35]	Monitor FIFO-full status flag to write address into the Address FIFO
af_almost_empty	1	The user interface Address FIFO empty status flag output. The user application can write to the Address FIFO when this signal is asserted until the write data FIFO-full status flag is asserted.	FIFO16 Almost Empty Flag
ctrl_waf_RdEn	1	Read Enable input to Address FIFO in the user interface	This signal is asserted for one CLKDIV_0 clock cycle when the controller state is write, read, Load Mode register, Precharge All, Auto Refresh, or Active resulting from dynamic command requests. Figure 3-29 shows the timing waveform for a burst length of 8 with two back-to-back writes followed by two back-to-back reads.

Table 3-26: Signals between User Interface and Controller (Cont'd)

Port Name	Port Width	Port Description	Notes
ctrl_wdf_Rden	1	Read Enable input to Write Data FIFO in the user interface	The controller asserts this signal one CLKDIV_0 clock cycle after the first write state. This signal remains asserted for one clock cycle for a burst length of 4 and two clock cycles for a burst length of 8. Figure 3-29 shows the timing waveform. Sufficient data must be available in the Write Data FIFO associated with a write address for the required burst length before issuing a write command. For example, for a 64-bit data bus and a burst length of 4, the user should input four 64-bit data words in the Write Data FIFO for every write address before issuing the write command.

The memory address (Waf_addr) includes the column address, row address, bank address, and chip-select width for deep memory interfaces.

Column Address

```
[`column_address - 1:0]
```

Row Address

```
[(`row_address + `column_address) - 1:`column_address]
```

Bank Address

```
[(`bank_address + `row_address + `column_address) - 1:(`column_address + `row_address)]
```

Chip Select

```
[`cs_width + `bank_address + `row_address + `column_address - 1:`bank_address + `row_address + `column_address]
```

Dynamic Command Request

Table 3-27 lists the commands supported from user interface.

Table 3-27: User Interface Commands

Command	Description
001	Auto Refresh
010	Precharge All
100	Write
101	Read

Figure 3-29 describes two consecutive writes followed by two consecutive reads with a burst length of 8. Table 3-28 lists the state signal values for Figure 3-29.

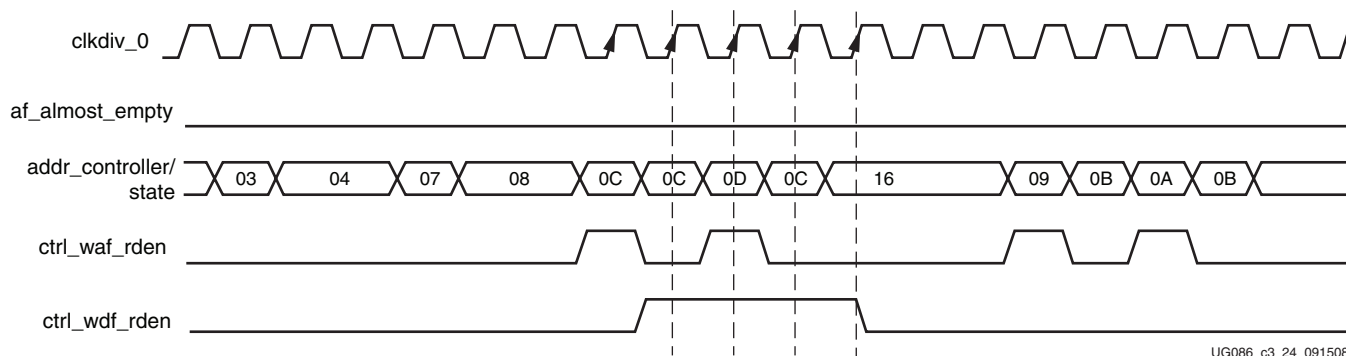


Figure 3-29: Controller Read of Command and Data from User Interface FIFOs for a Burst Length of 8

Table 3-28: State Signal Values for Figure 3-29

State Signal Value (hex)	Description
03	precharge
04	precharge_wait
07	active
08	active_wait
09	first_read
0A	burst_read
0B	read_wait
0C	first_write
0D	burst_write
0E	write_wait
16	write_read

Controller to Physical Layer Interface

Table 3-29 lists the signals between the controller and the physical layer.

Table 3-29: Signals between the Controller and Physical Layer

Signal Name	Signal Width	Signal Description	Notes
ctrl_wren	1	Output from the controller to the write datapath. Write DQS and DQ generation begins when this signal is asserted.	Asserted for two CLKDIV_0 cycles for a burst length of 4 and three CLKDIV_0 cycles for burst length of 8. Asserted one CLKDIV_0 cycle earlier than the WRITE command for CAS latency values of 4 and 5.
ctrl_wr_dis	1	Output from the controller to the write datapath. Write DQS and DQ generation ends when this signal is asserted.	Asserted for one CLKDIV_0 cycle for a burst length of 4 and two CLKDIV_0 cycles for burst length of 8. Asserted one CLKDIV_0 cycle earlier than the WRITE command for CAS latency values of 4 and 5.
ctrl_odd_latency	1	Output from the controller to the write datapath. Asserted when the selected CAS latency is an odd number. Required for generation of write DQS and DQ after the correct latency (CAS latency – 1).	
ctrl_RdEn_div0	1	Output from the controller to the datapath generated with each read command. This is delayed by the precalculated amount and is used as a write enable to the read data capture FIFOs.	This signal is asserted for one CLKDIV_0 clock cycle for a burst length of 4 and two clock cycles for a burst length of 8.
ctrl_dummyread_start	1	Output from the controller to the write datapath. When this signal is asserted, the strobe and data calibration begin.	This signal must be asserted when valid read data is available on the read data bus. This signal is deasserted when the dp_dly_slct_done signal is asserted.
dp_dly_slct_done	1	Output from the read datapath to the controller indicating the strobe and data calibration are complete.	This signal is asserted when the data and strobe are calibrated. Normal operation begins after this signal is asserted.

Figure 3-30 describes the timing waveform for control signals from the controller to the physical layer with a CAS latency of 4 and an additive latency of 0.

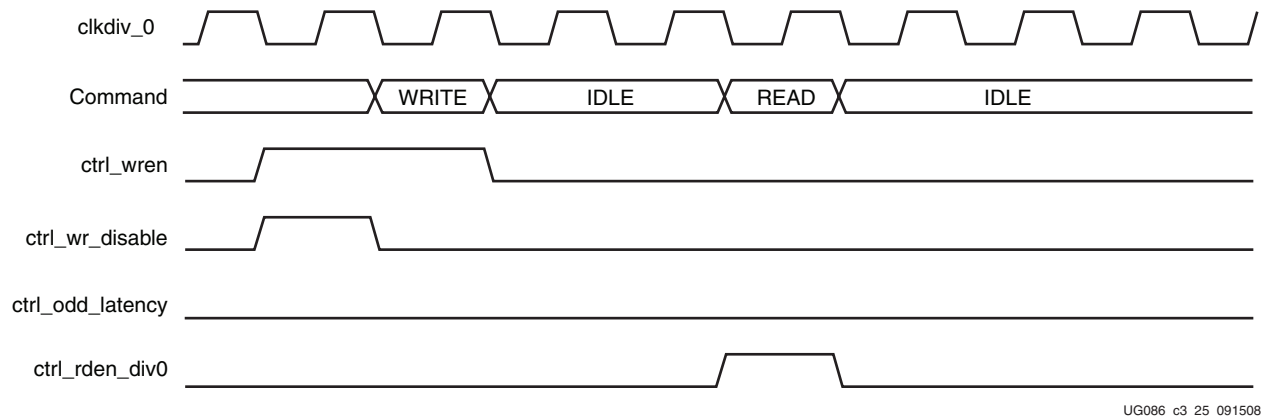


Figure 3-30: Timing Waveform for Control Signals from the Controller to the Physical Layer

SerDes DDR2 SDRAM Signal Allocations

MIG allows bank selection for different classes of memory signals. Table 3-30 shows the list of signals allocated in a group from bank selection checkboxes.

Table 3-30: SerDes DDR2 SDRAM Signal Allocations

Bank Selected	Signals Allocated in the Group
Address	Memory address, memory control, and memory clock signals
Data	Data, data mask, and data strobes
System Control	System reset from user interface and status signals
System Clock	System clocks from user interface

Note: Timing has been verified for most of the MIG generated configurations. For the best timing results, adjacent banks in the same column of the FPGA should be used. Banks that are separated by unbonded banks should be avoided because these can cause timing violations.

Simulating the DDR2 SDRAM Design

After generating the design, MIG creates a `sim` folder in the specified path. This folder contains simulation files for a particular design. The `sim` folder contains the external testbench, memory model, and `.do` file to simulate the generated design. The memory model files are currently generated in Verilog only. To learn more details about the files in the `sim` folder and to simulate the design, refer to “Simulation Guide,” page 499.

For single-rank DIMMs, MIG outputs only the base part memory model. In the simulation testbench (`sim_tb_top` in the `sim` folder), MIG instantiates the required number of memory models. For example, a 1 GB single-rank DIMM with the base part is 1 Gb, and MIG instantiates the base model eight times. If the MIG generated memory model is to be used with the user’s test bench, multiple instances should be used based on the selected configuration.

The MIG output memory model considers the `MEM_BITS` parameter by default for memory range allocation. This covers only a partial memory range, i.e., $2^{\text{MEM_BITS}}$. To allocate the full memory range, the `MAX_MEM` parameter should be set in the memory

model. Allocating the full memory range might exceed the memory of the operating system, thus causing memory allocation failure in simulations.

Simulation Violations

There might be simulation violations for frequencies such as 150 MHz where the clock period is not an integer value. At 150 MHz, the clock period value in the simulation testbench is 6.66 ns and the MIG tool rounds it to 6.67 ns. Consider a memory T_{RCD} value of 20 ns. MIG calculates the T_{RCD} count value based on the clock period, $RCD_COUNT_VALUE = 20/6.67 = 2.998 = 3$ (after rounding off) in the design parameter file. The T_{RCD} value for 3 clock cycles is $3 \times 6.66 = 19.98$, which causes timing violations by 20 ps. The difference between the clock period in the external simulation testbench versus the MIG tool causes timing violations. This is only one example case. There might be more such scenarios. These are only simulation warnings. Functionally, there should be no issues. To remove these warnings, the related count value can be increased by one.

Changing the Refresh Rate

The formula is similar to the Virtex-4 FPGA DDR2 direct-clocking case. However, since the refresh logic in the controller is running at half the memory bus rate, the formula is $MAX_REF_CNT = (\text{refresh interval}) / (2 * \text{clock period})$. For example, for a refresh rate of 3.9 μs with a memory bus running at 267 MHz:

$$MAX_REF_CNT = 3.9 \mu\text{s} / (2 * \text{clock period}) = 3.9 \mu\text{s} / 7.49 \text{ ns} = 521 \text{ (decimal)} = 0x209$$

If the above value exceeds $2^{MAX_REF_WIDTH} - 1$, the value of MAX_REF_WIDTH must be increased accordingly in `parameters_0.v` (or `.vhd`) to increase the width of the counter used to track the refresh interval.

Supported Devices

The design generated out of MIG is independent of memory package, hence the package part of the memory component is replaced with XX, where XX indicates a don't care condition. The tables below list the components (Table 3-31) and DIMMs (Table 3-32 through Table 3-34) supported by the tool for DDR2 SerDes clocking designs.

In supported devices, an X in the component column denotes a single alphanumeric character. For example MT47H128M4XX-3 can be either MT47H128M4BP-3 or MT47H128M4B6-3. An XX for Registered DIMMs denotes a single or two alphanumeric characters. For example, MT9HTF3272XX-667 can be either MT9HTF3272Y-667 or MT9HTF3272DY-667. Pin mapping for x4 RDIMMs is provided in Appendix G, “Low Power Options.”

Table 3-31: Supported Components for DDR2 SDRAM

Components	Packages (XX)	Components	Packages (XX)
MT47H64M4XX-3	BP	MT47H16M16XX-3	BG
MT47H64M4XX-37E	BP	MT47H16M16XX-37E	BG
MT47H64M4XX-5E	BP	MT47H16M16XX-5E	BG
MT47H128M4XX-3	B6,CB,GB	MT47H32M16XX-3	BN,CC,FN,GC
MT47H128M4XX-37E	B6,CB,GB	MT47H32M16XX-37E	BN,CC,FN,GC
MT47H128M4XX-5E	B6,CB,GB	MT47H32M16XX-5E	BN,CC,FN,GC
MT47H256M4XX-3	BT,HQ	MT47H64M16XX-3	BT,HR

Table 3-31: Supported Components for DDR2 SDRAM (Cont'd)

Components	Packages (XX)	Components	Packages (XX)
MT47H256M4XX-37E	BT,HQ	MT47H64M16XX-37E	BT,HR
MT47H256M4XX-5E	BT,HQ	MT47H64M16XX-5E	BT,HR
MT47H512M4XX-3	HG	MT47H128M16XX-3	HG
MT47H512M4XX-37E	HG	MT47H128M16XX-37E	HG
MT47H512M4XX-5E	HG	MT47H128M16XX-5E	--
MT47H32M8XX-3	BP	HYB18T1G800XXXX-3S	C2F,C2FL
MT47H32M8XX-37E	BP	HYB18T1G800XXXX-37	C2F,C2FL
MT47H32M8XX-5E	BP	HYB18T1G160XXXX-3S	C2F,C2FL
MT47H64M8XX-3	B6,CB,F6,GB	HYB18T1G160XXXX-37	C2F,C2FL
MT47H64M8XX-37E	B6,CB,F6,GB	HYB18T1G400XXXX-3S	C2F,C2FL
MT47H64M8XX-5E	B6,CB,F6,GB	HYB18T1G400XXXX-37	C2F,C2FL
MT47H128M8XX-3	BT,HQ	HYB18T512800XXXX-3S	B2F,B2FL
MT47H128M8XX-37E	BT,HQ	HYB18T512800XXXX-37	B2F,B2FL
MT47H128M8XX-5E	BT,HQ	HYB18T512160XXXX-3S	B2F,B2FL
MT47H256M8XX-3	HG	HYB18T512160XXXX-37	B2F,B2FL
MT47H256M8XX-37E	HG	HYB18T512400XXXX-3S	B2F,B2FL
MT47H256M8XX-5E	HG	HYB18T512400XXXX-37	B2F,B2FL

Table 3-32: Supported Registered DIMMs for DDR2 SDRAM

Registered DIMMs	Registered DIMMs
MT9HTF3272Y-667	MT18HTF6472Y-667
MT9HTF3272PY-667	MT18HTF6472PY-667
MT9HTF3272Y-53E	MT18HTF6472Y-53E
MT9HTF3272PY-53E	MT18HTF6472PY-53E
MT9HTF3272Y-40E	MT18HTF6472Y-40E
MT9HTF3272PY-40E	MT18HTF6472PY-40E
MT9HTF6472Y-667	MT18HTF12872Y-667
MT9HTF6472PY-667	MT18HTF12872PY-667
MT9HTF6472Y-53E	MT18HTF12872Y-53E
MT9HTF6472PY-53E	MT18HTF12872PY-53E
MT9HTF6472Y-40E	MT18HTF12872Y-40E
MT9HTF6472PY-40E	MT18HTF12872PY-40E
MT9HTF12872Y-667	MT18HTF25672Y-667
MT9HTF12872PY-667	MT18HTF25672PY-667

Table 3-32: Supported Registered DIMMs for DDR2 SDRAM (Cont'd)

Registered DIMMs	Registered DIMMs
MT9HTF12872Y-53E	MT18HTF25672Y-53E
MT9HTF12872PY-53E	MT18HTF25672PY-53E
MT9HTF12872Y-40E	MT18HTF25672Y-40E
MT9HTF12872PY-40E	MT18HTF25672PY-40E
MT18HTF6472G-53E	--

Table 3-33: Supported Unbuffered DIMMs for DDR2 SDRAM

Unbuffered DIMMs	Unbuffered DIMMs
MT4HTF1664AY-667	MT8HTF6464AY-40E
MT4HTF1664AY-53E	MT8HTF12864AY-667
MT4HTF1664AY-40E	MT8HTF12864AY-53E
MT4HTF3264AY-667	MT8HTF12864AY-40E
MT4HTF3264AY-53E	MT9HTF3272AY-667
MT4HTF3264AY-40E	MT9HTF3272AY-53E
MT4HTF6464AY-667	MT9HTF3272AY-40E
MT4HTF6464AY-53E	MT9HTF6472AY-667
MT4HTF6464AY-40E	MT9HTF6472AY-53E
MT8HTF6464AY-667	MT9HTF6472AY-40E
MT8HTF6464AY-53E	--

Table 3-34: Supported SODIMMs for DDR2 SDRAM

SODIMMs	SODIMMs
MT4HTF1664HY-667	MT8HTF3264HY-667
MT4HTF1664HY-53E	MT8HTF3264HY-53E
MT4HTF1664HY-40E	MT8HTF3264HY-40E
MT4HTF3264HY-667	MT8HTF6464HY-667
MT4HTF3264HY-53E	MT8HTF6464HY-53E
MT4HTF3264HY-40E	MT8HTF6464HY-40E

Hardware Tested Configurations

The frequencies shown in [Table 3-35](#) were achieved on the Virtex-4 FPGA ML461 Memory Interfaces Development Board under nominal conditions. This frequency should not be used to determine the maximum design frequency. The maximum design frequency supported in the MIG wizard is based on a combination of the TRCE results for fabric timing on multiple device/package combinations and I/O timing analysis using FPGA and memory timing parameters for a 64-bit wide interface.

Table 3-35: Hardware Tested Configurations

Synthesis Tools	XST and Synplicity
HDL	Verilog and VHDL
FPGA Device	XC4VLX25-FF668-11
Burst Lengths	4, 8
CAS Latency	4, 5
Additive Latency	0, 1, 2
8-bit Design	Tested on 16-bit Component "MT47H32M16XX-3"
64-bit Design	Tested on 64-bit UDIMM "MT8HTF6464AY-667"
72-bit Design	Tested on 72-bit RDIMM "MT9HTF6472Y-667"
Frequency Range	140 MHz to 400 MHz for component and Registered DIMMs
	140 MHz to 290 MHz for Unbuffered DIMMs

Implementing QDRII SRAM Controllers

This chapter describes how to implement QDRII SRAM interfaces for Virtex®-4 FPGAs generated with MIG. This design is based on XAPP703 [Ref 20].

Feature Summary

The QDRII controller design supports the following:

- A maximum frequency of 250 MHz
- 9-bit, 18-bit, 36-bit, and 72-bit data widths
- Burst lengths of two and four
- Implementation using different Virtex-4 devices
- Operation with any 9-bit, 18-bit, and 36-bit memory component
- Verilog and VHDL
- With and without a testbench
- With and without a DCM

Design Frequency Range

Table 4-1: Design Frequency Range in MHz

Memory	FPGA Speed Grade					
	-10		-11		-12	
	Min	Max	Min	Max	Min	Max
Component	120	200	120	240	120	250

Limitations

Four different FIFOs are accessible from the user interface: the Read Address FIFO, Read Data FIFO, Write Address FIFO, and Write Data FIFO. The Read Address FIFO is used to store the read command and read address. The Write Address FIFO is used to store the write command and write address. The Write Data FIFO is used to store the write data from the user interface. The controller stores the read data from the memory to the Read Data FIFO. The controller executes read commands only when the Read Address FIFO is not empty and the Read Data FIFO is not full. Similarly, the controller executes write commands only when the Write Address FIFO and Write Data FIFO are not empty. The sequence of commands executed by the controller might not be the same as the sequence of commands that are stored in the Read Address and Write Address FIFOs. The controller executes write and read commands alternately when it finds valid write and read

commands, irrespective of the sequence of commands that are written to the FIFOs from the user interface. Consider an example in which 10 write commands followed by 10 read commands are issued from the user interface, but the controller executes write, read, write, read... and so on. If the Read Address FIFO is empty or the Read Data FIFO is full, and the Write Address FIFO is not empty, the controller executes all write commands sequentially. Similarly, if the Write Address FIFO is empty, the Read Address FIFO is not empty, and the Read Data FIFO is not full, the controller executes all read commands sequentially.

The controller remains in the IDLE state when the Write Address FIFO is empty, and either the Read Address FIFO is empty or the Read Data FIFO is full.

Architecture

Figure 4-1 shows a top-level block diagram of the QDRII memory controller. One side of the QDRII memory controller connects to the user interface denoted as Block Application. The other side of the controller interfaces to QDRII memory. The memory interface data width is selectable.

Data is double-pumped to QDRII SRAM on both the positive and the negative clock edges. The HSTL_18 Class II/O standard is used for the data, address, and control signals.

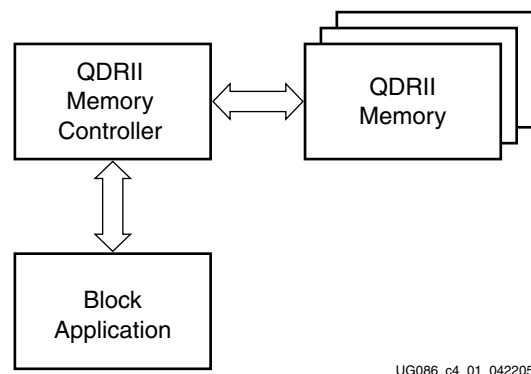


Figure 4-1: QDRII Memory Controller

QDRII SRAM interfaces are source-synchronous and double data rate like DDR SDRAM interfaces.

The key advantage to QDRII devices is they have separate data buses for reads and writes to SRAM.

Interface Model

The memory interface is layered to simplify the design and make the design modular.

Figure 4-2 shows the layered memory interface in the QDRII memory controller. The three layers are the application layer, the implementation layer, and the physical layer.

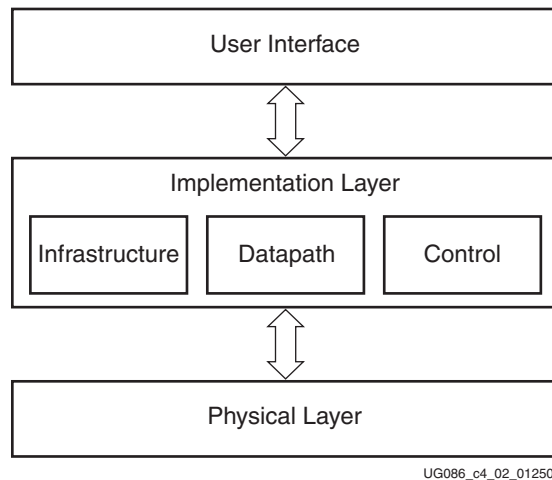


Figure 4-2: Interface Layering Model

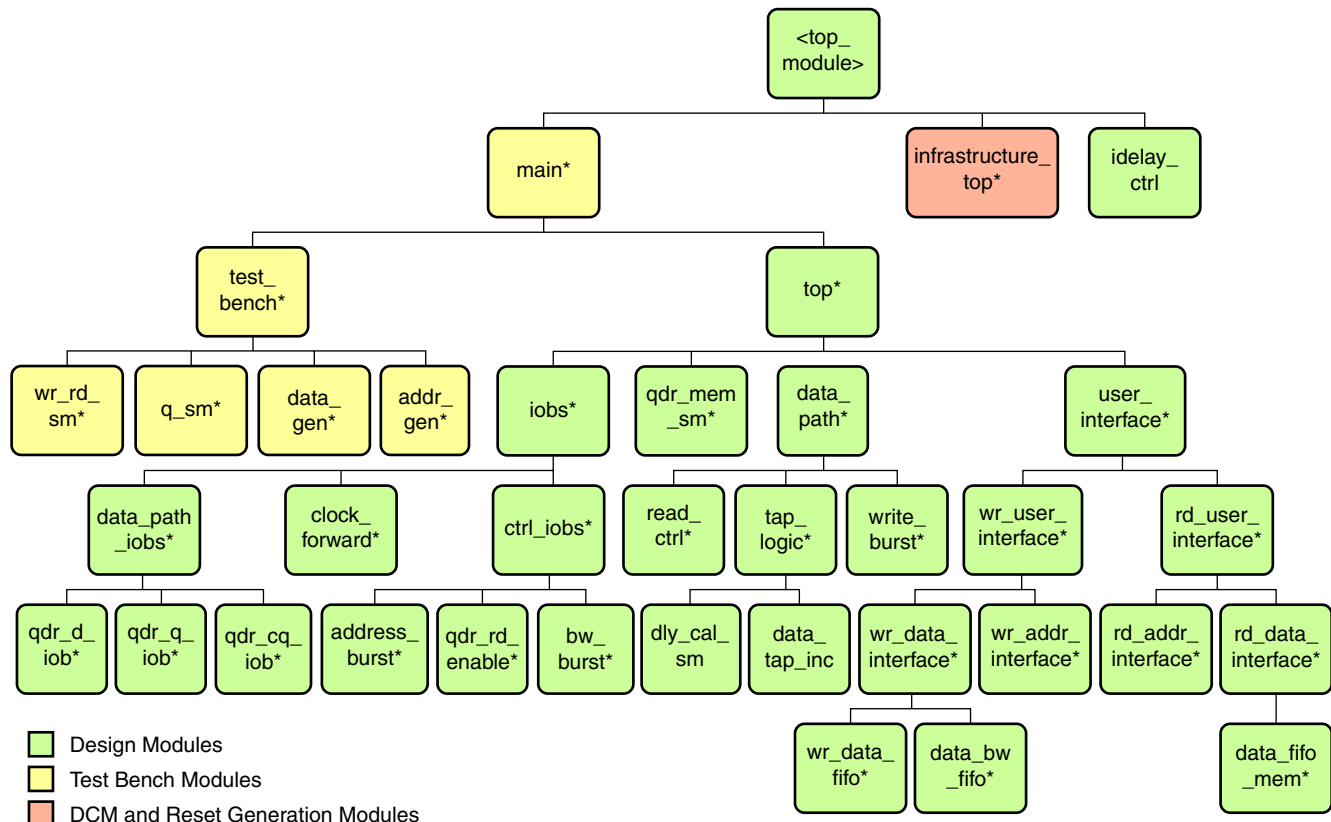
The application layer comprises the user interface, which initiates memory writes and reads by writing data and memory addresses to the User Interface FIFOs. The implementation layer comprises the infrastructure, datapath, and control logic.

- The infrastructure logic consists of the DCM and reset logic generation circuitry.
- The datapath logic consists of the calibration logic by which the data from the memory component is captured using the FPGA clock.
- The control logic determines the type of data transfer, that is, read/write with the memory component, depending on the User Interface FIFO's status signals.

The physical layer comprises the I/O elements of the FPGA. The controller communicates with the memory component using this layer. The I/O elements (such as IDDRs, ODDRs, and IDELAY elements) are associated with this layer.

Hierarchy

Figure 4-3 shows the QDRII SRAM controller hierarchy.



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Figure 4-3: QDRII SRAM Controller Hierarchy

Figure 4-3 shows the hierarchical structure of the QDRII SRAM design generated by MIG with a testbench and a DCM. The modules are classified as follows:

- Design modules
- Testbench modules
- Clocks and reset generation modules

There is a parameter file generated with the design that has all the user input and design parameters selected from MIG.

MIG can generate QDRII SRAM designs in four different ways:

- With a testbench and a DCM
- Without a testbench and with a DCM
- With a testbench and without a DCM
- Without a testbench and without a DCM

MIG outputs both an example_design and a user_design. The MIG-generated example_design includes the entire memory controller design along with a synthesized testbench (example user application). This testbench generates sample writes and reads and then uses comparison logic to verify that the data patterns written are the same as those received. This example_design can be used to test functionality both in simulation and in hardware. The user_design includes the memory controller design only. This design allows users to connect the MIG memory controller design to a user developed testbench (user application). Refer to Table 4-5, page 213 for user interface signals and to “Write

[Interface,” page 215](#) and [“Read Interface,” page 218](#) for timing restrictions on user interface signals.

Design clocks and resets are generated in the `infrastructure_top` module. When the **Use DCM** option is checked in MIG, a DCM primitive and the necessary clock buffers are instantiated in the `infrastructure_top` module. The inputs to this module are the differential design clock and a 200 MHz differential clock required for the IDELAYCTRL module. A user reset is also input to this module. Using the input clocks and reset signals, the system clocks and the system resets used in the design are generated in this module.

When the **Use DCM** option is unchecked in MIG, the `infrastructure_top` module does not have the DCM and the corresponding clock buffer instantiations; therefore, the system operates on the user-provided clocks. The system reset is generated in the `infrastructure_top` module using the `dcm_lock` signal and the ready signal of the IDELAYCTRL element. For more information on the clocking structure, refer to [“Clocking Scheme,” page 209](#).

Figure 4-4 shows a top-level block diagram of a QDRII SRAM design with a DCM and a testbench. Inputs to the design are referenced to a differential clock pair (refclk_p and refclk_n) for the controller design, a 200 MHz differential clock pair (dly_clk_200_p and dly_clk_200_n) for the IDELAYCTRL element, and the system reset signal, sys_rst_n. All design resets are generated using the dcm_locked signal, the sys_rst_n signal, and the dly_ready signal of the IDELAYCTRL element. The compare_error output signal indicates whether the design passes or fails. The dly_cal_done signal indicates the completion of initialization and calibration of the design. Because the DCM is instantiated in the infrastructure module, it generates the required clocks and reset signals for the design.

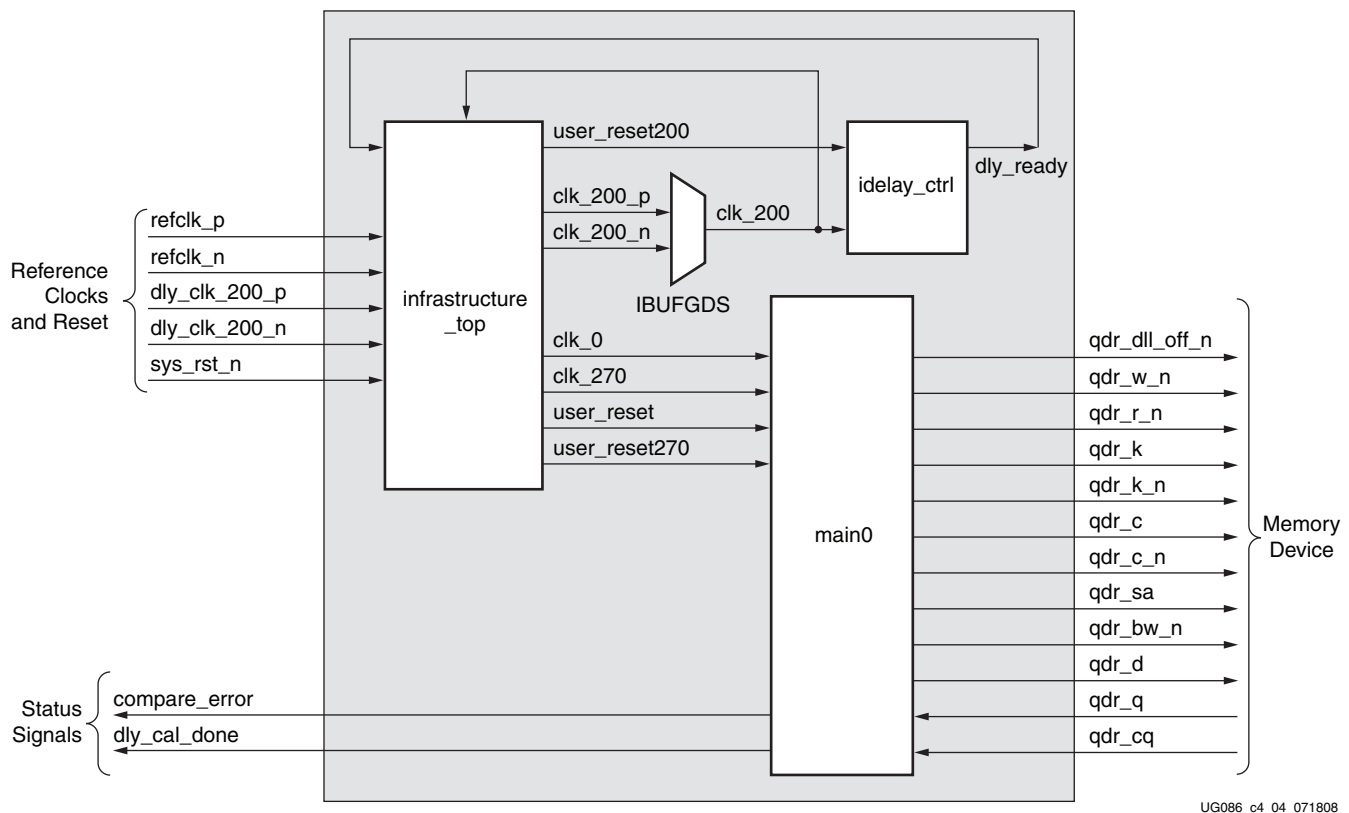
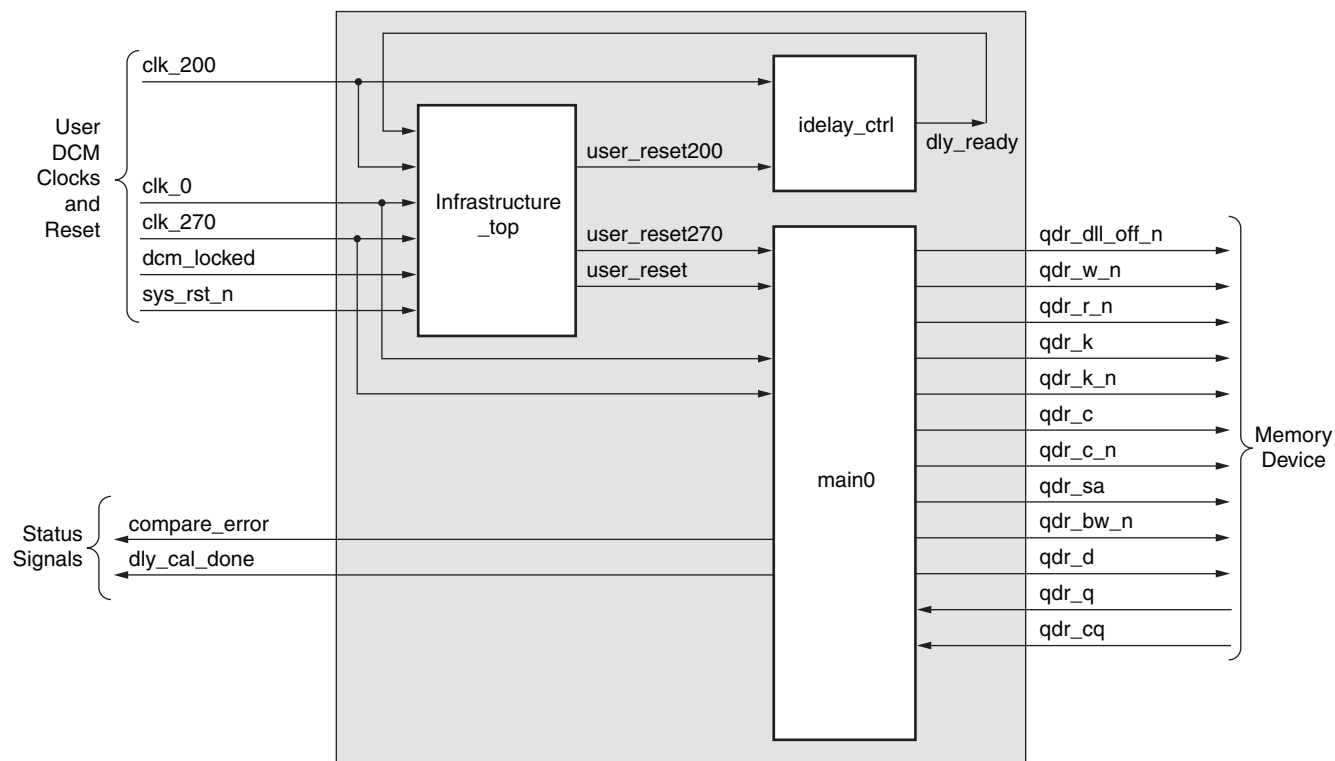


Figure 4-4: Top-Level Block Diagram of the QDRII SRAM Design with a DCM and a Testbench

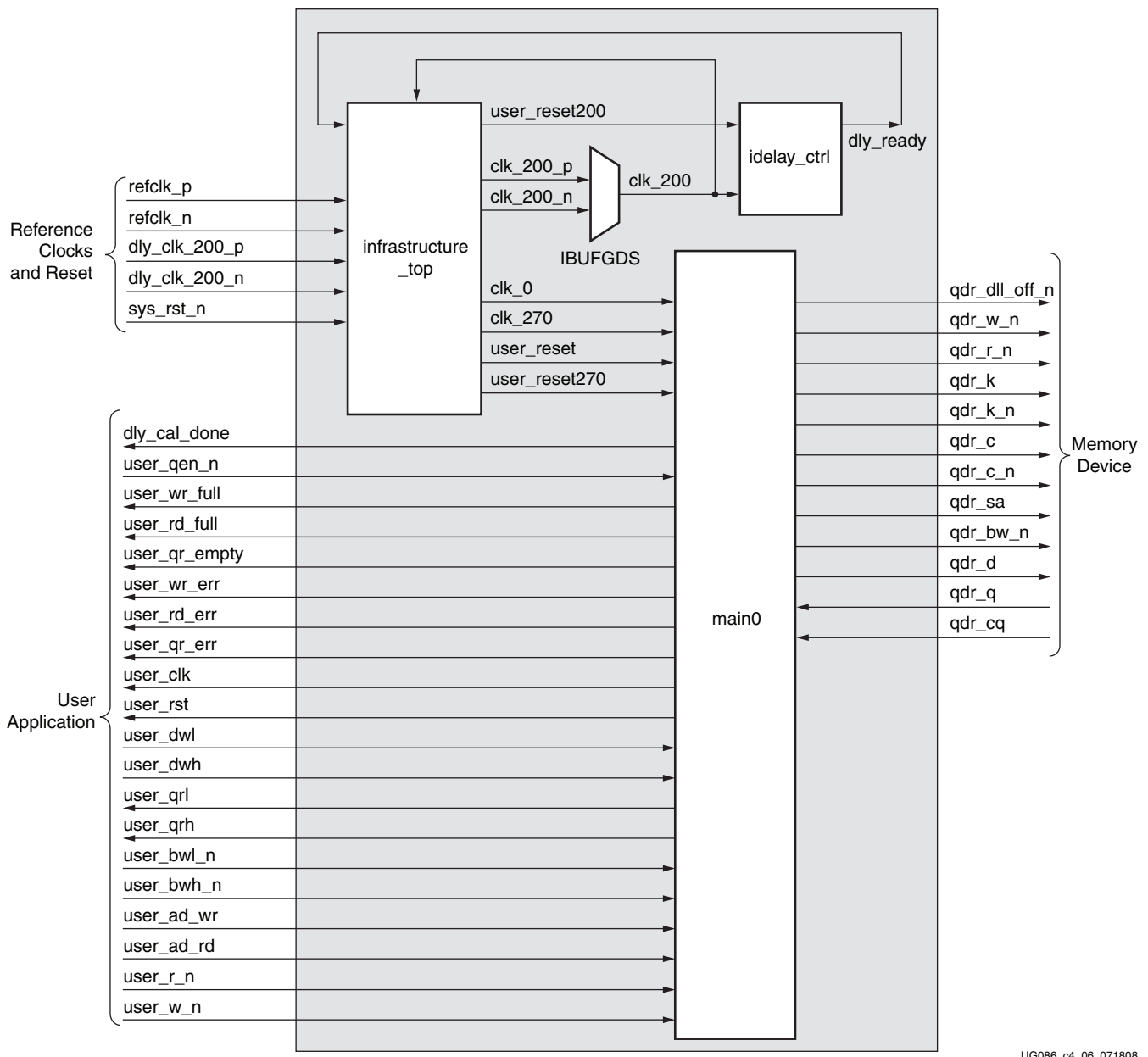
Figure 4-5 shows a top-level block diagram of a QDRII SRAM design without a DCM but with a testbench. The user should provide all the clocks and the dcm_locked signal. These clocks should be single-ended. sys_rst_n is the system reset signal. All design resets are generated using the dcm_locked signal, the sys_rst_n signal, and the dly_ready signal of the IDELAYCTRL element. The user application must have a DCM primitive instantiated in the design, and all user clocks should be driven through BUFs. The compare_error signal, which is the output of the design, indicates whether the design passes or fails. The testbench module does writes and reads, and also compares the read data with written data. The compare_error signal is set High on data mismatches. The dly_cal_done signal indicates the completion of initialization and calibration of the design.



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Figure 4-5: Top-Level Block Diagram of the QDRII SRAM Design with a Testbench but without a DCM

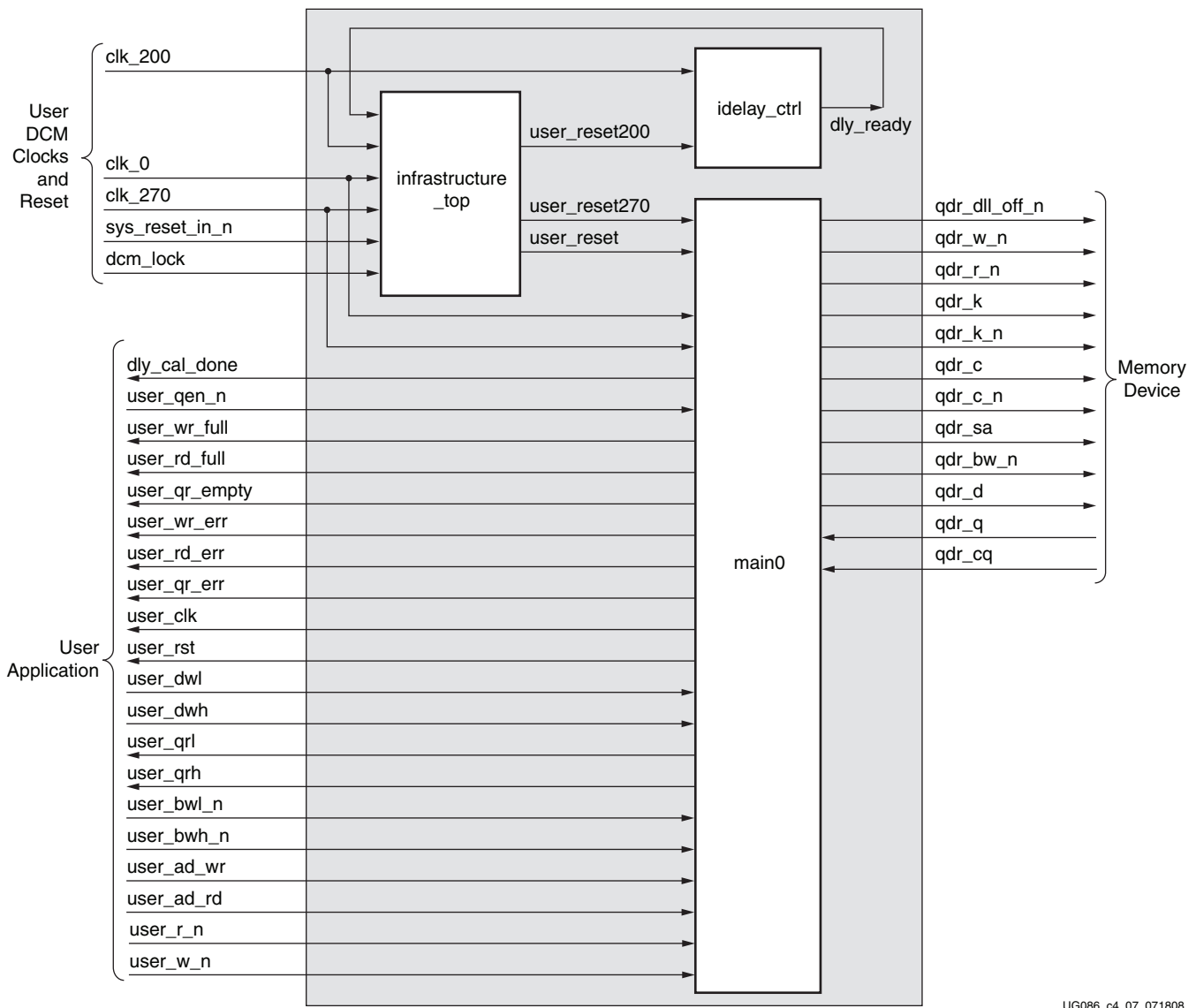
Figure 4-6 shows a top-level block diagram of a QDRII SRAM design with a DCM but without a testbench. `refclk_p` and `refclk_n` are differential input reference clocks. The DCM is instantiated in the infrastructure module that generates the required design clocks. `dly_clk_200_p` and `dly_clk_200_n` are used for the `IDELAYCTRL` element. `sys_rst_n` is the system reset signal. All design resets are generated using the `dcm_locked` signal, the `sys_rst_n` signal, and the `dly_ready` signal of `IDELAYCTRL` element. The user has to drive the user application signals. The design provides the `user_clk` and `user_rst` signals to the user to synchronize the user application signals with the design. The signal `user_clk` is connected to `clk0` clock signal in the controller. If the user clock domain is different from `clk0/user_clk`, the user should add FIFOs for all the inputs and output of the controller (user application signals), in order to synchronize them to `user_clk` clock. The `dly_cal_done` signal indicates the completion of initialization and calibration of the design.



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Figure 4-6: Top-Level Block Diagram of the QDRII SRAM Design with a DCM but without a Testbench

Figure 4-7 shows a top-level block diagram of a QDRII SRAM design without a DCM or a testbench. The user should provide all the clocks and the dcm_locked signal. These clocks should be single-ended. sys_rst_n is the system reset signal. All design resets are generated using the dcm_locked signal, the sys_rst_n signal, and the dly_ready signal of the IDELAYCTRL element. The user application must have a DCM primitive instantiated in the design, and all user clocks should be driven through BUFPGs. The user has to drive the user application signals. The design provides the user_clk and user_rst signals to the user to synchronize the user application signals with the design. The signal user_clk is connected to clk0 clock in the controller. If the user clock domain is different from clk0/user_clk, the user should add FIFOs for all the inputs and output of the controller (user application signals), in order to synchronize them to user_clk clock. The dly_cal_done signal indicates the completion of initialization and calibration of the design.

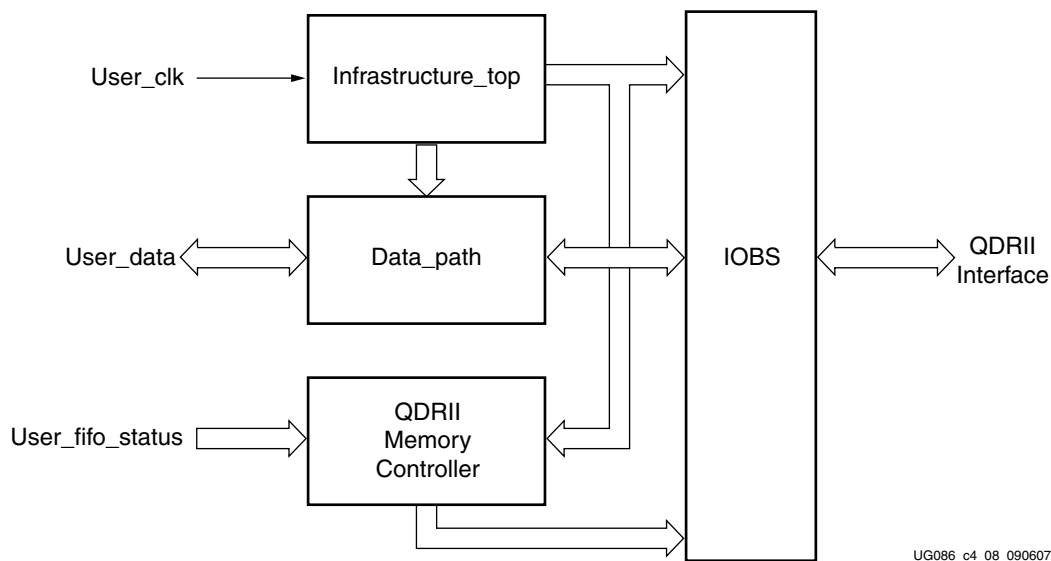


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Figure 4-7: Top-Level Block Diagram of the QDRII SRAM Design without a DCM or a Testbench

QDRII Memory Controller Modules

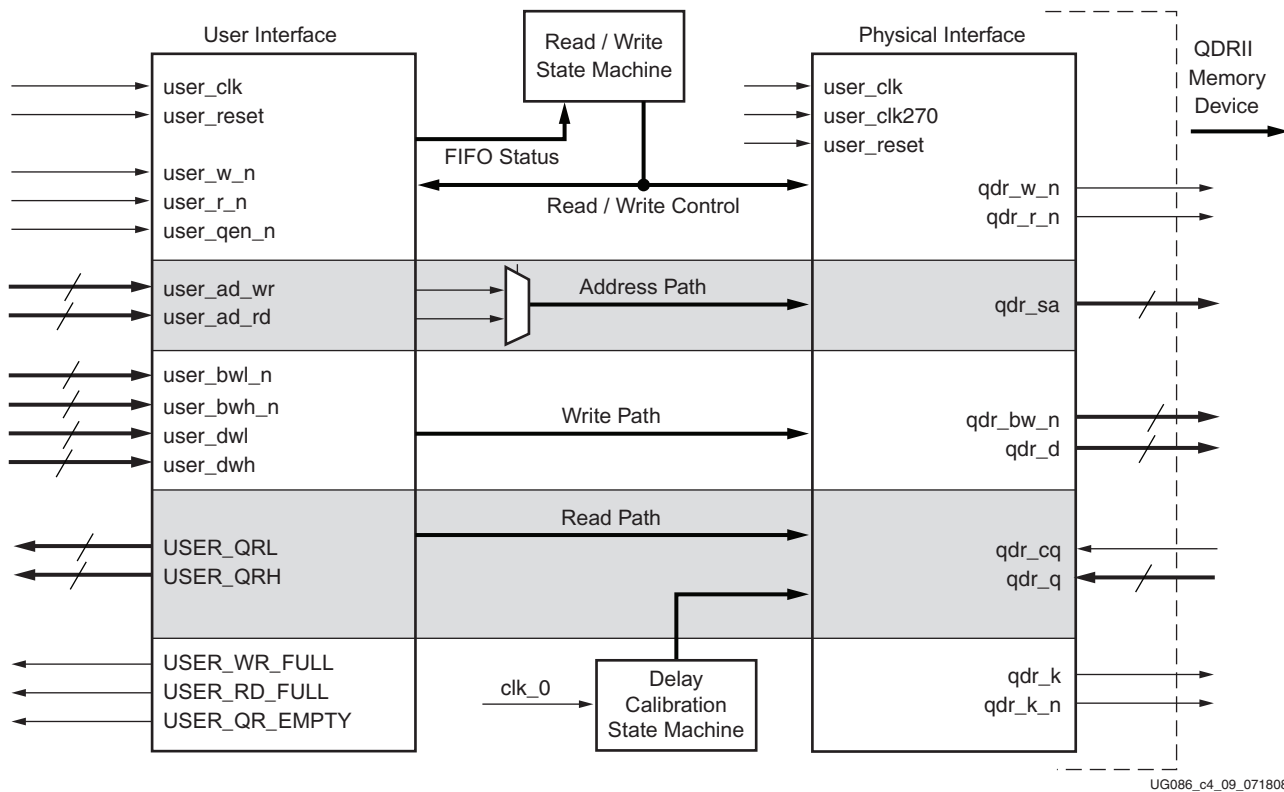
Figure 4-8 shows a detailed block diagram of the QDRII memory controller. The four blocks shown are subblocks of the top module. The functionalities of these blocks are explained in the subsections following the figure.



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Figure 4-8: QDRII Memory Controller Modules

Figure 4-9 shows the QDRII memory controller modules with a 36-bit interface.



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Figure 4-9: QDRII Memory Controller Modules

Controller

The QDRII memory controller initiates alternate Write and Read commands to the memory as long as the User Write Data FIFOs, the User Write Address FIFO, and the User Read Address FIFO are not empty, and the User Read Data FIFOs are not full.

The user writes the write data and the write address into the User Write Data FIFOs and the User Write Address FIFO, respectively. When neither the User Write Data FIFOs nor the User Write Address FIFO is empty, the QDRII controller generates a write-enable signal to the memory. When the write enable is asserted, the write data and the write address are transferred to memory from the User Write Data FIFOs and the User Write Address FIFO, respectively.

The read address from where the data is to be read from memory is stored by the user in the User Read Address FIFO. The QDRII memory controller generates a read-enable signal to the memory when the User Read Address FIFO is not empty and the User Read Data FIFOs are not full. When the read enable is asserted, the read address from the Read Address FIFO is transferred to memory. The captured read data from the memory corresponding to the read address is stored in the User Read Data FIFOs. The user can access the data read from memory by reading the User Read Data FIFOs.

Figure 4-10 shows the QDRII memory controller state machine for burst lengths of four. The controller state machine is in the IDLE state when the calibration is complete. When the User Write Data FIFO and the User Write Address FIFO are not empty (that is, when there are user-written write data and write address bits in the corresponding FIFOs), the state machine goes to the WRITE state, initiating a memory write of one complete burst.

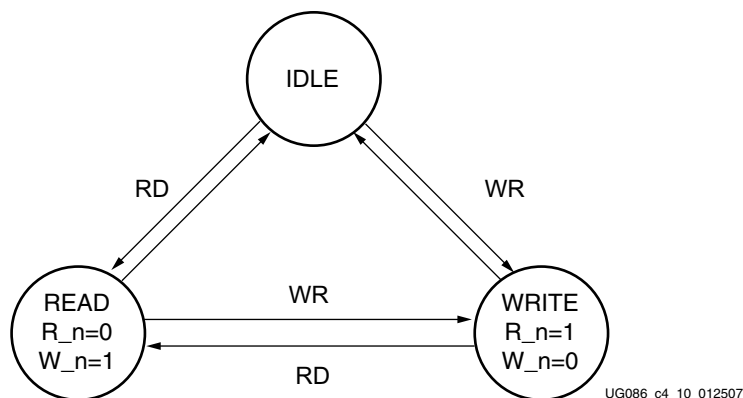


Figure 4-10: QDRII Memory Controller State Machine with Burst Lengths of 4

When the User Read Address FIFO is not empty (that is, the user has written read address bits into the User Read Address FIFO) and either Read Data FIFO is not full, the state machine goes to the READ state, initiating a memory read of one burst.

From the IDLE state, the QDRII memory controller can go to either the WRITE or the READ state depending on the not empty status of the Write Address FIFO and the Write Data FIFOs or the Read Address FIFO, and not full status of the Read Data FIFOs, respectively. Writes are given priority. In the WRITE state, a memory write is initiated, and the User Read Address Not Empty and User Read Data FIFOs full status are checked to transfer into the READ state. When the User Read Address FIFO is empty, or the User Read Data FIFOs are full, the state machine goes to the IDLE state.

In the READ state, a memory read is initiated, and the User Write Data and the User Write Address FIFO Not Empty status is checked before going to the WRITE state. If the FIFOs are empty, the state machine goes to the IDLE state.

Figure 4-11 shows a state machine of the QDR II memory controller for burst lengths of two. When calibration is complete, the state machine is in the IDLE state. When the User Write Data FIFO or Write Address FIFO is not empty (that is, when there are user-written write data and write address bits in the corresponding FIFOs), the state machine goes to the READ_WRITE state, initiating a memory write of one complete burst, or when the User Read Address FIFO is not empty, that is, the user has written read address bits into the User Read Address FIFO, and the User Read Data FIFOs are not full, the state machine goes to the READ_WRITE state, initiating a memory read of one complete burst.

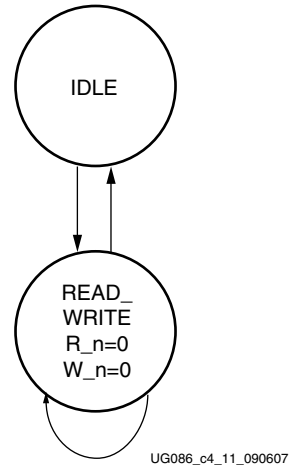


Figure 4-11: QDR II Memory Controller State Machine with Burst Lengths of 2

From the IDLE state, the QDR II memory controller goes to READ_WRITE state if either:

- the User Write Address FIFO and the User Write Data FIFO are not empty or,
- the User Read Address FIFO is not empty and the User Read Data FIFOs are not full

In the READ_WRITE state, the User Read Address Not Empty and User Read Data FIFOs Not Full status are checked to initiate a memory read. To initiate a memory write in the READ_WRITE state, the User Write Data FIFOs and the User Write Address FIFO Not Empty status are checked. If both the User Write Data FIFOs and User Write Address FIFO are empty, and the User Read Address FIFO is empty, or the User Read Data FIFOs are full, the state machine goes to the IDLE state. If the User Write Data FIFO and User Write Address FIFO are not empty, or the User Read Address FIFO is not empty and the User Read Data FIFO is not full, the state machine remains in the READ_WRITE state to issue memory writes or reads. The FIFOs are built using FIFO16 primitives in the data_bw_fifo, data_fifo_mem, rd_addr_interface, wr_addr_interface, and wr_data_fifo modules. Each FIFO has a threshold attribute called ALMOST_FULL_OFFSET whose value is set to F, by default, in the RTL. This value can be changed as needed. For valid FIFO threshold offset values, refer to UG070 [Ref 7].

Refer to XAPP703 [Ref 20] for detailed design and timing analysis of the QDR II memory controller module.

Datapath

The Datapath module transmits and receives data to and from the memories. Its major functions are listed below:

- Asserts a write-enable signal for memories with burst lengths of two or four
- Asserts a read-enable signal to memory and a write-enable signal to the User Read Data FIFO

- Generates increment/decrement signals (tap count) for IDELAY elements in the IOBS
- Center-aligns the data window to the FPGA clock

Refer to XAPP703 [Ref 20] for techniques on data writes to memory and data captures from memory. For burst lengths of two, the write-enable signal to memory is asserted at the same time that write data is driven. For burst lengths of four, the write-enable signal is asserted one clock before the write data is driven on the memory bus. The data is driven on both edges of the clock. The address to memory is driven for one full clock cycle for burst lengths of 4 and on both the edges of the clock cycle for burst lengths of 2.

Memory read data is edge-aligned with the source-synchronous clock, CQ. The QDRII memory clock, to which data is synchronized, is a free-running strobe. The free-running strobe from the memory CQ is captured using the FPGA clock. Thus the relation between the CQ strobe and the FPGA clock is found, and the strobe CQ is center-aligned with the FPGA clock. The same logic is applied to the read data Q window, which is center-aligned with the same FPGA clock. This in turn means that the same amount of tap delays are applied to both Q and CQ through IDELAY elements to center-align the Q and CQ windows with respect to the FPGA clock. By center-aligning the Read Data window Q with respect to the FPGA clock, the data capturing logic is complete.

The delay calibration circuit generates the delay reset, delay select, and delay increment values for IDELAY elements used in delaying strobes and data read from memory. The strobe is center-aligned with the FPGA clock, which results in the data window falling to the center of the FPGA clock. Refer to XAPP703 [Ref 20] for details about the delay calibration.

Infrastructure

The infrastructure (infrastructure_top) module generates the FPGA clock and reset signals. When differential clocking is used, refclk_p, refclk_n, dly_clk_200_p, and dly_clk_200_n signals appear. When single-ended clocking is used, refclk and idly_clk_200 signals appear. In addition, clocks are available for design use and a 200 MHz clock is provided for the IDELAYCTRL primitive. Differential and single-ended clocks are passed through global clock buffers before connecting to a DCM. For differential clocking, the output of the refclk_p/refclk_n buffer is single-ended and is provided to the DCM input. Likewise, for single-ended clocking, refclk is passed through a buffer and its output is provided to the DCM input. The outputs of the DCM are 0° and 270° phase-shifted versions of the input clock. After the DCM is locked, the design is in the reset state for at least 25 clocks. The infrastructure module also generates all of the reset signals required for the design.

Idelay_ctrl

This module instantiates the IDELAYCTRL primitive of the Virtex-4 FPGA. The IDELAYCTRL primitive is used to continuously calibrate the individual delay elements in its region to reduce the effect of process, temperature, and voltage variations. A 200 MHz clock has to be fed to this primitive.

The MIG tool instantiates the required number of IDELAYCTRLs in the RTL and uses the LOC constraints in the UCF file to fix their locations. The number of IDELAYCTRLs is defined by the IDELAYCTRL_NUM parameter in the idelay_ctrl module. In the RTL, DLY_READY is generated by doing a logical AND of the RDY signals of every IDELAYCTRL block.

IDELAYCTRL LOC constraints should be checked in the following cases:

- The MIG design is used with other IP cores or user designs that also require the use of IDELAYCTRL and IDELAYs.

- Previous ISE® software releases 8.2.03i and 9.1i had an issue with IDELAYCTRL block replication or trimming. When using these revisions of the ISE software, the user must instantiate and constrain the location of each IDELAYCTRL individually.

See UG070 [Ref 7] for more information on the requirements of IDELAYCTRL placement.

IOBS

All the input and output signals of the QDRII SRAM controller are implemented in the IOBS module. All address and byte enable signals are registered in the IOBs and driven out.

The IDELAY elements for the read strobe and data read from memory are implemented in the IOBS. The IOBS also implement bidirectional buffers for write and read data. It registers the output data (ODDR) before driving it out and registers the input data (IDDR).

Test Bench

The MIG tool generates two RTL folders, `example_design` and `user_design`. The `example_design` folder includes the synthesizable test bench, while `user_design` does not include the test bench modules. The MIG test bench performs one write command followed by one read command in an alternating manner for designs with a burst length of 4. For a burst length of 2, the test bench performs one write command and one read command in the same clock and repeats one write and one read command continuously. The number of words in a write command depends on the burst length. For a burst length of 4, the test bench writes a total of 4 data words for a single write command (2 rise data words and 2 fall data words). For a burst length of 2, the test bench writes a total of 2 data words. On every write command, the data pattern is incremented by one, and this is repeated with each subsequent write command. The initial data pattern for the first write command is 000. The test bench writes the 000, 001, 002, 003 data pattern in a sequence in which 000 and 002 are rise data words and 001 and 003 are fall data words for a 9-bit design. The falling edge data is always rising edge data plus one. For a burst length of 2, the data sequence for the first write command is 000, 001. The data sequence for the second write command is 002, 003. The pattern is then incremented for the next write command. For data widths greater than 9, the same data pattern is concatenated for the other bits. For a 36-bit design and a burst length of 4, the data pattern for the first write command is 000000000, 008040201, 010080402, 0180C0603.

Address generation logic generates the address in an incremental pattern for each write command. The same address location is repeated for the next read command. In Samsung components, the burst address increments are done by the memory, so the address is generated by the test bench in a linear incremental pattern. In Cypress parts, the MIG test bench increments the address for burst operation. After the address reaches the maximum value, it rolls back to the initial address, i.e., 00000.

During reads, comparison logic compares the read pattern with the pattern written, i.e., the 000, 001, 002, 003 pattern. For example, for a 9-bit design of burst length 4, the data written for a single write command is 000, 001, 002, and 003. During reads, the read pattern is compared with the 000, 001, 002, 003 pattern. Based on a comparison of the data, a status signal `error` is generated. If the data read back is the same as the data written, the error signal is 0, otherwise it is 1.

Clocking Scheme

Figure 4-12 shows the clocking scheme for this design. Global and local clock resources are used.

The global clock resources consist of a DCM, two BUFGs on DCM output clocks, and one BUFG for clk_200. The local clock resources consist of regional I/O clock networks (IBUFIO). The global clock architecture is discussed in this section.

The MIG tool allows the user to customize the design such that the DCM is not included. In this case, clk_0 and clk_270 must be supplied by the user.

Global Clock Architecture

The user must supply two input clocks to the design:

- A system clock running at the target frequency for the memory
- A 200 MHz clock for the IDELAYCTRL blocks.

These clocks can be either single-ended or differential. User can select single-ended or differential clock input option from MIG GUI. Differential clocks are connected to the IBUFGDS and single-ended clock is connected to IBUFG.

The system clock from the output of the IBUFGDS or the IBUFG is connected to the DCM to generate the various clocks used by the memory interface logic.

The clk_200 output of the IBUFGDS or the IBUFG is connected to the BUFG. The output of the BUFG is used for IDELAY IOB delay blocks for aligning read capture data.

The DCM generates two separate synchronous clocks for use in the design. This is shown in Table 4-2 and Figure 4-12. The clock structure is same for both example design and user design. For designs with out DCM instantiation, DCM and the BUFGs should be instantiated at user end to generate the required clocks.

Table 4-2: QDRII Interface Design Clocks

Clock	Description	Logic Domain
clk_0	Skew compensated replica of the input system clock.	The clock for the controller and the user interface logic. The QDRII bus-related I/O flip-flops (e.g., memory clocks). This clock is used to register the data, address, and command signals, and the address and data enables for the user interface logic ⁽¹⁾ . This clock is also used to generate the read data and read data valid signals.
clk_270	270° phase-shifted version of clk_0	Used in the write data path section of physical layer. Clocks write path control logic, QDRII side of the Write Data FIFO, and output flip-flops for D and memory control and address signals. This clock is also used to generate FIFO status signals.

Notes:

1. See “QDRII Controller System and User Interface Signals,” page 212 for timing requirements and restrictions on the user interface signals.

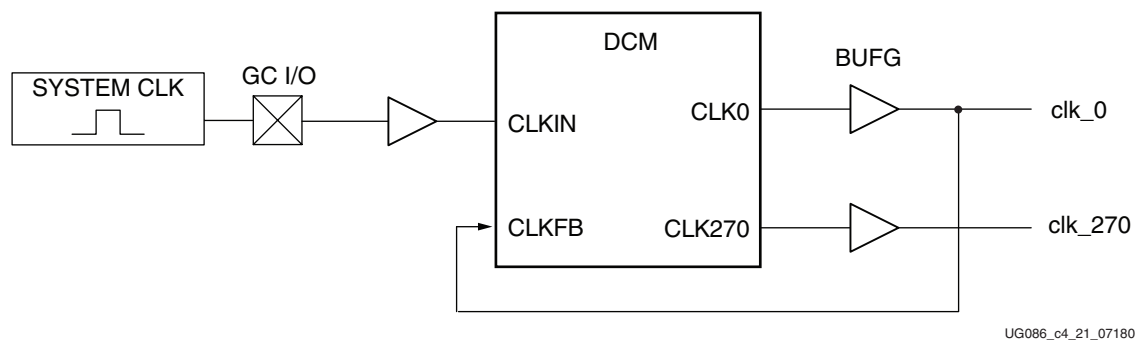


Figure 4-12: Clocking Scheme for QDRII Interface Logic

QDRII SRAM Initialization and Calibration

QDRII memory is initialized through a specified sequence. The QDRII device requires 2048 clock cycles of clock input after its DLL has been enabled. After the DCM clocks are stable, the controller waits for a specified amount of time before asserting the `qdr_dll_off_n` signal to the memory. This signal can also be pulled up to a High on the memory device without being driven from the FPGA.

Any command can be issued to the memory only after the 2048 clock cycle wait time. After 2048 clock cycles, the `INIT_DONE` signal is asserted indicating the completion of the initialization sequence. Following initialization, the relationship between the data and the FPGA clock is calculated using the TAP logic. The memory strobe CQ is a free-running clock from the memory component. Because the read data Q and the memory strobe CQ are edge-aligned, the strobe is passed through the IDELAY elements of the Virtex-4 device and the taps are adjusted to center-align the strobe pulse with respect to the FPGA clock. The same number of taps are applied to the data window's IDELAY element to center-align the data window with respect to the FPGA clock. XAPP701 [Ref 18] provides more information about the calibration architecture.

Calibration is done in two stages:

1. In the first stage of calibration, the read strobe CQ is center-aligned with respect to the FPGA clock. CQ is a free-running clock from QDRII memory. The read data Q is edge-aligned with the read strobe CQ. The first and second edges of the CQ strobe are detected using the FPGA clock to determine the center of the CQ window.

Once the CQ window is center-aligned with the FPGA clock, the same amount of delay (tap counts) is applied to the read data windows Q through the IDELAY element, so that the Q window is center-aligned with the FPGA clock.

Port `cq_q_cal_done` in the `data_path` module indicates the status of the first stage calibration. When `cq_q_cal_done` is asserted High, it indicates the completion of first stage calibration. After the first stage calibration is complete, the second stage calibration starts.

2. In the second stage of calibration, the write enable signal for the Read Data FIFO is determined by delaying the controller-issued read command. This delay is calibrated based on the delay between the read command and the corresponding read data at the Read Data FIFO. For this delay calibration, the controller writes a known fixed pattern of data into a memory location and reads back from the same location. This read data is compared against the known fixed pattern. The delay between the read command and the correct pattern read data comparison is the delay calibration.

The `final_dly_cal_done` port in the `data_path` module indicates the status of the second stage calibration. When `final_dly_cal_done` is asserted High, it indicates the completion of second stage calibration, which implies the completion of the whole initialization and calibration process. After the initialization and calibration is done (i.e., the `dly_cal_done` signal in `design_top` is asserted High), the controller can start issuing user commands to the memory.

In the second stage calibration, when the pattern read data does not match with the pattern write data, the controller does not issue any further pattern read commands, and the controller gets stuck in the calibration state. The design must be restarted for the calibration to start from the beginning.

QDRII Controller System and User Interface Signals

Table 4-3 through Table 4-4 describe the QDRII controller system interface signals with and without a DCM, respectively. Table 4-5 describes the QDRII user interface signals without a testbench. Table 4-6 describes the QDRII memory interface signals. In these tables, all signal directions are with respect to the QDRII memory controller.

Table 4-3: QDRII SRAM System Interface Signals (with a DCM)

Signal Name	Direction	Description
refclk_p, refclk_n	Input	Reference clock input made up of differential clock pairs. This clock pair goes to a differential input buffer. The differential buffer output goes to the DCM input. The DCM generates the required clocks for the design.
refclk	Input	Single-ended system clock input. This clock is an input to IBUFG. The IBUFG output is connected to the DCM clock input. The DCM generates the required clocks for the design. This input system clock is present only when the SINGLE_ENDED clocks option is selected in MIG FPGA options. When the DCM option is deselected, both differential or single-ended input system clocks are not present.
dly_clk_200_p, dly_clk_200_n	Input	200 MHz differential clock used in the idelay_ctrl logic.
sys_rst_n	Input	Reset to the QDRII memory controller.
compare_error	Output	This signal represents the status of the comparison between the read data and the corresponding write data.
dly_cal_done	Output	This signal is asserted when the design initialization and calibration is complete.

Table 4-4: QDRII SRAM System Interface Signals (without a DCM)

Signal Name	Direction	Description
clk_0	Input	Input clock
clk_270	Input	Input clock with a 270° phase difference.
clk_200	Input	200 MHz clock for the IDELAYCTRL primitives.
dcm_locked	Input	This active-High signal indicates whether the user DCM is locked or not.
sys_rst_n	Input	Reset to the QDRII memory controller.
compare_error	Output	This signal represents the status of the comparison between the read data and the corresponding write data.
dly_cal_done	Output	This signal is asserted when the design initialization and calibration is complete.

Table 4-5: QDRII SRAM User Interface Signals (without a Testbench)

Signal Name ⁽¹⁾	Direction	Description
user_wr_full	Output	This signal indicates the User Write FIFO status. It is asserted when either the User Write Address FIFO or the User Write Data FIFO is full. When this signal is asserted, any writes to the User Write Address FIFO and the User Write Data FIFO are invalid, possibly leading to controller malfunction.
user_rd_full	Output	This signal indicates the User Read Address FIFO status. It is asserted when the User Read Address FIFO is full. When this signal is asserted, all writes to the User Read Address FIFO are ignored.
user_qr_empty	Output	This signal indicates the User Read Data FIFO status. This signal is asserted when the User Read Data FIFO is empty. When this signal is asserted, all reads to the User Read Data FIFO are invalid.
user_wr_err	Output	This signal is asserted when an error occurs while writing to the User Write Data FIFO or the User Write Address FIFO.
user_rd_err	Output	This signal is asserted when an error occurs while writing to the User Read Address FIFO.
user_qr_err	Output	This signal is asserted when an error occurs while reading the User Read Data FIFO.
dly_cal_done	Output	This signal is asserted to indicate that the calibration is done.
user_clk ⁽²⁾	Output	All user interface signals are to be synchronized to this clock. The user_clk is sourced from clk_0 in the controller.
user_rst	Output	This reset is active until the DCM is not locked.
user_dw1 [(data_width-1):0]	Input	Positive-edge data for memory writes. This data bus is valid when user_w_n is asserted.
user_dwh [(data_width-1):0]	Input	Negative-edge data for memory writes. This data bus is valid when user_w_n is asserted.
user_qrl [(data_width-1):0]	Output	Positive-edge data read from memory. This data is output when user_qen_n is asserted.
user_qrh [(data_width-1):0]	Output	Negative-edge data read from memory. This data is output when user_qen_n is asserted.
user_bwl_n [(BW_width-1):0]	Input	Byte enables for QDRII memory positive-edge write data. These byte enables are valid when user_w_n is asserted.
user_bwh_n [(BW_width-1):0]	Input	Byte enables for QDRII memory negative-edge write data. These byte enables are valid when user_w_n is asserted.
user_ad_wr [(addr_width-1):0] ⁽³⁾	Input	QDRII memory address for write data. This bus is valid when user_w_n is asserted.
user_ad_rd [(addr_width-1):0] ⁽³⁾	Input	QDRII memory address for read data. This bus is valid when user_r_n is asserted.

Table 4-5: QDRII SRAM User Interface Signals (without a Testbench) (Cont'd)

Signal Name ⁽¹⁾	Direction	Description
user_qen_n	Input	This active-Low signal is the read enable for the User Read Data FIFOs. The QDRII memory controller captures the data read from memory and stores it in the Read Data FIFOs. The user can access these FIFOs to get the data read from memory.
user_w_n	Input	This active-Low signal is the write enable for the User Write Data and User Write Address FIFOs. The user asserts this signal to write new data to the FIFOs. The QDRII memory controller reads the data from the User Write Data FIFO and writes to memory at the address located in the User Write Address FIFO.
user_r_n	Input	This active-Low signal is the write enable for the User Read Address FIFO. The user asserts this signal to read new data from memory. The QDRII memory controller reads the address from the Read Address FIFO and does a memory read to the corresponding memory address.

Notes:

1. All user interface signal names are prepended with a controller number, for example, cntrl0_QDR_Q. QDRII SRAM devices currently support only one controller.
2. The user_clk is connected to clk_0 in the controller. If the user clock domain is different from clk_0 / user_clk of MIG, the user should add FIFOs for all data inputs and outputs of the controller, in order to synchronize them to the user_clk.
3. The number of address bits used depends on the density of the memory part. The controller ignores the unused bits, which can all be tied High.

Table 4-6: QDRII SRAM Interface Signals

Signal Name	Direction	Description
qdr_d	Output	During WRITE commands, the data is sampled on both edges of K.
qdr_q	Input	During READ commands, the data is sampled on both edges of the FPGA clk.
qdr_bw_n	Output	Byte enables for QDRII memory write data. The byte enables are valid when user_w_n is asserted
qdr_sa	Output	Address for READ and WRITE operations.
qdr_w_n	Output	This signal represents the WRITE command.
qdr_r_n	Output	This signal represents the READ command.
qdr_cq	Input	This read data clock transmitted by the QDRII SRAM is edge-aligned with the read data.
k, k_n	Output	Differential write data clocks.
c, c_n	Output	Input clock for output data.
qdr_dll_off_n	Output	The DLL is disabled when this signal is Low.

Write Interface

Figure 4-13 illustrates the user interface block diagram for write operations.

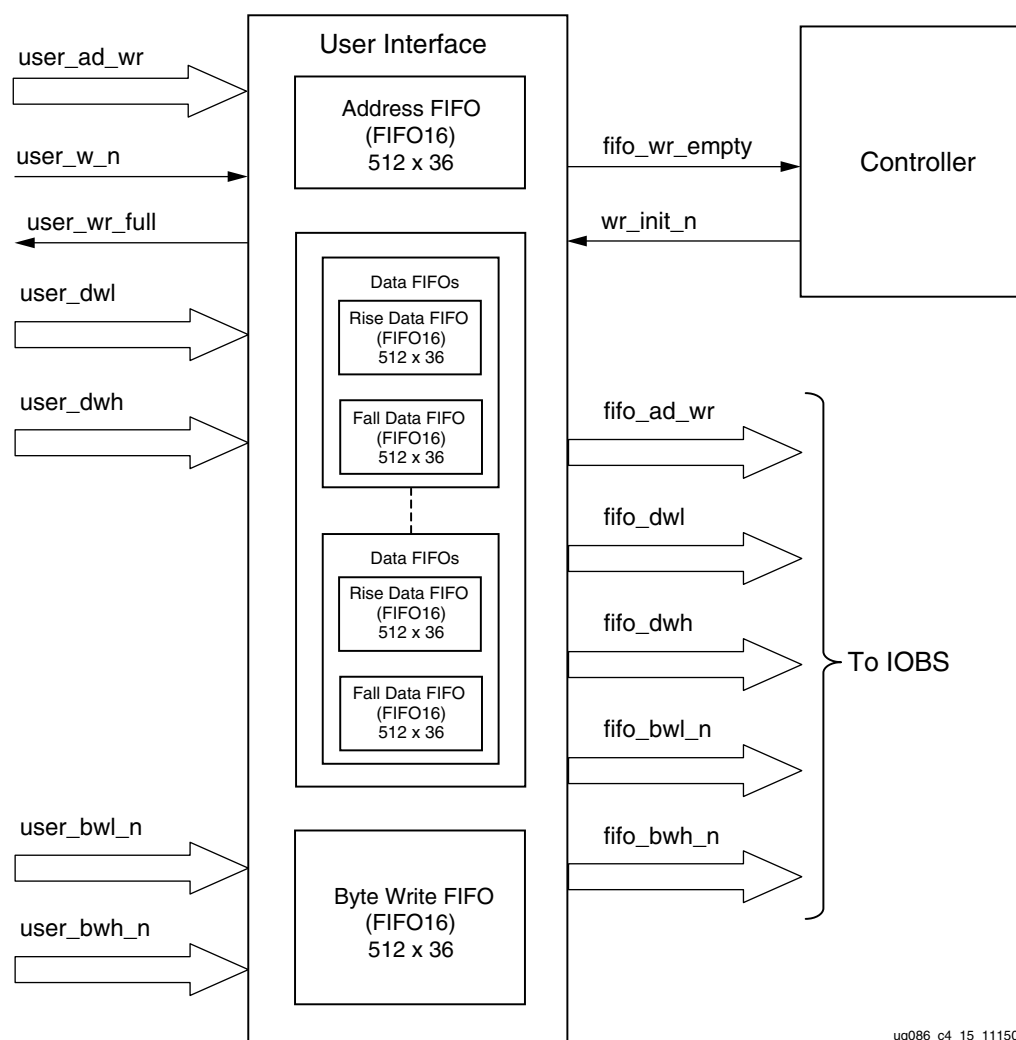


Figure 4-13: Write User Interface Block Diagram

The following steps describe the architecture of Address and Write Data FIFOs and how to perform a write burst operation to QDRII memory from user interface.

1. The user interface consists of an Address FIFO, Data FIFOs and a byte write FIFO. These FIFOs are built out of Virtex-4 FPGA FIFO16 primitives of configuration 512x 36.
2. The Address FIFO stores the QDRII memory address where the data is to be written from the user interface. A single instantiation of a FIFO16 constitutes the Address FIFO.
3. Two separate sets of Data FIFOs store the rising-edge and falling-edge data to be written to QDRII memory from the user interface. For 9-bit, 18-bit, and 36-bit data widths, two FIFO16s are required for storing rising-edge and falling-edge data. For a 72-bit data width, two FIFO16s are required for storing rising-edge data and two FIFO16s for storing falling-edge data. MIG instantiates the required number of FIFOs depending on the memory data width selected. For 9-bit and 18-bit configurations, the controller pads the extra bits of the Data FIFO with 0s.

4. The Byte Write FIFO stores the Byte Write signals to QDRII memory from the user interface. Extra bits are padded with zeros.
5. The user can initiate a write command to memory by writing to the Address FIFO, Data FIFOs, and Byte Write FIFOs when FIFO Full flags are deasserted and after the calibration done signal `dly_cal_done` is asserted. Users should not access any of these FIFOs until `dly_cal_done` is asserted. The `dly_cal_done` signal assures that the clocks are stable, the reset process is completed, and the controller is ready to accept commands. Status signal `user_wr_full` is asserted when the Address FIFO, Data FIFOs, or Byte Write FIFOs are full.
6. When `user_w_n` is asserted, `user_ad_wr` is stored in the Address FIFO, `user_dwl` and `user_dwh` are stored in the Data FIFO, and `user_bwl` and `user_bwh` are stored in the Byte Write FIFOs. A common write-enable signal is used to store the data into all three FIFOs.
7. The controller reads the Address, Data, and Byte Write FIFOs when they are not empty by issuing the `wr_init_n` signal. A QDRII memory write command is generated from the `wr_init_n` signal by properly timing it.

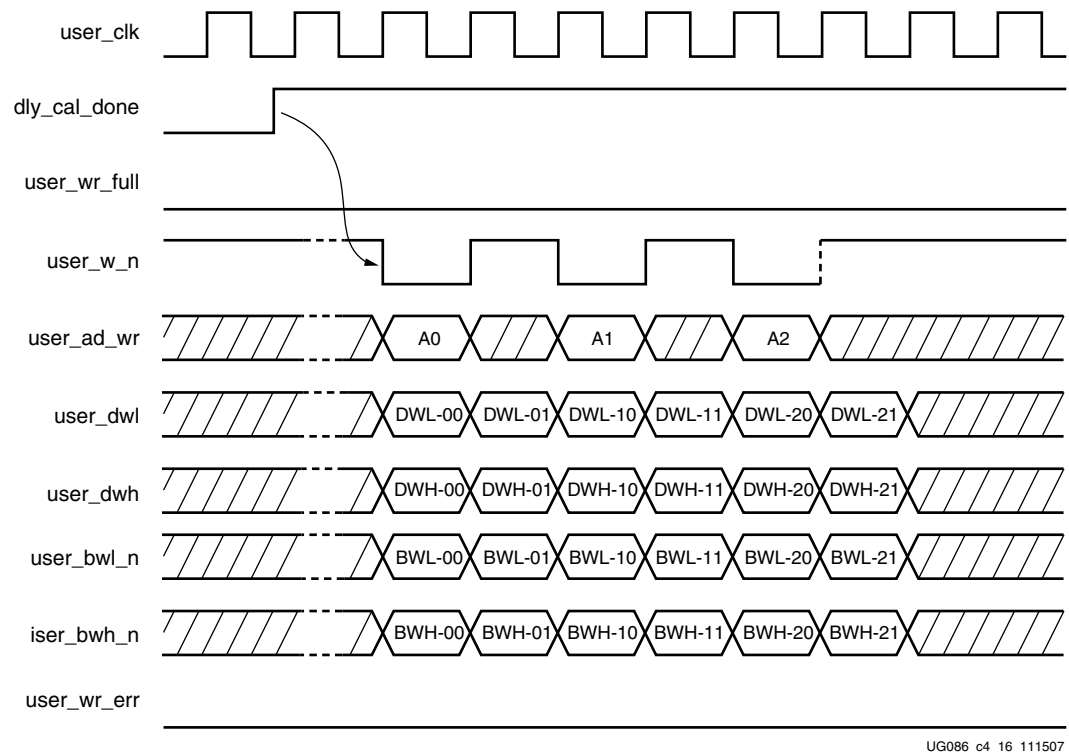
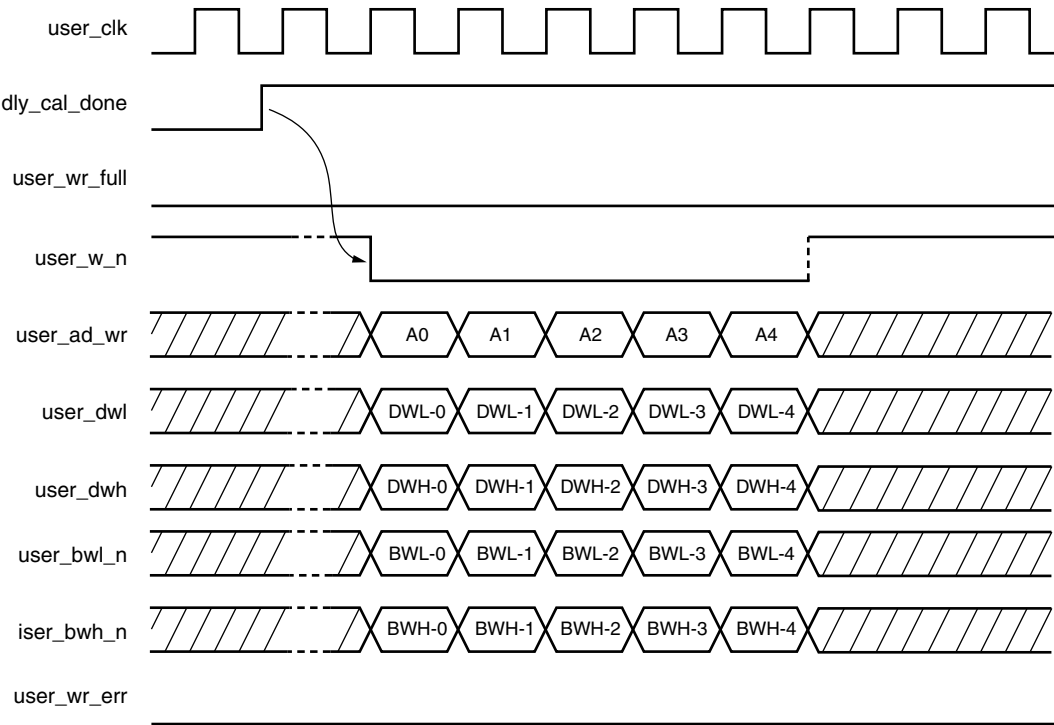


Figure 4-14: Write User Interface Timing Diagram for BL = 4

8. Figure 4-14 shows the timing diagram for a write command of BL = 4. The address must be asserted for one clock cycle as shown. For burst lengths of four, each write to the Address FIFO must have two writes to the Data FIFO consisting of two rising edge data and two falling edge data.
9. Figure 4-15 shows the timing diagram for a write command of BL = 2. For a burst length of two, each write to the Address FIFO is coupled to one write to the Data FIFO, consisting of one rising edge data and one falling edge data. For BL = 2, commands can be given in every clock.

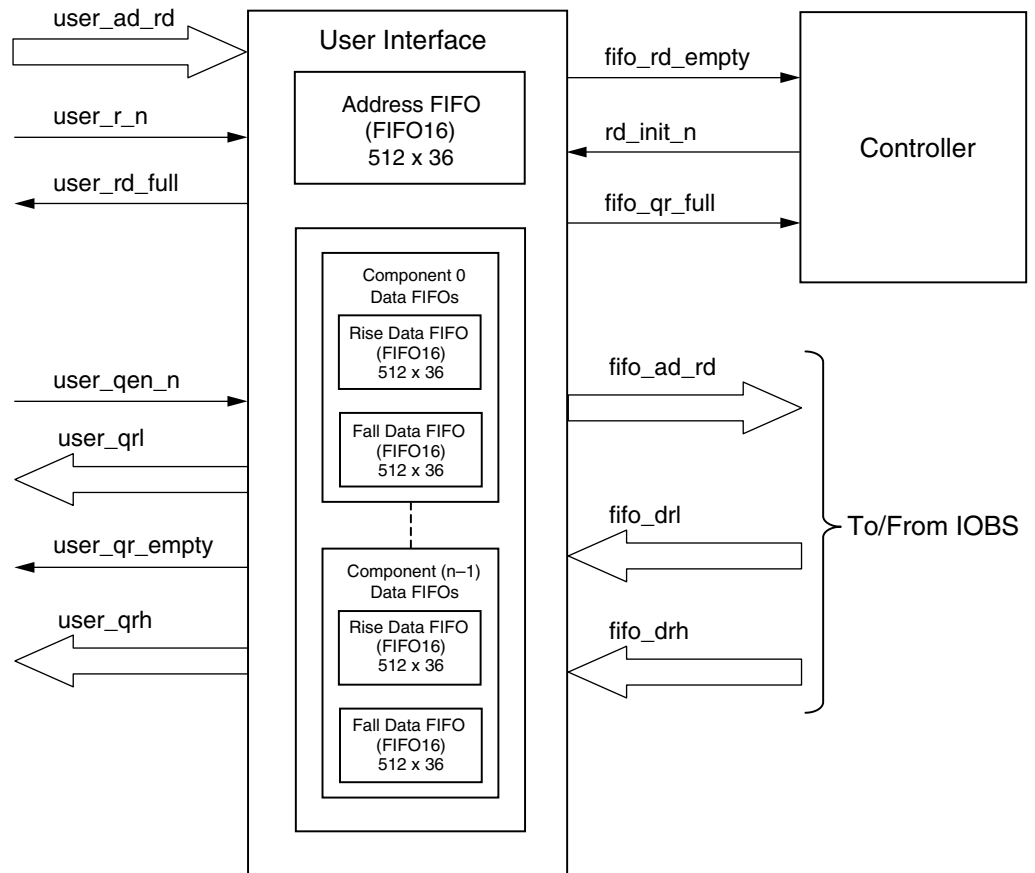


UG086_c4_17_010108

Figure 4-15: Write User Interface Timing Diagram for BL = 2

Read Interface

Figure 4-16 shows a block diagram for the read interface.



ug086_c4_18_111507

Figure 4-16: Read User Interface Block Diagram

The following steps describe the architecture of the Read Data FIFOs and show how to perform a QDRII SRAM burst read operation from the user interface.

1. The read user interface consists of an Address FIFO and a Read Data FIFO. The Address FIFO and Read Data FIFO are built from Virtex-4 FPGA FIFO16s of configuration 512 x 36.
2. The size of the Address FIFO is always of 512 x 16.
3. The number of Read Data FIFOs required depends on the number of QDRII components being used. Using 9-bit components for 36-bit data width, a total of eight FIFOs are required, four for rising-edge data and four for falling-edge data. Although each FIFO can accommodate 36-bit data, the requirement of having one FIFO per component arises from CQ pattern calibration, where an internal pattern calibration is done per CQ. The controller generates the Read Data FIFO write-enable signal for each FIFO separately depending on the CQ pattern calibration.
4. To initiate a QDRII read command, the user must write the Address FIFO when the FIFO full flag `user_rd_full` is deasserted and the calibration done signal `dly_cal_done` is asserted. Writing to the Address FIFO indicates to the controller that it is a Read command. The `dly_cal_done` signal assures that the controller clocks are stable, the internal reset process is completed, and the controller is ready to accept commands.

5. The user must issue an Address FIFO write-enable signal `user_r_n` along with the read address `user_ad_rd` to write the read address to the Address FIFO.
6. The controller reads the Address FIFO when status signal `fifo_rd_empty` is deasserted and generates the appropriate control signals to QDRII memory required for a read command.
7. Prior to the actual read and write commands, the design calibrates the latency (number of clock cycles) from when the read command is issued to when the data is received. Using this precalibrated delay information, the controller generates the write-enable signals to the Read Data FIFOs. The delay calibration is done per QDRII component.
8. The Low state of `user_qr_empty` indicates read data is available. Asserting `user_qen_n` reads rising-edge data and falling-edge data simultaneously on every rising edge of the clock.
9. Figure 4-17 and Figure 4-18 show the user interface timing diagrams for BL = 4 and BL = 2.
10. After the address is loaded into the Address FIFO, it can take 18 clock cycles (worst case) for the controller to write the Data FIFOs.

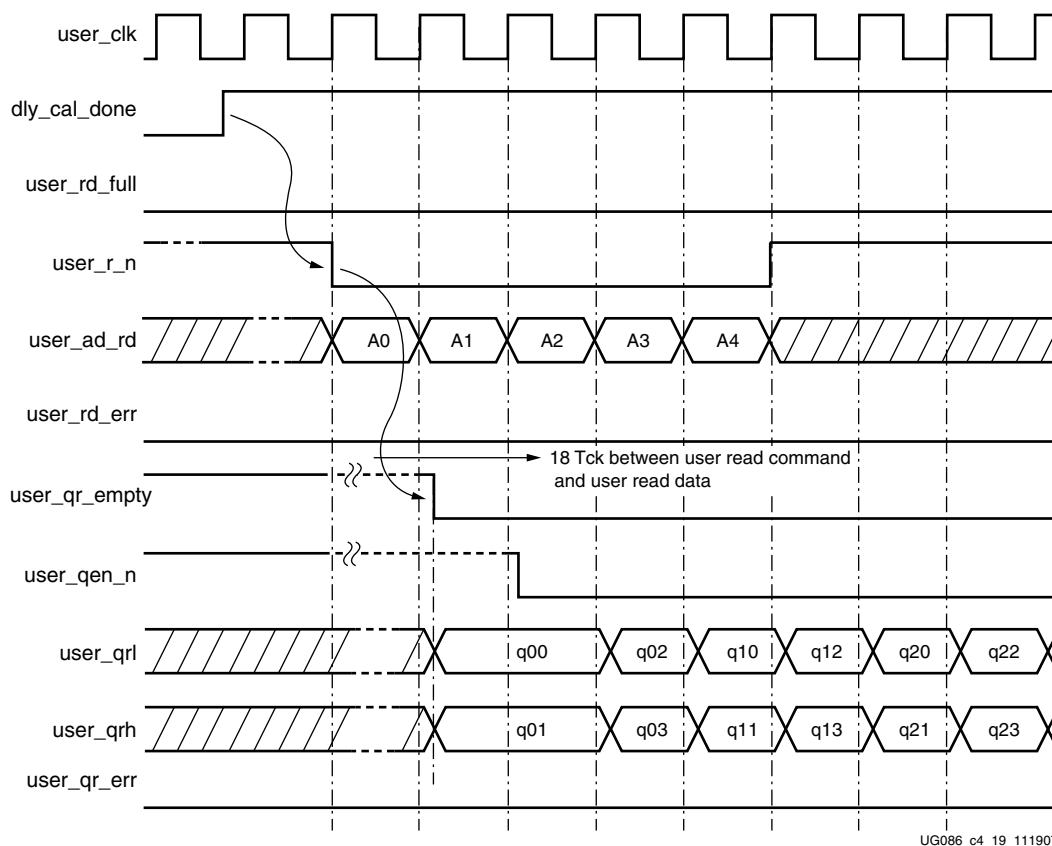


Figure 4-17: Read User Interface Timing Diagram for BL = 4

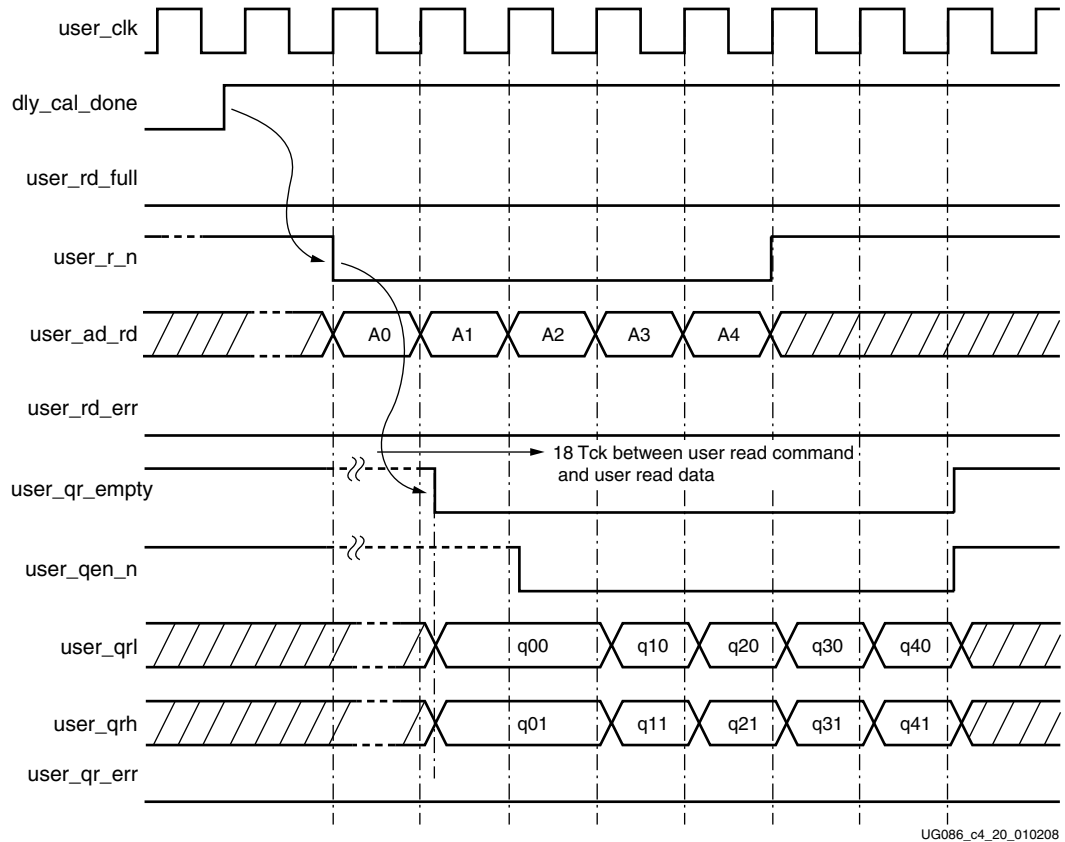


Figure 4-18: Read User Interface Timing Diagram for BL = 2

Table 4-7 shows the maximum read latency of the controller.

Table 4-7: Maximum Read Latency

Parameter	Number of Clocks	Description
User command to address FIFO empty flag	5 (2 + 3)	Two clocks for the two-stage pipeline before the FIFO input. An empty FIFO takes three clocks to deassert the empty status signal after the FIFO is written with the first data.
Command from controller state machine to QDR memory	3	One clock cycle to read the FIFO and two clocks for decoding and passing the command to QDR memory.
QDR command to FIFO input data	6	Two clocks for QDRII memory latency, two clocks for calibration delay, and two clocks for the input pipeline.
FIFO input to FIFO output	4	Four clocks to deassert the empty status signal in fall-through mode.
Total Latency	18	Total latency from read command issued to Address FIFO, to data input to user interface.

QDRII SRAM Signal Allocations

Table 4-8 shows the list of signals for a QDRII SRAM design allocated in a group from bank selection checkboxes in MIG.

Table 4-8: QDRII Signal Allocations

Bank Selected	Signals Allocated in the Group
Address	Memory address and memory control
Data Write	Memory write data and memory byte write
Data Read	Memory read data, memory CQ, and K and C clocks
System Control	System reset from the user interface and status signals
System Clock	System clocks from the user interface

When the Address box is checked in a bank, the address, qdr_w_n, qdr_r_n, and qdr_dll_off_n bits are assigned to that particular bank.

When the Data Write box is checked in a bank, the memory data write and memory byte write are assigned to that particular bank.

When the Data Read box is checked in a bank, the memory data read, memory read clocks, memory write clocks, and memory input clock for the output data are assigned to that particular bank.

When the System Control box is checked in a bank, the sys_rst_n, compare_error, and dly_cal_done bits are assigned to that particular bank.

When the System Clock box is checked in a bank, the refclk_p, refclk_n, dly_clk_200_p, and dly_clk_200_n bits are assigned to that particular bank.

For special cases, such as without a testbench and without a DCM, the corresponding input and output ports are not assigned to any FPGA pins in the design UCF because the user can connect these ports to the FPGA pins or can connect to some logic internal to the same FPGA.

Note: Timing has been verified for most of the MIG generated configurations. For the best timing results, adjacent banks in the same column of the FPGA should be used. Banks that are separated by unbonded banks should be avoided because these can cause timing violations.

Supported Devices

The design generated out of MIG is independent of the memory package, hence the package part of the memory component is replaced with X, where X indicates a *don't care* condition. Table 4-9 shows the list of components supported by MIG.

Table 4-9: Supported Devices for QDRII SRAM

Virtex-4 FPGAs (Verilog and VHDL)		
Components	Make	Configuration
CY7C1314BV18-167BZXC	Cypress	x36
CY7C1315BV18-250BZC	Cypress	x36
CY7C1426AV18-250BZC	Cypress	x9

Table 4-9: Supported Devices for QDRII SRAM (Cont'd)

Virtex-4 FPGAs (Verilog and VHDL)		
Components	Make	Configuration
CY7C1526V18-250BZC	Cypress	x9
CY7C1911BV18-250BZC	Cypress	x9
CY7C1515V18-250BZC	Cypress	x36
K7R160982B-FC25	Samsung	x9
K7R161882B-FC25	Samsung	x18
K7R161884B-FC25	Samsung	x18
K7R163682B-FC25	Samsung	x36
K7R163684B-FC25	Samsung	x36
K7R320982C-FC20	Samsung	x9
K7R320982M-FC20	Samsung	x9
K7R321882C-FC20	Samsung	x18
K7R321882M-FC20	Samsung	x18
K7R321884C-FC25	Samsung	x18
K7R321884M-FC25	Samsung	x18
K7R323682C-FC20	Samsung	x36
K7R323682M-FC20	Samsung	x36
K7R323684C-FC25	Samsung	x36
K7R323684M-FC25	Samsung	x36
K7R640982M-FC25	Samsung	x9
K7R641882M-FC25	Samsung	x18
K7R641884M-FC25	Samsung	x18
K7R643682M-FC25	Samsung	x36
K7R643684M-FC30	Samsung	x36

Simulating the QDRII SRAM Design

After generating the design, MIG creates a `sim` folder in the specified path. This folder contains simulation files for a particular design. The `sim` folder contains an external testbench and a `.do` file to simulate the generated design. To learn more details about the files in the `sim` folder and to simulate the design, refer to “[Simulation Guide](#),” page 499.

Hardware Tested Configurations

The frequencies shown in [Table 4-10](#) were achieved on the Virtex-4 FPGA ML461 Memory Interfaces Development Board under nominal conditions. This frequency should not be used to determine the maximum design frequency. The maximum design frequency supported in the MIG wizard is based on a combination of the TRCE results for fabric timing on multiple device/package combinations and I/O timing analysis using FPGA and memory timing parameters for a 72-bit wide interface.

Table 4-10: Hardware Tested Configurations

Synthesis Tools	XST and Synplicity
HDL	Verilog and VHDL
FPGA Device	XC4VLX25-FF668-11
Memory Component	K7R163684B-FC25
Burst Length	4
Data Widths	36, 72
36-bit Frequency Range	110 to 350 MHz
72-bit Frequency Range	110 to 320 MHz

Implementing DDRII SRAM Controllers

This chapter describes how to implement DDRII SRAM interfaces for Virtex®-4 FPGAs generated by MIG.

Feature Summary

This section summarizes the supported and unsupported features of the DDRII SRAM controller design.

Supported Features

The DDRII SRAM controller design supports:

- A maximum frequency of 250 MHz
- Data widths of 9, 18, 36, and 72 bits
- Burst lengths of two and four
- Implementation using different Virtex-4 devices
- Operation with any 9-bit, 18-bit, and 36-bit memory component
- Verilog and VHDL
- With and without a testbench
- With and without a DCM

Design Frequency Range

Table 5-1: Design Frequency Range in MHz

Memory	FPGA Speed Grade					
	-10		-11		-12	
	Min	Max	Min	Max	Min	Max
Component	120	200	120	240	120	250

Unsupported Features

The DDRII SRAM controller design does not support:

- DDR SIO memory

Architecture

Figure 5-1 shows a top-level block diagram of the DDRII SRAM controller interface. One side of the DDRII SRAM controller connects to the user interface denoted as *Block Application*. The other side of the controller interfaces to DDRII memory. The memory interface data width is selectable.

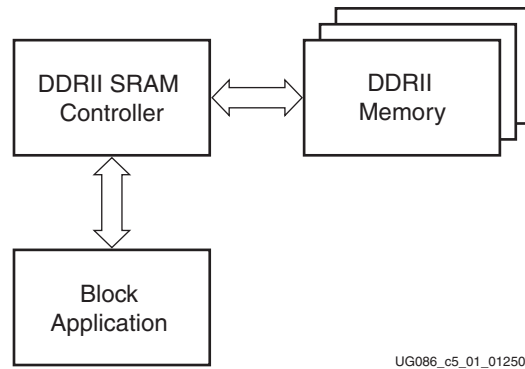


Figure 5-1: DDRII SRAM Controller Interface

Data is double-pumped to DDRII memory on both the positive and the negative edges of the clock. The HSTL_18 Class II I/O standard is used for data, and the HSTL_18 Class I I/O standard is used for address, control, and memory clock signals.

DDRII memory interfaces are source-synchronous and double data rate like DDR SDRAM interfaces.

Interface Model

The Memory interface is layered to simplify the design and make the design modular. Figure 5-2 shows the layered memory interface used in the DDRII SRAM controller. The three layers are the application layer, the implementation layer, and the physical layer.

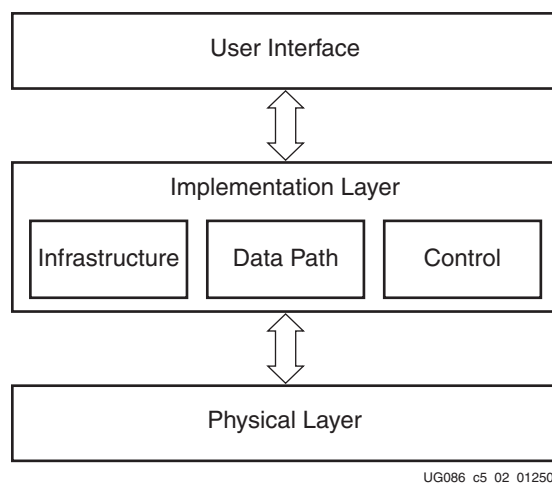


Figure 5-2: Interface Layering Model

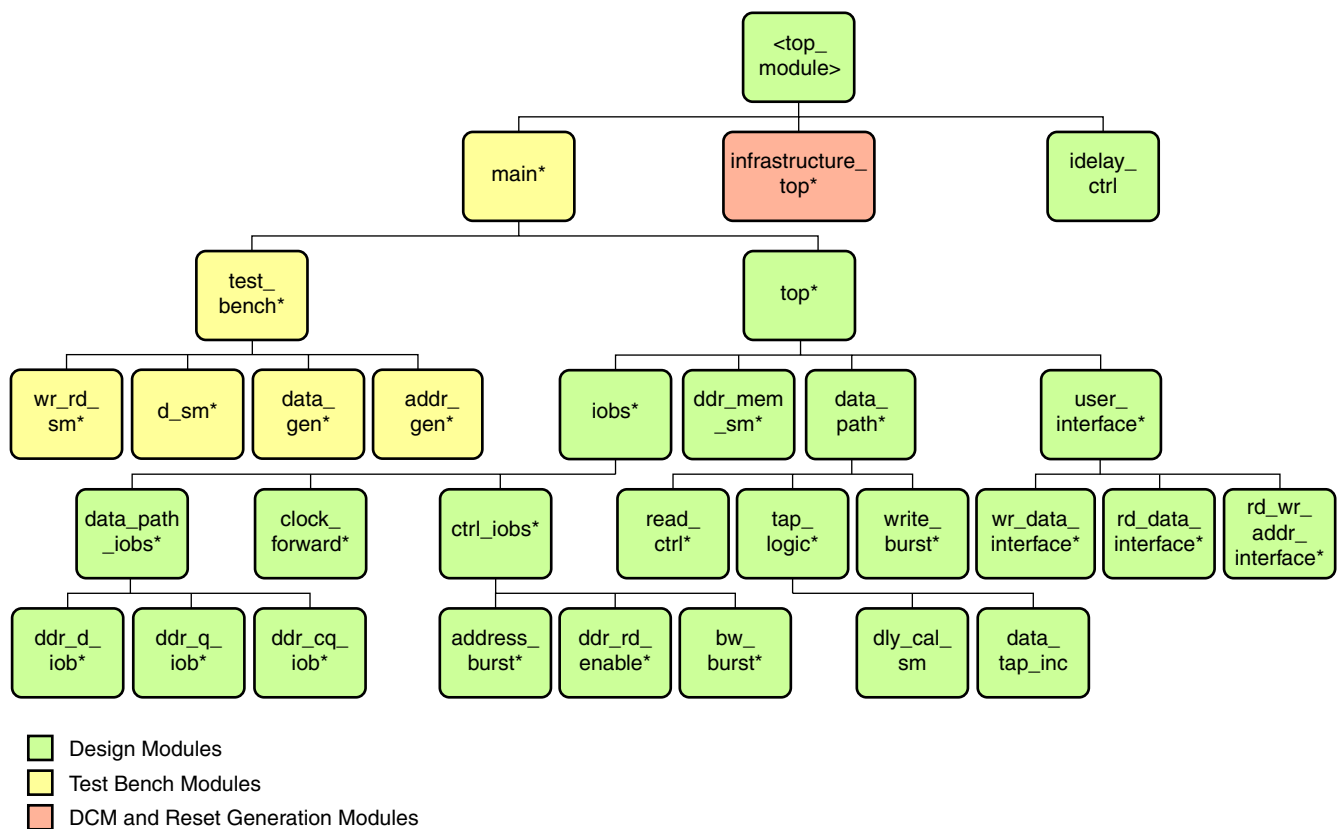
The application layer comprises the user interface, which initiates memory writes and reads by writing data and memory addresses to the User Interface FIFOs. The implementation layer comprises the infrastructure, datapath, and control logic.

- The infrastructure logic consists of the DCM and reset logic generation circuitry.
- The datapath logic consists of the calibration logic by which the data from the memory component is captured using the FPGA clock.
- The control logic determines the type of data transfer, that is, read/write with the memory component, depending on the User Interface FIFO's status signals.

The physical layer comprises the I/O elements of the FPGA. The controller communicates with the memory component using this layer. I/O elements (such as IDDRs, ODDRs, IDELAY, and OFLOPs) are associated with this layer.

Hierarchy

Figure 5-3 shows the hierarchical structure of the DDRII SRAM design generated by MIG with a testbench and a DCM.



UG086_c5_03_112907

Figure 5-3: **DDRII SRAM Controller Hierarchy**

The modules are classified as follows:

- Design modules
- Testbench modules
- Clocks and reset generation modules

There is a parameter file generated with the design that has all the user input and design parameters selected from MIG.

MIG can generate DDRII SRAM designs in four different ways:

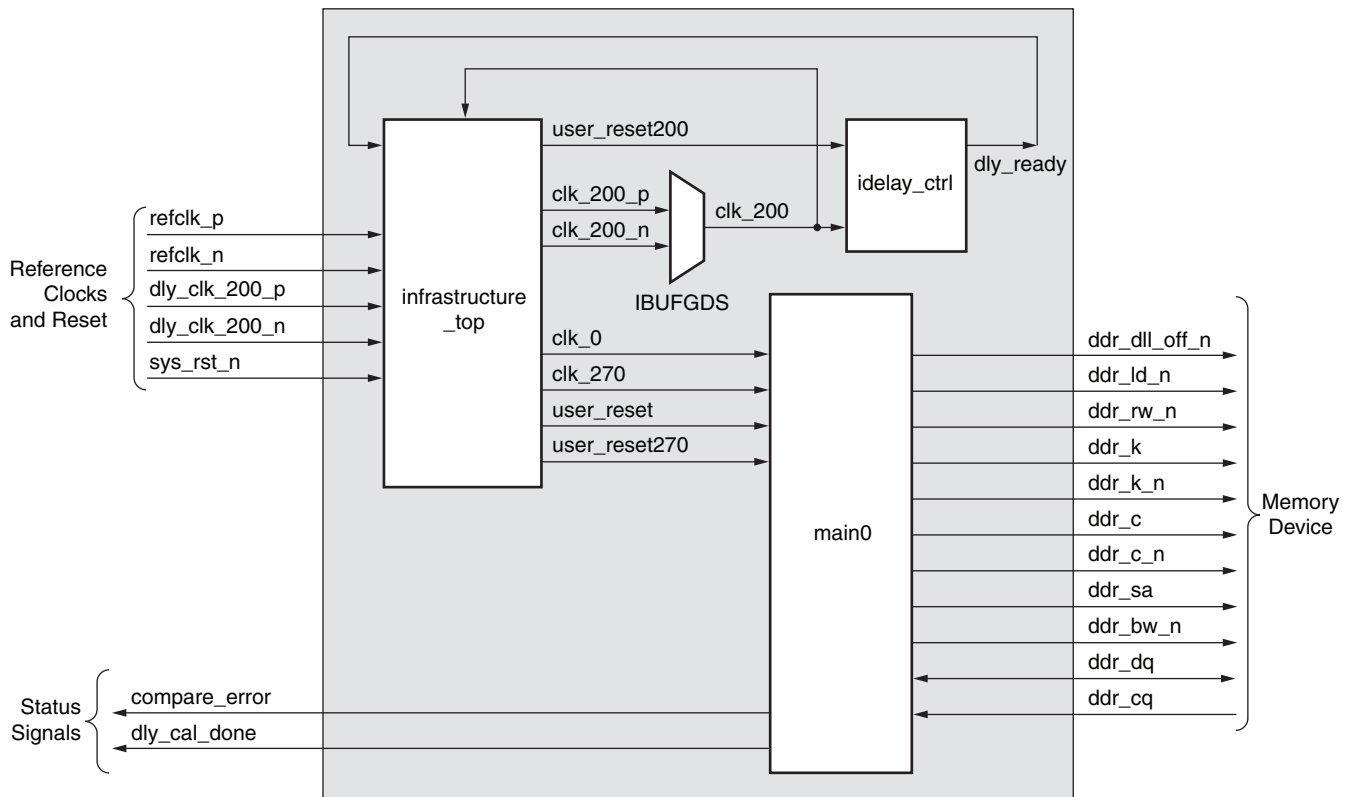
- With a testbench and a DCM
- Without a testbench and with a DCM
- With a testbench and without a DCM
- Without a testbench and without a DCM

MIG outputs both an `example_design` and a `user_design`. The MIG-generated `example_design` includes the entire memory controller design along with a synthesized testbench (example user application). This testbench generates sample writes and reads and then uses comparison logic to verify that the data patterns written are the same as those received. This `example_design` can be used to test functionality both in simulation and in hardware. The `user_design` includes the memory controller design only. This design allows users to connect the MIG memory controller design to a user developed testbench (user application). Refer to [Table 5-5](#) for user interface signals, [“Write Interface,” page 243](#) and [“Read Interface,” page 246](#) for timing restrictions on user interface signals, and [Figure 5-12, page 244](#) and [Figure 5-13, page 245](#) for write interface timing.

Design clocks and resets are generated in the `infrastructure_top` module. When **Use DCM** option is checked in MIG, a DCM primitive and the necessary clock buffers are instantiated in the `infrastructure_top` module. The inputs to this module are the differential design clock and a 200 MHz differential clock required for the `IDELAYCTRL` module. A user reset is also input to this module. Using the input clocks and reset signals, the system clocks and system resets used in the design are generated in this module.

When the **Use DCM** option is unchecked in MIG, the `infrastructure_top` module does not have the DCM and the corresponding clock buffer instantiations. Therefore, the system operates on the user-provided clocks. The system reset is generated in the `infrastructure_top` module using the `dcm_lock` signal and the ready signal of the `IDELAYCTRL` element. For more information on the clocking structure, refer to [“Clocking Scheme,” page 237](#).

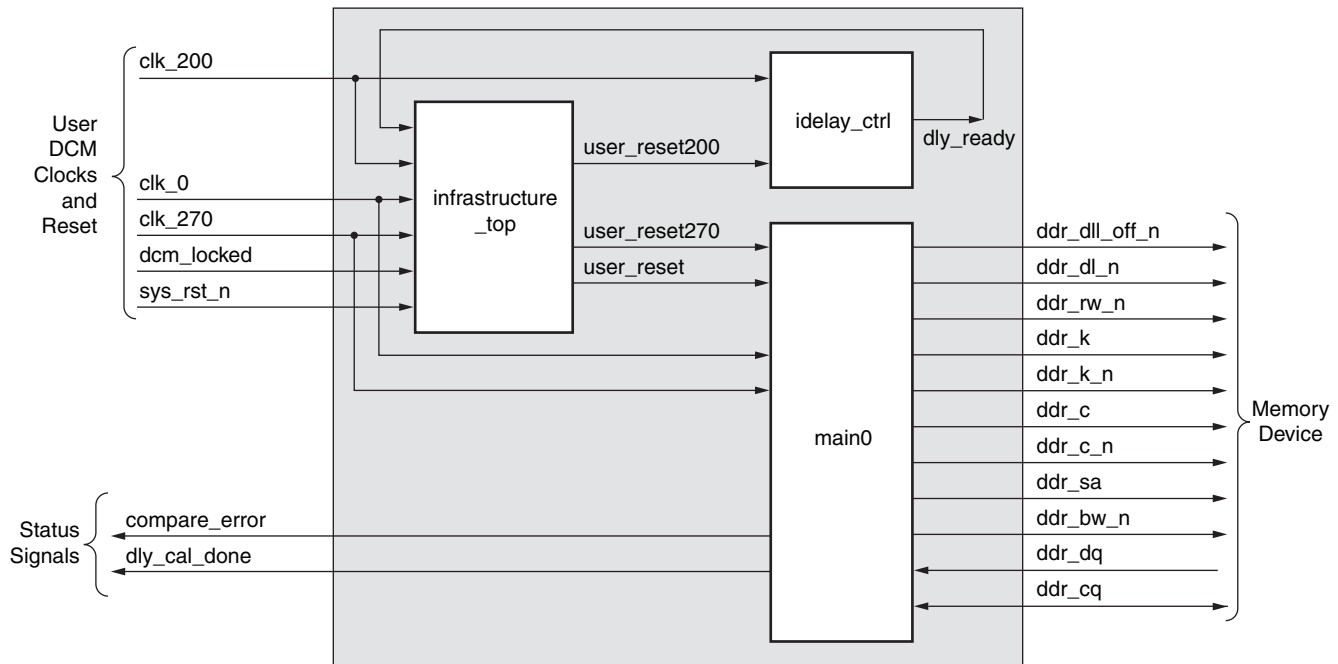
Figure 5-4 shows a top-level block diagram of a DDRII SRAM design with a DCM and a testbench. `refclk_p` and `refclk_n` are differential input reference clocks. The DCM is instantiated in the infrastructure module that generates the required design clocks. `dly_clk_200_p` and `dly_clk_200_n` are used for the `IDELAYCTRL` element. `sys_rst_n` is the system reset signal. All design resets are generated using the `dcm_locked` signal, the `sys_rst_n` signal, and the `dly_ready` signal of the `IDELAYCTRL` element. The `compare_error` output signal indicates whether the design passes or fails. The `dly_cal_done` signal indicates the completion of initialization and calibration of the design. Because the DCM is instantiated in the infrastructure module, it generates the required clocks and resets signals for the design.



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Figure 5-4: Top-Level Block Diagram of the DDRII SRAM Design with a DCM and a Testbench

Figure 5-5 shows a top-level block diagram of a DDRII SRAM design with a testbench but without a DCM. The user should provide all the clocks and the dcm_locked signal. These clocks should be single-ended. sys_rst_n is the system reset signal. All design resets are generated using the dcm_locked signal, the sys_rst_n signal, and the dly_ready signal of the IDELAYCTRL element. The user application must have a DCM primitive instantiated in the design, and all user clocks should be driven through BUFs. The compare_error output signal indicates whether the design passes or fails. The testbench module does writes and reads, and also compares the read data with the written data. The compare_error signal is driven High on data mismatches. The dly_cal_done signal indicates the completion of initialization and calibration of the design.



UG086_c5_05_071808

Figure 5-5: Top-Level Block Diagram of the DDRII SRAM Design without a DCM but with a Testbench

Figure 5-6, page 231 shows a top-level block diagram of a DDRII SRAM design with a DCM but without a testbench. refclk_p and refclk_n are differential input reference clocks. The DCM is instantiated in the infrastructure module that generates the required design clocks. dly_clk_200_p and dly_clk_200_n are used for the IDELAYCTRL element. sys_rst_n is the system reset signal. All design resets are generated using the dcm_locked signal, the sys_rst_n signal, and the dly_ready signal of the IDELAYCTRL element. The user has to drive the user application signals. The design provides the user_clk and user_rst signals to the user to synchronize the user application signals with the design. The signal user_clk is connected to clk0 clock signal in the controller. If the user clock domain is different from clk0/user_clk, the user should add FIFOs for all the inputs and output of the controller (user application signals), in order to synchronize them to user_clk clock. The dly_cal_done signal indicates the completion of initialization and calibration of the design.

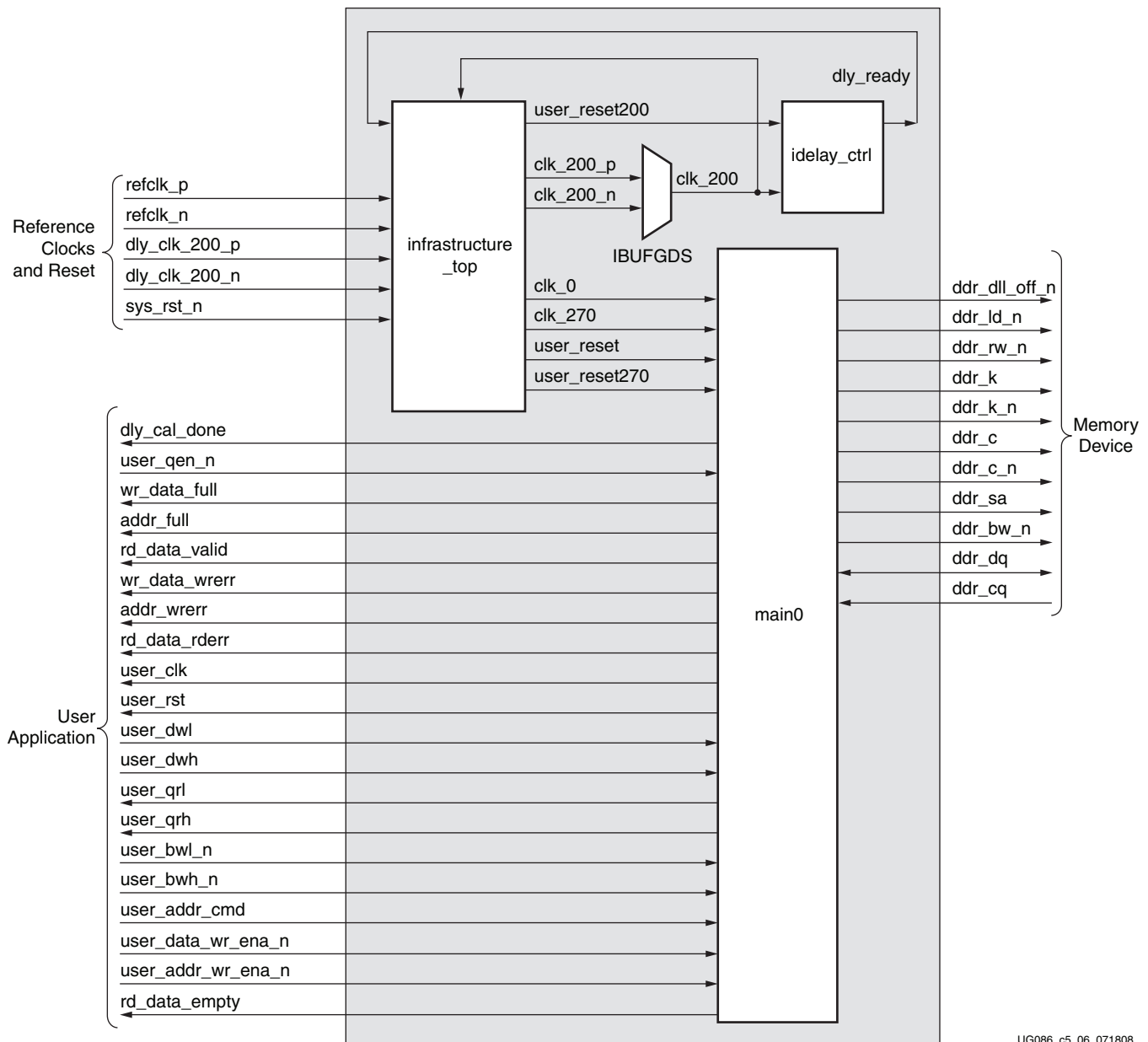
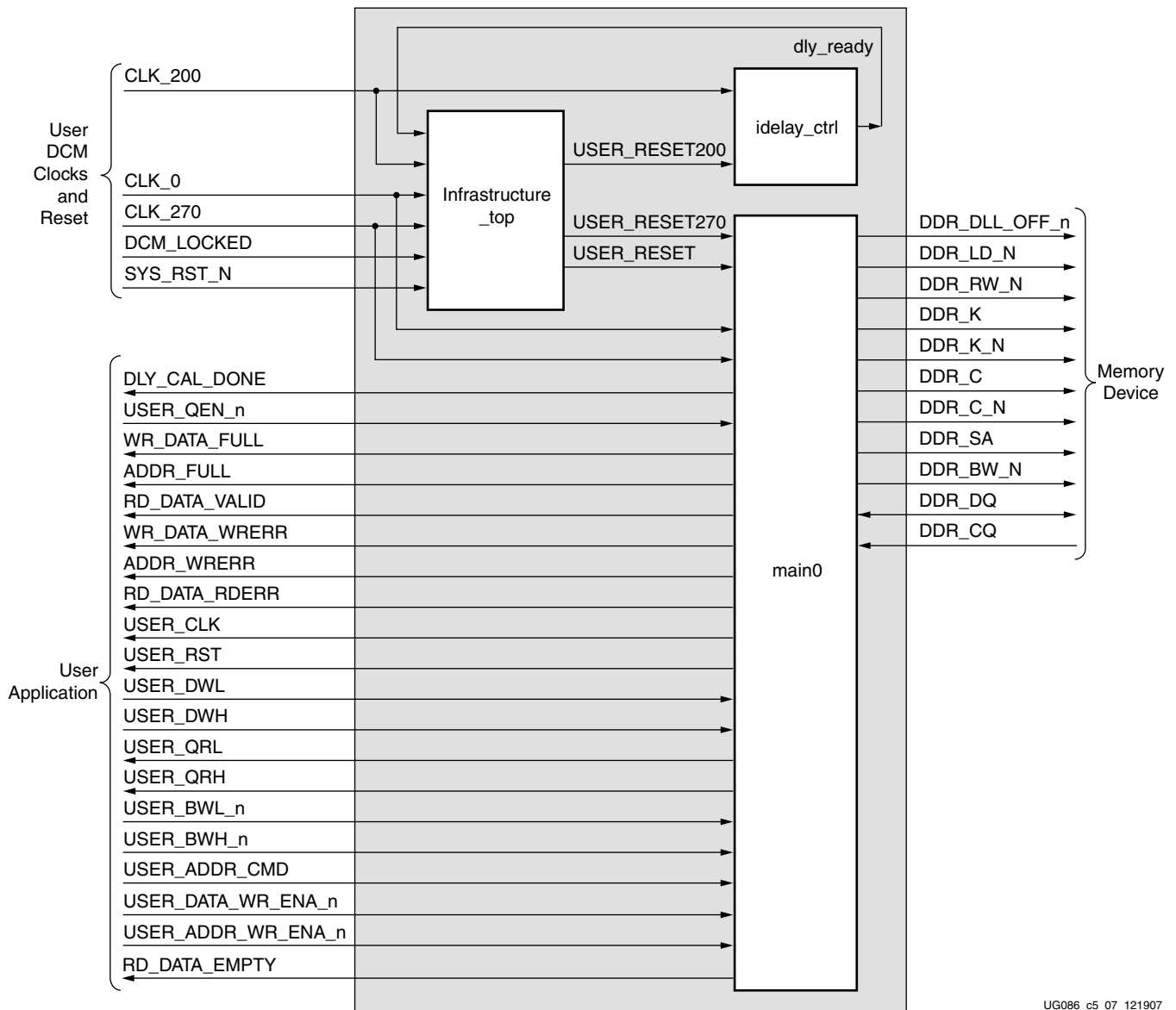


Figure 5-6: Top-Level Block Diagram of the DDRII SRAM Design with a DCM but without a Testbench

Figure 5-7 shows a top-level block diagram of a DDRII SRAM design without a DCM or a testbench. The user should provide all the clocks and the dcm_locked signal. These clocks should be single-ended. sys_rst_n is the system reset signal. All design resets are generated using the dcm_locked signal, the sys_rst_n signal, and the dly_ready signal of the IDELAYCTRL element. The user application must have a DCM primitive instantiated in the design, and all user clocks should be driven through BUFGs. The user has to drive the user application signals. The design provides the user_clk and user_rst signals to the user to synchronize the user application signals with the design. The signal user_clk is connected to clk0 clock signal in the controller. If the user clock domain is different from clk0/user_clk, the user should add FIFOs for all the inputs and output of the controller (user application signals), in order to synchronize them to user_clk clock.

The dly_cal_done signal indicates the completion of initialization and calibration of the design.



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Figure 5-7: Top-Level Block Diagram of the DDRII SRAM Design without a DCM or a Testbench

DDRII SRAM Controller Modules

Figure 5-8 shows a detailed block diagram of the DDRII SRAM controller. The four blocks shown are subblocks of the top module. The functionalities of these blocks are explained in the subsections following the figure.

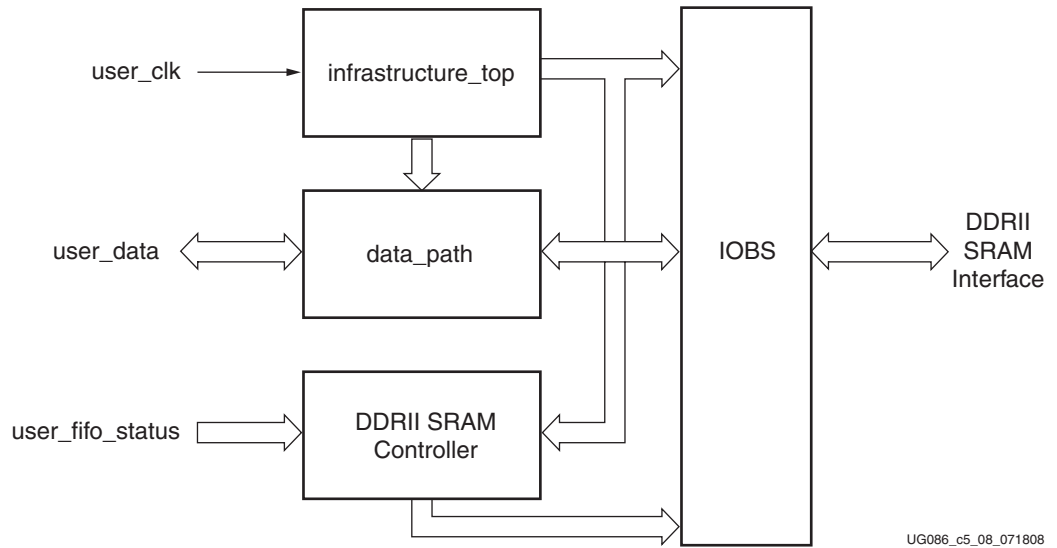


Figure 5-8: DDRII SRAM Controller Modules

Figure 5-9 shows the DDRII SRAM controller modules with a 36-bit interface.

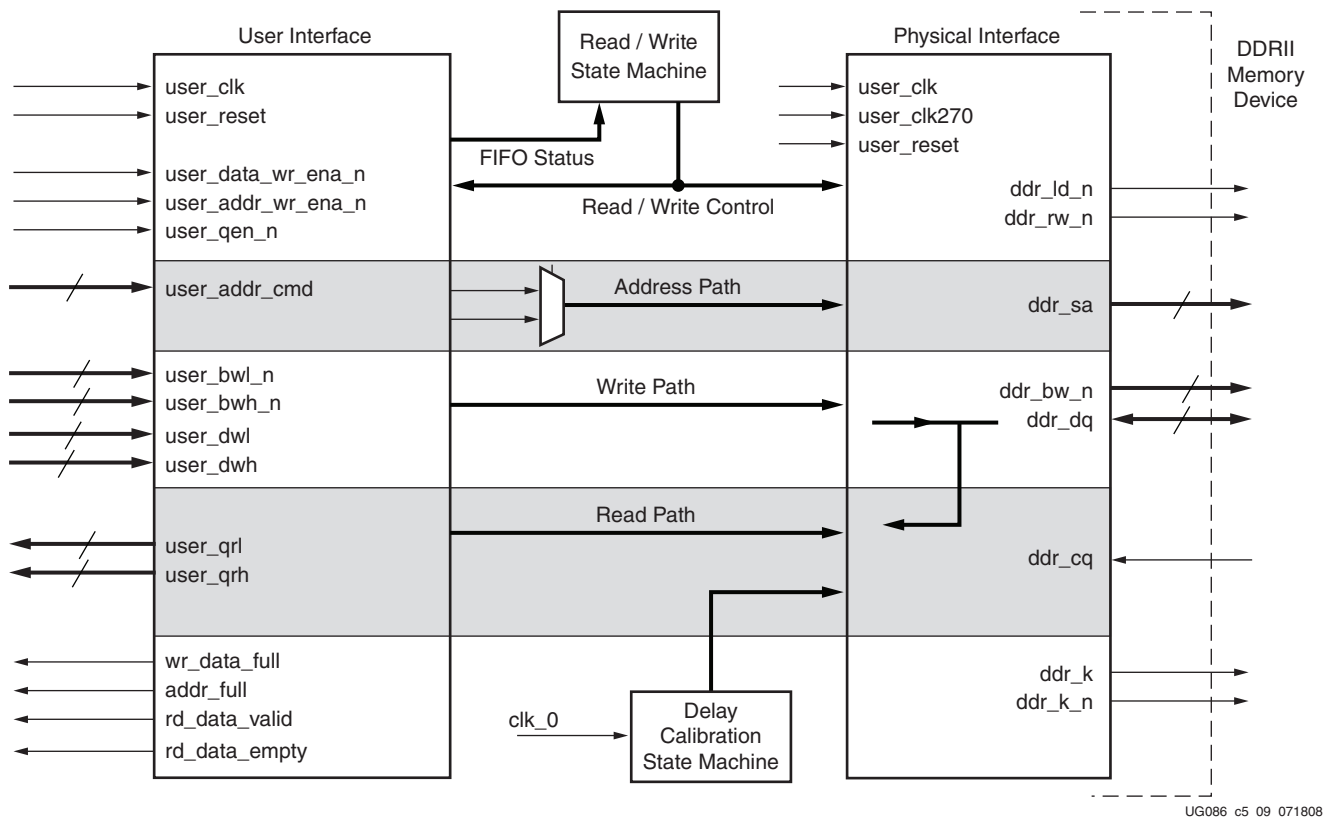


Figure 5-9: DDRII SRAM Controller Modules with Interface Signals

Controller

The DDRII SRAM controller initializes the memory, accepts and decodes the user commands, and generates the READ and WRITE commands. It also generates control signals for other modules. After power on it starts the calibration, after the calibration is completed it process the READ or WRITE commands.

Datapath

The Datapath module transmits and receives data to and from the memories. Its major functions are listed below:

- Asserts a write-enable signal for memories with burst lengths of two or four
- Asserts a read-enable signal to memory and a write-enable signal to the User Read Data FIFO
- Generates increment/decrement signals (tap count) for IDELAY elements in the IOBS
- Center-aligns the data window to the FPGA clock

Refer to XAPP703 [Ref 20] for techniques on data writes to memory and data captures from memory. For burst lengths of four and two, the write-enable signal is asserted one clock before the write data is driven on the memory bus. The data is driven on both edges of the clock. The address to memory is driven for one full clock cycle.

Memory read data is edge-aligned with the source-synchronous clock, CQ. The DDRII clock, CQ, to which read data is synchronized, is a free-running strobe. The free-running strobe from the memory CQ is captured using the FPGA clock. Thus the relation between the CQ strobe and FPGA clock is found, and the strobe CQ is center-aligned with the FPGA clock by delaying the CQ strobe in the IDELAY element. The same logic is applied to the read data window. The read data window is center-aligned with the same FPGA clock. This in turn means that the same amount of tap delays are applied on both the read data window and the strobe CQ through the IDELAY elements to center-align the read data and strobe CQ windows with respect to the FPGA clock. Center-aligning the read data window with respect to the FPGA clock completes the data capturing logic.

The delay calibration circuit generates the delay reset, delay select, and delay increment values for IDELAY elements used in delaying strobes and data read from memory. The strobe is center-aligned with the FPGA clock, which results in the data window falling to the center of the FPGA clock. Refer to XAPP703 [Ref 20] for details about the delay calibration.

Infrastructure

The infrastructure (infrastructure_top) module generates the FPGA clock and reset signals. When differential clocking is used, refclk_p, refclk_n, dly_clk_200_p, and dly_clk_200_n signals appear. When single-ended clocking is used, refclk and idly_clk_200 signals appear. In addition, clocks are available for design use and a 200 MHz clock is provided for the IDELAYCTRL primitive. Differential and single-ended clocks are passed through global clock buffers before connecting to a DCM. For differential clocking, the output of the refclk_p/refclk_n buffer is single-ended and is provided to the DCM input. Likewise, for single-ended clocking, refclk is passed through a buffer and its output is provided to the DCM input. The outputs of the DCM are 0° and 270° phase-shifted versions of the input clock. After the DCM is locked, the design is in the reset state for at least 25 clocks. The infrastructure module also generates all of the reset signals required for the design.

Idelay_ctrl

This module instantiates the IDELAYCTRL primitive of the Virtex-4 FPGA. The IDELAYCTRL primitive is used to continuously calibrate the individual delay elements in its region to reduce the effect of process, temperature, and voltage variations. A 200 MHz clock has to be fed to this primitive.

The MIG tool instantiates the required number of IDELAYCTRLs in the RTL and uses the LOC constraints in the UCF file to fix their locations. The number of IDELAYCTRLs is defined by the IDELAYCTRL_NUM parameter in the idelay_ctrl module. In the RTL, DLY_READY is generated by doing a logical AND of the RDY signals of every IDELAYCTRL block.

IDELAYCTRL LOC constraints should be checked in the following cases:

- The MIG design is used with other IP cores or user designs that also require the use of IDELAYCTRL and IDELAYs.
- Previous ISE® software releases 8.2.03i and 9.1i had an issue with IDELAYCTRL block replication or trimming. When using these revisions of the ISE software, the user must instantiate and constrain the location of each IDELAYCTRL individually.

See UG070 [Ref 7] for more information on the requirements of IDELAYCTRL placement.

IOBS

All the input and output signals of the DDRII SRAM controller are implemented in the IOBS module. All address and byte enable signals are registered in the IOBs and driven out.

The IDELAY elements for the read strobe and data read from memory are implemented in the IOBS. The IOBS also implements bidirectional buffers for write and read data. The IOBS registers the output data (ODDR) before driving it out and also registers the input data (IDDR).

Test Bench

The MIG tool generates two RTL folders, example_design and user_design. The example_design folder includes the synthesizable test bench, while user_design does not include the test bench modules. The MIG test bench performs one write command followed by one read command in an alternating manner. The number of words in a write command depends on the burst length. For a burst length of 4, the test bench writes a total of 4 data words for a single write command (2 rise data words and 2 fall data words). For a burst length of 2, the test bench writes a total of 2 data words. On every write command,

the data pattern is incremented by one, and this is repeated with each subsequent write command. The initial data pattern for the first write command is 000. The test bench writes the 000, 001, 002, 003 data pattern in a sequence in which 000 and 002 are rise data words and 001 and 003 are fall data words for a 9-bit design. The falling edge data is always rising edge data plus one. For a burst length of 2, the data sequence for the first write command is 000, 001. The data sequence for the second write command is 002, 003. The pattern is then incremented for the next write command. For data widths greater than 9, the same data pattern is concatenated for the other bits. For a 36-bit design and burst length of 4, the data pattern for the first write command is 000000000, 008040201, 010080402, 0180C0603.

Address generation logic generates the address in an incremental pattern for each write command. The same address location is repeated for the next read command. In Samsung components, the burst address increments are done by the memory, so the address is generated by the test bench in a linear incremental pattern. In Cypress parts, the MIG test bench increments the address for burst operation. After the address reaches the maximum value, it rolls back to the initial address, i.e., 00000.

During reads, comparison logic compares the read pattern with the pattern written, i.e., the 000, 001, 002, 003 pattern. For example, for a 9-bit design of burst length 4, the data written for a single write command is 000, 001, 002, and 003. During reads, the read pattern is compared with the 000, 001, 002, 003 pattern. Based on a comparison of the data, a status signal error is generated. If the data read back is the same as the data written, the error signal is 0, otherwise it is 1.

DDRII SRAM Initialization and Calibration

DDRII SRAM is initialized through a specified sequence. Following the initialization, the relationship between the read data and the FPGA clock is calculated using the TAP logic. After the DCM clocks are stable, the controller waits for a specified amount of time before asserting the DDR_DLL_OFF_n signal to the memory. This signal can also be pulled up to a High on the memory device without being driven from the FPGA.

The memory strobe CQ is a free-running clock from the memory component. Because the read data and the memory strobe CQ are edge-aligned, the strobe is passed through the IDELAY elements of the Virtex-4 device and the taps are adjusted to center-align the strobe pulse with respect to the FPGA clock. The same number of taps are applied to the data window's IDELAY element to center-align the data window with respect to the FPGA clock. XAPP701 [Ref 18] provides more information about the calibration architecture.

Calibration is done in two stages:

1. In the first stage of calibration, the read strobe CQ is center-aligned with respect to the FPGA clock. CQ is a free-running clock from DDRII SRAM. The read data window is edge-aligned with the read strobe CQ. The first and second edges of the CQ strobe are detected using the FPGA clock to determine the center of the CQ window.

Once the CQ window is center-aligned with the FPGA clock, the same amount of delay (tap counts) is applied to the read data window through the IDELAY element, so that the read data window is center-aligned with the FPGA clock.

Port `cq_q_cal_done` in the `data_path` module indicates the status of the first stage calibration. When `cq_q_cal_done` is asserted High, it indicates the completion of first stage calibration. After the first stage calibration is complete, the second stage calibration starts.

2. In the second stage of calibration, the write enable signal for the Read Data FIFO is determined by delaying the controller-issued read command. This delay is calibrated based on the delay between the read command and the corresponding read data at the Read Data FIFO. For this delay calibration, the controller writes a known fixed pattern of data into a memory location and reads back from the same location. This read data is compared against the known fixed pattern. The delay between the read command and the correct pattern read data comparison is the delay calibration.

The `final_dly_cal_done` port in the `data_path` module indicates the status of the second stage calibration. When `final_dly_cal_done` is asserted High, it indicates the completion of second stage calibration, which implies the completion of the whole initialization and calibration process. After the initialization and calibration is done (i.e., the `dly_cal_done` signal in `design_top` is asserted High), the controller can start issuing user commands to the memory.

In the second stage calibration, when the pattern read data does not match with the pattern write data, the controller does not issue any further pattern read commands and the controller gets stuck in the calibration state. The design must be restarted for the calibration to start from the beginning.

Clocking Scheme

Figure 5-10, page 238 shows the clocking scheme for this design. Global and local clock resources are used.

The global clock resources consist of a DCM, two BUFGs on DCM output clocks, and one BUFG for `clk_200`. The local clock resources consist of regional I/O clock networks (BUFIO). The global clock architecture is discussed in this section.

The MIG tool allows the user to customize the design such that the DCM is not included. In this case, `clk_0` and `clk_270` must be supplied by the user.

Global Clock Architecture

The user must supply two input clocks to the design:

- A system clock running at the target frequency for the memory
- A 200 MHz clock for the IDELAYCTRL blocks.

These clocks can be either single-ended or differential. User can select single-ended or differential clock input option from MIG GUI. Differential clocks are connected to the IBUFGDS and single-ended clock is connected to IBUFG.

The system clock from the output of the IBUFGDS or the IBUFG is connected to the DCM to generate the various clocks used by the memory interface logic.

The `clk_200` output of the IBUFGDS or the IBUFG is connected to the BUFG. The output of the BUFG is used for IDELAY IOB delay blocks for aligning read capture data.

The DCM generates three separate synchronous clocks for use in the design. This is shown in Table 5-2 and Figure 5-10, page 238. The clock structure is same for both example design

and user design. For designs with out DCM instantiation, DCM and the BUFGs should be instantiated at user end to generate the required clocks.

Table 5-2: DDRII Interface Design Clocks

Clock	Description	Logic Domain
clk_0	Skew compensated replica of the input system clock.	The clock for the controller and the user interface logic. The DDRII bus-related I/O flip-flops (e.g., memory clocks). This clock is used to register the data, address, and command signals, and the address and data enables for the user interface logic ⁽¹⁾ . This clock is also used to generate the read data and read data valid signals.
clk_270	270° phase-shifted version of clk_0	Used in the write data path section of physical layer. Clocks write path control logic, DDRII side of the Write Data FIFO, and output flip-flops for DQ and memory control and address signals. This clock is also used to generate FIFO status signals.

Notes:

1. See “DDRII SRAM Controller Interface Signals,” page 239 for timing requirements and restrictions on the user interface signals.

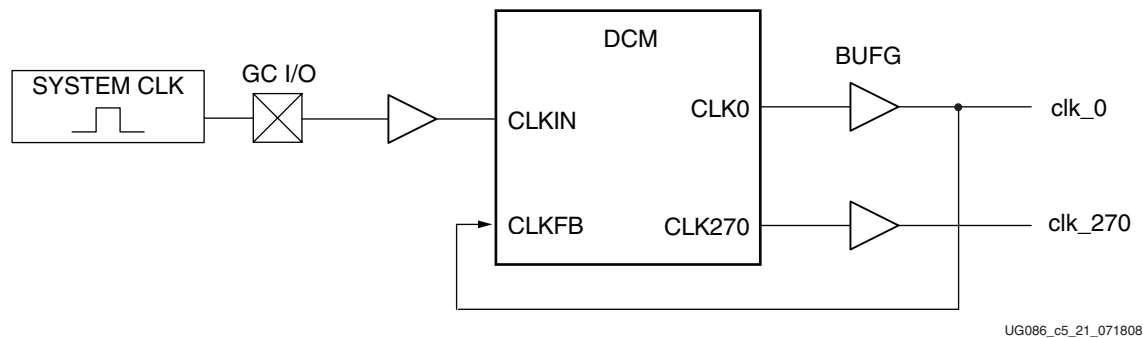


Figure 5-10: Clocking Scheme for DDRII Interface Logic

User Interface

The user interface consists of seven FIFOs. The User Write interface has four FIFOs: one FIFO is used for the memory address, two FIFOs contain positive-edge and negative-edge data for memory, and the remaining FIFO is used for Byte Writes. The DDRII SRAM controller checks the not empty status of these FIFOs and initiates a memory write. The user interface is single data rate (SDR). The controller handles the conversion from the SDR user interface to the DDR Memory interface and vice versa.

The User Read interface has three FIFOs, where one FIFO is used for the memory address and the remaining two FIFOs contain positive-edge and negative-edge data read from memory. The user writes to the User Read Address FIFO the memory address from which data is to be read. The DDRII SRAM controller checks the status of this FIFO and initiates

a memory read burst. The data read is stored in the User Read Data FIFOs. The user reads these FIFOs to access the data read from memory. The FIFOs are built using FIFO16 primitives in the rd_data_interface, rd_wr_addr_interface, and wr_data_interface modules. Each FIFO has a threshold attribute called ALMOST_FULL_OFFSET whose value is set to F, by default, in the RTL. This value can be changed as needed. For valid FIFO threshold offset values, refer to UG070 [Ref 7].

Refer to [Table 5-3](#) for how the user can access these FIFOs.

DDRII SRAM Controller Interface Signals

[Table 5-3](#) through [Table 5-4](#) describe the DDRII controller system interface signals. [Table 5-5](#) describes the DDRII SRAM user interface signals. [Table 5-6](#) describes the DDRII memory interface signals. In these tables, all signal directions are with respect to the DDRII memory controller.

Table 5-3: DDRII SRAM System Interface Signals (with a DCM)

Signal Name	Direction	Description
refclk_p, refclk_n	Input	Reference clock input made up of differential clock pairs. This clock pair goes to a differential input buffer. The differential buffer output goes to the DCM input. The DCM generates the required clocks for the design. This input system clock pair is present only when the DIFFERENTIAL clock option is selected in the MIG FPGA options page.
refclk	Input	Single-ended system clock input. This clock is an input to IBUFG. The IBUFG output is connected to the DCM clock input. The DCM generates the required clocks for the design. This input system clock is present only when the SINGLE_ENDED clocks option is selected in MIG FPGA options page. When DCM option is deselected, both differential or single-ended input system clocks are not present.
dly_clk_200_p, dly_clk_200_n	Input	200 MHz differential clock used in the IDELAY_CTRL logic. This input clock pair is present only when the DIFFERENTIAL clocks options is selected in the MIG FPGA options page.
idly_clk_200	Input	Single-ended 200 MHz IDELAYCTRL clock input. This clock is connected to an IBUFG. The IBUFG output is connected to input of BUFG. The output of this BUFG acts as IDELAYCTRL clock input. This input system clock is present only when the SINGLE_ENDED clocks option is selected in the MIG FPGA options page. When the DCM option is deselected, both differential and single-ended input system clocks are not present.
sys_rst_n	Input	Reset to the DDRII memory controller
compare_error	Output	This signal indicates the status of the comparison between the read data with the corresponding write data
dly_cal_done	Output	This signal is asserted when the design initialization and calibration is complete

Table 5-4: DDRII SRAM System Interface Signals (without a DCM)

Signal Name	Direction	Description
clk_0	Input	Input clock
clk_270	Input	Input clock with 270° phase difference
clk_200	Input	200 MHz clock for IDELAYCTRL primitives
dcm_locked	Input	This active-High signal indicates whether the user DCM is locked or not
sys_rst_n	Input	Reset to the DDRII memory controller
compare_error	Output	This signal indicates the status of the comparison between the read data with the corresponding write data
dly_cal_done	Output	This signal is asserted when the design initialization and calibration is complete

Table 5-5: DDRII SRAM User Interface Signals (without a Testbench)

Signal Name ⁽¹⁾	Direction	Description
wr_data_full	Output	This signal indicates the User Write FIFOs status. It is asserted when the User Write Data FIFOs are full. When this signal is asserted, any writes to the User Write Data FIFO are invalid, possibly leading to controller malfunction.
addr_full	Output	This signal indicates the User Read Write Address FIFO status. It is asserted when the User Read Write Address FIFO is full. When this signal is asserted, any writes to the User Read Write Address FIFO are ignored.
rd_data_valid	Output	This signal indicate to the user that data available at read data FIFOs.
wr_data_wrerr	Output	This signal is asserted when an error occurs while writing to the User Write Data FIFOs.
addr_wrerr	Output	This signal is asserted when an error occurs while writing to the User Read Write Address FIFO.
rd_data_rderr	Output	This signal is asserted when an error occurs while reading the User Read Data FIFO
dly_cal_done	Output	This signal is asserted to indicate that the calibration is done
user_clk ⁽²⁾	Output	All user interface signals are to be synchronized to this clock. The user_clk is sourced from the clk_0 in the controller.
user_rst	Output	This reset is active until the DCM is not locked
user_dwl [(data_width-1):0]	Input	Positive-edge data for memory writes. The data bus is valid when the WRITE command (DDR_LD_N=0 && DDR_RW_N=0) is asserted.

Table 5-5: DDRII SRAM User Interface Signals (without a Testbench) (Cont'd)

Signal Name ⁽¹⁾	Direction	Description
user_dwh [(data_width-1):0]	Input	Negative-edge data for memory writes. The data bus is valid when the WRITE command (DDR_LD_N=0 && DDR_RW_N=0) is asserted.
user_qrl [(data_width-1):0]	Output	Positive-edge data read from memory. This data is output when user_qen_n is asserted.
user_qrh [(data_width-1):0]	Output	Negative-edge data read from memory. This data is output when user_qen_n is asserted.
user_bwl_n [(bw_width-1):0]	Input	Byte enables for DDRII memory positive-edge write data. The byte enables are valid when the WRITE command (DDR_LD_N=0 && DDR_RW_N=0) is asserted.
user_bwh_n [(bw_width-1):0]	Input	Byte enables for DDRII memory negative-edge write data. The byte enables are valid when the WRITE command (DDR_LD_N=0 && DDR_RW_N=0) is asserted.
usr_addr_cmd[addr_width:0] ⁽³⁾	Input	DDRII memory address for read or write operation. This address is valid when USER_DATA_WR_ENA_n is asserted. An extra bit is driven by the user to represent the command.
user_qen_n	Input	This active-Low signal is the read enable for the User Read Data FIFOs. The DDRII memory controller captures the data read from memory and stores it in the Read Data FIFOs. The user can access these FIFOs to get the data read from memory.
user_data_wr_ena_n	Input	This active-Low signal is the write enable for the User Write Data FIFOs. The user asserts this signal to write new data to the FIFOs. The DDRII SRAM controller reads the data from the User Write Data FIFO and writes to memory.
user_addr_wr_ena_n	Input	This active-Low signal is the write enable for the User Read Write Address FIFO. The user asserts this signal to write write/read address and command in to user read write address FIFO.

Notes:

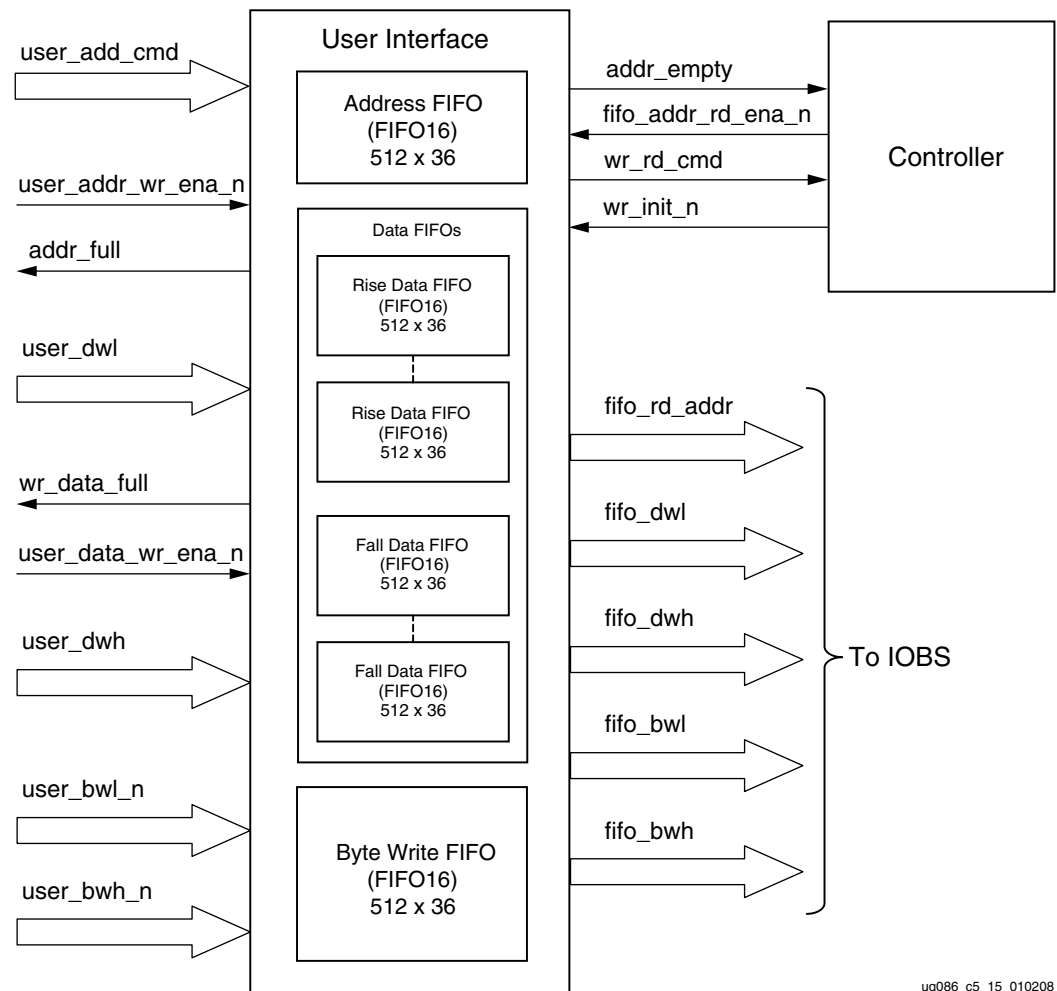
1. All user interface signal names are prepended with a controller number, for example, cntrl0_ddr_dq. DDRII SRAM devices currently support only one controller.
2. The user_clk signal is connected to clk_0 in the controller. If the user clock domain is different from clk_0 / user_clk of the MIG, the user should add FIFOs for all data inputs and outputs of the controller in order to synchronize them to the user_clk.
3. The number of address bits used depends on the density of the memory part. The controller ignores the unused bits, which can all be tied High.

Table 5-6: DDRII SRAM Interface Signals

Signal Name	Direction	Description
ddr_dq	Input/ Output	Bidirectional data bus. During READ commands, the data is sampled on both edges of the FPGA clk. During WRITE commands, the data is sampled on both edges of the K clk.
ddr_bw_n	Output	Byte enables for DDRII memory write data. The byte enables are valid when the WRITE command (DDR_LD_N=0 && DDR_RW_N=0) is asserted.
ddr_sa	Output	Address for READ and WRITE operations
ddr_ld_n	Output	Synchronous load pin. The bus cycle sequence is to be defined when this signal is Low.
ddr_rw_n	Output	Read/Write control pin. Read is active when High.
ddr_cq	Input	This read data clock, transmitted by DDRII SRAM, is edge-aligned with read data
k, k_n	Output	Differential write data clocks
c, c_n	Output	Input clock for output data
ddr_dll_off_n	Output	The DLL is disabled when this signal is Low

Write Interface

Figure 5-11 shows the user interface block diagram for write operations.



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Figure 5-11: Write User Interface Block Diagram

The following steps describe the architecture of the Address and Write Data FIFOs and show how to perform a write burst operation to DDRII memory from the user interface.

1. The user interface consists of an Address FIFO, Data FIFOs, and a Byte Write FIFO. These FIFOs are constructed using Virtex-4 FPGA FIFO16 primitives with a 512 x 36 configuration.
2. The common Address FIFO is used for both write and read commands, and comprises a command part and an address part. The command bit (bit 0 of the Address FIFO) discriminates between write and read commands; the address starts at bit 1. The command bit should be set to 0 for writes and to 1 for reads.
3. Two separate sets of Data FIFOs are used for storing the rising-edge and falling-edge data to be written to DDRII memory from the user interface. For 9-bit, 18-bit, and 36-bit data widths, two FIFO16s are required for storing rising-edge and falling-edge data. For 72-bit data width, two FIFO16s are required for rising-edge data and two for falling-edge data. MIG instantiates the required number of FIFOs to gain the required

- data width. For 9-bit and 18-bit configurations, the controller pads the extra bits of the Data FIFO with 0s.
4. The Byte Write FIFO is used to store the Byte Write signals to DDRII memory from the user interface. The controller internally pads all zeros for the unused bits.
 5. The user can initiate a write to memory by writing to the Address FIFO, Data FIFOs, and Byte Write FIFO when the FIFO full flags are deasserted and after `dly_cal_done` is asserted. The user should not access any of these FIFOs until `dly_cal_done` is asserted. The `dly_cal_done` signal assures that the clocks are stable, the reset process is completed, and the controller is ready to accept commands. Status signals `addr_full` and `wr_data_full` are asserted when the Address FIFO and Data FIFOs or Byte Write FIFO are full.
 6. When `user_addr_wr_ena_n` is asserted, the user address is stored in the Address FIFO. Similarly, when `user_data_wr_ena_n` is asserted, `user_dwl`, `user_dwh`, `user_bwl`, and `user_bwh` are stored into corresponding FIFOs. A common write-enable signal is used to enable both the Data FIFO and the Byte Write FIFO.
 7. The controller reads the address and decodes the command bit. The write command `wr_init_n` is issued if the command bit is 0 when the Address FIFO is not empty. This command acts as a read-enable to the Data and Byte Write FIFOs. The DDRII memory write command is generated from the `wr_init_n` signal by properly timing it.
 8. Figure 5-12 shows the timing diagram for a write command of BL = 4. The address should be asserted for one clock cycle as shown. For burst lengths of four, each write to the Address FIFO should have two writes to the Data FIFO consisting of two rising-edge data and two falling-edge data.

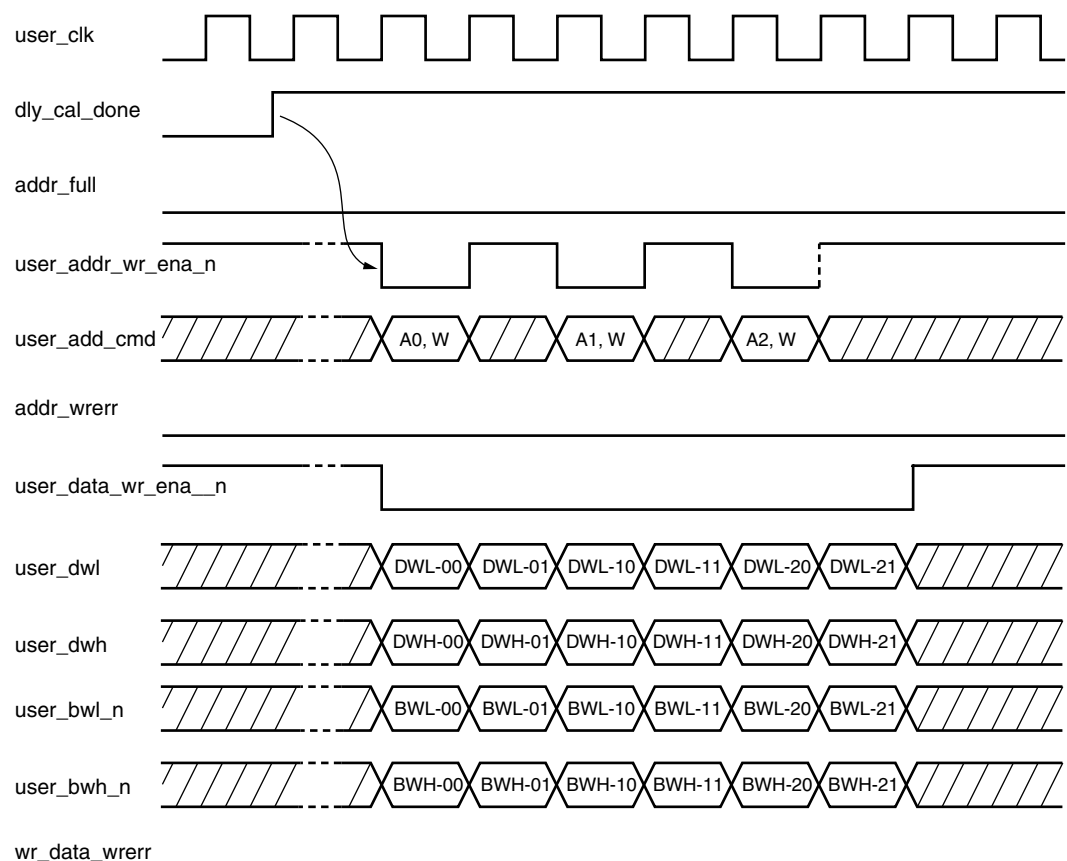
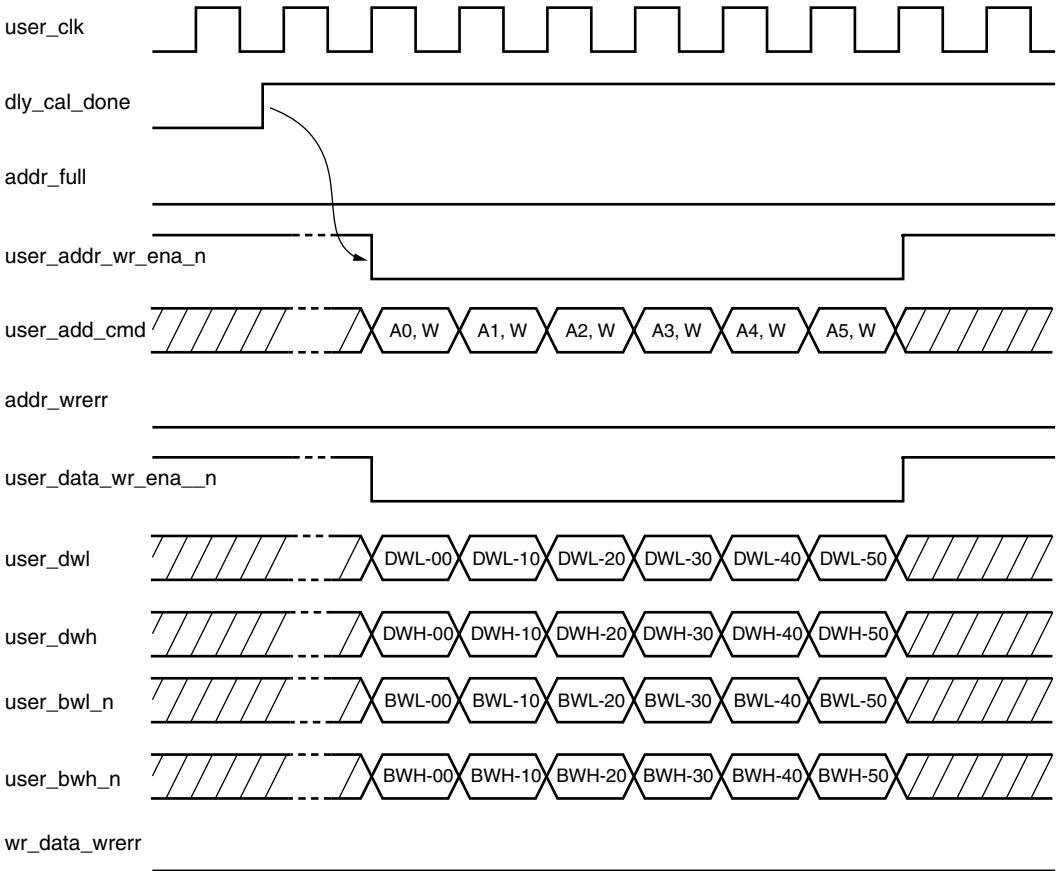


Figure 5-12: Write User Interface Timing diagram for BL = 4

9. [Figure 5-13](#) shows the timing diagram for a write command of BL = 2. For burst length of two, each write to Address FIFO has one write to Data FIFO, consisting of one rising-edge data and one falling-edge data. For burst length of two, commands can be given in every clock.

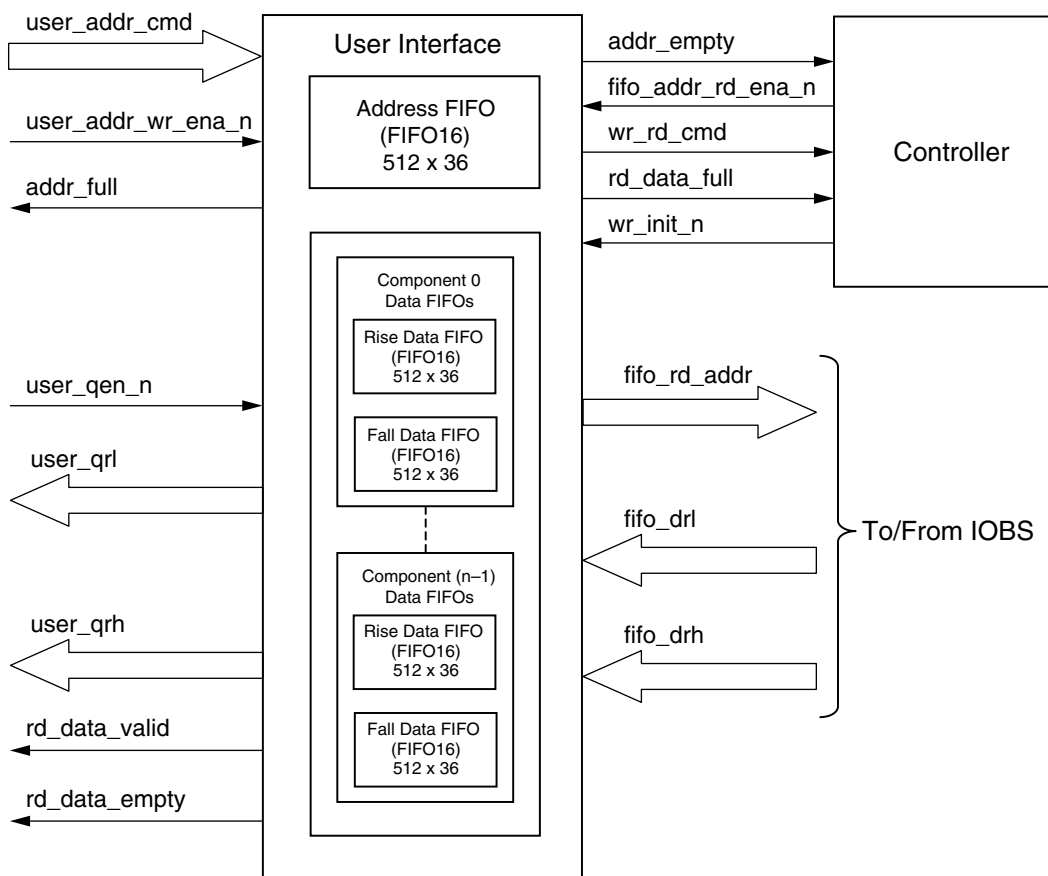


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Figure 5-13: Write User Interface Timing diagram for BL = 2

Read Interface

Figure 5-14 shows the user interface block diagram for read operations.



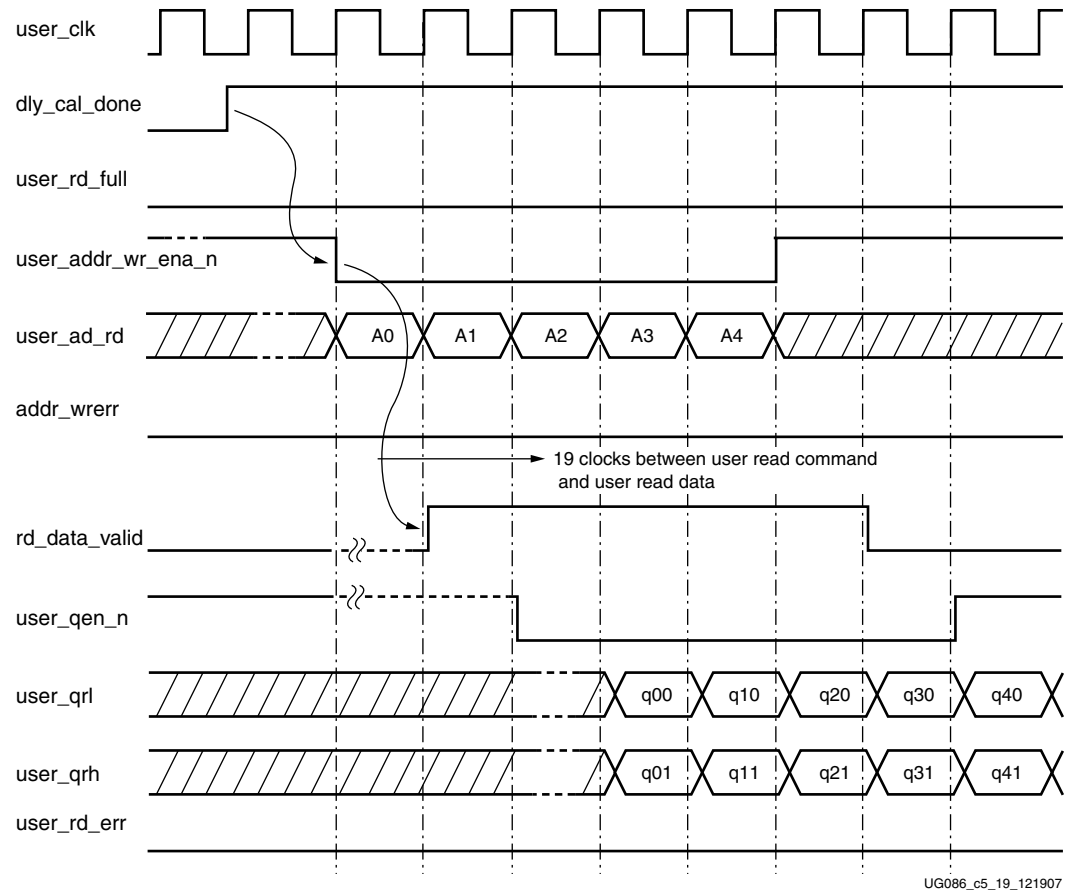
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Figure 5-14: Read User Interface Block Diagram

The following steps describe the architecture of Read Data FIFOs and show how to perform a burst read operation from DDRII SRAM from the user interface.

1. The read user interface consists of a common Address FIFO and a Read Data FIFO. The Address FIFO and Read Data FIFO are constructed using FIFO16s with a 512 x 16 configuration.
2. The number of Read Data FIFOs required depends on the number of DDRII components used. Using 9-bit components for 36-bit data width, a total of eight FIFOs are required, four FIFOs for rising-edge data and four FIFOs for falling-edge data. Though each FIFO can accommodate 36-bit data, the requirement of having one FIFO per component arises from the CQ pattern calibration. Internal pattern calibration is done per CQ. Controller generates the Read Data FIFO write-enable signal for each FIFO separately, depending on the CQ pattern calibration.
3. To initiate a DDRII read command, the user should write the Address FIFO with the command bit set to logic 1 when the FIFO `addr_full` flag is deasserted and the `dly_cal_done` signal is asserted. The `dly_cal_done` signal assures the controller clocks are stable, the internal reset process is completed, and the controller is ready to accept commands.

4. The user should issue the Address FIFO write enable signal `user_addr_wr_ena_n` along with `user_addr_cmd` to write the address to the Address FIFO.
5. When status signal `addr_empty` is deasserted, the controller reads the Address FIFO. If the command bit is 1 when the Read Data FIFO is not full, the appropriate control signal required for a read command is sent to the DDRII memory.
6. Prior to the actual read and write commands, the design calibrates the latency from the time the read command is issued to the time data is received in terms of the number of clock cycles. Using the precalibrated delay information between the read commands to read data, the controller generates the write-enable signals to the Read Data FIFOs. The delay calibration is done per DDRII component.
7. The Low state of `rd_data_empty` indicates read data is available. Asserting `user_qen_n` reads rising-edge data and falling-edge data simultaneously on every rising edge of the clock.
8. [Figure 5-15](#) and [Figure 5-16](#) shows the user interface timing diagrams for $BL = 2$ and $BL = 4$.



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Figure 5-15: Read User Interface Timing Diagram for BL = 2

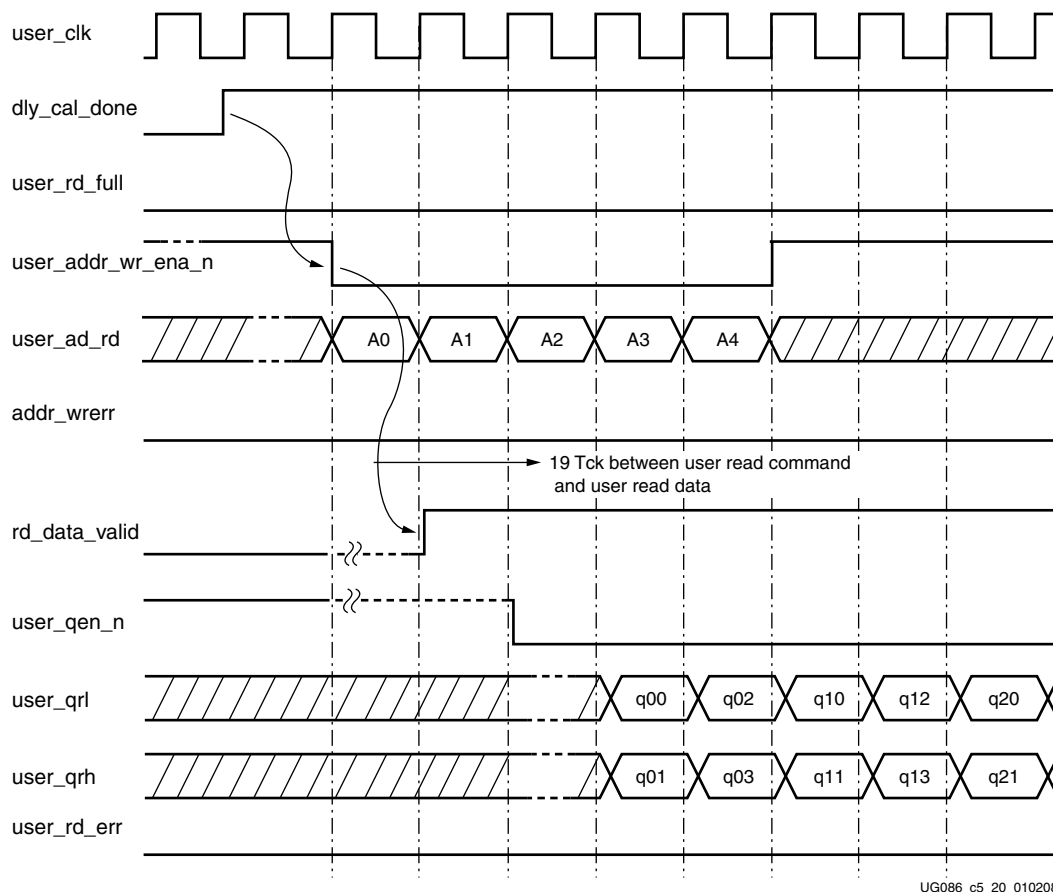


Figure 5-16: Read User Interface Timing Diagram for BL = 4

Table 5-7 shows the maximum read latency of the controller. Maximum latency occurs when the read command is given to an empty FIFO.

Table 5-7: Maximum Read Latency

Parameter	Number of Clocks	Description
User command to address FIFO empty flag	6 (2 + 4)	Two clocks for the two-stage pipeline before the FIFO input. An empty FIFO takes four clocks to deassert the empty status signal after the FIFO is written with the first data in first-word fall-through (FWFT) mode.
Command from controller state machine to DDR memory	3	Decoding and passing the command to DDR memory.
DDR command to FIFO input data	4	Two clocks for DDRII memory latency, two clocks for calibration delay.

Table 5-7: Maximum Read Latency (Cont'd)

Parameter	Number of Clocks	Description
FIFO input to FIFO output	6	Pipelines the write enable six clock cycles (two-stage pipeline at the FIFO and one reg for calibration, and four clocks for deassertion of read data fifo empty).
Total Latency	19	Total latency from read command issued to Address FIFO, to data input to user interface.

DDRII SRAM Signal Allocations

Table 5-8 shows the list of signals for a DDRII SRAM design allocated in a group from bank selection checkboxes in MIG.

Table 5-8: DDRII Signal Allocations

Bank Selected	Signals Allocated in the Group
Address	Memory address and memory control
Data	Memory data and memory byte read/write
System Control	System reset from the user interface and status signals
System Clock	System clocks from the user interface

When the Address box is checked in a bank, the address, ddr_ld_n, ddr_rw_n, ddr_dll_off_n bits are assigned to that particular bank.

When the Data box is checked in a particular bank, the memory data, the memory byte write, the memory read clocks, the memory write clocks, and the memory input clock for the output data are assigned to that particular bank.

When the System Control box is checked in a bank, the sys_rst_n, compare_error, and dly_cal_done bits are assigned to that particular bank.

When the System Clock box is checked in a bank, the refclk_p, refclk_n, dly_clk_200_p, and dly_clk_200_n bits are assigned to that particular bank.

For special cases, such as without a testbench and without a DCM, the corresponding input and output ports are not assigned to any pins of the FPGA in the design UCF because the user can connect these ports to the FPGA pins or can connect to some logic internal to the same FPGA.

Note: Timing has been verified for most of the MIG generated configurations. For the best timing results, adjacent banks in the same column of the FPGA should be used. Banks that are separated by unbonded banks should be avoided because these can cause timing violations.

Supported Devices

The design generated out of MIG is independent of the memory package, hence the package part of the memory component is replaced with X, where X indicates a don't care condition. Table 5-9 shows the list of components supported by MIG.

Table 5-9: Supported Devices for DDRII SRAM

Virtex-4 FPGAs (Verilog and VHDL)		
Components	Make	Configuration
CY7C1319BV18-250BZC	Cypress	x18
CY7C1318BV18-250BZC	Cypress	x18
CY7C1320BV18-200BZC	Cypress	x36
CY7C1320BV18-250BZC	Cypress	x36
CY7C1321AV18-250BZC	Cypress	x36
CY7C1321BV18-250BZC	Cypress	x36
CY7C1419AV18-250BZC	Cypress	x18
CY7C1420AV18-250BZC	Cypress	x36
CY7C1421AV18-250BZC	Cypress	x36
CY7C1427AV18-250BZC	Cypress	x9
CY7C1428AV18-250BZC	Cypress	x9
CY7C1518V18-250BZC	Cypress	x18
CY7C1520V18-250BZC	Cypress	x36
CY7C1916BV18-250BZC	Cypress	x9
CY7C1917BV18-250BZC	Cypress	x9
K7I161882B-FC25	Samsung	x18
K7I161884B-FC25	Samsung	x18
K7I163682B-FC25	Samsung	x36
K7I163684B-FC25	Samsung	x36
K7I321884C-FC25	Samsung	x18
K7I321884M-FC25	Samsung	x18
K7I323684C-FC25	Samsung	x36
K7I323684M-FC25	Samsung	x36
K7I641882M-FC25	Samsung	x18

Simulating the DDRII SRAM Design

After generating the design, MIG creates a `sim` folder in the specified path. This folder contains simulation files for a particular design. The `sim` folder contains an external testbench and a `.do` file to simulate the generated design. To learn more details about the files in the `sim` folder and to simulate the design, refer to [“Simulation Guide,” page 499](#).

Hardware Tested Configurations

This design is not hardware verified.

Implementing RLD RAM II Controllers

Reduced Latency DRAM (RLDRAM II) devices address high bandwidth memory requirements. The RLD RAM II utilizes an eight-bank architecture optimized for high-speed operation and a double data rate I/O for increased bandwidth. This chapter describes how to implement RLD RAM II interfaces for Virtex®-4 FPGAs generated with MIG. This design is based on XAPP710 [\[Ref 22\]](#).

Feature Summary

This section summarizes the supported and unsupported features of the RLD RAM II controller design.

Supported Features

The RLD RAM II controller design supports the following:

- A maximum frequency of 250 MHz
- Both SIO and CIO memories
- Multiplexed and non-multiplexed addresses
- All configurations (Config1, Config2, and Config3)
- x9, x18, and x36 components
- Data widths of 9, 18, 36, and 72 bits
- Back-to-back read and write operations
- Write followed by read operations
- Read followed by write operations
- All combinations of the Mode Register
- XST and Synplicity synthesis tools
- Verilog and VHDL
- With and without a testbench
- With or without a DCM

Design Frequency Range

Table 6-1: Design Frequency Range in MHz

Memory	FPGA Speed Grade					
	-10		-11		-12	
	Min	Max	Min	Max	Min	Max
Component (SIO/CIO)	175	200	175	230	175	250

Unsupported Features

The RLDRAM II controller design does not support:

- Commands in successive clocks with a burst length of 2. The controller processes these commands with one extra clock latency. For example, a READ or WRITE sequence of commands, BL = 2, Configuration = Any, CIO/SIO.

Supported RLDRAM II Devices

The RLDRAM II controller design supports the RLDRAM II devices from Micron indicated in Table 6-2. MIG generates the designs for the list of components mentioned in Table 6-2 in both VHDL and Verilog. The design generated out of MIG is independent of memory package, hence the package part of the memory component is replaced with XX, where XX indicates any package.

Table 6-2: Supported RLDRAM II Devices

Device	Make	CIO/SIO	Configuration	Speed Grade	Supported Data Widths (in bits)	Packages
MT49H32M9XX	Micron	CIO	x9	(-5), (-25), (-33)	9, 18, 36, 72	BM, FM
MT49H16M18XX	Micron	CIO	x18	(-5), (-25), (-33)	18, 36, 72	BM, FM
MT49H8M36XX	Micron	CIO	x36	(-5), (-25), (-33)	36, 72	BM, FM
MT49H32M9CXX	Micron	SIO	x9	(-5), (-25), (-33)	9, 18, 36, 72	BM, FM
MT49H16M18CXX	Micron	SIO	x18	(-5), (-25), (-33)	18, 36, 72	BM, FM

Architecture

Figure 6-1 shows a top-level block diagram of the RLDRAM II memory controller.

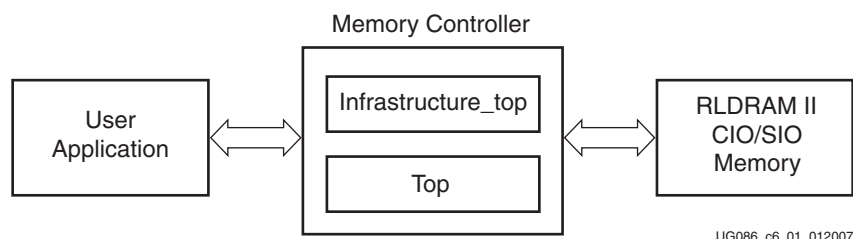


Figure 6-1: RLDRAM II Memory Controller Block Diagram

Figure 6-2 shows the hierarchical structure of the RLDRAM II design generated by MIG with a testbench and a DCM.

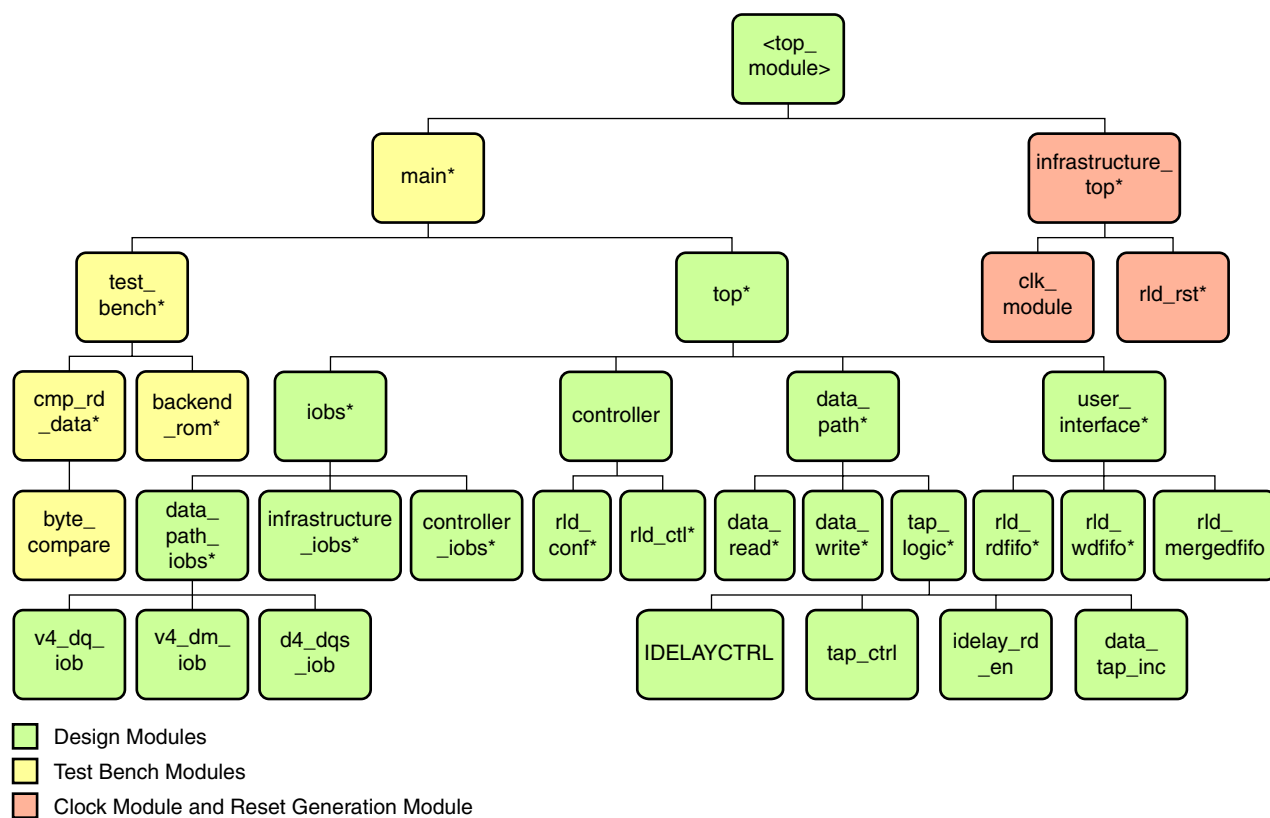


Figure 6-2: RLDRAM II Memory Controller Hierarchy

The modules are classified as follows:

- Design modules
- Testbench modules
- Clocks and reset generation modules

There is a parameter file generated with the design that has all the user input and design parameters selected from MIG.

MIG can generate four different RLDRAM II designs:

- With a testbench and a DCM
- Without a testbench and with a DCM
- With a testbench and without a DCM
- Without a testbench and without a DCM

MIG outputs both an `example_design` and a `user_design`. The MIG-generated `example_design` includes the entire memory controller design along with a synthesized testbench (example user application). This testbench generates sample writes and reads and then uses comparison logic to verify that the data patterns written are the same as those received. This `example_design` can be used to test functionality both in simulation and in hardware. The `user_design` includes the memory controller design only. This design allows users to connect the MIG memory controller design to a user developed testbench (user application). Refer to [Table 6-10, page 269](#) for user interface signals, the “[User Interface Accesses](#),” [page 271](#) for timing restriction on user interface signals, and [Figure 6-10, page 273](#) and [Figure 6-11, page 274](#) for write interface timing.

Design clocks and resets are generated in the `infrastructure_top` module, which comprises `clk_module` and `rld_rst` modules. The DCM clock is instantiated in the `clk_module` module for designs with a DCM. The differential design clock is an input to this module, which generates the system clocks. A user reset is input to the `rld_rst` module, which generates the system resets. A 200 MHz differential clock for the IDELAYCTRL module is derived from 200 MHz differential clocks. This clock is present in the top-level module.

The `clk_module` is not instantiated in the `infrastructure_top` module if the DCM option is not checked in MIG. So, the system operates on the user-provided clocks. The system reset is generated in the `rld_rst` module using the `dcm_lock` signal and the ready signal of the IDELAYCTRL element. For more information on the clocking structure, refer to “[Clocking Scheme](#),” [page 266](#).

Figure 6-3 shows a block diagram representation of an RLDRAM II design with a DCM and a testbench. The design inputs are the system clocks and the user reset. `sysreset_n` is the system reset signal. All design resets are generated using the `dcm_locked` signal, the `sysreset_n` signal, and the `idelay_ctrl_rdy` signal of the `IDELAYCTRL` element. The `pass_fail` output signal indicates whether the design passes or fails. The `init_done` signal indicates the completion of initialization and calibration of the design. Required clocks and reset signals for the design are generated from the `clk_module` and the `rld_rst` modules, respectively. The `clk_module` instantiates the DCM primitive. The `infrastructure_top` module instantiates the `clk_module` and the `rld_rst` modules.

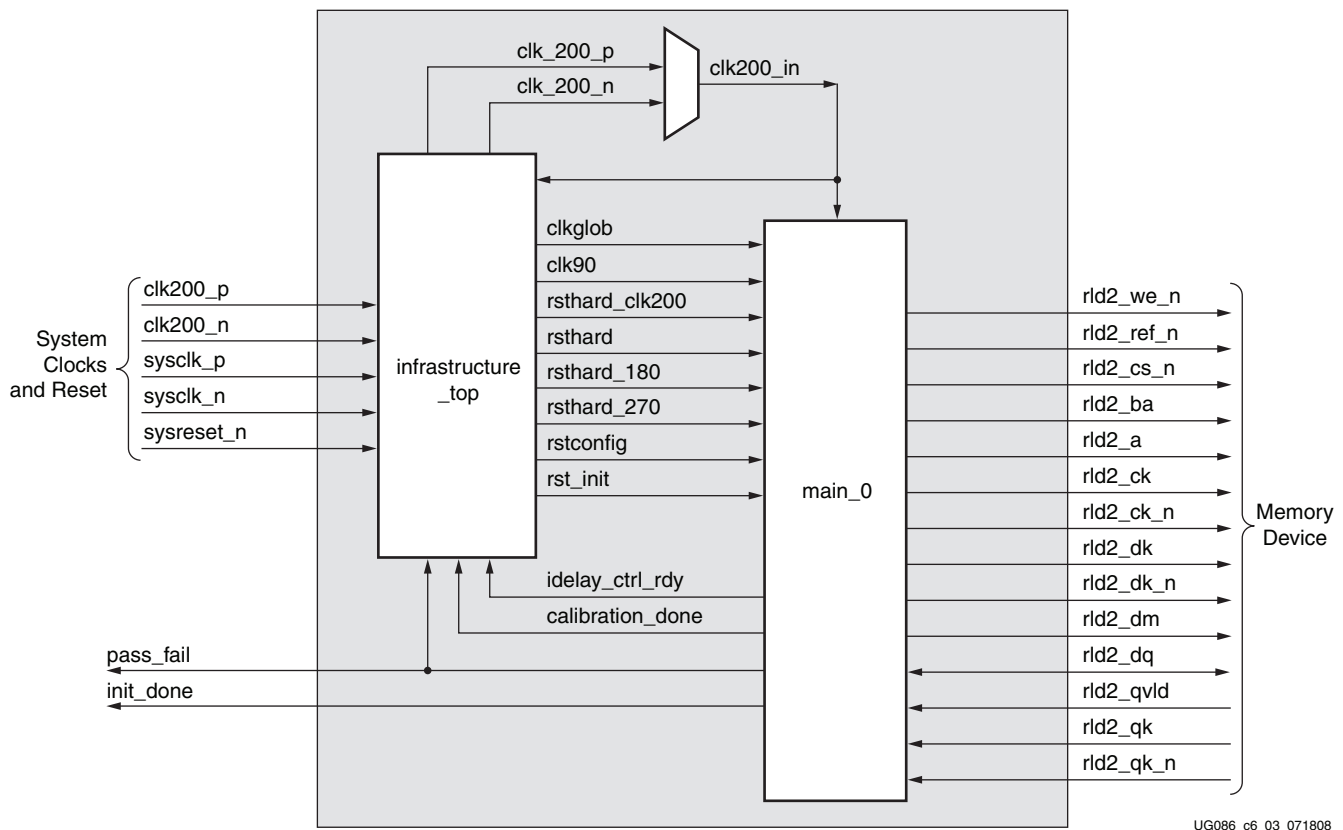
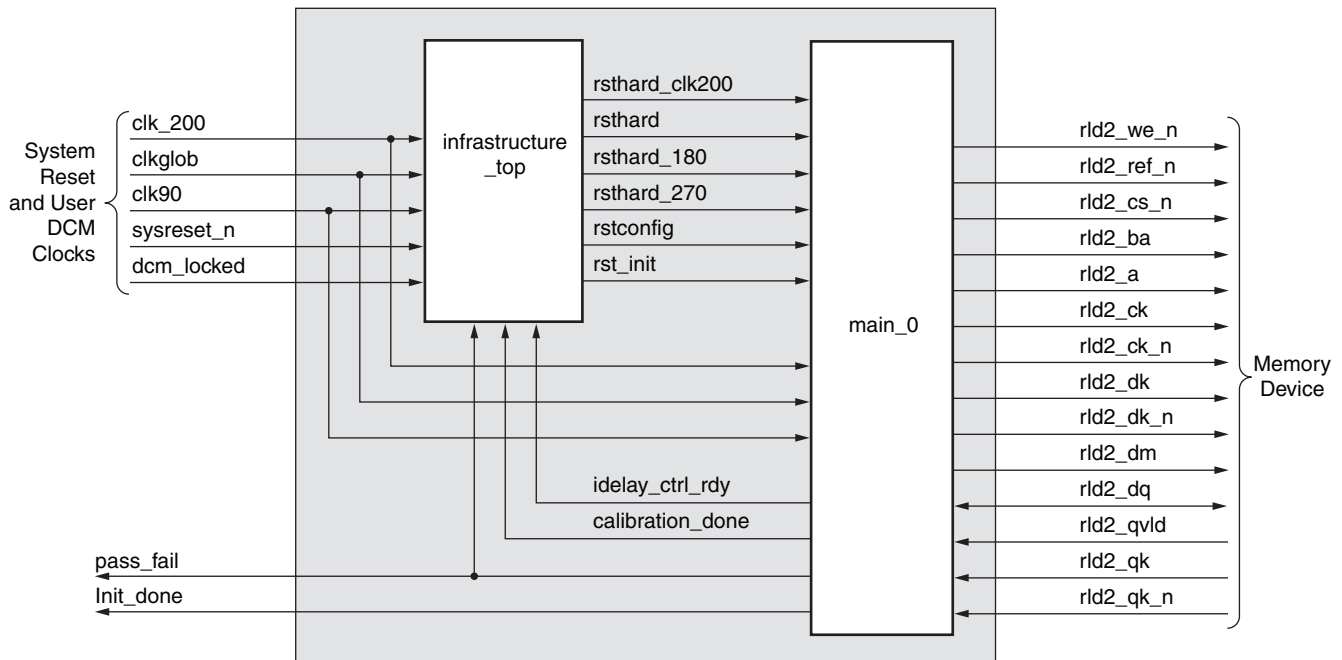


Figure 6-3: Top-Level Block Diagram of the RLDRAM II Design with a DCM and a Testbench

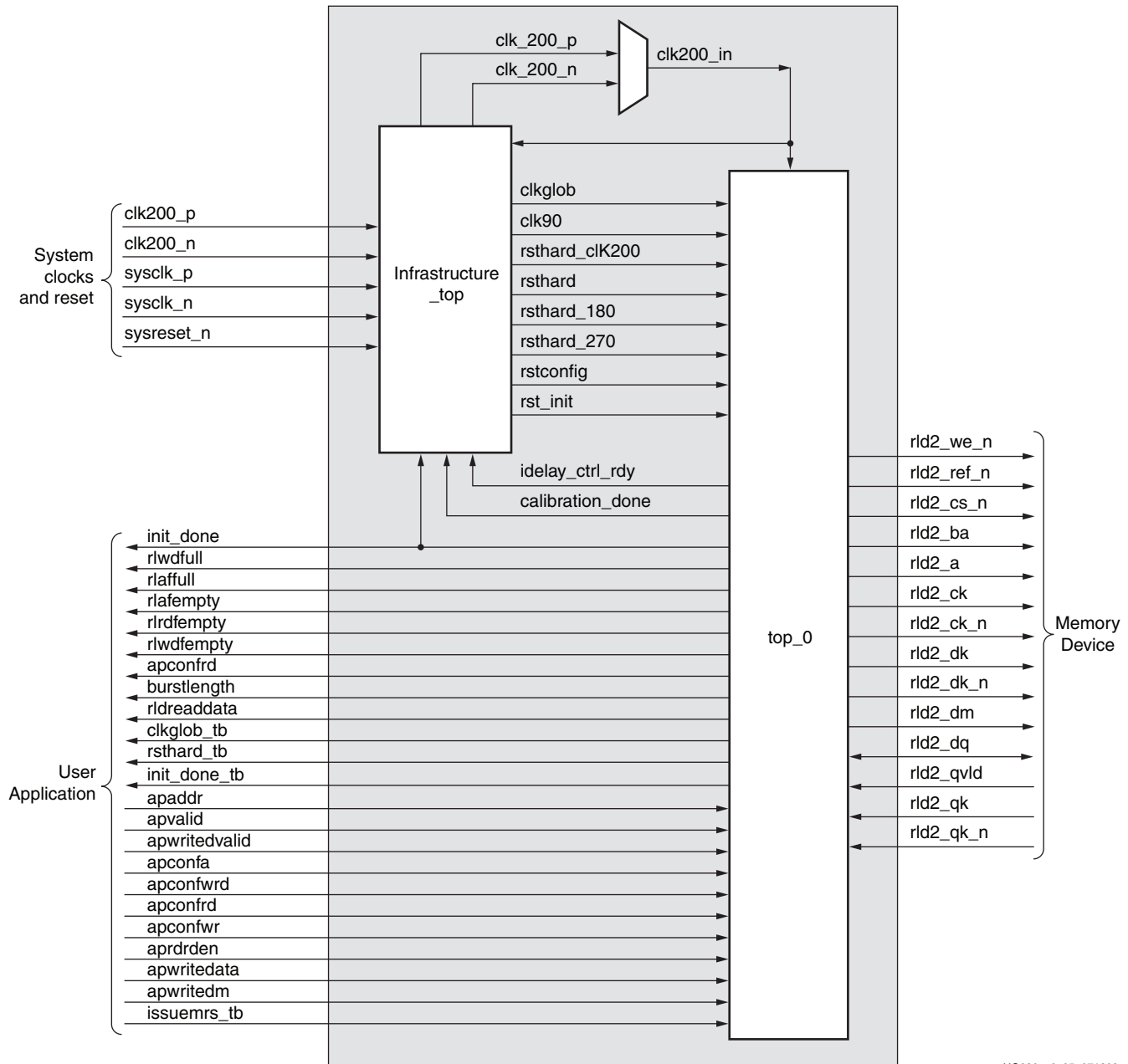
Figure 6-4 shows a block diagram representation of the top-level RLDRAM II module without a DCM but with a testbench. Design inputs are the user clocks and the user reset. sysreset_n is the system reset signal. All design resets are generated using the dcm_locked signal, the sysreset_n signal, and the idelay_ctrl_rdy signal of the IDELAYCTRL element. The design uses the user input clocks. These clocks should be single-ended. The user application must have a DCM primitive instantiated in the design, and all user clocks should be driven through BUFPGs. The pass_fail output signal indicates whether the design passes or fails. The init_done signal indicates the completion of initialization and calibration of the design.



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Figure 6-4: Top-Level Block Diagram of the RLDRAM II Design without a DCM but with a Testbench

Figure 6-5, page 259 shows a block diagram representation of the top-level RLDRAM II module with a DCM but without a testbench. Design inputs are the system clocks and reset. sysreset_n is the system reset signal. All design resets are generated using the dcm_locked signal, the sysreset_n signal, and the idelay_ctrl_rdy signal of the IDELAYCTRL element. User must drive the user application signals. The design provides the clkglob_tb and rsthard_tb signals to the user to synchronize the user application signals with the design. The signal clkglob_tb is connected to clkglob clock signal in the controller. If the user clock domain is different from clkglob/clkglob_tb, the user should add FIFOs for all the inputs and output of the controller (user application signals), in order to synchronize them to clkglob_tb clock. The required design clocks and design reset signals for the design are generated from the clk_module and the rld_rst modules, respectively. The clk_module instantiates the DCM primitive. The infrastructure_top module instantiates the clk_module and rld_rst modules. The init_done signal indicates the completion of initialization and calibration of the design.

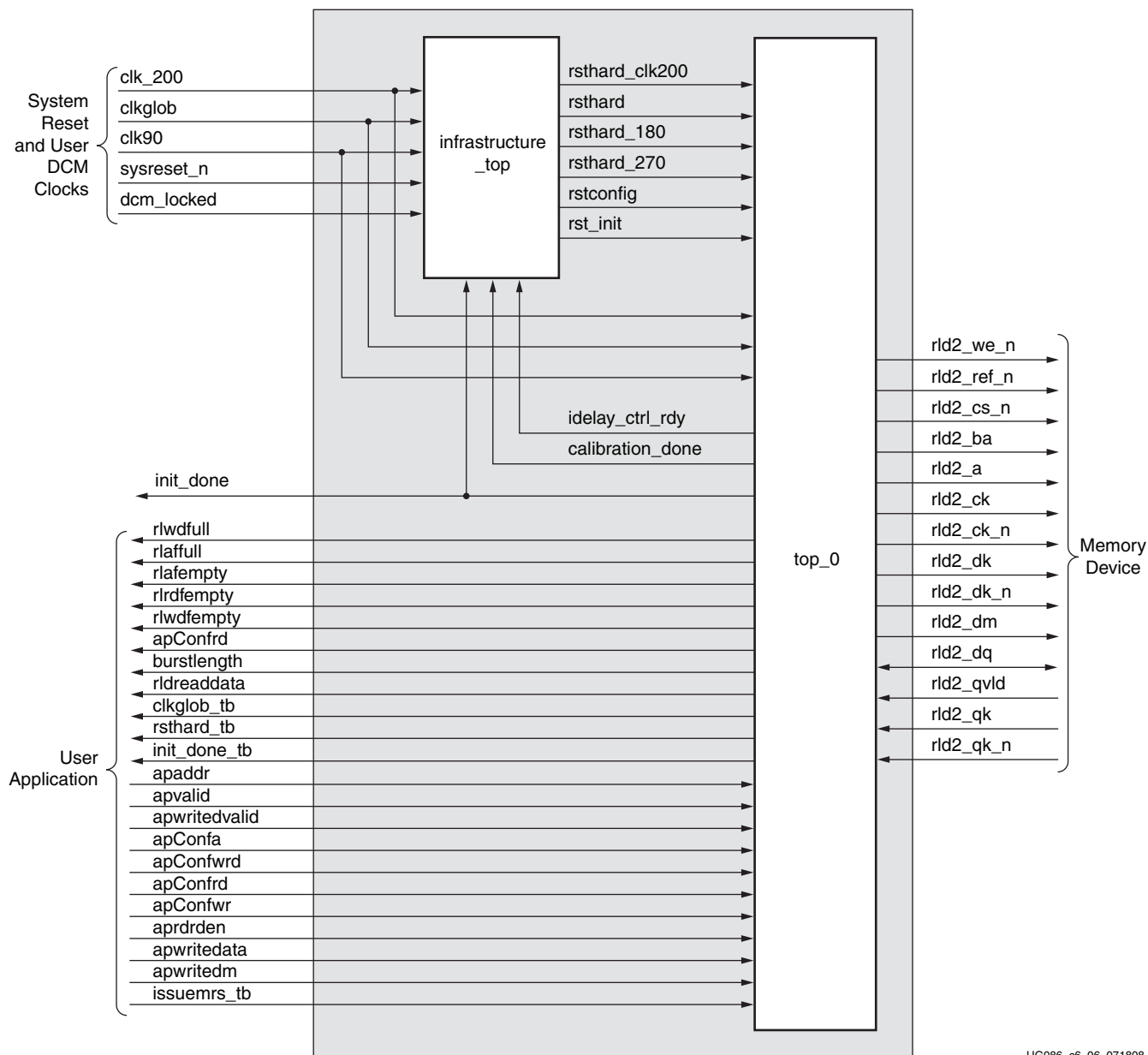


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Figure 6-5: Top-Level Block Diagram of the RLDRAM II Design with a DCM but without a Testbench

Figure 6-6 shows a block diagram representation of the top-level RLDRAM II module without a DCM or a testbench. Design inputs are the user clocks and the user reset. `sysreset_n` is the system reset signal. All design resets are generated using the `dcm_locked` signal, the `sysreset_n` signal, and the `idelay_ctrl_rdy` signal of the `IDELAYCTRL`. The design uses the user input clocks, which should be single-ended. The user application must have a DCM primitive instantiated in the design, and all user clocks should be driven through BUFGs. User must drive the user application signals. The design provides the `glob` and `rsthard_tb` signals to the user to synchronize the user application signals with the design. The signal `clkglob_tb` is connected to `clkglob` clock signal in the controller. If the user clock domain is different from `clkglob`/`clkglob_tb`, the user should add FIFOs for all the inputs and output of the controller (user application signals), in order to synchronize

them to clkglob_tb clock. The Init_done signal indicates the completion of initialization and calibration of the design.



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Figure 6-6: Top-Level Block Diagram of the RLDRAM II Design without a DCM or a Testbench

The RLDRAM II memory controller processes the user commands to generate the RLDRAM II interface signals. The RLDRAM II memory controller has a built-in synthesizable testbench to generate all the RLDRAM commands. The built-in testbench enables simulation and validation of the design in hardware. To interface with the user application, the RLDRAM II memory controller must be separated from the built-in testbench. MIG generates designs with and without a testbench. The following parameters are selectable through the GUI: the type of the RLDRAM (SIO or CIO), the data width, the burst length, multiplexed or non-multiplexed address, memory component, and other configuration values.

The design can use any selected banks of the Virtex-4 FPGAs. It can use different banks or the same banks for data, address, and control signals.

The HSTL_II_18 I/O standard is used for address, control, and data signals, and the DIFF_HSTL_II_DCI_18 I/O standard is used for clock signals.

Similar to other DRAM architectures, the RLDRAM II requires its entire content to be refreshed periodically. The AREF command initiates a refresh for the device and must be used each time a refresh is required. The RLDRAM II memory controller has an option to enable the execution of auto-refresh commands periodically. If this option is OFF, the user has to provide the auto-refresh commands at regular intervals.

Implemented Features

This section provides details on the supported features of the RLDRAM II controller.

Address Multiplexing

The RLDRAM II memory controller supports multiplexed and non-multiplexed address modes. Bit A5 of the Mode Register determines whether the address mode is multiplexed (A5 = 1) or non-multiplexed (A5 = 0). In multiplexed address mode, the address is provided to the RLDRAM II memory in two cycles, which are latched into the memory on two consecutive rising clock edges. The advantage of this approach is a maximum of 11 address bits are required to control the RLDRAM II memory.

In multiplexed address mode, the controller outputs an 11-bit address. The user has to properly connect the addresses to the RLDRAM II devices. [Table 6-3](#) provides the address mapping between the controller and the RLDRAM II devices for the multiplexed address mode.

Table 6-3: Address Mapping in Multiplexed Address Mode

Address	Address Mapping										
Output Address	A0	A1	A2	A3	A4	A5	A6	A7	A8	A9	A10
RLDRAM II Address	A0	A3	A4	A5	A8	A9	A10	A13	A14	A17	A18

CIO/SIO

The RLDRAM II memory controller supports both CIO and SIO memory components. The GUI provides an option to select the required memory components. The separate RLDRAM I/O interface transfers two 18-bit or 9-bit data words per clock cycle at the I/O balls. The read port has dedicated data outputs to support read operations, while the write port has dedicated input balls to support write operations. Output data is referenced to the

free-running output data clock. This architecture eliminates the need for high-speed bus turnarounds.

Data Capture Using the Direct-Clocking Technique

The read data from the RLDRAM II is captured using the direct-clocking technique. In this technique, data is delayed and center-aligned with respect to the internal FPGA clock. In this scheme, the internal FPGA clock captures the read data. The clock/strobe transmitted from the memory determines the delay value for the associated data bits. As a result, there are no restrictions on the number of data bits associated with a strobe. Because the strobe does not need to be distributed to the associated data bits, no additional clocking resources are required. Refer to XAPP701 [Ref 18] for details on this technique.

Calibration is done in two stages:

1. In the first stage of calibration, QK is center-aligned with respect to the FPGA clock. QK is a free-running clock from RLDRAM II. The DQ data is edge-aligned with the QK read strobe, and the QVLD read data valid signal is edge-aligned with the QK read strobe. The first and second edges of the QK strobe are detected using the FPGA clock to determine the center of the QK window.

Once the QK window is center-aligned with the FPGA clock, the same amount of delay (tap counts) is applied to the DQ through the IDELAY element, so that the DQ window is center-aligned with the FPGA clock. Signal `qk_tap_sel_done` in the `tap_logic` module indicates the status of the first stage calibration. When `qk_tap_sel_done` is asserted High, it indicates the completion of first stage calibration. After the first stage calibration is complete, the second stage calibration starts.

2. In the second stage of calibration, the write-enable signal for the read data FIFO is determined in order to store the read data from memory into the Read Data FIFO. QVLD from RLDRAM II is delayed such that it exactly aligns with the delayed DQ window. This delayed QVLD signal is used as the write-enable signal for the Read Data FIFO.

The `sel_done` port in the `data_path` module indicates the status of the second stage calibration. When `sel_done` is asserted High, it indicates the completion of second stage calibration, which implies the completion of the whole initialization and calibration process. After the initialization and calibration is done (i.e., the `init_done` signal in `design_top` is asserted High), the controller can start issuing user commands to the memory.

When calibration is complete, the `calibration_done` signal is asserted High.

The `tap_logic` module instantiates the IDELAYCTRL primitive of the Virtex-4 FPGA. The IDELAYCTRL primitive is used to continuously calibrate the individual delay elements in its region to reduce the effect of process, temperature, and voltage variations. A 200 MHz clock has to be fed to this primitive. The MIG tool instantiates the required number of IDELAYCTRLs in the RTL and uses the LOC constraints in the UCF file to fix their locations. The number of IDELAYCTRLs is defined by the IDELAYCTRL_NUM parameter in the `idelay_ctrl` module. In the RTL, IDELAY_CTRL_RDY is generated by doing a logical AND of the RDY signals of every IDELAYCTRL block.

IDELAYCTRL LOC constraints should be checked in the following cases:

- The MIG design is used with other IP cores or user designs that also require the use of IDELAYCTRL and IDELAYs.

- Previous ISE® software releases 8.2.03i and 9.1i had an issue with IDELAYCTRL block replication or trimming. When using these revisions of the ISE software, the user must instantiate and constrain the location of each IDELAYCTRL individually.

See UG070 [Ref 7] for more information on the requirements of IDELAYCTRL placement.

Memory Initialization

The RLDRAM II device must be powered up and initialized in a predefined manner. The controller handles the initialization sequence as described in this section.

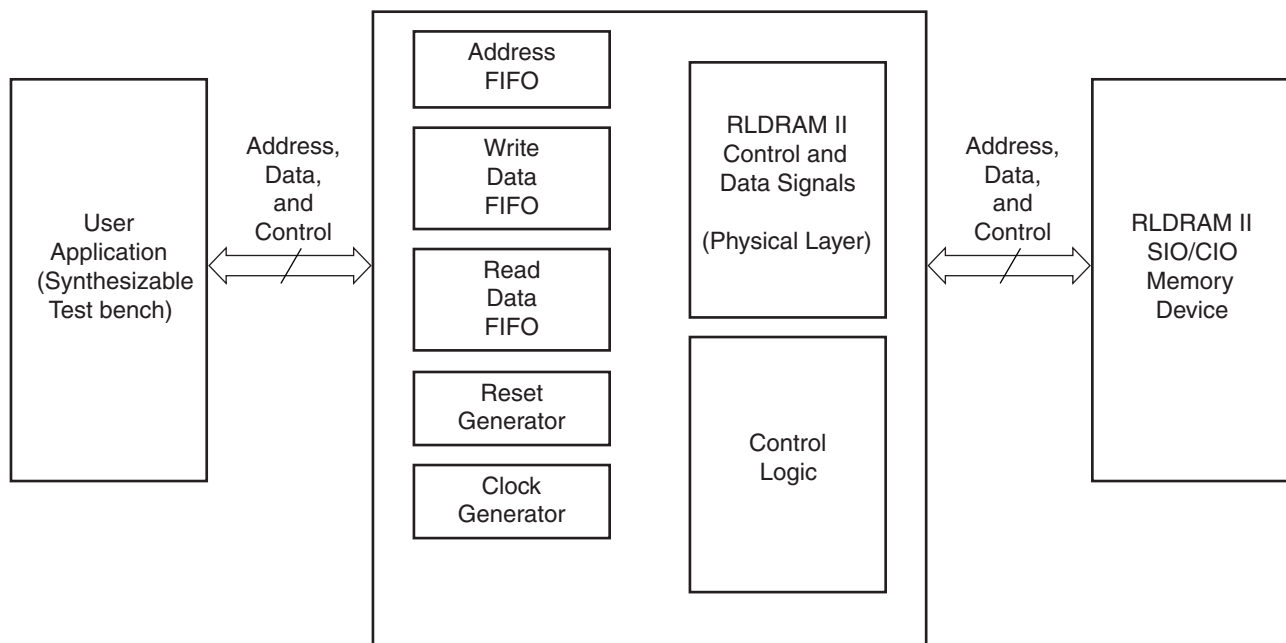
After all power supply and reference voltages are stable and the master clock (rld_ck and rld_ck_n) is stable, the RLDRAM II device requires a 200 μ s (minimum) delay prior to applying an executable command. After the 200 μ s (minimum) delay has passed, three MODE REGISTER SET (MRS) commands are issued. For non-multiplexed addressing, two dummy commands and one valid MRS command are issued. For multiplexed addressing, four MODE REGISTER SET (MRS) commands are issued, consisting of two dummy commands and two valid MRS commands.

Six clock cycles (t_{MRSC}) after the valid MRS commands, eight AUTO REFRESH commands are issued, one on each bank, separated by 2048 cycles.

Initialization is complete after t_{RC} . The number of clock cycles (t_{RC}) after auto refresh depends on the Mode Register configuration parameter. The RLDRAM II memory controller takes care of the t_{RC} value for different configurations. The device is ready for normal operation as indicated by the init_done outputs to the application.

Block Diagram Description

Figure 6-7 shows a detailed block diagram of the RLDRAM II memory controller. The major blocks of the controller are described following the figure.



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Figure 6-7: Detailed Block Diagram of the RLDRAM II Memory Controller

User Interface

The user interface of the RLDRAM II memory controller is a FIFO-based implementation. Three FIFOs are used: an Address FIFO, a Write Data FIFO, and a Read Data FIFO.

FIFO generator v4.2 is used in this design. It can be generated using XCO files located in the `par` folder or by using the FIFO generator tool of CORE Generator™ software. FIFO generator v4.2 is used in the `rld_mergedfifo`, `rld_rdfifo`, and `rld_wrfifo` modules. The FIFO has various threshold attributes whose offset values can be changed based on the requirement in the XCO files provided in the `par` folder. Alternatively, the FIFO generator can be regenerated using the FIFO generator tool of CORE Generator software with various threshold offset values. For valid FIFO threshold offset values, refer to DS317 [Ref 37].

Test Bench

The MIG tool generates two different RTL folders, `example_design` and `user_design`. The `example_design` includes the synthesizable test bench, while `user_design` does not include the test bench modules. The MIG test bench performs eight write commands and eight read commands in an alternating fashion. The number of words in a write command depends on the burst length. For a burst length of 4, the test bench writes a total of 32 data words for all eight write commands (16 rise data words and 16 fall data words). For a burst length of 8, the test bench writes a total of 64 data words. It writes the data pattern of 1EE, 011, 1AA, 055 in a sequence in which 1EE and 1AA are rise data words and 011 and 055 are fall data words for a 9-bit design. The falling edge data is the complement of the rising edge data. For a burst length of 2, the data sequence for the first write command is 1EE, 011 and the data sequence for the second write command is 1AA, 055. For a burst length of 4, the data pattern for the first write command is 1EE, 011, 1AA, 055, and the same pattern is repeated for all the remaining write commands. For a burst length of 8, the data pattern for the first write command is 1EE, 011, 1AA, 055, 1EE, 011, 1AA, 055, and the same pattern is repeated for all the remaining write commands. This data pattern is repeated in the same order based on the number of data words written. For data widths greater than 9, the same data pattern is concatenated for the other bits. For a 36-bit design and burst length of 4, the data pattern for the first write command is F77BBDDEE, 088442211, D56AB55AA, 2A954AA55.

Address generation logic generates eight different addresses for eight write commands. The same eight address locations are repeated for the following eight read commands. The read commands are performed at the same locations where the data is written. There are a total of 16 different address locations for 16 write commands, and the same address locations are generated for 16 read commands. Upon completion of a total of 32 commands, including both writes and reads (8 writes, 8 reads, 8 writes, 8 reads), address generation rolls back to the first address of the first write command, and the same address locations are repeated. The MIG test bench exercises only a certain memory area. The address is formed such that all address bits are exercised. During writes, a new address is generated for every burst operation on the column boundary.

During reads, comparison logic compares the read pattern with the pattern written, i.e., the 1EE, 011, 1AA, 055 pattern. For example, for a 9-bit design of burst length 4, the data written for a single write command is 1EE, 011, 1AA, 055. During reads, the read pattern is compared with the 1EE, 011, 1AA, 055 pattern. Based on a comparison of the data, a `PASS_FAIL` status signal is generated. If the data read back is the same as the data written, the `PASS_FAIL` signal value is 010, otherwise it is 100. A `PASS_FAIL` signal value of 001 indicates that the calibration process is not yet complete.

Address FIFO

This FIFO serves as the buffer for the user interface to store addresses corresponding to the read and write data as well as the user-controlled refreshes. All reads, writes, and user refreshes are scheduled in this FIFO. This synchronous FIFO is 26 bits wide and 16 words deep. [Table 6-4](#) defines the configuration of the 26 bits.

Table 6-4: Address FIFO Bit Configuration

Bit Configuration	Description
25	User Refresh
24	Read/ $\overline{\text{Write}}$
[23:3]	Memory Address bits A[20:0]
[2:0]	Memory Bank Address bits BA[2:0]

Write Data FIFO

The Write Data FIFO serves as a buffer for the user interface to store data to be written into memory. This synchronous FIFO is two times the memory data width plus the data mask (DM) width and is 15 words deep. For a burst length of two, each location in the Write Data FIFO comprises the required data. For a burst length of four, two locations in the Write Data FIFO comprise the required data. For a burst length of eight, four locations in the Write Data FIFO comprise the required data.

[Table 6-5](#) defines the FIFO configuration for 36-bit data width using x36 memory components.

Table 6-5: Write Data FIFO Bit Configuration for 36-bit Data Width

Bit Configuration	Description
[73:72]	Write Data Mask
[71:0]	Write Data

Read Data FIFO

The Read Data FIFO serves as a buffer for the RLDRAM II memory controller to store data it has read from the memory. This synchronous FIFO is two times the width of the memory data width and 16 words deep. For x18 memory components, an 18-bit wide Base FIFO is used, and for x36 memory components, a 36-bit wide Base FIFO is used. Multiple Base FIFO instances are used to match the two times memory data width. For x18 components with a 36-bit data width, the Base Read FIFO width is 18 bits. Four Read FIFO instances are used to get two times the memory data width. For a burst length of two, each location in the Read Data FIFO constitutes the data read from the memory. For a burst length of four, two locations in the Read Data FIFO constitute the data read from the memory. For a burst length of eight, four locations in the Read Data FIFO constitute the data read from the memory.

[Table 6-6](#) defines the configuration of the Read Data FIFO for the selected memory data width of 36 bits.

Table 6-6: Read Data FIFO Bit Configuration for a 36-bit Data Width

Bit Configuration	Description
[71:0]	Read Data

Clock Generator

The clock generator module generates the FPGA clock and reset signals. When differential clocking is used, sysclk_p, sysclk_n, clk200_p, and clk200_n signals appear. When single-ended clocking is used, sysclk and idly_clk_200 signals appear. In addition, clocks are available for design use and a 200 MHz clock is provided for the IDELAYCTRL primitive. Differential and single-ended clocks are passed through global clock buffers before connecting to a DCM. For differential clocking, the output of the sysclk_p/sysclk_n buffer is single-ended and is provided to the DCM input. Likewise, for single-ended clocking, sysclk is passed through a buffer and its output is provided to the DCM input. The outputs of the DCM are clkglob (0° phase-shifted version of the input clock) and clk90 (90° phase-shifted version of the input clock). After the DCM is locked, the design is in the reset state for at least 25 clocks. The RLDRAM II controller works using these clocks.

Reset Generator

This block generates different reset signals. It also performs the initialization and configuration (MRS) of the RLDRAM II memories.

Control Logic

The logic in this block controls NOP, READ, WRITE, and USER REFRESH operations with the memories. The RLDRAM II memory controller is triggered with data in the Address FIFO. Bit 24 of the Address FIFO discriminates between read and write commands. Bit 25 is the USER REFRESH command. If the auto refresh bit is ON, the controller generates the AUTO REFRESH command periodically. The controller issues a read or a write grant only when there is no user refresh request command or no pending internal refresh request. If there is a pending refresh request, the RLDRAM II memory controller issues the read or the write grant after the refresh is done.

Clocking Scheme

Figure 6-8, page 267 shows the clocking scheme for this design. Global and local clock resources are used.

The global clock resources consist of a DCM, two BUFGs on DCM output clocks, and one BUFG for clk_200. The local clock resources consist of regional I/O clock networks (BUFIO). The global clock architecture is discussed in this section.

The MIG tool allows the user to customize the design such that the DCM is not included. In this case, clkglob and clk90 must be supplied by the user.

Global Clock Architecture

The user must supply two input clocks to the design:

- A system clock running at the target frequency for the memory
- A 200 MHz clock for the IDELAYCTRL blocks.

These clocks can be either single ended or differential. User can select single ended or differential clock input option from MIG GUI. Differential clocks are connected to the IBUFGDS and single ended clock is connected to IBUFG.

The system clock from the output of the IBUFGDS or the IBUFG is connected to the DCM to generate the various clocks used by the memory interface logic.

The clk_200 output of the IBUFGDS or the IBUFG is connected to the BUFG. The output of the BUFG is used for IDELAY IOB delay blocks for aligning read capture data.

The DCM generates three separate synchronous clocks for use in the design. This is shown in Table 6-7 and Figure 6-8, page 267. The clock structure is same for both example design and user design. For designs with out DCM instantiation, DCM and the BUFGs should be instantiated at user end to generate the required clocks.

Table 6-7: RLDRAM II Interface Design Clocks

Clock	Description	Logic Domain
clkglob	Skew compensated replica of the input system clock.	The clock for the controller and the user interface logic. The RLDRAM II bus-related I/O flip-flops (e.g., memory clocks). This clock is used to register the data, address, and command signals, and the address and data enables for the user interface logic ⁽¹⁾ . This clock is also used to generate the read data, read data valid, and FIFO status signals.
clk90	90° phase-shifted version of clkglob	Used in the write data path section of physical layer. Clocks write path control logic, RLDRAM II side of the Write Data FIFO, and output flip-flops for D and memory control and address signals.

Notes:

1. See "User Interface Accesses," page 271 for timing requirements and restrictions on the user interface signals.

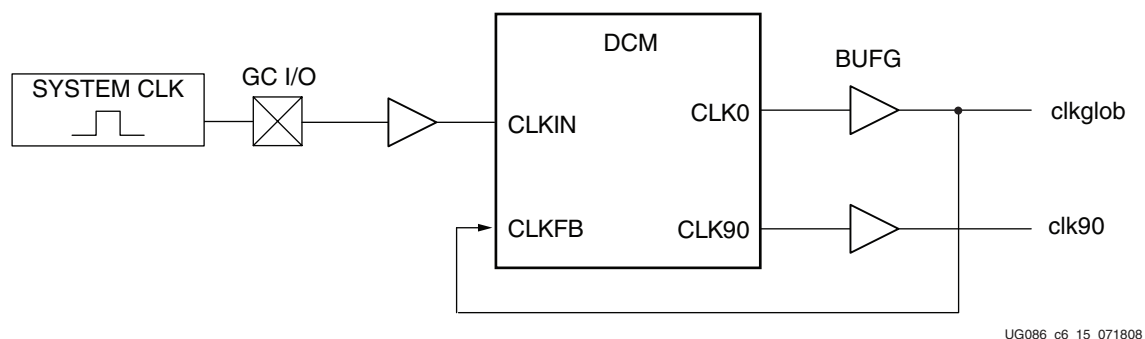


Figure 6-8: Clocking Scheme for RLDRAM II Interface Logic

RLDRAM II Control Signal Physical Layer

This block has the pads that interface with the RLDRAM II data signals. A calibration circuit samples the QK/ $\overline{\text{QK}}$ signals using the ChipSync™ technology feature of the

Virtex-4 FPGA. The FPGA clock samples both the data and clock (for calibration) and the data itself to capture it in the same clock domain. Refer to XAPP701 [Ref 18] for more details.

RLDRAM II Interface Signals

Table 6-8 and Table 6-9 define the RLDram II system interface signals with and without a DCM, respectively.

Table 6-8: RLDram II System Interface Signals (with a DCM)

Signal Name	Direction	Description
sysclk_p, sysclk_n	Input	System clock input made up of differential clock pairs. This clock pair goes to a differential input buffer. The differential buffer output goes to the DCM input. The DCM generates the required clocks for the design. This input system clock pair is present only when the DIFFERENTIAL clocks option is selected in the MIG FPGA options page.
sysclk	Input	Single-ended system clock input. This clock is an input to IBUFG. The IBUFG output is connected to the DCM clock input. The DCM generates the required clocks for the design. This input system clock is present only when the SINGLE_ENDED clocks option is selected in the MIG FPGA options page. When the DCM option is deselected, both differential or single-ended input system clocks are not present.
clk200_p, clk200_n	Input	Differential clock used in the idelay_ctrl logic. This input clock pair is present only when the DIFFERENTIAL clocks option is selected in the MIG FPGA options page.
idly_clk_200	Input	Single-ended 200 MHz IDELAYCTRL clock input. This clock is connected to an IBUFG. The IBUFG output is connected to input of BUFG. The output of this BUFG acts as IDELAYCTRL clock input. This input system clock is present only when the SINGLE_ENDED clocks option is selected in the MIG FPGA options page. When the DCM option is deselected, both differential and single-ended input system clocks are not present.
sysreset_n	Input	Active-Low reset to the RLDram II controller.
pass_fail[2:0]	Output	This signal bus indicates the status the comparison between the read data compared with the corresponding write data. 001: INITIALIZATION STATE 010: PASS 100: FAIL
init_done	Output	This signal is asserted when the design initialization and calibration is complete.

Table 6-9: RLDram II System Interface Signals (without a DCM)

Signal Name	Direction	Description
clkglob	Input	Input clock
clk90	Input	Input clock with a 90° phase difference

Table 6-9: RLDRAM II System Interface Signals (without a DCM) (Cont'd)

Signal Name	Direction	Description
clk_200	Input	200 MHz clock for Idelayctrl primitives
dcm_locked	Input	This active-High signal indicates whether the user DCM is locked or not
sysreset_n	Input	Active-Low reset to the RLDRAM II controller
pass_fail[2:0]	Output	This signal bus indicates the status the comparison between the read data compared with the corresponding write data. 001: INITIALIZATION STATE 010: PASS 100: FAIL
init_done	Output	This signal is asserted when the design initialization and calibration is complete

Table 6-10 describes the RLDRAM II user interface signals.

Table 6-10: RLDRAM II User Interface Signals (without a Testbench)

Signal Name ⁽¹⁾	Direction	Description
rlwdfull	Output	Almost full status signal for the Write Data FIFO. When this signal is asserted, the user can write three more data words into the FIFO.
rlaffull	Output	Almost full status signal for the Address FIFO. When this signal is asserted, the user can write two more data words into the FIFO.
rlafempty	Output	Empty status signal for the Address FIFO
rlrdfempty	Output	Empty status signal for the Read Data FIFO
rlwdfempty	Output	Empty status signal for the Write Data FIFO
apaddr[25:0] ⁽²⁾	Input	Address FIFO data input. This bus consists of the user-defined bank address, the address, the WRITE/READ command, and the user-defined REFRESH command.
apvalid	Input	Address FIFO write-enable signal
apwritedvalid	Input	Write Data FIFO write-enable signal
aprdrden	Input	Read enable for the Read Data FIFO
burstlength[1:0]	Output	Indicates the number of bursts that can be written to or read from the memory: 00: Burst length = 2 01: Burst length = 4 10: Burst length = 8
rldreaddata[(2*n)-1:0]	Output	Read data from the memory, where n is the data width of the design. This read data is stored in the Read Data FIFOs and can be read from the FIFOs depending upon the status of the FIFOs.
apwritedata[(2*n)-1:0]	Input	Write data to be written into the memory, where n is the data width of the design. This data is stored in the Write Data FIFO and is written into the memory depending upon the controller status (write command).
apwritedm[m-1:0]	Input	Data mask of the write data, where m is the number of data mask bits associated with the write data width.
clkglob_tb	Output	clkglob clock input. All the corresponding signals must be synchronized with clkglob_tb. The clkglob_tb clock is sourced from clkglob clock in the controller.

Table 6-10: RLDRAM II User Interface Signals (without a Testbench) (Cont'd)

Signal Name ⁽¹⁾	Direction	Description
rsthard_tb	Output	Active-Low system reset for the user interface, synchronous with clkglob_tb.
init_done_tb	Output	When asserted, this signal indicates that memory initialization is complete.
issuemrs_tb	Input	A pulse on this input makes the controller program the Mode Register into the memory. This signal is synchronous with clkglob. (At power-up, MRS is done as part of the initialization.)

Notes:

1. All user interface signal names are prepended with a controller number, for example, cntrl0_apWriteData. RLDRAM II devices currently support only one controller. See "User Interface Accesses" for timing requirements and restrictions on the user interface signals.
2. The number of address bits used depends on the density of the memory part. The controller ignores the unused bits, which can all be tied High.

Table 6-11 describes the RLDRAM II memory interface signals.

Table 6-11: RLDRAM II Memory Interface Signals

Signal Name	Direction	Description
rld2_dq (cio)	Input/ Output	Data input/outputs. During READ commands, the data is captured using the FPGA clock. During WRITE commands, the data is sampled on both edges of DK.
rld2_d (sio)	Output	Write data
rld2_q (sio)	Input	Read data
rld2_a	Output	Row and column addresses for READ and WRITE operations. During a MODE REGISTER SET command, the address inputs define the register settings.
rld2_ba	Output	These bank addresses select the internal bank to which to apply commands.
rld2_we_n	Output	Write-enable command
rld2_ref_n	Output	REFRESH command
rld2_cs_n	Output	Chip-select command
rld2_dm	Output	Data mask signals for the write data
rld2_qvld	Input	Data valid signals transmitted by the RLDRAM II devices. They indicate valid read data.
rld2_qk, rld2_qk_n	Input	Differential read data clocks. These clocks are transmitted by the RLDRAM II devices and are edge-aligned with the read data.
rld2_dk, rld2_dk_n	Output	Differential write data clocks.
rld2_ck, rld2_ck_n	Output	Master differential clocks for addresses and commands.

User Command Interface

The current implementation supports commands that come in successive clocks with one extra clock latency.

User Interface Accesses

The user backend logic communicates with the memory controller through a FIFO-based user interface. This interface consists of three related buses:

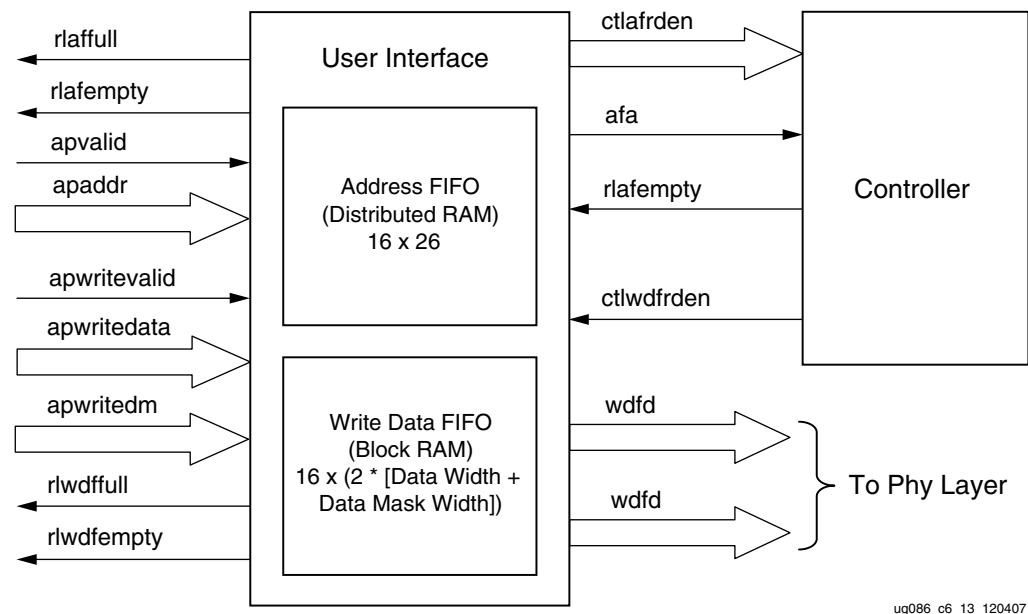
- A Command/ Address FIFO bus accepts write/read commands as well as the corresponding memory address from the user
- A Write Data FIFO bus accepts the corresponding write data when the user issues a write command on the command/address bus
- A Read bus on which the corresponding read data for an issued read command is returned

The user interface has the following timing and signaling restrictions:

- Commands and write data cannot be written by the user until calibration is complete (as indicated by `init_done`). In addition, the `apvalid` and `app_wdf_wren` interface signals need to be held Low until calibration is complete.
- When issuing a write command, the first write data word must be written to the Write Data FIFO either prior to or on the same clock cycle as the write command is issued. In addition, the write data must be written by the user over consecutive clock cycles; there cannot be a break between words. These restrictions arise from the fact that the controller assumes write data is available when it receives the write command from the user.
- The `clkglob_tb` signal is connected to `clkglob` in the controller. If the user clock domain is different from `clkglob` / `clkglob_tb` of MIG, the user should add FIFOs for all data inputs and outputs of the controller in order to synchronize them to the `clkglob_tb`.

Write Interface

Figure 6-9 shows the user interface block diagram for write operations.



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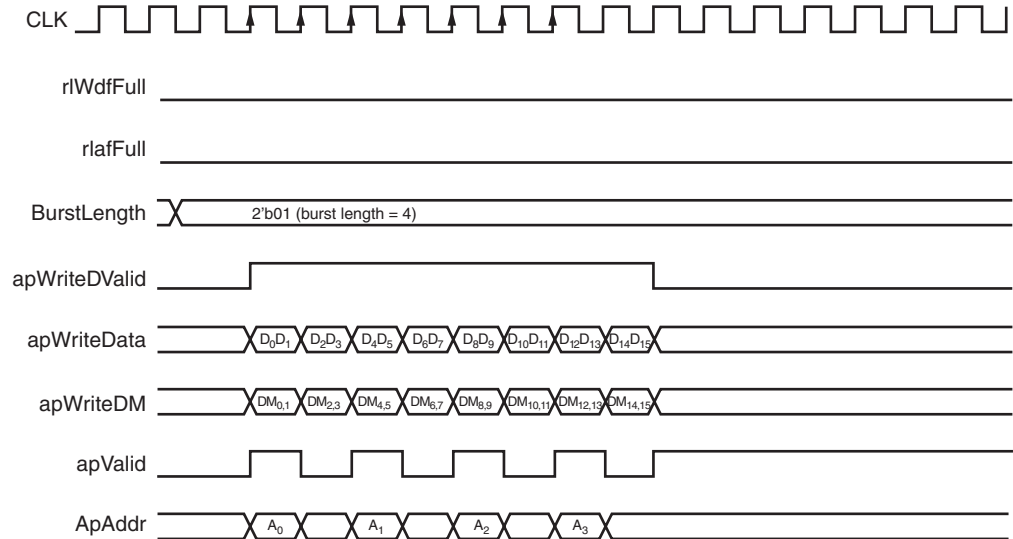
Figure 6-9: User Interface Block Diagram for Write Operations

The following steps describe the architecture of the Address and Write Data FIFOs and show how to perform a write burst operation to RLDRAM II from the user interface.

1. The user interface consists of an Address FIFO and a Write Data FIFO. These FIFOs are constructed using the FIFO generator module of the CORE Generator software. Address FIFO is a distributed RAM with 16 x 26 configuration. Data FIFO is a block RAM, with a depth of 16 locations and width equal to two times the data width and data mask width together.
2. The Common Address FIFO is used for both write and read commands, and comprises a command part and an address part. Command bits discriminate between write and read commands.
3. User interface data width apwritedata is twice that of the memory data width. For every memory component there is a mask bit. For 9-bit memory width, the user interface is 20 bits consisting of rising-edge data, falling-edge data, rising-edge mask bit, and falling-edge mask bit.
4. For a 9-bit memory component with 72-bit data, the user interface data width apwritedata is 144 bits, and the mask data apwritedm is 8 bits.
5. The user can initiate a write to memory by writing to the Address FIFO and the Write Data FIFO when the FIFO Full flags are deasserted and after the init_done signal is asserted. Status signal rlafull is asserted when Address FIFO is full, and similarly rlwdfull is asserted when Write Data FIFO is full.
6. Both the Address FIFO and Write Data FIFO Full flags are deasserted with power-on.
7. The user should assert the Address FIFO write-enable signal apvalid along with address apaddr to store the write address and write command into the Address FIFO.
8. The user should assert the Data FIFO write-enable signal apwritedata valid along with write data apwritedata and mask data apwritedm to store the write data and mask

data into the Write Data FIFO. The user should provide both rise and fall data together for each write to the Data FIFO.

9. The controller reads the Address FIFO by issuing the `ctlafrden` signal. The controller reads the Write Data FIFO by issuing the `ctlwdfdrden` signal after the Address FIFO is read. It decodes the command part after the Address FIFO is read.



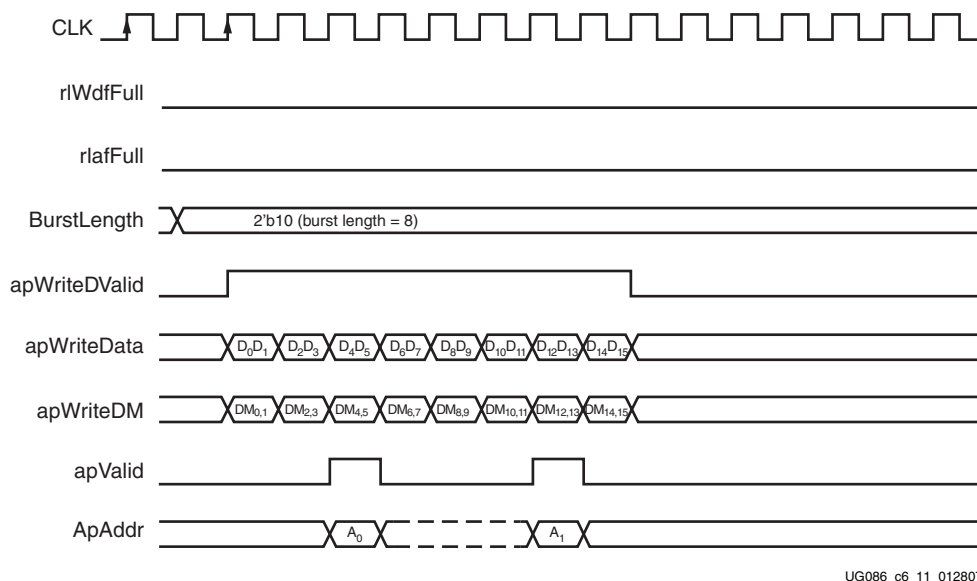
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Figure 6-10: RLDram II Write Burst Timing Diagram (BL = 4), Four Bursts

10. The write command timing diagram in Figure 6-10 is derived from the MIG-generated testbench. As shown (burst length of 4), each write to the Address FIFO must be coupled with two writes to the Data FIFO. Similarly, for a burst length of 8, every write to the Address FIFO must be coupled with four writes to the Data FIFO. Failure to follow this rule can cause unpredictable behavior.

Note: The user can start filling the Write Data FIFO two clocks after the Address FIFO is written, because there is a two-clock latency between the command fetch and reading the Data FIFO. Using the terms shown in Figure 6-9, therefore, the user can assert the A0 address two clocks before D0D1.

11. The write command timing diagram in Figure 6-11, page 274 is derived from the MIG-generated testbench. As shown (burst length of 8), each write to the Address FIFO must be coupled with four writes to the Data FIFO. Because the controller first reads the address and command together, the address need not coincide with the last data. After the command is analyzed (nearly two clocks later for a worst-case timing scenario), the controller sequentially reads the data in four clocks. Thus, there are six clocks from the time the address is read to the time the last data is read.

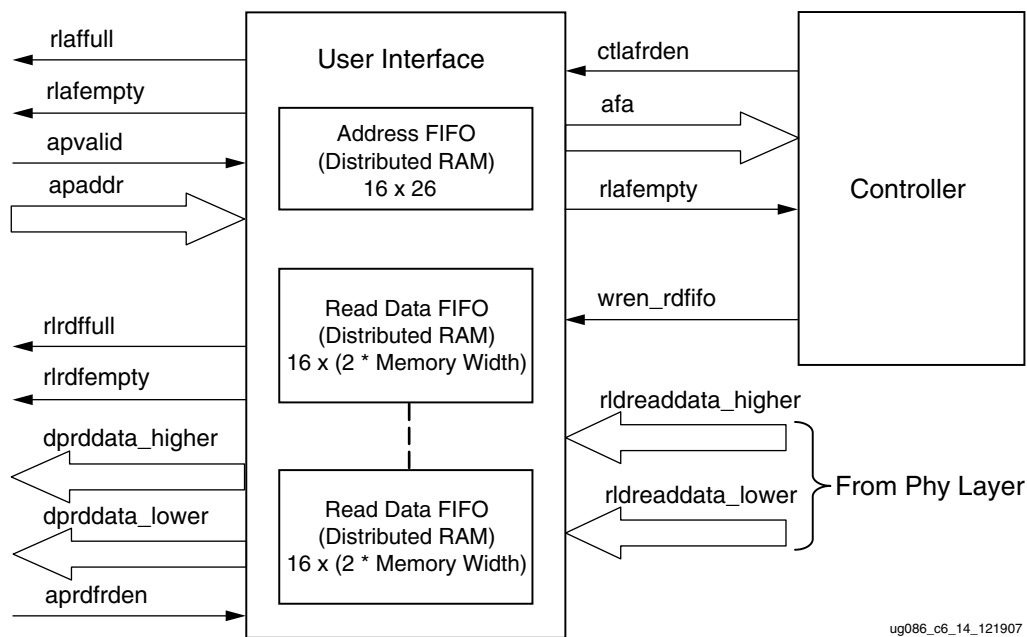


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Figure 6-11: RLDRAM II Write Burst Timing Diagram (BL = 8), Two Bursts

Read Interface

Figure 6-12 shows a block diagram of the read interface.



ug086_c6_14_121907

Figure 6-12: User Interface Block Diagram for Read Operations

The following steps describe the architecture of the Read Data FIFOs and show how to perform a burst read operation from RLDRAM II from the user interface.

1. The read user interface consists of an Address FIFO and a Read Data FIFO. The Address FIFO is common to both read and write operations. The Read Data FIFOs are constructed using the CORE Generator FIFO generator module. The Read Data FIFO is a Distributed RAM with depth of 16 locations and width equal to two times the

memory device width, consisting of rising-edge data and falling-edge data. For example, for a 9-bit memory component, the Read Data FIFO configuration is 16 x 18. MIG instantiates a number of Read Data FIFO modules depending on the QK signal width of the design. For example, for 9-bit memory component and 72-bit data width designs, MIG instantiates a total of nine Read Data FIFO modules.

2. The user can initiate a read to memory by writing to the Address FIFO when the FIFO Full flag `rlaffull` is deasserted and after `init_done` is asserted.
3. To write the read address and read command into the Address FIFO, the user should issue the Address FIFO write-enable signal `apvalid` along with read address `apaddr`.
4. The controller reads the Address FIFO containing the address and command. After decoding the command, the controller generates the appropriate control signals to memory.
5. Prior to the actual read and write commands, the design calibrates the latency (number of clock cycles) from the time the read command is issued to the time data is received. Using this pre-calibrated delay information, the controller generates the write-enable signals to the Read Data FIFOs.
6. The `rlrdfempty` signal is deasserted when data is available in the Read Data FIFOs.
7. The user can read the read data from the Read Data FIFOs by asserting `aprdfrden` to High.

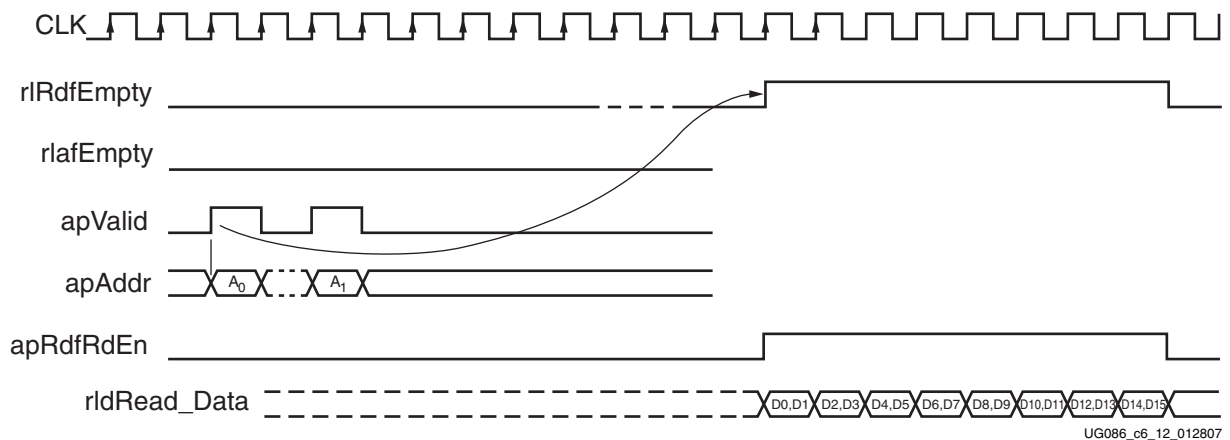


Figure 6-13: RLDRAM II Read Burst Timing Diagram (BL = 8), Two Bursts

8. Figure 6-13 shows the user interface timing diagram for a burst length of 8. The read latency is calculated from the point when the read command is given by the user to the point when the `rlrdfempty` signal is deasserted. The minimum latency in this case is 21 clocks. Where no auto-refresh request is pending, the user commands are issued after initialization is completed, and the first command issued is a Read command. The controller executes the commands only after initialization is done, as indicated by the `init_done` signal.
9. After the address and command are loaded into the Address FIFO, it takes 21 clock cycles minimum for the controller to deassert the `rlrdfempty` signal.
10. Read data is available only when the `rlrdfempty` signal is deasserted. The user can access the read data by asserting the `aprdfrden` signal, a read enable signal to the Read Data FIFOs, to High.

Note: The RLDRAM controller does not check the status of the Read Data FIFO, and can issue read commands even when the Read Data FIFO is full. The user must make this determination and ensure that read commands are not issued by the controller when the Read Data FIFO is full.

Table 6-12: Read Command Latency

Parameter	Number of Clocks	Description
User command to deassertion of the Address FIFO empty flag	1	When the read command is given to an empty FIFO, it takes one clock time to deassert the empty flag
Controller command reading and decoding time	3	The FIFO outputs the data one clock after the read command. Two clocks for decoding the command.
Command from the controller to the controller IOB's output	3	Three-stage pipeline
RLDRAM II command to read data latency (max)	8	RLDRAM II worst-case latency
Read data from the IOB to dq_iob	2	Two-stage pipeline from IOB to dq_iob
dq_iob output to Read Data FIFO input	2	Two-stage pipeline
Read Data FIFO input to Read Data FIFO output	2	One clock for deassertion of empty signal, and one clock for outputting the data
Total Latency	21	Total of all latencies

In general, read latency varies based on the following parameters:

- Configuration
- The number of commands already in the FIFO pipeline before the read command is issued
- Whether commands are interrupted when the periodic AUTO REFRESH command is issued
- Whether the user issues the commands before initialization is complete (if so, the latency cannot be determined)
- Board-level and chip-level propagation delays for both memory and FPGA

RLDRAM II Signal Allocations

MIG shows the checkboxes listed in Table 6-13 when a bank is selected for an RLDRAM II design.

Table 6-13: RLDRAM II Signal Allocation

Bank Selected by Checkbox	Signals Allocated in the Group
Address	Memory address, memory control, and memory clocks
Data (CIO)	Memory data and memory data mask
Data_Write (SIO)	Memory write data, memory data mask, and memory write clocks
Data_Read (SIO)	Memory read data, memory QVLD, and memory read clocks

Table 6-13: RLDRAM II Signal Allocation (Cont'd)

Bank Selected by Checkbox	Signals Allocated in the Group
System Control	System reset from the user interface and status signals
System Clock	System clocks from the user interface

When the Address box is checked in a particular bank, the bank address, the address, the WE_N, the REF_N, and the CS_N bits are assigned to that particular bank.

When the Data box is checked in a particular bank for a CIO design, the memory data, the memory data mask, the memory data valid (QVLD), the memory read clock, the memory write clock, the memory address, and the command clock bits are assigned to that particular bank.

When the Data_Write box is checked in a particular bank for an SIO design, the memory data write, the memory data mask, and the memory write clock bits are assigned to that particular bank.

When the Data_Read box is checked in a particular bank for an SIO design, the memory data read, the memory data valid (QVLD), the memory read clock, the memory address, and the command clock bits are assigned to that particular bank.

When the System Control box is checked in a particular bank, the sysreset_n, the pass_fail, and the Init_done bits are assigned to that particular bank.

When the System Clock box is checked in a particular bank, the sysclk_p, sysclk_n, CLK200_p, and CLK200_n bits are assigned to that particular bank.

For special cases, such as without a testbench and without a DCM, the corresponding input and output ports are not assigned to any FPGA pins in the design UCF because the user can connect these ports to the FPGA pins or can connect to some logic internal to the same FPGA.

Note: Timing has been verified for most of the MIG generated configurations. For the best timing results, adjacent banks in the same column of the FPGA should be used. Banks that are separated by unbonded banks should be avoided because these can cause timing violations.

Simulating the RLDRAM II Design

After generating the design, MIG creates a `sim` folder in the specified path. This folder contains simulation files for a particular design. The `sim` folder contains the external testbench, memory model, and `.do` file to simulate the generated design. The memory model files are currently generated in Verilog only. To learn more details about the files in the `sim` folder and to simulate the design, refer to “[Simulation Guide](#),” page 499.

While simulating VHDL designs, the XilinxCoreLib library needs to be mapped. This is used by the `fifo_generator_v5_3.vhd` module present in the `sim` directory. An example mapping is shown here for reference:

```
vmap xilinxcorelib
/proj/xbuils/c/libs/M.53c.0/modelsim/6.5c/lin64/lib/xilinxcorelib
```

Hardware Tested Configurations

The frequencies shown in [Table 6-14](#) were achieved on the Virtex-4 FPGA ML461 Memory Interfaces Development Board under nominal conditions. This frequency should not be used to determine the maximum design frequency. The maximum design frequency supported in the MIG wizard is based on a combination of the TRCE results for fabric timing on multiple device/package combinations and I/O timing analysis using FPGA and memory timing parameters for a 72-bit wide interface.

Table 6-14: Hardware Tested Configurations

FPGA Device	XC4VLX25-FF668-11
Memory Component	MT49H16M18XX-25
Data Bus Options	CIO
Data Width	36
Configuration	1, 2, 3
Burst Length	2, 4, 8
Addressing Mode	Multiplexing and Non-Multiplexing Addressing mode
Frequency	120 MHz to 330 MHz
Flow Vendors	Synplicity and XST
Design Entry	VHDL and Verilog



Section III: Spartan-3/3E/3A/3AN/3A DSP FPGA to Memory Interfaces

Chapter 7, "Implementing DDR SDRAM Controllers"

Chapter 8, "Implementing DDR2 SDRAM Controllers"

Implementing DDR SDRAM Controllers

This chapter describes how to implement DDR SDRAM interfaces for Spartan®-3, Spartan-3E, Spartan-3A, Spartan-3AN, and Spartan-3A DSP FPGAs. The designs are based on XAPP768c [Ref 24].

Feature Summary

This section summarizes the supported and unsupported features of the DDR SDRAM controller design.

Supported Features

The DDR SDRAM controller design supports the following:

- Burst lengths of two, four, and eight
- CAS latencies of 2, 2.5, and 3
- Sequential and interleaved burst types
- Auto refresh
- Data mask enable/disable option
- System clock, differential and single-ended
- Linear addressing
- Spartan-3 FPGA maximum frequency:
 - 133 MHz with a -4 speed grade device
 - 166 MHz with a -5 speed grade device
- Spartan-3E FPGA maximum frequency:
 - 133 MHz with a -4 speed grade device
 - 166 MHz with a -5 speed grade device
- Spartan-3A, Spartan-3AN, and Spartan-3A DSP FPGA maximum frequency:
 - 133 MHz with a -4 speed grade device
 - 166 MHz with a -5 speed grade device
- Components, unbuffered DIMMs, registered DIMMs, and SODIMMs
- With and without a testbench
- With or without a DCM
- All Spartan-3, Spartan-3E, Spartan-3A, Spartan-3AN, and Spartan-3A DSP FPGAs
- Verilog and VHDL
- XST and Synplicity synthesis tools

Unsupported Features

Single burst of burst length two.

Design Frequency Ranges

Table 7-1: Design Frequency Range in MHz

FPGA Family	Memory	FPGA Speed Grade			
		-4		-5	
		Min	Max	Min	Max
Spartan-3	Component	77	133	77	166 ⁽¹⁾
	DIMM	77	133	77	133
Spartan-3A/3AN/3A DSP	Component	77	133	77	166
	DIMM	77	133	77	166
Spartan-3E	Component	77	133	77	166
	DIMM	(Not supported)			

Notes:

1. Spartan-3 devices support 133 MHz for data widths greater than 32 bits.

Controller Architecture

DDR SDRAM Interface

High-speed memory interfaces are source-synchronous and double data rate. They transfer data on both edges of the clock cycle. A memory interface can be modularly represented as shown in [Figure 7-1](#). Creating a modular interface has many advantages. It allows designs to be ported easily, and it also makes sharing parts of the design across different types of memory interfaces possible.

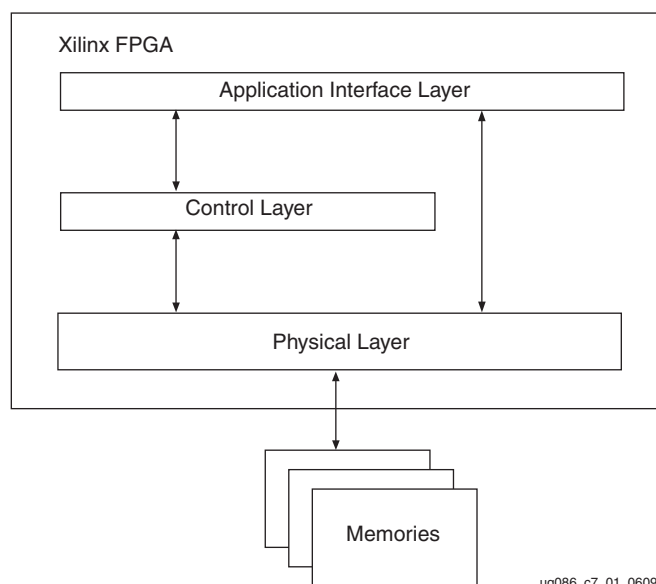
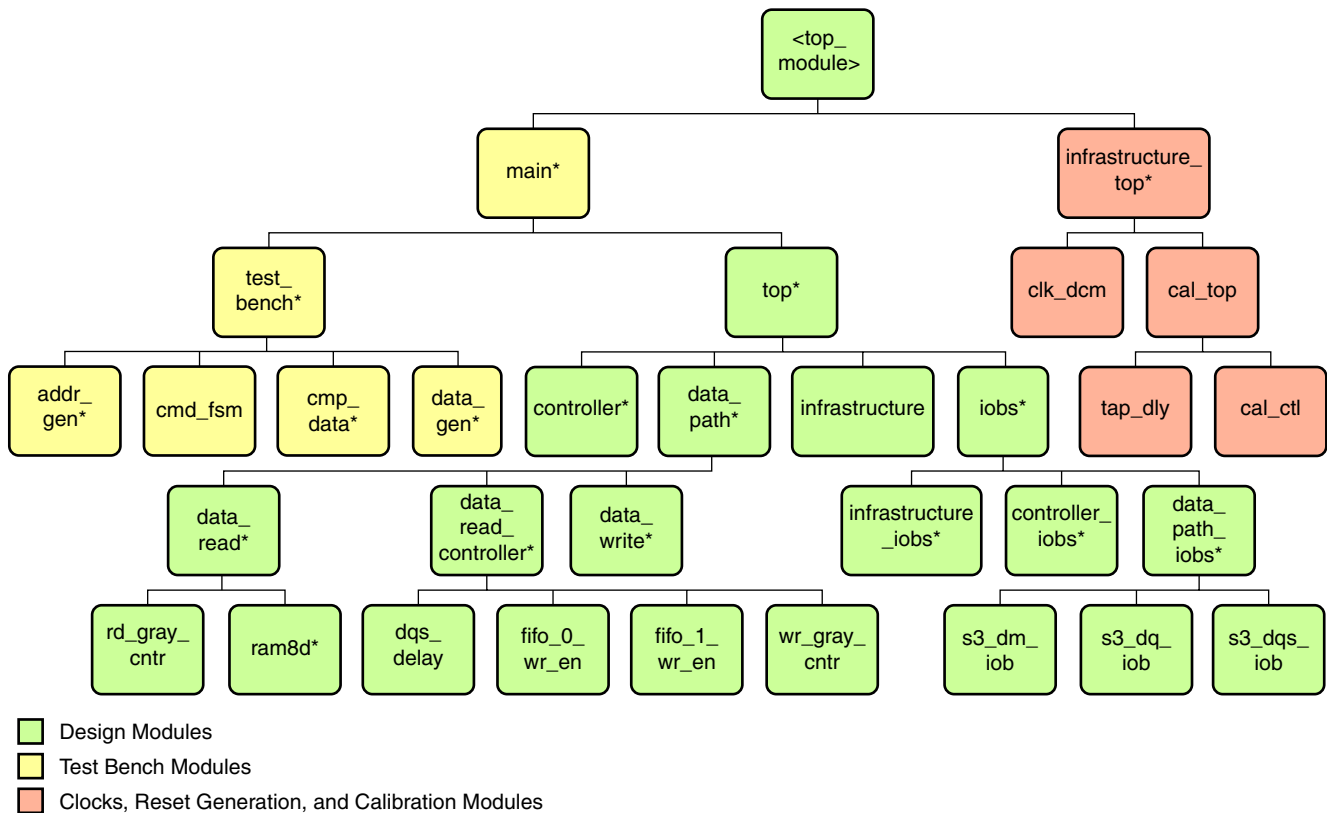


Figure 7-1: **Modular Memory Interface Representation**

Hierarchy

Figure 7-2 shows the hierarchical structure of the DDR SDRAM design generated by MIG with a testbench and a DCM. In the figure, the physical and control layers are clearly separated. MIG generates the entire controller, as shown in this hierarchy, including the testbench. The user can replace the testbench with a design that makes use of the DDR SDRAM interface.



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Figure 7-2: Hierarchical Structure of the DDR SDRAM Design with a Testbench

The modules are classified as follows:

- Design modules
- Testbench modules
- Clocks, reset generation, and calibration modules

There is a parameter file generated with the design that has all the user input and design parameters selected from MIG.

MIG can generate four different DDR SDRAM designs:

- With a testbench and a DCM
- Without a testbench and with a DCM
- With a testbench and without a DCM
- Without a testbench and without a DCM

For designs generated without a testbench, the testbench modules in [Figure 7-2](#) are not present in the design. In this case, the user interface signals appear in the <top_module> module. The list of user interface signals is in [Table 7-9](#).

The infrastructure_top module has the clock and the reset generation module of the design. It instantiates a DCM in the module when selected by MIG. The differential design clock is an input to this module. A user reset is also input to this module. Using the input clocks and reset signals, system clocks and system reset are generated in this module which is used in the design. Infrastructure_top also consists of calibration logic.

The DCM primitive is not instantiated in the infrastructure_top module if the **Use DCM** option is unchecked. Therefore, the system operates on the user-provided clocks. The system reset is generated in the infrastructure module using the dcm_lock input signal.

MIG Tool Design Options

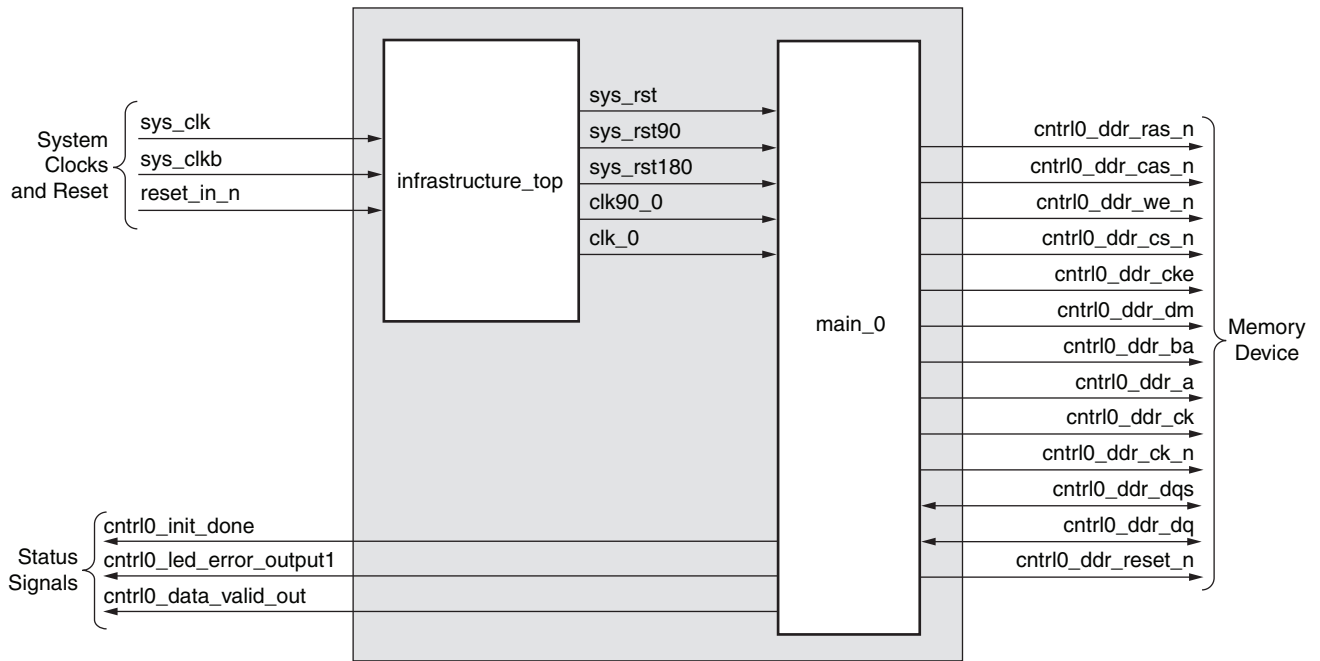
MIG provides various options to generate the design with or without a testbench or with or without a DCM. This section provides detailed descriptions of the type of design generated by the user using various options. [Figure 7-3, page 286](#) and [Figure 7-4, page 287](#) show the differential system clock. For more information on the clocking structure, refer to “Clocking Scheme,” [page 294](#).

MIG outputs example_design and user_design. The MIG-generated example_design includes the memory controller and synthesized testbench. The example_design can be used to simulate the design and to test its functionality. Whereas the user_design includes the memory controller design only. Users should develop a testbench (user application) and should interface with the MIG memory controller design. Refer to [Table 7-9, page 297](#) for user interface signals and “DDR SDRAM Write and Read Operations,” [page 300](#) for write and read timing shown in [Figure 7-10, page 301](#) and [Figure 7-11, page 302](#).

[Figure 7-3, page 286](#) shows a block diagram representation of the top-level module of a DDR SDRAM design with a DCM and a testbench. “Clocking Scheme,” [page 294](#) describes how various clocks are generated using the DCM. The input clocks can be differential or single-ended based on the system clock selection in GUI.

For differential, differential clocks sys_clk and sys_clkb appear as input ports, whereas for single-ended sys_clk_in appears as input port. The DCM clock is instantiated in the infrastructure_top module that generates the required design clocks. The reset_in_n signal is the active-Low system reset signal. All design resets are gated by the dcm_lock signal.

The cntrl0_led_error_output1 output signal indicates whether the test passes or fails. When set, this signal indicates that the test has failed. The testbench module does writes and reads, and also compares the read data with the written data. The cntrl0_data_valid_out signal indicates whether the read data is valid or not.



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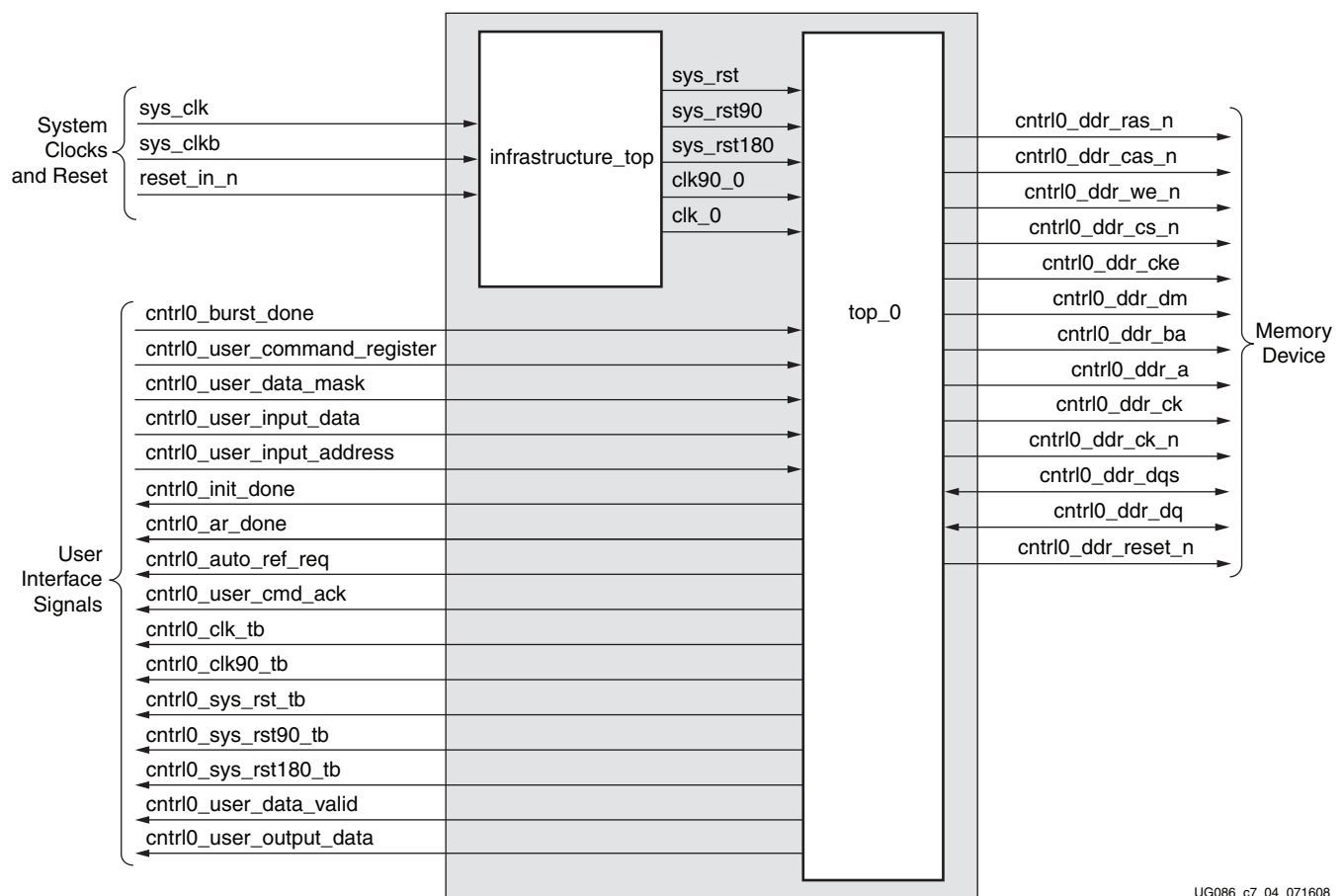
Figure 7-3: MIG Output of the DDR SDRAM Controller Design with a DCM and a Testbench

Figure 7-4 shows a block diagram representation of the top-level module for a DDR SDRAM design with a DCM but without a testbench. “Clocking Scheme,” page 294 describes how various clocks are generated using the DCM. The input clocks can be differential or single-ended based on system clock selection in GUI.

For differential, differential clocks `sys_clk` and `sys_clkb` appear as input ports, whereas for single-ended `sys_clk_in` appears as input port.

The DCM clock is instantiated in the `infrastructure_top` module that generates the required design clocks. `reset_in_n` is the active-Low system reset signal. All design resets are gated by the `dcm_lock` signal.

The user interface signals are listed in Figure 7-4. The design provides the `clk_tb`, `clk90_tb`, `sys_rst_tb`, `sys_rst90_tb`, and `sys_rst180_tb` signals to the user in order to synchronize with the design. The signals `clk_tb`, `clk90_tb`, `sys_rst_tb`, `sys_rst90_tb`, and `sys_rst180_tb` are connected to clocks `clk_0` and `clk90_0` and reset signals `sys_rst`, `sys_rst90`, and `sys_rst180`, respectively, in the controller. If the user clock domain is different from `clk_tb/clk90_tb`, then the user should add FIFOs for all the inputs and outputs of the controller (user application signals) in order to synchronize them to `clk_tb/clk90_tb`.

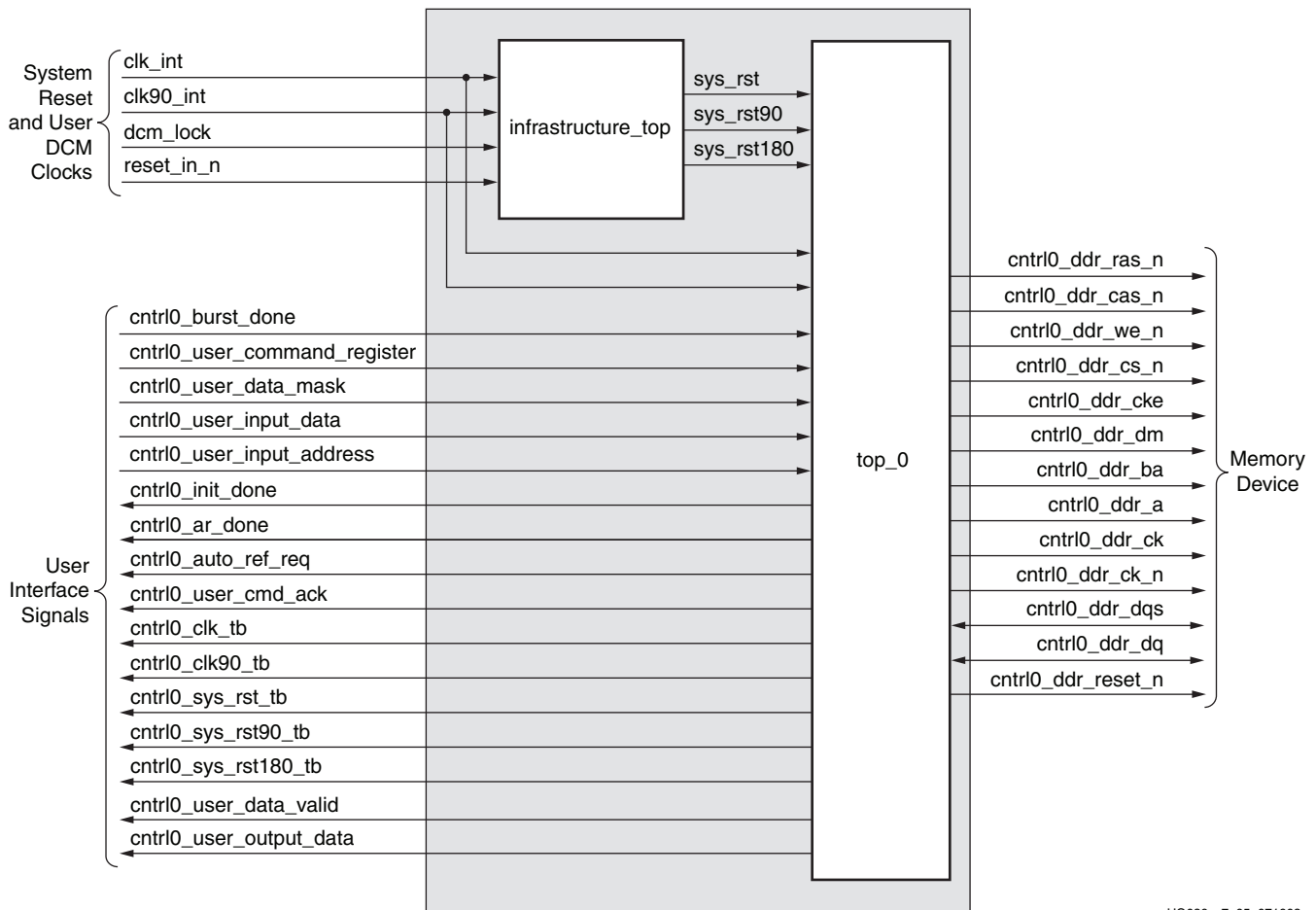


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Figure 7-4: MIG Output of the DDR SDRAM Controller Design with a DCM but without a Testbench

Figure 7-5 shows a block diagram representation of the top-level module for a DDR SDRAM design without a DCM or a testbench. “Clocking Scheme,” page 294 describes how various clocks are generated using the DCM. The user should provide all the clocks and the dcm_lock signal. These clocks should be single-ended. reset_in_n is the active-Low system reset signal. All design resets are gated by the dcm_lock signal. All design resets are gated by the dcm_lock signal.

The user interface signals are listed in Figure 7-5. The design provides the clk_tb, clk90_tb, sys_rst_tb, sys_rst90_tb, and sys_rst180_tb signals to the user in order to synchronize with the design. The signals clk_tb, clk90_tb, sys_rst_tb, sys_rst90_tb, and sys_rst180_tb are connected to clocks clk_0 and clk90_0 and reset signals sys_rst, sys_rst90, and sys_rst180, respectively, in the controller. If the user clock domain is different from clk_tb/clk90_tb, then the user should add FIFOs for all the inputs and outputs of the controller (user application signals) in order to synchronize them to clk_tb/clk90_tb.



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Figure 7-5: MIG Output of the DDR SDRAM Controller Design without a DCM or a Testbench

Figure 7-6 shows a block diagram representation of the top-level module of a DDR SDRAM design without a DCM but with a testbench. “Clocking Scheme,” page 294 describes how various clocks are generated using the DCM. The user should provide all the clocks and the dcm_lock signal. These clocks should be single-ended. reset_in_n is the active-Low system reset signal. All design resets are gated by the dcm_lock signal.

The cntrl0_led_error_output1 output signal indicates whether the test passes or fails. The testbench module does writes and reads, and also compares the read data with the written data. The cntrl0_led_error_output1 signal is driven High on data mismatches. The cntrl0_data_valid_out signal indicates whether the read data is valid or not.

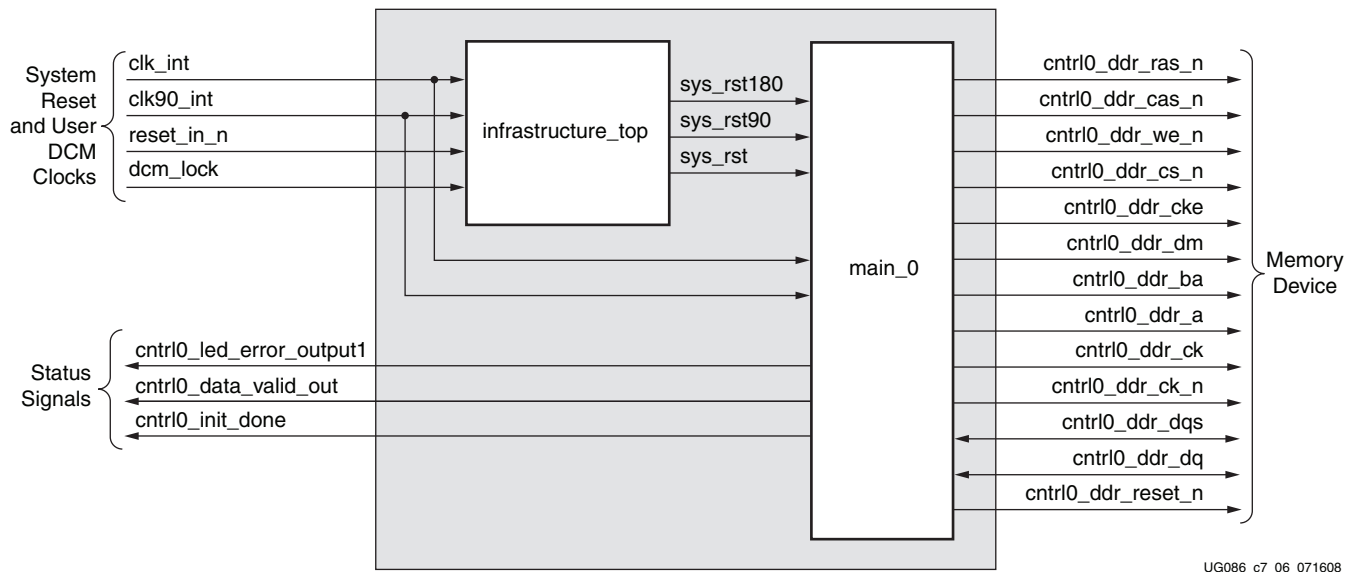


Figure 7-6: MIG Output of the DDR SDRAM Controller Design without a DCM but with a Testbench

All the memory device interface signals shown in Figure 7-3 through Figure 7-6 might not necessarily appear for all designs generated from MIG. For example, the cntrl0_ddr_reset_n port appears in the port list for Registered DIMM designs only. Similarly, cntrl0_ddr_dm appears only for parts that have data mask signals. A few RDIMMs do not have data mask, and cntrl0_ddr_dm does not appear in the port list for these parts.

Figure 7-7 shows a detailed block diagram of the DDR SDRAM controller. All four blocks shown are subblocks of the ddr1_top module. The functionality of these blocks is explained in following sections.

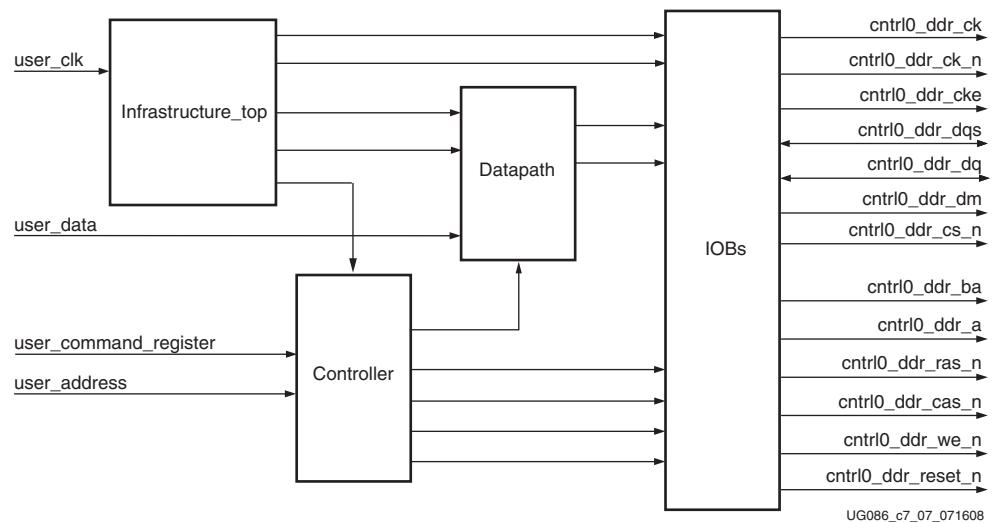


Figure 7-7: Memory Controller Block Diagram

Controller

The controller module accepts and decodes user commands and generates read, write, and memory initialization commands. The controller also generates signals for other modules.

The memory is initialized and powered up using a defined process. The controller state machine handles the initialization process upon receiving an initialization command.

Datapath

This module transmits and receives data to and from the memories. Major functions include storing the read data and transferring write data and write enable to the IOBS module. The data_read, data_write, data_path_IOBs, and data_read_controller modules perform the actual read and write functions. For more information, refer to XAPP768c [Ref 24].

Data Read Controller

This module generates all control signals that are used for data_read.

Data Read

The data_read module contains the read datapaths for the DDR SDRAM interface. Details for this module are described in XAPP768c [Ref 24].

Data Write

This module contains the write datapath for the DDR SDRAM interface. The write data and write enable signals are forwarded together to the DDR SDRAM through IOB flip-flops. The IOBs are implemented in the data_path_iobs module.

infrastructure_top

The infrastructure module generates the FPGA clock and reset signals. For differential clocking, sys_clk and sys_clkb ports are used as inputs to the IBUFGDS_LVDS_25 buffer and the output of the buffer is driven to the DCM input. For single-ended clocking, the sys_clk_in port is used as an input to the IBUFG buffer; the output of the buffer is driven to the DCM input. A DCM generates the clock and its inverted version. The infrastructure module also generates all of the reset signals required for the design.

The calibration circuit is also implemented in this module. If there is no DCM, the clocks are driven from the user interface.

IOBs

All input and output signals of the FPGA are implemented in the IOB registers.

Test Bench

MIG generates two different RTL folders, example_design and user_design. The example_design includes the synthesizable test bench, while user_design does not include the test bench modules. The MIG test bench performs five write commands and five read commands in an alternating fashion. The number of words in a write command depends on the burst length. For a burst length of 4, every write command writes four data words. For all five write commands, the test bench writes a total of 20 data words (10 rise data words and 10 fall data words). For a burst length of 8, the test bench writes a total of 40 data words. The pattern data is shown in Table 7-2, Table 7-3, and Table 7-4 for burst lengths of 2, 4, and 8, respectively.

Table 7-2: Data Pattern for Burst Length of 2

Burst	Rise	Fall
1	96	69
2	2C	D3
3	58	A7
4	B1	4E
5	63	9C

Table 7-3: Data Pattern for Burst Length of 4

Burst	Rise	Fall
1	96	69
	2C	D3
2	58	A7
	B1	4E
3	63	9C
	C6	39

Table 7-3: Data Pattern for Burst Length of 4 (Cont'd)

Burst	Rise	Fall
4	8C	73
	18	E7
5	31	CE
	62	9D

Table 7-4: Data Pattern for Burst Length of 8

Burst	Rise	Fall
1	96	69
	2C	D3
	58	A7
	B1	4E
2	63	9C
	C6	39
	8C	73
	18	E7
3	31	CE
	62	9D
	C4	3B
	88	77
4	10	EF
	21	DE
	42	BD
	85	7A
5	0A	F5
	15	EA
	2B	D4
	56	A9

The falling edge data is the complement of the rising edge data. The data pattern is repeated for the next set of five burst write commands based on the selected burst length, as shown in Table 7-2, Table 7-3, and Table 7-4. This data pattern is repeated in the same order based on the number of data words written. For data widths greater than 8, the same data pattern is concatenated for the other bits. For a 32-bit design and a burst length of 8, the data pattern for the first write command is 96969696, 69696969, 2C2C2C2C, D3D3D3D3, 58585858, A7A7A7A7, B1B1B1B1, 4E4E4E4E.

For all five write commands, five different address locations are generated, as shown in [Table 7-5](#). Read commands read the data from the same locations where writes are performed. The column address is incremented based on the burst length from one write command to the next write command. The row address is the same for all five write commands. For the next five write commands, the row address is incremented by 2, and this continues for each subsequent group of five write commands. Only five bits are used for row address generation. The row address rolls back to the initial value on reaching the terminal value. The bank address is the same for all five write commands, but it gets incremented for the next five write commands. This continues until the terminal count value is reached, depending on whether the selected memory part has a 4- or 8-bank architecture. The MIG test bench exercises only a certain memory area. [Table 7-5](#) provides the details of how the bank, row, and column address are incremented in the test bench.

Table 7-5: Address Generation in Test Bench

Address	Address for First Five Writes/Reads	Address for Second Five Writes/Reads	Description
Bank	0	1	<p>The bank address increments by 1. For a 2-bit bank address, the sequence is 0, 1, 2, 3.</p> <p>For a 3-bit bank address, the sequence is 0, 1, 2, 3, 4, 5, 6, 7.</p> <p>The bank address rolls back to the initial address 0 when it reaches the maximum value.</p>
Row	2	4	<p>The row address increments by 2 and starts with 2. Only five bits are used to generate the row address. 2, 4, 6, 8, 10, 12, 14, 16, 18, 20, 22, 24, 26, 28, 30 (5'b00010 to 5'b11110).</p> <p>The row address rolls back to the initial value of 2, when it reaches the maximum value.</p>
Column	0, 8, 16, 24, 32	0, 8, 16, 24, 32	<p>The column address increments in multiples of the burst length.</p> <p>For BL = 8, the address sequence for the first set of five write/read commands is 0, 8, 16, 24, 32.</p> <p>For BL = 4, the address sequence for the first set of five write/read commands is 0, 4, 8, 12, 16.</p> <p>For BL = 2, the address sequence for the first set of five write/read commands is 0, 2, 4, 8, 10.</p> <p>The same column address is repeated for the next set of commands.</p>

During reads, the read data is compared with the pattern written. For example, for an 8-bit data width and a burst length of 4, the write data for a single write command is 96, 69, 2C, D3. During reads, the read pattern is compared with the 96, 69, 2C, D3 pattern. If the data read back matches with the data written, the `led_error_output1` signal is set to 0, otherwise, it is set to 1 to indicate an error condition.

Clocking Scheme

Figure 7-8, page 295 shows the clocking scheme for this design. Global and local clock resources are used.

The global clock resources consist of a DCM and two BUFGs. The local clock resources consist of regional I/O clock networks (BUFIO). The global clock architecture is discussed in this section.

The MIG tool allows the user to customize the design such that the DCM is not included. In this case, `clk_0` and `clk90_0` must be supplied by the user.

Global Clock Architecture

The user must supply a system clock running at the target frequency for the memory.

This clock can be either single-ended or differential. User can select single-ended or differential clock input option from MIG GUI. Differential clocks are connected to the IBUFGDS and single-ended clock is connected to IBUFG.

The system clock from the output of the IBUFGDS or the IBUFG is connected to the DCM to generate the various clocks used by the memory interface logic.

The DCM generates two separate synchronous clocks for use in the design. This is shown in Table 7-6 and Figure 7-8, page 295. The clock structure is the same for both example design and user design. For designs without DCM instantiation, DCM and the BUFGs should be instantiated at user end to generate the required clocks.

Table 7-6: DDR Interface Design Clocks

Clock	Description	Logic Domain
<code>clk_0</code>	Skew compensated replica of the input system clock.	The clock for the controller and the user interface logic, most of the DDR bus-related I/O flip-flops (e.g., memory clock, control/address, output DQS strobe). This is also used to register the address and command signals from the user interface.
<code>clk90_0</code>	90° phase-shifted version of CLK0.	Used in the user interface logic, the write data path section of physical layer, write path control logic and output flip-flops for DQ and DM. This is also used to register data from the user interface and generate the read data and read data valid signals for the user interface logic.

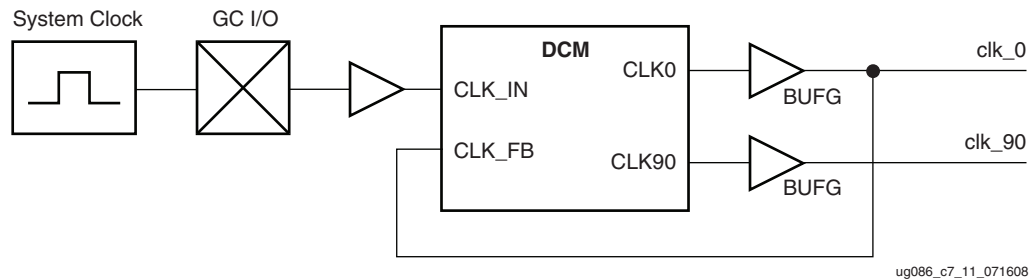


Figure 7-8: Clocking Scheme for DDR Interface Logic

Interface Signals

Table 7-7 lists the DDR SDRAM interface signals, directions, and descriptions to and from DDR SDRAM controller. The signal direction is with respect to the DDR SDRAM controller. Active-Low polarity is indicated with _n appended to the signal name. Table 7-7 is common for designs with and without testbenches. The signal cntrl0_ddr_reset_n is present only for registered DIMMs.

Table 7-7: DDR SDRAM Interface Signal Descriptions

Signal Name	Signal Direction	Description
cntrl0_ddr_a	Output	Address
cntrl0_ddr_dq	Input/Output	Data
cntrl0_ddr_dqs	Input/Output	Data Strobe
cntrl0_ddr_ras_n	Output	Command
cntrl0_ddr_cas_n	Output	Command
cntrl0_ddr_we_n	Output	Command
cntrl0_ddr_ba	Output	Bank Address
cntrl0_ddr_ck	Output	Clock
cntrl0_ddr_ck_n	Output	Inverted Clock
cntrl0_ddr_cs_n	Output	Chip Select
cntrl0_ddr_cke	Output	Clock Enable
cntrl0_ddr_dm	Output	Data Mask
cntrl0_ddr_reset_n	Output	Reset

Table 7-8 lists the DDR SDRAM clock, reset, and status signals for designs with and without testbenches. Except for the cntrl0_led_error_output1 signal, all other signals in Table 7-8 are present in designs either with or without testbenches. The cntrl0_led_error_output1 signal is present only in designs with a testbench.

Table 7-8: DDR SDRAM Clock, Reset, and Status Signals

Signal Name	Direction	Description
sys_clk and sys_clkb	Input	These signals are the system clock differential signals. They are driven from the user application for designs with DCMs. These two signals are given to a differential buffer, and the output of the differential buffer is connected to a clock's DCM. The DCM generates the required clocks to the design modules. These signals are not present when the design is generated without a DCM. When there is no DCM, the user application should drive the required clocks to the design.
clk_int and clk90_int	Input	These signals are the design clocks used in all modules. These clocks are to be driven from the user application only when the DDR SDRAM controller is generated without a DCM. These two clocks should be generated from the same source (DCM output) with a 90° phase shift.
reset_in_n	Input	This signal is the system reset signal. By default, this signal is active Low. The parameter file contains a parameter called RESET_ACTIVE_LOW. An active-High reset input can be selected by changing this parameter to 0.
cntrl0_led_error_output1	Output	This signal is asserted when there is a read data mismatch with the write data. This signal is usually used to connect the LED on the hardware to indicate a data error.
cntrl0_data_valid_out	Output	This signal is asserted when there is valid read data in the read FIFO. The signal LED error output is generated when this signal is High and there is a data mismatch. This signal can be driven to a status LED on the hardware.
cntrl0_rst_dqs_div_in	Input	This loopback signal is connected to the cntrl0_rst_dqs_div_out signal on the board. Refer to XAPP768c [Ref 24] for the functionality of this signal.
cntrl0_rst_dqs_div_out	Output	This loopback signal is connected to the cntrl0_rst_dqs_div_in signal on the board.
dcm_lock	Input	This signal is present only in designs without a DCM.
cntrl0_init_done	Output	The DDR SDRAM controller asserts this signal to indicate that the DDR SDRAM initialization is complete.

Table 7-9 describes the DDR SDRAM controller user interface signals used between the ddr1_top (design top-level module) and user application modules in designs without a testbench. These signals are buried one level down the hierarchy from memory interface top for with testbench design.

Table 7-9: DDR SDRAM Controller User Interface Signals (without a Testbench)

Signal Names	Direction ⁽¹⁾	Description												
cntrl0_user_input_data[(2 <i>n</i> −1):0]	Input	This bus is the write data to the DDR SDRAM from the user interface, where <i>n</i> is the width of the DDR SDRAM data bus. The DDR SDRAM controller converts single data rate to double data rate on the physical layer side. The data is valid on the DDR SDRAM write command. In 2 <i>n</i> , the MSB is rising-edge data and the LSB is falling-edge data.												
cntrl0_user_data_mask[(2 <i>m</i> −1):0]	Input	This bus is the data mask for write data. Like user_input_data, it is twice the size of the data mask bus at memory, where <i>m</i> is the size of the data mask at the memory interface. In 2 <i>m</i> , the MSB applies to rising-edge data and the LSB applies to falling-edge data.												
cntrl0_user_input_address [(ROW_ADDRESS + COLUMN_ADDRESS + BANK_ADDRESS−1):0] ⁽²⁾	Input	<p>This bus is the DDR SDRAM row, column, and bank address. This bus is the combination of row, column, and bank addresses for DDR SDRAM writes and reads. For example, for a given memory if row_address = 13, column_address = 11, bank_address = 2, and the user_input_address = 26, then:</p> <ul style="list-style-type: none">• Bank Address from the user interface = A[1:0]• Column Address from the user interface = A[12:2]• Row Address part from the user interface = A[25:13]												
cntrl0_user_command_register [2:0]	Input	<p>Supported user commands for the DDR SDRAM controller:</p> <table><tr><th>user_command[2:0]</th><th>User Command Description</th></tr><tr><td>000</td><td>NOP</td></tr><tr><td>010</td><td>Memory (DDR SDRAM) initialization</td></tr><tr><td>100</td><td>Write</td></tr><tr><td>110</td><td>Read</td></tr><tr><td>Others</td><td>Reserved</td></tr></table>	user_command[2:0]	User Command Description	000	NOP	010	Memory (DDR SDRAM) initialization	100	Write	110	Read	Others	Reserved
user_command[2:0]	User Command Description													
000	NOP													
010	Memory (DDR SDRAM) initialization													
100	Write													
110	Read													
Others	Reserved													
cntrl0_burst_done	Input	This signal is used to terminate a read or write command. This signal must be asserted after the last address for one clock for BL=2, two clocks for BL=4, and four clocks for BL=8. The DDR SDRAM controller supports write burst or read burst capability for a single row. The user must terminate the transfer on a column boundary and must re-initialize the controller for the next row of transactions on a column boundary.												
cntrl0_user_output_data [(2 <i>n</i> −1):0]	Output	This is the read data from the DDR SDRAM. The DDR SDRAM controller converts the DDR data from the DDR SDRAM to SDR data. As the DDR data is converted to SDR data, the width of this bus is 2 <i>n</i> , where <i>n</i> is data width of the DDR SDRAM data bus.												
cntrl0_user_data_valid	Output	When asserted, this signal indicates cntrl0_user_output_data[(2 <i>n</i> −1):0] is valid.												

Table 7-9: DDR SDRAM Controller User Interface Signals (without a Testbench) (Cont'd)

Signal Names	Direction ⁽¹⁾	Description
cntrl0_user_cmd_ack	Output	This is the acknowledgement signal for a user read or write command. It is asserted by the DDR SDRAM controller during a write or read to/from the DDR SDRAM. The user should not issue any new commands to the controller until this signal is deasserted.
cntrl0_init_done	Output	The DDR SDRAM controller asserts this signal to indicate that the DDR SDRAM initialization is complete.
cntrl0_auto_ref_req ⁽³⁾	Output	This signal is asserted based on the frequency. For example, for a frequency of 166 MHz, the signal is asserted every ~7.6 μ s until the controller issues an auto-refresh command to the memory. Upon seeing this signal, the user should terminate any ongoing command after completion of the current burst cycle by asserting the cntrl0_burst_done signal. To ensure reliable operation, users should terminate the current command within 15 to 20 clock cycles after cntrl0_auto_ref_req is asserted. The frequency with which this signal is asserted is determined by the MAX_REF_CNT value in the parameter file. The MAX_REF_CNT value is set in the parameter file based on the frequency selected from the tool.
cntrl0_ar_done ⁽³⁾	Output	This indicates that the auto-refresh command was completed to DDR SDRAM. The DDR SDRAM controller asserts this signal for one clock after giving an auto-refresh command to the DDR SDRAM and completion of T_{RFC} time. The T_{RFC} time is determined by the rfc_count_value in the parameter file. T_{RFC} is the minimum time required for the DDR SDRAM to complete the refresh command. The Refresh command is completed only after the assertion of the cntrl0_ar_done signal. The user can assert the next command any time after the assertion of the cntrl0_ar_done signal.

Notes:

1. All of the signal directions are with respect to the DDR SDRAM controller.
2. Linear addressing is used, i.e., the row address immediately follows the column address bits, and the bank address follows the row address bits, thus supporting more devices. The number of address bits used depends on the density of the memory part. The controller ignores the unused bits, which can all be tied High.
3. For more information on auto refresh refer to ["Auto Refresh,"](#) page 303.

Resource Utilization

A local inversion clocking technique is used in this design. The DCM generates only clk0 and clk90. One DCM and two BUFGMUXs are used. The Spartan-3 generation FPGA designs operate at 166 MHz and below.

DDR SDRAM Initialization

Before issuing the memory read and write commands, the controller initializes the DDR SDRAM using the memory initialization command. The user can give the initialization command only after all reset signals are deactivated. The controller is in the reset state for 200 μ s after power up. For design optimization, a 200 μ s timer is generated from the refresh counter. The refresh timer is a function of frequency. Therefore, at lower frequencies, the 200 μ s timer waits more than 200 μ s. Because wait200 happens only during the power-up sequence, design performance is not degraded. All resets are asserted for 200 μ s because DDR SDRAM requires a 200 μ s delay prior to applying an executable command after all power supply and reference voltages are stable. The controller asserts the clock enable to memory after 200 μ s.

All the load mode register parameters are taken from the Mode Register values in the parameter file. The user has to enter the load mode parameters from the GUI while generating the design from MIG. When the Init command is received from the user interface, the controller starts DDR SDRAM initialization. The controller then writes this data into the Load Mode Register. Once the DDR SDRAM is initialized, the DDR SDRAM controller asserts the init_done signal.

Figure 7-9 shows the timing for the memory initialization command.

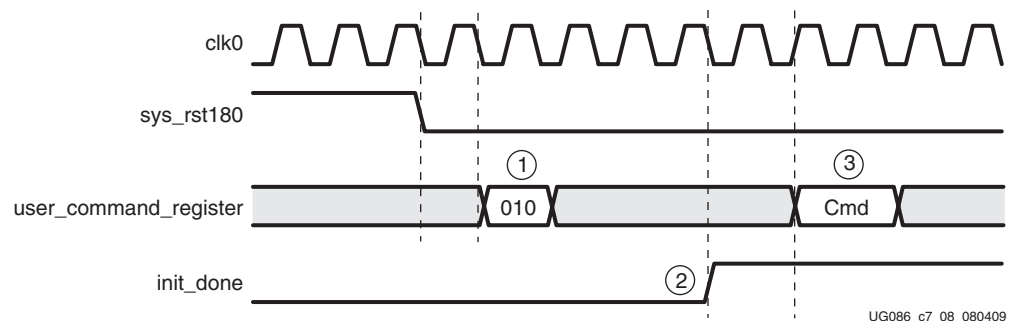


Figure 7-9: DDR SDRAM Initialization

1. When the 200 μ s timer expires, all the system resets (sys_rst, sys_rst90, and sys_rst180) go down. After sys_rst180 is deasserted, the user can place the initialization command on user_command_register[2:0] on a falling edge of clk0 for one clock cycle. This starts the initialization sequence.
2. The DDR SDRAM controller indicates that the initialization is complete by asserting the init_done signal on a falling edge of clk0. The init_done signal is asserted throughout the period.
3. After init_done is asserted, the user can pass the next command at any time.

DDR SDRAM Write and Read Operations

In Spartan-3 generation FPGA designs, prior to issuing a read or write operation, the user must assert the first address and command simultaneously and wait for a command acknowledge signal. The assertion time of the command acknowledge varies depending on the controller status. After the command acknowledge is asserted, the user waits for three clock cycles before sending the next address. This three clock cycle time is the Active to Command (t_{RCD}) delay for a read or write command as defined in the memory specification. Subsequent addresses are sent once every two clock cycles for a burst length of four.

If the user clock domain is different from $clk0$ and $clk90$ of the MIG, then the user must synchronize all the user interface signals to the $clk0$ and $clk90$ that are shown in [Figure 7-10](#) and [Figure 7-11](#), page 302.

Write

[Figure 7-10](#) shows the timing diagram for a write to DDR SDRAM with a burst length of four. The user initiates the write command by sending a Write command to the DDR SDRAM controller. To terminate a write burst, the user asserts the `burst_done` signal for two clocks after the last `user_input_address`. For a burst length of two, the `burst_done` signal should be asserted for one clock. For a burst length of four, the `burst_done` signal should be asserted for two clocks. For a burst length of eight, the `burst_done` signal should be asserted for four clock cycles.

The write command is asserted on the falling edge of $clk0$. In response to a write command, the DDR SDRAM controller acknowledges with the `usr_cmd_ack` signal on a falling edge of $clk0$. The `usr_cmd_ack` signal is generated in the next clock after the write command is asserted, if the controller is not busy. If there is an ongoing refresh command, the `usr_cmd_ack` signal is asserted after completion of the refresh command. The user asserts the first address (row + column + bank address) with the write command and keeps it asserted for three clocks after `usr_cmd_ack` assertion. Any subsequent write addresses are asserted on an alternate falling edge of $clk0$ after deasserting the first memory address. For a burst length of two, subsequent addresses are asserted on each clock cycle, and for a burst length of eight, subsequent addresses are asserted once every four clock cycles. The first user data is asserted on a rising edge of $clk90$ after `usr_cmd_ack` is asserted. As the SDR data is converted to DDR data, the width of this bus is $2n$, where n is data width of DDR SDRAM data bus.

For a burst length of four, only two data words (each of $2n$) are given to the DDR SDRAM controller for each user address. For a burst length of two, one data word is passed for each burst. For a burst length of eight, four data words are passed for each burst. Internally, for Burst Length = 4, the DDR SDRAM controller converts into four data words, each of n bits. To terminate the write burst, the user asserts `burst_done` on a falling edge of $clk0$ for two clocks. The `burst_done` signal is asserted after the last memory address. Any further commands to the DDR SDRAM controller are given only after the `usr_cmd_ack` signal is deasserted. After `burst_done` is asserted, the controller terminates the burst and issues a precharge to the memory. The `usr_cmd_ack` signal is deasserted after completion of the precharge.

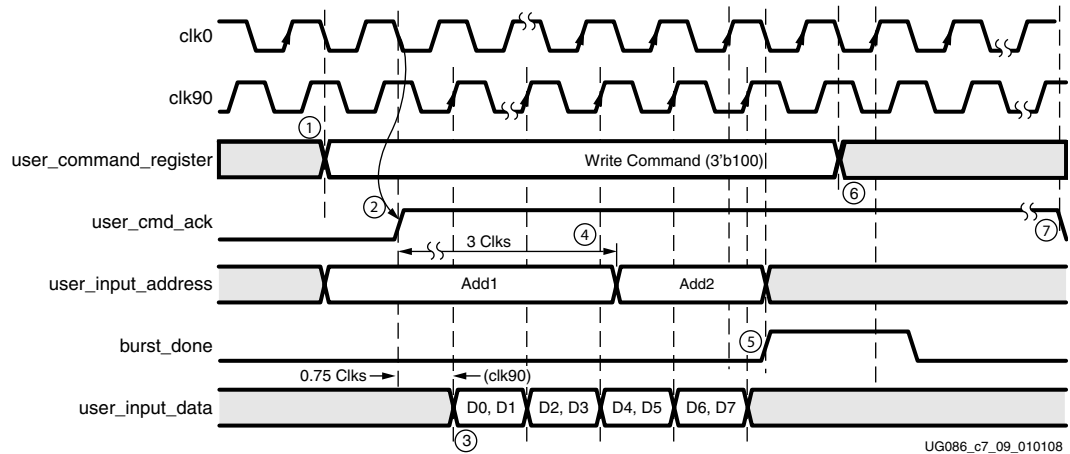


Figure 7-10: DDR SDRAM Write Burst, Burst Lengths of Four and Two Bursts

1. A memory write is initiated by issuing a write command to the DDR SDRAM controller. The write command must be asserted on a falling edge of clk0.
2. The DDR SDRAM controller acknowledges the write command by asserting the user_cmd_ack signal on a falling edge of clk0. The earliest this signal is asserted is one clock after the command. The maximum number of clock cycles it takes to assert cmd_ack signal depends on the refresh period.
3. The first user_input_address must be placed along with the command. The input data is asserted with the clk90 signal after the user_cmd_ack signal is asserted.
4. The user asserts the first address (row + column + bank address) with the write command and keeps it asserted for three clocks after usr_cmd_ack assertion. The user_input_address signal is asserted on a falling edge of clk0. All subsequent addresses are asserted on alternate falling edges of clk0 for burst lengths of four, on each clock for burst lengths of two, and once in four clocks for burst lengths of eight.
5. To terminate the write burst, burst_done is asserted after the last user_input_address. The burst_done signal is asserted for two clock cycles with respect to the falling edge of clk0 for burst lengths of four.
6. The user command is deasserted after burst_done is asserted.
7. The controller deasserts the user_cmd_ack signal after completion of precharge to the memory. The next command must be given only after user_cmd_ack is deasserted. Back-to-back write operations are supported only within the same bank and row.

Read

The user initiates a memory read with a read command to the DDR SDRAM controller. [Figure 7-11](#) shows the memory read timing diagram for a burst length of four.

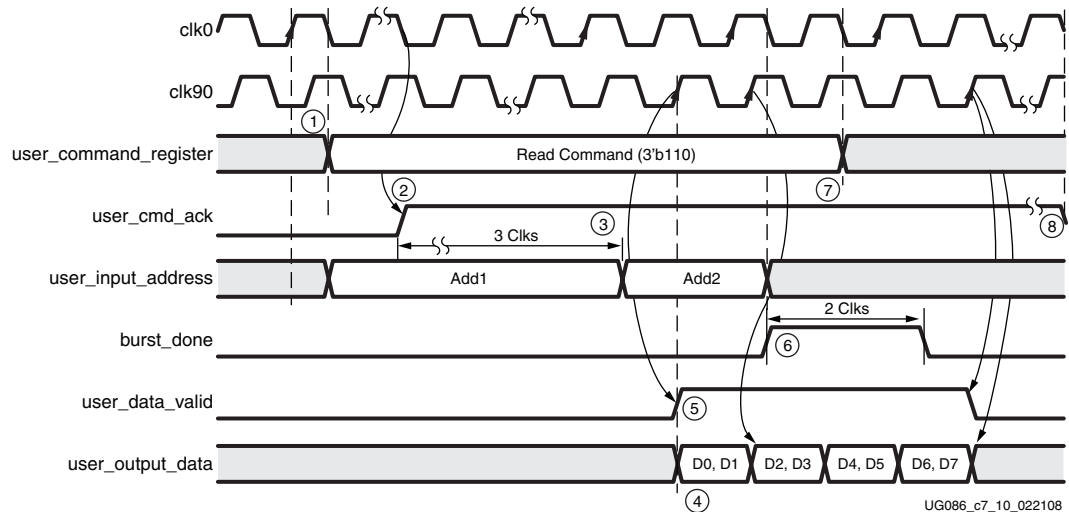


Figure 7-11: DDR SDRAM Read, Burst Lengths of Four and Two Bursts

The user provides the first memory address with the read command, and subsequent memory addresses upon receiving the `usr_cmd_ack` signal. Data is available on the user data bus with the `user_data_valid` signal. To terminate read burst, the user asserts the `burst_done` signal on a falling edge of `clk0` for two clocks with the deassertion of the last `user_input_address`. The `burst_done` signal is asserted for one clock for burst lengths of two, two clocks for burst lengths of four, and four clocks for burst lengths of eight. The controller does not support single burst read operation for burst length of two.

The read command flow is similar to the write command flow.

1. A memory read is initiated by issuing a read command to the DDR SDRAM controller. The read command is accepted on a falling edge of `clk0`.
2. The first read address must be placed along with the read command. In response to the read command, the DDR SDRAM controller asserts the `user_cmd_ack` signal on a falling edge of `clk0`. The `usr_cmd_ack` signal is asserted a minimum of one clock cycle after the read command is asserted. This signal is delayed if there is an ongoing refresh cycle, in which case it is asserted after the current refresh command completes.
3. The user asserts the first address (row + column + bank address) with the read command and keeps it asserted for three clocks after `usr_cmd_ack` is asserted. The `user_input_address` signal is then accepted on the falling edge of `clk0`. All subsequent memory read addresses are asserted on alternate falling edges of `clk0` for burst lengths of four. The subsequent addresses are changed on every clock for burst lengths of two, on alternate clocks for burst lengths of four, and once in four clocks for burst lengths of eight.
4. The data on `user_output_data` is valid only when the `user_data_valid` signal is asserted.
5. The data read from the DDR SDRAM is available on `user_output_data`, which is asserted with `clk90`. Because the DDR SDRAM data is converted to SDR data, the width of this bus is $2n$, where n is the data width of the DDR SDRAMs. For a read burst length of four, the DDR SDRAM controller outputs only two data words with each user address. For a burst length of two, the controller outputs one data word, and for a burst length of eight, the controller outputs four data words.
6. To terminate the read burst, `burst_done` is asserted for two clocks on the falling edge of `clk0`. The `burst_done` signal is asserted after the last memory address.

7. The user command is deasserted after burst_done is asserted.
8. The controller deasserts the user_cmd_ack signal after completion of precharge to the memory. Any further commands to the DDR SDRAM controller should be given after user_cmd_ack is deasserted. Back-to-back read operations are supported only within the same bank and row. Approximately 17 clock cycles pass between the time a read command is asserted on the user interface and the time data becomes available on the user interface.

Table 7-10 shows the read latency for CL = 3.

Table 7-10: Read Command to Read Data Latency

Parameter	Number of Clocks
User Read command to command ack	1
Command ack to Active command	3
Active to Read command	3
Memory Read command to data valid	10
Total clocks	17

In general, read latency varies based on the following parameters

- CAS latency
- If the user issues the commands before initialization is complete, the latency cannot be determined

Auto Refresh

The DDR SDRAM controller does a memory refresh at intervals determined by the frequency. For example, for a frequency of 166 MHz, an auto-refresh request is raised every ~7.6 μ s. The user must terminate any ongoing commands within 20 clock cycles, when auto_ref_req flag is asserted. The user must assert the burst_done signal at the end of the current burst transaction when sensing the auto_ref_req flag for terminating the current transaction. The auto_ref_req flag is asserted until the controller issues a refresh command to the memory. The user must wait for completion of the auto-refresh command before giving any commands to the controller when auto_ref_req is asserted.

The ar_done signal is asserted by the controller on completion of the auto-refresh command—i.e., after T_{RFC} time. The ar_done signal is asserted with clk180 for one clock cycle.

The controller sets the MAX_REF_CNT value in the parameter file according to the frequency selected for a refresh interval (7.7 μ s). The rfc_count_value value in the parameter file defines T_{RFC} , the time between the refresh command to Active or another refresh command.

After completion of the auto-refresh command, the next command can be given any time after ar_done is asserted.

The current testbench generates five consecutive write bursts followed by five read burst commands. For every group of five write/read commands, the controller issues an active command followed by five write/read commands, and then a precharge command to the memory. All five burst commands take up a maximum of 20 clock cycles. After every precharge command, the controller state machine goes to an idle state and checks for an

auto_ref_req. When an auto_ref_req is asserted, the controller issues an auto refresh command to the memory if it is in an idle state. In the worst case, the controller takes 20 clocks to go from burst_done to the auto refresh command and to the memory. The controller issues auto refresh commands to the memory within 40 clock cycles after auto_ref_req is asserted. Because the delay from auto_ref_req to the refresh command to the memory is within the specified number of clocks even in the worst case scenario, the testbench does not need to terminate the write or read transaction on the auto_ref_req signal.

For example, at 77 MHz, an auto_ref_req is generated every 7.292 μ s, and at 166 MHz, it is generated every 7.572 μ s. The MAX_REF_CNT parameter is set to the following values at 77 MHz and 166 MHz frequencies to allow 40 clock cycles of delay from auto_ref_req to the refresh command:

Average periodic refresh = 7.8125 μ s

$\text{MAX_REF_CNT} = (7812.5 \text{ ns} - 40 \times \text{clk_period}) / \text{clk_period}$

At 77 MHz (13 ns): $\text{MAX_REF_CNT} = (7812.5 \text{ ns} - 40 \times 13) / 13 = 7292.5 / 13 = 560$

At 166 MHz (6 ns): $\text{MAX_REF_CNT} = (7812.5 \text{ ns} - 40 \times 6) / 6 = 7572.5 / 6 = 1262$

User transactions should be terminated within 20 clock cycles of the auto_ref_req signal being asserted. The ar_done signal is asserted for one clock period by the controller on completion of an auto refresh command (i.e., after T_{RFC} time). Normal read and write commands can be issued to the controller any time after ar_done is asserted.

Changing the Refresh Rate

Change the global `define (for Verilog) or constant (for VHDL) variable MAX_REF_CNT in mymodule_parameters_0.v (or .vhd) so that $\text{MAX_REF_CNT} = (\text{refresh interval in clock periods}) = (\text{refresh interval}) / (\text{clock period})$. For example, for a refresh rate of 7.7 μ s with a memory bus running at 133 MHz:

$\text{MAX_REF_CNT} = 7.7 \mu\text{s} / (\text{clock period}) = 7.7 \mu\text{s} / 7.5 \text{ ns} = 1026 \text{ (decimal)} = 0x402$

If the above value exceeds $2^{\text{MAX_REF_WIDTH}} - 1$, the value of MAX_REF_WIDTH must be increased accordingly in parameters_0.v (or .vhd) to increase the width of the counter used to track the refresh interval.

Load Mode

MIG does not support the user LOAD MODE command. The mode register values from the parameter file are loaded into the Load Mode register during initialization.

UCF Constraints

Some constraints are required to successfully create the design. The following examples explain the different constraints in the UCF.

Calibration Circuit Constraints

All LUTs in the matched delay circuits are constrained to specific locations in the device.

For example:

```
INST "infrastructure_top0/cal_top0/tap_dly0/10" RLOC=X0Y6;
INST "infrastructure_top0/cal_top0/tap_dly0/10" U_SET =
    delay_calibration_chain;
INST "infrastructure_top0/cal_top0/tap_dly0/gen_tap1[0].r" RLOC=X0Y6;
INST "infrastructure_top0/cal_top0/tap_dly0/gen_tap1[0].r" U_SET =
    delay_calibration_chain;
INST "infrastructure_top0/cal_top0/tap_dly0/gen_tap1[1].r" RLOC=X0Y6;
INST "infrastructure_top0/cal_top0/tap_dly0/gen_tap1[1].r" U_SET =
    delay_calibration_chain;
```

Data and Data Strobe Constraints

Data and data strobe signals are assigned to specific pins in the device; placement constraints related to the dqs_delay circuit and the FIFOs used for the data_read module are specified.

Example:

```
NET "cntrl0_DDR_DQS[0]" LOC = Y6;
INST "ddr1_top0/data_path0/data_read_controller0/gen_delay[0].dqs_delay_col0/one"
LOC = SLICE_X0Y110;
INST "ddr1_top0/data_path0/data_read_controller0/gen_delay[0].dqs_delay_col0/one"
BEL = F;
NET "cntrl0_DDR_DQ[0]" LOC = Y4;
INST "ddr1_top0/data_path0/data_read0/gen_strobe[0].strobe/fifo0_bit0" LOC =
SLICE_X2Y111;
```

The I/O standards for all the memory interface signals are required to be specified.

MAXDELAY Constraints

The MAXDELAY constraints define the maximum allowable delay on the net. Following are the list of MAXDELAY constraints used in Spartan FPGA designs in the UCF on different nets. The values provided here vary depending on FPGA family and the device type. Some values are dependent on frequency. The constraints shown here are from example_design. The hierarchy paths of the nets are different between example_design and user_design.

```
NET "infrastructure_top0/cal_top0/tap_dly0/tap[7]" MAXDELAY = 350ps;
NET "infrastructure_top0/cal_top0/tap_dly0/tap[15]" MAXDELAY = 350ps;
NET "infrastructure_top0/cal_top0/tap_dly0/tap[23]" MAXDELAY = 350ps;
```

These constraints are used to minimize the tap delay inverter connection wire length. This delay should be minimized to calibrate the delay of a tap (LUT element) accurately. These values are independent of frequency and vary from family to family and device to device. Without these constraints, the tool might synthesize longer routes between the tap connections. Inappropriate delays in this circuit could cause the design to fail in hardware.

```
NET "main_00/top0/dqs_int_delay_in*" MAXDELAY = 675ps;
```

This constraint is used for the DQS nets from the I/O pad to the input of the LUT delay chain. Without this constraint, the nets take unpredictable delays that affect the Data Valid window. In Spartan-3 generation FPGA designs, data is latched using the DQS signal. In order to latch the correct data, DQS is delayed using LUT delay elements to center-align with respect to the input read data. Incorrect data could be latched if the delays on this net are unpredictable. Unpredictable delays might also cause the design to have intermittent failures, which are difficult to debug in hardware.

```
NET "main_00/top0/dqs_div_rst" MAXDELAY = 460ps;
```

The net `dqs_div_rst` is the loopback signal. This signal is used as an enable for read data FIFOs and FIFO write pointers after it is delayed using the LUT delay elements. The overall delay on this net should be comparable with the delay on the DQS signal. This net is constrained to control the overall delay. Both the `dqs_div_rst` and DQS signals take similar paths. If the delay on the `dqs_div_rst` signal is higher, the first read data from memory might be missed.

```
NET
"main_00/top0/data_path0/data_read_controller0/gen_delay*dqs_delay_col
*/delay*" MAXDELAY = 140ps;
NET
"main_00/top0/data_path0/data_read_controller0/rst_dqs_div_delayed/
delay*" MAXDELAY = 140 ps;
```

These constraints are required to minimize the wire delays between the LUT elements of a LUT delay chain that is used to delay the DQS and `rst_dqs_div` loopback signal. Higher wire delays between LUT delay elements can shift the data valid window, which in turn can cause incorrect data to be latched. Therefore, the MAXDELAY constraint is required for these nets.

```
NET "main_00/top0/data_path0/data_read_controller0/rst_dqs_div"
MAXDELAY = 3383 ps;
NET "main_00/top0/data_path0/data_read0/fifo*_wr_en*"
MAXDELAY = 3007ps;
```

These constraints are required because these paths are not constrained otherwise. The total delay on the `rst_dqs_div` and `fifo_wr_en` nets must not exceed the clock period. The total delay on both the nets is set to 85% of the clock period, leaving 15% as margin. These delays vary with frequency.

```
NET "main_00/top0/data_path0/data_read0/fifo*_wr_addr[*]"
MAXDELAY = 5610ps;
```

The MAXDELAY constraint is required on FIFO write address because this path is not constrained otherwise. This is a single clock cycle path. It is set to 80% of the clock period, leaving 20% as margin because this net generally meets the required constraint.

I/O Banking Rules

There are I/O banking rules to be followed for I/O pin allocations, stating that the I/O signals allocated in a bank should adhere to compatible I/O standards. Refer to the “Rules Concerning Banks” section for additional information regarding I/O banking rules in DS099 [Ref 28] and DS312 [Ref 29].

Design Notes

Spartan-3/3E/3A/3AN/3A DSP FPGA Pin Allocation Rules

The pin allocation rules are different for top/bottom and left/right banks because of the local clock structure of Spartan FPGAs.

Pin Allocation Rules for Left/Right Banks

1. When a DQS is allocated, its associated DQ bits should be allocated within five tiles above and six tiles below the DQS tile.
2. The DQ bits should not be allocated in the DQS tile.
3. The rst_dqs_div signal should be placed in the center of the data bank.

Pin Allocation Rules for Top/Bottom Banks

1. All DQ bits corresponding to DQS are required to be placed to the right of its DQS tile.
2. All DQ bits corresponding to the DQS should be within five I/O tiles of the DQS tile.
3. A DQ bit should not be allocated in the same I/O tile where DQS is allocated.

Top/Bottom Bank Support

MIG does not support top/bottom banks for Spartan 3E/3A/3AN/3A DSP devices. For some I/O pads, the fabric slices are not located next to the IOBs. These I/O pads cannot be used for pin allocation. By excluding these I/O pins, there are not enough pins to allocate DQ and DQS signals according to the pin allocation rules.

DDR SDRAM Signal Allocations

MIG allows banks to be selected for different classes of memory signals. [Table 7-11](#) shows the list of signals allocated in a group from bank selection checkboxes.

Table 7-11: DDR SDRAM Signal Allocations

Bank Selected	Signals Allocated in the Group
Address	Memory address and memory control
Data	Data, data mask, data strobes, and memory clock signals
System Control	System reset from the user interface and status signals
System Clock	System clocks from the user interface

Supported Devices

This section provides tables for the memory components supported by Spartan-3, Spartan-3A, Spartan-3AN, Spartan-3A DSP, and Spartan-3E devices.

The design generated out of MIG is independent of memory speed grade, hence the package part of the memory component is replaced with X, where X indicates a don't care condition. Pin mapping for x4 RDIMMs is provided in [Appendix G, "Low Power Options."](#)

The tables below list the components (Table 7-12) and DIMMs (Table 7-13 through Table 7-15) supported by the tool for Spartan-3 FPGA DDR local clocking designs.

Table 7-12: Supported Components for DDR SDRAM Local Clocking (Spartan-3 FPGAs)

Components	Packages (XX)	Components	Packages (XX)
MT46V32M4XX-5B	-	MT46V32M4XX-75	P,TG
MT46V64M4XX-5B	BG,FG,P,TG	MT46V64M4XX-75	FG,P,TG
MT46V128M4XX-5B	BN,FN,P,TG	MT46V128M4XX-75	BN,FN,P,TG
MT46V256M4XX-5B	P,TG	MT46V256M4XX-75	P,TG
MT46V16M8XX-5B	TG,P	MT46V16M8XX-75	P,TG
MT46V32M8XX-5B	BG,FG,P,TG	MT46V32M8XX-75	FG,P,TG
MT46V64M8XX-5B	BN,FN,P,TG	MT46V64M8XX-75	BN,FN,P,TG
MT46V128M8XX-5B	-	MT46V128M8XX-75	P,TG
MT46V8M16XX-5B	TG,P	MT46V8M16XX-75	P,TG
MT46V16M16XX-5B	BG,FG,P,TG	MT46V16M16XX-75	BG,FG,P,TG
MT46V32M16XX-5B	BN,FN,P,TG	MT46V32M16XX-75	-
MT46V64M16XX-5B	-	MT46V64M16XX-75	P,TG

Table 7-13: Supported Unbuffered DIMMs for DDR SDRAM Local Clocking (Spartan-3 FPGAs)

Unbuffered DIMMs	Packages (X)	Unbuffered DIMMs	Packages (X)
MT4VDDT1664AX-40B	G,Y	MT8VDDT3264AX-40B	G,Y
MT4VDDT3264AX-40B	G,Y	MT9VDDT3272AX-40B	Y

Table 7-14: Supported Registered DIMMs for DDR SDRAM Local Clocking (Spartan-3 FPGAs)

Registered DIMMs	Packages (X)	Registered DIMMs	Packages (X)
MT9VDDF3272X-40B	G,Y	MT18VDDF3272X-40B	G,Y
MT9VDDF3272X-40B	G,Y	MT18VDDF12872X-40B	G,Y

Table 7-15: Supported SODIMMs for DDR SDRAM Local Clocking (Spartan-3 FPGAs)

SODIMMs	Packages (X)	SODIMMs	Packages (X)
MT4VDDT3264HX-40B	G,Y	MT9VDDT3272HX-40B	
MT4VDDT1664HX-40B	Y	MT9VDDT6472HX-40B	G,Y
MT8VDDT3264HX-40B	-	MT9VDDT12872HX-40B	-
MT8VDDT6464HX-40B	G,Y		

The tables below list the components (Table 7-16) and DIMMs (Table 7-17 through Table 7-19, page 309) supported by the tool for Spartan-3A/3AN FPGA DDR local clocking designs.

Table 7-16: Supported Components for DDR SDRAM Local Clocking (Spartan-3A/3AN FPGAs)

Components	Packages (XX)	Components	Packages (XX)
MT46V32M4XX-5B	-	MT46V32M4XX-75	P,TG
MT46V64M4XX-5B	BG,FG,P,TG	MT46V64M4XX-75	FG,P,TG
MT46V128M4XX-5B	BN,FN,P,TG	MT46V128M4XX-75	BN,FN,P,TG
MT46V256M4XX-5B	P,TG	MT46V256M4XX-75	P,TG
MT46V16M8XX-5B	TG,P	MT46V16M8XX-75	P,TG
MT46V32M8XX-5B	BG,FG,P,TG	MT46V32M8XX-75	FG,P,TG
MT46V64M8XX-5B	BN,FN,P,TG	MT46V64M8XX-75	BN,FN,P,TG
MT46V128M8XX-5B	-	MT46V128M8XX-75	P,TG
MT46V8M16XX-5B	TG,P	MT46V8M16XX-75	P,TG
MT46V16M16XX-5B	BG,FG,P,TG	MT46V16M16XX-75	BG,FG,P,TG
MT46V32M16XX-5B	BN,FN,P,TG	MT46V32M16XX-75	-
MT46V64M16XX-5B	-	MT46V64M16XX-75	P,TG

Table 7-17: Supported Unbuffered DIMMs for DDR SDRAM Local Clocking (Spartan-3A/3AN FPGAs)

Unbuffered DIMMs	Packages (X)	Unbuffered DIMMs	Packages (X)
MT4VDDT1664AX-40B	G,Y	MT8VDDT3264AX-40B	G,Y
MT4VDDT3264AX-40B	G,Y	MT9VDDT3272AX-40B	Y

Table 7-18: Supported Registered DIMMs for DDR SDRAM Local Clocking (Spartan-3A/3AN FPGAs)

Registered DIMMs	Packages (X)	Registered DIMMs	Packages (X)
MT9VDDF3272X-40B	G,Y	MT9VDDF3272X-40B	G,Y

Table 7-19: Supported SODIMMs for DDR SDRAM Local Clocking (Spartan-3A/3AN FPGAs)

SODIMMs	Packages (X)	SODIMMs	Packages (X)
MT4VDDT3264HX-40B	G,Y	MT9VDDT3272HX-40B	--
MT4VDDT1664HX-40B	Y	MT9VDDT6472HX-40B	G,Y
MT8VDDT3264HX-40B	-	MT9VDDT12872HX-40B	--
MT8VDDT6464HX-40B	G,Y	--	--

The tables below list the components ([Table 7-20](#)) and DIMMs ([Table 7-21](#) and [Table 7-22](#)) supported by the tool for Spartan-3A DSP FPGA DDR local clocking designs.

Table 7-20: Supported Components for DDR SDRAM Local Clocking (Spartan-3A DSP FPGAs)

Components	Packages (XX)	Components	Packages (XX)
MT46V32M4XX-5B	-	MT46V32M4XX-75	P,TG
MT46V64M4XX-5B	BG,FG,P,TG	MT46V64M4XX-75	FG,P,TG

Table 7-20: Supported Components for DDR SDRAM Local Clocking (Spartan-3A DSP FPGAs) (Cont'd)

Components	Packages (XX)	Components	Packages (XX)
MT46V128M4XX-5B	BN,FN,P,TG	MT46V128M4XX-75	BN,FN,P,TG
MT46V256M4XX-5B	P,TG	MT46V256M4XX-75	P,TG
MT46V16M8XX-5B	TG,P	MT46V16M8XX-75	P,TG
MT46V32M8XX-5B	BG,FG,P,TG	MT46V32M8XX-75	FG,P,TG
MT46V64M8XX-5B	BN,FN,P,TG	MT46V64M8XX-75	BN,FN,P,TG
MT46V128M8XX-5B	-	MT46V128M8XX-75	P,TG
MT46V8M16XX-5B	TG,P	MT46V8M16XX-75	P,TG
MT46V16M16XX-5B	BG,FG,P,TG	MT46V16M16XX-75	BG,FG,P,TG
MT46V32M16XX-5B	BN,FN,P,TG	MT46V32M16XX-75	-
MT46V64M16XX-5B	-	MT46V64M16XX-75	P,TG

Table 7-21: Supported Unbuffered DIMMs for DDR SDRAM Local Clocking (Spartan-3A DSP FPGAs)

Unbuffered DIMMs	Packages (X)	Unbuffered DIMMs	Packages (X)
MT4VDDT1664AX-40B	G,Y	MT8VDDT3264AX-40B	G,Y
MT4VDDT3264AX-40B	G,Y		

Table 7-22: Supported SODIMMs for DDR SDRAM Local Clocking (Spartan-3A DSP FPGAs)

SODIMMs	Packages (X)	SODIMMs	Packages (X)
MT4VDDT3264HX-40B	G,Y	MT8VDDT3264HX-40B	-
MT4VDDT1664HX-40B	Y	MT8VDDT6464HX-40B	G,Y

Table 7-23 lists the components supported by the tool for Spartan-3E FPGA DDR local clocking designs.

Table 7-23: Supported Components for DDR SDRAM Local Clocking (Spartan-3E FPGAs)

Components	Packages (XX)	Components	Packages (XX)
MT46V32M4XX-5B	-	MT46V32M4XX-75	P,TG
MT46V64M4XX-5B	BG,FG,P,TG	MT46V64M4XX-75	FG,P,TG
MT46V128M4XX-5B	BN,FN,P,TG	MT46V128M4XX-75	BN,FN,P,TG
MT46V256M4XX-5B	P,TG	MT46V256M4XX-75	P,TG
MT46V16M8XX-5B	TG,P	MT46V16M8XX-75	P,TG
MT46V32M8XX-5B	BG,FG,P,TG	MT46V32M8XX-75	FG,P,TG
MT46V64M8XX-5B	BN,FN,P,TG	MT46V64M8XX-75	BN,FN,P,TG
MT46V128M8XX-5B	-	MT46V128M8XX-75	P,TG
MT46V8M16XX-5B	TG,P	MT46V8M16XX-75	P,TG
MT46V16M16XX-5B	BG,FG,P,TG	MT46V16M16XX-75	BG,FG,P,TG

Table 7-23: Supported Components for DDR SDRAM Local Clocking (Spartan-3E FPGAs)

Components	Packages (XX)	Components	Packages (XX)
MT46V32M16XX-5B	BN,FN,P,TG	MT46V32M16XX-75	-
MT46V64M16XX-5B	-	MT46V64M16XX-75	P,TG

Simulating the Spartan-3/3E/3A/3AN/3A DSP FPGA Design

After generating the design, MIG creates a `sim` folder in the specified path. This folder contains simulation files for the generated design. The `sim` folder contains the external testbench, memory model, and `.do` file to simulate the generated design. The memory model files are currently generated in Verilog only. To learn more details about the files in the `sim` folder and to simulate the design, refer to “[Simulation Guide](#),” page 499.

For single-rank DIMMs, MIG outputs only the base part memory model. In the simulation testbench (`sim_tb_top` in the `sim` folder), MIG instantiates the required number of memory models. For example, a 1 GB single-rank DIMM with the base part is 1 Gb, and MIG instantiates the base model eight times. If the MIG generated memory model is to be used with the user’s test bench, multiple instances should be used based on the selected configuration.

The MIG output memory model considers the `part_mem_bits` parameter by default for memory range allocation. This covers only a partial memory range, i.e., $2^{\text{part_mem_bits}}$. To allocate the full memory range, the `FULL_MEM` parameter should be set in the memory model, which in turn sets the `full_mem_bits` parameter for memory allocation. Allocating the full memory range might exceed the memory of the operating system, thus causing memory allocation failure in simulations.

Hardware Tested Configurations

The frequencies shown in [Table 7-24](#) and [Table 7-25](#) were achieved on the Spartan-3 FPGA Memory Interface Board and Spartan-3E FPGA Starter Kit, respectively, under nominal conditions. This frequency should not be used to determine the maximum design frequency. The maximum design frequency supported in the MIG wizard is based on a combination of the TRCE results for fabric timing on multiple device/package combinations and I/O timing analysis using FPGA and memory timing parameters for a 64-bit wide interface.

Table 7-24: Hardware Tested Configurations for Spartan-3 FPGA DDR SDRAM Designs

Synthesis Tools	XST
HDL	Verilog and VHDL
FPGA Device	XC3S1500FG676-5
Burst Lengths	2 and 8
CAS Latency (CL)	2 and 2.5
64-bit Design	Tested on 16-bit Component “MT46V16M16XX-75”
	64-bit DIMM “MT4VDDT3264AX”

Table 7-24: Hardware Tested Configurations for Spartan-3 FPGA DDR SDRAM Designs

Synthesis Tools	XST
Frequency Range	67 MHz to 170 MHz for CL = 2
	40 MHz to 190 MHz for CL = 2.5

Table 7-25: Hardware Tested Configurations for Spartan-3E FPGA DDR SDRAM Designs

Synthesis Tools	XST
HDL	Verilog and VHDL
FPGA Device	XC3S500EFG320-4
Burst Lengths	2 and 4
CAS Latency (CL)	2 and 2.5
16-bit Design	Tested on 16-bit Component "MT46V32M16XX-6T"
Frequency Range	80 MHz to 170 MHz for CL = 2
	80 MHz to 170 MHz for CL = 2.5

Implementing DDR2 SDRAM Controllers

This chapter describes how to implement DDR2 SDRAM interfaces for Spartan®-3, Spartan-3A, Spartan-3AN, and Spartan-3A DSP FPGAs generated by MIG. This design is based on XAPP768c [Ref 24].

Feature Summary

This section summarizes the supported and unsupported features of the DDR2 SDRAM controller design.

Supported Features

The DDR2 SDRAM controller design supports the following:

- Burst lengths of four and eight
- Sequential and interleaved burst types
- CAS latency of 3
- Auto refresh
- Data mask enable/disable option
- System clock, differential and single-ended
- Linear addressing
- Spartan-3 FPGA maximum frequency:
 - 133 MHz with a -4 speed grade device
 - 166 MHz with a -5 speed grade device
- Spartan-3A, Spartan-3AN, and Spartan-3A DSP FPGA maximum frequency:
 - 133 MHz with a -4 speed grade device
 - 166 MHz with a -5 speed grade device
- Components, unbuffered DIMMs, and registered DIMMs
- Verilog and VHDL
- XST and Synplicity synthesis tools
- With and without a testbench
- With or without a DCM

Unsupported Features

The DDR2 SDRAM controller design does not support:

- CAS Latencies of 4 and 5
- Additive latencies of 1, 2, 3 and 4
- Auto Precharge
- Redundant DQS (RDQS)
- Dual rank DIMMs and Deep design

Design Frequency Ranges

Table 8-1: Design Frequency Range in MHz

FPGA Family	Memory	FPGA Speed Grade			
		-4		-5	
		Min	Max	Min	Max
Spartan-3	Component	125	133	125	166 ⁽¹⁾
	DIMM	125	133	125	133
Spartan-3A/3AN/3A DSP	Component	125	133	125	166
	DIMM	125	133	125	166

Notes:

1. Spartan-3 devices support 133 MHz for data widths greater than 32 bits.

Controller Architecture

DDR2 SDRAM Interface

High-speed memory interfaces are source-synchronous and double data rate. They transfer data on both edges of the clock cycle. A memory interface can be modularly represented as shown in Figure 8-1. Creating a modular interface has many advantages. It allows designs to be ported easily, and it also makes sharing parts of the design across different types of memory interfaces possible.

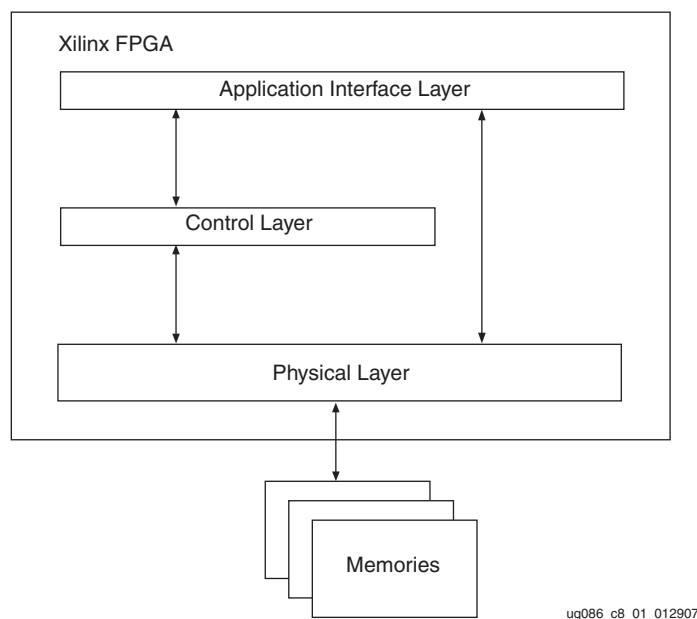
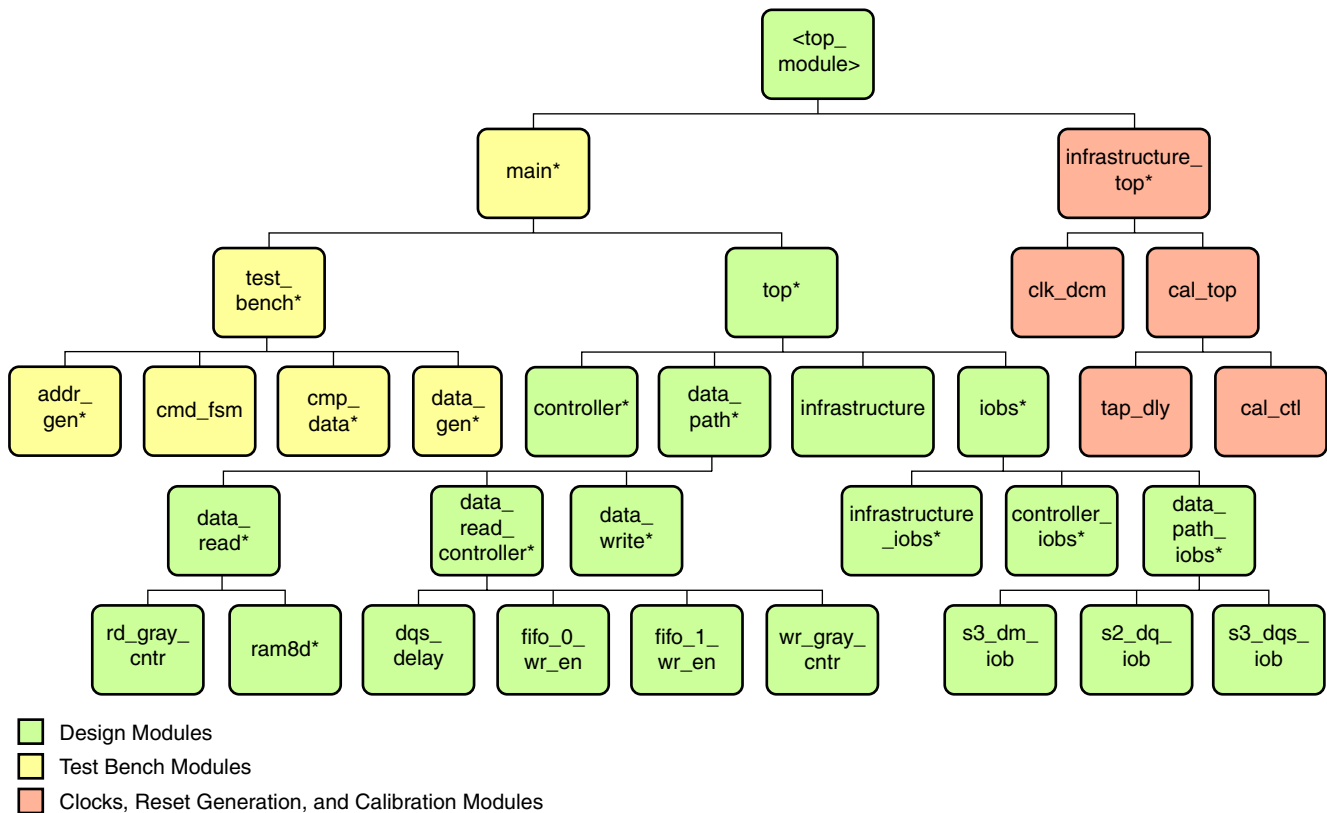


Figure 8-1: Modular Memory Interface Representation

Hierarchy

Figure 8-2 shows the hierarchical structure of the DDR2 SDRAM design generated by MIG with a testbench and a DCM. In the figure, the physical and control layers are clearly separated. MIG generates the entire controller, as shown in this hierarchy, including the testbench. The user can replace the testbench with a design that makes use of the DDR2 SDRAM interface.



Note: A block with a * has a parameter file included.

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Figure 8-2: Hierarchical Structure of the Design

The modules are classified as follows:

- Design modules
- Testbench modules
- Clocks, reset generation, and calibration modules

There is a parameter file generated with the design that has all the user input and design parameters selected from MIG.

MIG can generate four different DDR2 SDRAM designs:

- With a testbench and a DCM
- Without a testbench and with a DCM
- With a testbench and without a DCM
- Without a testbench and without a DCM

For a design without a testbench (user_design), the yellow shaded modules in [Figure 8-2](#) are not present in the design. The <top_module> module has the user interface signals for designs without a testbench. The list of user interface signals is provided in [Table 8-8](#).

The infrastructure_top module comprises the clock and the reset generation module of the design. It instantiates a DCM in the module when selected by MIG. The differential design clock is an input to this module. A user reset is also input to this module. Using the input clocks and reset signals, system clocks and system reset are generated in this module which is used in the design. Infrastructure_top also consists of calibration logic.

The DCM primitive is not instantiated in this module if the **Use DCM** option is unchecked. Therefore, the system operates on the user-provided clocks. The system reset is generated in the infrastructure_top module using the dcm_lock input signal. [Figure 8-3](#) and [Figure 8-4, page 319](#) represent the system clock for differential only.

MIG Tool Design Options

MIG provides various options to generate the design with or without a testbench or with or without a DCM. This section provides detailed descriptions of the type of design generated by the user using various options. [Figure 8-3, page 318](#) and [Figure 8-4, page 319](#) represent the system clock for differential only. For more information on the clocking structure, refer to “Clocking Scheme,” [page 325](#).

MIG outputs example_design and user_design. MIG generated example_design includes the memory controller and synthesized testbench. In order to simulate design and to test the functionality of the design example_design can be used. Whereas user_design includes the memory controller design only. User should develop test bench (User application) and should interface with MIG memory controller design. Refer to [Table 8-8, page 329](#) for user interface signals and “DDR2 SDRAM Write and Read operations” section for write and read timing shown in [Figure 8-8, page 326](#) and [Figure 8-11, page 333](#).

[Figure 8-3, page 318](#) shows a block diagram representation of the top-level module for a DDR2 SDRAM design with a DCM and a testbench. “Clocking Scheme,” [page 325](#) describes how various clocks are generated using the DCM. The input clocks can be differential or single-ended based on the system clock selection in the GUI. For differential, differential clocks sys_clk and sys_clkb appear as input ports, whereas for single-ended sys_clk_in appears as the input port. The DCM clock is instantiated in the infrastructure_top module that generates the required design clocks. reset_in_n is the active-Low system reset signal. All design resets are gated by the dcm_lock signal.

The cntrl0_led_error_output1 output signal indicates whether the case passes or fails. The testbench module does writes and reads, and also compares the read data with written data. The cntrl0_led_error_output1 signal is driven High on data mismatches. The cntrl0_data_valid_out signal indicates whether the read data is valid or not.

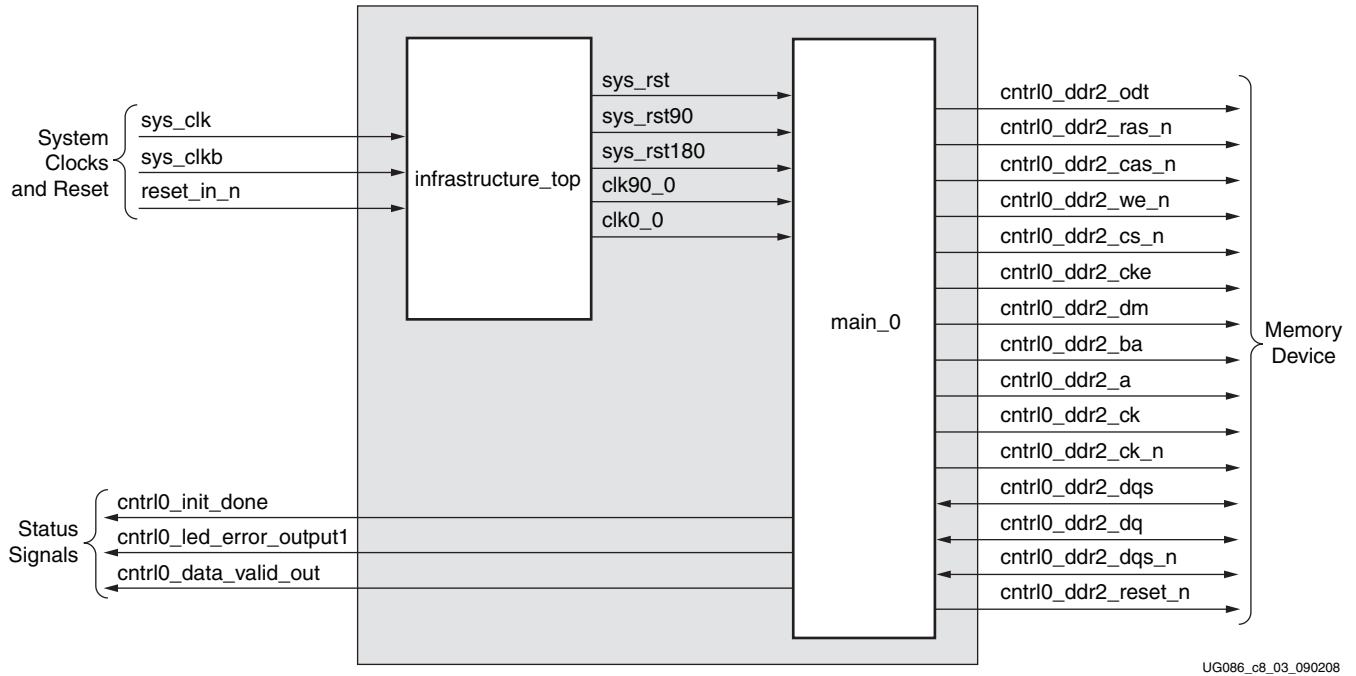


Figure 8-3: MIG Output of the DDR2 SDRAM Controller Design with a DCM and a Testbench

Figure 8-4 shows a block diagram representation of the top-level module for a DDR2 SDRAM design with a DCM but without a testbench. “Clocking Scheme,” page 325 describes how various clocks are generated using the DCM. The input clocks can be differential or single-ended based on the *System Clock* selection in the GUI.

For differential, differential clocks `sys_clk` and `sys_clkb` appear as input ports, whereas for single-ended `sys_clk_in` appears as the input port. The DCM clock is instantiated in the `infrastructure_top` module that generates the required design clocks. `reset_in_n` is the active-Low system reset signal. All design resets are gated by the `dcm_lock` signal.

The user interface signals are listed in Figure 8-4. The design provides the `clk_tb`, `clk90_tb`, `sys_rst_tb`, `sys_rst90_tb`, and `sys_rst180_tb` signals to the user in order to synchronize with the design. The signals `clk_tb`, `clk90_tb`, `sys_rst_tb`, `sys_rst90_tb`, and `sys_rst180_tb` are connected to clocks `clk_0` and `clk90_0` and reset signals `sys_rst`, `sys_rst90`, and `sys_rst180`, respectively, in the controller. If the user clock domain is different from `clk_tb`/`clk90_tb`, then the user should add FIFOs for all the inputs and outputs of the controller (user application signals) in order to synchronize them to `clk_tb`/`clk90_tb`.

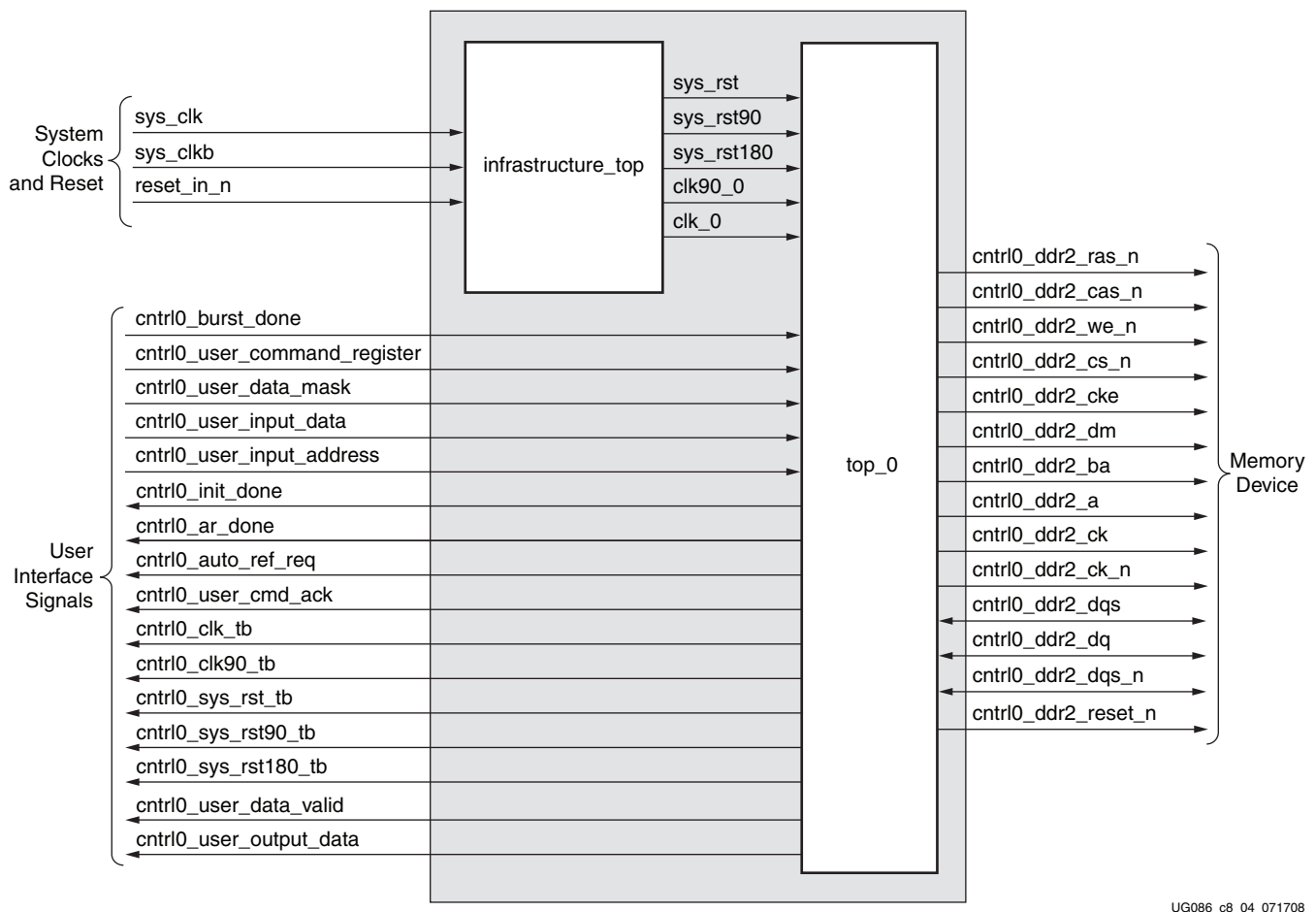
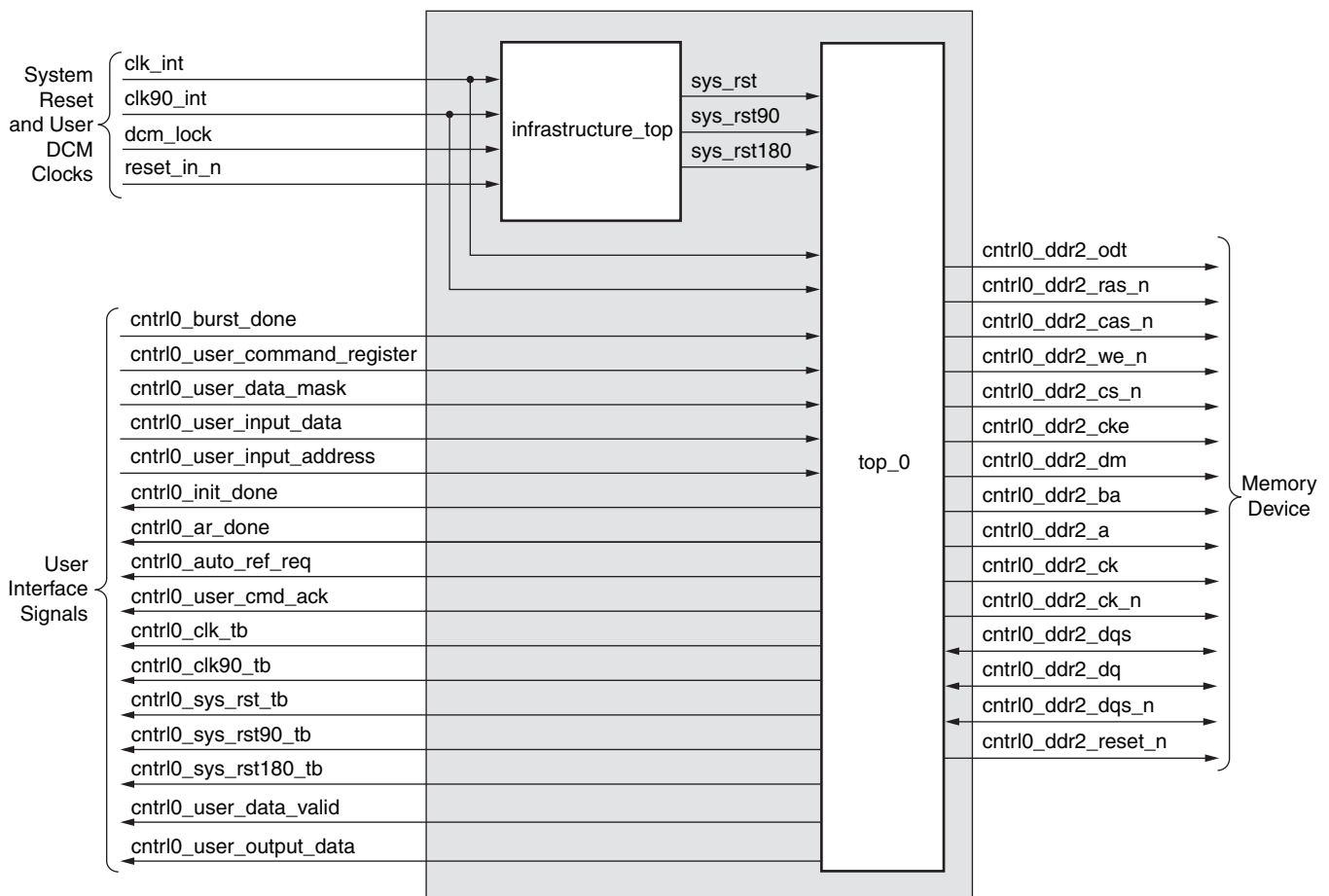


Figure 8-4: MIG Output of the DDR2 SDRAM Controller Design with a DCM but without a Testbench

Figure 8-5 shows a block diagram representation of the top-level module for a DDR2 SDRAM design without a DCM or a testbench. “Clocking Scheme,” page 325 describes how various clocks are generated using the DCM. The user should provide all the clocks and the dcm_lock signal. These clocks should be single-ended. reset_in_n is the active-Low system reset signal. All design resets are gated by the dcm_lock signal.

The user interface signals are listed in Figure 8-5. The design provides the clk_tb, clk90_tb, sys_rst_tb, sys_rst90_tb, and sys_rst180_tb signals to the user in order to synchronize with the design. The signals clk_tb, clk90_tb, sys_rst_tb, sys_rst90_tb, and sys_rst180_tb are connected to clocks clk_0 and clk90_0 and reset signals sys_rst, sys_rst90, and sys_rst180, respectively, in the controller. If the user clock domain is different from clk_tb/clk90_tb, then user should add FIFOs for all the inputs and outputs of the controller (user application signals) in order to synchronize them to clk_tb/clk90_tb.



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Figure 8-5: MIG Output of the DDR2 SDRAM Controller Design without a DCM or a Testbench

Figure 8-6 shows a block diagram representation of the top-level module for a DDR2 SDRAM design without a DCM but with a testbench. “Clocking Scheme,” page 325 describes how various clocks are generated using the DCM. The user should provide all the clocks and the dcm_lock signal. These clocks should be single-ended. reset_in_n is the active-Low system reset signal. All design resets are gated by the dcm_lock signal.

The cntrl0_led_error_output1 output signal indicates whether the case passes or fails. The testbench module does writes and reads, and also compares the read data with the written data. The cntrl0_led_error_output1 signal is driven High on data mismatches. The cntrl0_data_valid_out signal indicates whether the read data is valid or not.

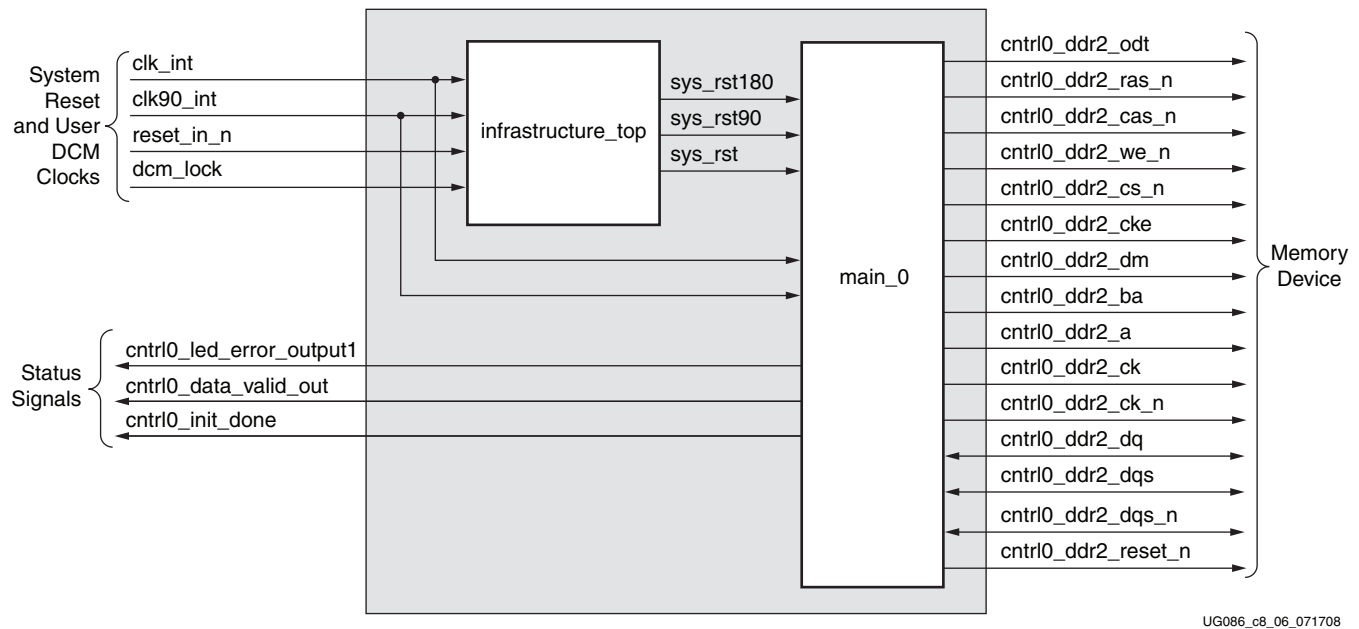


Figure 8-6: MIG Output of the DDR2 SDRAM Controller Design without a DCM but with a Testbench

All the Memory Device interface signals that are shown in Figure 8-3 through Figure 8-6 do not necessarily appear for all designs that are generated from MIG. For example, port cntrl0_ddr2_reset_n appears in the port list only for Registered DIMM designs. Similarly, cntrl0_ddr2_DQS_N does not appear for single-ended DQS designs. Port cntrl0_ddr2_dm appears only for the parts that contain a data mask. A few RDIMMs do not have a data mask, and cntrl0_ddr2_dm does not appear in the port list for these parts.

Figure 8-7 shows a detailed block diagram of the DDR2 SDRAM controller. All four blocks shown are subblocks of the `ddr2_top` module. The functionality of these blocks is explained in following sections.

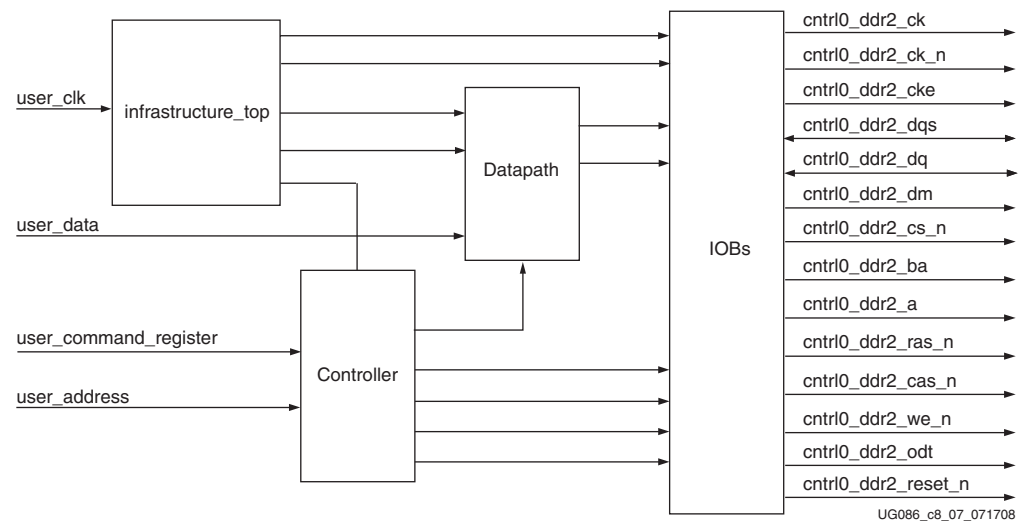


Figure 8-7: Memory Controller Block Diagram

Controller

The controller module accepts and decodes user commands and generates read, write, memory initialization, and load mode commands. The controller also generates signals for other modules.

The memory is initialized and powered up using a defined process. The controller state machine handles the initialization process upon receiving an initialization command.

Datapath

This module transmits and receives data to and from the memories. Major functions include storing the read data and transferring write data and write enable to the IOBS module. The `data_read`, `data_write`, `data_path_IOBs`, and `data_read_controller` modules perform the actual read and write functions. For more information, refer to XAPP768c [Ref 24].

Data Read Controller

This module generates all control signals that are used for the `data_read` module.

Data Read

The `data_read` module contains the read datapaths for the DDR2 SDRAM interface. Details for this module are described in XAPP768c [Ref 24].

Data Write

This module contains the write datapath for the DDR2 SDRAM interface. The write data and write enable signals are forwarded together to the DDR2 SDRAM through IOB flip-flops. The IOBs are implemented in the `datapath_IOBs` module.

Infrastructure_top

The infrastructure module generates the FPGA clock and reset signals. For differential clocking, sys_clk and sys_clkb ports are used as inputs to the IBUFGDS_LVDS_25 buffer and the output of the buffer is driven to the DCM input. For single-ended clocking, the sys_clk_in port is used as an input to the IBUFG buffer; the output of the buffer is driven to the DCM input. A DCM generates the clock and its inverted version. The infrastructure module also generates all of the reset signals required for the design.

IOBs

All input and output signals of the FPGA are implemented in the IOBs.

Test Bench

MIG generates two different RTL folders, example_design and user_design. The example_design includes the synthesizable test bench, while user_design does not include the test bench modules. The MIG test bench performs five write commands and five read commands in an alternating fashion. The number of words in a write command depends on the burst length. For a burst length of 4, every write command writes four data words. For all five write commands, the test bench writes a total of 20 data words (10 rise data words and 10 fall data words). For a burst length of 8, the test bench writes a total of 40 data words. The pattern data is shown in Table 8-2 and Table 8-3 for burst lengths of 4 and 8, respectively.

Table 8-2: Data Pattern for Burst Length of 4

Burst	Rise	Fall
1	96	69
	2C	D3
2	58	A7
	B1	4E
3	63	9C
	C6	39
4	8C	73
	18	E7
5	31	CE
	62	9D

Table 8-3: Data Pattern for Burst Length of 8

Burst	Rise	Fall
1	96	69
	2C	D3
	58	A7
	B1	4E

Table 8-3: Data Pattern for Burst Length of 8 (Cont'd)

Burst	Rise	Fall
2	63	9C
	C6	39
	8C	73
	18	E7
3	31	CE
	62	9D
	C4	3B
	88	77
4	10	EF
	21	DE
	42	BD
	85	7A
5	0A	F5
	15	EA
	2B	D4
	56	A9

The falling edge data is the complement of the rising edge data. The data pattern is repeated for the next set of five burst write commands based on the selected burst length, as given in Table 8-2 and Table 8-3. This data pattern is repeated in the same order based on the number of data words written. For data widths greater than 8, the same data pattern is concatenated for the other bits. For a 32-bit design and a burst length of 8, the data pattern for the first write command is 96969696, 69696969, 2C2C2C2C, D3D3D3D3, 58585858, A7A7A7A7, B1B1B1B1, 4E4E4E4E.

For all five write commands, five different address locations are generated, as shown in Table 8-4. Read commands read the data from the same locations where writes are performed. The column address is incremented based on the burst length from one write command to the next write command. The row address is the same for all five write commands. For the next five write commands, the row address is incremented by 2, and this continues for each subsequent group of five write commands. Only five bits are used for row address generation. The row address rolls back to the initial value on reaching the terminal value. The bank address is the same for all five write commands, but it gets incremented for the next five write commands. This continues until the terminal count value is reached, depending on whether the selected memory part has a 4- or 8-bank architecture. The MIG test bench exercises only a certain memory area. Table 8-4 provides the details of how the bank, row, and column address are incremented in the test bench.

Table 8-4: Address Generation in Test Bench

Address	Address for First Five Writes/Reads	Address for Second Five Writes/Reads	Description
Bank	0	1	<p>The bank address increments by 1. For a 2-bit bank address, the sequence is 0, 1, 2, 3.</p> <p>For a 3-bit bank address, the sequence is 0, 1, 2, 3, 4, 5, 6, 7.</p> <p>The bank address rolls back to the initial address 0 when it reaches the maximum value.</p>
Row	2	4	<p>The row address increments by 2 and starts with 2. Only five bits are used to generate the row address. 2, 4, 6, 8, 10, 12, 14, 16, 18, 20, 22, 24, 26, 28, 30 (5'b00010 to 5'b11110).</p> <p>The row address rolls back to the initial value of 2, when it reaches the maximum value.</p>
Column	0, 8, 16, 24, 32	0, 8, 16, 24, 32	<p>The column address increments in multiples of the burst length.</p> <p>For BL = 8, the address sequence for the first set of five write/read commands is 0, 8, 16, 24, 32.</p> <p>For BL = 4, the address sequence for the first set of five write/read commands is 0, 4, 8, 12, 16.</p> <p>The same column address is repeated for the next set of commands.</p>

During reads, the read data is compared with the pattern written. For example, for an 8-bit data width and a burst length of 4, the write data for a single write command is 96, 69, 2C, D3. During reads, the read pattern is compared with the 96, 69, 2C, D3 pattern. If the data read back matches with the data written, the `led_error_output1` signal is set to 0, otherwise, it is set to 1 to indicate an error condition.

Clocking Scheme

Figure 8-8 shows the clocking scheme for this design. Global and local clock resources are used.

The global clock resources consist of a DCM and several BUFGs. The local clock resources consist of regional I/O clock networks (BUFIO). The global clock architecture is discussed in this section.

The MIG tool allows the user to customize the design such that the DCM is not included. In this case, `clk_0` and `clk90_0` must be supplied by the user.

Global Clock Architecture

The user must supply a system clock running at the target frequency for the memory. This clock can be either single-ended or differential. User can select single-ended or differential clock input option from MIG GUI. Differential clocks are connected to the IBUFGDS and the single-ended clock is connected to IBUFG.

The system clock from the output of the IBUFGDS or the IBUFG is connected to the DCM to generate the various clocks used by the memory interface logic.

The DCM generates two separate synchronous clocks for use in the design, as shown in Table 8-5 and Figure 8-8. The clock structure is same for both the example design and the user design. For designs with out DCM instantiation, the DCM and the BUFGs should be instantiated at the user end to generate the required clocks.

Table 8-5: DDR2 Interface Design Clocks

Clock	Description	Logic Domain
clk0	Skew compensated replica of the input system clock.	The clock for the controller and the user interface logic, most of the DDR2 bus-related I/O flip-flops (e.g., memory clock, control/address). This is also used to register the address and command signals from the user interface.
clk90	90° phase-shifted version of clk0	Used in the user interface logic, the write data path section of physical layer, write path control logic and output flip-flops for DQ and DM. This is also used to register data from the user interface and generate the read data and read data valid signals for the user interface logic.

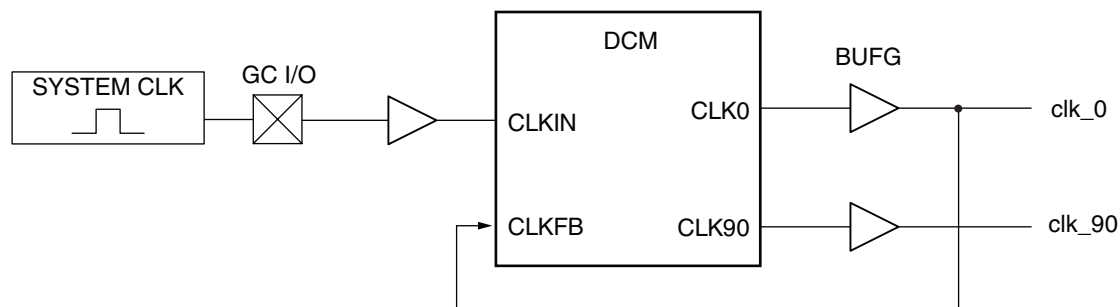


Figure 8-8: Clocking Scheme for DDR2 Interface Logic

Interface Signals

Table 8-6 shows the DDR2 SDRAM interface signals, directions, and descriptions. The signal direction is with respect to the DDR2 SDRAM controller. The `cntrl0_ddr2_reset_n` signal is present only for registered DIMMs, and the `cntrl0_ddr2_dqs_n` signal is present when DQS# Enable is selected in the Extended Mode register.

Table 8-6: DDR2 SDRAM Interface Signal Descriptions

Signal Name	Signal Direction	Description
<code>cntrl0_DDR2_A</code>	Output	Address
<code>cntrl0_DDR2_DQ</code>	Input/Output	Data
<code>cntrl0_DDR2_DQS</code>	Input/Output	Data Strobe
<code>cntrl0_ddr2_dqs_n</code>	Input/Output	Data Strobe
<code>cntrl0_DDR2_RAS_N</code>	Output	Command
<code>cntrl0_DDR2_CAS_N</code>	Output	Command
<code>cntrl0_DDR2_WE_N</code>	Output	Command
<code>cntrl0_DDR2_BA</code>	Output	Bank Address
<code>cntrl0_DDR2_CK</code>	Output	Clock
<code>cntrl0_DDR2_CK_N</code>	Output	Inverted Clock
<code>cntrl0_DDR2_CS_N</code>	Output	Chip Select
<code>cntrl0_DDR2_CKE</code>	Output	Clock Enable
<code>cntrl0_DDR2_DM</code>	Output	Data Mask
<code>cntrl0_DDR2_ODT</code>	Output	On-Die Termination
<code>cntrl0_ddr2_reset_n</code>	Output	Reset

Table 8-7 describes the DDR2 SDRAM controller system interface signals. Except for the cntlr0_led_error_output1 signal, all other signals in Table 8-7 are present in designs either with or without testbenches. The cntlr0_led_error_output1 signal is present only in designs with a testbench.

Table 8-7: DDR2 SDRAM Controller System Interface Signals

Signal Names	Direction	Description
sys_clk and sys_clkb	Input	These signals are the system clock differential signals. They are driven from the user application for designs with DCMs. These two signals are given to a differential buffer, and the output of the differential buffer is connected to a clock's DCM. The DCM generates the required clocks to the design modules. These signals are not present when the design is generated without a DCM. When there is no DCM, the user application should drive the required clocks to the design.
reset_in_n	Input	This is the system reset signal. By default, this signal is active Low. The parameter file contains a parameter called RESET_ACTIVE_LOW. An active-High reset input can be selected by changing this parameter to 0.
cntrl0_led_error_output1	Output	This signal is asserted when there is a read data mismatch with the write data. This signal is usually used to connect the LED on the hardware to indicate a data error.
cntrl0_data_valid_out	Output	This signal is asserted when there is valid read data in the read FIFO. The signal LED error output is generated when this signal is High and there is a data mismatch. This signal can be driven to a status LED on the hardware.
cntrl0_rst_dqs_div_in	Input	This loopback signal is connected to the cntrl0_rst_dqs_div_out signal on the board. Refer to XAPP768c [Ref 24] for the functionality of this signal.
cntrl0_rst_dqs_div_out	Output	This loopback signal is connected to the cntrl0_rst_dqs_div_in signal on the board.
dcm_lock	Input	This signal is present only in designs without a DCM.
cntrl0_init_done	Output	The DDR2 SDRAM controller asserts this signal to indicate that the DDR2 SDRAM initialization is complete.

Table 8-8 describes the DDR2 SDRAM controller system interface signals in designs without a testbench.

Table 8-8: DDR2 SDRAM Controller User Interface Signals (without a Testbench)

Signal Names	Direction ⁽¹⁾	Description	
cntrl0_user_input_data[(2 <i>n</i> −1):0]	Input	This bus is the write data to the DDR2 SDRAM from the user interface, where <i>n</i> is the width of the DDR2 SDRAM data bus. The DDR2 SDRAM controller converts single data rate to double data rate on the physical layer side. The data is valid on the DDR2 SDRAM write command. In 2 <i>n</i> , the MSB is rising-edge data and the LSB is falling-edge data.	
cntrl0_user_data_mask[(2 <i>m</i> −1):0]	Input	This bus is the data mask for write data. Like user_input_data, it is twice the size of the data mask bus at memory, where <i>m</i> is the size of the data mask at the memory interface. In 2 <i>m</i> , the MSB applies to rising-edge data and the LSB applies to falling-edge data.	
cntrl0_user_input_address [(ROW_ADDRESS + COLUMN_ADDRESS + BANK_ADDRESS − 1):0] ⁽²⁾	Input	This bus consists of the row address, the column address, and the bank address for DDR2 SDRAM writes and reads. The address sequence starting from the LSB is bank address, column address, and row address.	
cntrl0_user_command_register[2:0]	Input	Supported user commands for the DDR2 SDRAM controller:	
		user_command[2:0]	User Command Description
		000	NOP
		010	Initialize memory
		100	Write Request
		110	Read Request
	Others	Reserved	
cntrl0_burst_done	Input	This signal is used to terminate read or write command. This signal must be asserted after the last address for two clocks for BL=4 and for four clocks for BL =8. The DDR2 SDRAM controller supports write burst or read burst capability for a single row. The user must terminate the transfer on a column boundary and must re-initialize the controller for the next row of transactions on a column boundary.	
cntrl0_user_output_data[(2 <i>n</i> −1):0]	Output	This is the read data from the DDR2 SDRAM. The DDR2 SDRAM controller converts the DDR data from the DDR2 SDRAM to SDR data. As the DDR data is converted to SDR data, the width of this bus is 2 <i>n</i> , where <i>n</i> is data width of the DDR2 SDRAM data bus.	
cntrl0_user_data_valid	Output	When asserted, this signal indicates user_output_data[(2 <i>n</i> −1):0] is valid.	

Table 8-8: DDR2 SDRAM Controller User Interface Signals (without a Testbench) (Cont'd)

Signal Names	Direction ⁽¹⁾	Description
cntrl0_user_cmd_ack	Output	This is the acknowledgement signal for a user read or write command. It is asserted by the DDR2 SDRAM controller during a write or read to/from the DDR2 SDRAM. The user should not issue any new commands to the controller until this signal is deasserted.
cntrl0_init_done	Output	The DDR2 SDRAM controller asserts this signal to indicate that the DDR2 SDRAM initialization is complete.
cntrl0_auto_ref_req ⁽³⁾	Output	This signal is asserted based on the frequency. For example, for a frequency of 166 MHz, the signal is asserted every ~7.6 μ s. It is asserted until the controller issues an auto-refresh command to the memory. Upon seeing this signal, the user should terminate any ongoing command after the current burst transaction by asserting the cntrl0_burst_done signal. The frequency with which this signal is asserted is determined by the MAX_REF_CNT value in parameter file. cntrl0_auto_ref_req indicates the refresh request to the memory, and cntrl0_ar_done indicates completion of the auto-refresh command.
cntrl0_ar_done ⁽³⁾	Output	This indicates that the auto-refresh command was completed to DDR2 SDRAM. The DDR2 SDRAM controller asserts this signal for one clock after giving an auto-refresh command to the DDR2 SDRAM and completion of T _{RFC} time. The T _{RFC} time is determined by the rfc_count_value value in the parameter file. The user can assert the next command any time after the assertion of the cntrl0_ar_done signal.

Notes:

1. All of the signal directions are with respect to the DDR2 SDRAM controller.
2. Linear addressing is used, i.e., the row address immediately follows the column address bits, and the bank address follows the row address bits, thus supporting more devices. The number of address bits used depends on the density of the memory part. The controller ignores the unused bits, which can all be tied High.
3. For more information on auto refresh, refer to “Auto Refresh,” page 335.

Resource Utilization

A local inversion clocking technique is used in this design. The DCM generates only clk0 and clk90. One DCM and two BUFGMUXs are used. The Spartan-3 generation FPGA designs operate at 166 MHz and below.

DDR2 SDRAM Initialization

Before issuing the memory read and write commands, the controller initializes the DDR2 SDRAM using the memory initialization command. The user can give the initialization command only after all reset signals are deactivated. The controller is in the reset state for 200 μ s after power up. For design optimization, a 200 μ s timer is generated from the refresh counter. The refresh timer is a function of frequency. Therefore, at lower frequencies, the 200 μ s timer waits more than 200 μ s. Because wait200 happens only during the power-up sequence, design performance is not degraded. All resets are asserted for 200 μ s because DDR2 SDRAM requires a 200 μ s delay prior to applying an executable command after all

power supply and reference voltages are stable. The controller asserts clock-enable to memory after 200 μ s.

Load mode parameters are to be selected from the GUI while generating the design. These parameters are updated by MIG in the parameter file. When the INIT command is executed, the DDR2 SDRAM controller passes these values to the Memory Load Mode register. When the DDR2 SDRAM is initialized, the DDR2 SDRAM controller asserts the `init_done` signal.

Figure 8-9 shows the timing for the memory initialization command.

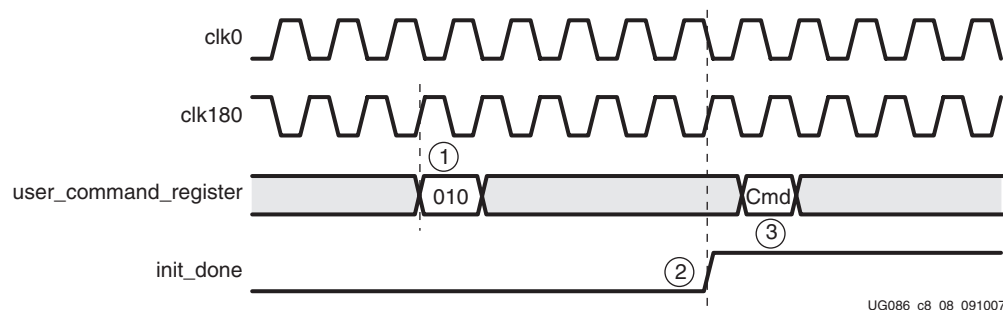


Figure 8-9: **DDR2 SDRAM Initialization**

1. The user places the initialization command on `user_command_register[2:0]` on a falling edge of `clk0` for one clock cycle. This starts the initialization sequence.
2. The DDR2 SDRAM controller indicates that the initialization is complete by asserting the `init_done` signal on a falling edge of `clk0`. The `init_done` signal is asserted throughout the period.
3. After `init_done` is asserted, the user can pass the next command at any time.

DDR2 SDRAM Write and Read Operations

In Spartan FPGA designs, prior to issuing a read or write operation, the user must assert the first address and command simultaneously and wait for a command acknowledge signal. The assertion time of the command acknowledge varies depending on the controller status. After the command acknowledge is asserted, the user waits for three clock cycles before sending the next address. This three clock cycle time is the Active-to-Command (t_{RCD}) delay for a read or write command as defined in the memory specification. Subsequent addresses are sent once every two clock cycles for a burst length of four.

If user clock domain is different from `clk0` and `clk90` of MIG, then user has to synchronize all the user interface signals to the `clk0` and `clk90` that are shown in Figure 8-10, page 332 and Figure 8-11, page 333.

Write

Figure 8-10 shows the timing diagram for a write to DDR2 SDRAM for a burst length of four. The user initiates the write command by sending a Write instruction to the DDR2 SDRAM controller. To terminate a write burst, the user asserts the burst_done signal for two clocks after the last user_input_address. The burst_done signal should be asserted for two clocks for burst lengths of four and four clocks for burst lengths of eight.

The write command is asserted on the falling edge of clk0. In response to a write command, the DDR2 SDRAM controller acknowledges with the usr_cmd_ack signal on a falling edge of clk0. If the controller is busy with a refresh, the usr_cmd_ack signal is not asserted until after the refresh command cycle completes. The user asserts the first address (row + column + bank address) with the write command and keeps it asserted for three clocks after usr_cmd_ack assertion. Any subsequent write addresses are asserted on alternate falling edges of clk0 after deasserting the first memory address for a burst length of four, and it is asserted once in four clocks for a burst length of eight. The first user data is asserted on a rising edge of clk90 after usr_cmd_ack is asserted. As the SDR data is converted to DDR data, the width of this bus is $2n$, where n is data width of DDR2 SDRAM data bus.

For a burst length of four, only two data words (each of $2n$) are given to the DDR2 SDRAM controller for each user address, and four data words are given for a burst length of eight. Internally, the DDR2 SDRAM controller converts into four data words for a burst length of four and eight data words for a burst length of eight, each of n bits. To terminate the write burst, the user asserts burst_done on a rising edge of clk180 for two clocks for a burst length of four and four clocks for a burst length of eight. The burst_done signal is asserted after the last memory address. Any further commands to the DDR2 SDRAM controller are given only after the usr_cmd_ack signal is deasserted. After burst_done is asserted, the controller terminates the burst and issues a precharge to the memory. The usr_cmd_ack signal is deasserted after completion of the precharge.

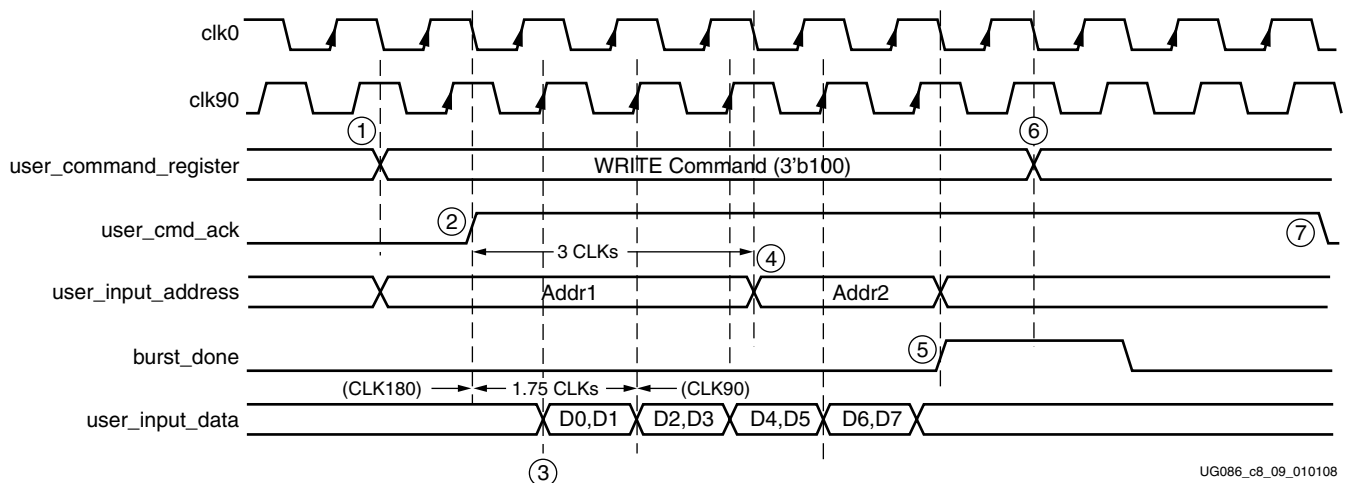


Figure 8-10: DDR2 SDRAM Write Burst, Burst Lengths of Four and Two Bursts

1. A memory write is initiated by issuing a write command to the DDR2 SDRAM controller. The write command must be asserted on a falling edge of clk0.
2. The DDR2 SDRAM controller acknowledges the write command by asserting the user_cmd_ack signal on a falling edge of clk0. The user_cmd_ack signal is asserted a minimum of one clock cycle after the write command is asserted. If the controller is

- busy with a refresh, the `usr_cmd_ack` signal is not asserted until after the refresh command cycle completes.
3. The first `user_input_address` must be placed along with the command. The input data is asserted with the `clk90` signal after the `user_cmd_ack` signal is asserted.
 4. The user asserts the first address (row + column + bank address) with the write command and keeps it asserted for three clocks after `usr_cmd_ack` assertion. The `user_input_address` signal is asserted on a falling edge of `clk0`. All subsequent addresses are asserted on alternate falling edges of `clk0`.
 5. To terminate the write burst, `burst_done` is asserted after the last `user_input_address`. The `burst_done` signal is asserted for two clock cycles.
 6. The user command is deasserted after `burst_done` is asserted.
 7. The controller deasserts the `user_cmd_ack` signal after completion of precharge to the memory. The next command must be given only after `user_cmd_ack` is deasserted. Back-to-back write operations are supported only within the same bank and row.

Read

The user initiates a memory read with a read command to the DDR2 SDRAM controller. [Figure 8-11](#) shows the memory read timing diagram for a burst length of four.

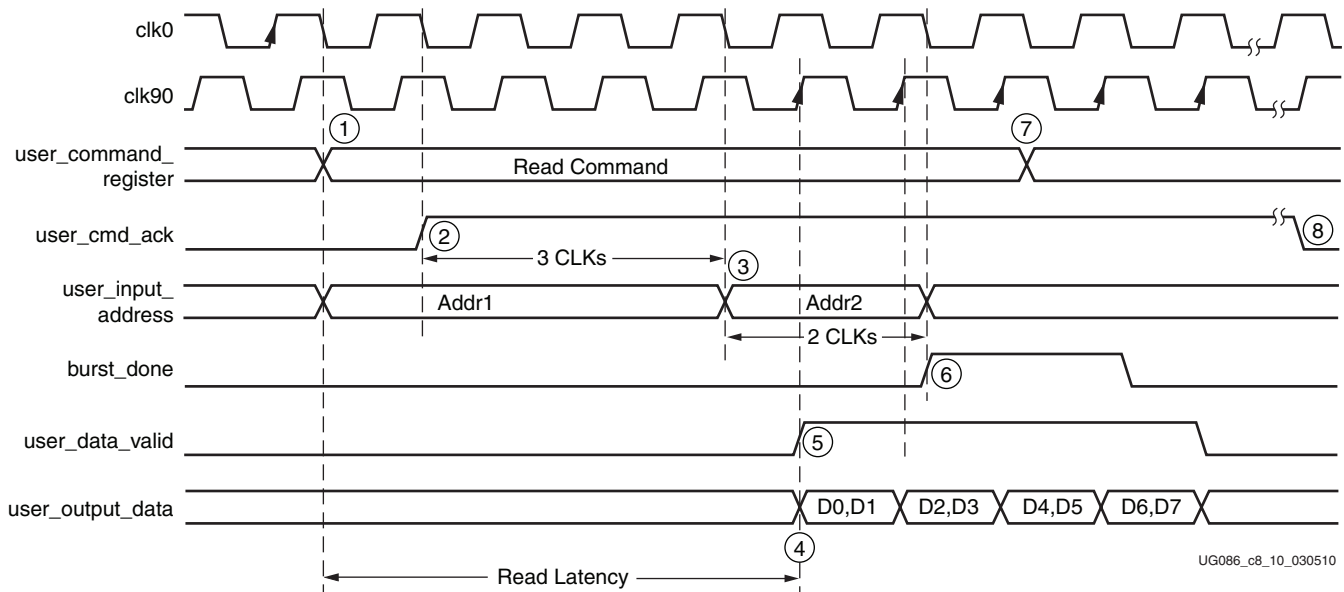


Figure 8-11: DDR2 SDRAM Read, Burst Lengths of Four and Two Bursts

The user provides the first memory address with the read command, and subsequent memory addresses upon receiving the `usr_cmd_ack` signal. Data is available on the user data bus with the `user_data_valid` signal. To terminate read burst, the user asserts the `burst_done` signal on a falling edge of `clk0` for two clocks with the deassertion of the last `user_input_address`. All subsequent addresses are asserted on alternate clocks for burst lengths of four, and subsequent addresses are asserted once every four clock cycles for burst lengths of eight.

For burst lengths of four, the `burst_done` signal is asserted for two clocks after the last address and for four clocks for burst lengths of eight.

The read command flow is similar to the write command flow.

1. A memory read is initiated by issuing a read command to the DDR2 SDRAM controller. The read command is accepted on a falling edge of `clk0`.
2. The first read address must be placed along with the read command. In response to the read command, the DDR2 SDRAM controller asserts the `user_cmd_ack` signal on a falling edge of `clk0`. The `user_cmd_ack` signal is asserted a minimum of one clock cycle after the read command is asserted. If the controller is busy with a refresh, the `usr_cmd_ack` signal is not asserted until after the refresh command cycle completes.
3. The user asserts the first address (row + column + bank address) with the read command and keeps it asserted for three clocks after `usr_cmd_ack` is asserted. The `user_input_address` signal is then accepted on the falling edge of `clk0`. All subsequent memory read addresses are asserted on alternate falling edges of `clk0`.
4. The data on `user_output_data` is valid only when the `user_data_valid` signal is asserted.
5. The data read from the DDR2 SDRAM is available on `user_output_data`, which is asserted with `clk90`. Because the DDR2 SDRAM data is converted to SDR data, the width of this bus is $2n$, where n is the data width of the DDR2 SDRAMs. For a read burst length of four, the DDR2 SDRAM controller outputs only two data words with each user address.
6. To terminate the read burst, `burst_done` is asserted for two clocks on the falling edge of `clk0`. The `burst_done` signal is asserted after the last memory address.
7. The user command is deasserted after `burst_done` is asserted.
8. The controller deasserts the `user_cmd_ack` signal after completion of precharge to the memory. Any further commands to the DDR2 SDRAM controller should be given after `user_cmd_ack` is deasserted. Back-to-back read operations are supported only within the same bank and row. Approximately 17 clock cycles pass between the time a read command is asserted on the user interface and the time data becomes available on the user interface.

Table 8-9 shows the read latency for $CL = 3$.

Table 8-9: Read Command to Read Data Latency

Parameter	Number of Clocks
User read command to command ack	1
Command ack to active command	3
Active to read command	3
Memory read command to data valid	10
Total clocks	17

In general, read latency varies based on the following parameters:

- CAS latency
- If the user issue the commands before initialization is complete, the latency cannot be determined

Auto Refresh

The DDR2 SDRAM controller does a memory refresh at intervals determined by the frequency. For example, for a frequency of 166 MHz, an auto-refresh request is raised every ~7.6 μ s. The user must terminate any ongoing commands when auto_ref_req flag is asserted after the current burst transaction by asserting the burst_done signal. The auto_ref_req flag is asserted until the controller issues a refresh command to the memory. The user must wait for completion of the auto-refresh command before giving any commands to the controller when auto_ref_req is asserted.

The ar_done signal is asserted by the DDR2 SDRAM controller upon completion of the auto-refresh command—i.e., after T_{RFC} time. The ar_done signal is asserted on the falling edge of clk0 for one clock cycle.

The controller sets the MAX_REF_CNT value in the parameter file according to the frequency and selected memory component for a refresh interval (7.7 μ s). The rfc_count_value setting in the parameter file defines T_{RFC} , the time between the refresh command to Active or another refresh command.

After completion of the auto-refresh command, the next command can be given any time after ar_done is asserted.

The current testbench generates five consecutive write bursts followed by five read burst commands. For every group of five write/read commands, the controller issues an active command followed by five write/read commands, and then a precharge command to the memory. All five burst commands take up a maximum of 20 clock cycles. After every precharge command, the controller state machine goes to an idle state and checks for an auto_ref_req. When an auto_ref_req is asserted, the controller issues an auto refresh command to the memory if it is in an idle state. In the worst case, the controller takes 20 clocks to go from burst_done to the auto refresh command and to the memory. The controller issues auto refresh commands to the memory within 40 clock cycles after auto_ref_req is asserted. Because the delay from auto_ref_req to the refresh command to the memory is within the specified number of clocks even in the worst case scenario, the testbench does not need to terminate the write or read transaction on the auto_ref_req signal.

For example, at 77 MHz, an auto_ref_req is generated every 7.292 μ s, and at 166 MHz, it is generated every 7.572 μ s. The MAX_REF_CNT parameter is set to the following values at 77 MHz and 166 MHz frequencies to allow 40 clock cycles of delay from auto_ref_req to the refresh command:

Average periodic refresh = 7.8125 μ s

$MAX_REF_CNT = (7812.5 \text{ ns} - 40 \times \text{clk_period}) / \text{clk_period}$

At 77 MHz (13 ns): $MAX_REF_CNT = (7812.5 \text{ ns} - 40 \times 13) / 13 = 7292.5 / 13 = 560$

At 166 MHz (6 ns): $MAX_REF_CNT = (7812.5 \text{ ns} - 40 \times 6) / 6 = 7572.5 / 6 = 1262$

User transactions should be terminated within 20 clock cycles of the auto_ref_req signal being asserted. The ar_done signal is asserted for one clock period by the controller on completion of an auto refresh command (i.e., after T_{RFC} time). Normal read and write commands can be issued to the controller any time after ar_done is asserted.

Changing the Refresh Rate

Change the global `define (for Verilog) or constant (for VHDL) variable MAX_REF_CNT in mymodule_parameters_0.v (or .vhd) so that MAX_REF_CNT = (refresh interval in

clock periods) = (refresh interval) / (clock period). For example, for a refresh rate of 7.7 μ s with a memory bus running at 133 MHz:

$$\text{MAX_REF_CNT} = 7.7 \mu\text{s} / (\text{clock period}) = 7.7 \mu\text{s} / 7.5 \text{ ns} = 1026 \text{ (decimal)} = 0x402$$

If the above value exceeds $2^{\text{MAX_REF_WIDTH}} - 1$, the value of MAX_REF_WIDTH must be increased accordingly in parameters_0.v (or .vhd) to increase the width of the counter used to track the refresh interval.

Load Mode

MIG does not support the LOAD MODE command.

UCF Constraints

Some constraints are required to successfully create the design. The following examples explain the different constraints in the UCF for XST.

Calibration Circuit Constraints

All LUTs in the matched delay circuits are constrained to specific locations in the device.

Example:

```
INST "infrastructure_top0/cal_top0/tap_dly0/10" RLOC=X0Y6;
INST "infrastructure_top0/cal_top0/tap_dly0/10" U_SET =
    delay_calibration_chain;
INST "infrastructure_top0/cal_top0/tap_dly0/gen_tap1[0].r" RLOC=X0Y6;
INST "infrastructure_top0/cal_top0/tap_dly0/gen_tap1[0].r" U_SET =
    delay_calibration_chain;
INST "infrastructure_top0/cal_top0/tap_dly0/gen_tap1[1].r" RLOC=X0Y6;
INST "infrastructure_top0/cal_top0/tap_dly0/gen_tap1[1].r" U_SET =
    delay_calibration_chain;
```

Data and Data Strobe Constraints

Data and data strobe signals are assigned to specific pins in the device; placement constraints related to the dqs_delay circuit and the FIFOs used for the data_read module are specified.

Example:

```
NET "cntrl0_DDR2_DQS[0]" LOC = Y6;
INST "ddr2_top0/data_path0/data_read_controller0/gen_delay[0].dqs_delay_col0/
one" LOC = SLICE_X0Y110;
INST "ddr2_top0/data_path0/data_read_controller0/gen_delay[0].dqs_delay_col0/
one" BEL = F;
NET "cntrl0_DDR2_DQ[0]" LOC = Y5;
INST "ddr2_top0/data_path0/data_read0/gen_strobe[0].strobe/fifo0_bit0" LOC =
SLICE_X2Y111;
```

MAXDELAY Constraints

The MAXDELAY constraints define the maximum allowable delay on the net. Following are the list of MAXDELAY constraints used in Spartan FPGA designs in the UCF on different nets. The values provided here vary depending on FPGA family and the device type. Some values are dependent on frequency. The constraints shown here are from example_design. The hierarchy paths of the nets are different between example_design and user_design.

```
NET "infrastructure_top0/cal_top0/tap_dly0/tap[7]" MAXDELAY = 350ps;
NET "infrastructure_top0/cal_top0/tap_dly0/tap[15]" MAXDELAY = 350ps;
NET "infrastructure_top0/cal_top0/tap_dly0/tap[23]" MAXDELAY = 350ps;
```

These constraints are used to minimize the tap delay inverter connection wire length. This delay should be minimized to calibrate the delay of a tap (LUT element) accurately. These values are independent of frequency and vary from family to family and device to device. Without these constraints, the tool might synthesize longer routes between the tap connections. Inappropriate delays in this circuit could cause the design to fail in hardware.

```
NET "main_00/top0/dqs_int_delay_in*" MAXDELAY = 675ps;
```

This constraint is used for the DQS nets from the I/O pad to the input of the LUT delay chain. Without this constraint, the nets take unpredictable delays that affect the Data Valid window. In Spartan-3 generation FPGA designs, data is latched using the DQS signal. In order to latch the correct data, DQS is delayed using LUT delay elements to center-align with respect to the input read data. Incorrect data could be latched if the delays on this net are unpredictable. Unpredictable delays might also cause the design to have intermittent failures, which are difficult to debug in hardware.

```
NET "main_00/top0/dqs_div_rst" MAXDELAY = 460ps;
```

The net `dqs_div_rst` is the loopback signal. This signal is used as an enable for read data FIFOs and FIFO write pointers after it is delayed using the LUT delay elements. The overall delay on this net should be comparable with the delay on the DQS signal. This net is constrained to control the overall delay. Both the `dqs_div_rst` and DQS signals take similar paths. If the delay on the `dqs_div_rst` signal is higher, the first read data from memory might be missed.

```
NET
"main_00/top0/data_path0/data_read_controller0/gen_delay*dqs_delay_col
*/delay*" MAXDELAY = 140ps;
NET
"main_00/top0/data_path0/data_read_controller0/rst_dqs_div_delayed/
delay*" MAXDELAY = 140 ps;
```

These constraints are required to minimize the wire delays between the LUT elements of a LUT delay chain that is used to delay the DQS and `rst_dqs_div` loopback signal. Higher wire delays between LUT delay elements can shift the data valid window, which in turn can cause incorrect data to be latched. Therefore, the MAXDELAY constraint is required for these nets.

```
NET "main_00/top0/data_path0/data_read_controller0/rst_dqs_div"
MAXDELAY = 3383 ps;
NET "main_00/top0/data_path0/data_read0/fifo*_wr_en*"
MAXDELAY = 3007ps;
```

These constraints are required because these paths are not constrained otherwise. The total delay on the `rst_dqs_div` and `fifo_wr_en` nets must not exceed the clock period. The total delay on both the nets is set to 85% of the clock period, leaving 15% as margin. These delays vary with frequency.

```
NET "main_00/top0/data_path0/data_read0/fifo*_wr_addr[*]"
MAXDELAY = 5610ps;
```

The MAXDELAY constraint is required on FIFO write address because this path is not constrained otherwise. This is a single clock cycle path. It is set to 80% of the clock period, leaving 20% as margin because this net generally meets the required constraint.

The FROM-TO constraints are:

```
NET "infrastructure_top0/clk_dcm0/clk" TNM_NET = "clk0";
NET "main_00/top0/data_path0/dqs_delayed_col*" TNM_NET = "dqs_clk";
TIMESPEC "TS_CLK" = FROM "clk0" TO "dqs_clk" 18 ns DATAPATHONLY;
NET "infrastructure_top0/clk_dcm0/clk90" TNM_NET = "clk90";
TIMESPEC "TS_CLK90" = FROM "dqs_clk" TO "clk90" 18 ns DATAPATHONLY;
NET "main_00/top0/data_path0/data_read_controller0/gen_wr_en*
fifo*_wr_en_inst/clk"
TNM_NET = "fifo_we_clk";
TIMESPEC "TS_WE_CLK" = FROM "dqs_clk" TO "fifo_we_clk" 5 ns
DATAPATHONLY;
NET "main_00/top0/data_path0/data_read_controller0/gen_wr_addr*fifo*
_wr_addr_inst/clk" TNM_NET = "fifo_waddr_clk";
TIMESPEC "TS_WADDR_CLK" = FROM "dqs_clk" TO "fifo_waddr_clk" 5 ns
DATAPATHONLY;
```

These paths are not the real timing paths in the design context. To get rid of unconstrained paths, FROM-TO constraints are used. The values used here are not related to the design clock period, but are chosen such that no violations are reported. There is no restriction on these values, and the constraints can always be relaxed if there are any timing violations.

I/O Banking Rules

There are I/O banking rules to be followed for I/O pin allocations, stating that the I/O signals allocated in a bank should adhere to compatible I/O standards. Refer to the “Rules Concerning Banks” section for additional information regarding I/O banking rules in DS099 [Ref 28].

Design Notes

The DDR2 SDRAM design is not validated on hardware. The MAXDELAY constraints in the UCF are set based on the selected frequency.

Calibration circuit details and data capture techniques are covered in XAPP768c [Ref 24].

Tool Output

When the design is generated from the tool, it outputs docs, example_design, and user_design folders. The example_design consists of the design *with* test_bench, and user_design consists of the design *without* test_bench. Each folder contains rtl, par, synth, and sim folders. The sim folder contains simulation files for the generated design. The sim folder contains the external testbench, memory model, and .do file to simulate the generated design. The memory model files are currently generated in Verilog only. To learn more details about the files in the sim folder and to simulate the design, refer to “Simulation Guide,” page 499.

For single-rank DIMMs, MIG outputs only the base part memory model. In the simulation testbench (sim_tb_top in the sim folder), MIG instantiates the required number of memory models. For example, a 1 GB single-rank DIMM with the base part is 1 Gb, and MIG instantiates the base model eight times. If the MIG generated memory model is to be used with the user’s test bench, multiple instances should be used based on the selected configuration.

The MIG output memory model considers the MEM_BITS parameter by default for memory range allocation. This covers only a partial memory range, i.e., $2^{\text{MEM_BITS}}$. To

allocate the full memory range, the MAX_MEM parameter should be set in the memory model, which in turn sets the full_mem_bits parameter for memory allocation. Allocating the full memory range might exceed the memory of the operating system, thus causing memory allocation failure in simulations.

DDR2 SDRAM Signal Allocations

MIG allows banks to be selected for different classes of memory signals. [Table 8-10](#) shows the list of signals allocated in a group from bank selection checkboxes.

Table 8-10: DDR2 SDRAM Signal Allocations

Bank Selected	Signals Allocated in the Group
Address	Memory address and memory control
Data	Data, data mask, data strobes and memory clock signals
System Control	System reset from user interface and status signals
System Clock	System clocks from the user interface

Supported Devices

The design generated out of MIG is independent of memory speed grade, hence the package part of the memory component is replaced with X, where X indicates a don't care condition. See [Appendix G, "Low Power Options."](#)

The tables below list the components ([Table 8-11](#)) and DIMMs ([Table 8-12](#) through [Table 8-14](#)) supported by the tool for Spartan-3 FPGA DDR2 local clocking designs.

Table 8-11: Supported Components for DDR2 SDRAM Local Clocking (Spartan-3 FPGAs)

Components	Packages (XX)	Components	Packages (XX)
MT47H64M4XX-3	BP	MT47H16M16XX-3	BG
MT47H64M4XX-37E	BP	MT47H16M16XX-37E	BG
MT47H64M4XX-5E	BP	MT47H16M16XX-5E	BG
MT47H128M4XX-3	B6,CB,GB	MT47H32M16XX-3	BN,CC,FN,GC
MT47H128M4XX-37E	B6,CB,GB	MT47H32M16XX-37E	BN,CC,FN,GC
MT47H128M4XX-5E	B6,CB,GB	MT47H32M16XX-5E	BN,CC,FN,GC
MT47H256M4XX-3	BT,HQ	MT47H64M16XX-3	BT,HR
MT47H256M4XX-37E	BT,HQ	MT47H64M16XX-37E	BT,HR
MT47H256M4XX-5E	BT,HQ	MT47H64M16XX-5E	BT,HR
MT47H512M4XX-3	HG	MT47H128M16XX-3	HG
MT47H512M4XX-37E	HG	MT47H128M16XX-37E	HG
MT47H512M4XX-5E	HG	MT47H128M16XX-5E	--
MT47H32M8XX-3	BP	HYB18T1G800XXXX-3S	BF,BFL,BC
MT47H32M8XX-37E	BP	HYB18T1G800XXXX-37	BF,BFL,BC
MT47H32M8XX-5E	BP	HYB18T1G160XXXX-3S	BF,BFV,BFL,BC

Table 8-11: Supported Components for DDR2 SDRAM Local Clocking (Spartan-3 FPGAs) (Cont'd)

Components	Packages (XX)	Components	Packages (XX)
MT47H64M8XX-3	B6,CB,F6,GB	HYB18T1G160XXXX-37	BF,BFV,BFL,BC
MT47H64M8XX-37E	B6,CB,F6,GB	HYB18T1G400XXXX-3S	BF,BFL,BC
MT47H64M8XX-5E	B6,CB,F6,GB	HYB18T1G400XXXX-37	BF,BFL,BC
MT47H128M8XX-3	BT,HQ	HYB18T512800XXXX-3S	B2F,B2C,B2FL
MT47H128M8XX-37E	BT,HQ	HYB18T512800XXXX-37	B2F,B2C,B2FL
MT47H128M8XX-5E	BT,HQ	HYB18T512160XXXX-3S	B2F,B2C,B2FL
MT47H256M8XX-3	HG	HYB18T512160XXXX-37	B2F,B2C,B2FL
MT47H256M8XX-37E	HG	HYB18T512400XXXX-3S	B2F,B2C,B2FL
MT47H256M8XX-5E	HG	HYB18T512400XXXX-37	B2F,B2C,B2FL

Table 8-12: Supported Unbuffered DIMMs for DDR2 SDRAM Local Clocking (Spartan-3 FPGAs)

Unbuffered DIMMs	
MT4HTF1664AY-667	MT8HTF6464AY-40E
MT4HTF1664AY-40E	MT8HTF12864AY-667
MT4HTF1664AY-53E	MT8HTF12864AY-40E
MT4HTF3264AY-667	MT8HTF12864AY-53E
MT4HTF3264AY-40E	MT9HTF3272AY-667
MT4HTF3264AY-53E	MT9HTF3272AY-40E
MT4HTF6464AY-667	MT9HTF3272AY-53E
MT4HTF6464AY-40E	MT9HTF6472AY-667
MT4HTF6464AY-53E	MT9HTF6472AY-53E
MT8HTF6464AY-667	MT9HTF6472AY-40E
MT8HTF6464AY-53E	--

Table 8-13: Supported Registered DIMMs for DDR2 SDRAM Local Clocking (Spartan-3 FPGAs)

Registered DIMMs	
MT9HTF3272Y-53E	MT18HTF6472Y-53E
MT9HTF3272PY-53E	MT18HTF6472PY-53E
MT9HTF3272Y-40E	MT18HTF6472Y-40E
MT9HTF3272PY-40E	MT18HTF6472PY-40E
MT9HTF6472Y-53E	MT18HTF12872Y-53E
MT9HTF6472PY-53E	MT18HTF12872PY-53E
MT9HTF6472Y-40E	MT18HTF12872Y-40E
MT9HTF6472PY-40E	MT18HTF12872PY-40E
MT9HTF12872Y-53E	MT18HTF25672Y-53E

Table 8-13: Supported Registered DIMMs for DDR2 SDRAM Local Clocking (Spartan-3 FPGAs) (Cont'd)

Registered DIMMs	
MT9HTF12872PY-53E	MT18HTF25672PY-53E
MT9HTF12872Y-40E	MT18HTF25672Y-40E
MT9HTF12872PY-40E	MT18HTF25672PY-40E
MT18HTF6472G-53E	--

Table 8-14: Supported SODIMMs for DDR2 SDRAM Local Clocking (Spartan-3 FPGAs)

SODIMMs	
MT4HTF1664HY-667	MT8HTF3264HY-53E
MT4HTF1664HY-53E	MT8HTF3264HY-40E
MT4HTF1664HY-40E	MT8HTF6464HY-667
MT4HTF3264HY-667	MT8HTF6464HY-53E
MT4HTF3264HY-53E	MT8HTF6464HY-40E
MT4HTF3264HY-40E	MT9HTF12872CHY-667
MT8HTF3264HY-667	MT9HTF12872CHY-53E

The tables below list the components (Table 8-15) and DIMMs (Table 8-16 through Table 8-18) supported by the tool for Spartan-3A/AN FPGA DDR2 local clocking designs.

Table 8-15: Supported Components for DDR2 SDRAM Local Clocking (Spartan-3A/AN FPGAs)

Components	Packages (XX)	Components	Packages (XX)
MT47H64M4XX-3	BP	MT47H16M16XX-3	BG
MT47H64M4XX-37E	BP	MT47H16M16XX-37E	BG
MT47H64M4XX-5E	BP	MT47H16M16XX-5E	BG
MT47H128M4XX-3	B6,CB,GB	MT47H32M16XX-3	BN,CC,FN,GC
MT47H128M4XX-37E	B6,CB,GB	MT47H32M16XX-37E	BN,CC,FN,GC
MT47H128M4XX-5E	B6,CB,GB	MT47H32M16XX-5E	BN,CC,FN,GC
MT47H256M4XX-3	BT,HQ	MT47H64M16XX-3	BT,HR
MT47H256M4XX-37E	BT,HQ	MT47H64M16XX-37E	BT,HR
MT47H256M4XX-5E	BT,HQ	MT47H64M16XX-5E	BT,HR
MT47H512M4XX-3	HG	MT47H128M16XX-3	HG
MT47H512M4XX-37E	HG	MT47H128M16XX-37E	HG
MT47H512M4XX-5E	HG	MT47H128M16XX-5E	--
MT47H32M8XX-3	BP	HYB18T1G800XXXX-3S	BF,BFL,BC
MT47H32M8XX-37E	BP	HYB18T1G800XXXX-37	BF,BFL,BC
MT47H32M8XX-5E	BP	HYB18T1G160XXXX-3S	BF,BFV,BFL,BC
MT47H64M8XX-3	B6,CB,F6,GB	HYB18T1G160XXXX-37	BF,BFV,BFL,BC

Table 8-15: Supported Components for DDR2 SDRAM Local Clocking (Spartan-3A/AN FPGAs)

Components	Packages (XX)	Components	Packages (XX)
MT47H64M8XX-37E	B6,CB,F6,GB	HYB18T1G400XXXX-3S	BF,BFL,BC
MT47H64M8XX-5E	B6,CB,F6,GB	HYB18T1G400XXXX-37	BF,BFL,BC
MT47H128M8XX-3	BT,HQ	HYB18T512800XXXX-3S	B2F,B2C,B2FL
MT47H128M8XX-37E	BT,HQ	HYB18T512800XXXX-37	B2F,B2C,B2FL
MT47H128M8XX-5E	BT,HQ	HYB18T512160XXXX-3S	B2F,B2C,B2FL
MT47H256M8XX-3	HG	HYB18T512160XXXX-37	B2F,B2C,B2FL
MT47H256M8XX-37E	HG	HYB18T512400XXXX-3S	B2F,B2C,B2FL
MT47H256M8XX-5E	HG	HYB18T512400XXXX-37	B2F,B2C,B2FL

Table 8-16: Supported Unbuffered DIMMs for DDR2 SDRAM Local Clocking (Spartan-3A/AN FPGAs)

Unbuffered DIMMs	
MT4HTF1664AY-667	MT8HTF6464AY-40E
MT4HTF1664AY-40E	MT8HTF12864AY-667
MT4HTF1664AY-53E	MT8HTF12864AY-40E
MT4HTF3264AY-667	MT8HTF12864AY-53E
MT4HTF3264AY-40E	MT9HTF3272AY-667
MT4HTF3264AY-53E	MT9HTF3272AY-53E
MT4HTF6464AY-667	MT9HTF3272AY-40E
MT4HTF6464AY-40E	MT9HTF6472AY-667
MT4HTF6464AY-53E	MT9HTF6472AY-53E
MT8HTF6464AY-667	MT9HTF6472AY-40E
MT8HTF6464AY-53E	--

Table 8-17: Supported Registered DIMMs for DDR2 SDRAM Local Clocking (Spartan-3A/AN FPGAs)

Registered DIMMs	
MT9HTF3272Y-53E	MT9HTF6472Y-40E
MT9HTF3272PY-53E	MT9HTF6472PY-40E
MT9HTF3272Y-40E	MT9HTF12872Y-53E
MT9HTF3272PY-40E	MT9HTF12872PY-53E
MT9HTF6472Y-53E	MT9HTF12872Y-40E
MT9HTF6472PY-53E	MT9HTF12872PY-40E

*Table 8-18: Supported SODIMMs for DDR2 SDRAM
Local Clocking (Spartan-3A/AN FPGAs)*

SODIMMs	
MT4HTF1664HY-667	MT8HTF3264HY-53E
MT4HTF1664HY-53E	MT8HTF3264HY-40E
MT4HTF1664HY-40E	MT8HTF6464HY-667
MT4HTF3264HY-667	MT8HTF6464HY-53E
MT4HTF3264HY-53E	MT8HTF6464HY-40E
MT4HTF3264HY-40E	MT9HTF12872CHY-667
MT8HTF3264HY-667	MT9HTF12872CHY-53E

The tables that follow list the components (Table 8-19) and DIMMs (Table 8-20 and Table 8-21) supported by the tool for Spartan-3A DSP FPGA DDR2 local clocking designs.

Table 8-19: Supported Components for DDR2 SDRAM Local Clocking (Spartan-3A DSP FPGAs)

Components	Packages (XX)	Components	Packages (XX)
MT47H64M4XX-3	BP	MT47H16M16XX-3	BG
MT47H64M4XX-37E	BP	MT47H16M16XX-37E	BG
MT47H64M4XX-5E	BP	MT47H16M16XX-5E	BG
MT47H128M4XX-3	B6,CB,GB	MT47H32M16XX-3	BN,CC,FN,GC
MT47H128M4XX-37E	B6,CB,GB	MT47H32M16XX-37E	BN,CC,FN,GC
MT47H128M4XX-5E	B6,CB,GB	MT47H32M16XX-5E	BN,CC,FN,GC
MT47H256M4XX-3	BT,HQ	MT47H64M16XX-3	BT,HR
MT47H256M4XX-37E	BT,HQ	MT47H64M16XX-37E	BT,HR
MT47H256M4XX-5E	BT,HQ	MT47H64M16XX-5E	BT,HR
MT47H512M4XX-3	HG	MT47H128M16XX-3	HG
MT47H512M4XX-37E	HG	MT47H128M16XX-37E	HG
MT47H512M4XX-5E	HG	MT47H128M16XX-5E	--
MT47H32M8XX-3	BP	HYB18T1G800XXXX-3S	BF,BFL,BC
MT47H32M8XX-37E	BP	HYB18T1G800XXXX-37	BF,BFL,BC
MT47H32M8XX-5E	BP	HYB18T1G160XXXX-3S	BF,BFV,BFL,BC
MT47H64M8XX-3	B6,CB,F6,GB	HYB18T1G160XXXX-37	BF,BFV,BFL,BC
MT47H64M8XX-37E	B6,CB,F6,GB	HYB18T1G400XXXX-3S	BF,BFL,BC
MT47H64M8XX-5E	B6,CB,F6,GB	HYB18T1G400XXXX-37	BF,BFL,BC
MT47H128M8XX-3	BT,HQ	HYB18T512800XXXX-3S	B2F,B2C,B2FL
MT47H128M8XX-37E	BT,HQ	HYB18T512800XXXX-37	B2F,B2C,B2FL
MT47H128M8XX-5E	BT,HQ	HYB18T512160XXXX-3S	B2F,B2C,B2FL
MT47H256M8XX-3	HG	HYB18T512160XXXX-37	B2F,B2C,B2FL
MT47H256M8XX-37E	HG	HYB18T512400XXXX-3S	B2F,B2C,B2FL
MT47H256M8XX-5E	HG	HYB18T512400XXXX-37	B2F,B2C,B2FL

Table 8-20: Supported Unbuffered DIMMs for DDR2 SDRAM Local Clocking (Spartan-3A DSP FPGAs)

Unbuffered DIMMs	
MT4HTF1664AY-667	MT4HTF6464AY-40E
MT4HTF1664AY-40E	MT4HTF6464AY-53E
MT4HTF1664AY-53E	MT8HTF6464AY-667
MT4HTF3264AY-667	MT8HTF6464AY-53E
MT4HTF3264AY-40E	MT8HTF6464AY-40E
MT4HTF3264AY-53E	MT8HTF12864AY-667
MT4HTF6464AY-667	--

Table 8-21: Supported SODIMMs for DDR2 SDRAM Local Clocking (Spartan-3A DSP FPGAs)

SODIMMs	
MT4HTF1664HY-667	MT8HTF3264HY-53E
MT4HTF1664HY-53E	MT8HTF3264HY-40E
MT4HTF1664HY-40E	MT8HTF6464HY-667
MT4HTF3264HY-667	MT8HTF6464HY-53E
MT4HTF3264HY-53E	MT8HTF6464HY-40E
MT4HTF3264HY-40E	--
MT8HTF3264HY-667	--

Maximum Data Widths

Table 8-22 provides the maximum data widths for Spartan-3 FPGAs. Table 8-23 provides the maximum data widths for Spartan-3E FPGAs. Table 8-24 provides the maximum data widths for single-ended DQS Spartan-3A FPGAs (differential DQS is disabled). Table 8-25 provides the maximum data widths for differential DQS Spartan-3A FPGAs (differential DQS is enabled). Table 8-26 provides the maximum data widths for differential DQS Spartan-3AN FPGAs (single/differential DQS is enabled). Table 8-27 provides the maximum data widths for differential DQS Spartan-3A DSP FPGAs (single/differential DQS is enabled). All the supported data width tables have the Mask Enable option enabled.

Table 8-22: Spartan-3 FPGA Maximum Data Width for DDR and DDR2 Memories

Serial Number	FPGA	Maximum Data Width when Data, Address, and Control are Allocated in...										
		...Different Banks						...the Same Bank				
		Bank 2	Bank 3	Bank 6	Bank 7	Left	Right	Bank 2	Bank 3	Banks 6/7	Left	Right
1	XC3S50CP132	0	0	0	0	8	8	0	0	0	0	0
2	XC3S50PQ208	0	0	0	0	8	8	0	0	0	0	0
3	XC3S50TQ144	0	0	0	0	8	8	0	0	0	0	0
4	XC3S200FT256	8	8	8	8	16	16	0	0	0	8	8
5	XC3S200PQ208	0	8	0	0	16	16	0	0	0	0	0
6	XC3S200TQ144	0	0	0	0	8	8	0	0	0	0	0
7	XC3S400FG320	8	8	8	8	24	24	0	0	0	16	16
8	XC3S400FG456	16	8	16	8	32	24	0	0	0	16	16
9	XC3S400FT256	8	8	8	8	16	16	0	0	0	8	8
10	XC3S400PQ208	0	0	0	0	8	8	0	0	0	0	0
11	XC3S400TQ144	0	0	0	0	8	8	0	0	0	0	0
12	XC3S1000FG320	8	8	8	8	24	24	0	0	0	16	16
13	XC3S1000FG456	16	16	16	16	48	48	8	8	8	32	32
14	XC3S1000FG676	24	24	24	24	48	48	8	8	8	32	32

Table 8-22: Spartan-3 FPGA Maximum Data Width for DDR and DDR2 Memories (Cont'd)

Serial Number	FPGA	Maximum Data Width when Data, Address, and Control are Allocated in...										
		...Different Banks						...the Same Bank				
		Bank 2	Bank 3	Bank 6	Bank 7	Left	Right	Bank 2	Bank 3	Banks 6/7	Left	Right
15	XC3S1000FT256	8	8	8	8	16	16	0	0	0	8	8
16	XC3S1500FG320	8	8	8	8	24	24	0	0	0	16	16
17	XC3S1500FG456	16	16	16	16	48	48	8	8	8	40	40
18	XC3S1500FG676	32	32	32	32	72	72	16	16	16	48	48
19	XC3S2000FG456	16	16	16	16	48	48	8	8	8	32	32
20	XC3S2000FG676	32	32	32	32	72	72	16	16	16	56	56
21	XC3S2000FG900	32	32	32	40	72	72	24	24	24	64	64
22	XC3S4000FG676	24	32	32	32	72	72	16	16	16	56	48
23	XC3S4000FG900	40	40	40	40	72	72	32	32	32	72	72
24	XC3S4000FG1156	48	48	48	48	72	72	32	32	32	72	72
25	XC3S5000FG676	24	24	24	32	64	64	16	16	16	48	48
26	XC3S5000FGG676	24	24	24	32	64	64	16	16	16	48	48
27	XC3S5000FG900	40	40	40	40	72	72	32	32	32	72	72
28	XC3S5000FG1156	56	56	48	56	72	72	40	40	40	72	72

Table 8-23: Spartan-3E FPGA Maximum Data Width for DDR SDRAMs

Serial Number	FPGA	Maximum Data Width when Data, Address, and Control are Allocated in...		
		...Different Banks		...the Same Bank
		Left	Right	Left/Right
1	XC3S100ECP132	8	8	0
2	XC3S100ETQ144	8	8	0
3	XC3S250ECP132	8	0	0
4	XC3S250EFT256	16	16	0
5	XC3S250EPQ208	16	16	0
6	XC3S250ETQ144	8	8	0
7	XC3S500ECP132	8	0	0
8	XC3S500EFG320	24	24	8
9	XC3S500EFT256	16	16	8
10	XC3S500EPQ208	8	8	0
11	XC3S1200EFG320	16	16	16
12	XC3S1200EFG400	32	32	16
13	XC3S1200EFT256	16	8	8
14	XC3S1600EFG320	16	16	8

Table 8-23: Spartan-3E FPGA Maximum Data Width for DDR SDRAMs (Cont'd)

Serial Number	FPGA	Maximum Data Width when Data, Address, and Control are Allocated in...		
		...Different Banks		...the Same Bank
		Left	Right	Left/Right
15	XC3S1600EFG400	24	32	16
16	XC3S1600EFG484	48	40	32

Table 8-24: Spartan-3A FPGA Single-Ended DQS Maximum Data Width (Differential DQS Disabled)

Serial Number	FPGA	Maximum Data Width when Data, Address, and Control are Allocated in...		
		...Different Banks		...the Same Bank
		Left/Right	Left	Right
1	XC3S50ATQ144	8	0	0
2	XC3S50AFT256	8	0	0
3	XC3S200AFT256	16	8	8
4	XC3S200AFG320	16	16	16
5	XC3S400AFT256	16	8	8
6	XC3S400AFG320	24	8	16
7	XC3S400AFG400	32	16	16
8	XC3S700AFT256	16/8	0	0
9	XC3S700AFG400	32	16	16
10	XC3S700AFG484	40	24	32
11	XC3S1400AFT256	16/8	0	0
12	XC3S1400AFG484	40	24	32
13	XC3S1400AFG676	72	48	48

Table 8-25: Spartan-3A FPGA Differential DQS Maximum Data Width (Differential DQS Enabled)

Serial Number	FPGA	Maximum Data Width when Data, Address, and Control are Allocated in...			
		...Different Banks		...the Same Bank	
		Left	Right	Left	Right
1	XC3S50ATQ144	8	8	0	0
2	XC3S200AFG320	24	24	8	16
3	XC3S200AFT256	16	24	8	8
4	XC3S400AFG320	24	24	8	16
5	XC3S400AFG400	32	32	16	16
6	XC3S400AFT256	16	16	8	8

Table 8-25: Spartan-3A FPGA Differential DQS Maximum Data Width (Differential DQS Enabled) (Cont'd)

Serial Number	FPGA	Maximum Data Width when Data, Address, and Control are Allocated in...			
		...Different Banks		...the Same Bank	
		Left	Right	Left	Right
7	XC3S700AFG400	24	32	16	16
8	XC3S700AFG484	40	40	24	32
9	XC3S1400AFG484	40	40	24	32
10	XC3S1400AFG676	64	64	48	48
11	XC3S50AFT256	8	8	0	0
12	XC3S700AFT256	16	8	0	0
13	XC3S1400AFT256	16	8	0	0

Table 8-26: Spartan-3AN FPGA DQS Maximum Data Width (Single/Differential DQS Enabled)

Serial Number	FPGA	Maximum Data Width when Data, Address, and Control are Allocated in...			
		...Different Banks		...the Same Bank	
		Left	Right	Left	Right
1	XC3S50ANTQG144	8	8	0	0
2	XC3S50ANFTG256	8	8	0	0
3	XC3S200ANFTG256	16	24	8	8
4	XC3S400ANFGG400	32	32	16	16
5	XC3S700ANFGG484	40	40	24	32
6	XC3S1400ANFGG676 ⁽¹⁾	64	64	48	48

Notes:

1. For the XC3S1400ANFGG676 part, MIG can generate 72-bit single-ended DQS RDIMM with address and data on different banks.

Table 8-27: Spartan-3A DSP FPGA DQS Maximum Data Width (Single/Differential DQS Enabled)

Serial Number	FPGA	Maximum Data Width when Data, Address, and Control are Allocated in...			
		...Different Banks		...the Same Bank	
		Left	Right	Left	Right
1	XC3SD1800A-CS484	32	32	16	16
2	XC3SD3400A-CS484	32	32	16	16
3	XC3SD1800A-FG676	64	64	48	48
4	XC3SD3400A-FG676	64	64	48	48

DIMM Support for Spartan-3 Generation Devices

Table 8-28: DIMM Support for Spartan-3 Devices

Serial Number	FPGA	64-bit DIMM			72-bit DIMM		
		x4	x8	x16	x4	x8	x16
1	XC3S1500FG676	No	Yes	Yes	No	Yes	Yes
2	XC3S2000FG676	No	Yes	Yes	No	Yes	Yes
3	XC3S4000FG676	No	Yes	Yes	No	Yes	Yes
4	XC3S5000FG676	No	Yes	Yes	No	No	No
5	XC3S2000FG900	Yes	Yes	Yes	Yes	Yes	Yes
6	XC3S4000FG900	Yes	Yes	Yes	Yes	Yes	Yes
7	XC3S5000FG900	Yes	Yes	Yes	Yes	Yes	Yes
8	XC3S4000FG1156	Yes	Yes	Yes	Yes	Yes	Yes
9	XC3S5000FG1156	Yes	Yes	Yes	Yes	Yes	Yes
10	XC3S1500LFG676	No	Yes	Yes	No	Yes	Yes
11	XC3S4000LFG900	Yes	Yes	Yes	Yes	Yes	Yes

Table 8-29: DIMM Support for Spartan-3A and Spartan-3AN Devices

Serial Number	FPGA	64-bit DIMM			72-bit DIMM		
		x4	x8	x16	x4	x8	x16
1	XC3S1400AFG676	No	Yes	Yes	No	Yes	Yes
2	XC3S1400ANFGG676	No	Yes	Yes	No	Yes	Yes

Table 8-30: DIMM Support for Spartan-3A DSP Devices

Serial Number	FPGA	64-bit DIMM			72-bit RDIMM		
		x4	x8	x16	x4	x8	x16
1	XC3SD1800AFG676	No	Yes	Yes	No	No	No
2	XC3SD3400AFG676	No	Yes	Yes	No	No	No

Note: Spartan-3E devices do not support 64-bit or 72-bit DIMMs.

Design Frequency Range in MHz for Spartan-3 Generation Devices

Table 8-31: Spartan-3 Generation FPGA Component Controllers

FPGA Family	DDR SDRAM		DDR2 SDRAM	
	≤ 32-bit	> 32-bit	≤ 32-bit	> 32-bit
Spartan-3A/3AN/3A DSP	166	166	166	166
Spartan-3E	166	166	NS	NS
Spartan-3	166	133	166	133

Notes:

NS = not supported.

Table 8-32: Spartan-3 Generation FPGA DIMM Controllers

FPGA Family	DDR SDRAM	DDR2 SDRAM
Spartan-3A/3AN/3A DSP	166	166
Spartan-3E	NS	NS
Spartan-3	133	133

Notes:

1. NS = not supported.

Supported IO Standards

Table 8-33 shows the I/O standards supported for MIG generated Spartan FPGA families.

Table 8-33: Supported I/O Standards for MIG-Generated Spartan FPGA Families

Standard	Vcco	Drive/Class	Spartan-3A/3AN/3A DSP	Spartan-3E	Spartan-3
LVCMOS	1.8V	8MA	All Banks	All Banks	All Banks
		16MA	Banks 1/3	All Banks	All Banks
	2.5V	12MA	All Banks	All Banks	All Banks
		24MA	Banks 1/3	All Banks	All Banks
SSTL	1.8V	I	All Banks	All Banks	All Banks
		II	All Banks (1)	-	All Banks
	2.5V	I	All Banks	All Banks	All Banks
		II	All Banks (1)	-	All Banks

Table 8-33: Supported I/O Standards for MIG-Generated Spartan FPGA Families

Standard	Vcco	Drive/Class	Spartan-3A/3AN/3A DSP	Spartan-3E	Spartan-3
DIFF_SSTL	1.8V	I	All Banks	All Banks	-
		II	All Banks (2)	-	-
	2.5V	I	All Banks	All Banks	-
		II	All Banks (2)	-	All Banks
LVDS	2.5V	-	All Banks (3)	All Banks	All Banks

Notes:

1. Outputs are restricted to banks 1 and 3. Inputs are unrestricted.
2. These high-drive outputs are restricted to banks 1 and 3. Inputs are unrestricted.
3. These differential outputs are restricted to banks 0 and 2. Inputs are unrestricted.

Hardware Tested Configurations

The frequencies shown in [Table 8-34](#) were achieved on the Spartan-3A FPGA Starter Kit under nominal conditions. This frequency should not be used to determine the maximum design frequency. The maximum design frequency supported in the MIG wizard is based on a combination of the TRCE results for fabric timing on multiple device/package combinations and I/O timing analysis using FPGA and memory timing parameters for a 64-bit interface.

Table 8-34: Hardware Tested Configurations for Spartan-3A FPGA DDR2 SDRAM Designs

Synthesis Tools	XST
HDL	Verilog and VHDL
FPGA Device	XC3S700AFG484-4
Burst Lengths	4 and 8
CAS Latency (CL)	3
16-bit Design	Tested on 16-bit Component "MT47H32M16XX-5E"
Frequency Range	25 MHz to 225 MHz

The frequency shown in [Table 8-35](#) was achieved on the Spartan-3A DSP FPGA 3400A Development Board under nominal conditions. This frequency should not be used to determine the design frequency. The maximum design frequency supported in the MIG wizard is based a combination of the TRCE results for fabric timing on multiple device/package combinations and I/O timing analysis using FPGA and memory timing parameters for a 64-bit interface.

Table 8-35: Hardware Tested Configurations for Spartan-3A DSP FPGA DDR2 SDRAM Designs

Synthesis Tools	XST
HDL	Verilog and VHDL
FPGA Device	XC3SD3400AFG676-4
Burst Lengths	4 and 8
CAS Latency (CL)	3
32-bit Design	Tested on 64-bit SO DIMM "MT4HTF6464HY-667"
Frequency	133 MHz

Section IV: Virtex-5 FPGA to Memory Interfaces

Chapter 9, “Implementing DDR2 SDRAM Controllers”

Chapter 10, “Implementing QDRII SRAM Controllers”

Chapter 11, “Implementing DDR SDRAM Controllers”

Chapter 12, “Implementing DDRII SRAM Controllers”

Implementing DDR2 SDRAM Controllers

This chapter describes how to implement DDR2 SDRAM interfaces for Virtex®-5 FPGAs generated by MIG. The DDR2 SDRAM design supports frequencies up to 333 MHz. This design is based on XAPP858 [Ref 27].

Interface Model

DDR2 SDRAM interfaces are source-synchronous and double data rate. They transfer data on both edges of the clock cycle. A memory interface can be modularly represented as shown in Figure 9-1. A modular interface has many advantages. It allows designs to be ported easily and also makes it possible to share parts of the design across different types of memory interfaces.

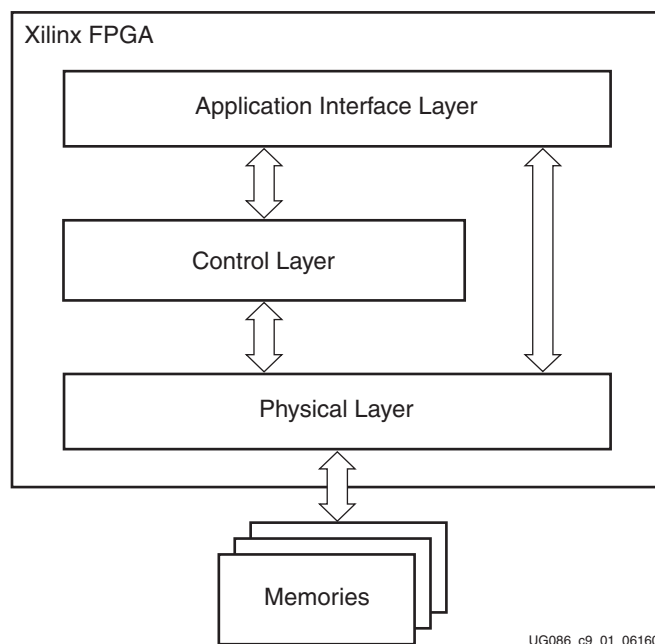


Figure 9-1: Modular Memory Interface Representation

Feature Summary

This section summarizes the supported and unsupported features of the DDR2 SDRAM controller design.

Supported Features

The DDR2 SDRAM controller design supports:

- Burst lengths of four and eight
- Sequential and interleaved burst types
- CAS latencies of 3, 4, and 5
- Additive latencies of 0, 1, 2, 3, and 4
- Differential DQS
- ODT
- Verilog and VHDL
- Byte wise data masking
- Precharge and auto refresh
- Bank management
- Linear addressing
- ECC
- Different memories (density/speed)
- Memory components, registered DIMMs, unbuffered DIMMs, and SODIMMs
- Deep support for Dual Rank DIMMs of value 2
- With and without a testbench
- With and without a PLL
- Multicontroller (DDR2) and Multiple Interfaces (DDR2 and QDRII)
- PPC440 pinout
- Data mask
- Two bytes per bank
- System clock, differential and single-ended

The supported features are described in more detail in [“Architecture.”](#)

Design Frequency Ranges

Table 9-1: Design Frequency Range in MHz

Memory	FPGA Speed Grade					
	-1		-2		-3	
	Min	Max	Min	Max	Min	Max
Component	125	266	125	300	125	333
RDIMM	125	266	125	300	125	333
UDIMM or SODIMM ⁽¹⁾	125	266	125	266	125	266

Table 9-1: Design Frequency Range in MHz (Cont'd)

Memory	FPGA Speed Grade					
	-1		-2		-3	
	Min	Max	Min	Max	Min	Max
Deep Memory /Dual Rank DIMM/Twin Die Components	125	150	125	150	125	150

Notes:

1. It is possible to go faster than 266 MHz, but it requires care and IBIS simulations and possibly using the parameter to send the CS out earlier depending on the load. For more details, see XAPP858 [Ref 27].

Unsupported Features

The DDR2 SDRAM controller design does not support:

- Single-ended DQS
- Redundant DQS (RDQS)
- Deep support for components, single-rank DIMMs and deep value of 4

Architecture

Implemented Features

This section provides details on the supported features of the DDR2 SDRAM controller.

Burst Length

The DDR2 SDRAM controller supports burst lengths of four and eight. Through the “Set mode register(s)” option, the burst length can be selected. For a design without a testbench (user_design), the user has to provide bursts of the input data based on the chosen burst length. Bits M2:M0 of the Mode Register define the burst length, and bit M3 indicates the burst type (see the Micron data sheet). Read and write accesses to the DDR2 SDRAM are burst-oriented. It determines the maximum number of column locations accessed for a given READ or WRITE command.

CAS Latency

The DDR2 SDRAM controller supports CAS latencies of 3, 4, and 5. The CAS latency (CL) can be selected in the “Set mode register(s)” option. CL is implemented in the phy_write module. During data write operations, the generation of the dqs_oe_n and dqs_rst_n signals varies according to the CL in the phy_write module. During read data operations, the generation of the ctrl_rden signal varies according to the CL in the ctrl module. Bits M4:M6 of the Mode Register define the CL (see the Micron data sheet). CL is the delay in clock cycles between the registration of a READ command and the availability of the first bit of output data.

Additive Latency

DDR2 SDRAM devices support a feature called posted CAS additive latency (AL). The DDR2 SDRAM supports ALs of 0, 1, 2, 3, and 4. AL can be selected in the “Set mode

register(s)” option. AL is implemented in the DDR2 SDRAM ctrl module. The ctrl module issues READ/WRITE commands prior to t_{RCD} (minimum) depending on the user-selected AL value in the Extended Mode Register. This feature allows the READ command to be issued prior to t_{RCD} (minimum) by delaying the internal command to the DDR2 SDRAM by AL clocks. Posted CAS AL makes the command and data bus efficient for sustainable bandwidths in DDR2 SDRAM. Bits E3:E5 of the Extended Mode Register define the value of AL (see the Micron data sheet).

Data Masking

DDR2 SDRAM design supports data masking per byte. Masking per nibble is not supported due to the limitation of the internal block RAM based FIFOs. So, the masking of data can be done on per byte basis. The mask data is stored in the Data FIFO along with the actual data.

MIG supports a data mask option. If this option is checked in the GUI, MIG generates a design with data mask pins. This option can be chosen if the selected part has data masking. DDR2 SDRAM designs do not support read-modify-write operations in ECC mode. The mask bits to the SDRAM should never be asserted while in the ECC mode. Thus, when ECC is selected, the data masking selection is disabled in the GUI.

Precharge

The PRECHARGE command is used to close the open row in a bank if there is a command to be issued in the same bank. The Virtex-5 FPGA DDR2 controller issues a PRECHARGE command only if there is already an open row in the particular bank where a read or write command is to be issued, thus increasing the efficiency of the design. The auto precharge function is not supported in this design. The design ties the A10 bit Low during normal reads and writes.

Auto Refresh

The auto refresh command is issued to the memory at specified intervals of time. The memory issues an auto refresh command to refresh the charge to retain the data.

Bank Management

A Virtex-5 FPGA DDR2 SDRAM controller design supports bank management that increases the efficiency of the design. The controller keeps track of whether the bank being accessed already has an open row or not and also decides whether a PRECHARGE command should be issued or not to that bank. When bank management is enabled via the MULTI_BANK_EN parameter, a maximum of four banks/rows can open at any one time. A least recently used (LRU) algorithm is employed to keep the three most recently used banks and to close the least recently used bank when a new bank/row location needs to be accessed. The bank management feature can also be disabled by clearing MULTI_BANK_EN. For more information on Bank Management, refer to application note XAPP858 [Ref 27].

Linear Addressing

The DDR2 SDRAM controller supports linear addressing. Linear addressing refers to the way the user provides the address of the memory to be accessed. For Virtex-5 FPGA DDR2 SDRAM controllers, the user provides the address information through the app_af_addr signal. As the densities of the memory devices vary, the number of column address bits and row address bits also change. In any case, the row address bits in the app_af_addr

signal always start from the next higher bit, where the column address ends. This feature increases the number of devices that can be supported with the design.

Different Memories (Density/Speed)

The DDR2 SDRAM controller supports different densities. For DDR2 components shown in MIG, densities vary from 256 Mb to 2 Gb, and the DIMM densities vary from 256 Mb to 2 Gb. The user can select the various configurations from the “Create new memory part” option. The supported maximum column address is 13, the maximum row address is 15, and the maximum bank address is 3. The design can decode write and read addresses from the user in the DDR2 SDRAM ctrl module. The user address consists of column, row, and bank addresses.

Deep Memories

The MIG DDR2 SDRAM controller supports Dual Rank DIMMs with depth of 2. For deep memory implementations, MIG generates chip selects, CKE signals, and ODT signals for each memory. The clock widths (CK and CK_N) are a multiple factor of the deep configuration chosen in MIG.

For deep memories, DDR2 SDRAMs are initialized one after the other to avoid loading the address and control buses, and the calibration is done on the last memory. Apart from initialization, the DDR2 SDRAM controller module also demultiplexes the column, row, and bank addresses from the user address. The module also decodes the chip selects and rank addresses for DIMMs.

On-Die Termination

The DDR2 SDRAM controller supports on-die termination (ODT). Through the “Set mode register(s)” option from the GUI, the user can disable ODT or can choose 75, 150, or 50. ODT can turn the termination on and off as needed to improve signal integrity in the system.

ODT is only enabled on writes to DDR2 memory. It is disabled on read operations. One single dual-rank DIMM is populated in a single slot. Rank 1 and Rank 2 of slot 1 or slot 2 are referred to as CS0 and CS1. ODT0 should be connected to the ODT signal of CS0 and ODT1 should be connected to the ODT signal of CS1. ODT0 is enabled when writing to CS0 or CS1. During read operations, the ODT is disabled. In this configuration, ODT for CS1 is always off. [Table 9-2](#) shows ODT control during write operations, and [Table 9-3](#) shows ODT control during read operations.

Table 9-2: ODT Control during Writes

Configuration		Write to	DRAM at Slot 1 (ODT On/Off)		DRAM at Slot 2 (ODT On/Off)	
Slot 1	Slot 2		Rank 1	Rank 2	Rank 1	Rank 2
DR	Empty	Slot 1	On	Off	N/A	N/A
Empty	DR	Slot 2	N/A	N/A	On	Off
SR	Empty	Slot 1	On	N/A	N/A	N/A
Empty	SR	Slot 2	N/A	N/A	On	N/A

Table 9-3: ODT Control during Reads

Configuration		Read from	DRAM at Slot 1 (ODT On/Off)		DRAM at Slot 2 (ODT On/Off)	
Slot 1	Slot 2		Rank 1	Rank 2	Rank 1	Rank 2
DR	Empty	Slot 1	Off	Off	N/A	N/A
Empty	DR	Slot 2	N/A	N/A	Off	Off
SR	Empty	Slot 1	Off	N/A	N/A	N/A
Empty	SR	Slot 2	N/A	N/A	Off	N/A

Note: The Virtex-5 FPGA DDR2 interface requires that if parallel termination is used at the memory end, it must be ODT rather than external termination resistor(s). This is a requirement of the read capture scheme used. For more information on the need for ODT, refer to XAPP858 [Ref 27].

Multicontrollers

MIG supports multicontrollers for DDR2 SDRAMs and multiple interfaces for DDR2 SDRAMs and QDR II SRAMs. Up to eight controllers are supported. In multicontroller and multiple interface designs, every controller can have a different frequency. The number of controllers that can have different frequencies is limited by the number of PLLs available in the selected FPGA. For example, a total of six PLL resources are available for the XC5VLX50 device, so a maximum of six controllers can have different frequencies. Even though the number of controllers selected in the GUI is eight, a maximum of six controllers can have different frequencies. Thus, for the remaining two controllers, the user should select one of the already selected frequencies. Refer to the Virtex-5 FPGA User Guide [Ref 10] for PLL resources available for various devices.

For a single controller design, all memory and user interface signals appear as shown in Figure 9-7 and Table 9-6 based on the selected part. For a multicontroller design, all memory and user interface signal names are prepended with the controller number. For example, for a two controller design (two DDR2 controllers), the ddr2_dq port appears as c0_ddr2_dq and c1_ddr2_dq. A similar naming convention is followed for the parameters provided in Table 9-2. Some parameters, such as HIGH_PERFORMANCE_MODE, CLK_TYPE and RST_ACT_LOW, are common for all the controllers and do not have the controller number prepended.

Two Bytes Per Bank

MIG supports Two Byte per bank option. If this option is checked in GUI, MIG allocates only 2 bytes of Data in each bank. By default this option is unchecked and MIG allocated 3 bytes of Data in each bank.

System Clock

MIG supports differential and single-ended system clocks. Based on the selection in the GUI, input system clocks and IDELAY clocks are differential or single-ended.

IODELAY Performance Mode

In Virtex-5 family devices, the power dissipation of the IODELAY elements can be controlled using the HIGH_PERFORMANCE_MODE parameter. The values of this parameter can be either TRUE or FALSE.

When this parameter value is set to TRUE, the IODELAY jitter value per tap is reduced. This reduction results in a slight increase in power dissipation from the IODELAY element. When this parameter value is set to FALSE, the IODELAY power dissipation is reduced, but with an increase in the jitter value per tap.

The value of this parameter can be selected from the MIG FPGA options page. Users can also manually set this parameter value to TRUE or FALSE in the design top-level block HDL module.

Refer to [Appendix E, “Debug Port”](#) for more information on the IODELAY Performance Mode.

Generic Parameters

The DDR2 SDRAM design is a generic design that works for most of the features mentioned above. User input parameters are defined as parameters for Verilog and generics in VHDL in the design modules and are passed down the hierarchy. For example, if the user selects a burst length of 4, then it is defined as follows in the <top_module> module:

```
parameter BURST_LEN = 4,           // burst length (in doublewords)
```

The user can change this parameter in <top_module> for various burst lengths to get the desired output. The same concept applies to most of the other parameters listed in the <top_module> module. The user cannot change REG_ENABLE and CLK_TYPE to reflect those changes directly. The user should manually edit <top_module> for port connections and other logical changes. [Table 9-4](#) lists the details of all parameters.

Table 9-4: Parameterization of DDR2 SDRAM Virtex-5 FPGA Design

Category	Parameter Name	Description	Other Notes	Value Restrictions
Memory Width	BANK_WIDTH	Number of memory bank address bits		
	CKE_WIDTH	Number of memory clock enable outputs		
	CLK_WIDTH	Number of differential clock outputs	Determined by the number of components/modules (one pair per component)	
	COL_WIDTH	Number of memory column bits		
	CS_BITS	$\log_2(\text{CS_NUM})$	Used for chip-select related address decode. See notes for CS_NUM and CS_WIDTH.	
	CS_NUM	Number of separate chip selects	Different from CS_WIDTH. For example, for a 32-bit data bus consisting of 2 x16 parts, CS_NUM = 1, but CS_WIDTH = 2 (that is, a single chip select drives two separate outputs, one for each component)	$\text{CS_WIDTH} / \text{CS_NUM} = \text{integer}$
	CS_WIDTH	Number of memory chip selects	Determined by the number of components/modules (one per component)	$\text{CS_WIDTH} / \text{CS_NUM} = \text{integer}$
	DM_WIDTH	Number of data mask bits	Can be different value than DQS_WIDTH if x4 components are used	$(\text{DQS_WIDTH} * \text{DQ_PER_DQS}) / 8$
	DQ_BITS	$\log_2(\text{DQS_WIDTH} * \text{DQ_PER_DQS})$	Used for data bus calibration decode	$(\text{DQ_WIDTH}) / \text{Number of data bits}$
	DQ_WIDTH	Number of data bits	Must set to $\text{DQS_WIDTH} * \text{DQ_PER_DQS}$. Equal to total number of data bits, including ECC bits.	$\text{DQS_WIDTH} * \text{DQ_PER_DQS}$
	DQ_PER_DQS	Number of memory DQ data bits per strobe		
	DQS_BITS	$\log_2(\text{DQS_WIDTH})$		
	DQS_WIDTH	Number of memory DQS strobes		
	ODT_WIDTH	Number of ODT control outputs	Determined by the number of components/modules (one per component)	
	ROW_WIDTH	Number of memory address bits		
	APPDATA_WIDTH	Number of data bits at user backend interface		If ECC Disabled: $2 * (\text{DQ_WIDTH})$ If ECC Enabled: $2 * (\text{DQ_WIDTH} - 8 * (\text{DQ_WIDTH} / 72))$

Table 9-4: Parameterization of DDR2 SDRAM Virtex-5 FPGA Design (Cont'd)

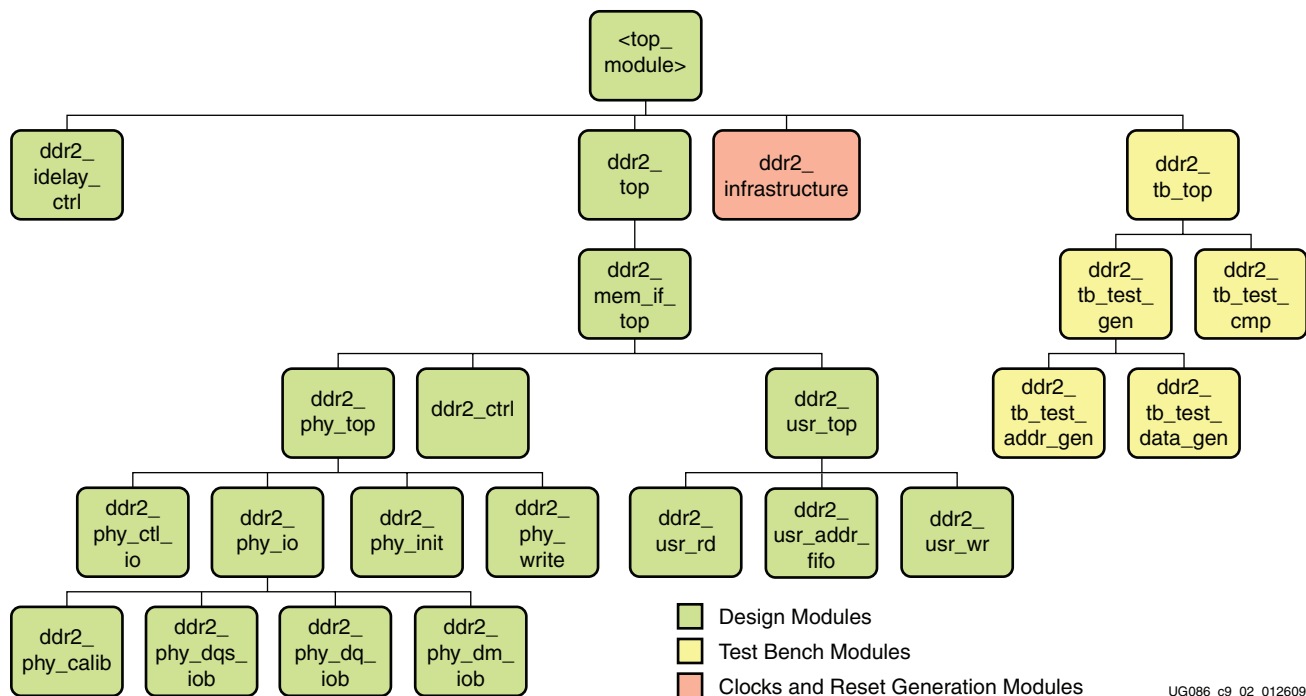
Category	Parameter Name	Description	Other Notes	Value Restrictions
Memory Options	ADDITIVE_LAT	Additive latency		(0,1,2,3,4)
	BURST_LEN	Burst length		(4,8) for DDR2, (2,4,8) for DDR
	BURST_TYPE	burst type (0: sequential, 1: interleaved)		(0,1)
	CAS_LAT	CAS latency (equal to 6 for CL = 2.5)		(3,4,5) for DDR2, (2,3,6) for DDR
	ECC_ENABLE	Enable ECC		Set to 0
	MULTI_BANK_EN	Bank management enable	If enabled, up to 4 banks are kept open; otherwise, one bank is kept open	(0,1)
	ODT_TYPE	ODT termination value	0: ODT disabled 1: 75 Ω 2: 150 Ω 3: 50 Ω	(0,1,2,3)
	REDUCE_DRV	Reduced strength memory I/O enable. Set (1) for reduced I/O drive strength.	Not supported for all DDR/DDR2 widths	(0,1)
	REG_ENABLE	Set for registered memory module	Accounts for an extra clock cycle delay on address/control for registered module	(0,1)
	TWO_T_TIME_EN	Enable "2T" timing for control/address signals	0: Disable 2T timing 1: Enable 2T timing	(0,1)
Memory Timing	TREFI_NS	Auto refresh interval (in ns)	Take directly from memory datasheet	
	T _{RAS}	Active to precharge delay (in ps)	Take directly from memory datasheet	
	T _{RCD}	Active to read/write delay (in ps)	Take directly from memory datasheet	
	T _{RFC}	Refresh to refresh, refresh to active delay (in ps)	Take directly from memory datasheet	
	T _{RP}	Precharge to command delay (in ps)	Take directly from memory datasheet	
	T _{RTP}	Read to precharge delay (in ps)	Take directly from memory datasheet	
	T _{WR}	Used to determine write to precharge (in ps)	Take directly from memory datasheet	
	T _{WTR}	Write to read (in ps)	Take directly from memory datasheet	

Table 9-4: Parameterization of DDR2 SDRAM Virtex-5 FPGA Design (Cont'd)

Category	Parameter Name	Description	Other Notes	Value Restrictions
Miscellaneous	CLK_PERIOD	Memory clock period (in ps)	Used for PHY calibration and PLL/DCM (if applicable) setting	
	CLK_TYPE	Input Clock Type	Determined by system clock selection in GUI.	("DIFFERENTIAL_ENDED", "SINGLE_ENDED")
	DLL_FREQ_MODE	DCM Frequency Mode	Determined by CLK_PERIOD. Needed only if the DCM option is selected.	("LOW", "HIGH")
	DDR2_TYPE	Select either DDR or DDR2 interface	0: DDR 1: DDR2 Provided from the mem_if_top level and below	(0,1)
	SIM_ONLY	Enable to bypass initial 200 μ s power-on delay. Abbreviated calibration sequence (only one bit for Stage 1, one strobe for Stages 2–4).		(0,1)
	RST_ACT_LOW	Indicates the polarity of input reset signal (sys_rst_n)	1: Reset is active Low. 0: Reset is active High.	(0,1)
	DEBUG_EN	Enable Calibration Debug Port	See Appendix E for details	(0,1)
	HIGH_PERFORMANCE_MODE	IODELAY High Performance Mode Parameter value	This parameter value represents HIGH_PERFORMANCE_MODE of IODELAY as TRUE or FALSE. This will result in the higher or lower power dissipation at the output of IODELAY element.	Verilog : String. "TRUE", "FALSE". VHDL : Boolean : TRUE, FALSE.

Hierarchy

Figure 9-2 shows the hierarchical structure of the DDR2 SDRAM design generated by MIG with a testbench and a PLL.



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Figure 9-2: Hierarchical Structure of the Virtex-5 FPGA DDR2 Design

The modules are classified as follows:

- Design modules
- Testbench modules
- Clocks and reset generation modules

MIG can generate four different DDR2 SDRAM designs:

- With a testbench and a PLL
- Without a testbench and with a PLL
- With a testbench and without a PLL
- Without a testbench and without a PLL

For a design without a testbench (user_design), the yellow shaded modules in Figure 9-2 are not present in the design. The <top_module> module has the user interface signals for designs without a testbench. The list of user interface signals is provided in Table 9-8.

Design clocks and resets are generated in the infrastructure module. The PLL/DCM is instantiated in infrastructure module when selected by MIG. The inputs to this module are the differential design clock and a 200 MHz differential clock for the IDELAYCTRL module. A user reset is also input to this module. Using the input clocks and reset signals, system clocks and system reset are generated in this module which is used in the design.

The PLL/DCM primitive is not instantiated in this module if the **No PLL** option is selected. So, the system operates on the user-provided clocks. The system reset is generated in the infrastructure module using the locked input signal.

Constraints

The Virtex-5 FPGA DDR2 design uses a combination of the IOB flop (IDDR) and fabric-based flops for read data capture. This requires the use of pinout-dependent location constraints. For more details, see [Appendix B, “Pinout-Related UCF Constraints for Virtex-5 FPGA DDR2 SDRAMs.”](#)

In Virtex-5 FPGA DDR2 designs containing single PPC440 processors (FX30T-FF65, FX70T-FF665, and FX70T-FF1136), data cannot be allocated to non-DCI banks (Bank 1 and Bank 2). Because PPC440 processor blocks are closer to the I/O pads, location constraints for DQ read-data capture flip-flops (for second # stage capture) will not find slices closer to I/Os. Therefore, a Virtex-5 FPGA DDR2 design cannot generate squelch constraints for Bank 1 and Bank 2 and these two non-DCI banks are not selectable in the GUI.

Verifying UCF/HDL Modifications

The user should perform the following checks to ensure that the timing is met:

- All UCF timing constraints (PERIOD, MAXDELAY, FROM-TO) must be met.
- Additional delay and skew requirements specific to the MIG Virtex-5 FPGA DDR2 interface and specified through the use of attributes embedded in the RTL source code must be met.

MIG Read Capture Delay and Skew Requirements

The Virtex-5 FPGA DDR2 interface requires that certain routes between the IDDR and fabric flip-flops be tightly constrained to limit their total net delay and their skew with respect to each other. This is required to meet the timing requirements for DDR2 read data capture. The place and route (PAR) report must be examined to confirm that these requirements were met. The read capture circuit is explained in more detail in XAPP858 [\[Ref 27\]](#).

The ISE® software places the fabric flip-flops and routes the nets from the IDDR to these fabric flip-flops according to delay and inter-net skew requirements. The paths are not covered by UCF timing constraints. The delay and inter-net skew requirements are specified using the XIL_PAR_DELAY and XIL_PAR_SKEW attributes, respectively, within the MIG HDL source code. The MIG tool determines and sets these attributes based on user performance requirements. The design should always be regenerated using the MIG tool if any of the design parameters are changed. Similarly, the values of these attributes should not be modified without using MIG to regenerate the design.

The user can verify that these delay and skew requirements were met by checking the output of the PAR report. If these requirements are met, the PAR report displays:

```
INFO:PAR:### - <X> number of MIG cores have been detected in your design
and have been successfully placed and routed. All appropriate timing
requirements have been met.
```

If any of the requirements have not been met, either MAP or PAR issues one of two possible errors.

If MAP is unable to place the fabric flip-flops close to their corresponding IDDR due to a conflict with other logic that has been specifically constrained in those locations, MAP issues the following error:

```
ERROR: Place: 1240 - Placement has failed for the IP core generated by
MIG because non-related components have been locked to slice locations
required for the MIG core. Please change or remove the location
constraints for these non-related components so that they don't
```

conflict with MIG placement. Below is a list of the slice locations, the component that is currently locked to this location, and the MIG component that needs to be placed in the same location:

Slice Location	Currently Locked	Component MIG Component
SLICE_X0Y119		
u_ddr2_tb_top_0/u_tb_test_cmp/gen_rd_data[4].ff_rd_data_r1		
u_ddr2_top_0/u_mem_if_top/u_phy_top/u_phy_io/gen_dq[0].u_iob_dq/stg2b_out_fall		

If PAR is unable to meet any of the read capture delay or skew requirements, PAR issues the following error message and lists the failing nets:

```
ERROR: Route:537 - A core generated by the Memory Interface Generator (MIG) has been detected in this design but PAR is unable to route the critical signals of this core to meet the necessary skew and delay requirements. Please ensure that there are no location constraints or Directed Routing constraints on the MIG core logic/routes that could conflict with automatic placement and routing. To generate an NCD that can be used for debugging in FPGA Editor, please re-run PAR with the environment variable XIL_PAR_DISABLE_MIG_ANALYSIS 1. Note that if this NCD is used, the design can fail in hardware. Below is the list of nets in which PAR had problems routing optimally:
```

```
Sig:
u_ddr2_top_0/u_mem_if_top/u_phy_top/u_phy_io/gen_dq[0].u_iob_dq/stg1_out_rise_sg3
Sig:
u_ddr2_top_0/u_mem_if_top/u_phy_top/u_phy_io/gen_dq[1].u_iob_dq/stg1_out_rise_sg3
```

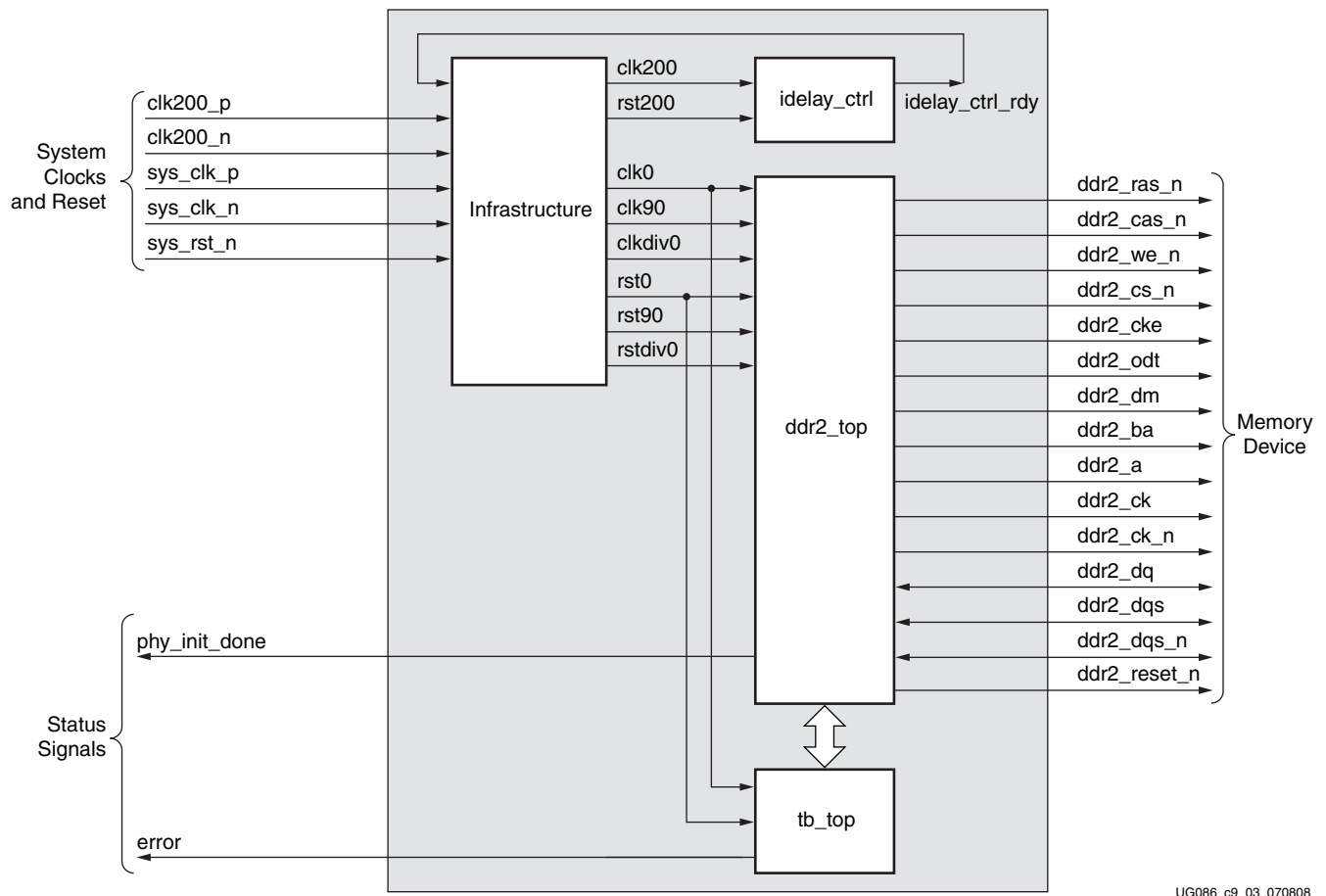
MIG Tool Design Options

MIG provides various options to generate the design with or without a testbench or with or without a PLL. This section provides detailed descriptions of the type of design generated by the user using various options. [Figure 9-3](#) and [Figure 9-4](#) represent the system clock for differential only. For more information on the clocking structure, refer to [“Clocking Scheme,” page 377](#).

MIG outputs both an `example_design` and a `user_design`. The MIG-generated `example_design` includes the entire memory controller design along with a synthesized testbench (example user application). This testbench generates sample writes and reads and then uses comparison logic to verify that the data patterns written are the same as those received. This `example_design` can be used to test functionality both in simulation and in hardware. The `user_design` includes the memory controller design only. This design allows users to connect the MIG memory controller design to a user developed testbench (user application). Refer to [Table 9-5, page 378](#) for user interface signals, the [“User Interface Accesses,” page 381](#) for timing restriction on user interface signals, and [Figure 9-12, page 384](#) for write interface timing.

[Figure 9-3](#) shows a top-level block diagram of a DDR2 SDRAM design with a PLL and a testbench. The `sys_clk_p` and `sys_clk_n` pair are differential input system clocks. [“Clocking Scheme,” page 377](#) describes how various clocks are generated using the PLL. The PLL is instantiated in the infrastructure module that generates the required design clocks. `clk200_p` and `clk200_n` are used for the `idelay_ctrl` element. `Sys_rst_n` is an active-Low system reset signal. All design resets are generated using it. The error output signal indicates whether the case passes or fails. The testbench module does writes and reads,

and also compares the read data with written data. The error signal is driven High on data mismatches. The phy_init_done signal indicates the completion of initialization and calibration of the design.



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Figure 9-3: Top-Level Block Diagram of the DDR2 SDRAM Design with a PLL and a Testbench

Figure 9-4 shows a top-level block diagram of a DDR2 SDRAM design with a PLL but without a testbench. The `sys_clk_p` and `sys_clk_n` signals are differential input system clocks. “Clocking Scheme,” page 377 describes how various clocks are generated using the PLL. The PLL is instantiated in the infrastructure module that generates the required design clocks. The `clk200_p` and `clk200_n` signals are used for the `idelay_ctrl` element. The `sys_rst_n` signal is the active-Low system reset signal. All design resets are gated by the locked signal. The user has to drive the user application signals. The design provides the `clk_tb` and `reset_tb` signals to the user in order to synchronize with the design. The `clk0_tb` signal is connected to `clk0` in the controller. If the user clock domain is different from `clk0/clk0_tb`, the user should add FIFOs for all the inputs and outputs of the controller (user application signals) in order to synchronize them to the `clk0_tb` clock. The `phy_init_done` signal indicates the completion of initialization and calibration of the design.

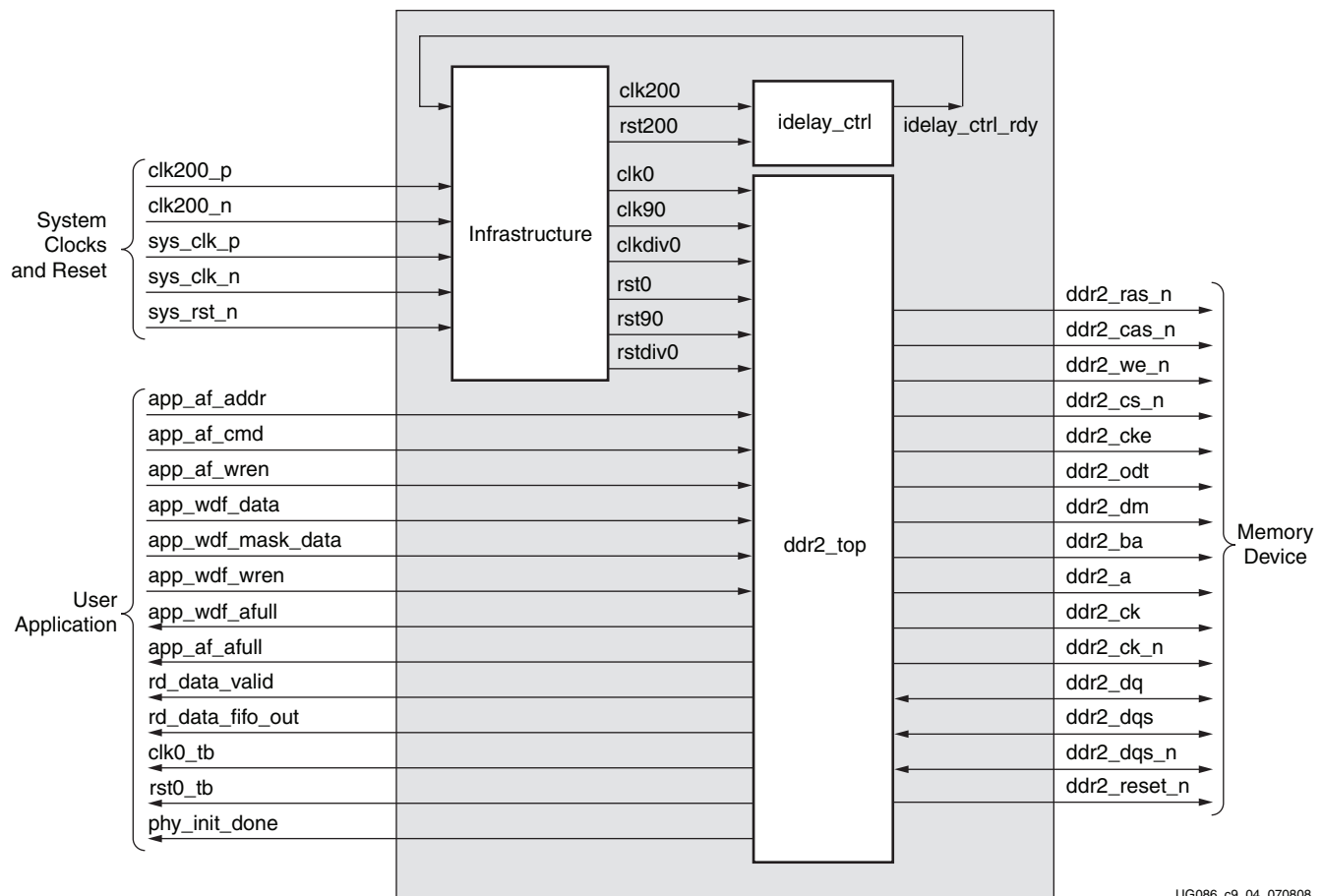
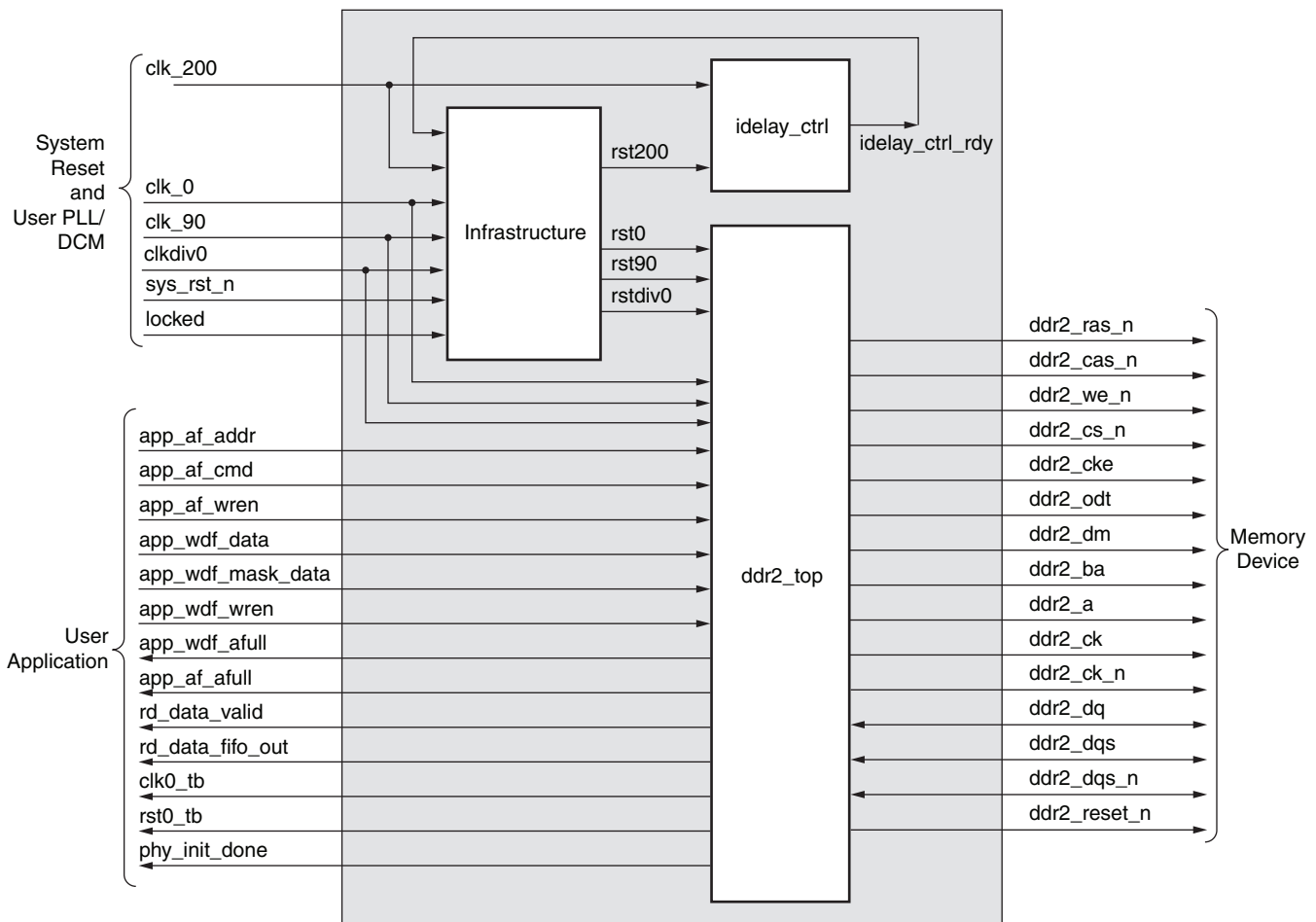


Figure 9-4: Top-Level Block Diagram of the DDR2 SDRAM Design with a PLL but without a Testbench

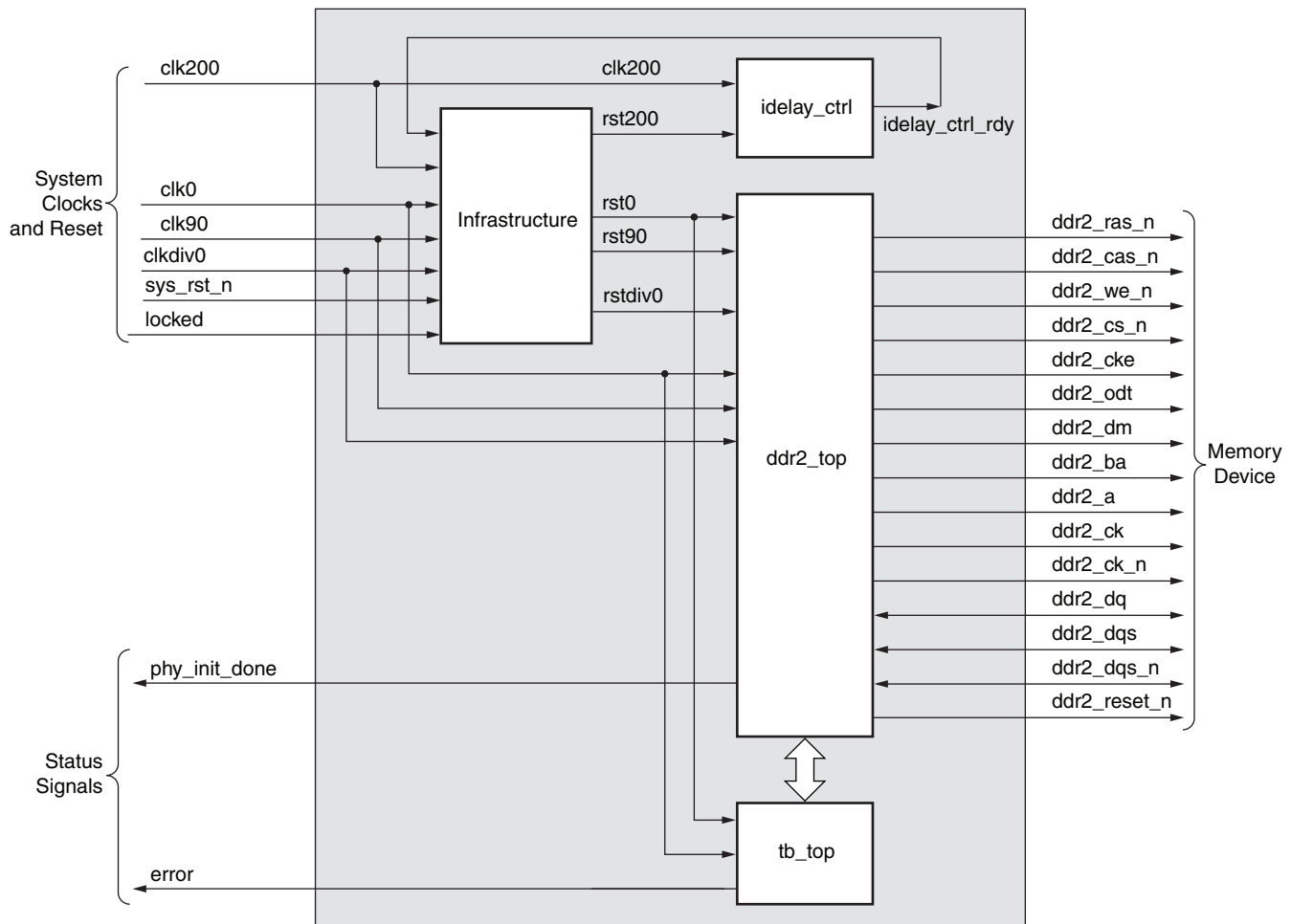
Figure 9-5 shows a top-level block diagram of a DDR2 SDRAM design without a PLL or a testbench. The user should provide all the design clocks and the locked signal. “Clocking Scheme,” page 377 explains the details of how to generate the design clocks from the user interface. These clocks should be single-ended. The sys_rst_n signal is the active-Low system reset signal. All design resets are gated by the locked signal. The user application must have a PLL/DCM primitive instantiated in the design, and all user clocks should be driven through BUFs. The user has to drive the user application signals. The design provides the clk_tb and reset_tb signals to the user in order to synchronize with the design. The clk0_tb signal is connected to clk0 in the controller. If the user clock domain is different from clk0/clk0_tb, the user should add FIFOs for all the inputs and outputs of the controller (user application signals) in order to synchronize them to the clk0_tb clock. The phy_init_done signal indicates the completion of initialization and calibration of the design.



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Figure 9-5: Top-Level Block Diagram of the DDR2 SDRAM Design without a PLL or a Testbench

Figure 9-6 shows a top-level block diagram of a DDR2 SDRAM design without a PLL but with a testbench. The user should provide all the clocks and the locked signal. “[Clocking Scheme](#),” page 377 explains the details of how to generate the design clocks from the user interface. These clocks should be single-ended. `sys_rst_n` is the active-Low system reset signal. All design resets are gated by the locked signal. The user application must have a PLL/DCM primitive instantiated in the design, and all user clocks should be driven through BUFGs. The error output signal indicates whether the case passes or fails. The testbench module does writes and reads, and also compares the read data with the written data. The error signal is driven High on data mismatches. The `phy_init_done` signal indicates the completion of initialization and calibration of the design.



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Figure 9-6: Top-Level Block Diagram of the DDR2 SDRAM Design without a PLL but with a Testbench

DDR2 Controller Submodules

Figure 9-7 is a detailed block diagram of the DDR2 SDRAM controller. The design top module is expanded to show various internal blocks. The functions of these blocks are explained in the subsections following the figure.

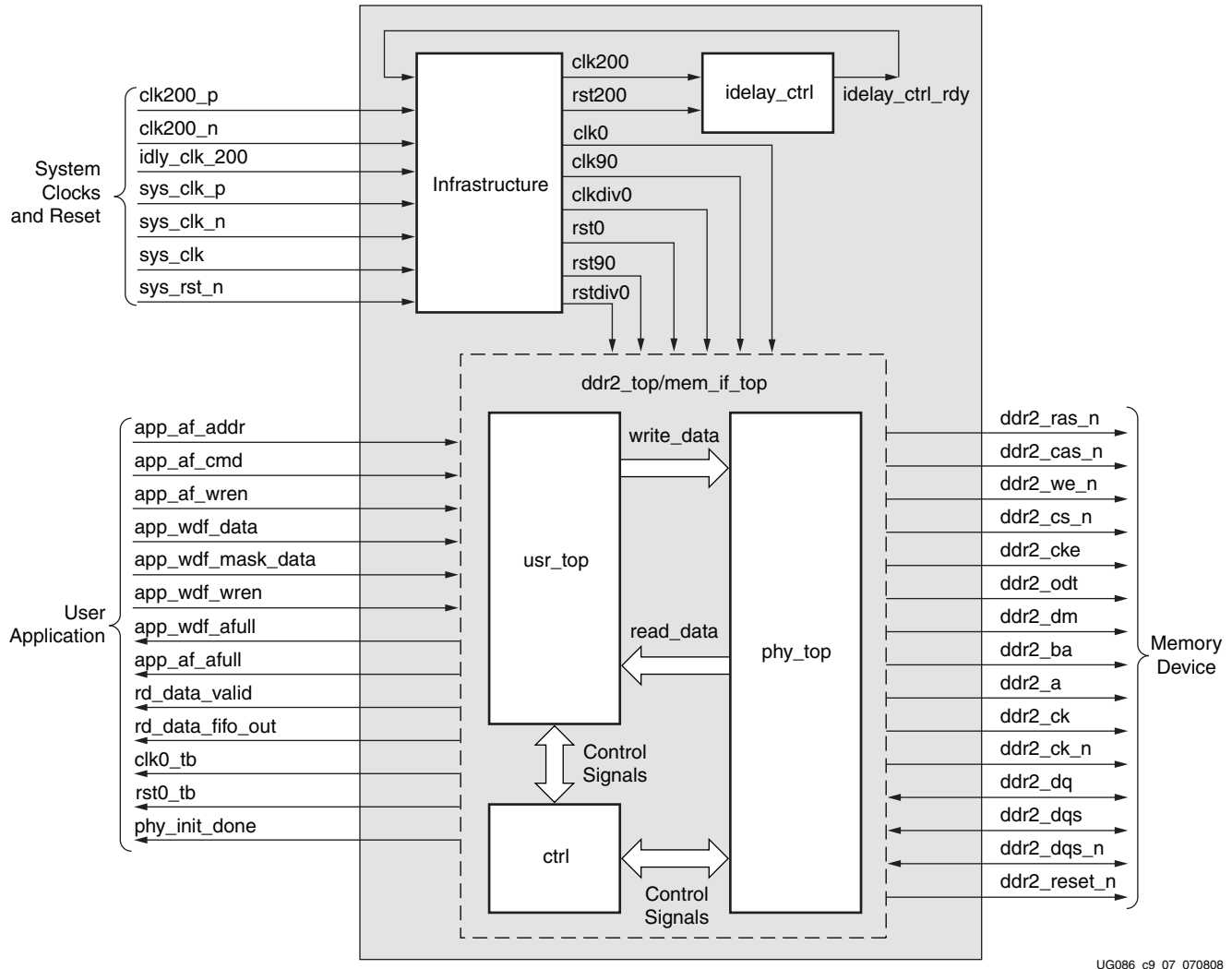


Figure 9-7: DDR2 Memory Controller Block Diagram

Infrastructure

The infrastructure module generates the design clocks and reset signals. When differential clocking is used, `sys_clk_p`, `sys_clk_n`, `clk_200_p`, and `clk_200_n` signals appear. When single-ended clocking is used, `sys_clk` and `idly_clk_200` signals appear. In addition, clocks are available for design use and a 200 MHz clock is provided for the `IDELAYCTRL` primitive. Differential and single-ended clocks are passed through global clock buffers before connecting to a PLL/DCM. For differential clocking, the output of the `sys_clk_p/sys_clk_n` buffer is single-ended and is provided to the PLL/DCM input. Likewise, for single-ended clocking, `sys_clk` is passed through a buffer and its output is provided to the PLL/DCM input. The outputs of the PLL/DCM are `clk0` (0° phase-shifted version of the input clock) `clk90` (90° phase-shifted version of the input clock), and `clkdiv0`

(half the frequency of the input clock and phase aligned with clk0). After the PLL/DCM is locked, the design is in the reset state for at least 25 clocks. The infrastructure module also generates all of the reset signals required for the design.

PLL/DCM

In MIG 3.0 and later, the DCM is replaced with a PLL for all Virtex-5 FPGA designs. If the user selects a design with a PLL in the GUI, the infrastructure module will have both PLL and DCM codes. The CLK_GENERATOR parameter enables either a PLL or a DCM in the infrastructure module. The CLK_GENERATOR parameter is set to PLL by default. If the user wants to use DCM, this parameter should be changed manually to DCM.

For designs without a PLL, the user application must have a PLL/DCM primitive instantiated in the design, and all user clocks should be driven through BUFs.

Idelay_ctrl

This module instantiates the IDELAYCTRL primitive of the Virtex-5 FPGA. The IDELAYCTRL primitive is used to continuously calibrate the individual delay elements in its region to reduce the effect of process, temperature, and voltage variations. A 200 MHz clock has to be fed to this primitive. For more information on IDELAYCTRLs, refer to section [“Verify IDELAYCTRL Instantiation for Virtex-4 and Virtex-5 FPGA Designs”](#) in [Chapter 14](#).

Ctrl

The ctrl module is the main controller of the Virtex-5 FPGA DDR2 SDRAM controller design. It generates all the control signals required for the DDR2 memory interface and the user interface. During the normal operation, this module toggles the memory address and control signals.

The ctrl module decodes the user command and issues the specified command to the memory. The app_af_cmd signal is decoded as a write command when it equals 3'b000, and app_af_cmd is decoded as a read command when it equals 3'b001. The commands and control signals are generated based on the input burst length and CAS latency. The controller state machine issues the commands in the correct sequence while determining the timing requirements of the memory.

In the multi-bank mode (MULTIBANK_EN = 1), the controller has the ability to keep four banks open at a time. The banks are opened in the order of the commands that are presented to the controller. In the event that four banks are already opened and an access arrives to the fifth bank, the least recently used bank is closed and the new bank is opened. All the banks are closed during auto refresh and are opened as commands are presented to the controller. Depending on the traffic pattern, the multi-bank enable mode can increase the efficiency of the design.

In the single-bank mode (MULTIBANK_EN = 0), the controller keeps one bank open at a time. When there is an access to a different bank or to a different row in the current bank, the controller closes the current row and bank and opens the new row and bank.

phy_top

The phy_top module is the top level of the physical interface of the design. The physical layer includes the input/output blocks (IOBs) and other primitives used to read and write the double data rate signals to and from the memory, such as IDDR and ODDR. This module also includes the IODELAY elements of the Virtex-5 FPGA. These IODELAY

elements are used to delay the data signals to capture the valid data into the Read Data FIFO.

The memory control signals, such as RAS_N, CAS_N, and WE_N, are driven from the buffers in the IOBs. All the input and output signals to and from the memory are referenced from the IOB to compensate for the routing delays inside the FPGA.

The `phy_init` module, which is instantiated in the `phy_top` module, is used to initialize the DDR2 memory in a predefined sequence according to the JEDEC standard for DDR2 SDRAM.

The `phy_calib` module calibrates the design to align the strobe signal such that it always captures the valid data in the FIFO. This calibration is needed to compensate for the trace delays between the memory and the FPGA devices.

The `phy_write` module splits the user data into rise data and fall data to be sent to the memory as a double data rate signal using ODDR. Similarly, while reading the data from memory, the data from IDDR is combined to get a single vector that is written into the read FIFO.

usr_top

The `usr_top` module is the user interface block of the design. It receives and stores the user data, command, and address information in respective FIFOs. The `ctrl` module generates the required control signals for this module. During a write operation, the data stored in the `usr_wr_fifo` is read and given to the physical layer to output to the memory. Similarly, during a read operation, the data from the memory is read via IDDR and written into the FIFOs. This data is given to the user with a valid signal (`rd_data_valid`), which indicates valid data on the `rd_data_fifo_out` signal. [Table 9-6](#) lists the user interface signals.

The FIFO36 and FIFO36_72 primitives are used for loading address and data from the user interface. The FIFO36 primitive is used in the `ddr2_usr_addr_fifo` module. The FIFO36_72 primitive is used in the `ddr2_usr_wr` and `ddr2_usr_rd` modules. Every FIFO has two FIFO threshold attributes, `ALMOST_EMPTY_OFFSET` and `ALMOST_FULL_OFFSET`, that are set to 7 and F, respectively, in the RTL by default. These values can be changed as needed. For valid FIFO threshold offset values, refer to UG190 [\[Ref 10\]](#).

Test Bench

The MIG tool generates two RTL folders, `example_design` and `user_design`. The `example_design` folder includes the synthesizable test bench, while `user_design` does not include the test bench modules. The MIG test bench performs eight write commands and eight read commands in an alternating fashion. The number of words in a write command depends on the burst length. For a burst length of 4, the test bench writes a total of 32 data words for all eight write commands (16 rise data words and 16 fall data words). For a burst length of 8, the test bench writes a total of 64 data words. It writes the data pattern of FF, 00, AA, 55, 55 AA, 99, 66 in a sequence of which FF, AA, 55, and 99 are rise data words and 00, 55, AA, and 66 are fall data words for an 8-bit design. The falling edge data is the complement of the rising edge data. For a burst length of 4, the data sequence for the first write command is FF, 00, AA, 55, and the data sequence for the second write command is 55, AA, 99, 66. For a burst length of 8, the data pattern for the first write command is FF, 00, AA, 55, 55 AA, 99, 66 and the same pattern is repeated for all the remaining write commands. This data pattern is repeated in the same order based on the number of data words written. For data widths greater than 8, the same data pattern is concatenated for the other bits. For a 32-bit design and a burst length of 8, the data pattern for the first write command is FFFFFFFF, 00000000, AAAAAAAAAA, 55555555, 55555555, AAAAAAAAAA, 99999999, 66666666.

Address generation logic generates eight different addresses for eight write commands. The same eight address locations are repeated for the following eight read commands. The read commands are performed at the same locations where the data is written. There are total of 32 different address locations for 32 write commands, and the same address locations are generated for 32 read commands. Upon completion of a total of 64 commands, including both writes and reads (eight writes and eight reads repeated four times), address generation rolls back to the first address of the first write command and the same address locations are repeated. The MIG test bench exercises only a certain memory area. The address is formed such that all address bits are exercised. During writes, a new address is generated for every burst operation on the column boundary.

During reads, comparison logic compares the read pattern with the pattern written, i.e., the FF, 00, AA, 55, 55 AA, 99, 66 pattern. For example, for an 8-bit design of burst length 4, the data written for a single write command is FF, 00, AA, 55. During reads, the read pattern is compared with the FF, 00, AA, 55 pattern. Based on a comparison of the data, a status signal error is generated. If the data read back is the same as the data written, the error signal is 0, otherwise it is 1. Comparison logic only compares the DATA bits and not the ECC data pattern. For example, for a 72-bit ECC design, comparison logic only compares 64 bits. The 8 MSBs (ECC bits) are not compared.

DDR2 SDRAM Initialization

DDR2 memory is initialized through a specified sequence as per both Micron and JEDEC specifications. Initialization logic is implemented in the physical layer.

DDR2 SDRAM Design Calibration

Before issuing user read and write commands, the read datapath is calibrated to ensure that correct data is captured into the CLK0 domain of the FPGA. Calibration logic is implemented in the physical layer of the design. [Figure 9-8](#) shows overall calibration sequence.

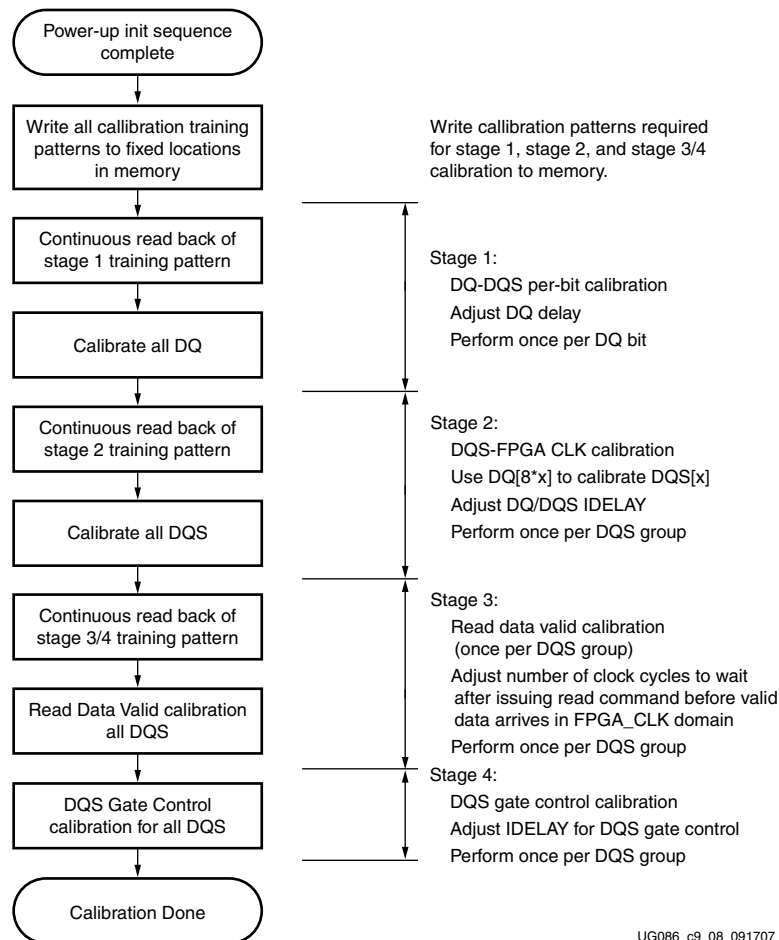


Figure 9-8: Overall Design Calibration Sequence

The first calibration stage is used to position the DQS in the DQ valid window. This synchronizes the capture of DQ using DQS in the IDDR flop. A training pattern of 1 for rise and 0 for fall data is written into the memory and is continuously read back. The DQ and IDELAYS are adjusted depending upon the DQ to DQS relationship. Per-bit deskew is performed on the DQ bits.

The second calibration stage is between the DQS and the FPGA clock. This synchronizes the transfer of data between the IDDR flop and flip-flops located in the FPGA fabric. The DQ and DQS IDELAY taps are incremented together to align to the FPGA clock domain.

The third calibration stage is the read-enable calibration, which is used to generate a read valid signal. The memory devices do not provide a signal indicating when the read data is valid. The read data is delayed by CAS latency, additive latency, the PCB trace, and the I/O buffer delays. The read-enable calibration is used to determine the delay between issuing a read command and the arrival of the read data.

The fourth calibration stage is used to align the DQS Gate signal from the controller to the falling edge of DQS. The DQS Gate controls the clock enable to the DQ IDDRs. It is used to prevent clocking of invalid data into the IDDR after the read postamble. This can happen because the DQS is 3-stated by the memory at the end of a read. The DQS can then go into an indeterminate value, causing false clocking of the IDDR.

After initialization and calibration is done, the controller is signaled to start normal operation of the design. Now, the controller can start issuing user write and read commands to the memory.

Clocking Scheme

[Figure 9-10, page 378](#) shows the clocking scheme for this design. Global and local clock resources are used.

The global clock resources consist of a PLL or a DCM, three BUFGs on PLL/DCM output clocks, and one BUFG for clk200. The local clock resources consist of regional I/O clock networks (BUFIO). The global clock architecture is discussed in this section.

The MIG tool allows the user to customize the design such that the PLL/DCM is not included. In this case, clk0, clk90, clkdiv0 and IDELAYCTRL clock clk200 must be supplied by the user.

Global Clock Architecture

The user must supply two input clocks to the design:

- A system clock running at the target frequency for the memory
- A 200 MHz clock for the IDELAYCTRL blocks.

These clocks can be either single-ended or differential. User can select single-ended or differential clock input option from MIG GUI. Differential clocks are connected to the IBUFGDS and single-ended clock is connected to IBUFG.

The system clock from the output of the IBUFGDS or the IBUFG is connected to the PLL/DCM to generate the various clocks used by the memory interface logic.

The clk200 output of the IBUFGDS or the IBUFG is connected to the BUFG. The output of the BUFG is used for IDELAY IOB delay blocks for aligning read capture data.

The PLL/DCM generates three separate synchronous clocks for use in the design. This is shown in [Table 9-5, page 378](#), [Figure 9-9, page 378](#), and [Figure 9-10, page 378](#). The clock structure is the same for both example design and user design. For designs without PLL instantiation, PLL/DCM and the BUFGs should be instantiated at user end to generate the required clocks.

Table 9-5: DDR2 Interface Design Clocks

Clock	Description	Logic Domain
clk0	Skew compensated replica of the input system clock.	The clock for the controller and the user interface logic, most of the DDR2 bus-related I/O flip-flops (e.g., memory clock, control/address, output DQS strobe, and DQ input capture). This clock is used to register the data, address, and command signals, and the address and data enables for the user interface logic ⁽¹⁾ . This clock is also used to generate the read data, read data valid, and FIFO status signals.
clk90	90° phase-shifted version of clk0	Used in the write data path section of physical layer. Clocks write path control logic, DDR2 side of the Write Data FIFO, and output flip-flops for DQ.
clkdiv0	Divided-by-2 and edge-aligned version of clk0	Clocks the memory initialization and read capture timing calibration state machines in the PHY layer.

Notes:

1. See “User Interface Accesses,” page 381 for timing requirements and restrictions on the user interface signals.

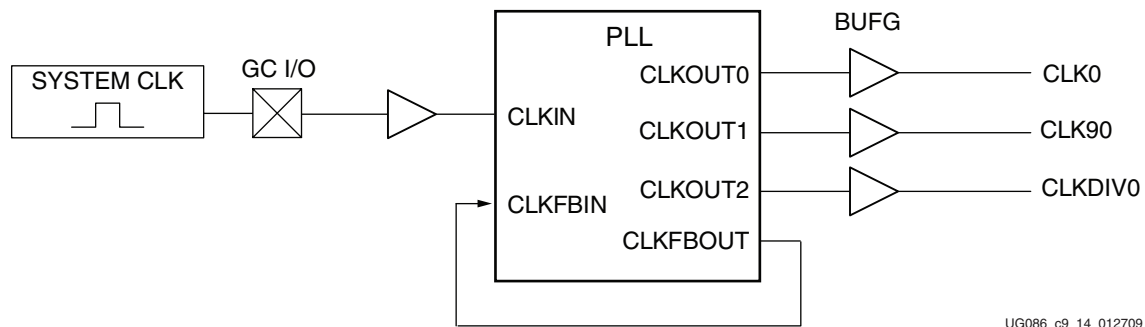


Figure 9-9: Clocking Scheme for DDR2 Interface Logic Using PLL

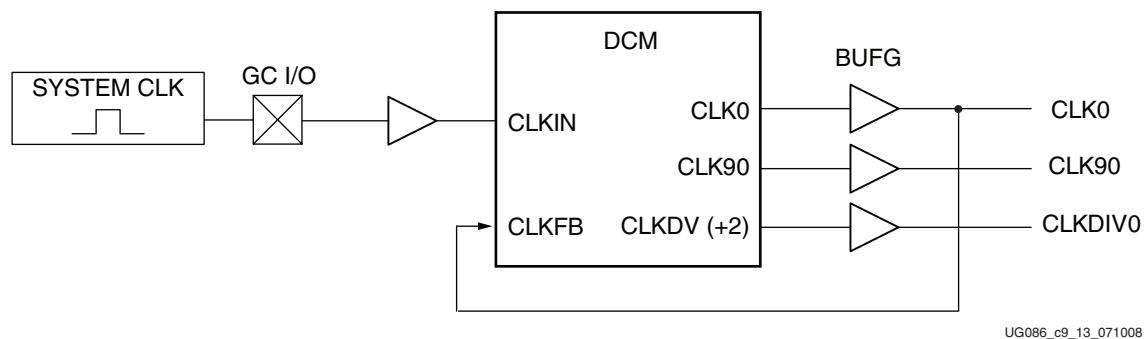


Figure 9-10: Clocking Scheme for DDR2 Interface Logic Using DCM

DDR2 SDRAM System and User Interface Signals

Table 9-6 and Table 9-7 describe the system interface signals for designs generated with and without a PLL, respectively.

Table 9-6: DDR2 SDRAM Controller System Interface Signals (with a PLL)

Signal Name	Direction	Description
sys_clk_p, sys_clk_n	Input	Differential input clock to the PLL/DCM. The DDR2 controller and memory operate at this frequency. This differential input clock pair is present only when the DIFFERENTIAL clocks option is selected in MIG FPGA options page.
sys_clk	Input	Single-ended input clock to the PLL/DCM. The DDR2 controller and memory operate at this frequency. This input clock is present only when the SINGLE_ENDED clocks option is selected in the MIG FPGA options page.
clk200_p, clk200_n	Input	200 MHz differential input clock for the IDELAYCTRL primitive of Virtex-5 FPGAs. This differential input clock pair is present only when the DIFFERENTIAL clocks option is selected in MIG FPGA options page.
idly_clk_200	Input	200 MHz single-ended input clock for the IDELAYCTRL primitive of Virtex-5 FPGAs. This input clock is present only when the SINGLE_ENDED clocks option is selected in the MIG FPGA options page.
sys_rst_n	Input	Active-Low reset to the DDR2 controller.

Table 9-7: DDR2 SDRAM Controller System Interface Signals (without a PLL)

Signal	Direction	Description
clk0	Input	The DDR2 SDRAM controller and memory operate on this clock.
clk90	Input	90° phase-shifted clock with the same frequency as clk0.
clkdiv0	Input	Clocks the memory initialization and read capture timing calibration state machines in the PHY layer.
clk200	Input	200 MHz differential input clock for the IDELAYCTRL primitive of Virtex-5 FPGAs.
sys_rst_n	Input	Active-Low reset to the DDR2 SDRAM controller. This signal is used to generate the synchronous system reset.
locked	Input	The status signal indicating whether the PLL is locked or not. This signal is used to generate the synchronous system reset.

Table 9-8 describes the user interface signals.

Table 9-8: DDR2 SDRAM Controller User Interface Signals

Signal	Direction ⁽¹⁾	Description
app_af_cmd[2:0]	Input	3-bit command to the Virtex-5 FPGA DDR2 SDRAM design. app_af_cmd = 3'b000 for write command app_af_cmd = 3'b001 for read command Other combinations are invalid. Functionality of the controller is unpredictable for unimplemented commands.
app_af_addr[30:0] ⁽²⁾	Input	Gives information about the address of the memory location to be accessed. This bus contains the bank address, the row address, and the column address. Column address = app_af_addr[COL_WIDTH-1: 0] Row address = app_af_addr[ROW_WIDTH+COL_WIDTH-1: COL_WIDTH] Bank address = app_af_addr[BANK_WIDTH+ROW_WIDTH+COL_WIDTH-1: ROW_WIDTH+COL_WIDTH] Chip select ⁽³⁾ = app_af_addr[BANK_WIDTH+ROW_WIDTH+COL_WIDTH]
app_af_wren	Input	Write enable to the User Address FIFO. This signal should be synchronized with the app_af_addr and app_af_cmd signals.
app_wdf_data[2*DQ_WIDTH-1:0]	Input	User input data. It should contain the fall data and the rise data. Rise data = app_wdf_data[DQ_WIDTH-1: 0] Fall data = app_wdf_data[2*DQ_WIDTH-1: DQ_WIDTH]
app_wdf_mask_data[2*DM_WIDTH-1: 0]	Input	User mask data. It should contain the masking information for both rise and fall data. Rise mask data = app_wdf_mask_data[DM_WIDTH-1: 0] Fall mask data = app_wdf_mask_data[2*DM_WIDTH-1: DM_WIDTH]
app_wdf_wren	Input	Write enable for the User Write FIFO. This signal should be synchronized with the app_wdf_data and app_wdf_mask_data signals.
app_af_afull	Output	Almost Full status of the Address FIFO. When this signal is asserted, the user can write 12 more locations into the FIFO.
app_wdf_afull	Output	Almost Full status of the User Write FIFO. When this signal is asserted, the user can write 12 more locations into the FIFO.
rd_data_valid	Output	Status signal indicating read data is valid on the read data bus.
rd_data_fifo_out[2*DQ_WIDTH-1: 0]	Output	Read data from the memory.
phy_init_done	Output	Indicates the completion of initialization and calibration of the design.
clk0_tb	Output	Clock output to the user. All user interface signals must be synchronized with this clock. This signal is sourced from clk0 in the controller.

Table 9-8: DDR2 SDRAM Controller User Interface Signals (Cont'd)

Signal	Direction ⁽¹⁾	Description
rst0_tb	Output	Active-High reset for the user interface.

Notes:

1. Direction indicated in the table is referenced from the design perspective. For example, input here indicates that the signal is input to the design.
2. Addressing in Virtex-5 FPGAs is linear addressing (i.e., the row address immediately follows the column address bits, and the bank address follows the row address bits, thus supporting more devices). The number of address bits used depends on the density of the memory part. The controller ignores the unused bits, which can all be tied High.
3. For single-rank devices, Chip Select is *not* taken from the user address (i.e., app_af_addr). Hence, the controller always selects all of the existing devices. For dual-rank devices, the corresponding device *is* selected based on the Chip Select value. In other words, for dual-rank devices, the Chip Select is taken from the user address (i.e., app_af_addr). CS0 is selected for a Chip Select value of 0, and CS1 is selected for a Chip Select value of 1.

Table 9-9 lists the signals between the user interface and the controller.

Table 9-9: Signals between User Interface and Controller

Port Name	Port Width	Port Description
af_cmd	3	Output of the Address FIFO in the user interface. Monitors the FIFO full status flag to the write address into the Address FIFO.
af_addr	31	Output of the Address FIFO in the user interface. The mapping of these address bits is [30:0]: Memory Address (CS, Bank, Row, Column). Monitors the FIFO full status flag to the write address into the Address FIFO.
af_empty	1	The user interface Address FIFO empty status flag output. The user application can write to the Address FIFO when this signal is asserted until the write data FIFO full status flag is asserted. FIFO36 Almost Empty flag.
ctrl_af_rden	1	Read Enable input to Address FIFO in the user interface. This signal is asserted for one clock cycle when the controller state is write or read resulting from dynamic command requests.

User Interface Accesses

The user backend logic communicates with the memory controller through a FIFO-based user interface. This interface consists of three related buses: (1) a command/address FIFO bus accepts write/read commands as well as the corresponding memory address from the user, (2) a write data FIFO bus accepts the corresponding write data when the user issues a write command on the command/address bus, and (3) a read bus on which the corresponding read data for an issued read command is returned.

The user interface has the following timing and signaling restrictions:

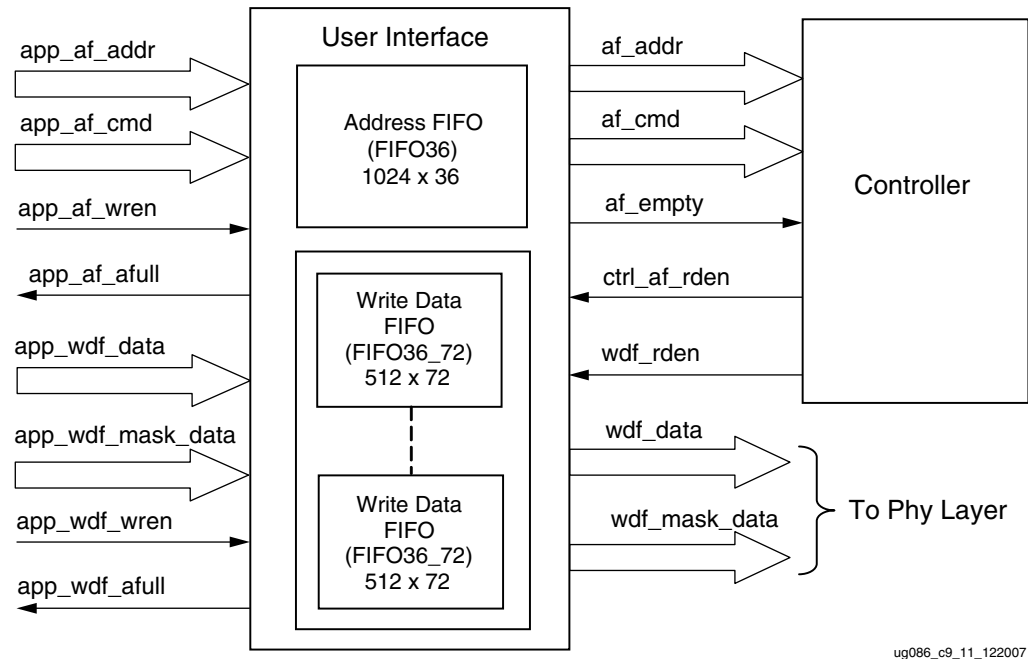
1. When issuing a write command, the first write data word must be written to the Write Data FIFO either prior to or on the same clock cycle as the when the write command is issued. In addition, the write data must be written by the user over consecutive clock cycles; there cannot be a break between words. These restrictions arise from the fact

that the controller assumes write data is available when it receives the write command from the user.

- The `clk0_tb` signal is connected to `clk0` in the controller. If the user clock domain is different from `clk0` / `clk0_tb` of MIG, the user should add FIFOs for all data inputs and outputs of the controller in order to synchronize them to the `clk0_tb`.

Write Interface

Figure 9-11 shows the user interface block diagram for write operations.



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Figure 9-11: User Interface Block Diagram for Write Operation

The following steps describe the architecture of the Address and Write Data FIFOs and show how to perform a write burst operation to DDR2 SDRAM from the user interface.

- The user interface consists of an Address FIFO and a Write Data FIFO. The Write Data FIFO is constructed using the Virtex-5 FPGA FIFO36_72 primitive with a 512 x 72 configuration. The 72-bit architecture comprises one 64-bit port and one 8-bit port. For Write Data FIFOs, the 64-bit port is used for data bits and the 8-bit port is used for mask bits for ECC-disabled designs. Mask bits are available only when supported by the memory part and when data mask is enabled in the MIG GUI. Some memory parts, such as Registered DIMMs of x4 parts, do not support mask bits.
- In ECC-enabled designs, the 64-bit port is used for data bits and the 8-bit port is used for ECC data. The attributes passed to the Virtex-5 FPGA FIFO36_72 primitive are different for ECC-enabled designs; attribute `EN_ECC_WRITE` is set to `TRUE` for ECC-enabled designs to enable the generation of ECC data.
- The Address FIFO is constructed using the Virtex-5 FPGA FIFO36 primitive with a 1024 x 36 configuration. The 36-bit architecture comprises one 32-bit port and one 4-bit port. The 32-bit port is used for the address (`app_af_addr`) and the 4-bit port is used for the command (`app_af_cmd`).

4. The Address FIFO is common for both Write and Read commands. It comprises an address part and a command part. Command bits discriminate between write and read commands.
5. User interface data width `app_wdf_data` is twice that of the memory data width. For an 8-bit memory width, the user interface is 16 bits consisting of rising-edge data and falling-edge data. There is a mask bit for every 8 bits of data. For 72-bit memory data, the user interface data width `app_wdf_data` is 144 bits, and the mask data `app_wdf_mask_data` is 18 bits.
6. The minimum configuration of the Write Data FIFO is 512 x 72 for a memory data width of 8 bits. For an 8-bit memory data width, the least-significant 16 bits of the data port are used for write data and the least-significant two bits of the 8-bit port are used for mask bits. The controller internally pads all zeros for the most-significant 48 bits of the 64-bit port and the most-significant 6 bits of the 8-bit port.
7. Depending on the memory data width, MIG instantiates multiple `FIFO36_72s` to gain the required width. For designs using 8-bit to 32-bit data width, one `FIFO36_72` is instantiated; for 72-bit data width, a total of three `FIFO36_72s` are instantiated. The bit architecture comprises 32 bits of rising-edge data, 4 bits of rising-edge mask, 32 bits of falling-edge data, and 4 bits of falling-edge mask, which are all stored in a `FIFO36_72`. MIG routes `app_wdf_data` and `app_wdf_mask_data` to `FIFO36_72s` accordingly.
8. The user can initiate a write to memory by writing to the Address FIFO and the Write Data FIFO when the FIFO full flags are deasserted. Status signal `app_af_full` is asserted when the Address FIFO is full; similarly, `app_wdf_full` is asserted when the Write Data FIFO is full.
9. At power on, both the Address FIFO and Write Data FIFO full flags are deasserted.
10. The user should assert Address FIFO write-enable signal `app_af_wren` along with address `app_af_addr` and command `app_af_cmd` to store the address and command into Address FIFO.
11. The user data should be synchronized to the `clk_tb` clock. The user should assert the Data FIFO write-enable signal `app_wdf_wren` along with write data `app_wdf_data` and mask data `app_wdf_mask_data` to store the write data and mask data into the Write Data FIFOs. The user should provide both rising-edge and falling-edge data together for each write to the Data FIFO. The Virtex-5 FPGA DDR2 SDRAM controller design supports byte-wise masking of data only.
12. The write command should be given by keeping `app_af_cmd = 3'b000` and asserting `app_af_wren`. Address information is given on the `app_af_addr` signal. Address and command information is written into the User Address FIFO.
13. After the completion of the initialization and calibration process and when the User Address FIFO empty signal is deasserted, the controller reads the Command and Address FIFO and issues a write command to the DDR2 SDRAM.
14. The write timing diagram in [Figure 9-12](#) is derived from the MIG-generated testbench for a burst length of 4. As shown, each write to the Address FIFO should have two writes to the Data FIFO. The `phy_init_done` signal indicates memory initialization and calibration completion.

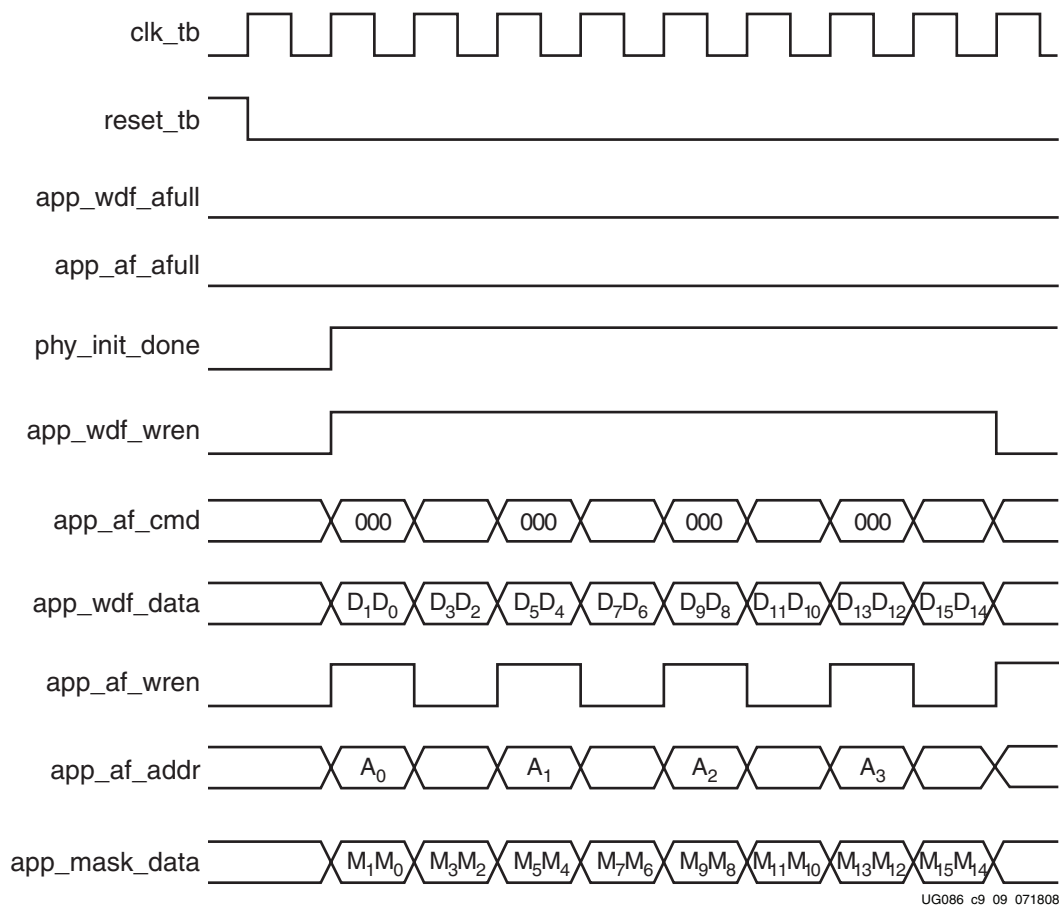
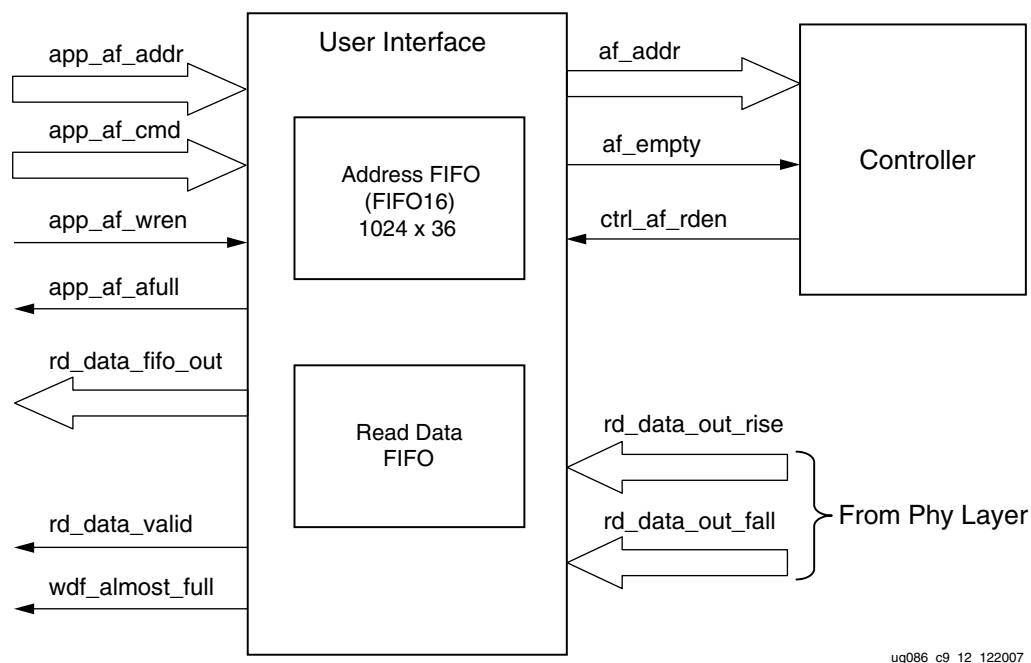


Figure 9-12: DDR2 SDRAM Write Burst for Four Bursts (BL = 4)

Read Interface

Figure 9-13 shows the block diagram of the read interface.



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Figure 9-13: User Interface Block Diagram for Read Operation

The following steps describe the architecture of the Read Data FIFO and show how to perform a read burst operation from DDR2 SDRAM from user interface.

1. The Read Data FIFOs are constructed using the Virtex-5 FPGA FIFO36_72 primitive with a 512 x 72 configuration for ECC-enabled designs. For non-ECC designs, read data is latched using the flops.
2. In ECC-enabled designs, the 64-bit port is used for data bits and the 8-bit port is used for ECC data. The Virtex-5 FPGA FIFO36_72 performs ECC comparison when the attribute EN_ECC_READ is set during read operation. MIG instantiates the FIFOs appropriately for ECC or non-ECC designs.
3. The user can initiate a read to memory by writing to the Address FIFO when the FIFO full flag `app_af_afull` is deasserted.
4. To write the read address and read command into the Address FIFO, the user should issue the Address FIFO write-enable signal `app_af_wren` along with read address `app_af_addr` and `app_af_cmd` is the command (set to 001 for a read command).
5. The controller reads the Address FIFO and generates the appropriate control signals to memory. After decoding `app_af_cmd`, the controller issues a read command to the memory at the specified address.
6. Prior to the actual read and write commands, the design calibrates the latency in number of clock cycles from the time the read command is issued to the time the data is received. Using this precalibrated delay information, the controller stores the read data in the Read Data FIFOs.
7. The `rd_data_valid` signal is asserted when data is available in the Read Data FIFOs.
8. When the calibration is completed, the controller generates the control signals to capture the read data from the FIFO according to the CAS latency selected by the user.

The `rd_data_valid` signal is asserted when the read data is available to the user, and `rd_data_fifo_out` is the read data from the memory to the user.

9. Figure 9-14 shows the user interface timing diagram for burst length of four.

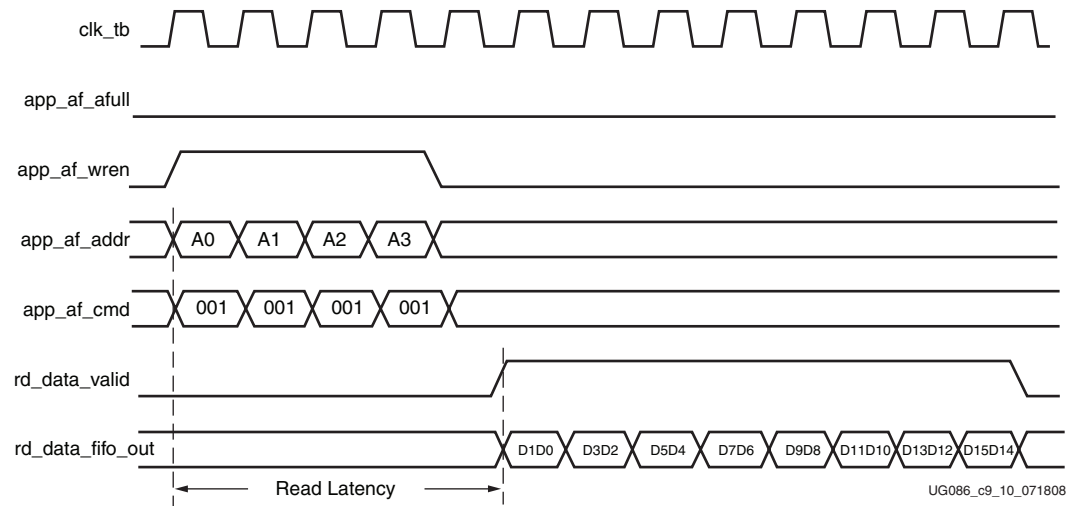


Figure 9-14: DDR2 SDRAM Read Burst (BL = 4) for Four Bursts

Read latency is defined as the time between when the read command is written to the user interface bus until when the corresponding first piece of data is available on the user interface bus (see Figure 9-14).

When benchmarking read latencies, it is important to specify the exact conditions under which the measurement occurs.

Read latency varies based on the following parameters:

- Number of commands already in the FIFO pipeline before the read command is issued
- Whether an ACTIVATE command needs to be issued to open the new bank/row
- Whether a PRECHARGE command needs to be issued to close a previously opened bank
- Specific timing parameters for the memory, such as T_{RAS} and T_{RCD} in conjunction with the bus clock frequency
- Commands can be interrupted, and banks/rows can forcibly be closed when the periodic AUTO REFRESH command is issued
- CAS latency
- Board-level and chip-level (for both memory and FPGA) propagation delays

Table 9-10 and Table 9-11 show read latencies for the Virtex-5 FPGA DDR2 interface for two different conditions. Table 9-10 shows the case where a row activate is not required prior to issuing a read command on the DDR bus. This situation is possible, for example, when bank management is enabled, and the read targets an already opened bank. Table 9-11 shows the case when a read results in a bank/row conflict. In this case, a precharge of the previous row must be followed by an activation of the new row, which increases read latency. Other specific conditions are noted in the footnotes for each table.

Table 9-10: Read Latency without Precharge and Activate

Parameter	Number of Clocks
User READ command to empty signal deassertion (using FIFO36)	1 clock
Empty signal to READ command on DDR2 bus	8.5 clocks
READ command to read valid assertion	8.5 clocks
Total	18 clocks

Notes:

1. Test conditions: Clock frequency = 333 MHz, CAS latency = 5, DDR2 -3E speed grade device.
2. Access conditions: Read to an already open bank/row is issued to an empty control/address FIFO.
3. Some entries have fractional clock cycles because the inverted version of CLK0 is used to drive the DDR2 memory.
4. The Virtex-5 FPGA DDR2 interface uses a FIFO36 for the address/control FIFO. It is possible to shorten the READ command to empty signal deassertion latency by implementing the FIFO as a distributed RAM FIFO or removing the FIFO altogether, as the application requires.

Table 9-11: Read Latency with Precharge and Activate

Parameter	Number of Clocks
User READ command to empty signal deassertion (using FIFO36)	1 clock
Empty signal to PRECHARGE command on DDR2 bus	8.5 clocks
PRECHARGE to ACTIVE command to DDR2 memory	4 clocks
ACTIVE to READ command to DDR2 memory	4 clocks
READ command to read valid assertion	8.5 clocks
Total	26 clocks

Notes:

1. Test conditions: Clock frequency = 333 MHz, CAS latency = 5, DDR2 -3E speed grade device.
2. Access conditions: Read that results in a bank/row conflict is issued to an empty control/address FIFO. This requires that the previous bank/row be closed first.
3. Some entries have fractional clock cycles because the inverted version of CLK0 is used to drive the DDR2 memory.
4. The Virtex-5 FPGA DDR2 interface uses a FIFO36 for the address/control FIFO. It is possible to shorten the READ command to empty signal deassertion latency by implementing the FIFO as a distributed RAM FIFO or removing the FIFO altogether, as the application requires.

DDR2 SDRAM Signal Allocations

MIG allows banks to be selected for different classes of memory signals. Table 9-12 shows the list of signals allocated in a group from bank selection checkboxes.

Table 9-12: DDR2 SDRAM Signal Allocations

Bank Selected	Signals Allocated in the Group
Address	Memory address, memory control, and memory clock signals
Data	Data, data mask, and data strobes
System Control	System reset from user interface and status signals
System Clock	System clocks from the user interface

Note: Timing has been verified for most of the MIG generated configurations. For the best timing results, adjacent banks in the same column of the FPGA should be used. Banks that are separated by unbonded banks should be avoided because these can cause timing violations.

Simulating the DDR2 SDRAM Design

After generating the design, MIG creates a `sim` folder in the specified path. This folder contains simulation files for a particular design. The `sim` folder contains the external testbench, memory model, and `.do` file to simulate the generated design. The memory model files are currently generated in Verilog only. To learn more details about the files in the `sim` folder and to simulate the design, refer to “Simulation Guide,” page 499.

For both single- and dual-rank DIMMs, MIG outputs only the base part memory model. In the simulation testbench (`sim_tb_top` in the `sim` folder), MIG instantiates the required number of memory models. For example, a 1 GB single-rank DIMM with the base part is 1 Gb, and MIG instantiates the base model eight times. A dual-rank part (2 GB capacity) with the base part is 1 Gb. MIG instantiates a 1 Gb model 16 times (the first 8 instances correspond to CS0, and the remaining 8 instances correspond to CS1). If the MIG generated memory model is to be used with the user’s test bench, multiple instances should be used based on the selected configuration.

The MIG output memory model considers the `MEM_BITS` parameter by default for memory range allocation. This covers only a partial memory range, i.e., $2^{\text{MEM_BITS}}$. To allocate the full memory range, the `MAX_MEM` parameter should be set in the memory model. Allocating the full memory range might exceed the memory of the operating system, thus causing memory allocation failure in simulations.

Changing the Refresh Rate

The top-level parameter `TREFI_NS` should be changed to the selected refresh interval in ns. For example, to change the refresh rate to 3.9 μ s, set `TREFI_NS` to 3900. The controller issues a refresh approximately every $(\text{TREFI_NS} \times 1000) / \text{CLK_PERIOD}$ clock cycles, where `CLK_PERIOD` is the top-level parameter defining the clock period in ps. If the value in the formula exceeds 4095, the width signal `refi_cnt_r` in the `CTRL` module must be manually increased beyond 12 bits.

The `CKE` counter is a down-counter that is used to set the refresh interval, and its value is initialized to all ones during reset. To change `TREFI_NS`, `cke_200us_cnt_r` in the `ddr2_phy_init` HDL file must also be modified. This ensures that the 200 μ s initialization time is preserved. Bits must be added or removed based on the change made to the refresh interval.

Supported Devices

The design generated out of MIG is independent of memory package, hence the package part of the memory component is replaced with `XX` or `XXX`, where `XX` or `XXX` indicates a don't care condition. The tables below list the components (Table 9-8) and DIMMs (Table 9-11) supported by the tool for the DDR2 design. In supported devices, `X` in the components column denotes a single alphanumeric character. For example, `MT47H128M4XX-3` can be either `MT47H128M4BP-3` or `MT47H128M4B6-3`. `XX` for Registered DIMMs denotes a single or two alphanumeric characters. For example, `MT9HTF3272XX-667` can be either `MT9HTF3272Y-667` or `MT9HTF3272DY-667`. See Appendix G, “Low Power Options.”

Table 9-13: Supported Components for DDR2 SDRAM (Virtex-5 FPGAs)

Components	Packages (XX)	Components	Packages (XX)
MT47H64M4XX-3	BP	MT47H16M16XX-3	BG
MT47H64M4XX-37E	BP	MT47H16M16XX-37E	BG
MT47H64M4XX-5E	BP	MT47H16M16XX-5E	BG
MT47H128M4XX-3	B6,CB,GB	MT47H32M16XX-3	BN,CC,FN,GC
MT47H128M4XX-37E	B6,CB,GB	MT47H32M16XX-37E	BN,CC,FN,GC
MT47H128M4XX-5E	B6,CB,GB	MT47H32M16XX-5E	BN,CC,FN,GC
MT47H256M4XX-3	BT,HQ	MT47H64M16XX-3	BT,HR
MT47H256M4XX-37E	BT,HQ	MT47H64M16XX-37E	BT,HR
MT47H256M4XX-5E	BT,HQ	MT47H64M16XX-5E	BT,HR
MT47H512M4XX-3	HG	MT47H128M16XX-3	HG
MT47H512M4XX-37E	HG	MT47H128M16XX-37E	HG
MT47H512M4XX-5E	HG	MT47H128M16XX-5E	--
MT47H512M8XXX-25	THM	MT47H1G4XXX-3	THM
MT47H512M8XXX-3	THM	MT47H1G4XXX-37E	THM
MT47H512M8XXX-37E	THM	HYB18T1G800XXXX-37	C2F,C2FL
MT47H32M8XX-3	BP	HYB18T1G160XXXX-3S	C2F,C2FL
MT47H32M8XX-37E	BP	HYB18T1G160XXXX-37	C2F,C2FL
MT47H32M8XX-5E	BP	HYB18T1G400XXXX-3S	C2F,C2FL
MT47H64M8XX-3	B6,CB,F6,GB	HYB18T1G400XXXX-37	C2F,C2FL
MT47H64M8XX-37E	B6,CB,F6,GB	HYB18T512800XXXX-3S	B2F,B2FL
MT47H64M8XX-5E	B6,CB,F6,GB	HYB18T512800XXXX-37	B2F,B2FL
MT47H128M8XX-3	BT,HQ	HYB18T512160XXXX-3S	B2F,B2FL
MT47H128M8XX-37E	BT,HQ	HYB18T512160XXXX-37	B2F,B2FL
MT47H128M8XX-5E	BT,HQ	HYB18T512400XXXX-3S	B2F,B2FL
MT47H256M8XX-3	HG	HYB18T512400XXXX-37	B2F,B2FL
MT47H256M8XX-37E	HG	MT47H256M8XX-5E	HG

Table 9-14: Supported Registered DIMMs for DDR2 SDRAM (Virtex-5 FPGAs)

MT9HTF3272Y-667	MT18HTF12872Y-40E
MT9HTF3272PY-667	MT18HTF12872PY-40E
MT9HTF3272Y-53E	MT18HTF25672Y-667
MT9HTF3272PY-53E	MT18HTF25672PY-667
MT9HTF3272Y-40E	MT18HTF25672Y-53E
MT9HTF3272PY-40E	MT18HTF25672PY-53E
MT9HTF6472Y-667	MT18HTF25672Y-40E

Table 9-14: Supported Registered DIMMs for DDR2 SDRAM (Virtex-5 FPGAs)

MT9HTF6472PY-667	MT18HTF25672PY-40E
MT9HTF6472Y-53E	MT18HTF6472DY-667
MT9HTF6472PY-53E	MT18HTF6472PDY-667
MT9HTF6472Y-40E	MT18HTF6472DY-53E
MT9HTF6472PY-40E	MT18HTF6472PDY-53E
MT9HTF12872Y-667	MT18HTF6472DY-40E
MT9HTF12872PY-667	MT18HTF6472PDY-40E
MT9HTF12872Y-53E	MT18HTF12872DY-667
MT9HTF12872PY-53E	MT18HTF12872PDY-667
MT9HTF12872Y-40E	MT18HTF12872DY-53E
MT9HTF12872PY-40E	MT18HTF12872PDY-53E
MT18HTF6472G-53E	MT18HTF12872DY-40E
MT18HTF6472Y-667	MT18HTF12872PDY-40E
MT18HTF6472PY-667	MT18HTF25672DY-667
MT18HTF6472Y-53E	MT18HTF25672PDY-667
MT18HTF6472PY-53E	MT18HTF25672DY-53E
MT18HTF6472Y-40E	MT18HTF25672PDY-53E
MT18HTF6472PY-40E	MT18HTF25672DY-40E
MT18HTF12872Y-667	MT18HTF25672PDY-40E
MT18HTF12872PY-667	MT36HTJ51272Y-667
MT18HTF12872Y-53E	MT36HTJ51272Y-53E
MT18HTF12872PY-53E	MT36HTJ51272Y-40E
MT36HTF51272Y-667	MT36HTF51272Y-53E
MT36HTF51272Y-40E	--

Table 9-15: Supported UDIMMs for DDR2 SDRAM (Virtex-5 FPGAs)

MT4HTF1664AY-667	MT9HTF3272AY-40E
MT4HTF1664AY-53E	MT9HTF6472AY-667
MT4HTF1664AY-40E	MT9HTF6472AY-53E
MT4HTF3264AY-667	MT9HTF6472AY-40E
MT4HTF3264AY-53E	MT16HTF25664AX-667
MT4HTF3264AY-40E	MT16HTF25664AX-53E
MT4HTF6464AY-667	MT16HTF25664AX-40E
MT16HTF51264AY-667	MT16HTF51264AY-53E

Table 9-15: Supported UDIMMs for DDR2 SDRAM (Virtex-5 FPGAs)

MT4HTF6464AY-53E	MT18HTF6472AY-667
MT4HTF6464AY-40E	MT18HTF6472AY-53E
MT8HTF6464AY-667	MT18HTF6472AY-40E
MT8HTF6464AY-53E	MT18HTF12872AY-667
MT8HTF6464AY-40E	MT18HTF12872AY-53E
MT8HTF12864AY-667	MT18HTF12872AY-40E
MT8HTF12864AY-53E	MT18HTF25672AY-667
MT8HTF12864AY-40E	MT18HTF25672AY-53E
MT9HTF3272AY-667	MT18HTF25672AY-40E
MT9HTF3272AY-53E	MT18HTF51272AY-667
MT18HTF51272AY-53E	MT18HTF51272AY-40E

Table 9-16: Supported SODIMMs for DDR2 SDRAM (Virtex-5 FPGAs)

MT4HTF1664HY-667	MT8HTF6464HY-40E
MT4HTF1664HY-53E	MT8HTF3264HDY-667
MT4HTF1664HY-40E	MT8HTF3264HDY-53E
MT4HTF3264HY-667	MT8HTF3264HDY-40E
MT4HTF3264HY-53E	MT8HTF6464HDY-667
MT4HTF3264HY-40E	MT8HTF6464HDY-53E
MT8HTF3264HY-667	MT8HTF6464HDY-40E
MT8HTF3264HY-53E	MT16HTF25664HY-667
MT8HTF3264HY-40E	MT16HTF25664HY-53E
MT8HTF6464HY-667	MT16HTF25664HY-40E
MT8HTF6464HY-53E	MT16HTS51264HY-667
MT16HTS51264HY-53E	--

Hardware Tested Configurations

The frequencies shown in [Table 9-17](#) were achieved on the Virtex-5 FPGA ML561 Memory Interfaces Development Board under nominal conditions. These frequencies should not be used to determine the maximum design frequency. The maximum design frequency supported in the MIG wizard is based on a combination of the TRCE results for fabric timing on multiple device/package combinations and I/O timing analysis using FPGA and memory timing parameters for a 72-bit wide interface.

Table 9-17: Hardware Tested Configurations

Synthesis Tools	XST and Synplicity
HDL	Verilog and VHDL
FPGA Device	XC5VLX50T-FF1136-2
Burst Lengths	4, 8

Table 9-17: Hardware Tested Configurations

Synthesis Tools	XST and Synplicity
CAS Latency (CL)	3, 4, 5
Additive Latency	0, 1, 2, 3, 4
32-bit Design	Tested on 16-bit Component MT47H32M16XX-3
72-bit RDIMM Design	Tested on 72-bit DIMM MT9HTF6472Y-667
72-bit UDIMM Design	Tested on 72-bit DIMM MT9HTF6472AY-667
ECC verified	72-bit RDIMM and UDIMM design
Component, CL=3, 4, 5	100 MHz to 400 MHz
DIMM, CL=3	100 MHz to 280 MHz
DIMM, CL=4, 5	100 MHz to 400 MHz

DDR2 PPC440

Supported Features

- Supports a maximum performance of 333 MHz in the fastest speed grade
- Supports 16-bit, 32-bit, and 64-bit data widths, and 72-bit data width with ECC (DQ:DQS = 8:1)
- Supports DDR2 SDRAM single-rank registered DIMMs, SODIMMs, UDIMMs, and components. RDIMMs support a maximum of 9 loads. SODIMMs and UDIMMs support a maximum of 4 loads.
- Supports the following DDR2 SDRAM features:
 - CAS latencies (3, 4, 5)
 - Additive latencies (0, 1, 2, 3, 4)
 - On-die termination (ODT)
 - Burst lengths (4, 8)
- Supports bank management (up to four banks open)

Unsupported Features

- GUI options
 - Verify UCF and Update Design and UCF
 - Data mask
 - Two bytes per bank
 - System clock type
- Dual Rank DIMMs
- Multi controllers

Introduction

By selecting the PPC440 option the MIG tool will output a UCF that is optimal for the PowerPC440 in the selected Virtex-5 FXT device. This limits the location of the memory interface to the banks adjacent to the PPC440 hard block. This also limits the supported memory interface widths to 16-bit, 32-bit, and 64-bit data widths, and 72-bit data width with ECC. And the only supported DQ:DQS ratio is 8:1.

Compatible FPGAs and UCF

FPGAs LX50T-FF1136, LX85T-FF1136 and SX50T-FF1136 are only compatible with FXT FPGAs for 16-bit and 32-bit interfaces. The Virtex-5 FX30T and FX70T FPGAs are single-processor devices whereas the Virtex-5 FX100T, FX130T, and FX200T FPGAs are dual-processor devices. If the target FXT device is a dual processor device then the top or bottom processor can be selected using the PowerPC440 Block Selection drop box in the 'Pin Compatible FPGAs' page. When selecting compatible devices, if the target device and the compatible device have different processor counts the MIG tool will output a UCF that is optimal for the device with a single processor and the PowerPC440 Block Selection drop box will be grayed out. When selecting compatibility between Virtex-5 SXT/LXT and FXT devices the MIG tool will output a UCF that is optimal for the FXT device.

The DDR2 SDRAM design that is output by MIG cannot be used to interface to the PowerPC440 Memory Controller Interface (MCI). The EDK tool must be used to generate the ppc440mc_ddr2 processor core (pcore) that interfaces to the PowerPC440 MCI. Technical details on the ppc440mc_ddr2 pcore are provided in [DS567](#), *DDR2 Memory Controller for PowerPC 440 Processors Data Sheet*. Additional constraints required in the UCF when using the ppc440mc_ddr2 pcore are: AREA_GROUP, PowerPC440 block location constraint for dual processor devices, and BRAM location constraints for the write and read data FIFOs. Uncomment all these constraints in UCF file of MIG generated output. MIG will not output the AREA group constraints, PPC440 location constraints and block RAM constraints in the UCF for LX and SX series devices when the **FXT Compatible Devices** option is selected.

The following is an example for FX100T-FF1738 device constraints from MIG output:

```
#INST "u_ddr2_top/*" AREA_GROUP="AREA_DDR2"; AREA_GROUP "AREA_DDR2"
RANGE=SLICE_X0Y0:SLICE_X15Y79;
#INST "mem_ctrl_ppc440" LOC = PPC440_X0Y0;
#INST "*/.gen_rdf[0].u_rdf" LOC = RAMB36_X0Y11;
#INST "*/.gen_rdf[0].u_rdf1" LOC = RAMB36_X0Y10;
#INST "*/.gen_wdf[0].u_usr_wr_fifo/.u_wdf" LOC = RAMB36_X0Y9;
#INST "*/.gen_wdf[1].u_usr_wr_fifo/.u_wdf" LOC = RAMB36_X0Y8;
#INST "*/.gen_rdf[0].u_rmw_data0" LOC = RAMB36_X0Y13;
#INST "*/.gen_rdf[0].u_rmw_data1" LOC = RAMB36_X0Y12;
```

Uncomment all above constraints in the UCF.

The system reset signal MI_MCRESET is renamed to sys_rst_n.

PowerPC Supported FPGA Devices

PPC440 designs are supported for the following FPGAs:

- XC5VFX30T-FF665
- XC5VFX70T-FF665
- XC5VFX70T-FF1136

- XC5VFX100T-FF1136
- XC5VFX100T-FF1738
- XC5VFX130T-FF1738
- XC5VFX200T-FF1738

Implementing QDRII SRAM Controllers

This chapter describes how to implement QDRII SRAM interfaces for Virtex®-5 FPGAs generated by MIG. This design is based on XAPP853 [Ref 26].

Feature Summary

This section summarizes the supported and unsupported features of the QDRII controller design.

Supported Features

The QDRII controller design supports the following:

- A maximum frequency of 300 MHz
- 18-bit, 36-bit, and 72-bit data widths
- Burst lengths of four and two
- Implementation using different Virtex-5 devices
- Support for DCI Cascading
- Operation with 18-bit and 36-bit memory components
- Verilog and VHDL
- With and without a testbench
- With and without a PLL

Design Frequency Ranges

Table 10-1: Design Frequency Range in MHz

Memory	FPGA Speed Grade					
	-1		-2		-3	
	Min	Max	Min	Max	Min	Max
Component	120	250	120	300	120	300

Unsupported Features

The QDRII controller design does not support:

- 9-bit data widths
- 9-bit memory components

Architecture

Figure 10-1 shows a top-level block diagram of the QDRII memory controller. One side of the QDRII memory controller connects to the user interface denoted as User Interface. The other side of the controller interfaces to QDRII memory. The memory interface data width is selectable from MIG.

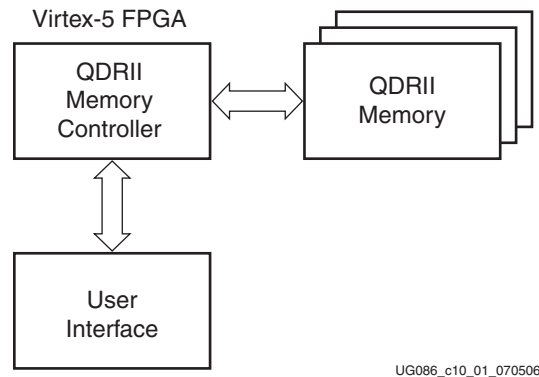


Figure 10-1: QDRII Memory Controller

The QDR operation can support double data rate read and write operations through separate data output and input ports with the same cycle. Memory bandwidth is maximized because data can be transferred into SRAM on every edge of the clock and transferred out of SRAM on every edge of the read clock. Independent read and write ports eliminate the need for high-speed bus turnaround.

Read and write addresses are latched on positive edges of the input clock K. A common address bus is used to access the addresses for both read and write operations. The key advantage to QDRII devices is they have separate data buses for reads and writes to SRAM.

Interface Model

The QDRII memory interface is layered to simplify the design and make the design modular. Figure 10-2 shows the layered memory interface in the QDRII memory controller. The two layers are the application layer and the implementation and physical layer.

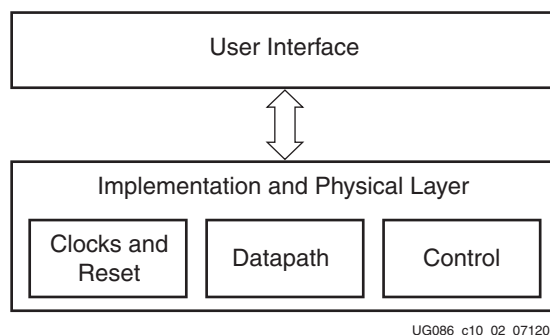


Figure 10-2: Interface Layering Model

The application layer creates the user interface, which initiates memory writes and reads by writing data and memory addresses to the User Interface FIFOs.

The implementation and physical layer comprises:

- Clocks and reset generation logic
- Datapath logic
- Control logic

Clocks and reset generation logic constitute a PLL/DCM primitive, which derives different phase-shifted versions of the user-supplied differential clocks (sys_clk_p and sys_clk_n). These phase-shifted versions of clocks run throughout the controller design. A 200 MHz user-supplied differential clock is used for the idelay control elements. Reset signals are generated for different clock domains using the user-supplied reset signal (sys_rst_n), the locked signal, and idelay control elements ready signal.

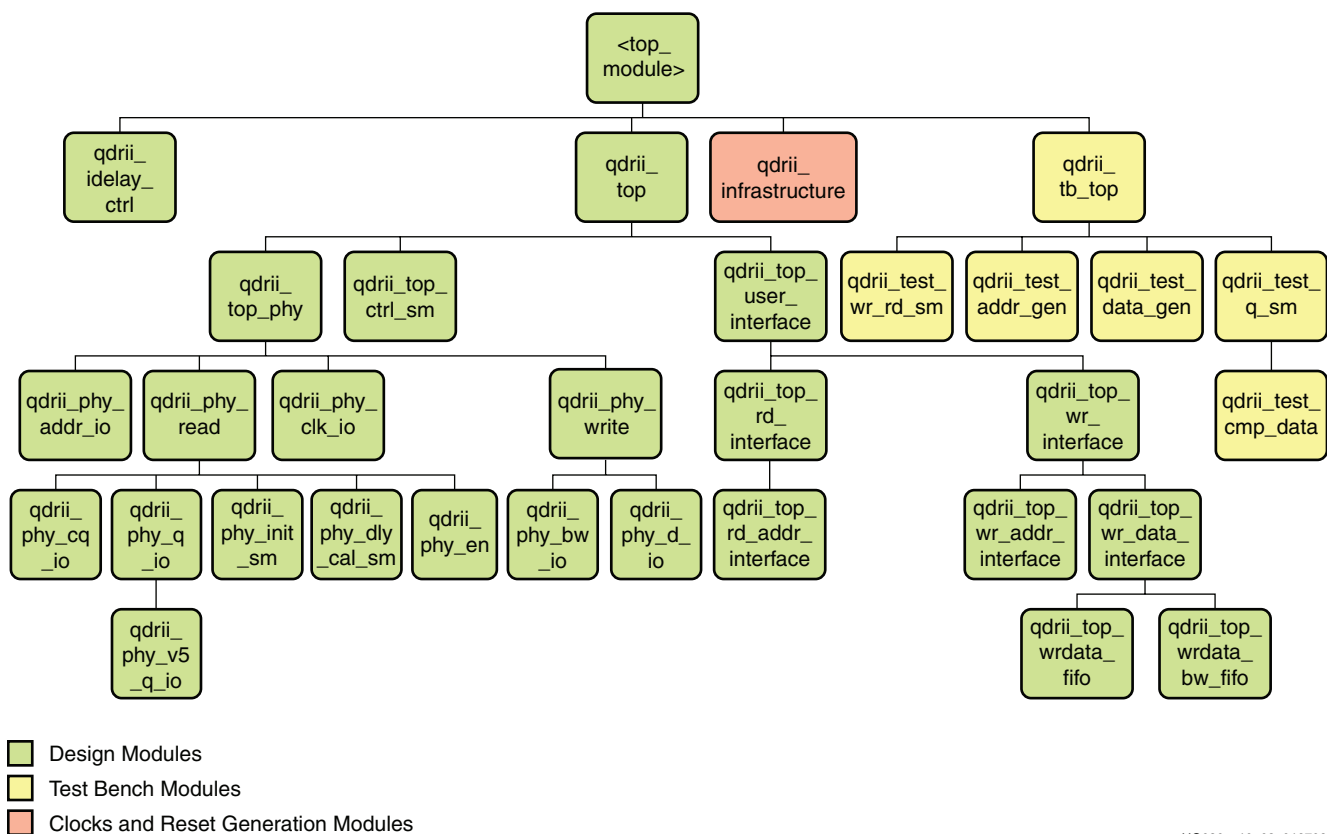
The Datapath logic consists of the memory write clocks, the read clocks, the data write generation logic, and the read data capturing logic.

The Control logic constitutes read/write command generation logic, depending on the status signals of the User Interface FIFO.

The above mentioned logic interfaces with memory through IDDRs, ODDRs, OFLOPs, ISERDES elements, etc., which are associated with the physical layer.

Hierarchy

Figure 10-3 shows the hierarchical structure of the QDRII SRAM design generated by MIG with a testbench and a PLL.



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Figure 10-3: Hierarchical Structure of the Virtex-5 FPGA QDRII SRAM Design

The modules are classified as follows:

- Design modules
- Testbench modules
- Clocks and reset generation modules

MIG can generate four different QDRII SRAM designs:

- With a testbench and a PLL
- Without a testbench and with a PLL
- With a testbench and without a PLL
- Without a testbench and without a PLL

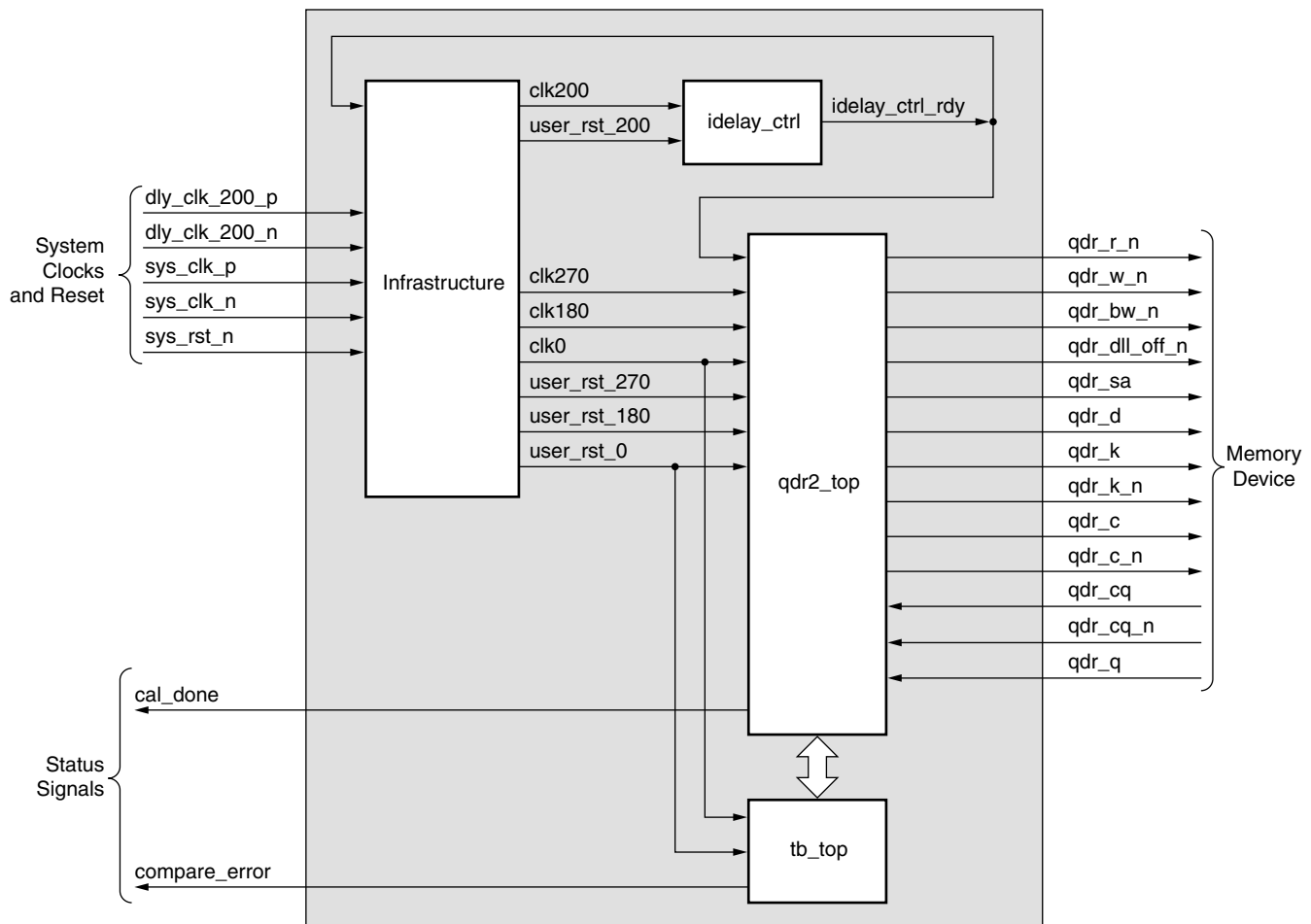
MIG outputs both an `example_design` and a `user_design`. The MIG-generated `example_design` includes the entire memory controller design along with a synthesized testbench (example user application). This testbench generates sample writes and reads and then uses comparison logic to verify that the data patterns written are the same as those received. This `example_design` can be used to test functionality both in simulation and in hardware. The `user_design` only includes the memory controller design. The yellow shaded modules in [Figure 10-3](#) are not present in the design. This design allows users to connect the MIG memory controller design to a user developed testbench (user application). Refer to [Table 10-5, page 414](#) for user interface signals and to [“User Interface Accesses,” page 415](#) for timing restriction on user interface signals.

Design clocks and resets are generated in the infrastructure module. The PLL/DCM clock is instantiated in the infrastructure module for designs with a PLL. The inputs to this module are the differential design clock and a 200 MHz differential clock for the IDELAYCTRL module. A user reset is also input to this module. Using the input clocks and reset signal, system clocks and system reset signals are generated in this module, which are used in the design.

The PLL/DCM primitive is not instantiated in this module if the “No PLL” option is selected. So, the system operates on the user-provided clocks. The system reset signals are generated in the infrastructure module using the locked input signal, the input reset signal, and the idelay control element’s ready signal. For more information on the clocking structure, refer to [“Clocking Scheme,” page 410](#).

The QDRII design is generated in two configurations with and without a testbench (`example_design` and `user_design` respectively). The top-level module with testbench (`example_design`) has the design top, testbench, IDELAY control, and clock and reset modules. Without a testbench (`user_design`), the `mem_test_bench` module is removed from the top-level module. By default, MIG outputs both designs (`example_design` and `user_design`) in two separate RTL folders, and the user can choose the appropriate design.

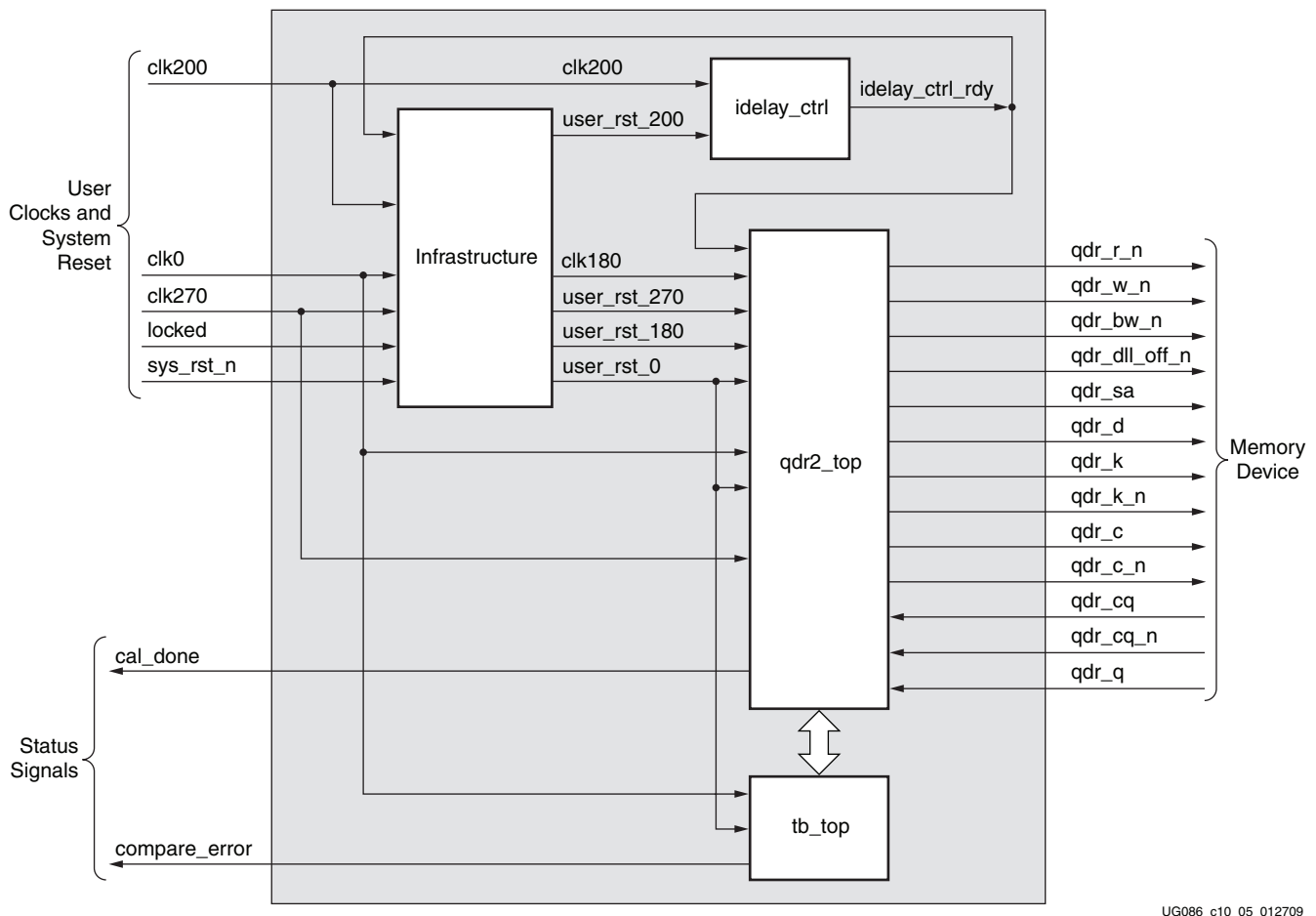
Figure 10-4 shows a top-level block diagram of a QDRII SRAM design with a PLL and a testbench. The sys_clk_p and sys_clk_n pair are differential input system clocks. “[Clocking Scheme](#),” page 410 describes how various clocks are generated using the PLL. The PLL is instantiated in the infrastructure module that generates the required design clocks. dly_clk_200_p and dly_clk_200_n are used for the idelay_ctrl element. Sys_rst_n is an active-Low system reset signal. All design resets are generated using the sys_rst_n signal, the locked signal, and the dly_ready signal of the IDELAYCTRL element. The compare_error output signal indicates whether the design passes or fails. The testbench module called “tb_top” generates the user interface data, address, and command signals. The user data bits and address bits are stored in the corresponding User Interface FIFOs. The compare_error signal is driven High on data mismatches. The cal_done signal indicates the completion of initialization and calibration of the design.



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Figure 10-4: Top-Level Block Diagram of the QDRII SRAM Design with a PLL and a Testbench

Figure 10-5 shows a top-level block diagram of a QDRII SRAM design without a PLL but with a testbench. The user should provide all the clocks and the locked signal. “Clocking Scheme,” page 410 explains how to generate the design clocks from the user interface. These clocks should be single-ended. `sys_rst_n` is the active-Low system reset signal. All design resets are generated using the `sys_rst_n` signal, the locked signal, and the `dly_ready` signal of the `IDELAYCTRL` element. The user application must have a PLL/DCM primitive instantiated in the design, and all user clocks should be driven through BUFs. The `compare_error` output signal indicates whether the case passes or fails. The testbench module called “`tb_top`” generates the user interface data, address, and command signals. The user data bits and address bits are stored in the corresponding User Interface FIFOs. The `compare_error` signal is driven High on data mismatches. The `cal_done` signal indicates the completion of initialization and calibration of the design.

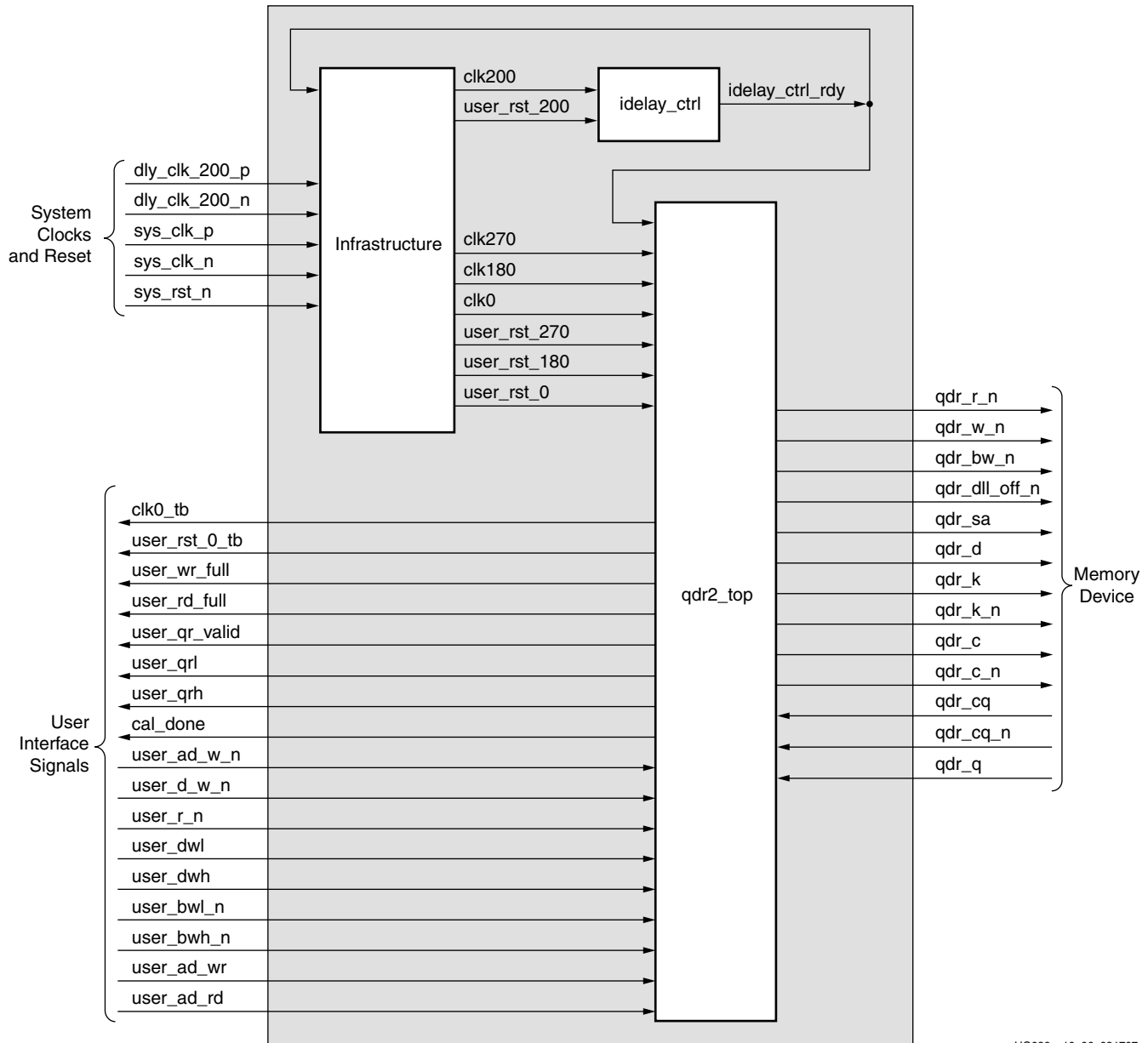


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Figure 10-5: Top-Level Block Diagram of the QDRII SRAM Design without a PLL but with a Testbench

Figure 10-6, page 401 shows a top-level block diagram of a QDRII SRAM design with a PLL but without a testbench. The `sys_clk_p` and `sys_clk_n` pair are differential input system clocks. “Clocking Scheme,” page 410 describes how various clocks are generated using the PLL. The PLL is instantiated in the infrastructure module that generates the required design clocks. `dly_clk_200_p` and `dly_clk_200_n` are used for the `idelay_ctrl` element. `sys_rst_n` is an active-Low system reset signal, and all design resets are generated using the `sys_rst_n` signal, the locked signal, and the `dly_ready` signal of the `IDELAYCTRL` element. The user has to drive the user application signals. The design provides the `clk0_tb` and `user_rst_0_tb` signals to the user in order to synchronize the user application signals

with the design. The signal `clk0_tb` is connected to clock `clk0` in the controller. If the user clock domain is different from `clk0/clk0_tb`, the user should add FIFOs for all the input and outputs of the controller (user application signals) in order to synchronize them to `clk0_tb`. The `cal_done` signal indicates the completion of initialization and calibration of the design.

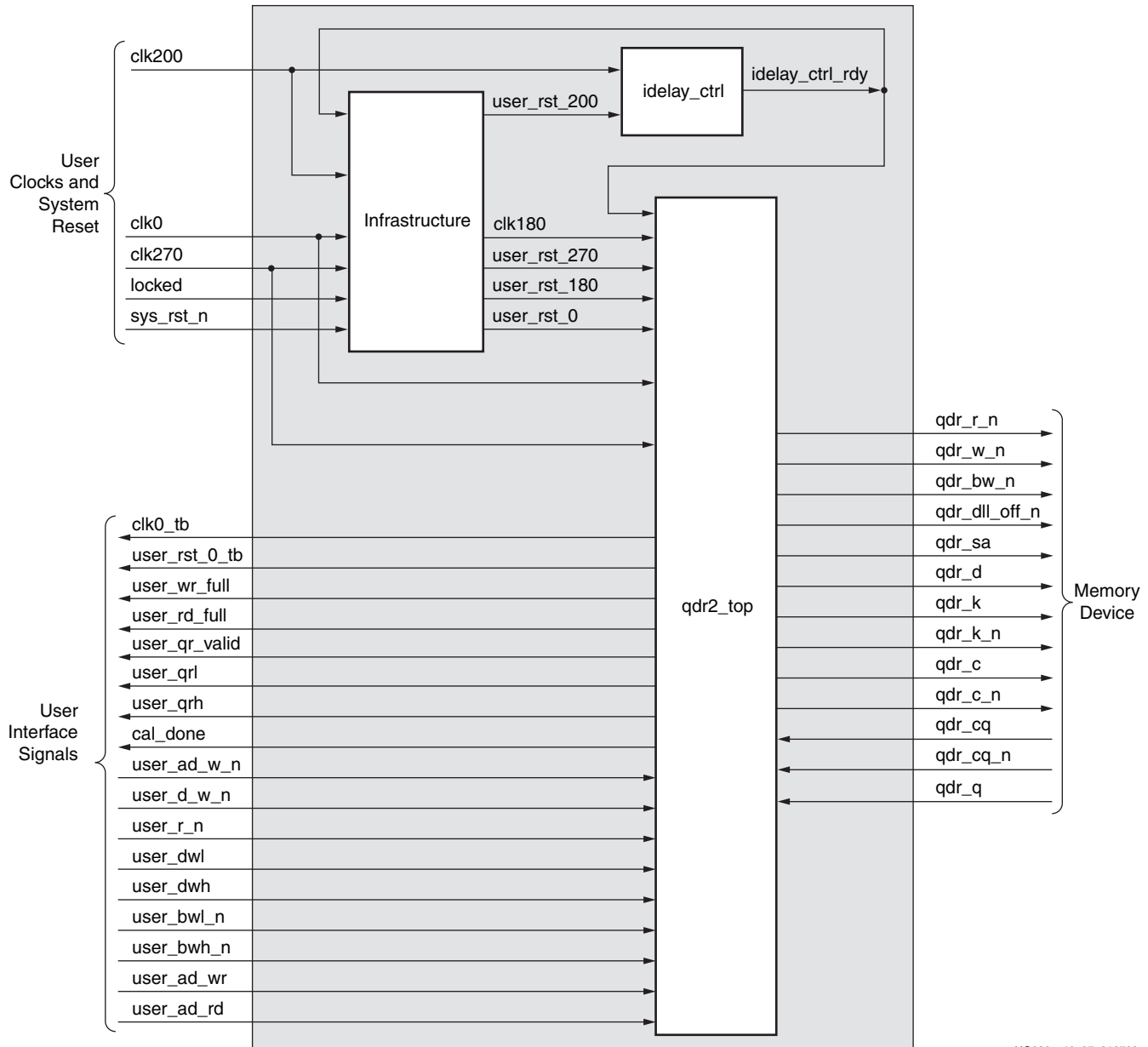


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Figure 10-6: Top-Level Block Diagram of the QDRII SRAM Design with a PLL but without a Testbench

Figure 10-7, page 402 shows a top-level block diagram of a QDRII SRAM design without a PLL or a testbench. The user should provide all the clocks and the locked signal. “[Clocking Scheme](#),” page 410 explains how to generate the design clocks from the user interface. These clocks should be single-ended. `sys_rst_n` is the active-Low system reset signal. All design resets are generated using the `sys_rst_n` signal, the locked signal, and the `dly_ready` signal of the `IDELAYCTRL` element. The user application must have a PLL/DCM primitive instantiated in the design, and all user clocks should be driven through BUFGs.

The user has to drive the user application signals. The design provides the `clk0_tb` and `user_rst_0_tb` signals to the user in order to synchronize the user application signals with the design. The `clk0_tb` signal is connected to the `clk0` clock in the controller. If the user clock domain is different from `clk0/clk0_tb`, the user should add FIFOs for all the inputs and outputs of the controller (user application signals) in order to synchronize them to `clk0_tb`. The `cal_done` signal indicates the completion of initialization and calibration of the design.



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Figure 10-7: Top-Level Block Diagram of the QDRII SRAM Design without a PLL or a Testbench

QDRII Memory Controller Modules

Figure 10-8 shows a detailed block diagram of the QDRII memory controller.

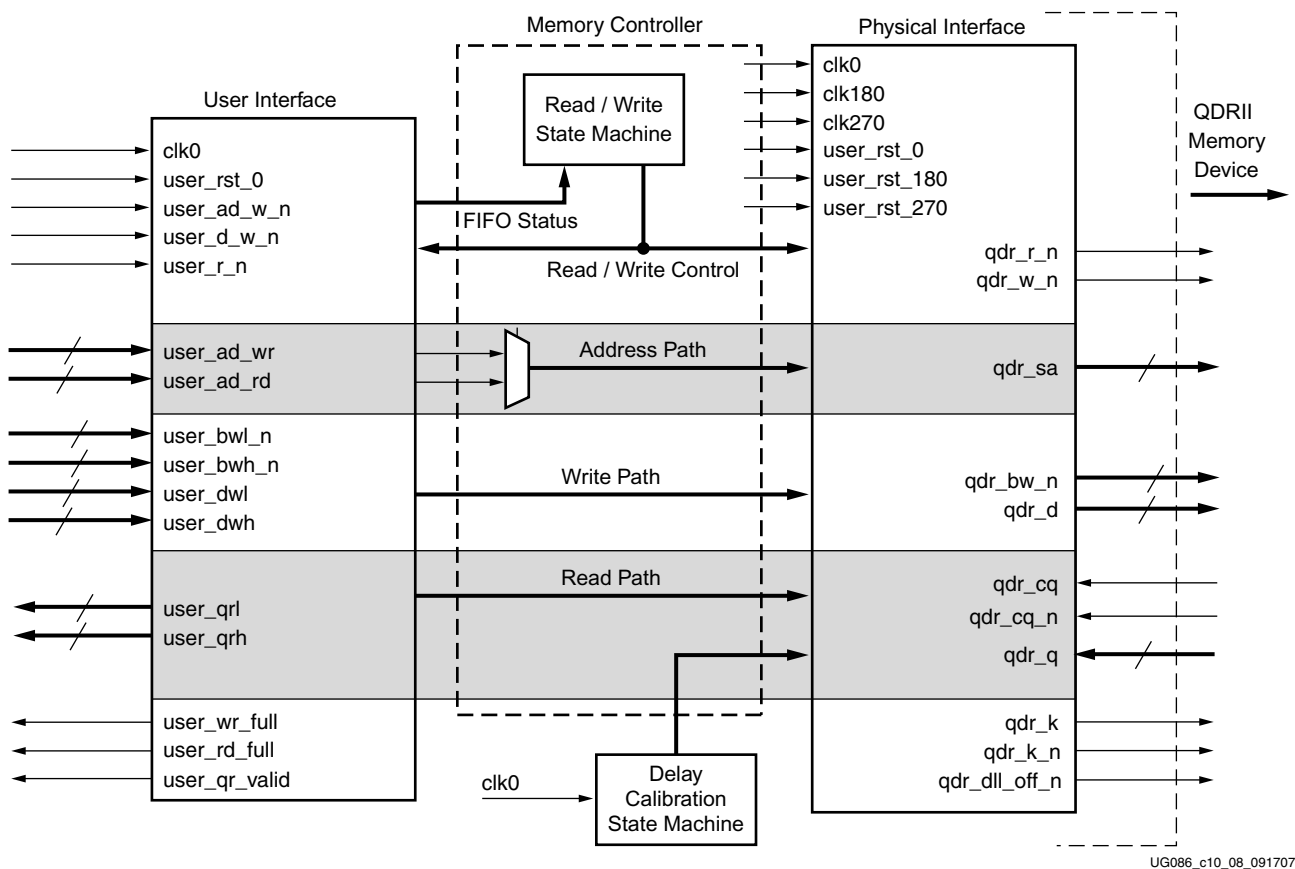


Figure 10-8: QDRII Memory Controller Modules using FIFO Interface

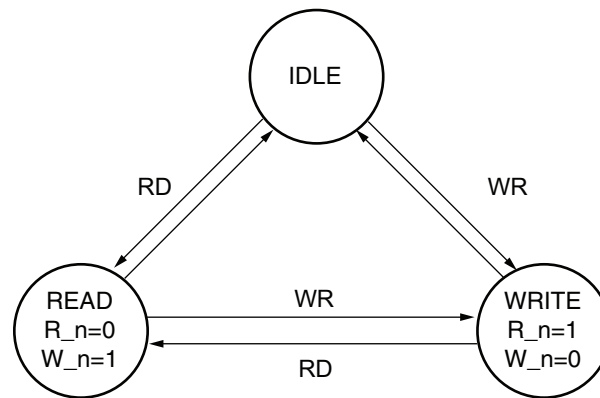
Controller

The QDRII memory controller initiates alternate WRITE and READ commands to the memory as long as the User Write Address FIFO and the User Read Address FIFO are not empty.

The user writes the write data, its corresponding byte write enable, and the Write Address bits into the User Write Data FIFOs, the User Byte Write FIFO, and the User Write Address FIFOs, respectively. When the User Write Address FIFO is not empty, the QDRII controller generates a write-enable signal to the memory. When the write enable is asserted, the write data, the byte write enable, and the write address bits are transferred to memory from the User Write Data FIFOs, the User Byte Write FIFO, and the User Write Address FIFO, respectively.

The read address from where the data is to be read from the memory is stored by the user in the User Read Address FIFO. The QDRII memory controller generates a read-enable signal to the memory when the User Read Address FIFO is not empty. When the read enable is asserted, the read address from the Read Address FIFO is transferred to memory. When the read data from the memory corresponding to the read address is captured correctly, a valid user_qr_valid signal is asserted High. The user can access the read data corresponding to the read address only when the data valid signal user_qr_valid is asserted High.

Figure 10-9 shows a state machine of the QDR II memory controller for burst lengths of four. When calibration is complete (that is, when the cal_done signal is asserted), the state machine is in the IDLE state. When the User Write Address FIFO is not empty (that is, when the user has written the write data, the byte write enable, and the write address bits into their corresponding FIFOs, respectively), the state machine goes to the WRITE state, initiating a memory write of one burst.



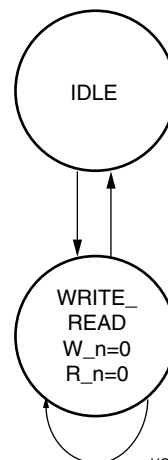
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Figure 10-9: QDR II Memory Controller State Machine with Burst Lengths of 4

When the User Read Address FIFO is not empty (that is, the user has written read address bits into the User Read Address FIFO), the state machine goes to the READ state, initiating a memory read of one burst.

From the IDLE state, the QDR II memory controller can go to either the WRITE or the READ state depending on the status of the User FIFOs. Writes are given priority. In the WRITE state, a memory write is initiated, and the User Read Address Not Empty status is checked in order to transfer into the READ state. When the User Read Address FIFO is empty, the state machine goes to the IDLE state.

In the READ state, a memory read is initiated, and the User Write Address FIFO Not Empty status is checked before going to the WRITE state. If the User Address FIFO is empty, the state machine goes to the IDLE state.



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Figure 10-10: QDR II Memory Controller State Machine with Burst Lengths of 2

Figure 10-10 shows a state machine of the QDR II memory controller for burst lengths of two when the FIFO user interface is used. When calibration is complete, the state machine

is in the IDLE state. When the User Write Address FIFO is not empty (that is, when the user has written the write data, the byte write enable, and the write address bits into their corresponding FIFOs), the state machine goes to the WRITE_READ state, initiating a memory write of one complete burst. When the User Read Address FIFO is not empty (that is, the user has written read address bits into the User Read Address FIFO), the state machine goes to the READ_WRITE state, initiating a memory read of one complete burst.

From the IDLE state, the QDR II memory controller goes to WRITE_READ state if either:

- the User Write Address FIFO is not empty, or
- the User Read Address FIFO is not empty.

In the WRITE_READ state, the User Read Address Not Empty status is checked to initiate a memory read. To initiate a memory write in the WRITE_READ state, the User Write Address FIFO not empty status is checked. If both the User Write Address FIFO and the User Read Address FIFO are empty, the state machine goes to the IDLE state. If either the User Write Address FIFO or the User Read Address FIFO is not empty, the state machine remains in the WRITE_READ state to issue memory writes or reads.

Refer to XAPP853 [Ref 26] for data capture techniques and timing analysis of the QDR II memory controller module.

Burst Length of Two Design without FIFO Interface

In designs with a burst length of two, user commands can be transferred directly to the physical layer. This design does not rely on the controller state machine to provide the write and read commands and instead forwards the commands directly to the physical layer.

The user can select this option by setting the BURST2_FIFO_INTERFACE parameter in the design_top file to FALSE. This option can be used when a write address and a read address need to be issued to the memory on the same cycle, the empty flag status of the Read Address FIFO and Write Address FIFO can be different, and the command order needs to be preserved.

Infrastructure

The infrastructure module generates the design clocks and reset signals. When differential clocking is used, sys_clk_p, sys_clk_n, clk_200_p, and clk_200_n signals appear. When single-ended clocking is used, sys_clk and idly_clk_200 signals appear. In addition, clocks are available for design use and a 200 MHz clock is provided for the IDELAYCTRL primitive. Differential and single-ended clocks are passed through global clock buffers before connecting to a PLL/DCM. For differential clocking, the output of the sys_clk_p/sys_clk_n buffer is single-ended and is provided to the PLL/DCM input. Likewise, for single-ended clocking, sys_clk is passed through a buffer and its output is provided to the PLL/DCM input. The outputs of the PLL/DCM are 180° and 270° phase-shifted versions of the input clock. After the PLL/DCM is locked, the design is in the reset state for at least 25 clocks. The infrastructure module also generates all of the reset signals required for the design.

PLL/DCM

In MIG 3.0 and later, the DCM is replaced with a PLL for all Virtex-5 FPGA designs. If the user selects a design with a PLL in the GUI, the infrastructure module will have both PLL and DCM codes. The CLK_GENERATOR parameter enables either a PLL or a DCM in the infrastructure module. The CLK_GENERATOR parameter is set to PLL by default. If the user wants to use DCM, this parameter should be changed manually to DCM.

ldelay_ctrl

This module instantiates the IDELAYCTRL primitive of the Virtex-5 FPGA. The IDELAYCTRL primitive is used to continuously calibrate the individual delay elements in its region to reduce the effect of process, temperature, and voltage variations. A 200 MHz clock has to be fed to this primitive.

MIG uses the “automatic” method for IDELAYCTRL instantiation in which the MIG HDL only instantiates a single IDELAYCTRL for the entire design. No location (LOC) constraints are included in the MIG-generated UCF. This method relies on the ISE® tools to replicate and place as many IDELAYCTRLs as needed (for example, one per clock region that uses IDELAYs). Replication and placement are handled automatically by the software tools if IDELAYCTRLs have same refclk, reset, and rdy nets. A new constraint called IODELAY_GROUP associates a set of IDELAYs with an IDELAYCTRL and allows for multiple IDELAYCTRLs to be instantiated without LOC constraints specified. ISE software generates the IDELAY_CTRL_RDY signal by logically ANDing the RDY signals of every IDELAYCTRL block.

The IODELAY_GROUP name should be checked in the following cases:

- The MIG design is used with other IP cores or user designs that also require the use of IDELAYCTRL and IDELAYs.
- Previous ISE software releases 8.2.03i and 9.1i had an issue with IDELAYCTRL block replication and trimming. When using these revisions of the ISE software, the user must instantiate and constrain the location of each IDELAYCTRL individually.

See UG190 [Ref 10] for more information on the requirements of IDELAYCTRL placement.

top_phy

This module is the interface between the controller and the memory. It consists of the following:

- Control logic that generates READ/WRITE commands and address signals to the memory.
- Write Data logic that associates the write data, the byte enable, and the write address with the WRITE commands and the read address with the READ commands. It also generates the write data pattern for calibration purposes.
- Read Data logic that comprises the read data capturing scheme and calibration logic.

IODELAY Performance Mode

In Virtex-5 family devices, the power dissipation of the IODELAY elements can be controlled using the HIGH_PERFORMANCE_MODE parameter. The values of this parameter can be either TRUE or FALSE.

When this parameter value is set to TRUE, the IODELAY jitter value per tap is reduced. This reduction results in a slight increase in power dissipation from the IODELAY element. When this parameter value is set to FALSE, the IODELAY power dissipation is reduced, but with an increase in the jitter value per tap.

The value of this parameter can be selected from the MIG FPGA options page. Users can also manually set this parameter value to TRUE or FALSE in the design top-level block HDL module.

Refer to [Appendix E, “Debug Port”](#) for more information on the IODELAY Performance Mode.

Multicontrollers

MIG supports multicontrollers for QDRII SRAMs and multiple interfaces for QDRII SRAMs and DDR2 SDRAMs. Up to eight controllers are supported. In multicontroller and multiple interface designs, every controller can have a different frequency. The number of controllers that can have different frequencies is limited by the number of PLLs available in the selected FPGA. For example, a total of six PLL resources are available for the XC5VLX50 device, so a maximum of six controllers can have different frequencies. Even though the number of controllers selected in the GUI is eight, a maximum of six controllers can have different frequencies. Thus, for the remaining two controllers, the user should select one of the already selected frequencies. Refer to the *Virtex-5 FPGA User Guide* [Ref 10] for PLL resources available for various devices.

For a single controller design, all memory signals and user interface signals appear as shown in [Figure 10-8, page 403](#) and [Table 10-5, page 414](#) based on the selected part. For a multicontroller design, all memory signal names and user interface signal names are prepended with the controller number. For example, for a two controller design (two QDR2 controllers), the qdr_d port appears as c0_qdr_d and c1_qdr_d. A similar naming convention is followed for the design parameters. Some parameters such as HIGH_PERFORMANCE_MODE, CLK_TYPE, and RST_ACT_LOW are common for all the controllers and do not have the controller number prepended.

DCI Cascading

In Virtex-5 family devices, I/O banks that need DCI reference voltage can be cascaded with other DCI I/O banks. One set of VRN/VRP pins can be used to provide reference voltage to several I/O banks. With DCI cascading, one bank (the master bank) must have its VRN/VRP pins connected to external reference resistors. Other banks in the same column (slave banks) can use DCI standards with the same impedance as the master bank, without connecting the VRN/VRP pins on these banks to external resistors. DCI impedance control in cascaded banks is received from the master bank. This results in more usable pins and in reduced power usage because fewer VR pins and DCI controllers are used.

The syntax for representing the DCI Cascading in the UCF is:

```
CONFIG DCI_CASCADE = "<master> <slave1> <slave2> ...";
```

There are certain rules that need to be followed in order to use DCI Cascade option:

1. The master and slave banks must all reside on the same column (left, center, or right) on the device.
2. Master and slave banks must have the same V_{CCO} and V_{REF} (if applicable) voltages.

This feature enables placing all 36 bits of read data, as well as the CQ and CQ# clocks, in the same bank when interfacing with 36-bit QDRII components.

MIG supports DCI Cascading. Following are the possibilities for generating the designs with DCI support using the DCI Cascade option.

- For x36 component designs, the DCI Cascade option is always enabled. This feature cannot be disabled if DCI support is needed.
- For x18 component designs, DCI Cascade is optional. DCI support for these designs can be selected with or without the DCI Cascade selection.
- For x18 component with 18-bit data width designs, the DCI Cascade option is disabled and cannot be utilized.

When DCI Cascade option is selected, MIG displays the master bank selection box for each column of the FPGA in the bank selection page.

- If an FPGA has no banks or has only non-DCI banks in a particular column, the master bank selection box for that column is not displayed.
- All the data read banks are treated as slave banks.
- When a data read bank is selected in a particular column, the master bank selection box for that particular column is activated and the rest of the master bank selection boxes for other columns are deactivated.
- In a particular column, when a data read bank is selected and there are no DCI banks left in that column for master banks selection, then the design cannot be generated. The data read banks must be moved to the other columns in order to select the master banks.
- The master bank selection box shows all the bank numbers in that particular column other than the data read banks and non-DCI banks in that column.
- There can be only one master bank selected for each column of banks.
- MIG utilizes VRN/VRP pins in the slave banks for pin allocation.
- For each master, VRN/VRP pins are reserved. When a selected master bank does not have any data read pins then a dummy input pin called masterbank_sel_pin is allocated and assigned the HSTL_I_DCI_18 I/O standard.
- The dummy input pin is required to satisfy the requirement of the master bank. Any master bank should have at least one input pin to program the DCI option, and the I/O standard of the master and slave banks should be the same.
- When all the banks in a particular column are allocated with data read pins, MIG chooses only the required banks for data read pins allocation depending upon the design data width. When there is only one bank allocation for data read pins in a column of banks of an FPGA, then that particular data read bank should not be selected as a master bank. Doing so would result in an inappropriate DCI Cascade syntax in the UCF of the generated design.

The center column banks of all the FPGAs are divided into two sections, top-column banks and bottom-column banks. Top-column banks are the banks available above the 0th bank, and the bottom column banks are the banks available below 0th bank. Therefore, there are two master bank selection boxes for the center column.

The VRN/VRP pins for a master bank do not need to be reserved in the reserve pins page.

Once the design is ready with the valid master and slave bank selection, the same master and slave bank information (along with the DCI Cascading syntax) is provided in the UCF when the design is generated.

For more information about DCI Cascade, refer to DCI Cascading in the *Virtex-5 FPGA User Guide* [Ref 10] and the *Xilinx® Constraints Guide*.

CQ/CQ_n Implementation

Controller uses CQ and CQ_n for capturing read data of a 36-bit component. CQ and CQ_n are placed on the P pins of the clock-capable I/Os. For a 36-bit component, CQ is used to capture the first 18 bits of the read data, and CQ_n is used to capture the second 18 bits of the read data. For an 18-bit component, only CQ is used for capturing the read data. CQ_n is not used, and it is connected to a dummy logic. This dummy logic is used just to retain CQ_n pin during PAR. Users can use the CQ_n pin if needed.

Pinout Considerations

It is recommended to select banks within the same column in MIG. This helps to avoid the clock tree skew that the design would incur while crossing from one column to another.

When the Data Read, Data Write, Address, and System Control pins are allocated to individual banks in a column, then the System Control pins must be allocated in a bank that is central to the rest of banks allocated. This helps reduce datapath and clock path skew.

For larger FPGAs (for example, FF1738, FF1760, and similar), it is recommended to place Data Read, Data Write, Address, and System Control pins in the same column to reduce datapath and clock path skew.

Test Bench

MIG generates two RTL folders, `example_design` and `user_design`. The `example_design` includes the synthesizable test bench, while `user_design` does not include the test bench modules. The MIG test bench performs one write command followed by one read command in an alternating manner for designs with a burst length of 4. For a burst length of 2, the test bench performs one write command and one read command in the same clock and repeats one write and one read command continuously. The number of words in a write command depends on the burst length. For a burst length of 4, the test bench writes a total 4 data words for a single write command (2 rise data words and 2 fall data words). For a burst length of 2, the test bench writes a total of 2 data words. The data pattern is an incremental pattern. On every write command, the data pattern is incremented by one, and this is repeated with each subsequent write command. The initial data pattern for the first write command is 000. The test bench writes the 000, 001, 002, 003 data pattern in a sequence in which 000 and 002 are rise data words, and 001 and 003 are fall data words for a 9-bit design. The falling edge data is always rising edge data plus one. For a burst length of 2, the data sequence for the first write command is 000, 001. The data sequence for the second write command is 002, 003. The pattern is then incremented for the next write command. For data widths greater than 9, the same data pattern is concatenated for the other bits. For a 36-bit design and a burst length of 4, the data pattern for the first write command is 000000000, 008040201, 010080402, 0180C0603.

Address generation logic generates the address in an incremental pattern for each write command. The same address location is repeated for the next read command. In Samsung components, the burst address increments are done by the memory, so the address is generated by the test bench in a linear incremental pattern. In Cypress parts, the MIG test bench increments the address for burst operation. After the address reaches the maximum value, it rolls back to the initial address, i.e., 00000.

During reads, comparison logic compares the read pattern with the pattern written, i.e., the 000, 001, 002, 003 pattern. For example, for a 9-bit design of burst length 4, the data written for a single write command is 000, 001, 002, and 003. During reads, the read pattern is compared with the 000, 001, 002, 003 pattern. Based on a comparison of the data, a status signal `error` is generated. If the data read back is the same as the data written, the error signal is 0, otherwise it is 1.

QDRII SRAM Initialization and Calibration

QDRII memory is initialized through a specified sequence. Following initialization, the relationship between the data and the FPGA clock is calculated using the TAP logic. The calibration logic is explained briefly as follows.

Calibration is done in three stages:

1. The read strobe CQ is edge-aligned with the read data Q from the memory. The read strobe is a free-running clock from the memory. In the first stage of calibration, the read strobe CQ is passed through the BUFIO, which delays the strobe by the amount of delay in the BUFIO. Now the read strobe CQ is out of synchronization with the read data Q.

A pattern of four bursts of data (with a value of '1' for rise data and '0' for fall data) is written into a particular location in memory. Continuous read commands are issued to the same location of the memory and the read data Q is delayed in the ISERDES, until it is center-aligned with respect to the delayed read strobe CQ.

The q_init_delay_done signal in the phy_read module indicates the status of the first stage calibration. When q_init_delay_done is asserted High, it indicates the completion of first-stage calibration. Now the CQ clocks are centered with respect to the Read Data Q at the input of the ISERDES.

2. In the second stage of calibration, the read data window is center-aligned with respect to the FPGA clock. Here another pattern of four bursts of data is written into a particular memory location. It is read back continuously from the same memory location, and the read data and the delay clock, CQ, are delayed until the registered read data is center-aligned with the FPGA clock.

When the registered read data is center-aligned with the FPGA clock, the alignment of the read data Q with respect to the FPGA clock is complete. The dly_cal_done signal in the phy_read module indicates the status of second-stage calibration.

3. In the third stage of calibration, the controller issues non-consecutive read commands to the memory. The internal read command signal generated by the controller is then delayed through a shift register until the delayed read command signal is aligned with the ISERDES read data output. Then another level of calibration is done to ensure alignment between the ISERDES data outputs from all the banks used in the interface.

This finishes the calibration of the read data Q, and the cal_done signal is asserted High.

XAPP853 [Ref 26] provides more information about the calibration architecture.

The user must strictly follow the pattern data and not modify it. The timing diagrams in “QDRII Controller Interface Signals” explain the user interface commands until the calibration is finished.

Clocking Scheme

Figure 10-12, page 412 shows the clocking scheme for this design. Global and local clock resources are used.

The global clock resources consist of a PLL or a DCM, two BUFGs on PLL/DCM output clocks, and one BUFG for clk200. The local clock resources consist of regional I/O clock networks (BUFIO). The global clock architecture is discussed in this section.

The MIG tool allows the user to customize the design such that the PLL/DCM is not included. In this case, system clocks clk0 and clk270, and IDELAYCTRL clock clk200 must be supplied by the user.

Global Clock Architecture

The user must supply two input clocks to the design:

- A system clock running at the target frequency for the memory
- A 200 MHz clock for the IDELAYCTRL blocks.

These clocks can be either single-ended or differential. The user can select a single-ended or differential clock input option from the MIG GUI. Differential clocks are connected to the IBUFGDS and the single-ended clock is connected to an IBUFG.

The system clock from the output of the IBUFGDS or the IBUFG is connected to the PLL/DCM to generate the various clocks used by the memory interface logic.

The clk200 output of the IBUFGDS or the IBUFG is connected to the BUFG. The output of the BUFG is used for IDELAY IOB delay blocks for aligning read capture data.

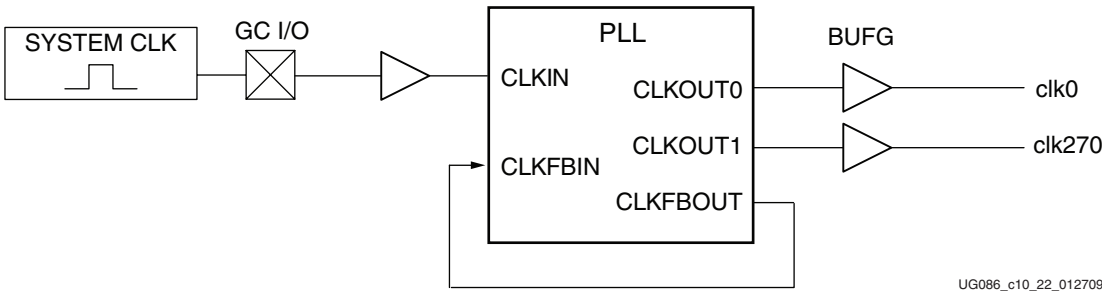
The PLL/DCM generates two separate synchronous clocks for use in the design. This is shown in Table 10-2, Figure 10-11, and Figure 10-12. The clock structure is same for both example design and user design. For designs without PLL/DCM instantiation, the PLL/DCM and the BUFGs should be instantiated at user end to generate the required clocks.

Table 10-2: QDRII Interface Design Clocks

Clock	Description	Logic Domain
clk0	Skew compensated replica of the input system clock.	The clock for the controller and the user interface logic. The QDRII bus-related I/O flip-flops (e.g., memory clocks). This clock is used to register the data, address, and command signals, and the address and data enables for the user interface logic ⁽¹⁾ . This clock is also used to generate the FIFO status signals.
clk270	270° phase-shifted version of clk0	Used in the write data path section of physical layer. Clocks write path control logic, the QDRII side of the Write Data FIFO, and output flip-flops for D and memory control and address signals. This clock is also used to generate the read data and read data valid signals for the user interface logic ⁽¹⁾ .

Notes:

1. See “User Interface Accesses,” page 415 for timing requirements and restrictions on the user interface signals.



UG086_c10_22_012709

Figure 10-11: Clocking Scheme for QDRII Interface Logic Using PLL

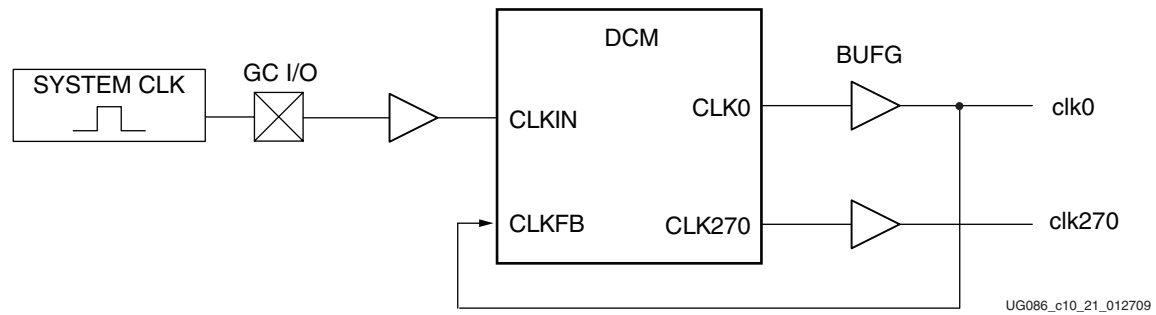


Figure 10-12: Clocking Scheme for QDRII Interface Logic Using DCM

QDRII Controller Interface Signals

Table 10-3 through Table 10-4 describe the QDRII controller system interface signals with and without a PLL, respectively. Table 10-5 describes the QDRII user interface signals. Table 10-6 describes the QDRII memory interface signals. In these tables, all signal directions are with respect to the QDRII memory controller.

Table 10-3: QDRII SRAM System Interface Signals (with a PLL)

Signal Name	Direction	Description
sys_clk_p, sys_clk_n	Input	System clock input made up of differential clock pairs. This clock pair goes to a differential input buffer. The differential buffer output goes to the PLL/DCM input. The PLL/DCM generates the required clocks for the design. This input system clock pair is present only when the DIFFERENTIAL clocks option is selected in the MIG FPGA options page.
sys_clk	Input	Single-ended system clock input. This clock goes to a IBUFG. The IBUFG output goes to the PLL/DCM input. The PLL/DCM generates the required clocks for the design. This input system clock is present only when the SINGLE_ENDED clocks option is selected in MIG FPGA options. When the PLL option is deselected, both differential or single-ended input system clocks are not present.
dly_clk_200_p, dly_clk_200_n	Input	200 MHz differential clock used in the idelay_ctrl logic. This input clock pair is present only when the DIFFERENTIAL clocks option is selected in the MIG FPGA options.
idly_clk_200	Input	Single-ended 200 MHz IDELAYCTRL clock input. This clock is connected to an IBUFG. The IBUFG output is connected to input of BUFG. The output of this BUFG acts as IDELAYCTRL clock input. This input system clock is present only when the SINGLE_ENDED clocks option is selected in the MIG FPGA options. When the PLL option is deselected, both differential or single-ended input system clocks are not present.
sys_rst_n	Input	Reset to the QDRII memory controller.
compare_error	Output	This signal represents the status of comparison of read data when compared to the corresponding write data.
cal_done	Output	This signal is asserted when the design initialization and calibration is complete.

Table 10-4: QDRII SRAM System Interface Signals (without a PLL)

Signal Name	Direction	Description
clk0	Input	Input clock
clk270	Input	Input clock with a 270° phase difference
clk200	Input	200 MHz clock for Idelayctrl primitives
locked	Input	This active-High signal indicates whether the user PLL/DCM is locked or not.

Table 10-4: QDRII SRAM System Interface Signals (without a PLL) (Cont'd)

Signal Name	Direction	Description
sys_rst_n	Input	Reset to the QDRII memory controller
compare_error	Output	This signal represents the status of the comparison between the read data with the corresponding write data.
cal_done	Output	This signal is asserted when the design initialization and calibration is complete.

Table 10-5: QDRII SRAM User Interface Signals (without a Testbench [user_design])

Signal Name	Direction	Description
user_wr_full	Output	This signal indicates the User Write FIFO status. It is asserted when either the User Write Address FIFO or the User Write Data FIFO is full. When this signal is asserted, any writes to the User Write Address FIFO and the User Write Data FIFO are invalid, possibly leading to controller malfunction.
user_rd_full	Output	This signal indicates the User Read Address FIFO status. It is asserted when the User Read Address FIFO is full. When this signal is asserted, any writes to the User Read Address FIFO are ignored.
user_qr_valid	Output	This status signal indicates that data read from the memory is available to the user.
clk0_tb	Output	All user interface signals are to be synchronized to this clock.
user_rst_0_tb	Output	This reset is active until the PLL/DCM is not locked.
user_dwl [(DATA_WIDTH-1):0]	Input	Positive-edge data for memory writes. This data bus is valid when user_d_w_n is asserted.
user_dwh [(DATA_WIDTH-1):0]	Input	Negative-edge data for memory writes. This data bus is valid when user_d_w_n is asserted.
user_qrl [(DATA_WIDTH-1):0]	Output	Positive-edge data read from memory. This data is output when user_qen_n is asserted.
user_qrh [(DATA_WIDTH-1):0]	Output	Negative-edge data read from memory. This data is output when user_qen_n is asserted.
user_bwl_n [(BW_WIDTH-1):0]	Input	Byte enables for QDRII memory positive-edge write data. The byte enables are valid when user_d_w_n is asserted.
user_bwh_n [(BW_WIDTH-1):0]	Input	Byte enables for QDRII memory negative-edge write data. The byte enables are valid when user_d_w_n is asserted.
user_ad_wr [(ADDR_WIDTH-1):0] ⁽¹⁾	Input	QDRII memory address for write data. This address is valid when user_ad_w_n is asserted.
user_ad_rd [(ADDR_WIDTH-1):0] ⁽¹⁾	Input	QDRII memory address for read data. This address is valid when user_r_n is asserted.
user_ad_w_n	Input	This active-Low signal is the write enable for the User Write Address FIFO.

Table 10-5: QDRII SRAM User Interface Signals (without a Testbench [user_design]) (Cont'd)

Signal Name	Direction	Description
user_d_w_n	Input	This active-Low signal is the write enable for the User Write Data FIFO and Byte Write FIFOs.
user_r_n	Input	This active-Low signal is the write enable for the User Read Address FIFO.

Notes:

1. The number of address bits used depends on the density of the memory part. The controller ignores the unused bits, which can all be tied to High.

Table 10-6: QDRII SRAM Interface Signals

Signal Name	Direction	Description
qdr_d	Output	During WRITE commands, the data is sampled on both edges of K.
qdr_q	Input	During READ commands, the data is sampled on both edges of FPGA clk.
qdr_bw_n	Output	Byte enables for QDRII memory write data. These enable signals are sampled on both edges of the K clock.
qdr_sa	Output	Address for READ and WRITE operations
qdr_w_n	Output	This signal represents the WRITE command.
qdr_r_n	Output	This signal represents the READ command.
qdr_cq, qdr_cq_n	Input	These signals are the read clocks transmitted by the QDRII SRAM. Both CQ and CQ_n are used for data capture in this design.
qdr_k, qdr_k_n	Output	Differential write data clocks
qdr_c, qdr_c_n	Output	Input clock to memory for the output data
qdr_dll_off_n	Output	Memory DLL disable when Low

User Interface Accesses

The user backend logic communicates with the memory controller through a FIFO-based user interface for designs with a burst length of four. This FIFO interface is optional for designs with a burst length of two.

The following section describes the user backend timing and the FIFO interface. Designs with a burst length of two that do not use the FIFO use the same timing as that of the FIFO interface. This FIFO interface consists of four related buses:

- A Write Address FIFO bus accepts memory write address from the user
- A Write Data FIFO bus accepts the write data corresponding to the memory write address
- A Read Address FIFO bus accepts the memory read address from the user

The user interface has the following timing and signaling restrictions:

- The Write/Read Address and Write Data FIFOs cannot be written by the user until calibration is complete (as indicated by cal_done). In addition, the user_ad_w_n,

user_d_w_n, and user_r_n interface signals need to be held High until calibration is complete.

- For issuing a write command, the memory write address must be written into the Read Address FIFO. The first write data word must be written to the Write Data FIFO on the same clock cycle as the when the write address is written. In addition, the write data burst must be written over consecutive clock cycles; there cannot be a break between bursts of data. These restrictions arise from the fact that the controller assumes write data is available when it receives the write command from the user.
- The clk0_tb signal is connected to clk0 in the controller. If the user clock domain is different from clk0 / clk0_tb of MIG, the user should add FIFOs for all data inputs and outputs of the controller in order to synchronize them to the clk0_tb. The timing for the non-FIFO user interface for controllers with a burst length of two is the same as that of the FIFO interface. With respect to the user backend, the timing remains the same for both the FIFO and non-FIFO user interface.

User Interface

The user interface has two interfaces: a Read user interface and a Write user interface.

The Read user interface consists of the Read Address interface modules. The Read Address interface consists of the Read Address FIFO. The user has to write the read address bits of the memory into this FIFO.

The Write User interface consists of the Write Data interface and the Write Address interface. The Write Address interface consists of the Write Address FIFO. The user has to write the write address bits of the memory into this FIFO.

The Write Data interface consists of the Write Data FIFO and the Byte Write FIFO. The width of the Write Data FIFO depends upon the data width of the controller design. There are two Write Data FIFOs for every controller: the LSB Write Data FIFO and the MSB Write Data FIFO. The outputs of these FIFOs are SDR and are later converted to DDR at the ODDR primitive before transferring to memory.

The Byte Write enable signals are stored in the Byte Write FIFO by the user.

The controller monitors the status signals of these User FIFOs and issues the READ/WRITE commands to the memory.

The user must wait until the cal_done signal is asserted by the controller, which indicates completion of calibration prior to writing the user data to the Write Data FIFOs, Byte Write FIFO, and Write Address FIFO. Even if the user wants to write any data in to these FIFOs before the completion of calibration, the data does not get written to these FIFOs. These Write Data FIFOs and Byte Write FIFOs write enable signals are considered valid only after the calibration is complete.

Refer to the timing diagrams in “[QDRII Controller Interface Signals](#)” for how the user can access these FIFOs.

The FIFO36 and FIFO36_72 primitives are used for loading address and data from the user interface. The FIFO36 primitive is used in the qdrii_top_wr_addr_interface, qdrii_top_rd_addr_interface, and qdrii_top_wrdata_bw_fifo modules. The FIFO36_72 primitive is used in the qdrii_top_wrdata_fifo module. Every FIFO has two FIFO threshold attributes, ALMOST_EMPTY_OFFSET and ALMOST_FULL_OFFSET, that are both set to 128 in the RTL, by default. These values can be changed as needed. For valid FIFO threshold offset values, refer to UG190 [\[Ref 10\]](#).

Table 10-7 lists the signals between the user interface and the controller.

Table 10-7: Signals between User Interface and Controller

Port Name	Port Width	Port Description
wr_empty	1	Empty status signal from Write Address FIFO. Monitors the FIFO empty status flags to issue write commands. If the Write Address FIFO is empty, the controller stops issuing write commands.
rd_empty	1	Empty status signal from Read Address FIFO. Monitors the FIFO empty status flag to issue read commands. If the Read Address FIFO is empty, the controller stops issuing read commands.
wr_init_n	1	Active-Low write command from the controller state machine. This write command is used for generation of the memory write command and also is used as a read enable signal to the Write Address FIFO and Write Data FIFO.
rd_init_n	1	Active-Low read command from the controller state machine. This read command is used for generation of the memory read command and also is used as a read enable signal to the read address FIFO.

Write Interface

Figure 10-13 illustrates the user interface block diagram for write operations.

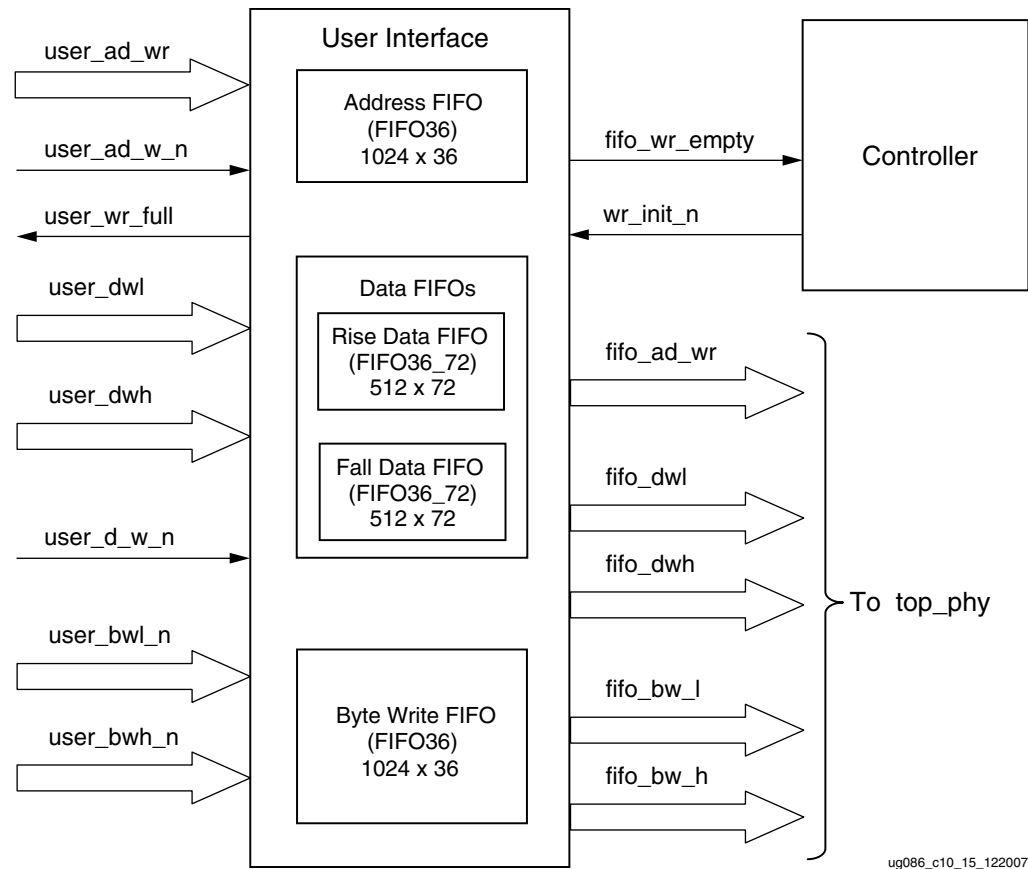


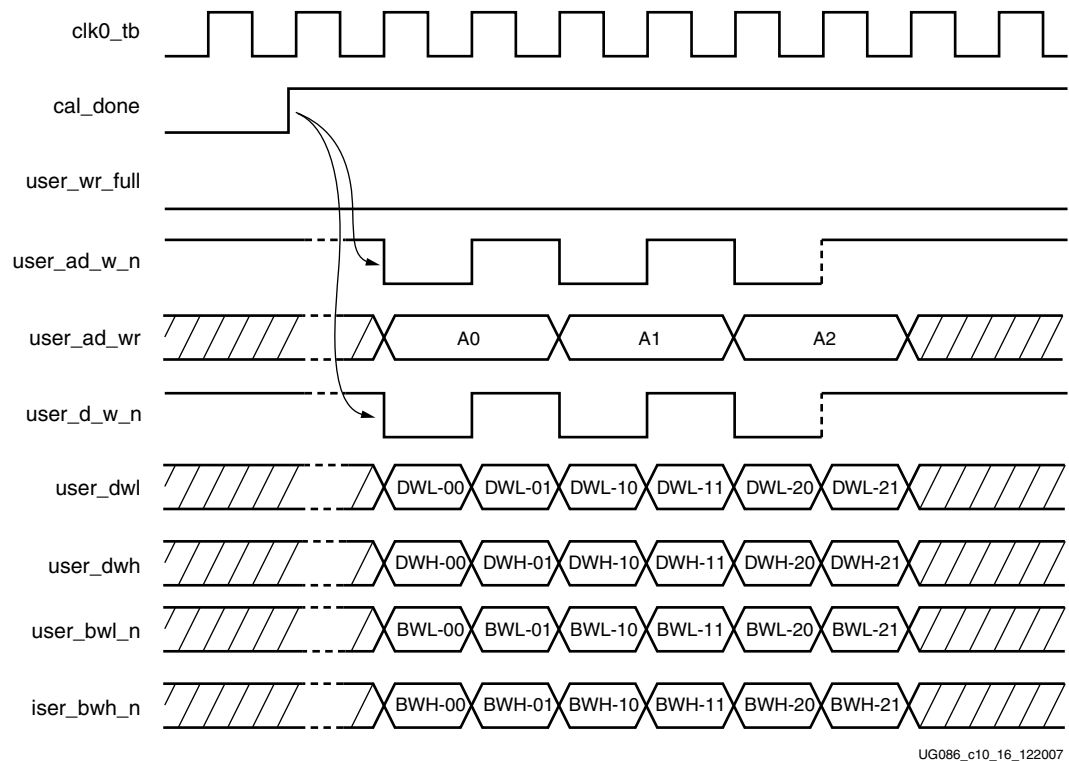
Figure 10-13: Write FIFO User Interface Block Diagram

The following steps describe the architecture of Address and Write Data FIFOs and how to perform a write burst operation to QDRII memory from user interface.

1. The user interface consists of an Address FIFO, Data FIFOs, and a Byte Write FIFO. These FIFOs are built out of Virtex-5 FPGA FIFO primitives. The Address FIFO is a FIFO36 primitive with 1K x 36 configuration. The Data FIFO is a FIFO36_72 primitive with 512 x 72 configuration.
2. The Address FIFO is used to store the memory address where the data is to be written from the user interface. A single instantiation of a FIFO36 constitutes the Address FIFO.
3. Two separate sets of Data FIFOs are used for storing the rising-edge and falling-edge data to be written to QDRII memory from the user interface. For 9-bit, 18-bit, and 36-bit configurations, the controller pads the extra bits of the Data FIFO with 0s.
4. The Byte Write FIFO is used to store the Byte Write signals to QDRII memory from the user interface. Extra bits are padded with zeros.
5. The user can initiate a write command to memory by writing to the Write Address FIFO, Write Data FIFO, and Byte Write FIFOs when the FIFO full flags are deasserted and after the calibration done signal `cal_done` is asserted. The user should not access any of these FIFOs until `cal_done` is asserted. During the calibration process, the

controller writes pattern data into the Data FIFOs. The `cal_done` signal assures that the clocks are stable, the reset process is completed, and the controller is ready to accept commands. Status signal `user_wr_full` is asserted when the Address FIFO, Data FIFOs, or Byte Write FIFOs are full.

6. When signal `user_ad_w_n` is asserted, `user_ad_wr` is stored in the Address FIFO. When signal `user_d_w_n` signal is asserted, `user_dwl` and `user_dwh` are stored into the Data FIFO, and `user_bwl` and `user_bwh` are stored into the Byte Write FIFOs. For proper controller functionality, `user_ad_w_n` and `user_d_w_n` must be asserted and deasserted simultaneously.
7. The controller reads the Address, Data, and Byte Write FIFOs when they are not empty by issuing the `wr_init_n` signal. The QDRII memory write command is generated from the `wr_init_n` signal by properly timing it.

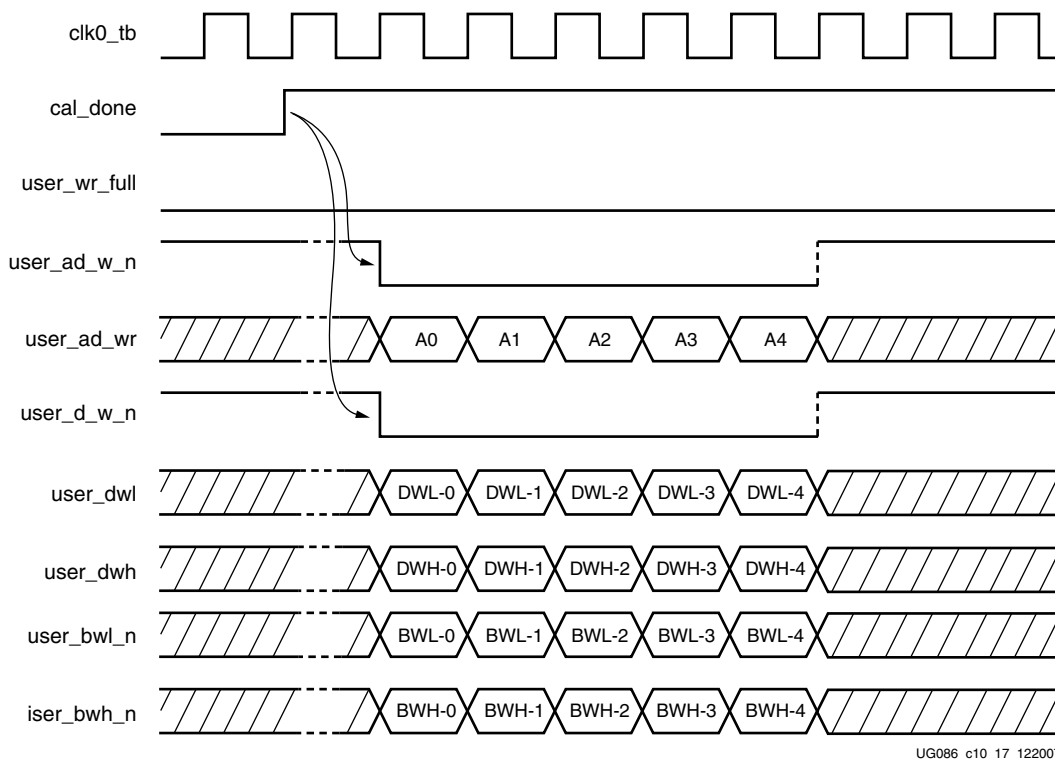


UG086_c10_16_122007

Figure 10-14: Write FIFO User Interface Timing Diagram for BL = 4

8. [Figure 10-14](#) shows the timing diagram for a write command with a burst length of four. The address should be asserted for one clock cycle as shown. For BL = 4, each write to the Address FIFO has two writes to the Data FIFO consisting of two rising-edge and two falling-edge data.
9. [Figure 10-15](#) shows the timing diagram for a write command with a burst length of two. For BL = 2, each write to the Address FIFO has one write to Data FIFO, consisting of one rising-edge and one falling-edge data. Commands can be given in every clock when BL = 2.

When `BURST2_FIFO_INTERFACE` is set to `FALSE` in `design_top`, the timing shown in [Figure 10-15](#) must be followed from the user side. Corresponding address and write data are provided in the same cycle associated with asserting `user_ad_w_n` and `user_d_w_n`. The `user_wr_full` and `user_rd_full` signals are tied Low in this case.



UG086_c10_17_122007

Figure 10-15: Write FIFO User Interface Timing Diagram for BL = 2

Table 10-8 shows the write latency of the controller.

Table 10-8: Maximum Write Latency

Parameter	Number of Clock Cycles	Description
User write command to Write Address FIFO empty flag	6	<ul style="list-style-type: none"> 2 clock cycles for register stages 4 clock cycles for empty flag deassertion in the FWFT mode
Read empty flag to command to the memory	2.5	<ul style="list-style-type: none"> 1 clock cycle to generate the write command in the controller state machine 1.5 cycles to transfer the command to the memory
Total Latency	8.5	

For a design with a burst length of two without FIFOs, the total write latency becomes 4.5 cycles. This is because the four clock cycle latency of the empty signal deassertion of the Write Address FIFO does not apply.

Read Interface

Figure 10-16 shows a block diagram for the read interface.

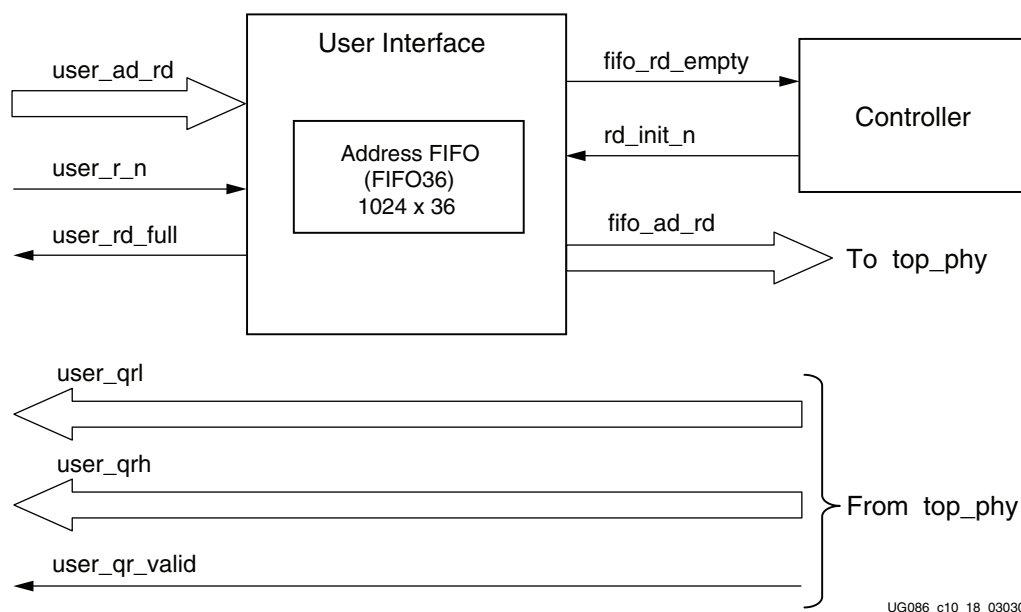


Figure 10-16: Read FIFO User Interface Block Diagram

The following steps describe the architecture of the read user interface and how to perform a QDRII SRAM burst read operation.

1. The read user interface consists of an Address FIFO built out of a Virtex-5 FPGA FIFO36 of configuration 1K x 16.
2. To initiate a QDRII read command, the user writes the Address FIFO when the FIFO full flag `user_rd_full` is deasserted and the calibration done signal `cal_done` is asserted. Writing to the Address FIFO is an indication to the controller that it is a Read command. The `cal_done` signal assures that the controller clocks are stable, the internal reset process is completed, and the controller is ready to accept commands.
3. The user should issue the Address FIFO write-enable signal `user_r_n` along with read address `user_ad_rd` to write the read address to the Address FIFO.
4. The controller reads the Address FIFO when status signal `fifo_rd_empty` is deasserted and generates the appropriate control signals to QDRII memory required for a read command.
5. Prior to the actual read and write commands, the design calibrates the latency in number of clock cycles from the time the read command is issued to the time the data is received. Using this precalibrated delay information, the controller generates the user valid signal `user_qr_valid`.
6. The High state of the `user_qr_valid` signal indicates that read data is available.
7. The user must access the read data as soon as `user_qr_valid` is asserted High.
8. Figure 10-17 and Figure 10-18 show the user interface timing diagrams for BL = 4 and BL = 2.
9. After the read address is loaded into the Read Address FIFO, it can take a maximum of 14 clock cycles, worst case, for the controller to assert `user_qr_valid` High.

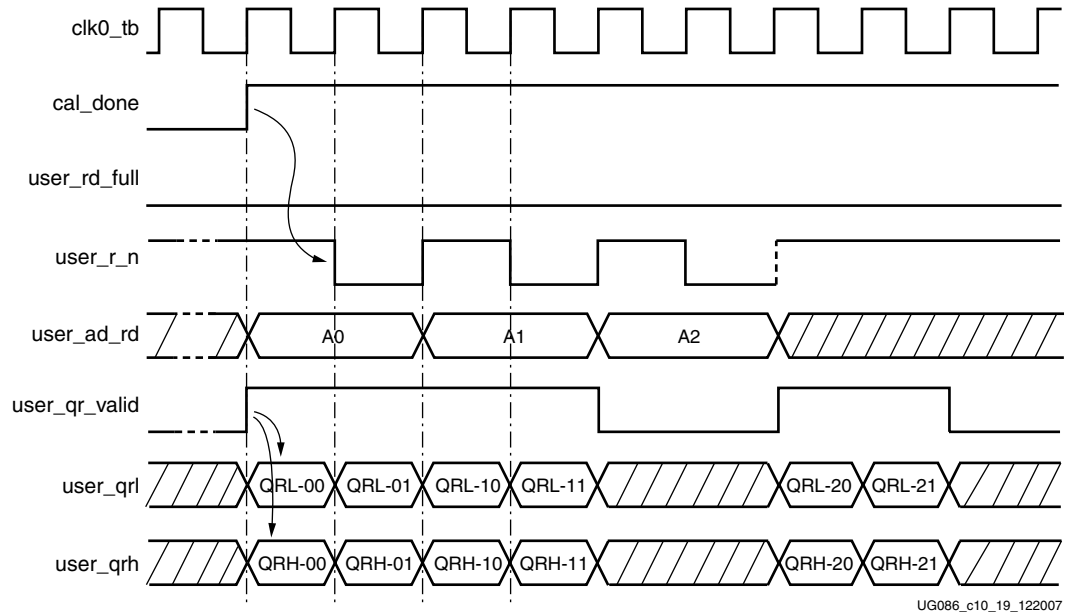


Figure 10-17: Read User Interface Timing Diagram for BL = 4

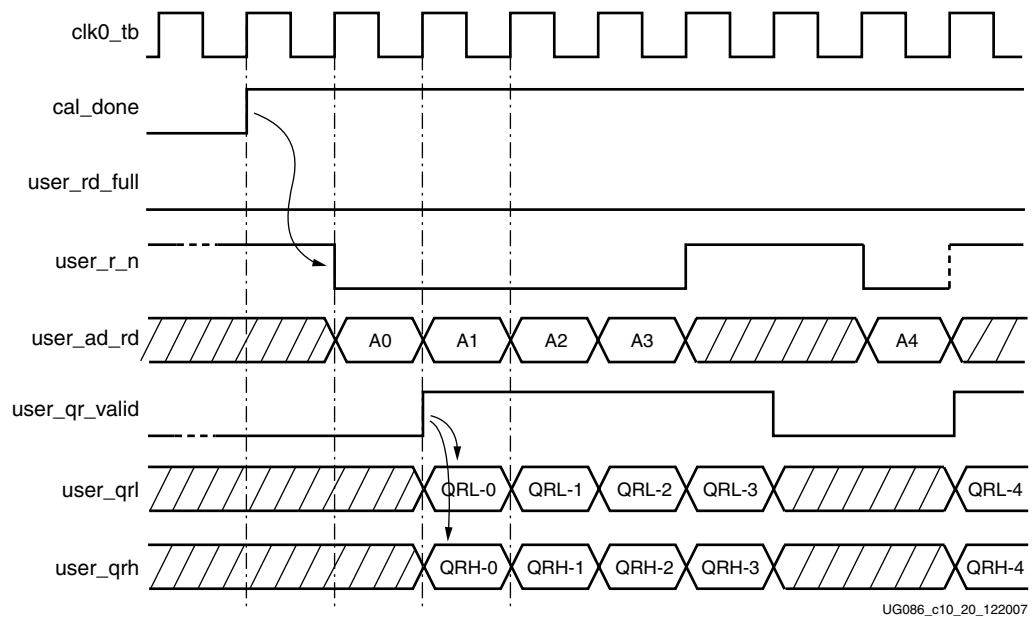


Figure 10-18: Read User Interface Timing Diagram for BL = 2

The BL = 2 example without the FIFO user interface uses the same input signal timing on the address, command, and data as the non-FIFO user interface.

Table 10-9 shows the read latency of the controller.

Table 10-9: Maximum Read Latency

Parameter	Number of Clock Cycles	Description
User read command to Read Address FIFO empty flag	6	<ul style="list-style-type: none"> 2 clock cycles for register stages 4 clock cycles for empty flag deassertion in the FWFT mode
Read empty flag to command to the memory	2.5	<ul style="list-style-type: none"> 1 clock cycle to generate the read command in the controller state machine 1.5 cycles to transfer the command to the memory
Memory read command to valid data available	5.5	<ul style="list-style-type: none"> 1.5 clock cycles of memory read latency 3 clock cycles to capture and transfer read data to the FPGA clock domain 1 clock cycle for aligning all the read data captured
Total Latency	14	

For a design with a burst length of two without FIFOs, the total read latency becomes 4.5 cycles. This is because the four clock cycle latency of the empty signal deassertion of the Read Address FIFO does not apply.

QDRII SRAM Signal Allocations

Table 10-10 shows the list of signals for a QDRII SRAM design allocated in a group from bank selection checkboxes in MIG.

Table 10-10: QDRII Signal Allocations

Bank Selected	Signals Allocated in the Group
Address	Memory address and memory control
Data_Write	Memory write data, memory byte write, and K and C clocks
Data_Read	Memory read data and memory CQ
System Control	System reset from the user interface and status signals
System Clock	System clocks from the user interface

MIG shows checkboxes for Address, Data_Write, Data_Read, System Control, and System_Clock when a bank is selected for a QDRII SRAM design.

When the Address box is checked in a bank, the address, qdr_w_n, qdr_r_n, and qdr_dll_off_n bits are assigned to that particular bank.

When the Data_Write box is checked in a bank, the memory data write, memory byte write bits, the memory write clocks, and the memory input clock for the output data are assigned to that particular bank.

When the Data_Read box is checked in a bank, the memory data read and memory read clocks are assigned to that particular bank.

When the System Control box is checked in a bank, the sys_rst_n, compare_error, and cal_done bits are assigned to that particular bank.

When the System Clock box is checked in a bank, the sys_clk_p, sys_clk_n, dly_clk_200_p, and dly_clk_200_n bits are assigned to that particular bank.

For special cases, such as without a testbench and without a PLL, the corresponding input and output ports are not assigned to any FPGA pins in the design UCF because the user can connect these ports to the FPGA pins or can connect to some logic internal to the same FPGA.

Note: Timing has been verified for most of the MIG generated configurations. For the best timing results, adjacent banks in the same column of the FPGA should be used. Banks that are separated by unbonded banks should be avoided because these can cause timing violations.

Supported Devices

The design generated out of MIG is independent of the memory package, hence the package part of the memory component is replaced with X, where X indicates any package. Table 10-11 shows the list of components supported by MIG.

Table 10-11: Supported Devices for QDRII SRAM

Virtex-5 FPGA (Verilog and VHDL)		
Components	Make	Configuration
CY7C1314BV18-167BZXC	Cypress	x36
CY7C1315BV18-250BZC	Cypress	x36
CY7C1515V18-250BZC	Cypress	x36
K7R161882B-FC25	Samsung	x18
K7R161884B-FC25	Samsung	x18
K7R161884B-FC30	Samsung	x18
K7R163682B-FC25	Samsung	x36
K7R163684B-FC25	Samsung	x36
K7R321884M-FC25	Samsung	x18
K7R321884C-FC25	Samsung	x18
K7R323682C-FC30	Samsung	x36
K7R323684M-FC25	Samsung	x36
K7R323684C-FC25	Samsung	x36
K7R641882M-FC25	Samsung	x18
K7R641884M-FC25	Samsung	x18
K7R641884M-FC30	Samsung	x18

Table 10-11: Supported Devices for QDRII SRAM (Cont'd)

Virtex-5 FPGA (Verilog and VHDL)		
Components	Make	Configuration
K7R643682M-FC25	Samsung	x36
K7R643684M-FC30	Samsung	x36

Simulating the QDRII SRAM Design

After generating the design, MIG creates a `sim` folder in the specified path. This folder contains simulation files for a particular design. The `sim` folder contains the external testbench, memory model, and `.do` file to simulate the generated design. The memory model files are currently generated in Verilog only. To learn more details about the files in the `sim` folder and to simulate the design, refer to “[Simulation Guide](#),” page 499.

Hardware Tested Configurations

The frequencies shown in [Table 10-12](#) were achieved on the Virtex-5 FPGA ML561 Memory Interface Development Board under nominal conditions. This frequency should not be used to determine the maximum design frequency. The maximum design frequency supported in MIG wizard is based on combination of the TRCE results for fabric timing on multiple device/package combinations and I/O timing analysis using FPGA and memory timing parameter for a 72-bit wide interface.

Table 10-12: Hardware Tested Configurations

FPGA Device	XC5VLX50TFF1136-2
Memory Component	K7R643684M-FC30
Data width	72
Burst Length	4
Frequency	100 MHz to 360 MHz
Flow Vendors	Synplicity and XST
Design Entry	VHDL and Verilog

Implementing DDR SDRAM Controllers

This chapter describes how to implement DDR SDRAM interfaces for Virtex®-5 FPGAs generated by MIG. This design is based on XAPP851 [Ref 25].

Interface Model

DDR SDRAM interfaces are source-synchronous and double data rate. They transfer data on both edges of the clock cycle. A memory interface can be modularly represented as shown in Figure 11-1. A modular interface has many advantages. It allows designs to be ported easily and also makes it possible to share parts of the design across different types of memory interfaces.

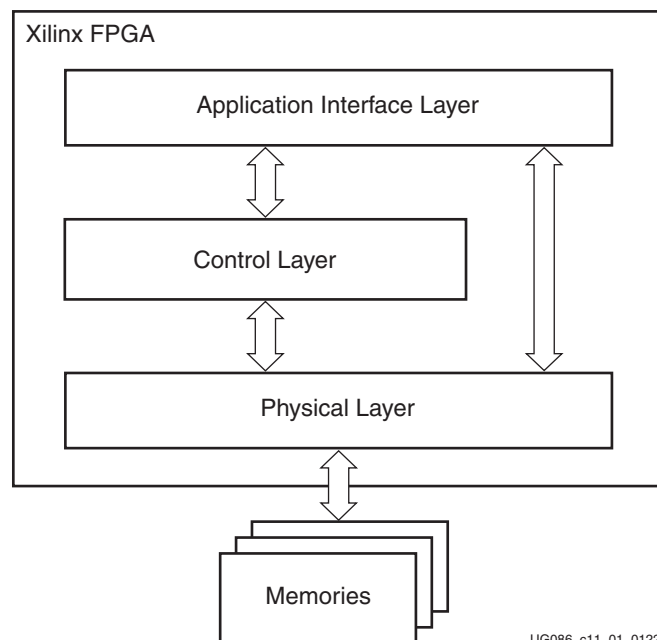


Figure 11-1: Modular Memory Interface Representation

Feature Summary

This section summarizes the supported and unsupported features of DDR SDRAM controller design.

Supported Features

The DDR SDRAM controller design supports the following:

- Burst lengths of two, four, and eight
- Sequential and interleaved burst types
- DDR SDRAM components and DIMMs
- CAS latencies of 2, 2.5, and 3
- Verilog and VHDL
- With and without a testbench
- Bank management
- Byte-wise data masking
- Linear addressing
- With and without a PLL
- Registered DIMMs, unbuffered DIMMs and SO-DIMMs
- Data mask
- System clock, differential and single-ended

The supported features are described in more detail in [“Architecture.”](#)

Design Frequency Ranges

Table 11-1: Design Frequency Range in MHz

Memory	FPGA Speed Grade					
	-1		-2		-3	
	Min	Max	Min	Max	Min	Max
Component	77	200	77	200	77	200
DIMM	77	200	77	200	77	200

Unsupported Features

The DDR SDRAM controller design does not support:

- Deep memories/dual rank DIMMs
- Multicontrollers

Architecture

Implemented Features

This section provides details on the supported features of the DDR SDRAM controller. The Virtex-5 FPGA DDR SDRAM design is a generic design that works for most of the features mentioned above. User input parameters are defined as parameters for Verilog and generics in VHDL in the design modules and are passed down the hierarchy. For example, if the user selects a burst length of 4, then it is defined as follows in the <top_module> module:

```
parameter BURST_LEN = 4,           // burst length (in doublewords)
```

The user can change this parameter for various burst lengths to get the desired output. The same concept holds for all the other parameters listed in the <top_module> module.

[Table 11-2](#) lists the details of all parameters.

Table 11-2: Parameterization of DDR SDRAM Virtex-5 FPGA Design

Category	Parameter Name	Description	Other Notes	Value Restrictions
Memory Width	BANK_WIDTH	Number of memory bank address bits		
	CKE_WIDTH	Number of memory clock enable outputs		
	CLK_WIDTH	Number of differential clock outputs	Determined by the number of components/modules (one pair per component)	
	COL_WIDTH	Number of memory column bits		
	CS_BITS	$\log_2(\text{CS_NUM})$	Used for chip-select related address decode. See notes for CS_NUM and CS_WIDTH.	
	CS_NUM	Number of separate chip selects	Different from CS_WIDTH. For example, for a 32-bit data bus with 2 x16 parts, CS_NUM = 1, but CS_WIDTH = 2 (that is, a single chip select drives two separate outputs, one for each component)	$\text{CS_WIDTH} / \text{CS_NUM} = \text{integer}$
	CS_WIDTH	Number of memory chip selects	Determined by the number of components/modules (one per component)	$\text{CS_WIDTH} / \text{CS_NUM} = \text{integer}$
	DM_WIDTH	Number of data mask bits	Can be a different value from DQS_WIDTH if x4 components are used	$(\text{DQ_WIDTH})/8$
	DQ_BITS	$\log_2(\text{DQS_WIDTH} * \text{DQ_PER_DQS})$	Used for data bus calibration decode	$(\text{DQ_WIDTH}) / \text{Number of data bits}$
	DQ_WIDTH	Number of data bits		
	DQ_PER_DQS	Number of memory DQ data bits per strobe		
	DQS_BITS	$\log_2(\text{DQS_WIDTH})$		
	DQS_WIDTH	Number of memory DQS strobes		
	ROW_WIDTH	Number of memory address bits		

Table 11-2: Parameterization of DDR SDRAM Virtex-5 FPGA Design (Cont'd)

Category	Parameter Name	Description	Other Notes	Value Restrictions
Memory Options	BURST_LEN	Burst length		(2,4,8)
	BURST_TYPE	Burst type (0: sequential, 1: interleaved)		(0,1)
	CAS_LAT	CAS latency (equal to 25 for CL = 2.5)		(2,25,3)
	MULTI_BANK_EN	Bank management enable	If enabled, up to four banks are kept open; otherwise, one bank is kept open	(0,1)
	REDUCE_DRV	Reduced strength memory I/O enable. Set (1) for reduced I/O drive strength.	Not supported for all DDR/DDR2 widths	(0,1)
	REG_ENABLE	Set (1) for registered memory module	Accounts for an extra clock cycle delay on address/control for a registered module	(0,1)
Memory Timing	T _{REFL_NS}	Auto refresh interval (in ns)	Take directly from memory data sheet	
	T _{RAS}	Active to precharge delay (in ps)	Take directly from memory data sheet	
	T _{RCD}	Active to read/write delay (in ps)	Take directly from memory data sheet	
	T _{RFC}	Refresh to refresh, refresh to active delay (in ps)	Take directly from memory data sheet	
	T _{RP}	Precharge to command delay (in ps)	Take directly from memory data sheet	
	T _{WR}	Used to determine write to precharge (in ps)	Take directly from memory data sheet	
	T _{WTR}	Write to read (in ps)	Take directly from memory data sheet	
Miscellaneous	CLK_PERIOD	Memory clock period (in ps)	Used for PHY calibration and PLL/DCM (if applicable) setting	
	DLL_FREQ_MODE	DCM Frequency Mode	Determined by CLK_PERIOD. Needed only if the DCM option is selected.	("LOW", "HIGH")
	DDR2_ENABLE	Select either DDR or DDR2 interface (equal to 1 for DDR2)	Provided from the mem_if_top level and below	(0,1)
	SIM_ONLY	Enable bypass of 200 μ s power-on delay		(0,1)
	RST_ACT_LOW	Indicates the polarity of the input reset signal (sys_rst_n)	1: Reset is active Low. 0: Reset is active High.	(0,1)
	HIGH_PERFORMANCE_MODE	IODELAY High Performance Mode Parameter value	This parameter value represents HIGH_PERFORMANCE_MODE of IODELAY as TRUE or FALSE. This will result in the higher or lower power dissipation at the output of IODELAY element.	Verilog : String. "TRUE", "FALSE". VHDL : Boolean : TRUE, FALSE.

Burst Length

Bits M0:M3 of the Mode Register define the burst length and burst type. Read and write accesses to the DDR SDRAM are burst-oriented. The burst length is programmable to either 2, 4, or 8 through the GUI. The burst length determines the maximum number of column locations accessed for a given READ or WRITE command. The DDR SDRAM ctrl module implements a burst length that is programmed.

CAS Latency

Bits M4:M6 of the Mode Register define the CAS latency (CL). CL is the delay in clock cycles between the registration of a READ command and the availability of the first bit of output data. CL can be set to 2, 2.5, or 3 clocks through the GUI. CAS latency is implemented in the ctrl module. For CL = 2.5, the input value is read as "25" in the design. During read data operations, the generation of the read_en signal varies according to the CL in the ctrl module.

Precharge

The PRECHARGE command is used to close the open row in a bank if there is a command to be issued in the same bank. The Virtex-5 FPGA DDR controller issues a PRECHARGE command only if there is already an open row in the particular bank where a read or write command is to be issued, thus increasing the efficiency of the design. The auto-precharge function is not supported in this design. This design ties the A10 bit Low during normal reads and writes.

Data Masking

Virtex-5 FPGA DDR SDRAM controllers support bitwise data masking of the data bits during a write operation. For x4 components, data masking cannot be done on a per nibble basis due to an internal block RAM based FIFO limitation. The mask data is stored into the FIFOs along with the write data. MIG supports a data mask option. If this option is checked in the GUI, MIG generates a design with data mask pins. This option can be chosen if the selected part has data masking.

Auto Refresh

An AUTO REFRESH command is issued to the DDR memory at specified intervals of time to refresh the charge to retain the data.

Bank Management

Bank management is done by the Virtex-5 FPGA DDR SDRAM controller design to increase the efficiency of the design. The controller keeps track of whether the bank being accessed already has an open row or not, and also decides whether a PRECHARGE command should be issued or not to that bank. When bank management is enabled via the MULTI_BANK_EN parameter, a maximum of four banks/rows can open at any one time. A least-recently-used (LRU) algorithm is employed to keep the three banks most recently used. It closes the bank least recently used when a new bank/row location needs to be accessed. The bank management feature can also be disabled by clearing MULTI_BANK_EN. In this case, only one bank is kept open at any one time. For more information on Bank Management, refer to application note XAPP858 [Ref 27].

Linear Addressing

Linear addressing refers to the way the user provides the address of the memory to be accessed. For Virtex-5 FPGA DDR SDRAM controllers, the user provides the address information through the `app_af_addr` signal. As the densities of the memory devices vary, the number of column address bits and row address bits also change. In any case, the row address bits in the `app_af_addr` signal always start from the next higher bit where the column address ends. This feature increases the coverage of more devices that can be supported with the design.

Different Memories (Density/Speed)

The DDR SDRAM controller supports different densities. For DDR components shown in MIG, densities can vary from 128 Mb to 1 Gb. The user can select the various configurations from the “Create custom part” option; the supported maximum column address is 13, the maximum row address is 15, and the maximum bank address is 2. The design can decode write and read addresses from the user in the DDR SDRAM ctrl module. The user address consists of column, row, and bank addresses.

System Clock

MIG supports differential and single-ended system clocks. Based on the selection in the GUI, input system clocks and IDELAY clocks are differential or single-ended.

IDELAY Performance Mode

In Virtex-5 family devices, the power dissipation of the IDELAY elements can be controlled using the `HIGH_PERFORMANCE_MODE` parameter. The values of this parameter can be either `TRUE` or `FALSE`.

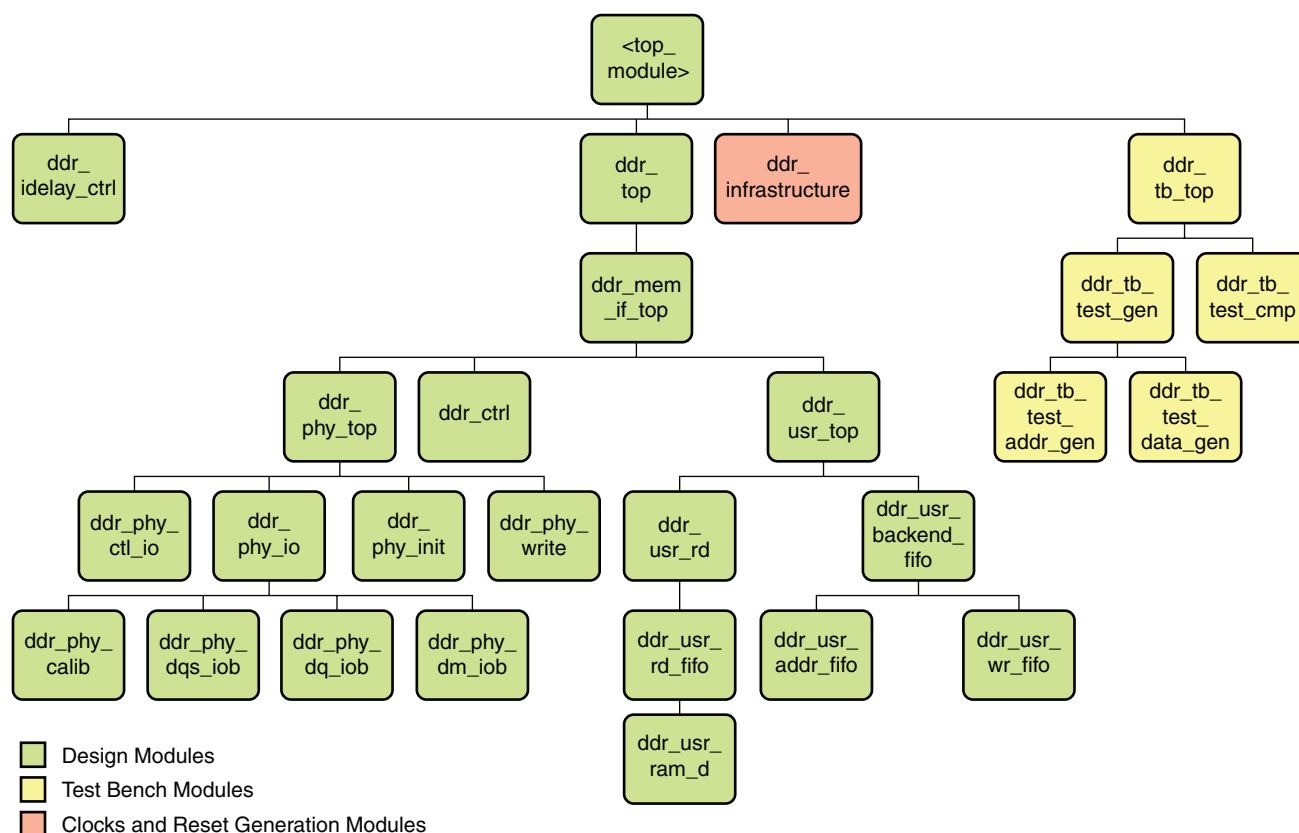
When this parameter value is set to `TRUE`, the IDELAY jitter value per tap is reduced. This reduction results in a slight increase in power dissipation from the IDELAY element. When this parameter value is set to `FALSE`, the IDELAY power dissipation is reduced, but with an increase in the jitter value per tap.

The value of this parameter can be selected from the MIG FPGA options page. Users can also manually set this parameter value to `TRUE` or `FALSE` in the design top-level block HDL module.

Refer to [Appendix E, “Debug Port”](#) for more information on the IDELAY Performance Mode.

Hierarchy

Figure 11-2 shows the hierarchical structure of the design generated by MIG with a PLL and a testbench.



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Figure 11-2: Hierarchical Structure of Virtex-5 FPGA DDR SDRAM Design

The modules are classified in three types:

- Design modules
- Testbench modules
- Clock and reset generation modules

MIG can generate four different DDR SDRAM designs:

- With a testbench and a PLL
- Without a testbench and with a PLL
- With a testbench and without a PLL
- Without a testbench and without a PLL

For designs without a testbench, the correspondingly yellow shaded modules are not present. In this case, the user interface signals appear in the <top_module> module. Table 11-4, page 444 provides a list of these signals.

The infrastructure module generates the clock and reset signals for the design. It instantiates a PLL when MIG generates a design with a PLL. The inputs to this module are the differential design clock and a 200 MHz differential clock for the IDELAYCTRL

module. A user reset is also input to this module. Using the input clocks and reset signals, the system clocks and the system reset are generated in this module, which is used in the design.

If the design has no PLL, the PLL primitive is not instantiated in the module. Instead, the system operates on the user-provided clocks. A system reset is also generated in the infrastructure module using the input locked signal.

MIG Design Options

MIG provides various options to generate the design with or without a testbench or with or without a PLL. This section provides detailed descriptions of the different types of designs the user can generate using the MIG options. The designs in [Figure 11-3](#) and [Figure 11-5, page 437](#) use the differential system clocks. For more information on the clocking structure, refer to [“Clocking Scheme,” page 442](#).

MIG outputs both an `example_design` and a `user_design`. The MIG-generated `example_design` includes the entire memory controller design along with a synthesized testbench (example user application). This testbench generates sample writes and reads and then uses comparison logic to verify that the data patterns written are the same as those received. This `example_design` can be used to test functionality both in simulation and in hardware. The `user_design` includes the memory controller design only. This design allows users to connect the MIG memory controller design to a user developed testbench (user application). Refer to [Table 11-4, page 444](#) for user interface signals, the [“User Interface Accesses,” page 449](#) for timing restriction on user interface signals, and [Figure 11-13, page 452](#) for write interface timing.

[Figure 11-3](#) shows a block diagram representation of the top-level module for a design with a PLL and a testbench. The inputs consist of differential clocks for the design and `Idelayctrl` modules and the user reset. [“Clocking Scheme,” page 442](#) describes how various clocks are generated using the PLL. The error output signal indicates whether the case passes or fails. The `phy_init_done` signal indicates the completion of initialization and calibration of the design. Because the PLL is instantiated in the infrastructure module, it generates the required clocks and reset signals for the design.

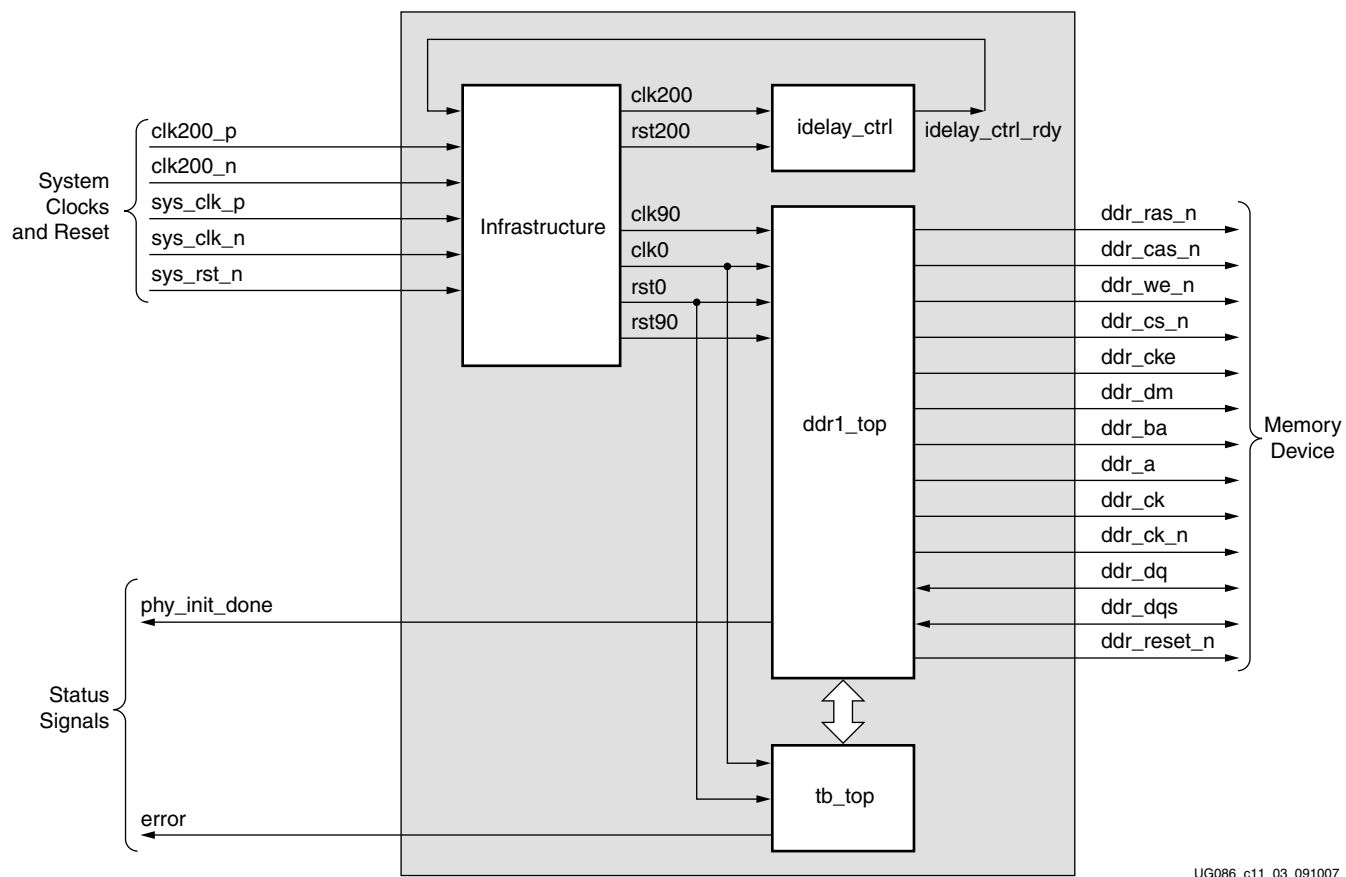
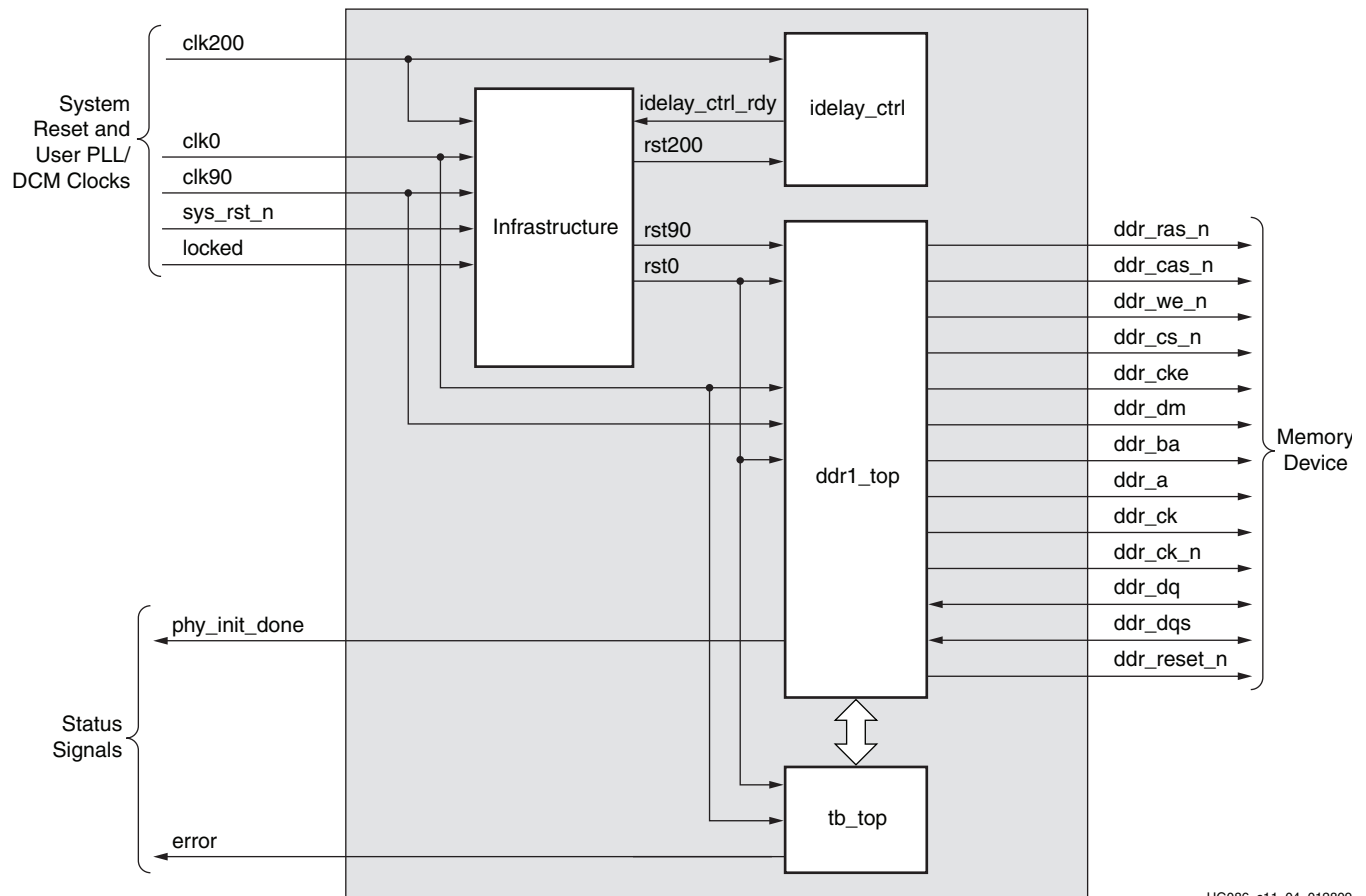


Figure 11-3: Top-Level Block Diagram of the DDR SDRAM Design with a PLL and a Testbench

Figure 11-4 shows a block diagram representation of the top-level module for a design with a testbench but without a PLL. “Clocking Scheme,” page 442 explains how to generate the design clocks from the user interface. The inputs consist of user clocks for the design and Idelayctrl modules and the user reset. The design uses the user input clocks. These clocks should be single-ended. The infrastructure module uses the input reset and locked signals to reset the design. The user application must have a PLL/DCM primitive instantiated in the design. The error output signal indicates whether the case passes or fails. The phy_init_done signal indicates the completion of initialization and calibration of the design.



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Figure 11-4: Top-Level Block Diagram of the DDR SDRAM Design with a Testbench but without a PLL

Figure 11-5 shows a block diagram representation of the top-level module for a design with a PLL but without a testbench. “Clocking Scheme,” page 442 describes how various clocks are generated using the PLL. The `phy_init_done` signal indicates the completion of initialization and calibration of the design. The user interface signals are also listed in the <top_module> module. The design provides the `clk0_tb` and `rst0_tb` signals to the user to synchronize with the design. The `clk0_tb` signal is connected to `clk0` in the controller. If the user clock domain is different from `clk0/clk0_tb`, the user should add FIFOs for all the inputs and outputs of the controller (user application signals) in order to synchronize them to the `clk0_tb` clock. Because the PLL is instantiated in the infrastructure module, it generates the required clock and reset signals for the design.

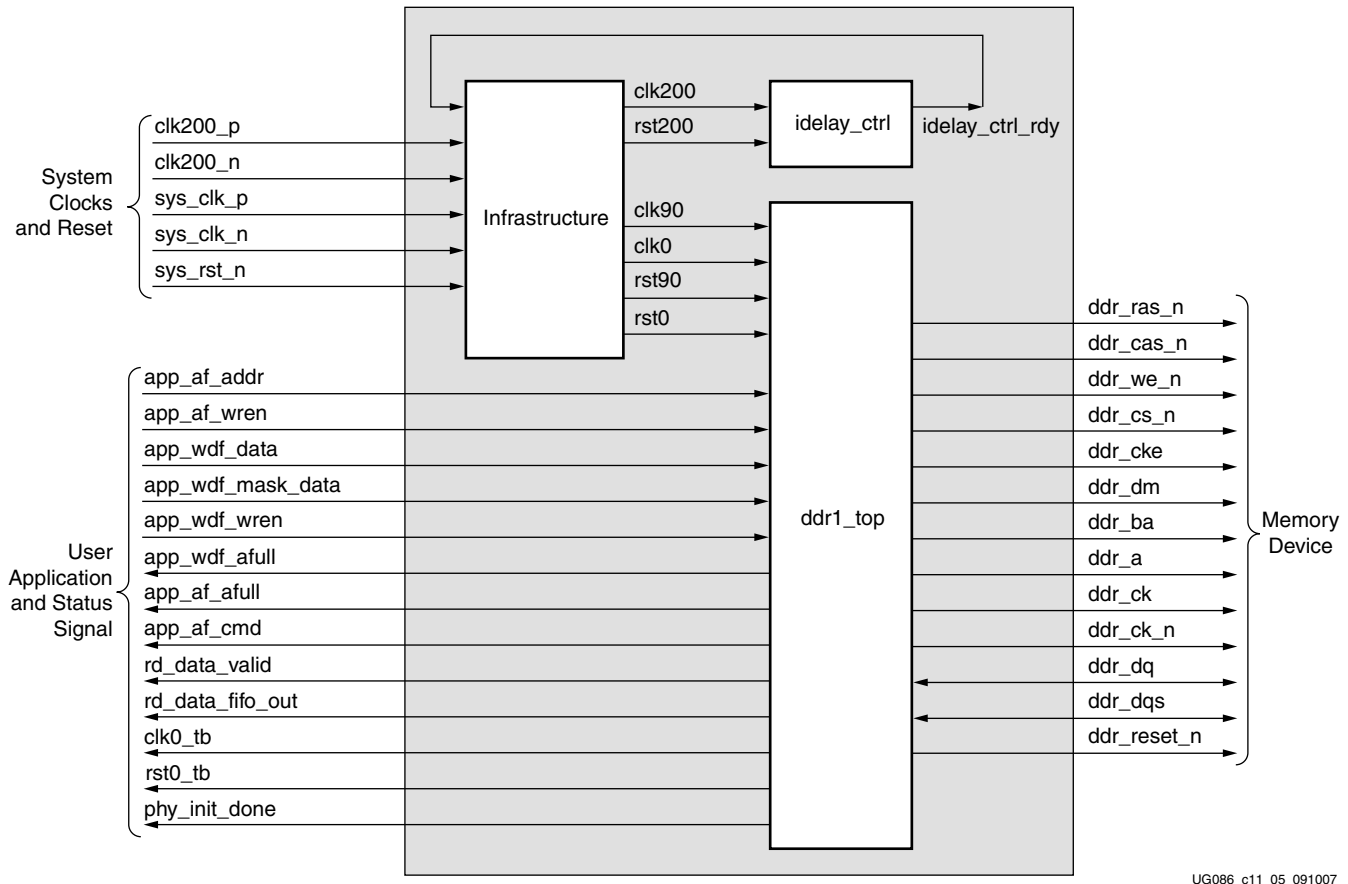


Figure 11-5: Top-Level Block Diagram of the DDR SDRAM Design with a PLL but without a Testbench

Figure 11-6 shows a block diagram representation of the top-level module for designs without a PLL or a testbench. The inputs consist of user clocks for the design and Idelayctrl modules and the user reset. The design uses the user input clocks. “Clocking Scheme,” page 442 explains how to generate the design clocks from the user interface. These clocks should be single-ended. To reset the design, the signals are generated using the input reset and the locked signals in the infrastructure module. The user application must have a PLL/DCM primitive instantiated in the design. The phy_init_done signal indicates the completion of initialization and calibration of the design. The user interface signals are also listed in the <top_module> module. The design provides the clk0_tb and rst0_tb signals to the user to synchronize with the design. The signal clk0_tb is connected to clock clk0 in the controller. If the user clock domain is different from clk0/clk0_tb, the user should add FIFOs for all the inputs and outputs of the controller (user application signals) in order to synchronize them to clk0_tb clock.

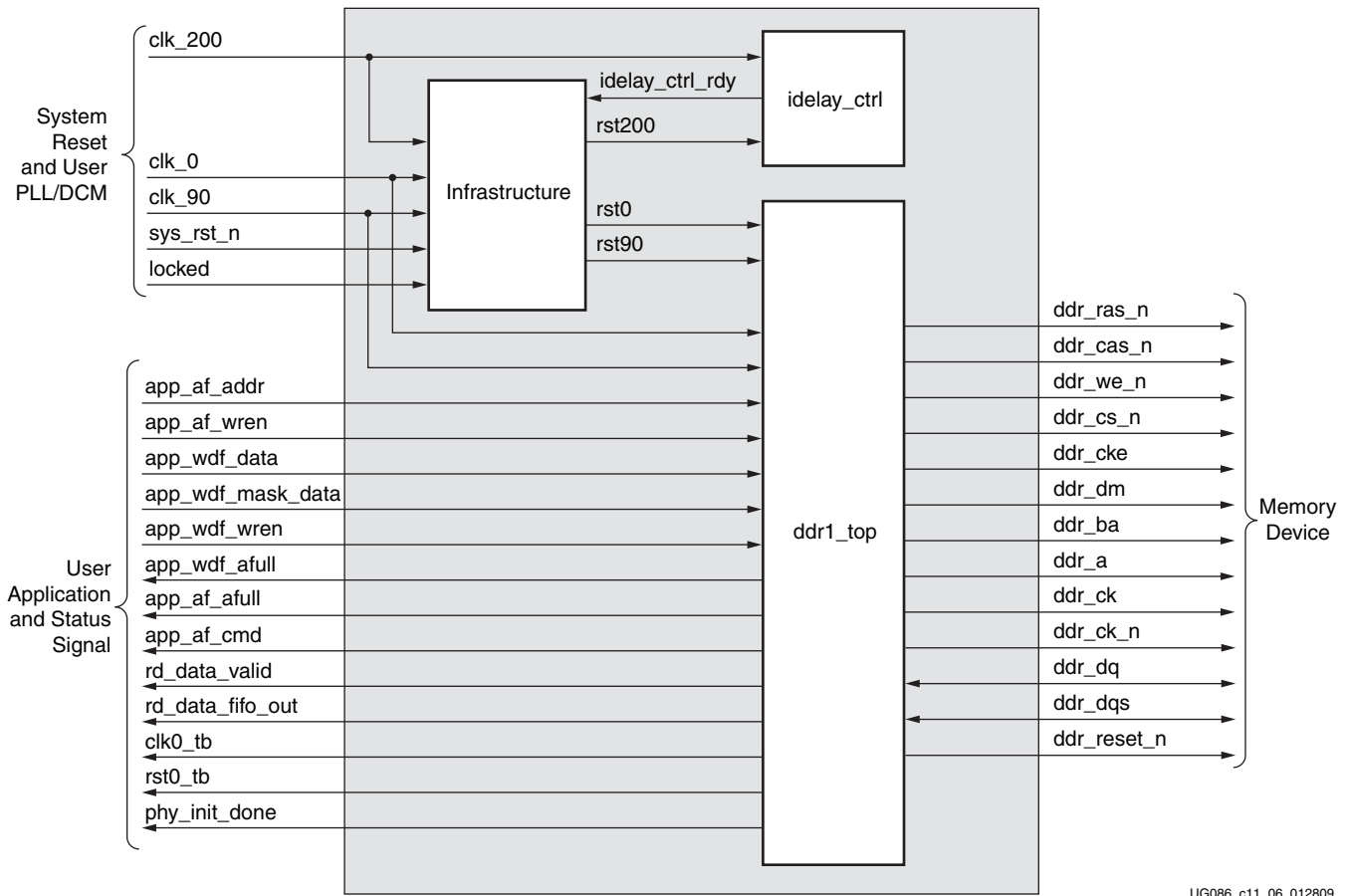
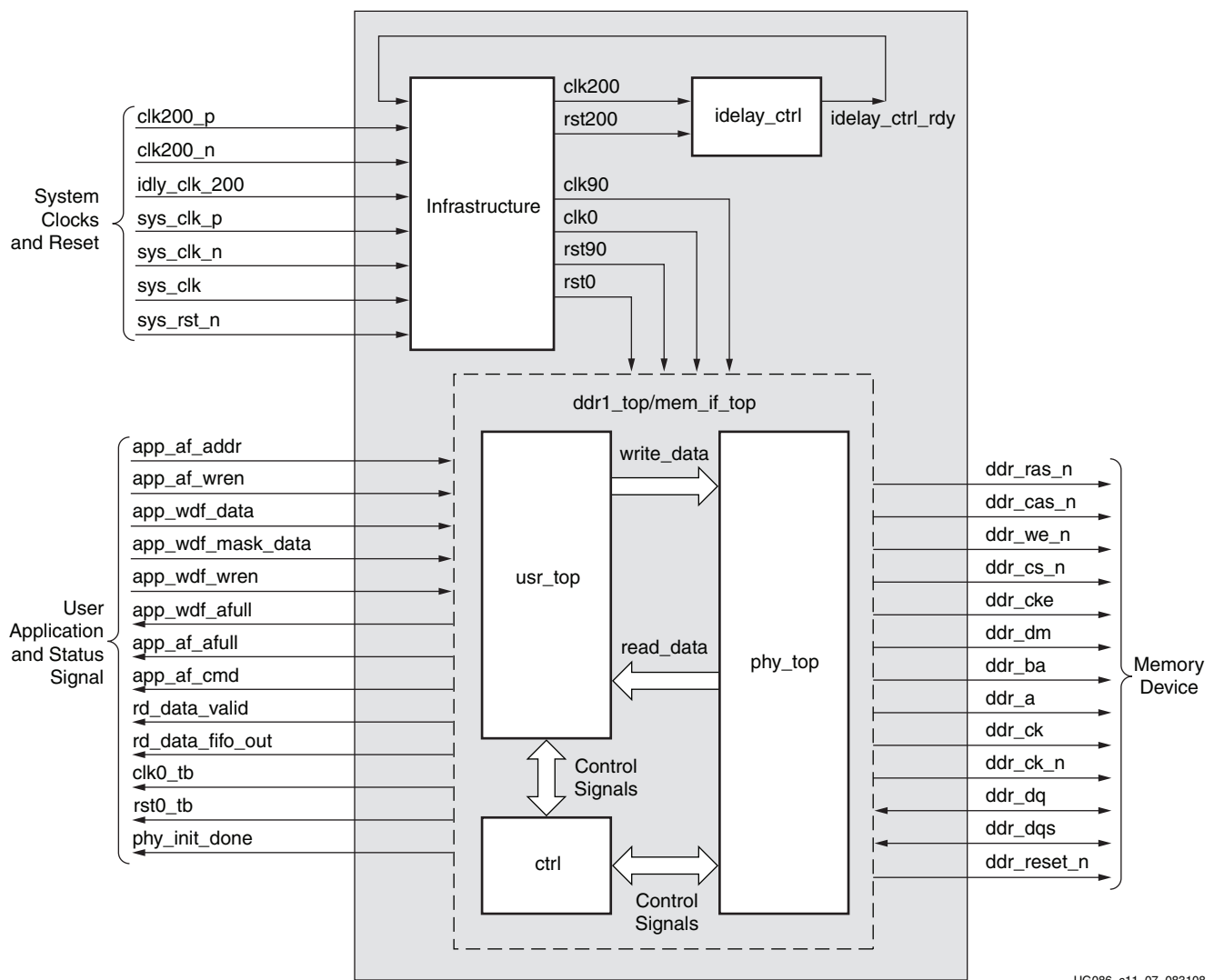


Figure 11-6: Top-Level Block Diagram of the DDR SDRAM Design without a PLL or a Testbench

Figure 11-7 shows an expanded block diagram of the design. The design's top module is expanded to show various internal blocks. The functions of these blocks are explained in following subsections.



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Figure 11-7: Detailed Block Diagram of the DDR SDRAM Design with a PLL but without a Testbench

Infrastructure

The infrastructure module generates the FPGA clock and reset signals. When differential clocking is used, `sys_clk_p`, `sys_clk_n`, `clk_200_p`, and `clk_200_n` signals appear. When single-ended clocking is used, `sys_clk` and `idly_clk_200` signals appear. In addition, clocks are available for design use and a 200 MHz clock is provided for the IDELAYCTRL primitive. Differential and single-ended clocks are passed through global clock buffers before connecting to a PLL/DCM. For differential clocking, the output of the `sys_clk_p/sys_clk_n` buffer is single-ended and is provided to the PLL/DCM input. Likewise, for single-ended clocking, `sys_clk` is passed through a buffer and its output is provided to the PLL/DCM input. The outputs of the PLL/DCM are `clk0` (0° phase-shifted version of the input clock) and `clk90` (90° phase-shifted version of the input clock). After the PLL/DCM is locked, the design is in the reset state for at least 25 clocks. The infrastructure module also generates all of the reset signals required for the design.

PLL/DCM

In MIG 3.0 and later, the DCM is replaced with a PLL for all Virtex-5 FPGA designs. If the user selects a design with a PLL in the GUI, the infrastructure module will have both PLL and DCM codes. The CLK_GENERATOR parameter enables either a PLL or a DCM in the infrastructure module. The CLK_GENERATOR parameter is set to PLL by default. If the user wants to use DCM, this parameter should be changed manually to DCM.

When the user chooses the no PLL option in the GUI, the design does not use any PLL/DCM primitives. Instead it works on the clocks provided by the user. The input clocks in this case have to be single-ended. The locked status and user input reset signals are the inputs to the module when there is no PLL. These signals are used to generate the synchronous system resets for the design.

idelay_ctrl

This module instantiates the IDELAYCTRL primitive of the Virtex-5 FPGA. The IDELAYCTRL primitive is used to continuously calibrate the individual delay elements in its region to reduce the effect of process, temperature, and voltage variations. A 200 MHz clock has to be fed to this primitive.

MIG uses the “automatic” method for IDELAYCTRL instantiation in which the MIG HDL only instantiates a single IDELAYCTRL for the entire design. No location (LOC) constraints are included in the MIG-generated UCF. This method relies on the ISE® tools to replicate and place as many IDELAYCTRLs as needed (for example, one per clock region that uses IDELAYs). Replication and placement are handled automatically by the software tools if IDELAYCTRLs have same refclk, reset, and rdy nets. A new constraint called IODELAY_GROUP associates a set of IDELAYs with an IDELAYCTRL and allows for multiple IDELAYCTRLs to be instantiated without LOC constraints specified. ISE software generates the IDELAY_CTRL_RDY signal by logically ANDing the RDY signals of every IDELAYCTRL block.

The IODELAY_GROUP name should be checked in the following cases:

- The MIG design is used with other IP cores or user designs that also require the use of IDELAYCTRL and IDELAYs.
- Previous ISE software releases 8.2.03i and 9.1i had an issue with IDELAYCTRL block replication or trimming. When using these revisions of the ISE software, the user must instantiate and constrain the location of each IDELAYCTRL individually.

See UG190 [Ref 10] for more information on the requirements of IDELAYCTRL placement.

ctrl

The ctrl module is the main controller of the Virtex-5 FPGA DDR SDRAM controller design. It generates all the control signals required for the DDR memory interface and the user interface. This module signals the FIFOs instantiated in the user interface to output the fed data in it and also signals the physical layer to output the data on the IOBs during a write operation. During a read operation, the data read from the memory is taken from the physical layer and written into the user interface FIFOs using the control signals generated by the ctrl module.

The ctrl module decodes the user command and issues the specified command to the memory. The app_af_cmd signal is decoded as a write command when it equals 3'b000, and app_af_cmd is decoded as a read command when it equals 3'b001. The commands and control signals are generated based on the input burst length and CAS latency. If the multi-bank option is enabled, the ctrl module also takes care of bank management, so as to

increase the efficiency of the design. At a given point of time, a maximum of four banks can be open. The controller issues a PRECHARGE command to the bank only if there is already an open row in that bank and the next command is to be issued to a different row. An ACTIVE command is generated to open the row in that particular bank. Thus the efficiency is increased.

phy_top

The phy_top module is the top level of the physical interface of the design. The physical layer includes the input/output blocks (IOBs) and other primitives used to read and write the double data rate signals to and from the memory, such as IDDR and ODDR. This module also includes the IODELAY elements of the Virtex-5 FPGA. These IODELAY elements are used to delay the input strobe and data signals to capture the valid data into the Read Data FIFO.

The memory control signals, such as RAS_N, CAS_N, and WE_N, are driven from the buffers in the IOBs. All the input and output signals to and from the memory are referenced from the IOB to compensate for the routing delays inside the FPGA.

The phy_init module, which is instantiated in the phy_top module, is used to initialize the DDR memory in a predefined sequence according to the JEDEC standard for DDR SDRAM.

The phy_calib module calibrates the design to align the strobe signal such that it always captures the valid data in the FIFO. This calibration is needed to compensate for the trace delays between the memory and the FPGA devices.

The phy_write module splits the user data into rise data and fall data to be sent to the memory as a double data rate signal using ODDR. Similarly, while reading the data from memory, the data from IDDR is combined to get a single vector that is written into the read FIFO.

usr_top

The usr_top module is the user interface block of the design. It receives and stores the user data, command, and address information in respective FIFOs. The ctrl module generates the required control signals for this module. During a write operation, the data stored in the usr_wr_fifo is read and given to the physical layer to output to the memory. Similarly, during a read operation, the data from the memory is read via IDDR and written into the FIFOs. This data is given to the user with a valid signal (rd_data_valid), which indicates valid data on the rd_data_fifo_out signal. See [“User Interface Accesses,” page 449](#) for required timing requirements and restrictions for user interface signals.

The FIFO36 and FIFO36_72 primitives are used for loading address and data from the user interface. The FIFO36 primitive is used in the ddr_usr_addr_fifo module. The FIFO36_72 primitive is used in the ddr_usr_wr module. Every FIFO has two FIFO threshold attributes, ALMOST_EMPTY_OFFSET and ALMOST_FULL_OFFSET, that are set to 7 and F, respectively, in the RTL by default. These values can be changed as needed. For valid FIFO threshold offset values, refer to UG190 [\[Ref 10\]](#).

Test Bench

The MIG tool generates two RTL folders, example_design and user_design. The example_design folder includes the synthesizable test bench, while user_design does not include the test bench modules. The MIG test bench performs eight write commands and eight read commands in an alternating fashion. The number of words in a write command depends on the burst length. For a burst length of 4, the test bench writes a total of 32 data

words for all eight write commands (16 rise data words and 16 fall data words). For a burst length of 8, the test bench writes a total of 64 data words. It writes the data pattern of FF, 00, AA, 55, 55 AA, 99, 66 in a sequence of which FF, AA, 55, and 99 are rise data words and 00, 55, AA, and 66 are fall data words for an 8-bit design. The falling edge data is the complement of the rising edge data. For a burst length of 4, the data sequence for the first write command is FF, 00, AA, 55, and the data sequence for the second write command is 55, AA, 99, 66. For a burst length of 8, the data pattern for the first write command is FF, 00, AA, 55, 55 AA, 99, 66 and the same pattern is repeated for all the remaining write commands. This data pattern is repeated in the same order based on the number of data words written. For data widths greater than 8, the same data pattern is concatenated for the other bits. For a 32-bit design and a burst length of 8, the data pattern for the first write command is FFFFFFFF, 00000000, AAAAAAAAAA, 55555555, 55555555, AAAAAAAAAA, 99999999, 66666666.

Address generation logic generates eight different addresses for eight write commands. The same eight address locations are repeated for the following eight read commands. The read commands are performed at the same locations where the data is written. There are total of 32 different address locations for 32 write commands, and the same address locations are generated for 32 read commands. Upon completion of a total of 64 commands, including both writes and reads (eight writes and eight reads repeated four times), address generation rolls back to the first address of the first write command and the same address locations are repeated. The MIG test bench exercises only a certain memory area. The address is formed such that all address bits are exercised. During writes, a new address is generated for every burst operation on the column boundary.

During reads, comparison logic compares the read pattern with the pattern written, i.e., the FF, 00, AA, 55, 55 AA, 99, 66 pattern. For example, for an 8-bit design of burst length 4, the data written for a single write command is FF, 00, AA, 55. During reads, the read pattern is compared with the FF, 00, AA, 55 pattern. Based on a comparison of the data, a status signal error is generated. If the data read back is the same as the data written, the error signal is 0, otherwise it is 1.

Clocking Scheme

Figure 11-9, page 444 shows the clocking scheme for this design. Global and local clock resources are used.

The global clock resources consist of a PLL or a DCM, two BUFGs on PLL/DCM output clocks, and one BUFG for clk200. The local clock resources consist of regional I/O clock networks (BUFIO). The global clock architecture is discussed in this section.

The MIG tool allows the user to customize the design such that the PLL/DCM is not included. In this case, system clocks clk0 and clk90, and IDELAYCTRL clock clk200 must be supplied by the user.

Global Clock Architecture

The user must supply two input clocks to the design:

- A system clock running at the target frequency for the memory
- A 200 MHz clock for the IDELAYCTRL blocks.

These clocks can be either single-ended or differential. The user can select a single-ended or differential clock input option from MIG GUI. Differential clocks are connected to the IBUFGDS and the single-ended clock is connected to an IBUFG.

The system clock from the output of the IBUFGDS or the IBUFG is connected to the PLL/DCM to generate the various clocks used by the memory interface logic.

The clk200 output of the IBUFGDS or the IBUFG is connected to the BUFG. The output of the BUFG is used for IDELAY IOB delay blocks for aligning read capture data.

The PLL/DCM generates two separate synchronous clocks for use in the design. This is shown in Table 11-3, Figure 11-8, and Figure 11-9, page 444. The clock structure is the same for both the example design and the user design. For designs without PLL/DCM instantiation, PLL/DCM and the BUFGs should be instantiated at the user end to generate the required clocks.

Table 11-3: DDR Interface Design Clocks

Clock	Description	Logic Domain
clk0	Skew compensated replica of the input system clock.	The clock for the controller and the user interface logic, most of the DDR bus-related I/O flip-flops (e.g., memory clock, control/address, output DQS strobe, and DQ input capture). This clock is used to register the data, address, and command signals, and the address and data enables for the user interface logic ⁽¹⁾ . This clock is also used to generate the FIFO status signals.
clk90	90° phase-shifted version of clk_0	Used in the write data path section of physical layer. Controls write path control logic, DDR side of the Write Data FIFO, and output flip-flops for DQ. This clock is also used to generate the read data and read data valid signals for the user interface logic ⁽¹⁾ .

Notes:

1. See "User Interface Accesses," page 449 for timing requirements and restrictions on the user interface signals.

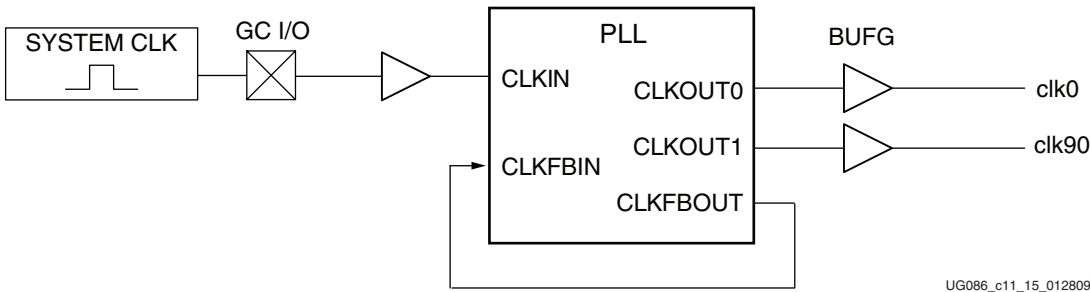


Figure 11-8: Clocking Scheme for QDRII Interface Logic Using PLL

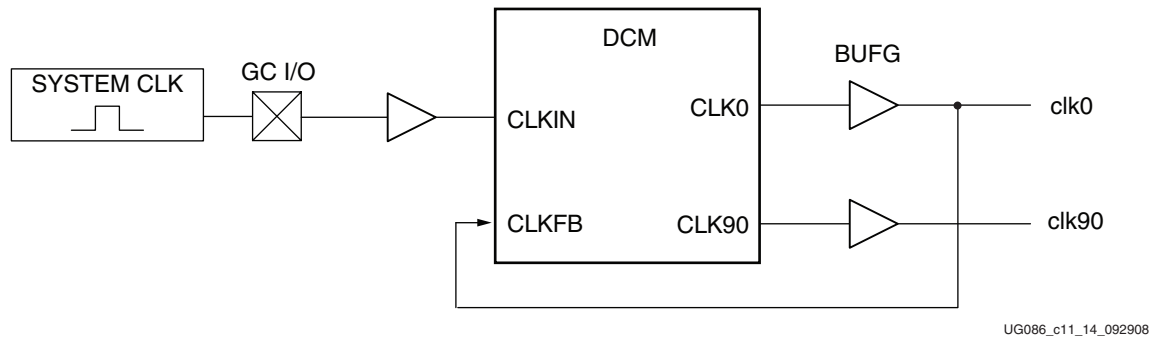


Figure 11-9: Clocking Scheme for DDR Interface Logic

Table 11-4 lists the user interface signals.

Table 11-4: User Interface Signals

Signal	Direction ⁽¹⁾	Description
app_af_cmd[2:0] ⁽²⁾	Input	3-bit command to the Virtex-5 FPGA DDR SDRAM design. app_af_cmd = 3'b000 for write commands app_af_cmd = 3'b001 for read commands Operation is not guaranteed if the user gives values other than the specified ones.
app_af_addr[30:0] ^(2, 3)	Input	Provides the address, row address, and column address of the memory location to be accessed. Column address = app_af_addr[COL_WIDTH-1: 0] Row address = app_af_addr[ROW_WIDTH+COL_WIDTH-1: COL_WIDTH] Bank address = app_af_addr[BANK_WIDTH+ROW_WIDTH+COL_WIDTH-1: ROW_WIDTH+COL_WIDTH]
app_af_wren ⁽²⁾	Input	Write enable to the user address FIFO. This signal should be synchronized with the app_af_addr and app_af_cmd signals.
app_wdf_data[2*DQ_WIDTH-1:0] ⁽²⁾	Input	User input data. It should have the fall data and the rise data. Rise data = app_wdf_data[DQ_WIDTH-1: 0] Fall data = app_wdf_data[2*DQ_WIDTH-1: DQ_WIDTH]
app_wdf_wren ⁽²⁾	Input	Write enable for the user write FIFO. This signal should be synchronized with the app_wdf_data and app_wdf_mask_data signals.
app_wdf_mask_data[2*DM_WIDTH-1: 0] ⁽²⁾	Input	User mask data. It should contain the masking information for both rise and fall data. Rise mask data = app_wdf_mask_data[DM_WIDTH-1: 0] Fall mask data = app_wdf_mask_data[2*DM_WIDTH-1: DM_WIDTH]
app_af_afull ⁽²⁾	Output	Almost Full status of the address FIFO. The user can write 12 more locations into the FIFO after app_af_afull is asserted.
app_wdf_afull ⁽²⁾	Output	Almost Full status of the user write FIFO. The user can write 12 more locations into the FIFO after app_wdf_afull is asserted.
rd_data_fifo_out[2*DQ_WIDTH-1: 0] ⁽²⁾	Output	Read data from the memory. Read data is stored in the user write FIFO.
rd_data_valid ⁽²⁾	Output	Status signal indicating that data read from the memory is available to the user.
clk0_tb	Output	Clock output to the user. All the user input data and commands must be synchronized with this clock. This signal is sourced from clk0 in the controller.

Table 11-4: User Interface Signals (Cont'd)

Signal	Direction ⁽¹⁾	Description
rst0_tb	Output	Active-High reset for the user interface.

Notes:

1. The direction indicated in this table is referenced from the design perspective. For example, input indicates that the signal is input to the design and output for the user.
2. See ["User Interface Accesses," page 449](#) for required timing requirements and restrictions for the user interface signals.
3. Addressing in the Virtex-5 FPGA is linear. That is, the row address bits immediately follow the column address bits, and the bank address bits follow the row address bits, thus supporting more devices. The number of address bits used depends on the density of the memory part. The controller ignores the unused bits, which can all be tied to High.

Table 11-5 lists the signals between the User interface and the controller.

Table 11-5: Signals between User Interface and Controller

Port Name	Port Width	Port Description
af_cmd	3	Output of the Address FIFO in the user interface. Monitors the FIFO full status flag to the write command into the Address FIFO.
af_addr	31	Output of the Address FIFO in the user interface. The mapping of these address bits is: [30:0]: Memory Address (Bank, Row, Column). Monitors the FIFO full status flag to the write address into the Address FIFO.
af_empty	1	The user interface Address FIFO empty status flag output. The user application can write to the Address FIFO when this signal is asserted until the write data FIFO full status flag is asserted. FIFO36 Almost Empty flag.
ctrl_af_rden	1	Read Enable input to Address FIFO in the user interface. This signal is asserted for one clock cycle when the controller state is write or read resulting from dynamic command requests.

Table 11-6: Design Status Signals

Signal	Direction	Description
phy_init_done	Output	Indicates the completion of initialization and calibration of the design.

System Interface Signals

Table 11-7 and Table 11-8 shows the system interface signals for designs with and without a PLL, respectively.

Table 11-7: System Interface Signals with a PLL

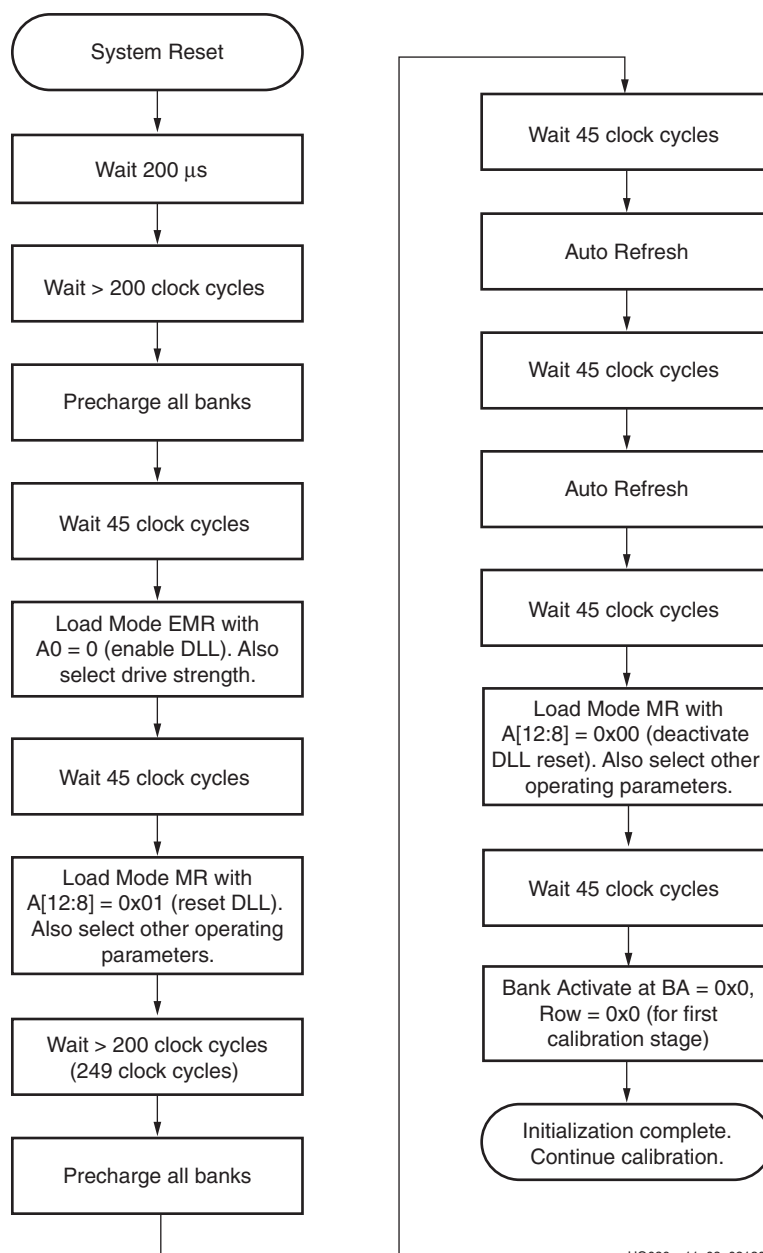
Signal	Direction	Description
sys_clk_p, sys_clk_n	Input	Differential input clocks to the PLL/DCM. The DDR SDRAM controller and memory operate on this clock. This differential input clock pair is present only when the DIFFERENTIAL clocks option is selected in MIG FPGA options page.
sys_clk	Input	Single-ended input clock to the PLL/DCM. The DDR controller and memory operate at this frequency. This input clock is present only when the SINGLE_ENDED clocks option is selected in the MIG FPGA options page.
sys_rst_n	Input	Active-Low reset to the DDR SDRAM controller.
clk200_p, clk200_n	Input	200 MHz differential input clock for the IDELAYCTRL primitive of Virtex-5 FPGA. This differential input clock pair is present only when the DIFFERENTIAL clocks option is selected in MIG FPGA options page.
idly_clk_200	Input	200 MHz single-ended input clock for the IDELAYCTRL primitive of Virtex-5 FPGAs. This input clock is present only when the SINGLE_ENDED clocks option is selected in the MIG FPGA options page.

Table 11-8: System Interface Signals without a PLL

Signal	Direction	Description
clk0	Input	The DDR SDRAM controller and memory operate on this clock.
sys_rst_n	Input	Active-Low reset to the DDR SDRAM controller. This signal is used to generate a synchronous system reset.
clk90	Input	90° phase-shifted clock with the same frequency as clk0.
clk200	Input	200 MHz input differential clock for the IDELAYCTRL primitive of the Virtex-5 FPGA.
locked	Input	The status signal indicating whether the PLL/DCM is locked or not. This signal is used to generate a synchronous system reset.

DDR SDRAM Initialization

DDR memory is initialized through a specified sequence as shown in [Figure 11-10](#). This initialization sequence is in accordance with JEDEC specifications for DDR SDRAMs. The initialization logic is implemented in the physical layer.

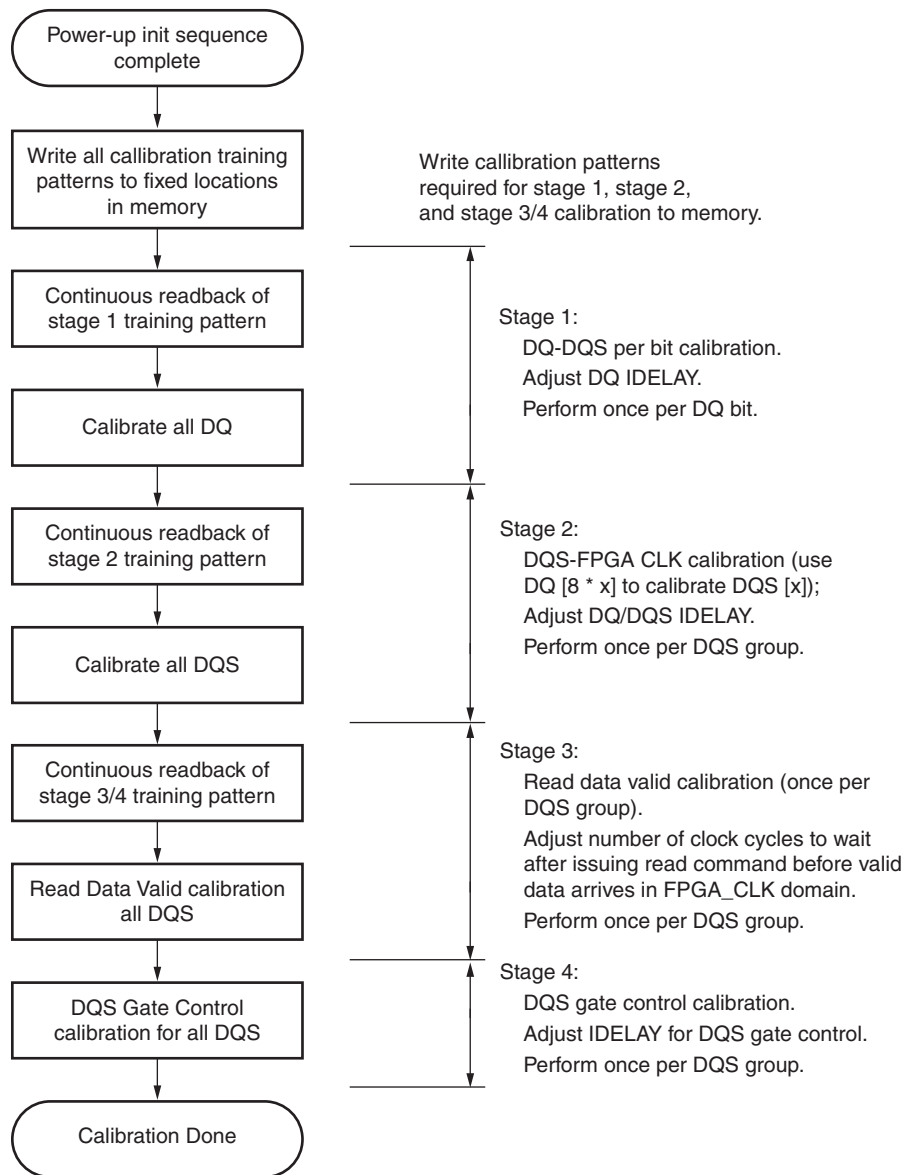


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Figure 11-10: DDR SDRAM Initialization

DDR SDRAM Design Calibration

Before issuing user read and write commands, the design is calibrated to ensure that correct data is captured in the ISERDES primitives of Virtex-5 FPGAs. Calibration logic is implemented in the physical layer of the design. Figure 11-11 shows the overall calibration sequence. For more details on the calibration algorithm for the Virtex-5 FPGA DDR interface, see XAPP851 [Ref 25].



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Figure 11-11: Overall Design Calibration Sequence

The first calibration stage sets the IDELAY value for each DQ (IDELAY for DQS remains at 0 during this time), and is performed even before a phase relationship between DQS and FPGA_CLK has been established. A training pattern of “10” (1 = rising, 0 = falling) is used to calibrate DQ.

The second calibration stage includes calibration between the DQS and the FPGA clock.

The third calibration stage is read-enable calibration, which compensates for the round-trip delay between when the read command is issued by the controller, and the captured read data is valid at the outputs of the ISERDES.

The fourth stage includes calibration of a squelch circuit that gates the input DQS to avoid the glitch that propagates to the second rank of flops in the ISERDES. The glitch occurs when DQS goes from the Low state to the 3-state level after the last edge of the DQS, which might cause a “false” rising and/or falling edge on the DQS input to the FPGA. Unless the DQS glitch is gated after the last DQS falling edge of a read burst, the data registered in the ISERDES might change prematurely. During calibration, an auto-refresh command is issued to memory at intervals depending on the stage of calibration.

After initialization and calibration is done, the controller is signaled to start normal operation of the design. Now, the controller can start issuing user write and read commands to the memory.

User Interface Accesses

The user backend logic communicates with the memory controller through a synchronous FIFO-based user interface. This interface consists of three related buses:

- a command/address FIFO bus accepts write/read commands as well as the corresponding memory address from the user
- a Write Data FIFO bus that accepts the corresponding write data when the user issues a write command on the command/address bus
- a read bus on which the corresponding read data for an issued read command is returned

The user interface has the following timing and signaling restrictions:

1. Commands and write data cannot be written by the user until calibration is complete (as indicated by `phy_init_done`). In addition, the following interface signals need to be held Low until calibration is complete: `app_af_wren`, `app_wdf_wren`, `app_wdf_data[]`, `app_wdf_mask_data[]`. Failure to hold these signals Low causes errors during calibration. This restriction arises from the fact that the Write Data FIFO is also used during calibration to hold the training patterns for the various stages of calibration.
2. When issuing a write command, the first write data word must be written to the Write Data FIFO either prior to, or on the same clock cycle as the when the write command is issued. In addition, the write data must be written by the user over consecutively clock cycles, there cannot be a break in between words. These restrictions arise from the fact that the controller assumes write data is available when it receives the write command from the user.
3. The output of the Read Data FIFO (specifically, the `rd_data_fifo_out` and `rd_data_valid` signals) are synchronous to `clk90`, and not to `clk0`. The user might need to insert an extra pipeline stage to resynchronize the data to `clk0` if place-and-route timing cannot be met on these 3/4 cycle paths.
4. The `clk0_tb` signal is connected to `clk0` in the controller. If the user clock domain is different from `clk0` / `clk0_tb` of MIG, the user should add FIFOs for all data inputs and outputs of the controller in order to synchronize them to the `clk0_tb`.

Write Interface

Figure 11-12 shows the user interface block diagram for write operations.

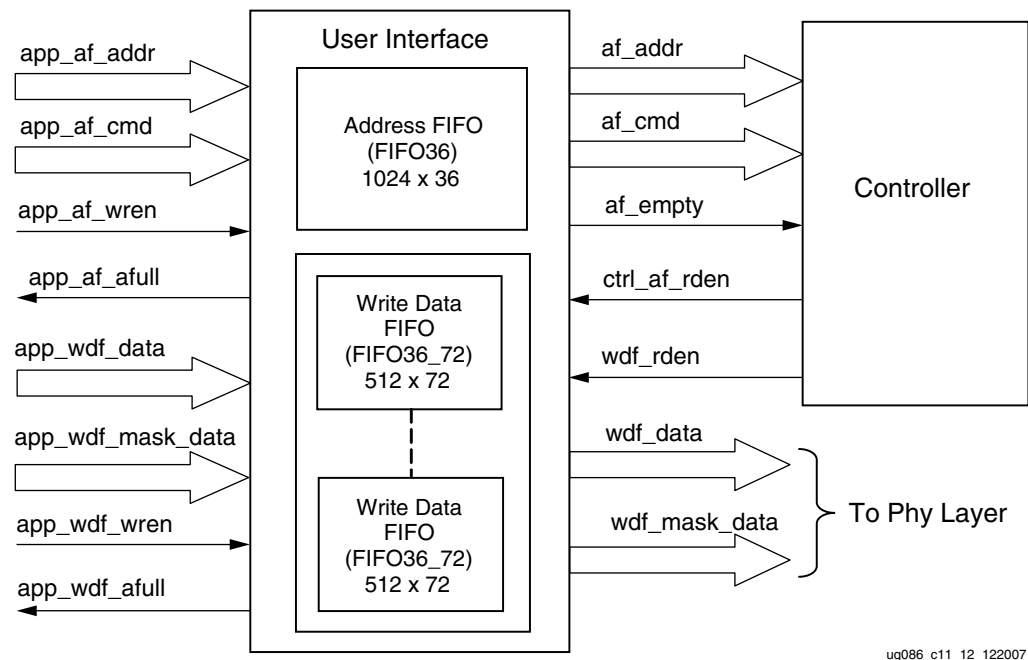


Figure 11-12: User Interface Block Diagram for Write Operations

The following steps describe the architecture of the Address and Write Data FIFOs and show how to perform a write burst operation to DDR SDRAM from the user interface.

1. The user interface consists of an Address FIFO and a Write Data FIFO. The Write Data FIFO is constructed using Virtex-5 FPGA FIFO36_72 primitive with a 512 x 72 configuration. The 72-bit architecture comprises one 64-bit port and one 8-bit port. For Write Data FIFOs, the 64-bit port is used for data bits and the 8-bit port is used for mask bits. Mask bits are available only when supported by the memory part and when the Data Mask is enabled in the MIG GUI. Some memory parts, such as Registered DIMMs of x4 parts, do not support mask bits.
2. The Address FIFO is constructed using Virtex-5 FPGA FIFO36 primitive with a 1024 x 36 configuration. The 36-bit architecture comprises one 32-bit port and one 4-bit port. The 32-bit port is used for addresses (app_af_addr), and the 4-bit port is used for commands (app_af_cmd).
3. The Address FIFO is common for both Write and Read commands. It comprises an address part and the command part. Command bits discriminate between write and read commands.
4. The user interface data width app_wdf_data is twice that of the memory data width. For an 8-bit memory width, the user interface is 16 bits consisting of rising edge data and falling edge data. For every 8 bits of data, there is a mask bit. For 72-bit memory data, the user interface data width app_wdf_data is 144 bits, and the mask data app_wdf_mask_data is 18 bits.
5. The minimum configuration of the Write Data FIFO is 512 x 72 for a memory data width of 8 bits. For an 8-bit memory data width, the least-significant 16 bits of the data port are used for write data and the least-significant two bits of the 8-bit port are used

for mask bits. The controller internally pads all zeros for the most-significant 48 bits of the 64-bit port and the most-significant six bits of the 8-bit port.

6. Depending on the memory data width, MIG instantiates multiple FIFO36_72s to gain the required width. For designs using 8-bit to 32-bit data width, one FIFO36_72 is instantiated; for 72-bit data width, a total of three FIFO36_72s are instantiated. The bit architecture comprises 32 bits of rising-edge data, 4 bits of rising-edge mask, 32 bits of falling-edge data, and 4 bits of falling-edge mask, which are all stored in a FIFO36_72. MIG routes the `app_wdf_data` and `app_wdf_mask_data` to FIFO36_72s accordingly.
7. The user can initiate a write to memory by writing to the Address FIFO and the Write Data FIFO when FIFO full flags are deasserted. Status signal `app_af_full` is asserted when the Address FIFO is full; similarly, `app_wdf_full` is asserted when Write Data FIFO is full.
8. At power-on, both Address FIFO and Write Data FIFO full flags are deasserted.
9. The user should assert Address FIFO write enable signal `app_af_wren` along with address `app_af_addr` and command `app_af_cmd` to store the address and command into Address FIFO.
10. The user data should be synchronized to the `clk_tb` clock. Data FIFO write-enable signal `app_wdf_wren` should be asserted to store write data `app_wdf_data` and mask data `app_wdf_mask_data` into the Write Data FIFOs. Rising-edge and falling-edge data should be provided together for each write to the Data FIFO. The Virtex-5 FPGA DDR SDRAM controller design supports byte-wise masking of data only.
11. The write command should be given by keeping `app_af_cmd = 3'b000` and asserting `app_af_wren`. Address information is given on the `app_af_addr` signal. Address and command information is written into the User Address FIFO.
12. After the completion of the initialization and calibration process and when the User Address FIFO empty signal is deasserted, the controller reads the command and address FIFO and issues a write command to the DDR SDRAM.

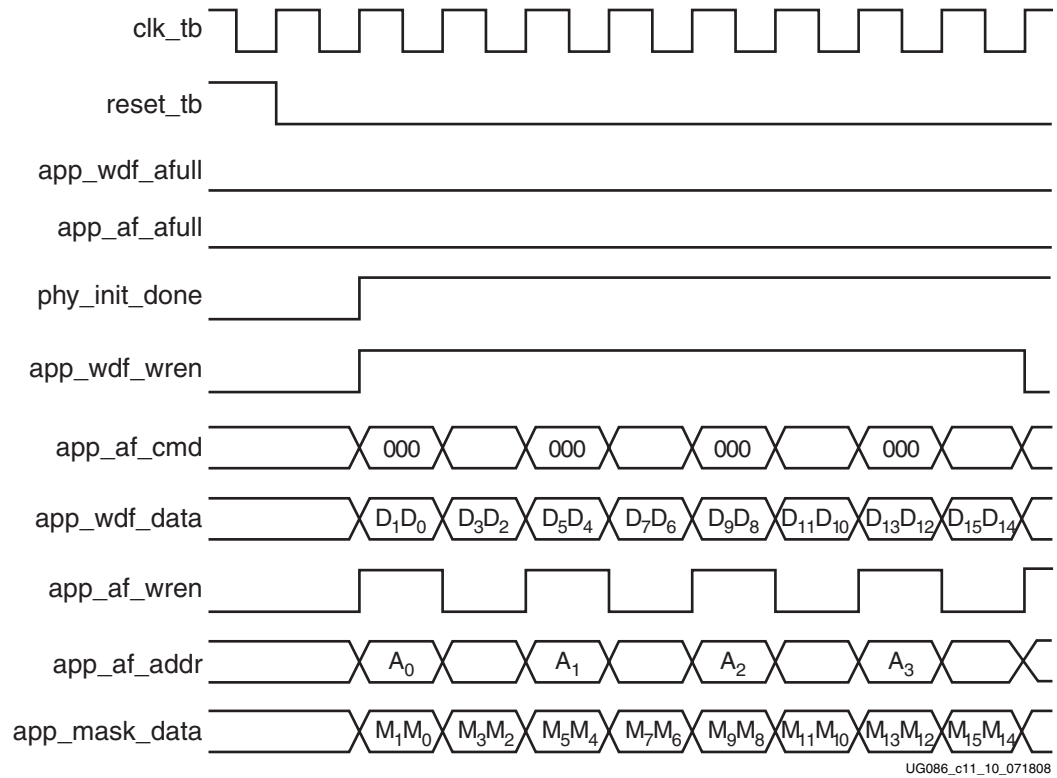


Figure 11-13: DDR SDRAM Write Burst for Four Bursts (BL = 4)

13. The write timing diagram in Figure 11-13 is derived from the MIG-generated testbench for a burst length of four (BL = 4). As shown, each write to Address FIFO should have two writes to the Data FIFO. The phy_init_done signal indicates memory initialization and calibration completion.

Read Interface

Figure 11-14 shows the block diagram of the read interface.

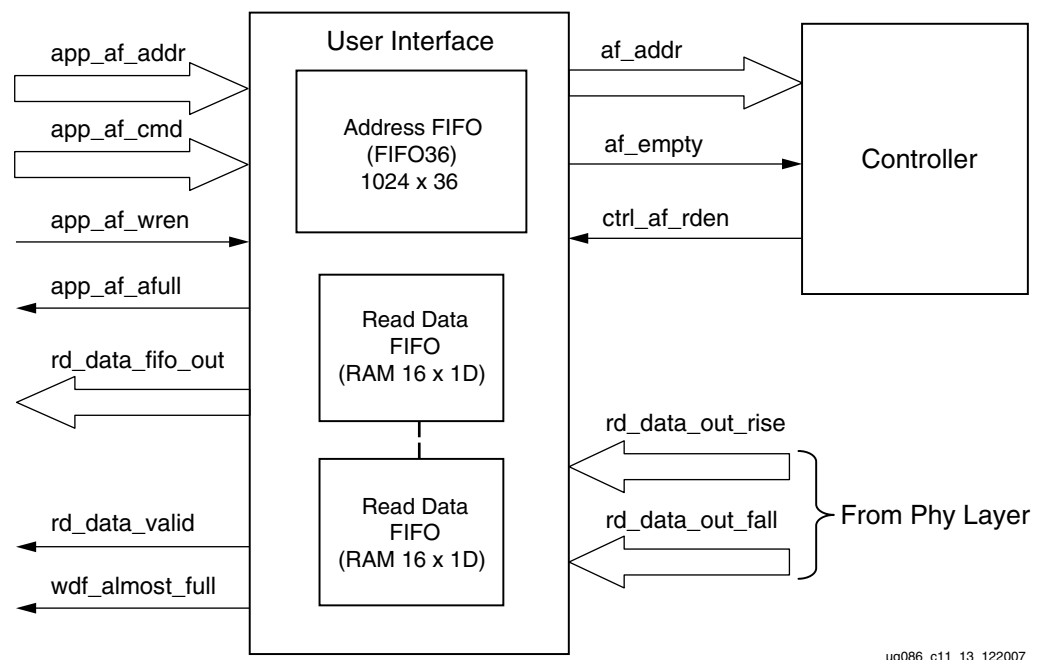
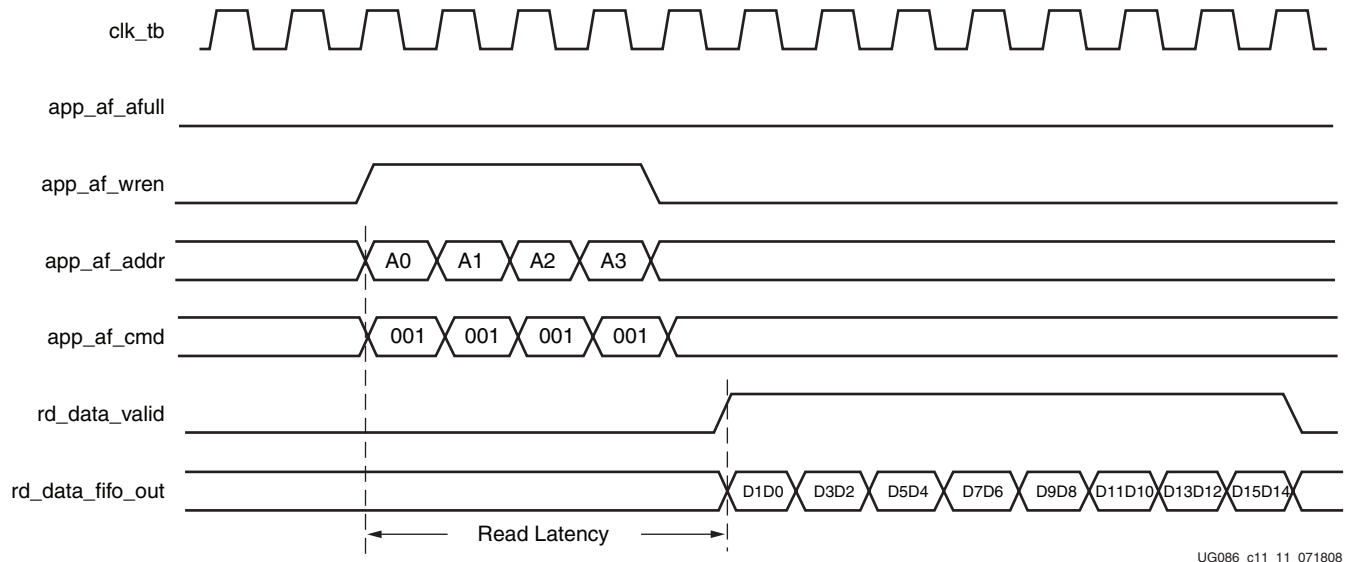


Figure 11-14: User Interface Block Diagram for Read Operation

The following steps describe the architecture of the Read Data FIFO and show how to perform a read burst operation from DDR SDRAM from the user interface.

1. The read user interface consists of an Address FIFO and a Read Data FIFO. The Address FIFO is common between reads and writes. The Read Data FIFO is built out of Distributed RAMs of 16 x 1 configuration. MIG instantiates the number of RAM16Ds depending on the data width. For example, for 8-bit data width, MIG instantiates a total of 16 RAM16X1Ds, 8 for rising-edge data and 8 for falling-edge data. Similarly, for 72-bit data width, MIG instantiates a total of 144 RAM16Ds, 72 for rising-edge data and 72 for falling-edge data.
2. The user can initiate a read to memory by writing to the Address FIFO when the FIFO full flag `app_af_full` is deasserted.
3. To write the read address and read command into the Address FIFO, the Address FIFO write enable signal `app_af_wren` should be issued, along with the memory read address `app_af_addr` and `app_af_cmd` commands (set to 001 for a read command).
4. The controller reads the Address FIFO and generates the appropriate control signals to memory. After decoding `app_af_cmd`, the controller issues a read command to the memory at the specified address.
5. Prior to the actual read and write commands, the design calibrates the latency in number of clock cycles from the time the read command is issued to the time the data is received. Using this precalibrated delay information, the controller stores the read data in Read Data FIFOs.
6. The `rd_data_valid` signal is asserted when data is available in the Read Data FIFOs.
7. When calibration is completed, the controller generates the control signals to capture the read data from the FIFO according to the CAS latency selected by the user. The

rd_data_valid signal is asserted when the read data is available to the user, and rd_data_fifo_out is the read data from the memory to the user.



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Figure 11-15: DDR SDRAM Read Burst for Four Bursts (BL = 4)

8. Figure 11-15 shows the user interface timing diagram for a read command, burst length of four.

Read latency is defined as the time between when the read command is written to the user interface bus until when the corresponding first piece of data is available on the user interface bus (see Figure 11-15).

When benchmarking read latencies, it is important to specify the exact conditions under which the measurement occurs.

Read latency varies based on the following parameters:

- Number of commands already in the FIFO pipeline before the read command is issued
- Whether an ACTIVATE command needs to be issued to open the new bank/row
- Whether a PRECHARGE command needs to be issued to close a previously opened bank
- Specific timing parameters for the memory, such as T_{RAS} and T_{RCD} in conjunction with the bus clock frequency
- Commands can be interrupted, and banks/rows can forcibly be closed when the periodic AUTO REFRESH command is issued
- CAS latency
- Board-level and chip-level (for both memory and FPGA) propagation delays

Table 11-9 and Table 11-10 show read latencies for the Virtex-5 FPGA DDR interface for two different conditions. Table 11-9 shows the case where a row activate is not required prior to issuing a read command on the DDR bus. This situation is possible, for example, when bank management is enabled, and the read targets an already opened bank. Table 11-10 shows the case when a read results in a bank/row conflict. In this case, a precharge of the previous row must be followed by an activation of the new row, which increases read latency. Other specific conditions are noted in the footnotes for each table.

Table 11-9: Read Latency without Precharge and Activate

Parameter	Number of Clock Cycles
User READ command to empty signal deassertion (using FIFO36)	5 clocks
Empty signal to READ command on DDR bus	4.5 clocks
READ command to read valid assertion	11.5 clocks
Total	21 clocks

Notes:

1. Test conditions: Clock frequency = 200 MHz, CAS latency = 3, DDR -5 speed grade device.
2. Access conditions: Read to an already open bank/row is issued to an empty control/address FIFO.
3. Some entries have fractional clock cycles because the inverted version of CLK0 is used to drive the DDR memory.
4. The Virtex-5 FPGA DDR interface uses a FIFO36 for the address/control FIFO. It is possible to shorten the READ command to empty signal deassertion latency by implementing the FIFO as a distributed RAM FIFO or removing the FIFO altogether, as the application requires.

Table 11-10: Read Latency with Precharge and Activate

Parameter	Number of Clock Cycles
User READ command to empty signal deassertion (using FIFO36)	5 clocks
Empty signal to PRECHARGE command on DDR bus	4.5 clocks
PRECHARGE to ACTIVE command to DDR memory	3 clocks
ACTIVE to READ command to DDR memory	4 clocks
READ command to read valid assertion	11.5 clocks
Total	28 clocks

Notes:

1. Test conditions: Clock frequency = 200 MHz, CAS latency = 3, DDR -5 speed grade device.
2. Access conditions: Read that results in a bank/row conflict is issued to an empty control/address FIFO. This requires that the previous bank/row be closed first.
3. Some entries have fractional clock cycles because the inverted version of CLK0 is used to drive the DDR memory.
4. The Virtex-5 DDR interface uses a FIFO36 for the address/control FIFO. It is possible to shorten the READ command to empty signal deassertion latency by implementing the FIFO as a distributed RAM FIFO or removing the FIFO altogether, as the application requires.

DDR SDRAM Signal Allocations

MIG allows banks to be selected for different classes of memory signals. Table 11-11 shows the list of signals allocated in a group from bank selection checkboxes.

Table 11-11: DDR SDRAM Signal Allocations

Bank Selected	Signals Allocated in the Group
Address	Memory address, memory control, and memory clock signals
Data	Data, data mask, and data strobes

Table 11-11: DDR SDRAM Signal Allocations (Cont'd)

Bank Selected	Signals Allocated in the Group
System Control	System reset from user interface and status signals
System Clock	System clocks from the user interface

Note: Timing has been verified for most of the MIG generated configurations. For the best timing results, adjacent banks in the same column of the FPGA should be used. Banks that are separated by unbonded banks should be avoided because these can cause timing violations.

Supported Devices

The design generated by MIG is independent of the memory package; therefore, the package part of the memory component is replaced with XX, where XX indicates a “don't care” condition. The tables below list the components (Table 11-12) and DIMMs (Table 11-13 through Table 11-15) supported by MIG for DDR SDRAM. See Appendix G, “Low Power Options.”

Table 11-12: Supported Components for DDR SDRAM (Virtex-5 FPGAs)

Components	Packages (XX)	Components	Packages (XX)
MT46V32M4XX-75	P,TG	MT46V32M4XX-5B	-
MT46V64M4XX-75	FG,P,TG	MT46V64M4XX-5B	BG,FG,P,TG
MT46V128M4XX-75	BN,FN,P,TG	MT46V128M4XX-5B	BN,FN,P,TG
MT46V256M4XX-75	P,TG	MT46V256M4XX-5B	P,TG
MT46V16M8XX-75	P,TG	MT46V16M8XX-5B	TG,P
MT46V32M8XX-75	FG,P,TG	MT46V32M8XX-5B	BG,FG,P,TG
MT46V64M8XX-75	BN,FN,P,TG	MT46V64M8XX-5B	BN,FN,P,TG
MT46V128M8XX-75	P,TG	MT46V128M8XX-5B	-
MT46V8M16XX-75	P,TG	MT46V8M16XX-5B	TG,P
MT46V16M16XX-75	BG,FG,P,TG	MT46V16M16XX-5B	BG,FG,P,TG
MT46V32M16XX-75	-	MT46V32M16XX-5B	BN,FN,P,TG
MT46V64M16XX-75	P,TG	MT46V64M16XX-5B	-

Table 11-13: Supported Unbuffered DIMMs for DDR SDRAM (Virtex-5 FPGAs)

Unbuffered DIMMs	Packages (X)	Unbuffered DIMMs	Packages (X)
MT4VDDT1664AX-40B	G,Y	MT8VDDT3264AX-40B	G,Y
MT4VDDT3264AX-40B	G,Y	MT9VDDT3272AX-40B	Y

Table 11-14: Supported Registered DIMMs for DDR SDRAM (Virtex-5 FPGAs)

Registered DIMMs	Packages (X)	Registered DIMMs	Packages (X)
MT9VDDF3272X-40B	G,Y	MT18VDDF6472X-40B	G,Y
MT9VDDF6472X-40B	G,Y	MT18VDDF12872X-40B	G,Y

Table 11-15: Supported SODIMMs for DDR SDRAM (Virtex-5 FPGAs)

SODIMMs	Packages (X)	SODIMMs	Packages (X)
MT4VDDT3264HX-40B	G,Y	MT9VDDT3272HX-40B	-
MT4VDDT1664HX-40B	Y	MT9VDDT6472HX-40B	G,Y
MT8VDDT3264HX-40B	-	MT9VDDT12872HX-40B	-
MT8VDDT6464HX-40B	G,Y		

Simulating a DDR SDRAM Design

After generating the design, MIG creates a `sim` folder in the specified path. This folder contains simulation files for a particular design. The `sim` folder contains the external testbench, memory model, and `.do` file to simulate the generated design. The memory model files are currently generated in Verilog only. To learn more details about the files in the `sim` folder and to simulate the design, refer to “[Simulation Guide](#),” page 499.

For single-rank DIMMs, MIG outputs only the base part memory model. In the simulation testbench (`sim_tb_top` in the `sim` folder), MIG instantiates the required number of memory models. For example, a 1 GB single-rank DIMM with the base part is 1 Gb, and MIG instantiates the base model eight times. If the MIG generated memory model is to be used with the user’s test bench, multiple instances should be used based on the selected configuration.

The MIG output memory model considers the `part_mem_bits` parameter by default for memory range allocation. This covers only a partial memory range, i.e., $2^{\text{part_mem_bits}}$. To allocate the full memory range, the `FULL_MEM` parameter should be set in the memory model, which in turn sets the `full_mem_bits` parameter for memory allocation. Allocating the full memory range might exceed the memory of the operating system, thus causing memory allocation failure in simulations.

Changing the Refresh Rate

The top-level parameter `TREFI_NS` should be changed to the selected refresh interval in ns. For example, to change the refresh rate to 3.9 μ s, `TREFI_NS` should be set to 3900. The controller issues a refresh approximately every $(\text{TREFI_NS} \times 1000) / \text{CLK_PERIOD}$ clock cycles, where `CLK_PERIOD` is the top-level parameter defining the clock period in terms of ps. If the value in the formula exceeds 4095, the `refi_cnt_r` signal in the CTRL module must be manually increased beyond 12 bits.

The CKE counter is a down-counter that is used to set the refresh interval, and its value is initialized to all ones during reset. To change `TREFI_NS`, `cke_200us_cnt_r` in the `ddr2_phy_init` HDL file must also be modified. This ensures that the 200 μ s initialization time is preserved. Bits must be added or removed based on the change made to the refresh interval.

Hardware Tested Configurations

The frequencies shown in [Table 11-16](#) were achieved on the Virtex-5 FPGA ML561 Memory Interfaces Development Board under nominal conditions. This frequency should not be used to determine the maximum design frequency. The maximum design frequency supported in the MIG wizard is based a combination of the TRCE results for fabric timing

on multiple device/package combinations and I/O timing analysis using FPGA and memory timing parameters for a 64-bit wide interface.

Table 11-16: Hardware Tested Configurations

Synthesis Tools	XST and Synplicity
HDL	Verilog and VHDL
FPGA Device	XC5VLX50T-FF1136-2
Burst Lengths	2, 4, 8
CAS Latency (CL)	2, 2.5, 3
32-bit Design	Tested on 16-bit Component "MT46V32M16XX-5B"
Component, CL=2	110 MHz to 170 MHz
Component, CL=2.5	110 MHz to 210 MHz
Component, CL=3	110 MHz to 250 MHz

Implementing DDRII SRAM Controllers

This chapter describes how to implement DDRII SRAM interfaces for Virtex®-5 FPGAs generated by MIG.

Feature Summary

This section summarizes the supported and unsupported features of DDRII SRAM controller design.

Supported Features

The DDRII SRAM controller design supports the following:

- A maximum frequency of 300 MHz
- 9-bit, 18-bit, 36-bit, and 72-bit data widths
- CIO and SIO controller designs
- Burst lengths of two and four
- Programmable read-followed-by-write latency
- Linear/burst increment of address bits
- Implemented using different Virtex-5 devices
- Support for DCI cascading
- Support for debug signals
- Operating with 9-bit, 18-bit and 36-bit memory parts
- Verilog and VHDL
- With and without a testbench
- With and without a PLL

Design Frequency Ranges

Table 12-1: Design Frequency Range in MHz

Memory	FPGA Speed Grade					
	-1		-2		-3	
	Min	Max	Min	Max	Min	Max
Component	120	250	120	300	120	300

Architecture

Figure 12-1 shows a top-level block diagram of the DDRII SRAM controller. One side of the DDRII SRAM memory controller connects to the user interface denoted as User Interface. The other side of the controller interfaces to DDRII SRAM memory. The memory interface data width is selectable from MIG.

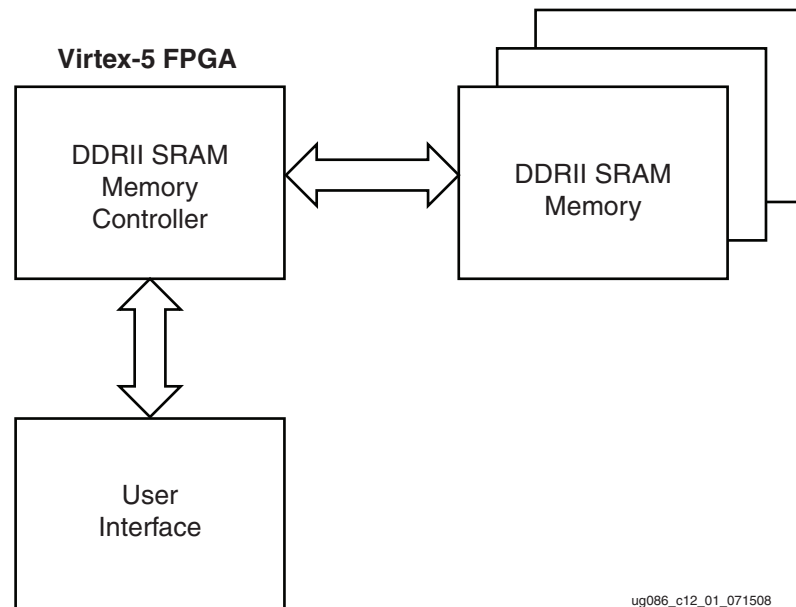


Figure 12-1: **DDRII SRAM Memory Controller**

Both common I/O (CIO) and separate I/O (SIO) DDRII SRAM designs are supported by MIG. SIO designs having independent read and write ports eliminate the need for high-speed bus turnaround.

Read and write addresses are latched on positive edges of the input clock K. A common address bus is used to access the addresses for both read and write operations.

Interface Model

DDRII SRAM interfaces are source-synchronous and double data rate. They transfer data on both edges of the clock cycle. A memory interface has many advantages. It allows designs to be ported easily and also makes it possible to share parts of the design across different types of memory interfaces.

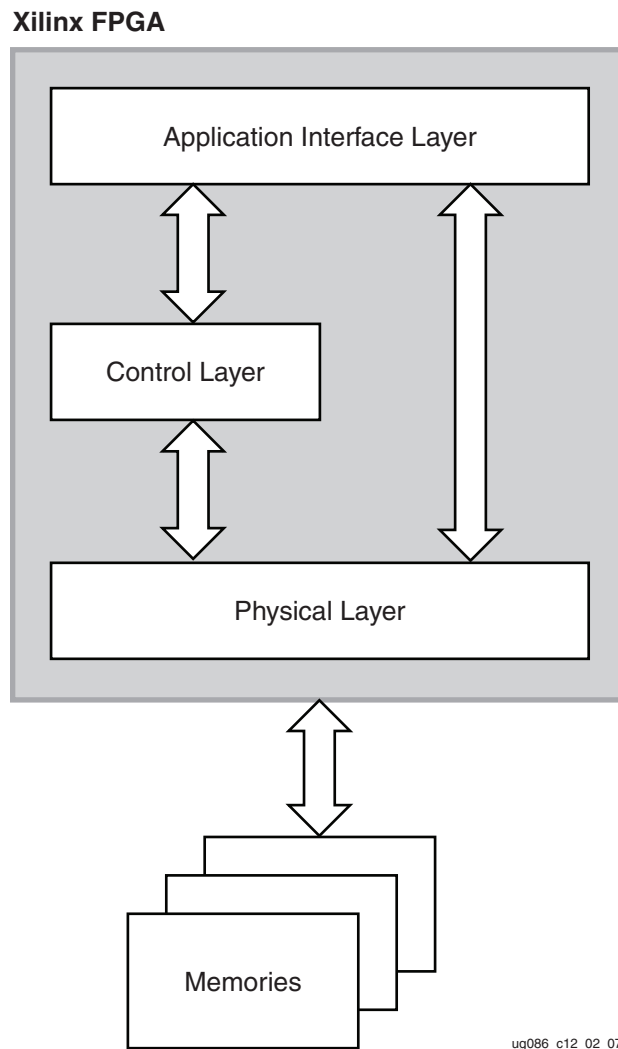


Figure 12-2: Modular Memory Interface Representation Diagram

Figure 12-2 shows the modular memory interface representation diagram. The application interface layer creates the user interface, which initiates memory writes and reads by writing data and memory addresses to the User Interface FIFOs.

The control layer comprises:

- Clocks and reset generation logic
- Datapath logic
- Control logic

Clocks and reset generation logic constitute a PLL/DCM primitive, which derives different phase-shifted versions of the user-supplied differential clocks (`sys_clk_p` and `sys_clk_n`). These phase-shifted versions of clocks run throughout the controller design. A 200 MHz user-supplied differential clock is used for the IDELAYCTRL elements. Reset signals are generated for different clock domains using the user-supplied reset signals (`sys_rst_n`), the locked signal, and the IDELAYCTRL ready signal (`idelay_ctrl_ready`).

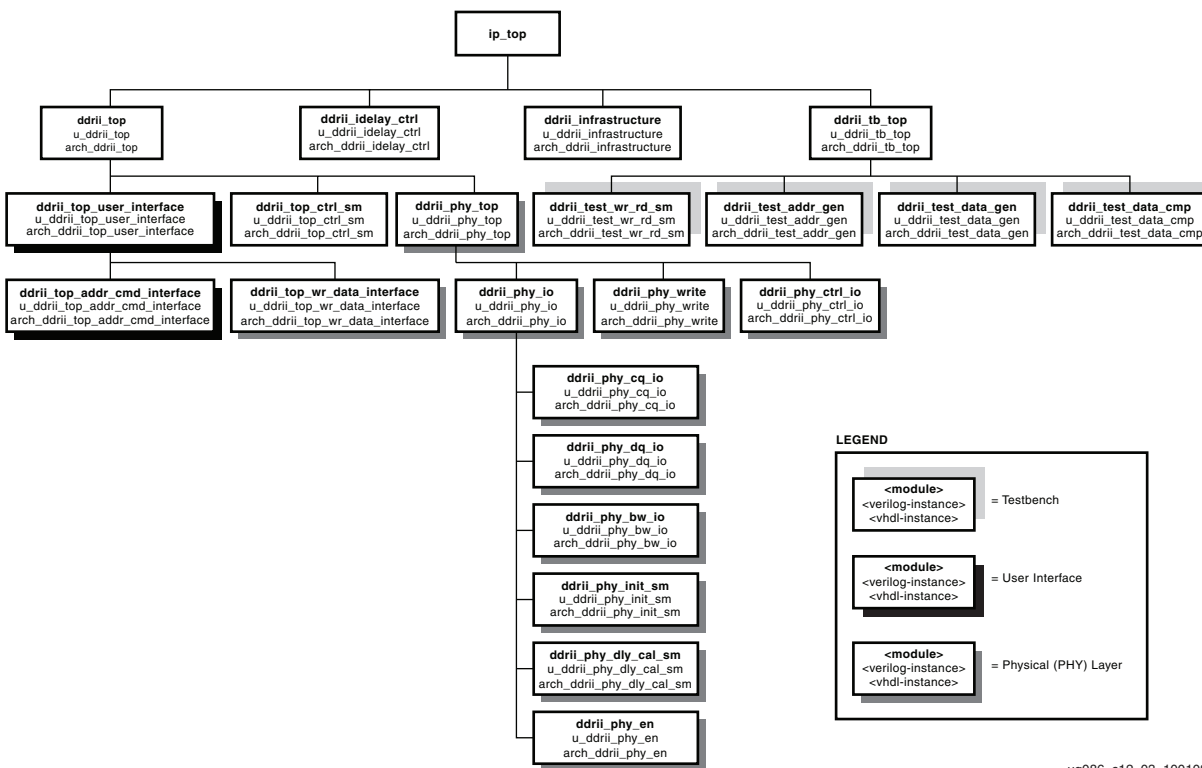
The Datapath logic consists of memory write clocks, the read clocks and the data write generation logic.

The Control logic constitutes read/write command generation logic, depending on the status signals of the User Interface FIFO.

The previously mentioned logic interfaces with memory through IDDRs, ODDRs, OFLOPS, ISERDES elements, and so on, which are associated with the physical layer. The read data capturing logic is also associated with the physical layer.

Hierarchy

Figure 12-3 shows the hierarchical structure of the DDRII SRAM design generated by MIG with a testbench and a PLL.



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Figure 12-3: Hierarchical Structure of the Virtex-5 FPGA DDRII SRAM

The modules are classified as follows:

- Design modules
- Testbench modules
- Clocks and reset generation modules

MIG can generate four different DDRII SRAM designs:

- With a testbench and a PLL
- Without a testbench and with a PLL
- With a testbench and without a PLL
- Without a testbench and without a PLL

MIG outputs both an `example_design` and a `user_design`. The MIG generated `example_design` includes the entire memory controller design along with a synthesized test bench (example user application). This testbench generates sample writes and reads and then uses comparison logic to verify the data patterns written are the same received. This `example_design` can be used to test functionality both in simulation and in hardware. The `user_design` includes the memory controller design only. This design allows users to connect the MIG memory controller design to a user developed testbench (user application). Refer to Table 12-4 for user interface signals, the “User Interface Accesses” for timing restriction on user interface signals.

For designs without a testbench (`user_design`), testbench modules are not present in the design. The `<top_module>` (top level) module has the user interface signals for designs without a testbench. The list of user interface signals is provided in [Table 12-4](#).

Design clock and resets are generated in the infrastructure module. The PLL/DCM clock is instantiated in the infrastructure module for designs with a PLL. The inputs to this module are the differential design clock and a 200 MHz differential clock for the IDELAYCTRL module. A user reset is also input to this module. Using the input clocks and reset signal, system clocks and system reset signals are generated in this module, which are used in the design.

The PLL/DCM primitive is not instantiated in this module if the PLL option is not selected. So, the system operates on the user-provided clocks. The system reset signals are generated in the infrastructure module using the locked input signal, the input reset signal, and the IDELAYCTRL ready signal (`idelay_ctrl_ready`). For more information on the clocking structure, refer to “[Clocking Scheme](#),” page 480.

MIG Design Options

MIG provides various options to generate the design with or without a PLL. MIG always generates two design folders, one with a testbench and the other without a testbench. This selection provides detailed descriptions of the type of the design generated by the user using various options.

[Figure 12-4](#) shows a top-level block diagram of a DDRII SRAM design with a PLL and a testbench. The `sys_clk_p` and `sys_clk_n` pair are differential input system clocks. “[Clocking Scheme](#),” page 480 describes how various clocks are generated using the PLL. The PLL/DCM is instantiated in the infrastructure module that generates the required design clocks. `dly_clk_200_p` and `dly_clk_200_n` are used for the IDELAYCTRL element. `Sys_rst_n` is an active-Low system reset signal. All design resets are generated using this system reset signal, the locked signal, and the IDELAYCTRL ready signal (`idelay_ctrl_ready`). The error output signal `compare_error` indicates whether the case passes or fails. The testbench module generates write and read address, write and read commands, write data to the controller. It also compares the read data with written data. The error signal is driven high on the data mismatches. The `cal_done` signal indicates the completion of initialization and calibration of the design.

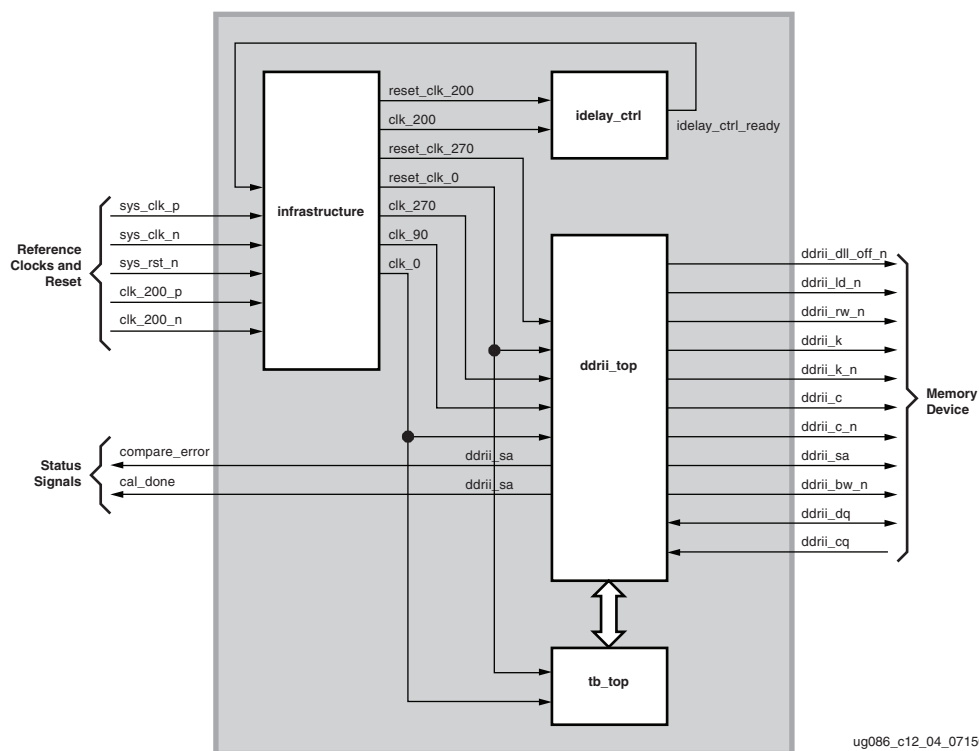


Figure 12-4: Top-Level Block Diagram of the DDRII SRAM Design with a PLL and a Testbench

Figure 12-5 shows a top-level block diagram of a DDRII SRAM design with a PLL but without a testbench. The `sys_clk_p` and `sys_clk_n` pair are differential input system clocks. “Clocking Scheme,” page 480 describes how various clocks are generated using the PLL. The PLL/DCM is instantiated in the `infrastructure` module that generates the required design clocks. `dly_clk_200_p` and `dly_clk_200_n` are used for the `IDELAYCTRL` element. `Sys_rst_n` is an active-Low system reset signal. All design resets are generated using this system reset signal, the locked signal, and the `IDELAYCTRL` ready signal (`idelay_ctrl_ready`). User has to drive the user application signals. The design provides the `clk_0_tb` and `reset_clk_0_tb` signals to the user in order to synchronize with the design. The signal `clk_0_tb` is connected to clock `clk_0` in the controller. If the user clock domain is different from `clk_0/clk_0_tb`, the user should add FIFOs for all the input and outputs of the controller (user application signals), in order to synchronize them to `clk_0_tb` clock. The `cal_done` signal indicates the completion of initialization and calibration of the design.

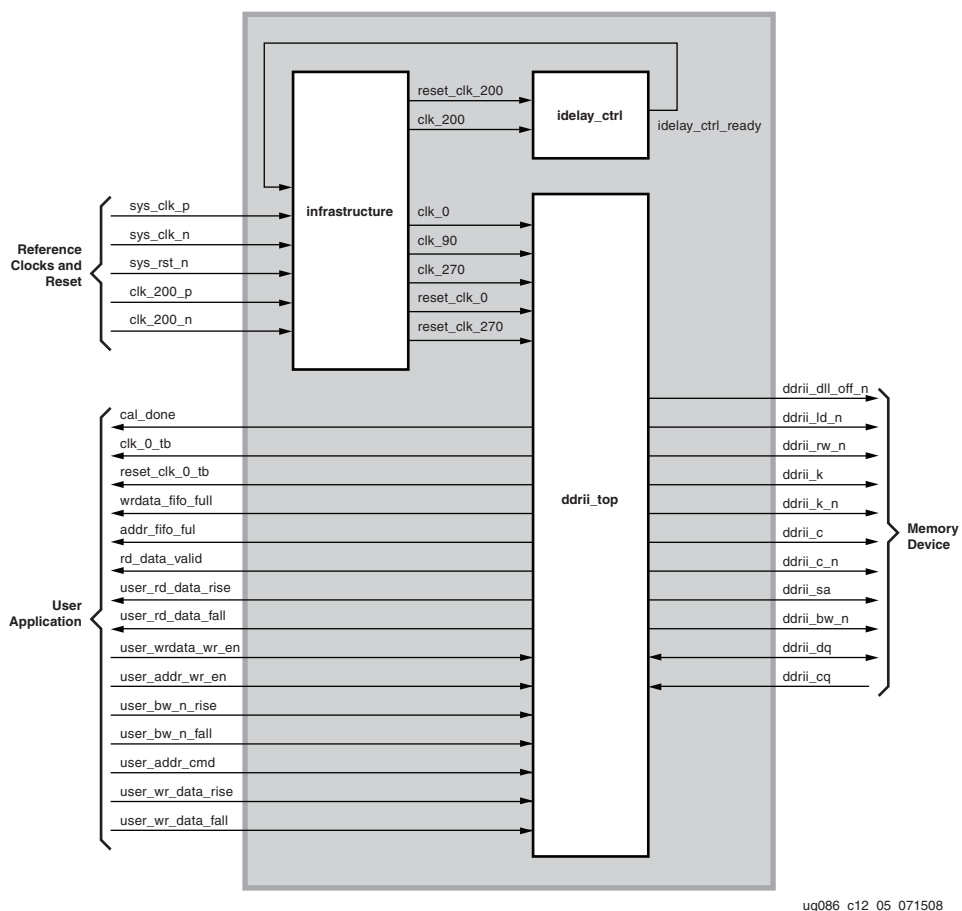


Figure 12-5: Top-Level Block Diagram of the DDRII SRAM Design with a PLL and without a Testbench

Figure 12-6 shows a top-level block diagram of a DDRII SRAM design without a PLL but with a testbench. User should provide all the clocks and the locked signal. “Clocking Scheme,” page 480 describes how to generate the design clocks from the user interface. These clocks should be single-ended. The sys_rst_n signal is an active-Low system reset. All design resets are generated using this system reset signal, locked signal, and the IDELAYCTRL ready signal (idelay_ctrl_ready). The user application must have a PLL/DCM primitive instantiated in the design, and all user clocks should be driven through BUFPGs. The error output signal compare_error indicates whether the case passes or fails. The testbench module generates write and read address, write and read commands, write data to the controller. It also compares the read data with written data. The error signal is driven high on the data mismatches. The cal_done signal indicates the completion of initialization and calibration of the design.

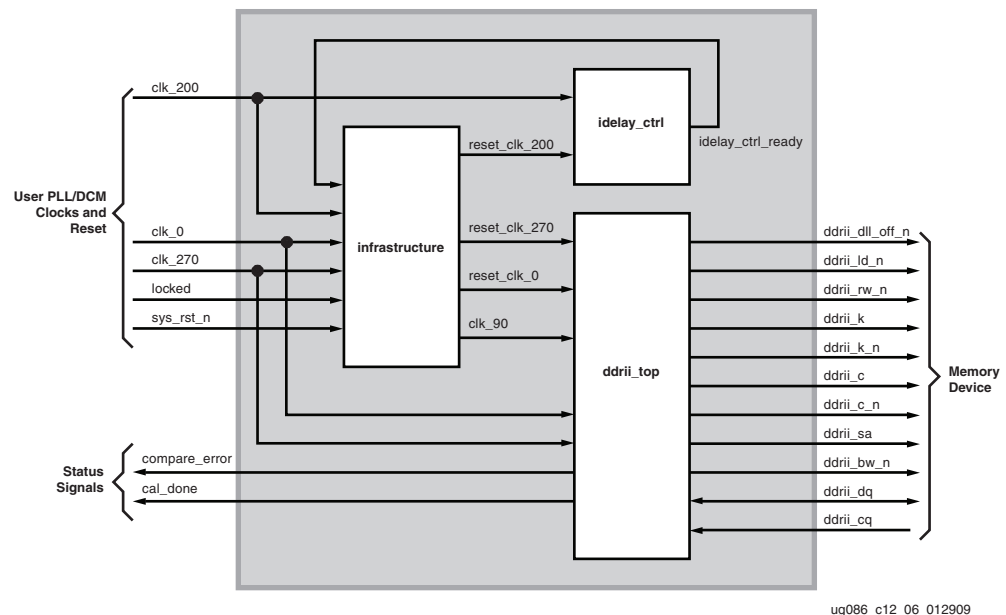


Figure 12-6: Top-Level Block Diagram of the DDRII SRAM Design without a PLL but with a Testbench

Figure 12-7 shows a top-level block diagram of a DDRII SRAM design without a PLL or a testbench. Users should provide all the clocks and the locked signal. “[Clocking Scheme,](#)” [page 480](#) describes how to generate the design clocks from the user interface. These clocks should be single-ended. The `sys_rst_n` signal is an active-Low system reset. All design resets are generated using this system reset signal, the locked signal, and the IDELAYCTRL ready signal (`idelay_ctrl_ready`). The user application must have a PLL/DCM primitive instantiated in the design, and all user clocks should be driven through BUFPGs. The user has to drive the user application signals. The design provides the `clk_0_tb` and `reset_clk_0_tb` signals to the user in order to synchronize with the design. The signal `clk_0_tb` is connected to clock `clk_0` in the controller. If the user clock domain is different from `clk_0/clk_0_tb`, the user should add FIFOs for all the input and outputs of the controller (user application signals), in order to synchronize them to `clk_0_tb` clock. The `cal_done` signal indicates the completion of initialization and calibration of the design.

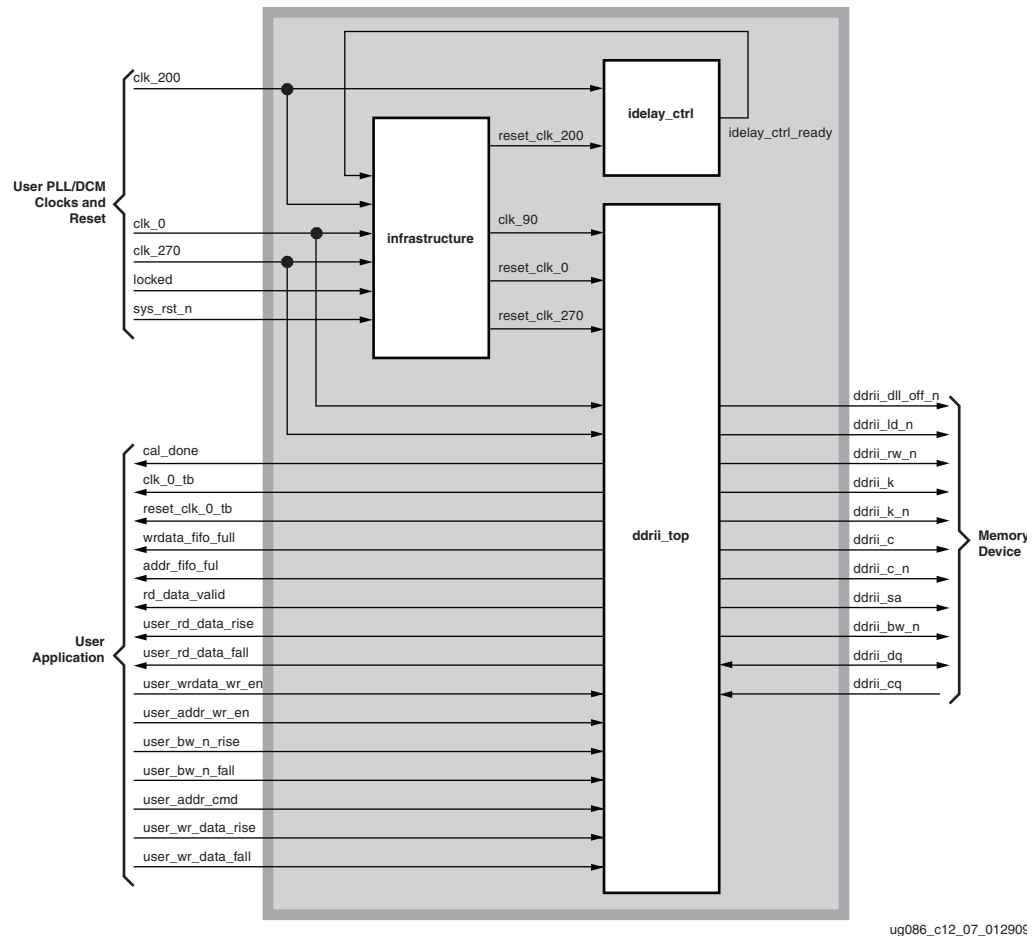


Figure 12-7: Top-Level Block Diagram of the DDRII SRAM Design without a PLL or a Testbench

Implemented Features

This section provides details on the supported features of the DDRII SRAM controller.

CIO/SIO

The DDRII SRAM memory controller supports both Common I/O (CIO) and Separate I/O (SIO) memory parts. MIG provides an option to select the required memory parts. CIO memory parts have support for Burst Lengths 2 and 4, whereas SIO memory parts have support only for Burst Length 2.

The memory type of the design generated using MIG is represented by a parameter `IO_TYPE` in the design top RTL module. This parameter value can be either SIO or CIO in the design top RTL module depending on the type of memory selected in MIG memory controller options.

DDRII SRAM memory controller design RTL modules are generic, which means to say that all the ports and logic related to both the memory types i.e., SIO and CIO (namely `ddrii_dq`-CIO port and `ddrii_d`, `ddrii_q`-SIO ports) are present in all RTL modules all the way up to the design top RTL module. When design is generated using MIG, depending on the type of memory selected in the memory controller options, the design top RTL module contains the parameter `IO_TYPE` value and the selected memory type ports.

Example: If the selected memory is a CIO part, then the design top RTL module has the parameter `IO_TYPE = CIO` and the `ddrii_dq` port.

User can change the memory type from SIO to CIO and vice-versa, with a considerable amount of design top RTL module and UCF modifications. Apart from changing the parameter value `IO_TYPE`, appropriated memory ports should also be added, and the unnecessary ports should either be connected to ground or left unconnected.

Example: If the parameter `IO_TYPE` value is changed from CIO to SIO in the design top RTL module, then the design top RTL module port list must have the ports `ddrii_d` and `ddrii_q`. The port `ddrii_dq` should be removed. The `ddrii_top` module instantiation in the design top RTL module must have the signals `ddrii_d` and `ddrii_q` port mapped. User must also take care of the UCF file which should be compatible with the modified design top RTL module.

The parameter `IO_TYPE` can only have the values CIO or SIO, other values will result in the controller misbehavior. Instead of modifying the RTL module manually, it is recommended to generate the appropriated design using MIG. Custom memory part feature can be utilized if required.

Programmable Read-Followed-by-Write Latency

Whenever there is a situation where an immediate write command has to be issued after a read command is issued, one extra clock cycle delay should be introduced before issuing the write command. According to memory vendor specifications, this will accommodate for data bus-turnaround period (read data to write data).

User can also increase this clock delay between read and write command. This can be done with the parameter `RD_TO_WR_LATENCY`. The value on this parameter infers the number of clocks controller has to wait between the read and write commands whenever there is a read followed by a write condition.

Controller introduces a single clock delay between read and write command whenever there is a read followed by a write condition. The parameter `RD_TO_WR_LATENCY` value

adds the delays (in terms of number of clock cycles) to the existing single clock delay between read and write command.

The parameter `RD_TO_WR_LATENCY` value should be an integer value between 0 and 3. Any other value other than from the specified will be considered as value 3.

This parameter is used only for CIO designs. For SIO designs, this parameter is ignored by the controller. For SIO designs there are separate data buses for read data and write data, hence there is no need for data bus-turnaround period.

Address Increment

The address generation logic generates an incremental address pattern. The address pattern can be generated as a linear incremental pattern or as burst incremental pattern. This depends on the parameter `BURST_INC`.

For some memory models the address bits for the data bursts are considered internally, hence a linear incremental address pattern will work. But for some memory models the address bits for the data bursts are not considered internally, they are included in the address given to the memory. Hence the address incrementing cannot be linear in this scenario, only burst increment of address bits should be given to the memory model.

Address generation logic generates a linear incremental pattern of address bits if the parameter `BURST_INC` is 0 and generates a burst incremental pattern of address bits if the parameter `BURST_INC` is 1. The value of the parameter `BURST_INC` can be integer and either 0 or 1.

MIG generates this parameter value depending on the type of the memory selected. User can even manually edit this value in the generated design top RTL module.

Reset-Active Low

The design reset signal `sys_rst_n` is an active-Low signal. This active-Low reset input pin is used to generate the design reset signals which run throughout the design. A parameter `RST_ACT_LOW` is provided in the design top module. This parameter indicates whether the input reset signal is an active-Low or active-High signal.

User can even drive an active-High reset signal as an input reset signal. But the parameter `RST_ACT_LOW` should be set to 0. This indicates that the input reset signal is an active-High signal.

The default value of this parameter is 1. This parameter must be manually modified by the user in the design top module depending upon the requirement. The value of the parameter `RST_ACT_LOW` can be either 0 or 1.

Debug Port

The debug port allows debugging and monitoring of physical layer read timing calibration logic and timing. This port consists of signals brought to the design top level HDL from the read calibration module (where the read timing calibration logic resides). These signals provide information for debugging hardware issues when calibration does not complete or read data errors are observed in the system even after calibration completes.

Debug port option can be enabled from MIG. By default the option is disabled. By enabling the option from MIG, the design top-level block parameter `DEBUG_EN` is set to 1. When this option is disabled the parameter value is 0. User can even enable/disable this parameter in the design top-level block HDL module manually.

For further details refer to [Appendix E, “Debug Port”](#).

IODELAY Performance Mode

In Virtex-5 family devices, the power dissipation of the IODELAY elements can be controlled using the HIGH_PERFORMANCE_MODE parameter. The values of this parameter can be either TRUE or FALSE.

When this parameter value is set to TRUE, the IODELAY jitter value per tap is reduced. This reduction results in a slight increase in power dissipation from the IODELAY element. When this parameter value is set to FALSE, the IODELAY power dissipation is reduced, but with an increase in the jitter value per tap.

The value of this parameter can be selected from the MIG FPGA options page. Users can also manually set this parameter value to TRUE or FALSE in the design top-level block HDL module.

Refer to [Appendix E, “Debug Port”](#) for more information on the IODELAY Performance Mode.

DCI Cascading

In Virtex-5 family devices, I/O banks that need DCI reference voltage can be cascaded with other DCI I/O banks. One set of VRN/VRP pins can be used to provide reference voltage to several I/O banks in the same column. With DCI cascading, one bank (the master bank) must have its VRN/VRP pins connected to external reference resistors. Other banks in the same column (slave banks) can use DCI standards with the same impedance as the master bank, without connecting the VRN/VRP pins on these banks to external resistors. DCI impedance control in cascaded banks is received from the master bank. This results in more usable pins and in reduced power usage because fewer VR pins and DCI controllers are used.

The syntax for representing the DCI Cascading in the UCF is:

```
CONFIG DCI_CASCADE = "<master> <slave1> <slave2> . . .";
```

There are certain rules that need to be followed in order to use **DCI Cascade** option:

1. The master and slave banks must all reside on the same column (left, centre, or right) on the device.
2. Master and slave banks must have the same VCCO and VREF (if applicable) voltages.

MIG supports DCI Cascading. This feature enables placing all 36 bits of read data, as well as the CQ and CQ# clocks, in the same bank when interfacing with 36-bit DDRII SRAM SIO memory parts. While interfacing the 36 bits of data of a 36-bit DDRII SRAM CIO memory part, first 18 bits of data and corresponding CQ are placed in one bank and the remaining 18 bits of data and corresponding CQ# are placed in another bank. This is done to prevent the WASSO limit from exceeding a given bank.

Following are the possibilities for generating the design with DCI support using the DCI Cascade option.

- For x36 SIO memory part designs, the DCI Cascade option is always enabled. This feature cannot be disabled if DCI support is needed.
- For x36 CIO memory part designs, the DCI Cascade is optional. DCI Support for these designs can be selected with or without the DCI Cascade selection. By default, the DCI Cascade option is disabled for these designs.

- For x18 memory part designs, DCI Cascade is optional. DCI support for these designs can be selected with or without the DCI Cascade selection. By default DCI Cascade option is disabled for these designs.
- For x18 memory part with 18-bit data width designs, the DCI Cascade option is disabled and cannot be utilized.

When DCI Cascade option is selected, MIG displays the master bank selection box for each column for the FPGA in the bank selection page.

- If an FPGA has no banks or has only non-DCI banks in a particular column, the master bank selection box for that column is not displayed.
- All the data read banks are treated as slave banks.
- When a data read bank is selected in a particular column, the master bank selection box for that particular column is activated and the rest of the master bank selection boxes for other columns are deactivated.
- In a particular column, when a data read bank is selected and there are no DCI banks left in that column for master banks selection, then the design cannot be generated. The data read banks must be moved to the other columns in order to select the master banks.
- The master bank selection box shows all the bank numbers in that particular column other than the data read banks and non-DCI banks in that column.
- There can be only one master bank selected for each column of banks.
- MIG utilizes VRN/VRP pins in the slave banks for pin allocation.
- For each master bank, VRN/VRP pins are reserved. When the selected master bank does not have at least one input or bidirectional pin of the HSTL_I_DCI_18 I/O standard, then MIG allocates a dummy input pin `masterbank_sel_pin` and the I/O standard of this dummy pin is assigned to HSTL_I_DCI_18. For example, consider an x18 SIO memory part design where the data read bank is selected as master bank, MIG reserves the VRN/VRP pins of the bank and the dummy input pin is not required.
- The dummy input pin is required to satisfy the requirement of the master bank. Any master bank should have at least one input or bidirectional pin of HSTL_I_DCI_18 I/O standard to program the DCI option.
- When all the banks in a particular column are allocated with data or data read pins, MIG chooses only the required banks for data or data read pin allocation, depending upon the design data width. When there is only one bank allocated for data/data read pins in a column of banks of an FPGA, then that particular data/data read bank should not be selected as a master bank. Doing so would result in an inappropriate DCI_Cascade syntax in the UCF of the generated design.

The center column banks of all the FPGAs are divided into two sections, top-column banks and bottom-column banks. Top-column banks are the banks available above the 0th bank, and the bottom column banks are the banks available below 0th bank. Therefore, there are two master bank selection boxes for the center column.

The VRN/VRP pins for a master bank do not need to be reserved in the reserve pins page.

Once the design is ready with the valid master and slave bank selection, the same master and slave bank information (along with the DCI Cascading syntax) is provided in the UCF when the design is generated.

For more information about DCI Cascade, refer to DCI Cascading in the *Virtex-5 FPGA User Guide* [Ref 10] and the *Xilinx® Constraints Guide*.

CQ/CQ_n Implementation

For x36 memory part, controller design uses both CQ and CQ_n for capturing the read data. CQ and CQ_n pins are allocated to P pins of an FPGA by MIG. For x36 memory part controller designs, first 18 bits of the read data is captured using CQ and the second 18 bits of the read data is captured using CQ_n.

For x18 memory part controller designs, only CQ is used for capturing the read data. CQ_n is not used and is connected to a dummy logic. This dummy logic is used just to retain CQ_n pin during the place and routing of the design.

Generic Parameters

The DDRII SRAM design is a generic design that works for all the features that are mentioned previously. User input parameters are defined as parameters for Verilog and generics in VHDL in the design modules and are passed down the hierarchy. For example, if the user selects a burst length of 4, then it is defined as follows in the <top_module> module:

```
Parameter BURST_LENGTH = 4,    // Burst Length
```

The user can change this parameter in <top_module> for various burst lengths to get the desired output. Same concept holds for all the other parameters listed in the <top_module> module. [Table 12-2](#) lists the details of all parameters.

Table 12-2: Parameterization of DDRII SRAM Virtex-5 FPGA Design

Category	Parameter Name	Description	Other Notes	Value Restrictions
Memory Parameters	BURST_LENGTH	Burst length of the design	For SIO designs, the value is only 2. For CIO designs, the value can be 2 or 4	Integer. 2 or 4
	BW_WIDTH	Number of Byte Write signals. One Byte Write signal for every 9 data (read data) bits		Integer. 1,2,3,4,5,6,7,8
	CLK_WIDTH	Number of input clock pairs. One input clock pair for every memory part	Number of K/K_n and C/C_n	Integer. 1,2,3,4,5,6,7,8
	CQ_WIDTH	Number of echo clock pairs. One echo clock pair for every memory part	Number of CQ/CQ_n	Integer. 1,2,3,4,5,6,7,8
	MEMORY_WIDTH	Data width of the memory part		Integer. 9,18,36
	ADDR_WIDTH	Address width of the memory part		Integer.
Design Parameters	BURST_INC	Address increment type. Linear incremental pattern or burst incremental pattern	1: Burst incremental pattern 0: Linear incremental pattern Needed only in the example design	Integer. 1,0
	CLK_FREQ	Design clock frequency	In MHz	Integer.
	DATA_WIDTH	Data width of the design		Integer. 9,18,36,72
	IO_TYPE	CIO (Common I/O) or SIO (Separate I/O)		String. "CIO", "SIO"
	DLL_FREQ_MODE	DCM frequency mode	Determined by CLK_PERIOD. Needed only if the DCM option is selected.	String. "HIGH", "LOW"
	RD_TO_WR_LATENCY	Number of clock cycle delays controller must insert between a read command and an immediate write command	The value selected can be only 0 or 1 or 2 or 3. Any other value will be considered as 3	Integer. 0,1,2,3
	SIM_ONLY	Enable to bypass initial 200µs power-on delay.		Integer. 0,1

Table 12-2: Parameterization of DDRII SRAM Virtex-5 FPGA Design (Cont'd)

Category	Parameter Name	Description	Other Notes	Value Restrictions
Miscellaneous	DEBUG_EN	To enable debug logic and able to view the debug signals on the ChipScope™ analyzer	See Appendix E, "Debug Port" for details	Integer. 1,0
	MASTERBANK_PIN_WIDTH	Number of Master bank input pins	Number of master banks selected and which have masterbank_sel_pin	Integer.
	HIGH_PERFORMANCE_MODE	IODELAY High Performance Mode Parameter value	This parameter value represents HIGH_PERFORMANCE_MODE of IODELAY as TRUE or FALSE. This will result in the Higher or lower power dissipation at the output of IODELAY element.	Verilog : String. "TRUE", "FALSE". VHDL : Boolean : TRUE, FALSE.

DDRII SRAM Memory Controller Modules

Figure 12-8 and Figure 12-9 shows the memory controller modules for both SIO and CIO memory types.

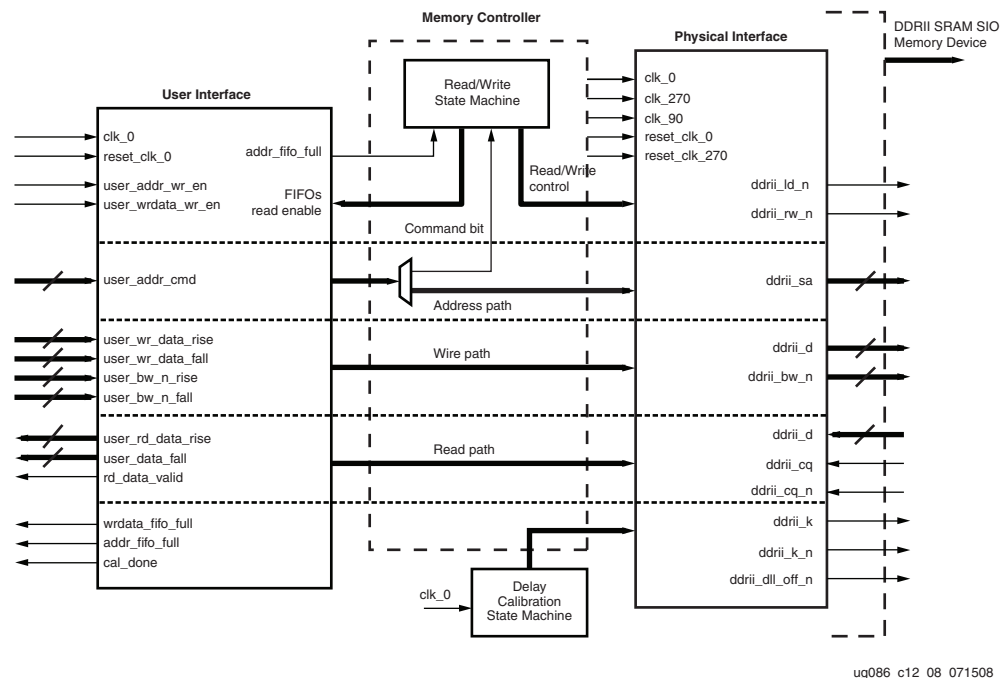
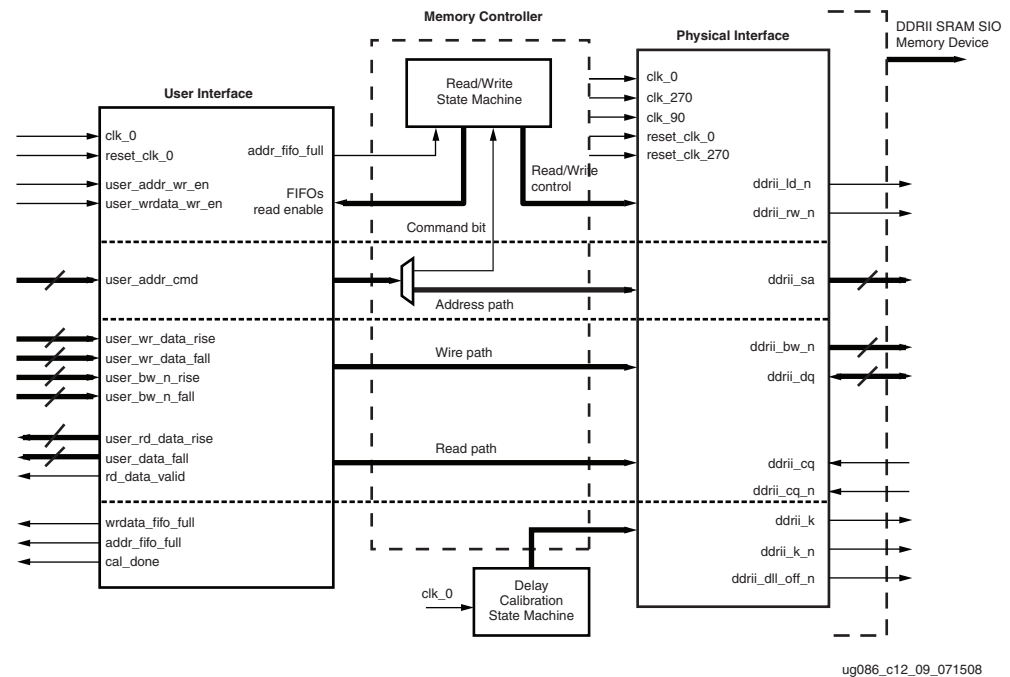


Figure 12-8: DDRII SRAM SIO Memory Controller Modules



ug086_c12_09_071508

Figure 12-9: DDRII SRAM CIO Memory Controller Modules

User Interface

User interface module receives and stores the user data, command and address information in respective FIFOs. The control module generates the required control signals for this module. During a write operation, the data stored in `wr_data_interface` is read and given to the physical layer to output to the memory. Similarly, during a read operation, the data from the memory is read via IDDR and is given to user with a valid signal (`rd_data_valid`). This valid signal indicates valid data on the `user_rd_data_rise` and `user_rd_data_fall` signals. Table 12-4 lists the user interface signals.

The FIFO36, FIFO36_72, and FIFO18 primitives are used for loading address and data from the user interface. The FIFO36 primitive is used in the `ddrii_top_addr_cmd_interface` module, the FIFO36_72 primitive is used in the `ddrii_top_wr_data_interface` module, and the FIFO18 primitive is used in the `ddrii_top_wr_data_interface` module. Every FIFO has two FIFO threshold attributes, `ALMOST_EMPTY_OFFSET` and `ALMOST_FULL_OFFSET`, that are set to 128 in the RTL. These values can be changed as needed. For valid FIFO threshold offset values, refer to UG190 [Ref 10].

Test Bench

MIG generates two RTL folders, `example_design` and `user_design`. The `example_design` includes the synthesizable test bench, while `user_design` does not include the test bench modules. The MIG test bench performs one write command followed by one read command in an alternating manner. The number of words in a write command depends on the burst length. For a burst length of 4, the test bench writes a total 4 data words for a single write command (2 rise data words and 2 fall data words). For a burst length of 2, the test bench writes a total of 2 data words. The data pattern is an incremental pattern. On every write command, the data pattern is incremented by one, and this is repeated with each subsequent write command. The initial data pattern for the first write command is

000. The test bench writes the 000, 001, 002, 003 data pattern in a sequence in which 000 and 002 are rise data words, and 001 and 003 are fall data words for a 9-bit design. The falling edge data is always rising edge data plus one. For a burst length of 2, the data sequence for the first write command is 000, 001. The data sequence for the second write command is 002, 003. The pattern is then incremented for the next write command. For data widths greater than 9, the same data pattern is concatenated for the other bits. For a 36-bit design and a burst length of 4, the data pattern for the first write command is 000000000, 008040201, 010080402, 0180C0603.

Address generation logic generates the address in an incremental pattern for each write command. The same address location is repeated for the next read command. In Samsung components, the burst address increments are done by the memory, so the address is generated by the test bench in a linear incremental pattern. In Cypress parts, the MIG test bench increments the address for burst operation. After the address reaches the maximum value, it rolls back to the initial address, i.e., 00000.

During reads, comparison logic compares the read pattern with the pattern written, i.e., the 000, 001, 002, 003 pattern. For example, for a 9-bit design of burst length 4, the data written for a single write command is 000, 001, 002, and 003. During reads, the read pattern is compared with the 000, 001, 002, 003 pattern. Based on a comparison of the data, a status signal error is generated. If the data read back is the same as the data written, the error signal is 0, otherwise it is 1.

Memory Controller

The DDRII SRAM memory controller can initiate write/read commands for both CIO and SIO memory parts. These write/read commands are issued as long as the User address-command FIFO is not empty. CIO designs support both Burst Length 4 and 2 whereas SIO designs support only Burst Length 2.

DDRII SRAM memory controller module (ddrii_top_ctrl_sm) is completely generic. This means to say that by just passing the correct parameter to this module, it generates read/write command signals for CIO/SIO, BL2/BL4 designs.

For CIO designs, controller takes care for the data bus-turnaround condition. When ever there is a situation where in an immediate write command has to be issued after a read command is issued, one extra clock cycle delay should be introduced before issuing the write command. According to memory vendor specifications, this will accommodate for data bus-turnaround period (read data to write data).

Controller introduces a single clock delay between read and write command whenever there is a read followed by a write condition. The parameter RD_TO_WR_LATENCY value adds the delays (in terms of number of clock cycles) to the existing single clock delay between read and write command.

The parameter RD_TO_WR_LATENCY value should be an integer value between 0 and 3. Any other value other than the specified will be considered as value 3.

For Separate I/O (SIO) designs there are separate data buses for read data and write data, so there is no need for data bus-turnaround. For Separate I/O (SIO) designs, controller will not consider the RD_TO_WR_LATENCY parameter.

Controller module decodes the user command and issues the specified command to the memory. The command_bit signal is decoded as a write command when it equals logic 0 and command_bit signal is decoded as a read command when it equals logic 1. The read/write command signals are generated based on the parameters BURST_LENGTH, IO_TYPE and RD_TO_WR_LATENCY. The controller state machine issues the commands in the correct sequence while determining the timing requirements of the memory.

Once the calibration is complete, controller issues a read enable to the address-command FIFO (ddrii_top_addr_cmd_interface module). The command bit is extracted from the output of the address-command FIFO. This command bit is then decoded to issue read/write commands. Figure 12-10 shows the controller state machine flow chart.

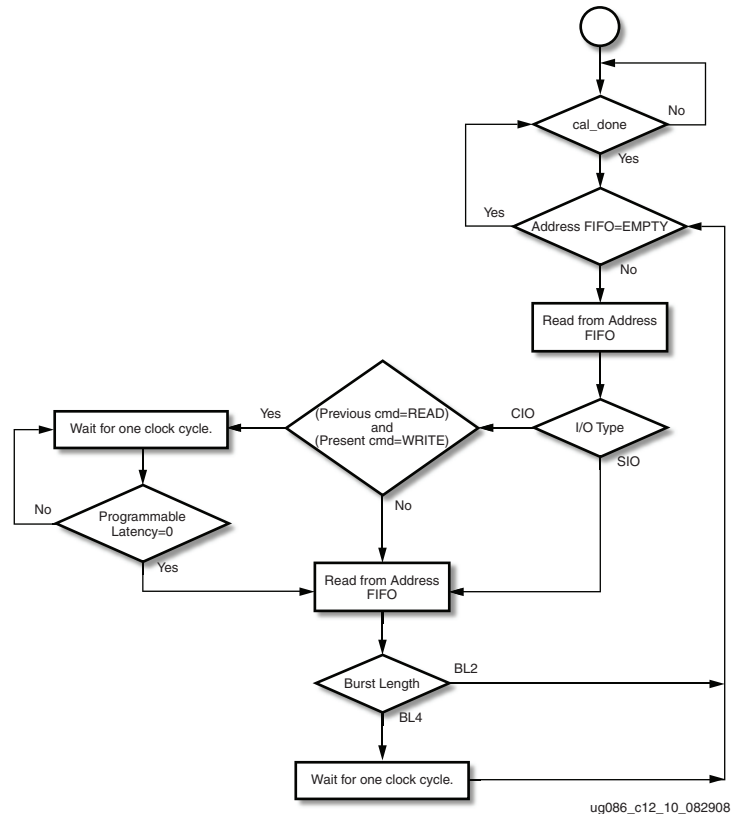


Figure 12-10: DDRII SRAM Memory Controller Flow Diagram

For Burst Length 4 controller designs, commands (read/write) to the memory are issued on every alternate clock. In this scenario controller issues read enable to the address-command FIFO on every alternate clock.

For Burst Length 2 controller designs, commands (read/write) to the memory are issued on every clock. In this scenario controller issues read enable to the address-command FIFO on every clock.

When ever the previous decoded command is a read command and the present command which is decoded is a write command, there is a need for introducing a single clock delay before the write command is issued to the memory. This single clock delay is for data bus-turnaround period. This single clock delay is applied on the decoded write command immediately. The same single clock delay is applied on the address-command FIFO read enable.

When the parameter RD_TO_WR_LATENCY value is non-zero value (any integer between 0 and 3), a delay (in number of clock cycles) specified by this parameter in addition to the single clock cycle delay is applied on the decoded write command before it is presented on to the command bus of the memory. The same delay is applied on the address-command FIFO read enable.

[illegible]

Figure 12-11: DDRII SRAM Memory Controller State Diagram

It is the interface between the controller and the memory. It includes the input/output blocks (IOBs) and other primitives used to read and write the double data rate signals to and from the memory, such as IDDR and ODDR. This module also includes the IODELAY elements of the Virtex-5 FPGA. These IODELAY elements are used to delay the data signals to capture the read data.

The memory control signals, such as `ld_n`, `rw_n` and `DLLoff_n` are driven from the buffers in the IOBs. All the input and output signals to and from the memory are referenced from the IOB to compensate for the routing delays inside the FPGA.

The `ddrii_phy_init_sm` module, which is instantiated in the `ddrii_phy_io` module, is used to initialize the DDRII SRAM memory in a predefined sequence according to the memory vendor specifications.

The `ddrii_phy_dly_cal_sm` and `ddrii_phy_en` modules calibrate the design to align the strobe such that it always captures the read data from the memory. A data valid signal `rd_data_valid` is generated to indicate the captured read data is a valid data.

The `ddrii_phy_write` module splits the user data into rise data and fall data to be sent to the memory as double data rate signal using ODDR.

Infrastructure

The infrastructure module generates the design clocks and reset signals. When differential clocking is used, `sys_clk_p`, `sys_clk_n`, `clk_200_p`, and `clk_200_n` signals appear. When single-ended clocking is used, `sys_clk` and `idly_clk_200` signals appear. In addition, clocks are available for design use and a 200 MHz clock is provided for the `IDELAYCTRL` primitive. Differential and single-ended clocks are passed through global clock buffers before connecting to a PLL/DCM. For differential clocking, the output of the `sys_clk_p/sys_clk_n` buffer is single-ended and is provided to the PLL/DCM input. Likewise, for single-ended clocking, `sys_clk` is passed through a buffer and its output is provided to the PLL/DCM input. The outputs of the PLL/DCM are 0° and 270° phase-shifted versions of the input clock). After the PLL/DCM is locked, the design is in the reset state for at least 25 clocks. The infrastructure module also generates all of the reset signals required for the design.

PLL/DCM

In MIG 3.0 and later, the DCM is replaced with a PLL for all Virtex-5 FPGA designs. If the user selects a design with a PLL in the GUI, the infrastructure module will have both PLL and DCM codes. The `CLK_GENERATOR` parameter enables either a PLL or a DCM in the infrastructure module. The `CLK_GENERATOR` parameter is set to PLL by default. If the user wants to use DCM, this parameter should be changed manually to DCM.

For designs without a PLL, the user application must have a PLL/DCM primitive instantiated in the design, and all user clocks should be driven through BUFGs.

Idelay_ctrl

This module instantiates the `IDELAYCTRL` primitive of the Virtex-5 FPGA. The `IDELAYCTRL` primitive is used to continuously calibrate the individual delay elements in its region to reduce the effect of process, temperature, and voltage variations. A 200 MHz clock has to be fed to this primitive.

MIG uses the “automatic” method for `IDELAYCTRL` instantiation in which the MIG HDL only instantiates a single `IDELAYCTRL` for the entire design. No location (LOC) constraints are included in the MIG-generated UCF. This method relies on the ISE® tools to replicate and place as many `IDELAYCTRL`s as needed (for example, one per clock region that uses `IDELAY`s). Replication and placement are handled automatically by the software tools if `IDELAYCTRL`s have same `refclk`, `reset`, and `rdy` nets. A new constraint called `IODELAY_GROUP` associates a set of `IDELAY`s with an `IDELAYCTRL` and allows for multiple `IDELAYCTRL`s to be instantiated without LOC constraints specified. ISE software generates the `IDELAY_CTRL_RDY` signal by logically ANDing the `RDY` signals of every `IDELAYCTRL` block.

The `IODELAY_GROUP` name should be checked in the following cases:

- The MIG design is used with other IP cores or user designs that also require the use of IDELAYCTRL and IDELAYs.
- Previous ISE software releases 8.2.03i and 9.1i had an issue with IDELAYCTRL block replication or trimming. When using these revisions of the ISE software, the user must instantiate and constrain the location of each IDELAYCTRL individually.

See UG190 [Ref 10] for more information on the requirements of IDELAYCTRL placement.

Clocking Scheme

Figure 12-13 shows the clocking scheme for this design. Global and local clock resources are used. The global clock resources consists of a PLL or a DCM, two BUFGs on PLL/DCM output clocks, and one BUFG for clk_200. The local clock resources consist of regional I/O clock networks (BUFIO). The global clock architecture is discussed in this selection.

The MIG tool allows the user to customize the design such that the PLL/DCM is not included. In this case, system clocks clk_0 and clk_270, and IDELAYCTRL clock clk_200 must be supplied by the user.

Global Clock Architecture

User must supply two input clocks to the design:

- A system clock running at the target frequency for the memory. This clock is used by the PLL/DCM to generate the various clocks used by the memory interface logic.
- A 200 MHz clock for the IDELAYCTRL block, which in turn are used for the IDELAY IOB delay blocks for aligning read capture data.

These clocks can be either differential or single-ended. User can select single-ended or differential ended clock input option from MIG FPGA options page. Differential clocks are connected to the IBUFGDS and the single-ended clocks are connected to IBUFG.

The system clock from the output of the IBUFGDS or the IBUFG is connected to the PLL/DCM to generate the various clocks used by the memory interface logic.

The clk_200 output of the IBUFGDS or the IBUFG is connected to BUFG. The output of the BUFG is used for IDELAY IOB delay blocks for aligning read capture data.

The PLL/DCM generates two separate synchronous clocks for use in the design. This is shown in [Table 12-3](#), [Figure 12-12](#), [page 482](#), and [Figure 12-13](#), [page 482](#). The clock structure is same for both example design and user design. For designs without PLL/DCM instantiation, PLL/DCM and BUFGs should be instantiated at user end to generate the required clocks.

Table 12-3: DDRII SRAM interface Design Clocks

Clock	Description	Logic Domain
clk_0	Skew compensated replica of the input system clock.	The clock for the controller and user interface logic, the DDRII SRAM bus-related I/O flip-flops (e.g., input data capture (DQ/Q), output data (DQ/D) and input clocks (CQ/CQ#). This clock is used to register the data, address, and command signals, and the address and data enables for the user interface logic ⁽¹⁾ . This clock is also used to generate read data, read data valid, and FIFO status signals.
clk_270	270° phase-shifted version of clk_0	The clocks for the DDRII SRAM memory address and control bus-related I/O flip-flops.

Notes:

1. See [“User Interface Accesses,” page 489](#) for timing requirements and restrictions on the user interface signals.

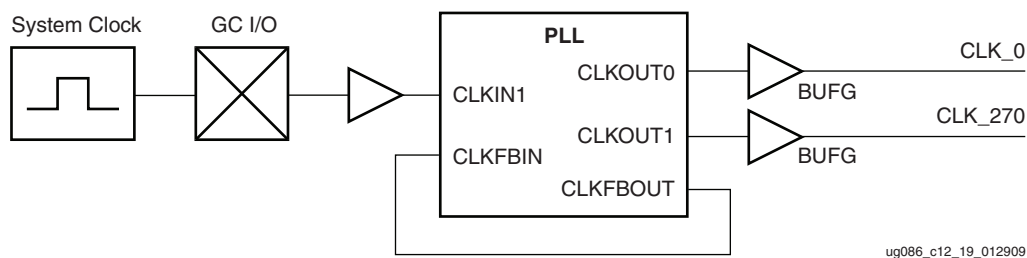


Figure 12-12: Clocking Scheme for QDRII Interface Logic Using PLL

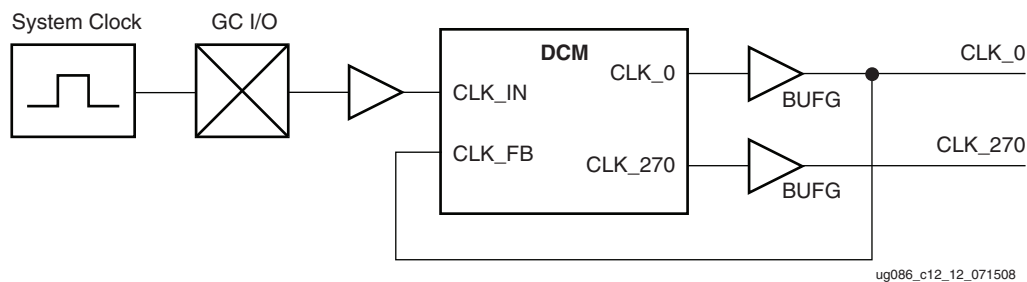


Figure 12-13: Clocking Scheme for DDRII SRAM Memory Interface Logic Using DCM

DDRII SRAM Initialization and Calibration

Initialization

DDRII SRAM memory is initialized through a specified sequence.

1. A 200 μ s wait period is initiated by the DDRII SRAM controller in order to achieve a stable power condition for the DDRII SRAM memory part.
2. After the stable power and clock (K,K#), `ddrii_dll_off_n` is set to high to enable DLL in DDRII SRAM memory part.
3. The additional wait period of 2048 clock cycles is applied in order to lock the DLL.
4. After this sequence of initialization, DDRII SRAM memory part is ready for calibration.

Delay Calibration

The delay calibration logic is responsible for providing the required amount of delay on the Read data and the input clocks (CQ/CQ#) to align the FPGA clock in the data valid window.

The delay calibration is enabled due to the available IODELAY elements in all the I/Os in the Virtex-5 device. The IODELAY elements delay the input read data by increments of 75 ps, up to a maximum delay of 5 ns. IDELAYCTRLs, available in every bank in Virtex-5 devices, and help to maintain the resolution of the IODELAY elements.

Calibration begins when the IDELAYCTRL ready signal has been asserted. Calibration is done in three stages:

1. *First Stage Calibration:* Calibration of input clocks (CQ/CQ#) with respect to read data.
2. *Second Stage Calibration:* Calibration of input clocks (CQ/CQ#) and read data with respect to the FPGA clock.
3. *Third Stage Calibration:* Read enable calibration that determines when the read data is valid. This helps to generate the data valid signal `rd_data_valid`.

First Stage Calibration: Calibration of input clocks (CQ/CQ#) and read data

This stage of calibration helps to align CQ/CQ# inside the data valid window. CQ/CQ# is delayed more than the read data by the delay on the BUFIO and the route delay of the CQ/CQ# before it clocks the read data in the ISERDES. In a case where the data valid window is considerably reduced, this delay on the BUFIO can move the edge of the CQ or the CQ# clock outside of the valid window. This calibration stage helps to avoid the de-synchronization of the clock and data. The calibration stage includes a dummy write to the memory with a constant rise data pattern of 1s and a constant fall data pattern of 0s followed by constant read to the same location until the first calibration is complete. The non-transitioning rise and fall data pattern helps to avoid any metastability caused by the FPGA clock in the second and third register stages in the ISERDES.

The steps involved in this stage include:

1. Increment CQ/CQ# delay taps to see if CQ/CQ# is within the valid window. If it is, continue to increment CQ/CQ# delay taps until the hold window range is measured.
2. Reset CQ/CQ# delay taps.
3. Increment read data delay taps to determine the read data setup window with respect to CQ/CQ#.

4. Reset read data delay taps.
5. If the hold window is greater than the setup, no tap increments are required. Otherwise, increment read data to the center of the valid window.

Completion of the first stage calibration is indicated with logic 1 on the signal `stg1_cal_done`.

Second Stage Calibration: Calibration of CQ/CQ# and read data with FPGA clock

This calibration stage helps to align CQ/CQ# and read data with respect to the FPGA clock. For reliable data capture and transfer of the data in to the FPGA fabric, the calibration is require to align the FPGA clock inside of the data capture by CQ/CQ#.

This stage includes a dummy write to the memory. The dummy write includes the following pattern: FF/00-55/AA, where FF and 55 refer to the rising data pattern during a four-word burst and 00 and AA refer to the falling data pattern.

The steps involved in this calibration stage are:

1. Increment CQ/CQ# and read data delay taps to delay CQ/CQ# and read data and determine the valid window range.
2. If this window is insufficient, which indicates that the CQ/CQ# and FPGA clock edge are aligned very closely to each other, continue to increment CQ/CQ# and read data delay taps to determine the valid window of CQ/CQ# and read data with respect to the next FPGA clock edge.
3. The calibration is complete when at least 15 taps of window are available at frequencies above 250 MHz and half the clock period worth of taps are available at frequencies lower than 250 MHz between CQ/CQ# and the FPGA clock.

Completion of the first stage calibration is indicated with logic 1 on the signal `stg3_cal_done`.

Third Stage Calibration: Read Enable Calibration

This stage is required to generate the read data valid signal. This includes non-contiguous read commands to align the data valid signals to the read data at the output of the ISERDES.

The calibration logic, built using an SRL16 as a shift register, helps to determine the number of register stages required by the read command signal to generate the correct read data valid signal. One read enable signals is generated for data captured by each CQ or CQ# clock. Based in the count value in the SRL shift register from all the banks, the read data from all the banks is aligned and presented to the user backend along with read data valid signal `rd_data_valid`.

This completes the delay calibration sequence. The completion of calibration is indicated with logic 1 on the signal `cal_done`.

DDRII SRAM Controller Interface Signals

Table 12-4 and Table 12-5 describe the DDRII SRAM controller system interface signals with and without a PLL, respectively. Table 12-6 describes the DDRII SRAM user interface signals. Table 12-7 describes the DDRII SRAM memory interface signals. In these tables, all signal directions are with respect to the DDRII SRAM memory controller.

Table 12-4: DDRII SRAM System Interface Signals (with a PLL)

Signal Name	Direction	Description
sys_clk_p, sys_clk_n	Input	System clock input made up of differential clock pairs. This clock pair goes to a differential input buffer. The differential buffer output goes to the PLL/DCM input. The PLL/DCM generates the required clocks for the design. This differential input clock pair is present only when the DIFFERENTIAL clocks option is selected in the MIG FPGA options page.
sys_clk	Input	Single-ended system clock input. This clock goes to a IBUFG. The IBUFG output goes to the PLL/DCM input. The PLL/DCM generates the required clocks for the design. This input system clock is present only when the SINGLE_ENDED clocks option is selected in the MIG FPGA options. When PLL option is deselected, both differential or single-ended input system clocks are not present.
dly_clk_200_p, dly_clk_200_n	Input	200 MHz differential clock used in the ddrii_idelay_ctrl logic. This differential input clock pair is present only when the DIFFERENTIAL clock option is selected in the MIG FPGA options page.
idly_clk_200	Input	Single-ended 200 MHz IDELAYCTRL clock input. This clock is connected to an IBUFG. The IBUFG output is connected to the input of a BUFG. The output of this BUFG acts as the IDELAYCTRL clock input. This input system clock is present only when the SINGLE_ENDED clocks option is selected in the MIG FPGA options. When the PLL option is deselected, both differential and single-ended input system clocks are not present.
sys_rst_n	Input	Reset to the DDRII SRAM memory controller.

Table 12-4: DDRII SRAM System Interface Signals (with a PLL) (Cont'd)

Signal Name	Direction	Description
compare_error	Output	This signal represents the status of the comparison of read data when compared to the corresponding write data.
cal_done	Output	This signal is asserted when the design initialization and calibration is complete.

Table 12-5: DDRII SRAM System Interface Signals (without a PLL)

Signal Name	Direction	Description
clk_0	Input	A 0° phase-shifted design input clock. This is an output of user PLL/DCM
clk_270	Input	A 270° phase-shifted design input clock. This is an output of user PLL/DCM.
clk_200	Input	200 MHz clock used in the ddrii_idelay_ctrl logic.
locked	Input	This active-High signal indicates whether the user PLL/DCM is locked or not.
sys_rst_n	Input	Reset to the DDRII SRAM memory controller
compare_error	Output	This signal represents the status of the comparison of read data when compared to the corresponding write data.
cal_done	Output	This signal is asserted when the design initialization and calibration is complete.

Table 12-6: DDRII SRAM User Interface Signals (without a Testbench [user_design])

Signal Name	Direction	Description
user_addr_wr_en	Input	This active-High signal is the write enable for the user address FIFO
user_wrdata_wr_en	Input	This active-High signal is the write enable for the user write data FIFO
user_wr_data_rise	Input	Positive-edge data for memory write. The contents of user_wr_data_rise bus are written in to rise data FIFO only when user_wrdata_wr_en is asserted.
user_wr_data_fall	Input	Negative-edge data for memory write. The contents of user_wr_data_fall bus are written in to fall data FIFO only when user_wrdata_wr_en is asserted.

Table 12-6: DDRII SRAM User Interface Signals (without a Testbench [user_design]) (Cont'd)

Signal Name	Direction	Description
user_bw_n_rise	Input	Byte write enables for DDRII SRAM memory positive-edge write data. The contents of user_bw_n_rise are written in to byte write FIFO only when user_wrdata_wr_en is asserted.
user_bw_n_fall	Input	Byte write enables for DDRII SRAM memory negative-edge write data. The contents of user_bw_n_fall are written in to byte write FIFO only when user_wrdata_wr_en is asserted.
user_addr_cmd[0]	Input	1-bit command to the Virtex-5 FPGA DDRII SRAM design. user_addr_cmd[0] = logic 0 for write command user_addr_cmd[0] = logic 1 for read command The contents of user_addr_cmb bus are written in to address FIFO only when user_addr_wr_en is asserted.
user_addr_cmd [ADDR_WIDTH:1] ⁽¹⁾	Input	Gives information about the address of the memory location to be accessed. The contents of user_addr_cmb bus are written in to address FIFO only when user_addr_wr_en is asserted.
clk_0_tb	Output	Clock output to the user. All the user interface signals must be synchronized with this clock. This signal is sourced from clock clk_0 in the controller.
reset_clk_0_tb	Output	Active high reset for the user interface.
wrdata_fifo_full	Output	FIFO full status signal of the user write data FIFOs.
addr_fifo_full	Output	FIFO full status signal of the user address FIFO
rd_data_valid	Output	Status signal indicating read data is valid on the read data bus.
user_rd_data_rise	Output	Positive-edge data read from memory.
user_rd_data_fall	Output	Negative-edge data read from memory.

Notes:

1. The number of address bits used depends on the density of the memory part. The controller ignores the unused bits, which can all be tied to High.

Table 12-7: DDRII SRAM Memory Interface Signals

Signal Name	Direction	Description
ddrii_dq	Bidirectional	During write commands, the data is sampled on both edges of K clock. During read commands, the data is sampled on both the edges of FPGA clock. This port will appear only for CIO designs.
ddrii_d	Output	During write commands, the data is sampled on both edges of K clock. This port will appear only for SIO designs.
ddrii_q	Input	During read commands, the data is sampled on both edges of FPGA clock. This port will appear only for SIO designs.
ddrii_bw_n	Output	Byte write enables for DDRII SRAM memory write data. These enable signals are sampled on both edges of the K clock.
ddrii_sa	Output	DDRII SRAM memory address for read and write operations.
ddrii_ld_n	Output	DDRII SRAM synchronous Load pin, bus cycle sequence is defined when it is low.
ddrii_rw_n	Output	DDRII SRAM read/write control pin. Read command when active-High, write command when active-Low.
ddrii_dll_off_n	Output	DDRII SRAM memory DLL Disable when low.
ddrii_cq, ddrii_cq_n	Input	DDRII SRAM memory output echo clocks. These are used for capturing the read data from the memory.
ddrii_k, ddrii_k_n	Output	DDRII SRAM memory input clocks. Memory write data is sampled on these clocks
ddrii_c, ddrii_c_n	Output	DDRII SRAM memory input clocks for output data. These signals are tied to high.

Table 12-8 lists the signals between the user interface and the controller.

Table 12-8: Signals between User Interface and Controller

Port Name	Port Width	Port Description
addr_fifo_empty	1	Empty status signal from the Address FIFO. Monitors the FIFO empty status flags to issue write and read commands.
command_bit	1	Output signal from the Address and Command FIFO. The first bit from the address and command FIFO output that represents the write/read command.
addr_fifo_rd_en	1	Read enable for the Address and command FIFO

User Interface Accesses

The user backend logic communicates with the memory controller through a FIFO-based user interface. This interface consists of four related buses:

- A Write Address FIFO bus accepts memory write address from the user
- A Write Data FIFO bus accepts the write data corresponding to the memory write address
- A Read Address FIFO bus accepts the memory read address from the user

The user interface has the following timing and signaling restrictions:

- The Write/Read Address and Write Data FIFOs cannot be written by the user until calibration is complete (as indicated by `cal_done`). In addition, the `user_ad_w_n`, `user_d_w_n`, and `user_r_n` interface signals need to be held high until calibration is complete.
- For issuing a write command, the memory write address must be written into the Read Address FIFO. The first write data word must be written to the Write Data FIFO on the same clock cycle as the when the write address is written. In addition, the write data burst must be written over consecutive clock cycles; there cannot be a break between bursts of data. These restrictions arise from the fact that the controller assumes write data is available when it receives the write command from the user.
- `clk_0_tb` is connected to `clk_0` in the controller. In case that user clock domain is different from `clk_0` / `clk_0_tb` of MIG, the user should add FIFOs for all data inputs and outputs of the controller to synchronize them to the `clk_0_tb`.

Write Interface

Figure 12-14 illustrates the user interface block diagram for write operations.

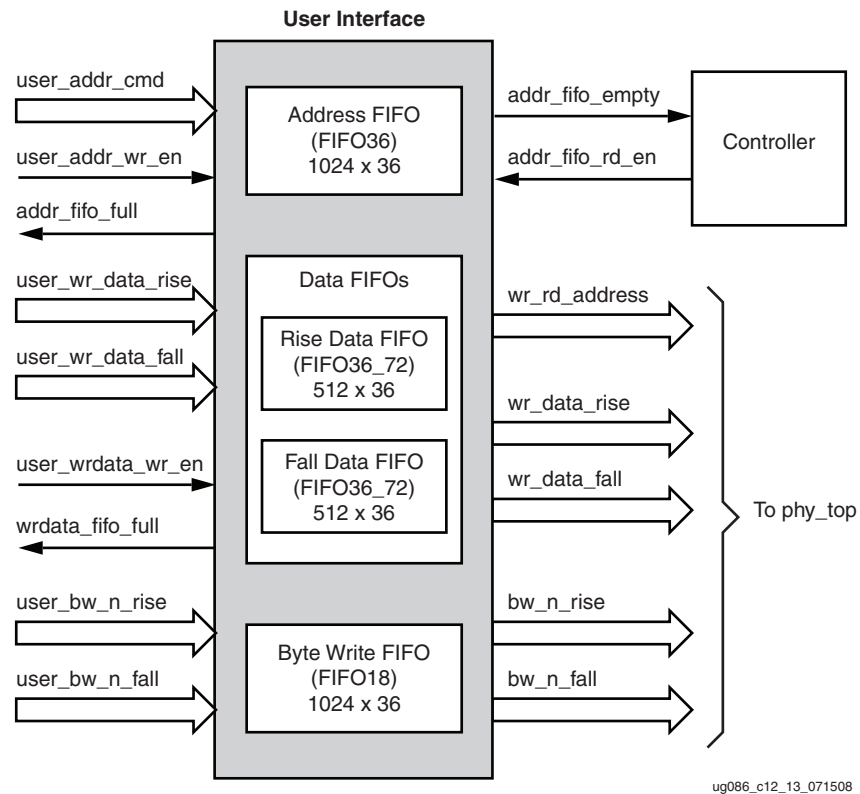


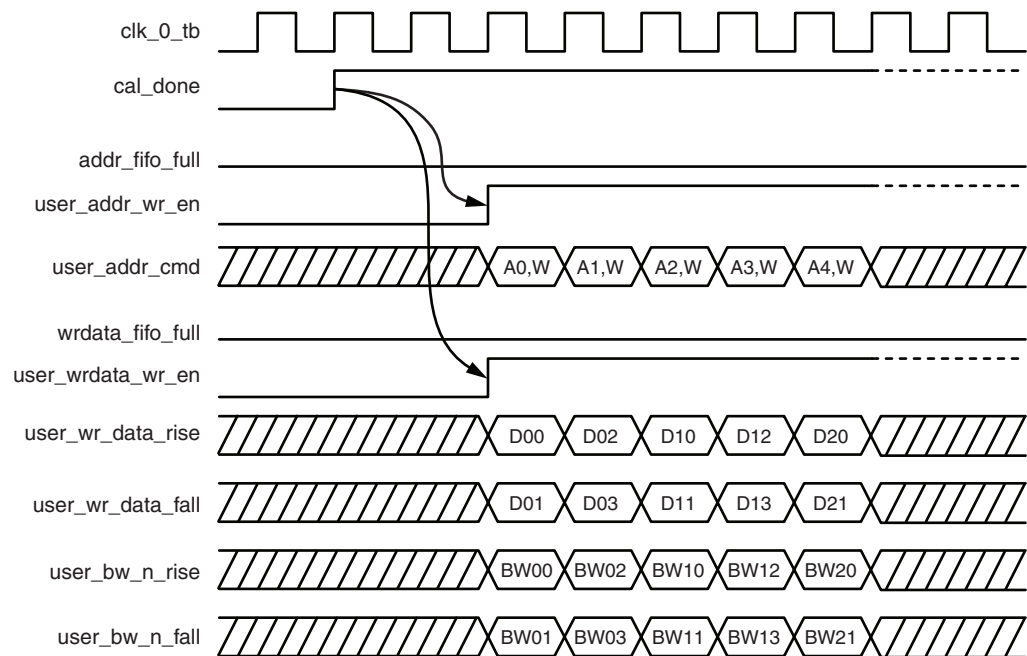
Figure 12-14: Write User Interface Block Diagram

The following steps describe the architecture of Address and Write Data FIFOs and how to perform a write burst operation to DDRII SRAM memory from user interface.

1. The user interface consists of an Address FIFO, Data FIFOs and a byte write FIFO. These FIFOs are built out of Virtex-5 FPGA FIFO primitives. Address FIFO is FIFO36 primitive with 1K x 36 configuration, Data FIFO is FIFO36_72 primitive with 512 x 72 configuration and Byte Write FIFO is FIFO18 primitive with 1024 x 18 configuration.
2. Address FIFO is common for both write and read commands. It comprises an address part and a command part. Command bit discriminate between write and read commands. Single instantiation of FIFO36 constitutes the Address FIFO.
3. Two separate sets of Data FIFOs are being used for storing the rising edge and falling edge data to be written to DDRII SRAM memory from user interface. For 9bit, 18bit and 36bit configurations, controller concatenates the extra bits of Data FIFO with 0s.
4. Byte Write FIFO is being used to store the Byte Write signals to DDRII SRAM memory from user interface. Extra bits are concatenated with zeros
5. User can initiate a write to memory by writing to the address FIFO and the write data FIFO only when the calibration is complete (cal_done signal is asserted high) and FIFOs full flags are asserted low. Users should not access any of these FIFOs until the signal cal_done is asserted. During Calibration process controller writes pattern data in to the Data FIFOs. Signal cal_done assures that the clocks are stable, reset process is completed, calibration is complete and the controller is ready to accept the user data

and commands. Status signal `addr_fifo_full` is asserted high when Address FIFO is full and status signal `wrdata_fifo_full` is asserted high or Data FIFOs or Byte Write FIFO are full.

6. Both the address FIFO and write data FIFO full flags are deasserted with power-on.
7. User should assert the address FIFO write enable signal `user_addr_wr_en` along with address bus `user_addr_cmd` to store the write address and write command in to the address FIFO.
8. The write command should be given by setting the `user_addr_cmd[0]` bit as logic 0.
9. User should assert the data FIFO write enable signal `user_wrdata_wr_en` along with write data `user_wr_data_rise`, `user_wr_data_fall` and `user_bw_n_rise`, `user_bw_n_fall` to store the rise data and fall data in to rise data FIFO and fall data FIFO and byte write enable for rise data and fall data in to byte write FIFO respectively.
10. Controller reads the Address, Data and Byte Write FIFOs when they are not empty. Controller reads the address FIFO by issuing the `addr_fifo_rd_en` signal. Controller reads the write data FIFO and byte write FIFOs by issuing the `wrdata_fifo_rd_en` signal after the address FIFO is read. Controller decodes the command part after the address FIFO is read.



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Figure 12-15: Write User Interface Timing Diagram for Burst Length 4

11. [Figure 12-15](#) shows the timing diagram for a write command with a burst length of four. As shown in the figure the command bit (`user_addr_cmd [0]`) is a write command (command bit is indicated as 'W') which is identified with a logic 0 on that bit. The address should be asserted for one clock cycle as shown. For burst length of four, each write to address FIFO has two write to the Data FIFO consisting of two rising-edge and two falling-edge data.
12. [Figure 12-16](#) shows the timing diagram for a write command with a burst length of two. As shown in the figure, the command bit (`user_addr_cmd [0]`) is a write command (command bit is indicated as W) which is identified with a logic 0 on that

bit. The address should be asserted for one clock cycle as shown. For burst length of two, each write to address FIFO has a single write to the Data FIFO consisting of a single rising-edge and single falling-edge data.

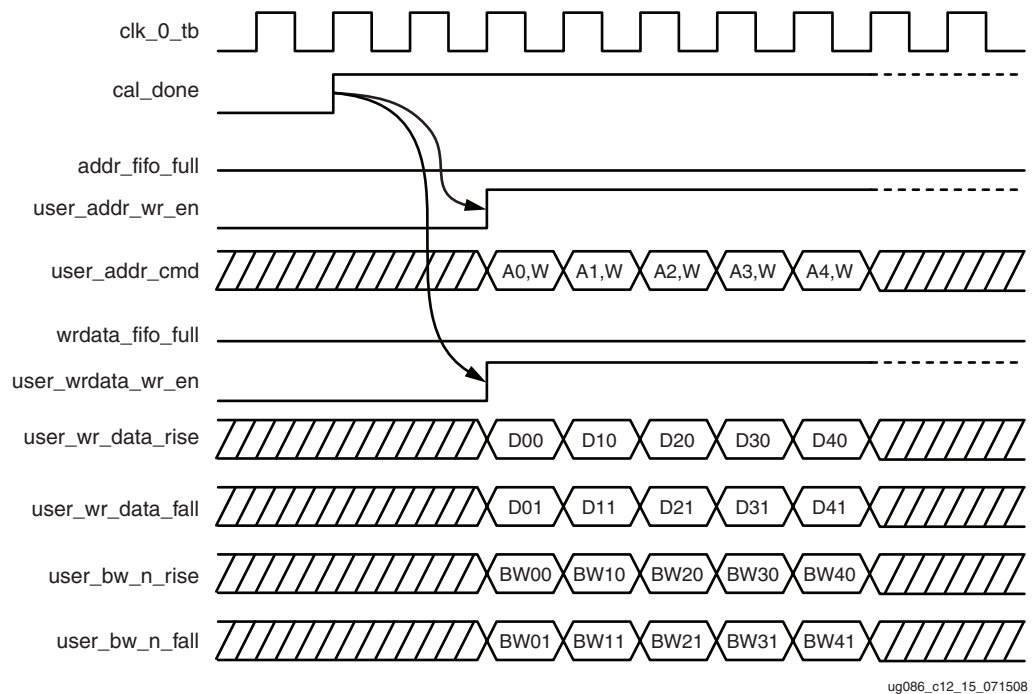


Figure 12-16: Write User Interface Timing Diagram for Burst Length 2

13. From the previous user interface timing diagrams, it is clear that writing addresses and command bits in to address FIFO and write data in to data FIFOs are two different and independent actions. Users must take complete responsibility for writing bursts of data bits corresponding to a particular address in to the respective FIFOs at the same time. If not, the controller will output an undesired data bits which will be written in to the memory.

Read Interface

Figure 12-17 illustrates the user interface block diagram for read operations.

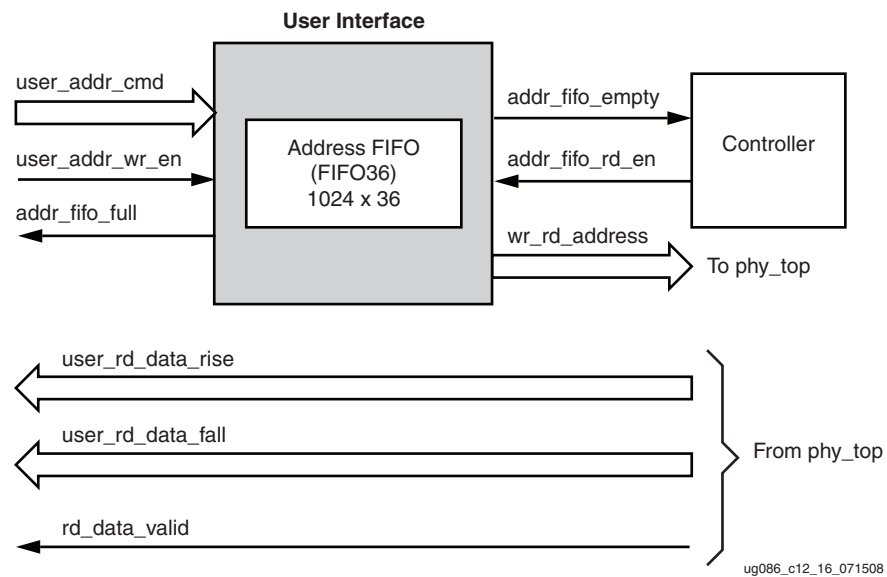


Figure 12-17: Read User Interface Block Diagram

The following steps describe the architecture of the read user interface and how to perform a DDRII SRAM burst read operation

1. The read user interface consists of an Address FIFO built out of a Virtex-5 FPGA FIFO18 configuration 1024 x 18.
2. User can initiate a read to the memory by writing to the address FIFO only when the calibration is complete (cal_done signal is asserted high) and FIFOs full flags are asserted low.
3. User should assert the address FIFO write enable signal user_addr_wr_en along with address bus user_addr_cmd to store the read address and read command in to the address FIFO.
4. The read command should be given by setting the user_addr_cmd[0] bit as logic 1.
5. Controller read the address FIFO when it is not empty by issuing the read enable signal addr_fifo_rd_en. After decoding user_addr_cmd [0] bit, the controller issues a read command to the memory at the specified address.
6. Prior to the actual read and write command, the design calibrates the latency in number of clock cycles from the time the read command is issued to the time the data is received. Using this pre-calibrated delay information, the controller delays the read data for required number of clocks.
7. The rd_data_valid signal is asserted high when data is available in the read data FIFOs.
8. User must access the read data as soon as rd_data_valid signal is asserted high.

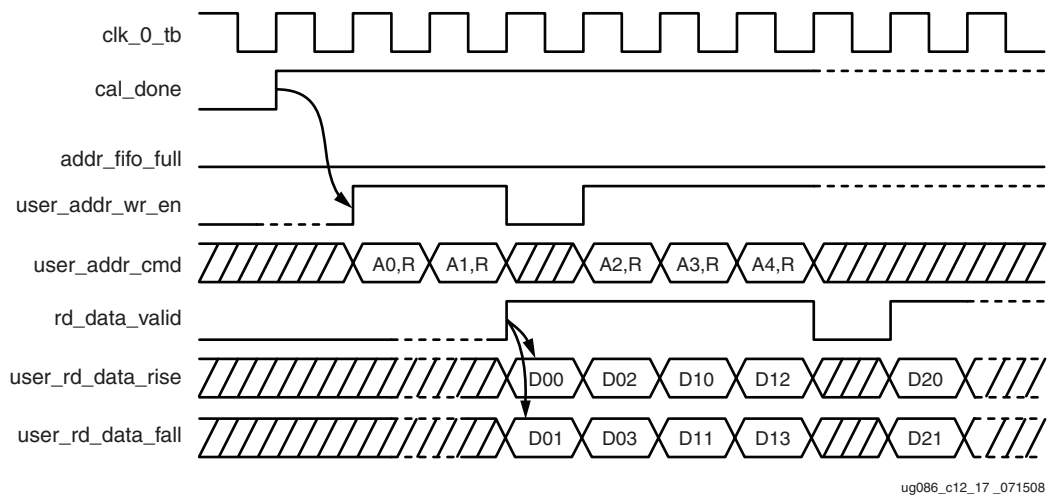


Figure 12-18: Read User Interface Timing Diagram for Burst Length 4

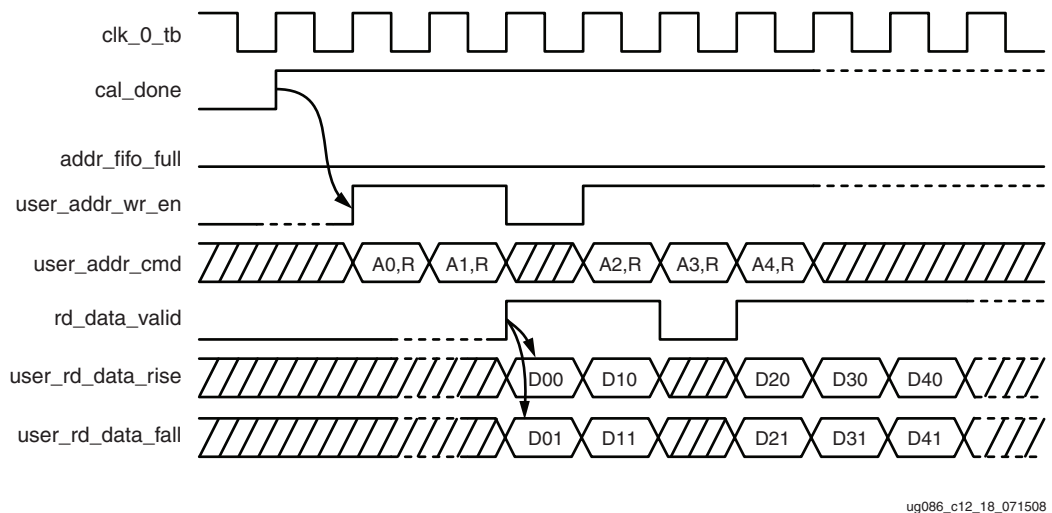


Figure 12-19: Read User Interface Timing Diagram for Burst Length 2

9. Figure 12-18 shows the timing diagram for a read command with a burst length of four. As shown in the figure the command bit (`user_addr_cmd[0]`) is a read command (command bit is indicated as 'R') which is identified with a logic 1 on that bit. The address should be asserted for one clock cycle as shown. For burst length of four, each read command is associated with four read data's, two rising-edge and two falling-edge data. The signal `rd_data_valid` is asserted high for two clocks for each read command issued to the memory. The read data captured is a valid data as long as the signal `rd_data_valid` is asserted high as shown in the figure.
10. Figure 12-19 shows the timing diagram for a read command with a burst length of two. As shown in the figure the command bit (`user_addr_cmd[0]`) is a read command (command bit is indicated as 'R') which is identified with a logic 1 on that bit. The address should be asserted for one clock cycle as shown. For burst length of two, each read command is associated with two read data's, one rising-edge and one falling-edge

data. The signal `rd_data_valid` is asserted high for one clock for each read command issued to the memory. The read data captured is a valid data as long as the signal `rd_data_valid` is asserted high as shown in the figure.

11. After the read command and the corresponding address bits are loaded in to the address FIFO, it can take a minimum of 14 clock cycles, for the controller to assert `rd_data_valid` high.

Table 12-9 shows the read latency of the controller.

Table 12-9: Maximum Read Latency

Parameter	Number of Clock Cycles	Description
User read command to address FIFO empty flag	4	<ul style="list-style-type: none"> 4 clock cycles for empty flag deassertion in the FWFT mode
Address empty flag to the read command on DDRII SRAM memory bus	5	<ul style="list-style-type: none"> 2 clock cycle to generate the read command in the controller state machine 3 clock cycles to transfer the command to the memory
DDRII SRAM memory read command to valid data available	5	<ul style="list-style-type: none"> 1.5 clock cycles of the memory read latency 2.5 clock cycles to capture and transfer read data to the FPGA clock domain 1 clock cycle for aligning all the read data capture
Total Latency	14	

DDRII SRAM Signal Allocations

Table 12-10: DDRII SRAM Signal Allocations

Bank Selected	Signals Allocated in the Group
Data	Memory Data, memory byte write, CQ/CQ#, K/K#, and C/C# clocks.
Data_Read	Memory read data and memory CQ/CQ#.
Data_Write	Memory write data, memory byte write, K/K#, and C/C# clocks.
Address	Memory address and memory control.
System_Control	System reset and status signals.
System_Clock	System clocks.

MIG shows checkboxes for Data, Address, System_Control and System_Clock in the bank selection for DDRII SRAM CIO designs.

MIG show checkboxes for Data_Read, Data_Write, System_Control and System_Clock in the bank selection for DDRII SRAM SIO designs.

For CIO designs, when Data box is checked in a bank, the memory data (DQ), memory byte write (BW), memory output echo clocks (CQ/CQ#), memory input clocks (K/K#) and memory input clocks for output data (C/C#) are assigned to that particular bank.

For SIO designs, when Data_Read box is checked in a bank, the memory read data (Q), memory output echo clocks (CQ/CQ#) are assigned to that particular bank.

For SIO designs, when Data_Write box is checked in a bank, the memory write data (D), memory byte write (BW), memory input clocks (K/K#) and memory input clocks for output data (C/C#) are assigned to that particular bank.

When System_Clock box is checked in a bank, the system reset signal sys_rst_n and the status signals compare_error and cal_done are assigned to that particular bank.

When the System_Clock box is checked in a bank, the design clock signals sys_clk_p, sys_clk_n, dly_clk_200_p and dly_clk_200_n are assigned to that particular bank.

For special cases, such as without a testbench (user_design), the corresponding input and output ports are not assigned to any FPGA pins in the design UCF because user can connect these ports to the FPGA pins or can connect to some logic internal to the same FPGA.

Note: Timing has been verified for most of the MIG generated configurations. For the best timing results, adjacent banks in the same column of the FPGA should be used. Banks that are separated by unbonded banks should be avoided because these can cause timing violations.

Pinout Considerations

It is recommended to select banks within the same column on MIG. This helps to avoid the clock tree skew that the design would incur while crossing from one column to another.

When the data read, data write, address and system control pins are allocated to individual banks in a column, then the system control pins must be allocated in a bank that is central to the rest of banks allocated. This helps reduce datapath and clock path skew.

For larger FPGAs (for example, FF1738, FF1760, and similar), it is recommended to place data read, data write, address and system control pins in the same column to reduce datapath and clock path skew.

Supported Devices

Table 12-11 lists the memory parts supported by MIG for DDRII SRAM design. In the supported devices, X in the memory part column denotes a single alphanumeric character. For example, K7I321884X can be either K7I321884C or K7I321884M.

Table 12-11: Supported memory parts for DDRII SRAM (Virtex-5 FPGAs)

Memory Part	Speed Grade	Density in Mb	Memory Width	Burst Length	IO Type	Vendor
K7I643684M	FC30	72	36	4	CIO	Samsung
K7I643682M	FC30	72	36	2	CIO	Samsung
K7I641884M	FC30	72	18	4	CIO	Samsung
K7I641882M	FC30, FC25	72	18	2	CIO	Samsung
K7I323684X	FC30, FC25	36	36	4	CIO	Samsung
K7I163682B	FC30, FC25	18	36	2	CIO	Samsung
K7I161884B	FC30, FC25	18	18	4	CIO	Samsung
K7I321884X	FC25	36	18	4	CIO	Samsung
K7I163684B	FC25	18	36	4	CIO	Samsung
K7I161882B	FC25	18	18	2	CIO	Samsung
CY7C1419AV18	300BZC, 250BZC	36	18	4	CIO	Cypress
CY7C1421AV18	300BZC, 250BZC	36	36	4	CIO	Cypress
CY7C1428AV18	300BZC, 250BZC	36	9	4	CIO	Cypress
CY7C1518V18	300BZC, 250BZC	72	18	2	CIO	Cypress
CY7C1520V18	300BZC, 250BZC	72	36	2	CIO	Cypress
CY7C1527V18	300BZC	72	9	2	CIO	Cypress
CY7C1420AV18	250BZC	36	36	2	CIO	Cypress
CY7C1427AV18	250BZC	36	9	2	CIO	Cypress
CY7C1320BV18	250BZC, 200BZC	18	36	2	CIO	Cypress
CY7C1321AV18	250BZC	18	36	4	CIO	Cypress
CY7C1321BV18	250BZC	18	36	4	CIO	Cypress
CY7C1318BV18	250BZC	18	18	2	CIO	Cypress
CY7C1319BV18	250BZC	18	18	4	CIO	Cypress
CY7C1916BV18	250BZC	18	9	2	CIO	Cypress
CY7C1917BV18	250BZC	18	9	4	CIO	Cypress
K7J643682M	FC30	72	36	2	SIO	Samsung
K7J641882M	FC30	72	18	2	SIO	Samsung
K7J321882M	FC30	36	18	2	SIO	Samsung
CY7C1393BV18	300BZC	18	18	2	SIO	Cypress
CY7C1424BV18	300BZC	36	36	2	SIO	Cypress

Simulating the DDRII SRAM Design

After generating the design, MIG creates a `sim` folder in the specified path. This folder contains simulation files for a particular design. The `sim` folder contains the external testbench, memory model, and `.do` file to simulate the generated design. The memory model files are currently generated in Verilog only. To learn more details about the files in the `sim` folder and to simulate the design, refer to [“Simulation Guide,” page 499](#).



Section V: Simulation Guide

Chapter 13, "Simulating MIG Designs"

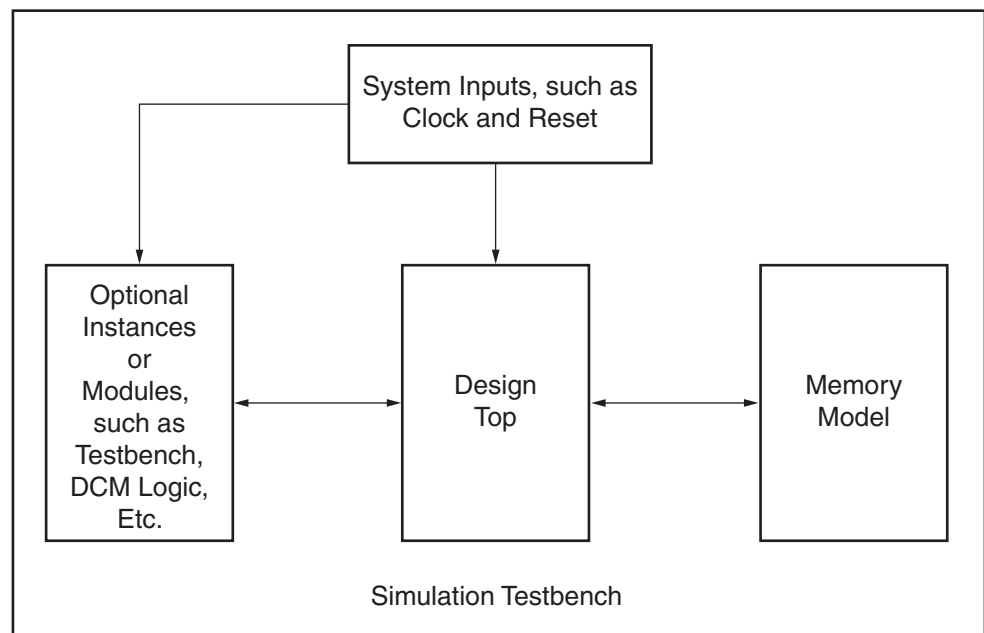
Simulating MIG Designs

A generic simulation testbench is supported for MIG generated designs. With this testbench, the user can simulate the design generated from MIG.

Introduction

The `sim` folder provides a simulation environment for the design generated in the ModelSim simulator. This folder includes the simulation testbench module (`sim_tb_top`) and various other modules to simulate the design properly. The simulation testbench module also generates system input signals, clocks, and resets to the design.

Figure 13-1 depicts a block diagram of the simulation environment.



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Figure 13-1: Block Diagram of Simulation Environment

The simulation testbench module integrates the complete system through port maps, a design clock, a clock for the IDELAYCTRL module, and reset generation logic. With clocks and system reset signals as inputs, the system can be divided into these blocks:

- **Optional instances:** These function as testbench modules for designs without testbenches and as DCM/PLL logic for designs without DCMs or PLLs. The testbench

here refers to a synthesizable test module that provides test inputs such as data, address, and commands to the design. In designs with a testbench, the testbench is part of the design top module. Similarly, DCM/PLL logic is part of design top for designs generated with DCMs or PLLs.

- Design top: In the example design, the design top module connects with the clocks, reset, memory interface signals, and status signals. In the user design, design top connects with the user interface signals, clocks, reset, memory interface signals, and status signals. Design top includes the controller part, an optional testbench, and DCM/PLL logic.
- Memory model: This is provided with the memory core of the component selected. MIG provides a memory model in Verilog only. VHDL memory models are not provided.

The simulation testbench module can be in Verilog or VHDL, depending on the HDL used in the design.

Supported Features

The MIG simulation environment supports:

- All component widths
- Designs with or without a testbench
- Designs with or without DCM/PLL
- All supported components and DIMMs (UDIMMs, SODIMMs and RDIMMs)
- Deep memories and ECC for Virtex®-4 FPGA DDR2 direct-clocking designs
- Differential and single-ended DQS for Virtex-4 FPGA DDR2 direct-clocking designs
- CIO and SIO for RLDRAM II designs
- CIO and SIO for Virtex-5 FPGA DDRII SRAM designs
- Multicontroller simulation testbenches for the Virtex-5 FPGA (QDRII SRAM and DDR2 SDRAM)

Unsupported Features

The MIG simulation environment does not support:

- Multicontroller simulation testbenches for Virtex-4 FPGA DDR2 direct-clocking designs
- VHDL memory models
- Cypress components for all SRAM designs

Note: The simulation testbench is specific to each design that is generated from MIG. Design parameters should not be changed after generating the design, except for the RESET_ACTIVE_LOW or RST_ACT_LOW parameters.

Simulating the Design

The design can be simulated using the ModelSim GUI either manually or by calling the `sim.do` file in ModelSim.

Method 1: Manual Simulation

1. Invoke ModelSim.
2. Create a new project.
3. Add design files to the project from the `rtl` folder, and add simulation files to the project from the `sim` folder. Only `.v` or `.vhd` files should be added to the project. Files with a `.vh` extension do not need to be added to the `sim` folder.
4. Map the `unisim` or `unisims_ver` libraries. This is needed to compile Xilinx primitives used in the design.
5. Compile the design. For Virtex-4 and Spartan®-3 FPGA VHDL designs, the design parameter file from the `rtl` folder needs to be compiled before other modules are compiled.
6. Load the design and map the library to it. For example, the following command is used to load a Virtex-4 FPGA DDR SDRAM design in Verilog:


```
vsim -t ps +notimingchecks -L unisims_ver work.sim_tb_top glbl
```

 The following command loads the same design in VHDL:


```
vsim -t ps +notimingchecks -L unisim work.sim_tb_top glbl
```
7. After loading, run the design for the required amount of time.

Method 2: Using the `sim.do` file

This method uses the `sim.do` file to simulate the design. This file contains ModelSim commands to create a new project, add files to the `sim` folder, and run the simulation for a specified period.

The steps involved in simulating a design are:

1. Invoke ModelSim.
2. Create a new project. (Optional.)
3. Change the directory to the working `sim` folder. (Optional.)
4. If the directory is set to the working directory, execute the following command at the ModelSim prompt:

```
do sim.do
```

If the working directory is not set in ModelSim, execute the following command at the `vsim` prompt:

```
do <working directory>/sim.do
```

For example:

```
do E:/simulations/test1/example_design/sim/sim.do
```

5. The run time depends on completion of calibration or memory initialization. After completion of calibration or initialization, simulation runs for an additional 50 μ s. For example, if it takes 212 μ s for the calibration to complete, the total run time is $212 + 50 = 262 \mu$ s. The user can still increase or decrease the run time. For more information on changing the run time, refer to [“Changing Simulation Run Time,” page 513](#). See also [“Design Notes,” page 514](#).

Files in sim Folder

MIG generates all the design files in the `rtl` folder, and the simulation files in the `sim` folder.

Virtex-5 FPGA Designs

This section describes the simulation files for various Virtex-5 FPGA designs.

DDR2 SDRAM

[Table 13-1](#) lists the files generated in the `sim` folder for Virtex-5 FPGA DDR2 SDRAM designs.

Table 13-1: Virtex-5 FPGA DDR2 SDRAM Simulation Files

File Name	Description
<code>sim_tb_top (.v or .vhd)</code>	This Verilog or VHDL external testbench file integrates the system and provides the system inputs.
<code>wiredly (.v or .vhd)</code>	This module is used to insert delay in a Verilog or VHDL design.
<code>ddr2_model.v</code>	This is the Verilog memory model for DDR2 SDRAM from Micron. This memory model is provided only in Verilog.
<code>ddr2_model_parameters.vh</code>	This parameter file is used by the <code>ddr2_model.v</code> Micron memory model. It lists all the parameters that define the memory type and timing parameters.
<code>hyb18t512xx0b2f_0129.v</code>	This is the Verilog memory model for the 512 MB DDR2 SDRAM from Qimonda. This memory model is provided only in Verilog.
<code>hyx18t1gxx0c2x.v</code>	This is the Verilog memory model for the 1 GB DDR2 SDRAM from Qimonda. This memory model is provided only in Verilog.
<code>set_hold.vh</code>	This checks the Setup and Hold Config file for the Verilog model used by the Qimonda memory model.
<code>qimonda_package.vhd</code>	This VHDL package file for Qimonda parts includes component declarations of all memory models.
<code>glbl.v</code>	This file initializes the simulator environment.
<code>sim.do</code>	This file lists the ModelSim commands required to run the test case.
<code>ddr2_tb_test_addr_gen,</code> <code>ddr2_tb_test_cmp,</code> <code>ddr2_tb_test_data_gen,</code> <code>ddr2_tb_test_gen,</code> <code>tb_top (.v or .vhd)</code>	These optional modules are only included in the <code>sim</code> folder of designs without testbenches, or in the <code>rtl</code> folder.

DDR SDRAM

[Table 13-2](#) lists the files generated in the `sim` folder for Virtex-5 FPGA DDR SDRAM designs.

Table 13-2: Virtex-5 FPGA DDR SDRAM Simulation Files

File Name	Description
<code>sim_tb_top(.v or .vhd)</code>	This Verilog or VHDL external testbench file integrates the system and provides the system inputs.
<code>wiredly(.v or .vhd)</code>	This module is used to insert delay in a Verilog or VHDL design.
<code>ddr_model.v</code>	This is the Verilog memory model for DDR SDRAM from Micron. This memory model is provided only in Verilog.
<code>ddr_model_parameters.vh</code>	This parameter file is used by the <code>ddr_model.v</code> Micron memory model. It lists all the parameters that define the memory type and timing parameters.
<code>glbl.v</code>	This file initializes the simulator environment.
<code>sim.do</code>	This file lists the ModelSim commands required to run the test case.
<code>ddr_tb_test_addr_gen</code> , <code>ddr_tb_test_cmp</code> , <code>ddr_tb_test_data_gen</code> , <code>ddr_tb_test_gen</code> , <code>ddr_tb_top(.v or .vhd)</code>	These optional modules are only included in the <code>sim</code> folder of designs without testbenches, or in the <code>rtl</code> folder.

QDRII SRAM

[Table 13-3](#) lists the files generated in the `sim` folder for Virtex-5 FPGA QDRII SRAM designs. Samsung and Cypress memory models are not available in the `sim` folder for simulations when the design is generated by the MIG tool. The appropriate memory model must be downloaded from the vendor's web site. MIG designs are functionally verified with the R12 version of the Samsung memory models.

Table 13-3: Virtex-5 FPGA QDRII SRAM Simulation Files

File Name	Description
<code>sim_tb_top(.v or .vhd)</code>	This Verilog or VHDL external testbench file integrates the system and provides the system inputs.
<code>glbl.v</code>	This file initializes the simulator environment.
<code>sim.do</code>	This file lists the ModelSim commands required to run the test case.

Table 13-3: Virtex-5 FPGA QDRII SRAM Simulation Files (Cont'd)

File Name	Description
qdr_ii_tb_top, qdr_ii_test_addr_gen, qdr_ii_test_cmp_data, qdr_ii_test_data_gen, qdr_ii_test_q_sm, qdr_ii_test_wr_rd_sm (.v or .vhd)	These optional modules are only included in the <code>sim</code> folder of designs without testbenches, or in the <code>rtl</code> folder.

DDRII SRAM

Table 13-4 lists the files generated in the `sim` folder for Virtex-5 FPGA DDRII SRAM designs. Samsung and Cypress memory models are not available in the `sim` folder for simulations when the design is generated by the MIG tool. The appropriate memory model must be downloaded from the vendor's web site. MIG designs are functionally verified with the R12 version of the Samsung memory models.

Table 13-4: Virtex-5 FPGA DDRII SRAM Simulation Files

File Name	Description
sim_tb_top (.v or .vhd)	This Verilog or VHDL external testbench file integrates the system and provides the system inputs.
wiredly (.v or .vhd)	This module is used to insert delay in a Verilog or VHDL design.
glbl.v	This file initializes the simulator environment.
sim.do	This file lists the ModelSim commands required to run the test case.
ddr_ii_tb_top, ddr_ii_test_addr_gen, ddr_ii_test_data_cmp, ddr_ii_test_data_gen, ddr_ii_test_wr_rd_sm (.v or .vhd)	These optional modules are only included in the <code>sim</code> folder of designs without testbenches, or in the <code>rtl</code> folder.

Multicontroller

Table 13-5 lists the files generated in the `sim` folder for Virtex-5 FPGA Multicontroller designs.

Table 13-5: Virtex-5 FPGA Multicontroller Simulation Files

File Name	Description
sim_tb_top (.v or .vhd)	This Verilog or VHDL external testbench file integrates the system and provides the system inputs.

Table 13-5: Virtex-5 FPGA Multicontroller Simulation Files (Cont'd)

File Name	Description
wiredly (.v or .vhd)	This module is used to insert delay in a Verilog or VHDL design.
ddr2_model_cX.v	This is the Verilog memory model for DDR2 SDRAM from Micron. This memory model is provided only in Verilog. The cX in the file name represents the controller number (e.g., c0, c1, etc.).
ddr2_model_parameters_cX.vh	This parameter file is used by the ddr2_model_cX.v Micron memory model. It lists all the parameters that define the memory type and timing parameters. The cX in the file name represents the controller number (e.g., c0, c1, etc.).
hyb18t512xx0b2f_0129_cX.v	This is the Verilog memory model for the 512 MB DDR2 SDRAM from Qimonda. This memory model is provided only in Verilog. The cX in the file name represents the controller number (e.g., c0, c1, etc.).
hyx18t1gxx0c2x_cX.v	This is the Verilog memory model for the 1 GB DDR2 SDRAM from Qimonda. This memory model is provided only in Verilog. The cX in the file name represents the controller number (e.g., c0, c1, etc.).
set_hold_cX.vh	This checks the Setup and Hold Config file for the Verilog model used by the Qimonda memory model. The cX in the file name represents the controller number (e.g., c0, c1, etc.).
glbl.v	This file initializes the simulator environment.
sim.do	This file lists the ModelSim commands required to run the test case. It includes memory parameters to be passed to the memory models of the respective controllers.
ddr2_tb_test_addr_gen, ddr2_tb_test_cmp, ddr2_tb_test_data_gen, ddr2_tb_test_gen,tb_top, qdrii_tb_top, qdrii_test_addr_gen, qdrii_test_cmp_data, qdrii_test_data_gen, qdrii_test_q_sm, qdrii_test_wr_rd_sm (.v or .vhd)	These optional modules are only included in the <code>sim</code> folder of designs without testbenches, or in the <code>rtl</code> folder.

Virtex-4 FPGA Designs

This section describes the simulation files for various Virtex-4 FPGA designs.

DDR2 SDRAM Direct Clocking

Table 13-6 lists the files generated in the `sim` folder for Virtex-4 FPGA DDR2 SDRAM direct-clocking designs.

Table 13-6: Virtex-4 FPGA DDR2 SDRAM Direct-Clocking Simulation Files

File Name	Description
<code>sim_tb_top(.v or .vhd)</code>	This Verilog or VHDL external testbench file integrates the system and provides the system inputs.
<code>wiredly(.v or .vhd)</code>	This module is used to insert delay in a Verilog or VHDL design.
<code>ddr2_model.v</code>	This is the Verilog memory model for DDR2 SDRAM from Micron. This memory model is provided only in Verilog.
<code>ddr2_model_parameters.vh</code>	This parameter file is used by the <code>ddr2_model.v</code> Micron memory model. It lists all the parameters that define the memory type and timing parameters.
<code>hyb18t512xx0b2f_0129.v</code>	This is the Verilog memory model for the 512 MB DDR2 SDRAM from Qimonda. This memory model is provided only in Verilog.
<code>hyx18t1gxx0c2x.v</code>	This is the Verilog memory model for the 1 GB DDR2 SDRAM from Qimonda. This memory model is provided only in Verilog.
<code>set_hold.vh</code>	This checks the Setup and Hold Config file for the Verilog model used by the Qimonda memory model.
<code>qimonda_package.vhd</code>	This VHDL package file for Qimonda parts includes component declarations of all memory models.
<code>glbl.v</code>	This file initializes the simulator environment.
<code>sim.do</code>	This file lists the ModelSim commands required to run the test case.
<code>addr_gen, backend_rom, cmp_rd_data, data_gen, test_bench(.v or .vhd)</code>	These optional modules are only included in the <code>sim</code> folder of designs without testbenches, or in the <code>rtl</code> folder.

DDR2 SDRAM SerDes

Table 13-7 lists the files generated in the `sim` folder for Virtex-4 FPGA DDR2 SDRAM SerDes designs.

Table 13-7: Virtex-4 FPGA DDR2 SDRAM SerDes Simulation Files

File Name	Description
<code>sim_tb_top (.v or .vhd)</code>	This Verilog or VHDL external testbench file integrates the system and provides the system inputs.
<code>wiredly (.v or .vhd)</code>	This module is used to insert delay in a Verilog or VHDL design.
<code>ddr2_model.v</code>	This is the Verilog memory model for DDR2 SDRAM from Micron. This memory model is provided only in Verilog.
<code>ddr2_model_parameters.vh</code>	This parameter file is used by the <code>ddr2_model.v</code> Micron memory model. It lists all the parameters that define the memory type and timing parameters.
<code>hyb18t512xx0b2f_0129.v</code>	This is the Verilog memory model for the 512 MB DDR2 SDRAM from Qimonda. This memory model is provided only in Verilog.
<code>hyx18t1gxx0c2x.v</code>	This is the Verilog memory model for the 1 GB DDR2 SDRAM from Qimonda. This memory model is provided only in Verilog.
<code>set_hold.vh</code>	This checks the Setup and Hold Config file for the Verilog model used by the Qimonda memory model.
<code>qimonda_package.vhd</code>	This VHDL package file for Qimonda parts includes component declarations of all memory models.
<code>glbl.v</code>	This file initializes the simulator environment.
<code>sim.do</code>	This file lists the ModelSim commands required to run the test case.
<code>addr_gen, backend_rom, cmp_rd_data, data_gen, test_bench (.v or .vhd)</code>	These optional modules are only included in the <code>sim</code> folder of designs without testbenches, or in the <code>rtl</code> folder.

DDR SDRAM

Table 13-8 lists the files generated in the `sim` folder for Virtex-4 FPGA DDR SDRAM designs.

Table 13-8: Virtex-4 FPGA DDR SDRAM Simulation Files

File Name	Description
<code>sim_tb_top (.v or .vhd)</code>	This Verilog or VHDL external testbench file integrates the system and provides the system inputs.
<code>wiredly (.v or .vhd)</code>	This module is used to insert delay in a Verilog or VHDL design.

Table 13-8: Virtex-4 FPGA DDR SDRAM Simulation Files (Cont'd)

File Name	Description
ddr_model.v	This is the Verilog memory model for DDR SDRAM from Micron. This memory model is provided only in Verilog.
ddr_model_parameters.vh	This parameter file is used by the ddr_model.v Micron memory model. It lists all the parameters that define the memory type and timing parameters.
glbl.v	This file initializes the simulator environment.
sim.do	This file lists the ModelSim commands required to run the test case.
addr_gen, backend_rom, cmp_rd_data, data_gen, test_bench (.v or .vhd)	These optional modules are only included in the sim folder of designs without testbenches, or in the rtl folder.

RLDRAM II

Table 13-9 lists the files generated in the sim folder for Virtex-4 FPGA RLDRAM II designs.

Table 13-9: Virtex-4 FPGA RLDRAM II Simulation Files

File Name	Description
sim_tb_top (.v or .vhd)	This Verilog or VHDL external testbench file integrates the system and provides the system inputs.
wiredly (.v or .vhd)	This module is used to insert delay in a Verilog or VHDL design.
rldram2_model.v	This is the Verilog memory model for RLDRAM II memory from Micron. This memory model is provided only in Verilog.
rldram2_model_parameters.vh	This parameter file is used by the rldram2_model.v memory model. It lists all the parameters that define the memory type and timing parameters.
fifo_generator_v4_1.v	This Verilog FIFO model is used by the design user interface for Verilog controller designs.
fifo_generator_v4_1.vhd	This VHDL FIFO model is used by the design user interface. This model utilizes the iputils_conv.vhd, iputils_misc.vhd, iputils_std_logic_arith.vhd, and iputils_std_logic_unsigned.vhd modules for compilation. These modules are used for the VHDL controller designs.
glbl.v	This file initializes the simulator environment.

Table 13-9: Virtex-4 FPGA RLDRAM II Simulation Files (Cont'd)

File Name	Description
<code>sim.do</code>	This file lists the ModelSim commands required to run the test case.
<code>backend_rom</code> , <code>byte_compare</code> , <code>cmp_rd_data</code> , <code>test_bench</code> (.v or .vhd)	These optional modules are only included in the <code>sim</code> folder of designs without testbenches, or in the <code>rtl</code> folder.

QDRII SRAM

Table 13-10 lists the files generated in the `sim` folder for Virtex-4 FPGA QDRII SRAM designs. Samsung and Cypress memory models are not available in the `sim` folder for simulations when the design is generated by the MIG tool. The appropriate memory model must be downloaded from the vendor's web site. MIG designs are functionally verified with the R12 version of the Samsung memory models.

Table 13-10: Virtex-4 FPGA QDRII SRAM Simulation Files

File Name	Description
<code>sim_tb_top (.v or .vhd)</code>	This Verilog or VHDL external testbench file integrates the system and provides the system inputs.
<code>glbl.v</code>	This file initializes the simulator environment.
<code>sim.do</code>	This file lists the ModelSim commands required to run the test case.
<code>addr_gen</code> , <code>data_gen</code> , <code>q_sm</code> , <code>test_bench</code> , <code>wr_rd_sm</code> (.v or .vhd)	These optional modules are only included in the <code>sim</code> folder of designs without testbenches, or in the <code>rtl</code> folder.

DDRII SRAM

Table 13-11 lists the files generated in the `sim` folder for Virtex-4 FPGA DDRII SRAM designs. Samsung and Cypress memory models are not available in the `sim` folder for simulations when the design is generated by the MIG tool. The appropriate memory model must be downloaded from the vendor's web site. The MIG designs are functionally verified with the R12 version of the Samsung memory models.

Table 13-11: Virtex-4 FPGA DDRII SRAM Simulation Files

File Name	Description
<code>sim_tb_top (.v or .vhd)</code>	This Verilog or VHDL external testbench file integrates the system and provides the system inputs.
<code>wiredly (.v or .vhd)</code>	This module is used to insert delay in a Verilog or VHDL design.
<code>glbl.v</code>	This file initializes the simulator environment.

Table 13-11: Virtex-4 FPGA DDRII SRAM Simulation Files (Cont'd)

File Name	Description
<code>sim.do</code>	This file lists the ModelSim commands required to run the test case.
<code>addr_gen</code> , <code>data_gen</code> , <code>d_sm</code> , <code>test_bench</code> , <code>wr_rd_sm</code> (.v or .vhd)	These optional modules are only included in the <code>sim</code> folder of designs without testbenches, or in the <code>rtl</code> folder.

Spartan-3 FPGA Designs

This section describes the simulation files for various Spartan-3 FPGA designs.

DDR2 SDRAM

Table 13-12 lists the files generated in the `sim` folder for Spartan-3 FPGA DDR2 SDRAM designs.

Table 13-12: Spartan-3 FPGA DDR2 SDRAM Simulation Files

File Name	Description
<code>sim_tb_top (.v or .vhd)</code>	This Verilog or VHDL external testbench file integrates the system and provides the system inputs.
<code>wiredly (.v or .vhd)</code>	This module is used to insert delay in a Verilog or VHDL design.
<code>ddr2_model.v</code>	This is the Verilog memory model for DDR2 SDRAM from Micron. This memory model is provided only in Verilog.
<code>ddr2_model_parameters.vh</code>	This parameter file is used by the <code>ddr2_model.v</code> Micron memory model. It lists all the parameters that define the memory type and timing parameters.
<code>hyb18t512xx0b2f_0129.v</code>	This is the Verilog memory model for the 512 MB DDR2 SDRAM from Qimonda. This memory model is provided only in Verilog.
<code>hyx18t1gxx0c2x.v</code>	This is the Verilog memory model for the 1 GB DDR2 SDRAM from Qimonda. This memory model is provided only in Verilog.
<code>set_hold.vh</code>	This checks the Setup and Hold Config file for the Verilog model used by the Qimonda memory model.
<code>qimonda_package.vhd</code>	This VHDL package file for Qimonda parts includes component declarations of all memory models.
<code>glbl.v</code>	This file initializes the simulator environment.

Table 13-12: Spartan-3 FPGA DDR2 SDRAM Simulation Files (Cont'd)

File Name	Description
sim.do	This file lists the ModelSim commands required to run the test case.
addr_gen, cmd_fsm, cmp_data, data_gen, test_bench (.v or .vhd)	These optional modules are only included in the sim folder of designs without testbenches, or in the rtl folder.

DDR SDRAM

Table 13-13 lists the files generated in the sim folder for Spartan-3 FPGA DDR SDRAM designs.

Table 13-13: Spartan-3 FPGA DDR SDRAM Simulation Files

File Name	Description
sim_tb_top (.v or .vhd)	This Verilog or VHDL external testbench file integrates the system and provides the system inputs.
wiredly (.v or .vhd)	This module is used to insert delay in a Verilog or VHDL design.
ddr_model.v	This is the Verilog memory model for DDR SDRAM from Micron. This memory model is provided only in Verilog.
ddr_model_parameters.vh	This parameter file is used by the ddr_model.v Micron memory model. It lists all the parameters that define the memory type and timing parameters.
glbl.v	This file initializes the simulator environment.
sim.do	This file lists the ModelSim commands required to run the test case.
addr_gen, cmd_fsm, cmp_data, data_gen, test_bench (.v or .vhd)	These optional modules are only included in the sim folder of designs without testbenches, or in the rtl folder.

Changing Simulation Run Time

Memory write and read can be performed correctly after calibration of the design at a given frequency for Virtex-4 and Virtex-5 FPGA designs, and after initialization of the design at a given frequency for Spartan-3/3E/3A/3AN/3A DSP FPGA designs. Thus, run time also depends upon the calibration period.

In the sim.do file, the run time is determined by the following example ModelSim commands:

```
when {/sim_tb_top/phy_init_done = 1} {
  if {[when -label a_100] == ""} {
    when -label a_100 { $now = 50 us } {
      nowhen a_100.....}}}
```

The when command checks for completion of calibration and then runs for an additional 50 μ s. To increase the run time after completion of calibration, 50 μ s should be changed to some other value, such as 100 μ s. There should be a space between the value and the unit:

```
when {$now = @800 us} {stop}
```

In the above example, this when command assumes importance if the previous condition (`/sim_tb_top/phy_init_done = 1`) does not become valid up to 800 μ s. ModelSim then pauses in this case and exits from the simulation.

Note: The run time value of the second when command (800 μ s) should always be greater than that of the first when command (50 μ s). Otherwise, the simulation result display at the end erroneously shows that the calibration failed for Virtex-4 and Virtex-5 designs, and initialization failed for Spartan-3/3E/3A/3AN/3A DSP designs.

Changing the Breakpoint Condition

From the example in [“Changing Simulation Run Time,” page 513](#), `/sim_tb_top/phy_init_done = 1` indicates the signal on which the breakpoint is set. This condition can be changed by changing the path and the value of the breakpoint. For more details, refer to the command reference section of the ModelSim reference manual.

Design Notes

This section provides notes on the various designs discussed in this chapter:

- The `sim.do` file contains commands that suppress Numeric Std package and Arithmetic operation warnings.
- At the end of simulation, a test result is displayed depending on whether or not the design generates an error signal. The displayed result does not consider the error or violations generated by the memory models or the simulator. The transcript file should be reviewed for any errors or warnings generated.
- If the license agreement is not accepted when generating the design, the memory model is not generated in the `sim` folder. In such a case, the memory model might have to be downloaded from a memory vendor site and then placed in the `sim` folder. The files should be renamed accordingly, as described in [“Files in sim Folder,” page 504](#). According to the design generated, the memory model parameters are passed from the `sim.do` file. For example, the following command is used for a Micron DDR2 SDRAM design:

```
vlog +incdir+. +define+x256Mb +define+sg3 +define+x8 ddr2_model.v
```

In this case, `+define+x256Mb` shows the device density. This parameter is not present in the downloaded memory model and should be ignored. The `+define+sg3` segment shows the memory speed grade and `+define+x8` shows the device data width.

- For DIMM designs, MIG uses instantiations of component models.
- In Qimonda parts, DDR2 SDRAM design simulations undergo a memory allocation failure and the ModelSim GUI closes automatically. This occurs only on certain systems (based on swap memory in Linux and cache memory in Windows). To avoid this, the address mapping for the `NO_SPARSE_MEM` and `SPARSE_MEM` Qimonda memory models are modified. The `SPARSE_ROW_BITS` and `SPARSE_COL_BITS` parameter values are modified. Address mapping for the `SPARSE_ROW_MAP` and `SPARSE_COL_MAP` parameters are modified based on the `SPARSE_ROW_BITS` and

SPARSE_COL_BITS parameter values. Similarly, the assignment statement for the all_bits parameter is modified in the memory model.

- When simulating designs for Qimonda parts, the simulator displays this error message:

```
# QI ERR: CKE has to be low during initial 200us period
```

The simulator displays this output even though CKE meets the 200 μ s period. This output can be ignored.

- While simulating VHDL designs that are generated using the Debug Signals option enabled in MIG, the simulator produces these warning messages:

```
# ** Warning: (vsim-3473) Component instance "ila_inst : ila" is not bound.
```

```
# Time: 0 ps Iteration: 0 Region: /sim_tb_top/u_mem_controller
File: ../rtl/test13_vhd_X0.vhd
```

```
# ** Warning: (vsim-3473) Component instance "vio_inst : vio" is not bound.
```

```
# Time: 0 ps Iteration: 0 Region: /sim_tb_top/u_mem_controller
File: ../rtl/test13_vhd_X0.vhd
```

```
# ** Warning: (vsim-3473) Component instance "icon_inst : icon" is not bound.
```

```
# Time: 0 ps Iteration: 0 Region: /sim_tb_top/u_mem_controller
File: ../rtl/test13_vhd_X0.vhd
```

These warning messages can be ignored because ila and icon instances are only useful for debugging the design in hardware.

- When simulating VHDL designs for Virtex-4 FPGA RLDRAM controllers, the XilinxCoreLib library needs to be mapped. This is used by the fifo_generator_v5_3.vhd module present in the sim directory. An example mapping is shown here for reference:

```
vmap xilinxcorelib
/proj/xbuils/clibs/M.53c.0/modelsim/6.5c/lin64/lib/xilinxcorelib
```

Known Issues

This section discusses some known issues that can occur during simulation.

Virtex-5 FPGA Designs

This section discusses known simulation issues in Virtex-5 FPGA designs.

DDR2 SDRAM

- For VHDL designs, these warning messages might be displayed due to metastable values during power on:

```
#Warning:NUMERIC_STD.TO_INTEGER: metavalue detected, returning 0
```

```
#Time: 0 ps
```

```
Iteration:0
```

```
Instance:/ddr2_test_tb/u_mem_controller/u_ddr2_top_0/u_mem_if_top_0/u_
phy_top_0/u_phy_io_0/gen_phy_calib/u_phy_calib_0/gen_chk_cnt__3
```

These messages are suppressed in the sim.do file and appear only if the design is simulated without using the sim.do file generated by MIG. These messages can be ignored.

- In x16 or x8 components with a data width of eight, this warning appears while compiling the design:

```
# ** Warning: [3] ../sim/sim_tb_top.vhd(316): Range 0 to -1 is null.
```

This warning only appears for VHDL designs and can be ignored.

- If the design is rerun without deleting old files that were generated during simulation, this warning might be displayed:

```
# ** Warning: (vlib-34) Library already exists at "work".
```

This warning can be ignored.

- While generating parts using Create Custom Part, proper address values must be entered. For Qimonda parts, 512 MB and 1 GB models are supported. For custom parts of bank address value 3, a 1 GB model is output. If the column address entered is less than or equal to 11, this error message is displayed:

```
"Address is Reversed"
```

Thus, the column address entered should be greater than 11.

DDR SDRAM

- For VHDL designs, these warning messages might be displayed due to metastable values during power on:

```
#Warning: NUMERIC_STD.TO_INTEGER: metavalue detected, returning 0
```

```
#Time: 0 ps
```

```
Iteration: 0
```

```
Instance:/ddr1_tb/u_mem_controller/u_ddr1_top_0/u_mem_if_top/u_phy_top  
/u_phy_io/gen_phy_calib_gate/u_phy_calib
```

These messages are suppressed in the `sim.do` file and appear only if the design is simulated without using the `sim.do` file generated by MIG. These messages can be ignored.

- In x16 or x8 components with a data width of eight, this warning appears while compiling the design:

```
# ** Warning: [3] ../sim/sim_tb_top.vhd(316): Range 0 to -1 is null.
```

This warning only appears for VHDL designs and can be ignored.

- If the design is rerun without deleting old files that were generated during simulation, this warning might be displayed:

```
# ** Warning: (vlib-34) Library already exists at "work".
```

This warning can be ignored.

QDR II SRAM

- Due to metastable values during power on, warning messages might be displayed. These messages are suppressed in the `sim.do` file and appear only if the design is simulated without using the `sim.do` file generated by MIG. These messages can be ignored.

DDR II SRAM

- Due to metastable values during power on, warning messages might be displayed. These messages are suppressed in the `sim.do` file and appear only if the design is simulated without using the `sim.do` file generated by MIG. These messages can be ignored.

Multicontroller

- While simulating multicontroller designs involving DDR2 SDRAM and QDR II SRAM controllers, the simulator displays these warning messages:

```
# ** Warning: ../sim/k7rxxx84x_r12_c1.v(336): [TMREN] - Redefinition
of macro: NUM_DATA.
# ** Warning: ../sim/k7rxxx84x_r12_c1.v(337): [TMREN] - Redefinition
of macro: NUM_BW.
# ** Warning: ../sim/k7rxxx84x_r12_c1.v(338): [TMREN] - Redefinition
of macro: SIZE_MEM.
```

These warnings arise because all the memory models are compiled first, and then each memory model is recompiled with the parameters set in MIG by the user. These messages can be ignored.

Virtex-4 FPGA Designs

This section discusses known simulation issues in Virtex-4 FPGA designs.

DDR2 SDRAM Direct Clocking

- Due to metastable values during power on, warning messages might be displayed. These messages are suppressed in the `sim.do` file and appear only if the design is simulated without using the `sim.do` file generated by MIG. These messages can be ignored.
- In x16 or x8 components with a data width of eight, this warning appears while compiling the design:


```
# ** Warning: [3] ../sim/sim_tb_top.vhd(316): Range 0 to -1 is null.
```

 This warning only appears for VHDL designs and can be ignored.
- If the design is rerun without deleting old files that were generated during simulation, this warning might be displayed:


```
# ** Warning: (vlib-34) Library already exists at "work".
```

 This warning can be ignored.
- While generating the parts using Create Custom Part, proper address values must be entered. For Qimonda parts, 512 MB and 1 GB models are supported. For custom parts of bank address value 3, a 1 GB model is output. If the column address entered is less than or equal to 11, this error message is displayed:


```
"Address is Reversed".
```

 Thus, the column address entered should be greater than 11.

DDR2 SDRAM SerDes

- Due to metastable values during power on, warning messages might be displayed. These messages are suppressed in the `sim.do` file and appear only if the design is simulated without using the `sim.do` file generated by MIG. These messages can be ignored.
- In x16 or x8 components with a data width of eight, this warning appears while compiling the design:


```
# ** Warning: [3] ../sim/sim_tb_top.vhd(316): Range 0 to -1 is null.
```

 This warning only appears for VHDL designs and can be ignored.
- If the design is rerun without deleting old files that were generated during simulation, this warning might be displayed:

```
# ** Warning: (vlib-34) Library already exists at "work".
```

This warning can be ignored.

- When simulating a design for Qimonda parts, the simulator displays this error message:

```
"# QI ERR: Illegal command".
```

This error arises before memory initialization and can be ignored.

- While generating parts using Create Custom Part, proper address values must be entered. For Qimonda parts, 512 MB and 1 GB models are supported. For custom parts of bank address value 3, a 1 GB model is output. If the column address entered is less than or equal to 11, this error message is displayed:

```
"Address is Reversed"
```

Thus, the column address entered should be greater than 11.

DDR SDRAM

- Due to metastable values during power on, warning messages might be displayed. These messages are suppressed in the `sim.do` file and appear only if the design is simulated without using the `sim.do` file generated by MIG. These messages can be ignored.

- In x16 or x8 components with a data width of eight, this warning appears while compiling the design:

```
# ** Warning: [3] ../sim/sim_tb_top.vhd(316): Range 0 to -1 is null.
```

This warning only appears for VHDL designs and can be ignored.

- If the design is rerun without deleting old files that were generated during simulation, this warning might be displayed:

```
# ** Warning: (vlib-34) Library already exists at "work".
```

This warning can be ignored.

RLDRAMII

- Although the DLL is not used, the memory model displays this warning message:

```
"Read prior to DLL locked. Failing to wait for synchronization to occur  
may result in violation of tAC or tdkCk parameters"
```

- For multiplexed addressing mode, the memory model issues displays this error message:

```
"Load mode reserved bits must be set to zero"
```

- Due to metastable values during power on, warning messages might be displayed. These messages are suppressed in the `sim.do` file and appear only if the design is simulated without using the `sim.do` file generated by MIG. These messages can be ignored.

QDRII SRAM

- Due to metastable values during power on, warning messages might be displayed. These messages are suppressed in the `sim.do` file and appear only if the design is simulated without using the `sim.do` file generated by MIG. These messages can be ignored.

DDRII SRAM

- Due to metastable values during power on, warning messages might be displayed. These messages are suppressed in the `sim.do` file and appear only if the design is simulated without using the `sim.do` file generated by MIG. These messages can be ignored.

Spartan-3 FPGA Designs

This section discusses known simulation issues in Spartan-3 FPGA designs.

DDR2 SDRAM

- Due to metastable values during power on, warning messages might be displayed. These messages are suppressed in the `sim.do` file and appear only if the design is simulated without using the `sim.do` file generated by MIG. These messages can be ignored.
- In x16 or x8 components with a data width of eight, this warning appears while compiling the design:

```
# ** Warning: [3] ../sim/sim_tb_top.vhd(316): Range 0 to -1 is null.
```

 This warning only appears for VHDL designs and can be ignored.
- If the design is rerun without deleting old files that were generated during simulation, this warning might be displayed:

```
# ** Warning: (vlib-34) Library already exists at "work".
```

 This warning can be ignored.
- When simulating a design for Qimonda parts, the simulator displays this error message:

```
"# QI ERR: Illegal command".
```

 This error arises before memory initialization and can be ignored.
- While generating parts using Create Custom Part, proper address values must be entered. For Qimonda parts, 512 MB and 1 GB models are supported. For custom parts of bank address value 3, a 1 GB model is output. If the column address entered is less than or equal to 11, this error message is displayed:

```
"Address is Reversed"
```

 Thus, the column address entered should be greater than 11.

DDR SDRAM

- Due to metastable values during power on, warning messages might be displayed. These messages are suppressed in the `sim.do` file and appear only if the design is simulated without using the `sim.do` file generated by MIG. These messages can be ignored.
- In x16 or x8 components with a data width of eight, this warning appears while compiling the design:

```
# ** Warning: [3] ../sim/sim_tb_top.vhd(316): Range 0 to -1 is null.
```

 This warning only appears for VHDL designs and can be ignored.
- If the design is rerun without deleting old files that were generated during simulation, this warning might be displayed:

```
# ** Warning: (vlib-34) Library already exists at "work".
```

 This warning can be ignored.



Section VI: Debug Guide

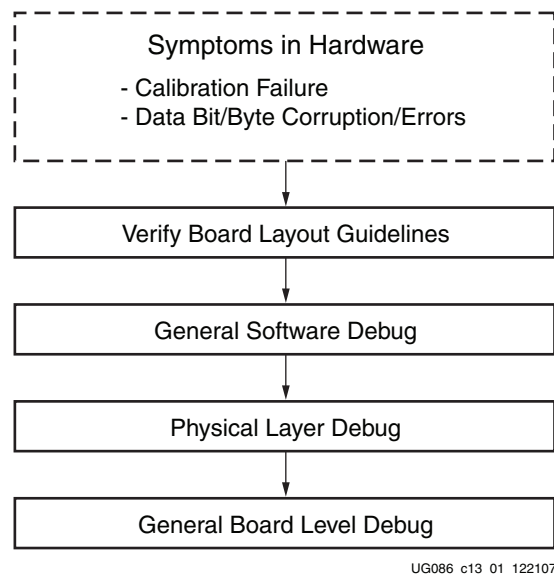
Chapter 14, "Debugging MIG DDR2 Designs"

Debugging MIG DDR2 Designs

Introduction

Debugging problems encountered during hardware testing of MIG-generated memory interfaces can be challenging. Because of the complexity involved in designing with memory interfaces, it is necessary to have a debugging process to narrow down to the root cause of the problem to then be able to focus on the required resolution.

This chapter provides a step-by-step process for debugging designs that use MIG-generated memory interfaces. It provides details on board layout verification, design implementation verification, usage of the physical layer of MIG controllers to debug board-level issues, and general board-level debug techniques. The information in this chapter is specific to DDR2 SDRAM designs. However, the techniques covered can be applied to other memory interfaces. The overall flow for debugging problems encountered in hardware for MIG-based memory interface designs is shown in [Figure 14-1](#):



UG086_c13_01_122107

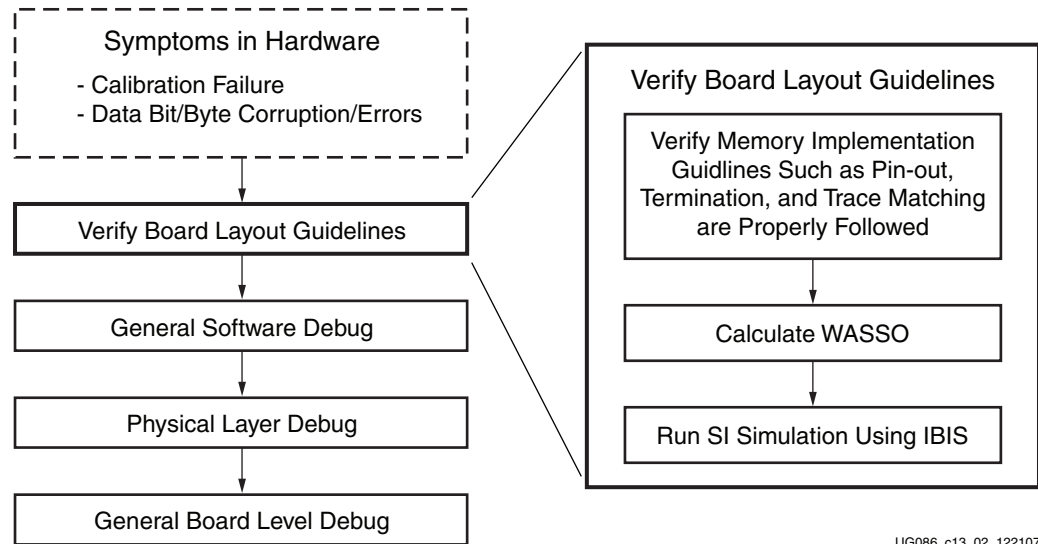
Figure 14-1: MIG Debug Flowchart

The following sections go into detail on each of these important debugging steps to aid in providing resolution to calibration failures and data corruptions or errors.

Verifying Board Layout

Introduction

There are three main steps in verifying the board layout for a memory interface, as shown in [Figure 14-2](#).



UG086_c13_02_122107

Figure 14-2: Verify Board Layout Guidelines

Memory Implementation Guidelines

See [Appendix A, "Memory Implementation Guidelines"](#) for specifications on pinout guidelines, termination, I/O standards, trace matching, and loading. The guidelines provided are specific to both memory technologies as well as MIG output designs. It is very important to verify that these guidelines have been read and considered during board-layout. Failure to follow these guidelines can result in problematic behavior in hardware, which is detailed throughout this chapter.

Calculate WASSO

It is important to take into consideration WASSO limits when generating a MIG pinout. The FPGA data sheets define the SSO limits for each bank. WASSO calculations take this into account along with design-specific parameters, such as board-level inductance, input logic-low threshold, input undershoot voltage, and output loading capacitance. WASSO ensures even distribution of fast/strong drivers across the package, that the number of simultaneously switching outputs does not exceed the per-bank limit and that the chip does not generate excessive ground bounce.

WASSO Calculators for Virtex®-4 devices [\[Ref 34\]](#) or Virtex-5 devices [\[Ref 35\]](#) should be used to find WASSO limits based on board-specific parameters.

These calculations should be run during both pre-board layout and post-board layout. The results found can then be entered in the Bank Selection page of the MIG GUI. (Refer to ["Bank Selection," page 54](#).) MIG follows these WASSO Limits when generating the pinout. Please see [Appendix C, "WASSO Limit Implementation Guidelines"](#) for further information.

Run SI Simulation Using IBIS

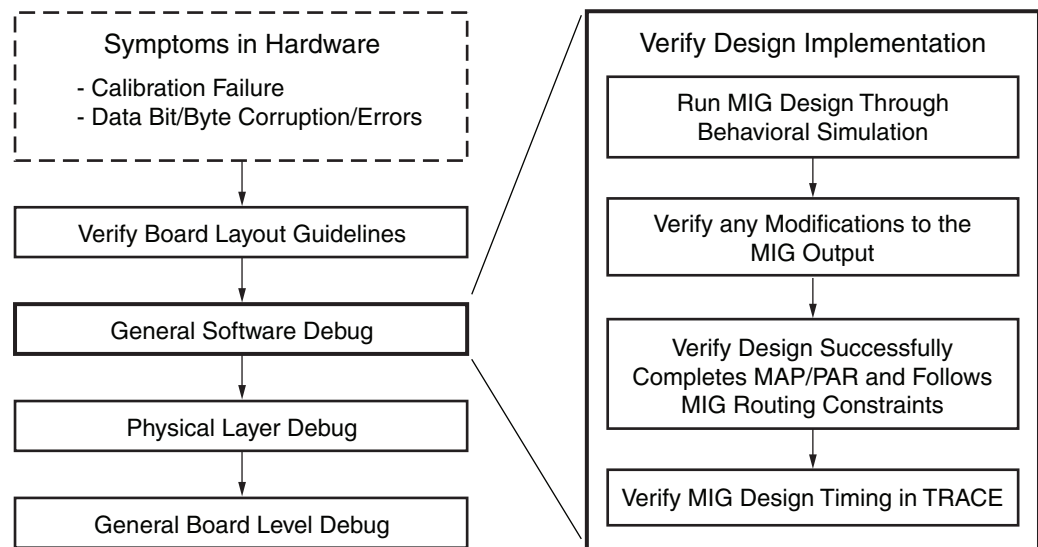
The final critical step in verifying board layout guidelines have been followed is to run signal integrity simulations using IBIS. These simulations should always be run both pre-board layout and post-board layout. The purpose of running these simulations is to confirm the signal integrity on the board.

The ML561 Hardware-Simulation Correlation chapter of the ML561 User Guide [Ref 14] can be used as a guideline. This chapter provides a detailed look at signal integrity correlation results for the ML561 board and can be used as an example for what to look at and what is good to see. It also provides steps to create a design specific IBIS model to aid in setting up the simulations.

Verifying Design Implementation

Introduction

There are four main steps in verifying the design implementation of a MIG output as shown in [Figure 14-3](#):



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Figure 14-3: Verify Design Implementation

Behavioral Simulation

Running behavioral simulation verifies the functionality of the design. Both the example_design and user_design provided with the MIG DDR2 controllers include a complete environment which allows the user to simulate the reference design and view the outputs. Scripts are provided to run behavioral simulation.

- For Virtex-4 family designs, see [“Simulating the DDR2 SDRAM Design”](#) in Chapter 3.
- For Spartan®-3/3E/3A/3AN/3A DSP family designs, see [“Tool Output”](#) in Chapter 8.
- For Virtex-5 family designs, see [“Simulating the DDR2 SDRAM Design”](#) in Chapter 9.

The Xilinx® UNISIM libraries must be mapped into the simulator. If the UNISIM libraries are not set up for your environment, go to the COMPILE chapter of the Development Systems Reference Guide section for assistance compiling Xilinx simulation models and setting up the simulator environment. This guide can be found in the ISE® Software Manuals.

Verify Modifications to MIG Output

There are two modifications to the MIG output that are commonly made:

1. Changing the pinout in the provided output UCF
2. Changing design parameters defined in the output source code

Both of these changes can cause problems with the implemented design that are not always visible to the user.

Changing the Pinout Provided in the Output UCF

MIG allows users to select the desired banks rather than the exact pin locations for the memory interface. This is because specific pin assignment guidelines must be followed. See [Appendix A, “Memory Implementation Guidelines”](#) for detailed pin assignment guidelines.

Following these pin assignment guidelines when making changes to the output pinout ensures proper pin placement. However, design implementation problems can still occur. The Virtex-5 and Spartan-3 FPGA DDR2 designs require specific placement constraints outside of the pin locations. These constraint values are dependent on the pinout and so the constraints output with the MIG UCF are not correct if the pin locations are changed. The Spartan-3 and Virtex-5 FPGA architecture-specific sections of this debug guide provide detailed information on these constraints and how changes cause problems.

It is always recommended to use the MIG pinout. If specific pins in the selected banks cannot be used for the memory interface, use the Reserve Pins feature of the MIG tool. (Refer to section [“Reserve Pins” in Chapter 1.](#)) If changes are made to the Virtex-4 or Virtex-5 FPGA pinout, the Verify UCF and Update Design and UCF feature should always be used to test the changes against the pin assignment guidelines. (Refer to section [“Load mig.prj and UCF” in Chapter 1.](#))

Changing Design Parameters

Often users need to change specific design parameters such as address/data widths, DDR2 memory parameters, and clock period after generating the DDR2 design. These modifications often require multiple changes to the MIG source code that are not always visible to the user. It is always recommended to re-run MIG when making any design parameter change.

For Spartan-3 and Virtex-4 family MIG designs, design parameters are defined through ``defines`. In some cases, changing one design parameter requires changing multiple ``defines` and/or portions of the source code. As an example, when changing the address or data bus widths, the source code replicates multiple instances that depend on the bus width. In this case, it is necessary to instantiate additional elements for new bits manually. Because of required modifications such as this, MIG should always be re-run when a design parameter change is required.

For Virtex-5 FPGA MIG designs, design parameters are defined using top-level parameters and generate statements. Changes to the code are no longer necessary. However, it is still recommended to re-run MIG when making design parameter modifications.

Verify Successful Placement and Routing

In order to ensure proper timing of address/control or writes to the memory, specific flip-flops must be pushed into IOBs. These flip-flops include address, control and data 3-state output. To ensure proper timing, the flip-flops must be located within the IOBs. The MIG source code provides attributes to push these flip-flops into their respective IOBs. The attributes, however, are specific to the synthesis tool selected in the CORE Generator software project options. If XST is selected, the attributes are specific only to XST. Ensure the synthesis tool selected in the CORE Generator software project options is used.

Once the design has successfully complete Place and Route, FPGA Editor can then be used to verify the correct placement of these flip-flops in the IOBs. Search for the address, control, and data IOBs in the 'List1' window under 'All Components.' Individually open each of these IOB components to verify the flip-flop is properly packed in the IOB. If the flops are not properly packed, ensure the synthesis attributes were picked up when running XST or Synplify Pro.

Verify IDELAYCTRL Instantiation for Virtex-4 and Virtex-5 FPGA Designs

Virtex-4 and Virtex-5 FPGA designs require instantiation of the IDELAYCTRL module in the HDL to support the use of the IDELAY ChipSync™ technology elements for read data capture.

Virtex-5 FPGA Designs

MIG uses the “Automatic” method for IDELAYCTRL instantiation: specifically, the MIG HDL only instantiates a single IDELAYCTRL for the entire design. No (LOC) constraints are included in the MIG-generated UCF. This method relies on the ISE tools to replicate and place as many IDELAYCTRLs (for example, one per clock region that use IDELAYs) as needed. Replication and placement are handled automatically by the software tools if the IDELAYCTRLs have the same refclk, reset, and rdy nets. A new constraint, IODELAY_GROUP, is available that associates a set of IDELAYs with an IDELAYCTRL and allows for multiple IDELAYCTRLs to be instantiated without LOC constraints specified. The ISE software generates the IDELAY_CTRL_RDY signal by logically ANDing the RDY signals of every IDELAYCTRL block.

Virtex-4 FPGA Designs

MIG instantiates the required number of IDELAYCTRLs in the RTL, and uses the LOC constraints in the UCF file to fix their locations. The number of IDELAYCTRLs is defined by the IDELAYCTRL_NUM parameter in the idelay_ctrl module. In the RTL, IDELAY_CTRL_RDY is generated by logically ANDing the RDY signals of every IDELAYCTRL block.

For Virtex-5 or Virtex-4 FPGA designs, the IODELAY_GROUP name and IDELAYCTRL LOC constraints should be checked in the following cases:

- The MIG design is used with other IP cores or user designs that also require the use of IDELAYCTRL and IDELAYs.
- Previous ISE software releases 8.2.03i and 9.1i had an issue with IDELAYCTRL block replication or trimming. When using these revisions of the ISE software, the user must instantiate and constrain the location of each IDELAYCTRL individually.

See the *Virtex-4 FPGA User Guide* [Ref 7] and *Virtex-5 FPGA User Guide* [Ref 10] for more information on the requirements of IDELAYCTRL placement.

Verify TRACE Timing

As a final check of proper software implementation of the MIG design, verify that all MIG provided timing constraints have completed successfully. There should be no failed timing paths in the provided MIG constraints. If the design was run in batch mode using the `ise_flow` script file, the TRACE output `<design_name>.twr` file can be opened. If the design was ran using the ISE tools, select the Analyze Post-Place and Route Static Timing option located under the Processes tab.

Debugging the Spartan-3 FPGA Design

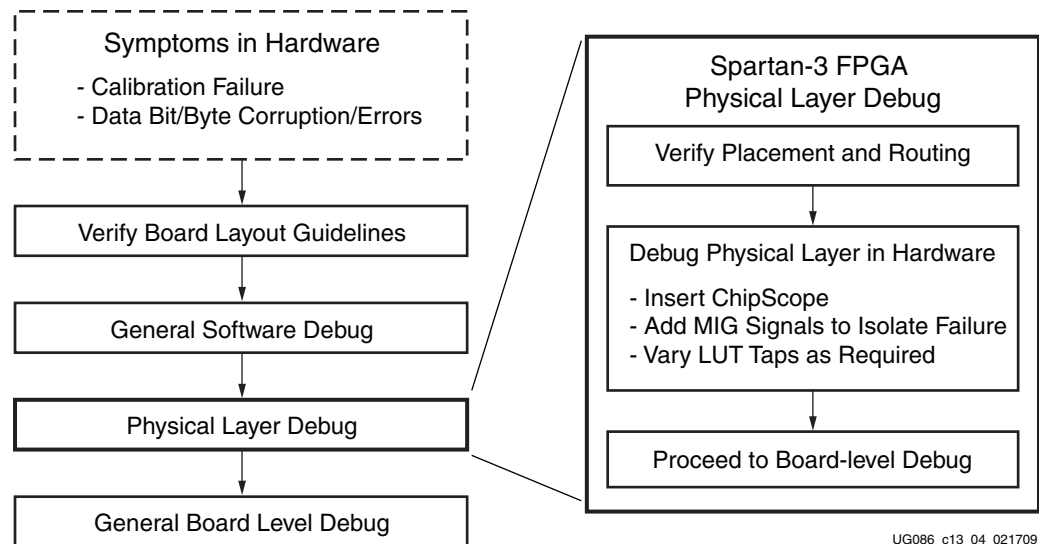
Introduction

For a detailed discussion of the Spartan-3 FPGA DDR2 interface design, see application notes XAPP454 [Ref 15] and XAPP768c [Ref 24].

Read Data Capture

Read data capture is executed using LUT based delay circuits to delay the DQS and loopback signals. The delayed DQS is then used to capture data into LUT RAM based FIFOs with the delayed loopback used as the write enable.

There are four main steps in debugging this data capture implementation as shown in Figure 14-4.



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Figure 14-4: Spartan-3 FPGA Physical Layer Debug

Verify Placement and Routing

The proper implementation of the data capture algorithm requires specific pinout and placement constraints which include PIN, LUT, BEL, and MAXDELAY, as well as usage of template routes during Place and Route.

MIG creates the appropriate UCF for the banks selected and should always be used. If changes are made to the pinout, the remaining placement constraints are no longer correct because these are based on the pin locations. Information on the specific guidelines used in

creating Spartan-3 generation FPGA UCFs are provided in [Appendix A, “Memory Implementation Guidelines.”](#) If these constraints are not followed, the data capture algorithm is not implemented properly and the results in hardware might not be as expected.

When the appropriate UCF is implemented, all related components are placed properly. This correct placement causes two specific routing algorithms (template routes) to be used during implementation of the PAR tools:

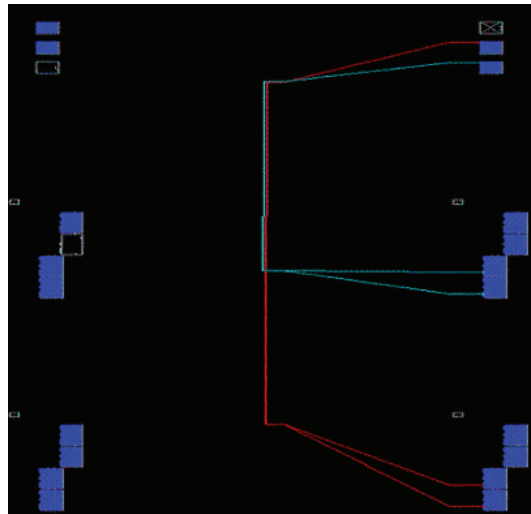
- Routing DQ bits from a PAD to a Distributed Memory component
- Routing delayed DQS strobe signals using Local Clocking resources
 - The PAR tools automatically treats Local Clocks as template routes and locks down the routes correctly without using the environment variable.

DQ Routing

The template router set through the environment variable ensures the data bits are routed from a PAD to a Distributed Memory to capture the data in an Asynchronous FIFO using the Local Clock to write the data, and a Global Clock to read the data. These routes require a template to guarantee that the delay remains constant between all data bits.

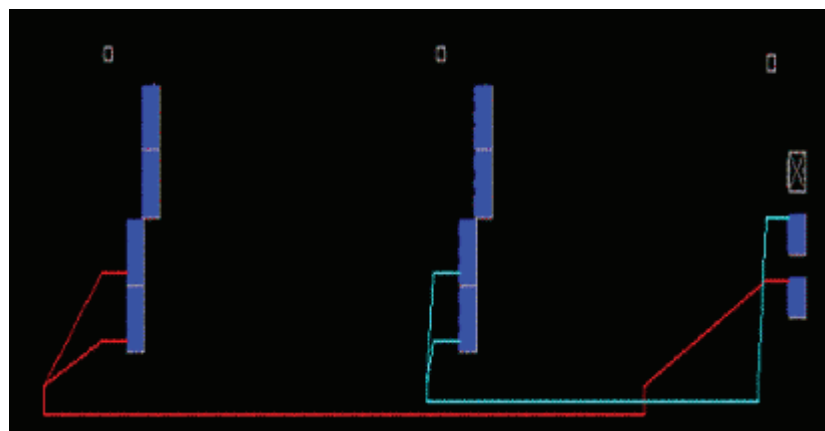
Once the design is implemented, load the resultant `.ncd` and `.pcf` files into FPGA Editor to visually verify the template routes for the data bits, as follows:

1. Open the design in FPGA Editor by selecting **Start** → **Programs** → **Xilinx ISE 10.1i** → **Accessories** → **FPGA Editor**, or load through the View/Edit Routed Design (FPGA Editor) option in the Processes tab of an ISE project.
2. In some cases, turning Stub Trimming off provides a better picture of the route. To do this, select **File** → **Main Properties** and turn off Stub Trimming in the General tab. When Stub Trimming is enabled, FPGA Editor does not display the entire route. If Stub Trimming is disabled, you can see the entire length of the routing segment. Stub Trimming is enabled in [Figure 14-5](#) and [Figure 14-6](#).
3. Search within the List1 window for `*dq*` under the All Nets pull-down. Select all of the DQ data bit nets (e.g., `main_00/top0/dq(0)`) within the window and highlight these nets by clicking the **Hilite** button in the right-hand column. This allows for visual inspection of the delay routes. Zoom into the area with the highlighted nets and verify that the placement looks like [Figure 14-5](#) or [Figure 14-6](#).



UG086_c13_05_122107

Figure 14-5: DQ Placement (Top/Bottom)



UG086_c13_06_122107

Figure 14-6: DQ Placement (Left/Right)

4. Next, verify that the delays on the nets are consistent. Again, select all of the DQ data bit nets in the List1 window. This time click on the **Delay** button located in the right-hand column. This lists the worst-case delay for the DQ bits. Using this delay information, inconsistent routing can be quickly identified. There should be less than 75 ps of skew (ideally less than 50 ps) between the data nets. The delay values depend on the device speed grade and Top/Bottom versus Left/Right implementation but have been observed to range between 300–700 ps.

If preferred, export the delay information to view the report in an Excel spreadsheet. Select **File** → **Export** to export the delay information to a .csv file.

DQS Routing

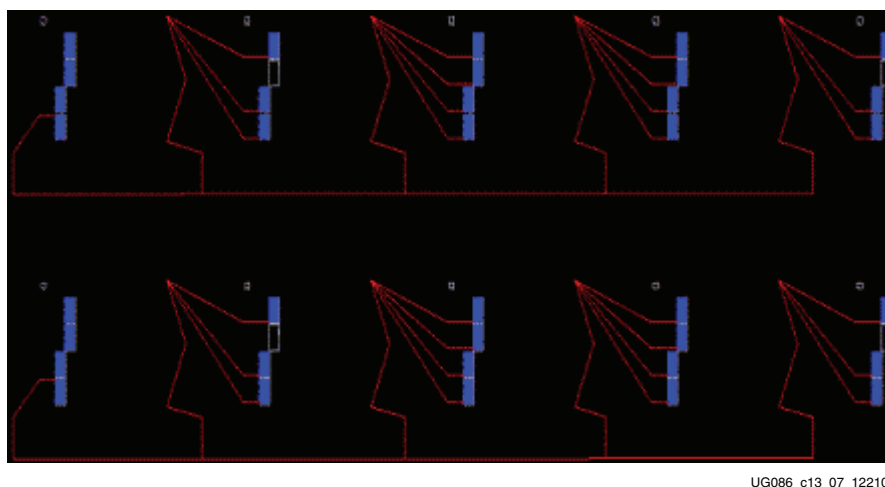
The delayed strobes (dqs*_delayed_col*) need to use the local clocking resources available in the device for the clock routing. The local routing resources used depend on the pin placement specified during generation in the MIG tool. Full hex lines that have low skew

are located throughout the device. Left and right implementations use Vertical Full Hex (VFULLHEX) lines for local clock routing. Top and bottom implementations use VLONG, VFULLHEX, and HFULLHEX lines for local clock routing.

PAR routes from the Local Clock PAD to a series of LUTs to implement the scheme explained in detail in XAPP768c. From the output of the final LUT delay, the delayed strobe/Local Clock (`dqs*_delayed_col*`) routes to all of the FIFO bits.

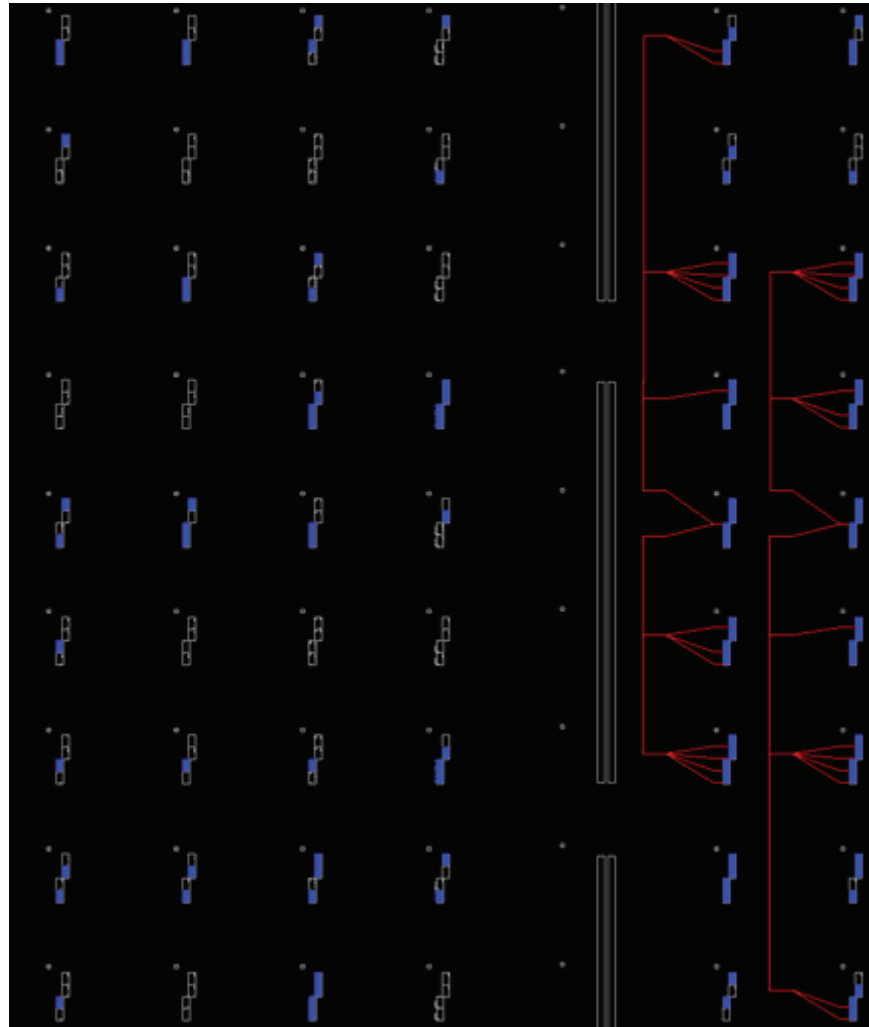
To verify the pinout and usage of the template router, the net skew and max delay on the local clock (`dqs*_delayed_col*`) must be within spec. To verify these values, open the PAR report (`.par` file) and scroll to the Clock Report section. For most Spartan-3 platform devices, the Net Skew is less than 40 ps, and the Max Delay is approximately 550 ps. For Spartan-3A and Spartan-3A DSP devices, the Net Skew is less than 65 ps, and the Max Delay is approximately 400 ps.

The FPGA Editor can then be used to view the local clock placement. To view the template routes for the delayed strobes, search in the List1 window for `*dqs*_delayed_col*` in the All Nets pull-down. Select all the nets (e.g., `main_00/top0/data_path0/dqs0_delayed_col0`) and select **Hilite** from the right-hand column. This command highlights the nets of interest. Then zoom into this range of highlighted signals to view the placement. If local clocking is used, one of the two structures shown in [Figure 14-7](#) and [Figure 14-8](#) is seen.



UG086_c13_07_122107

*Figure 14-7: Local Clock (Top/Bottom) for `dqs*_delayed_col*` LUT Delay Elements*



UG086_c13_08_122107

Figure 14-8: Local Clock (Left/Right) for dqs*_delayed_col* LUT Delay Elements

If the skew and delays are within spec and the layout for the Local Clock and Data bits match the previous figures, the template routes for DQS have been properly implemented.

If the DQ or delayed DQS signals do not verify properly, ensure that the UCF follows the guidelines specified in [Appendix A](#).

Debugging Physical Layer in Hardware

If problems are seen in hardware after verifying the correct implementation of the Spartan-3 generation FPGA design, there are two common issues that cause problems with the data capture algorithm:

- Incorrect Loopback timing
- Incorrect delay on DQS for read capture

Loopback Timing

The timing on the loopback signal is critical to the proper implementation of the data capture algorithm because the delayed loopback signal generates the write enable for the read data FIFOs. The causes for incorrect loopback timing are:

- Incorrect route delay on the loopback signal
 - The loopback signal must be delayed by the sum of the FPGA forward clock and the DQS trace length. This is most commonly implemented through a physical board trace.
- Changes to the MIG pinout after generation

The symptoms of incorrect loopback timing are:

- The first data in a burst is usually corrupted
- Depending on trace delays, only certain bits in the bus exhibit the problem

Incorrect DQS Delay

The appropriate delay on the DQS strobe signals is required for proper implementation of the Spartan-3 generation FPGA data capture algorithm. Common causes for incorrect DQS delay are:

- Mismatch in trace lengths for DQ and DQS
- Changes to the MIG pinout after generation
- Frequency changes without reimplementing of the design

If the delay on DQS is incorrect, the following symptoms can be seen in hardware:

- Incorrect data is seen intermittently
- Incorrect data is always seen

To debug either incorrect Loopback timing or incorrect DQS delay, insert a ChipScope™ Pro analyzer Virtual Input Output (VIO) core into the MIG design. The `tapfordqs1` signal located in the `cal_ctl.v/.vhd` source file should be added to the ChipScope tool VIO to view the number of taps in the delay paths. Use the VIO to increase or decrease the number of LUTs in the delay path while examining the resultant behavior in hardware. The number of taps increases/decreases for both the Loopback delay path and the DQS delay path. Once the appropriate number of LUT delays is found so the data corruption no longer occurs, the number of delays can then be changed within the source code. Changing the number of LUTs in the delay path can compensate for the incorrect loopback timing and incorrect DQS delay. See the *ChipScope Pro User Guide* [Ref 6] for detailed information on using ChipScope tool VIO.

Proceed to General Board-Level Debug

If the above verification of design implementation and debug of the data capture algorithm did not resolve the issues seen in hardware, there could be a problem on the board itself. Proceed to the “[General Board-Level Debug](#)” section for further guidance.

Debugging the Virtex-4 FPGA Direct-Clocking Design

Introduction

This section discusses internal signals to observe in order to assist in isolating problems that could occur during read data timing calibration in the Virtex-4 FPGA DDR2 direct-clocking design. For more information on the calibration algorithm used in this design, refer to application note XAPP702. [\[Ref 19\]](#)

Read Data Capture Timing Calibration

Read data timing calibration is executed over two stages:

- Stage 1: Aligning output of IDDR to internal (FPGA) clock
- Stage 2: Read Data Valid Calibration

The calibration logic is parallel, in that multiple calibration units are instantiated, one for each DQS group (e.g., each calibration unit handles 4 or 8 DQ bits).

What can break during calibration?

- Stage 2 calibration checks for a specific sequence of data back from the memory
- Data bit issues (e.g., stuck-at-bit, PCB trace open/short) causes calibration to hang during Stage 2
 - Each calibration unit must be checked individually to pinpoint exactly which bit(s) failed and/or DQS groups failed

The overall calibration state machine flow diagram is shown in [Figure 14-9](#).

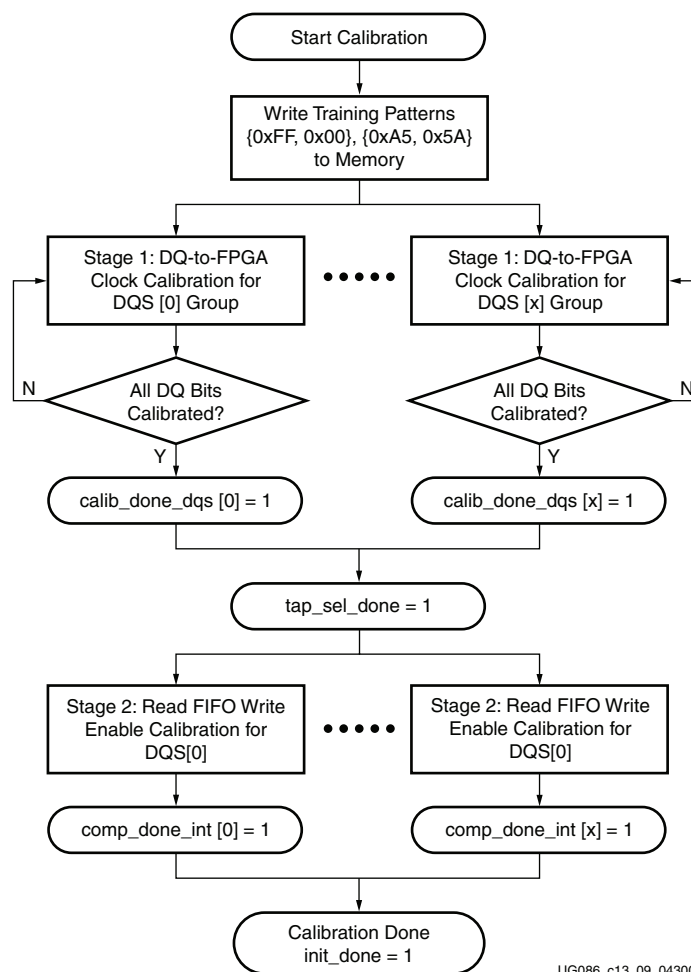


Figure 14-9: Virtex-4 FPGA DDR2 Direct-Clocking Overall Calibration Flowchart

Signals of Interest

The status signals shown in Table 14-1 can be used to help determine where the failure occurs:

Table 14-1: Virtex-4 FPGA Direct-Clocking Status Signals

Signal	Description
calib_done_dqs[x:0]	Asserted when individual Stage 1 calibration units have finished (one per DQS group)
tap_sel_done	Asserted when all Stage 1 calibration units have completed
comp_done_int[x:0]	Asserted when individual Stage 2 calibration units have finished (one per DQS group)
init_done	Asserted when all calibration stages successfully completed

Proceed to General Board-Level Debug

If the above verification of design implementation and debug of the data capture algorithm does not resolve the issues seen in hardware, there could be a problem on the board itself. Proceed to the [“General Board-Level Debug”](#) section for further guidance.

Debugging the Virtex-4 FPGA SerDes Design

Introduction

This section discusses internal signals to observe in order to assist in isolating problems that could occur during read data timing calibration in the Virtex-4 FPGA DDR2 SerDes design. For more information on the calibration algorithm used in this design, refer to application note XAPP721. [\[Ref 23\]](#)

Read Data Capture Timing Calibration

Read data timing calibration is executed over three stages:

- Stage 1: Aligning output of the first stage of the ISERDES to the FPGA clock
- Stage 2: Fine adjustment of Data-to-Strobe (DQ-to-DQS) capture timing into first stage of ISERDES
- Stage 3: Read data valid calibration

The calibration logic is parallel, in that multiple calibration units are instantiated, one for each DQS group (e.g., each calibration unit handles 4 or 8 DQ bits).

What can break during calibration?

- Calibration can hang at any of the stages. All stages look for a specific training pattern back from the memory. If it is not received, calibration sticks in an infinite loop reading back the data.
- Data bit issues (e.g., stuck-at-bit, PCB trace open/short) can cause calibration to hang
 - Each calibration unit must be checked individually to pinpoint exactly which bit(s) failed and/or DQS groups failed

The overall calibration state machine flow diagram is shown in [Figure 14-10](#).

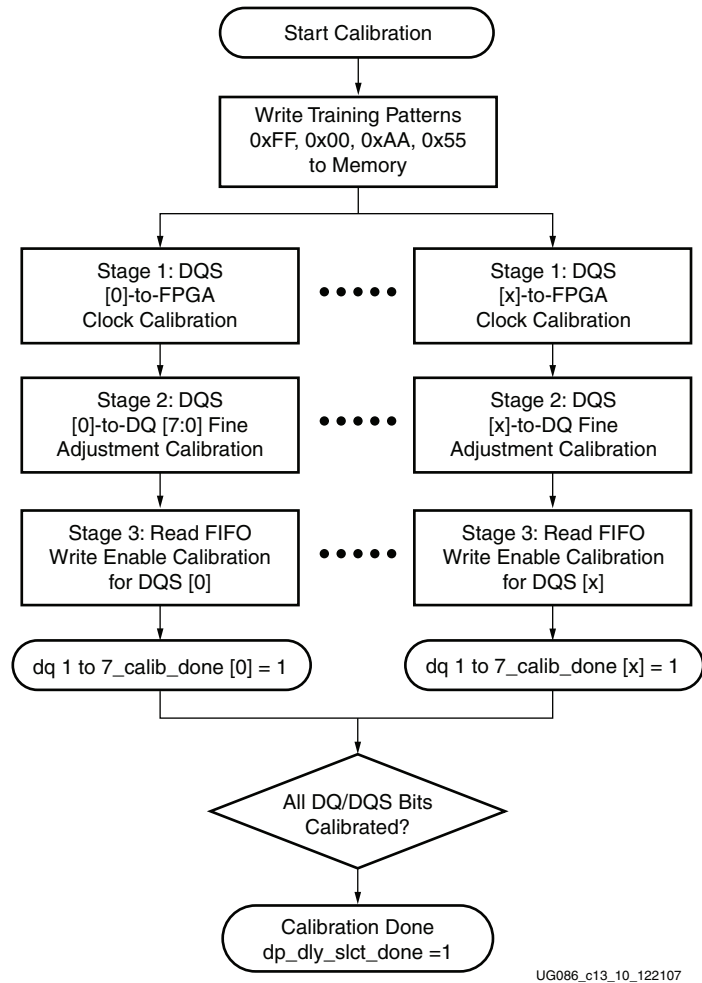


Figure 14-10: Virtex-4 FPGA DDR2 SerDes Overall Calibration Flowchart

Signals of Interest

The status signals shown in Table 14-2 can be used to help determine where the failure occurs:

Table 14-2: Virtex-4 FPGA SerDes Status Signals

Signal	Description
calib_done_dqs[x:0]	Asserted when individual Stage 1 calibration units have finished (one per DQS group)
tap_sel_done	Asserted when all Stage 1 calibration units have completed
comp_done_int[x:0]	Asserted when individual Stage 2 calibration units have finished (one per DQS group)
init_done	Asserted when all calibration stages successfully completed

Proceed to General Board-Level Debug

If the above verification of design implementation and debug of the data capture algorithm did not resolve the issues seen in hardware, there could be a problem on the board itself. Proceed to the [“General Board-Level Debug”](#) section for further guidance.

Debugging the Virtex-5 FPGA Design

Introduction

This section discusses internal signals to observe in order to assist in isolating problems that could occur during read data timing calibration in the Virtex-5 FPGA DDR2 design. Additional UCF and other parameter requirements of this design are also discussed. For more information on this design, refer to application note XAPP858 [\[Ref 27\]](#).

Verify Placement and Routing

Historically, unlike the MIG Spartan-3 FPGA interface designs, most MIG Virtex-4 and Virtex-5 FPGA designs have had only pin location (LOC) and clock (PERIOD) constraints in the UCF. In some cases AREA_GROUP constraints were included to assist with meeting timing. The MIG Virtex-5 FPGA DDR design does require location and internal timing constraints for specific read data capture related circuits.

The MIG Virtex-5 FPGA DDR2 adds a number of additional constraints to the design. This design requires properly setting both top-level parameters in HDL and constraints in the UCF that are pinout-dependent. The additional constraints in the UCF consists of location constraints for certain fabric-based resources, and internal timing (MAXDELAY) constraints. These constraints arise from changes to the read-capture path from previous revisions of MIG Virtex-5 FPGA DDR2 designs.

When creating a design in MIG, MIG automatically generates the proper HDL and UCF constraint values. However, if it becomes necessary to make changes to the MIG-generated pinout, these constraints must be manually modified. The procedure for doing so is discussed in [Appendix B, “Pinout-Related UCF Constraints for Virtex-5 FPGA DDR2 SDRAMs.”](#)

In addition, the MIG Virtex-5 FPGA DDR2 design requires that certain logic placement and routes related to the read data capture be tightly constrained. MAP or PAR issue an error if any of these requirements cannot be met. For more information on these requirements, see [“Constraints,”](#) page 366.

Debugging Calibration Failures

If the phy_init_done signal is not asserted, calibration has failed. To determine why calibration has failed, it is best to start debugging using just the MIG generated example design rather than the full user design. Calibration consists of four stages, as outlined in [“DDR2 SDRAM Design Calibration,”](#) page 375. Although problems can occur in any of the stages, the calibration state machine always passes through the first two stages of calibration regardless of whether or not the correct data was returned from the memory. Because of this, the actual data returned from the memory on rd_data_rise and rd_data_fall during each stage of calibration should be looked at. The signals listed in [Table 14-3](#) should be monitored through the ChipScope analyzer during the calibration stages and compared to the expected data.

Table 14-3: Virtex-5 FPGA SerDes Status Signals

Signal	Description
phy_init_done	Asserted when both initialization of memory and read capture timing calibration has completed
calib_start[3:0]	Pulsed for one clock cycle as each calibration stage is entered
calib_done[3:0]	Driven to a static 1 as each calibration stage is finished
rd_data_rise	Captured (synchronized) rising edge read data from DDR2
rd_data_fall	Captured (synchronized) falling edge read data from DDR2
cal1_dq_count	Binary value indicating the current DQ bit being calibrated during Stage 1
cal2_dq_count	Binary value indicate the current DQS group being calibrated during Stage 2

By triggering on the end of each stage of calibration using the calib_done signals and looking at the read data prior to moving to the next stage, it is possible to determine what caused calibration to fail. The expected data patterns for each stage can be seen in [Table 14-4](#).

Table 14-4: Expected Data Patterns

Stage	rd_data_rise	rd_data_fall
1	All 0xF	All 0x0
2	First word: All 0xF Second word: All 0x0	First word: All 0xF Second word: All 0x0
3	First word: All 0x1 Second word: All 0xE	First word: All 0xE Second word: All 0x1
4	First word: All 0x1 Second word: All 0xE	First word: All 0xE Second word: All 0x1

For further debugging, the calibration state machine can be found in the PHY_CALIB.V/VHD module and is documented in XAPP858 [Ref 27]. The correct behavior can be confirmed by running the example simulation provided by the MIG tool. If calibration fails, it is important to verify that the board layout guidelines have been followed (see “[Verifying Board Layout](#),” page 524) and to proceed to the “[General Board-Level Debug](#),” page 540 section.

Physical Layer Debug Port

The Virtex-5 FPGA DDR2 design HDL contains an optional port to allow the user to observe and control the IDELAY tap values for the DQ, DQS, and DQS Gate signals after read capture timing calibration. This is described in [Appendix E, “Debug Port.”](#)

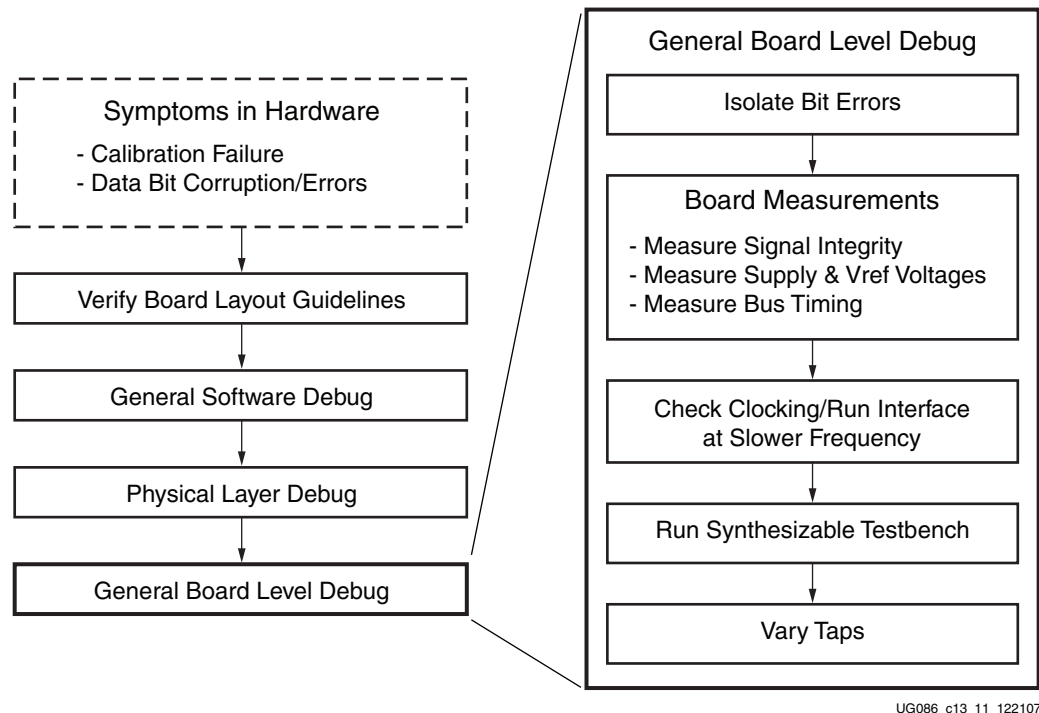
Proceed to General Board-Level Debug

If the above verification of design implementation and debug of the data capture algorithm does not resolve the issues seen in hardware, there could be a problem on the board itself. Proceed to the “General Board-Level Debug” section for further guidance.

General Board-Level Debug

Overall Flow

The flowchart shown in Figure 14-11 documents recommended steps to try during board-level debug.



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Figure 14-11: General Board-Level Debug Flowchart

Isolating Bit Errors

In this step, the user stays in the HDL domain and tries to isolate when/where the bit errors are occurring.

When are the error(s) occurring?

- Data belonging to certain DQS groups?
- On accesses to certain addresses, banks, or ranks of memory?
 - For example, on designs that can support multiple varieties of DIMM modules, make sure to support all possible address and bank bit combinations
- Only occur for certain data patterns or sequences?
 - This can indicate a shorted or open connection on the PCB
 - This can also indicate an SSO or cross-talk issue
- Does the design use multiple DIMM sockets?

- All MIG designs that support multiple DIMM sockets (“deep” configurations) calibrate only on the first DIMM socket, and the maximum frequency is reduced from the maximum achievable if only one rank of memory is used. This was done to account for both the additional loading and the fact that there are no inherent, process-related timing differences between the DIMM sockets. Factors that cause the timing to be different between the DIMMs—for example, PCB trace routing differences between the FPGA and each of the DIMMs—can result in read failures on all but the very first DIMM.

It might also be necessary to determine whether the data corruption is due to writes or reads. This can be difficult to determine because, if the writes are the issue, readback of the data appears corrupted as well. In addition, issues with control/address timing affect both writes and reads. Some experiments that can be tried to isolate the issue:

- If the errors are intermittent, have the controller issue a small initial number of writes, followed by continuous reads from those locations. Do the reads intermittently yield bad data? If so, this might point to a read problem.
- Check/vary the control and address timing:
 - For a heavily loaded control/address bus (as is the case for an unregistered or SO-DIMM), it might be necessary to use 2T timing to allow for more setup and hold time for the control/address signals.
 - Note that the chip select (CS_N) signal to the memory remains a 1T signal, even though it can also have a heavy load. In this case, it might be necessary to advance the assertion of CS_N by a quarter of a clock cycle. This requires changing the code for the CS_N output flop to use CLK90 instead of CLK0.
- Check/Vary only write timing:
 - If on-die termination is used, check that the correct value is enabled in the DDR2 device and that the timing on the ODT signal relative to the write burst is correct.
 - For Virtex-5 FPGA designs, it is possible to use ODELAY to vary the phase of DQ relative to DQS. In addition, a PLL (rather than a DCM) can be used to generate CLK0 and CLK90 used for the write output timing. The phase outputs of a PLL can be fine-tuned, and in this way the phase between DQ and DQS can be varied.
- Vary only read timing:
 - Vary the LUT or IDELAY taps after calibration for the bits that are returning bad data. This affects only the read capture timing.
 - For Virtex-4 and Virtex-5 FPGA designs, check the IDELAY values after calibration. (For the Virtex-5 FPGA DDR2 design, the PHY layer debug port can be used.) Look for variations between IDELAY values. IDELAY values should be very similar for DQs in the same DQS group.

Board Measurements

Refer to the HW-Simulation Correlation Section in the ML561 User Guide [\[Ref 14\]](#) as a guide for expected bus signal integrity.

Supply Voltage Measurements

Check the reference voltage levels:

- For I/O:
 - 1.8V: VCCO, DDR2 VDDQ

- 0.9V: VREF
- 0.9V: VTT Termination
- Internal:
 - 1.8V: DDR2 VDD, DDR2 VDDL
 - 2.5V: FPGA VCCAUX
 - 1.0V or 1.2V: VCCINT

Make sure to check these levels when the bus is active. It is possible these levels are correct when the bus is idle but droop when the bus is active.

Clocking

If the memory interface is having issues running at the target speed, try running the interface at a lower speed.

- Unfortunately, not all designs can accommodate this, as it is dependent on the clock generation scheme used.
- Running at a lower speed increases marginal setup time and/or hold time due to PCB trace mismatch, poor SI, and excessive loading.

If excessive input/system clock jitter might be an issue, the onboard PLL can be used in Virtex-5 FPGA designs to filter input clock jitter.

Synthesizable Testbench

MIG provides a “synthesizable testbench” containing a simple state machine. The state machine takes the place of the user-specific backend logic and issues a simple repeating write-read memory test. This can be used as an alternative to the user's backend logic to provide a test of the memory interface during initial hardware bring-up. The advantage of using the synthesizable testbench is that it rules out any issues with the user's backend logic interfacing with the MIG User Interface block.

The testbench has limitations. It only checks a limited number of memory locations, and the data pattern is a repeating pattern. The user can change the testbench code to expand its capabilities.

Varying Read Capture Timing

For Virtex-4 and Virtex-5 FPGA designs, the IDELAY values for DQ and DQS can be varied post-calibration. The user can determine the extent of the read valid window in this way. The customer can also use this feature for margin testing. This feature is supported in HDL in the Virtex-5 FPGA DDR2 design. In other designs, the user must modify the HDL to add the hooks to vary the IDELAY taps.

For Spartan-3 FPGA designs, LUTs are used to delay the DQS and the loopback signal. The user can modify the code to use a different number of LUT delays to change the DQ-DQS timing, but there is a much larger granularity (approximately 250–600 ps) than with the IDELAY element of Virtex-4 and Virtex-5 FPGAs.

Section VII: Appendices

Appendix A, “Memory Implementation Guidelines”

*Appendix B, “Pinout-Related UCF Constraints for Virtex-5
FPGA DDR2 SDRAMs”*

Appendix C, “WASSO Limit Implementation Guidelines”

Appendix D, “SSO for Spartan FPGA Designs”

Appendix E, “Debug Port”

*Appendix F, “Analyzing MIG Designs in the ChipScope
Analyzer with CDC”*

Appendix G, “Low Power Options”

Appendix G, “Low Power Options”

Memory Implementation Guidelines

This appendix provides rules for designing reference design boards generated by the MIG tool. It is organized into two sections:

- “Generic Memory Interface Guidelines”

The rules in this section apply to all memory interfaces discussed in this document.

- “Memory-Specific Guidelines”

The rules in this section relate to specific memories:

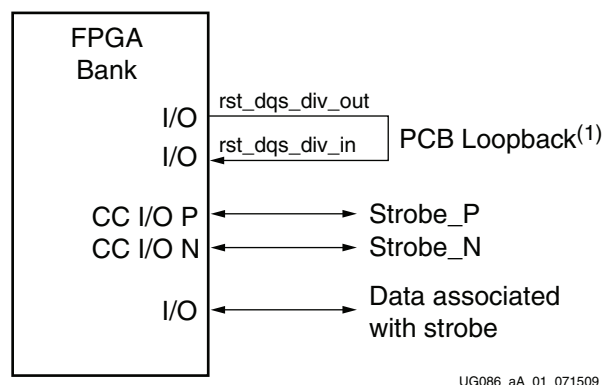
- DDR/DDR2 SDRAM
- QDRII SRAM
- RLDRAM II

UG079 [Ref 9] and UG199 [Ref 14] provide more detailed analysis. UG072 [Ref 8] and UG203 [Ref 12] provide additional information on how to obtain maximum performance for high-speed interfaces.

Generic Memory Interface Guidelines

This section specifies rules common to all memory interfaces. The “Memory-Specific Guidelines” section provides exceptions or additions to any and all guidelines in this section.

Figure A-1 illustrates a typical FPGA bank used to capture read data.



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Notes:

1. Only Spartan FPGA designs require the loopback signal.

Figure A-1: FPGA Bank with Data, Strobes, and PCB Loopback

Timing Analysis

MIG generates timing analysis spreadsheets for all designs of the Virtex®-5 and Virtex-4 families, and Spartan® series under the `docs` folder. Each design has different timing analysis spreadsheets for `read_data_timing`, `write_data_timing`, and `addr_cntrl_timing`.

Evaluation of the PERIOD constraint by the static timing analyzer is not sufficient to determine if the memory interface is functional at a particular frequency. The PERIOD constraint covers the internal timing between synchronous elements. These spreadsheets cover the concept of timing budgets for the interface between the FPGA and memory device.

The spreadsheets provide information about the data valid window and the margins available at the selected frequency. They also provide information about different uncertainty parameters that are to be considered for timing analysis.

Pin Assignments

MIG generates pin assignments for a memory interface based on certain rules depending on the design technique, but does not provide the best possible pin assignment for every board implementation. During layout it might be necessary to swap pin locations depending on the number of layers available and the interface topology. The best way to change the pin assignment is to first apply changes on a byte basis then swap bits within a byte. Calculate the PCB loopback length, if required, after pin swapping and trace matching. The following rules of thumb are provided to help designers determine how pins can be swapped.

Any changes to the pin assignments require modifications to the UCF provided by MIG and might require changes to the source code depending on the changes made.

For all MIG Virtex and Spartan FPGA designs, the address and control pins can be swapped with each other as needed to avoid crossing of the nets on the printed circuit board.

Spartan-3/3E/3A/3A DSP FPGA Memory Implementation Guidelines for DDR/DDR2 SDRAM Interfaces

This section outlines general pin assignment guidelines for DDR/DDR2 SDRAM implementation. However, additional guidelines should be followed when targeting Spartan-3/3E/3A/3A DSP devices.

MIG generates a UCF that follows the guidelines listed below. Xilinx recommends using the pinout created by MIG. Follow the guidelines below if the MIG pinout is modified.

UCF Generation Rules and Temporary File Data Management

The pin allocation rules are different for top/bottom and left/right banks because of the local clock structure of Spartan FPGAs.

Pin Allocation Rules for Left/Right Banks

1. The IOBs of the DQ bits must be placed five tiles above or six tiles below the IOB tile of the associated DQS bit. This is necessary because the MIG design uses low-skew routing resources to route DQS to the data capture FIFOs of its dq bits. The unbonded tiles (even though they cannot be used) also count toward this +5/-6 guideline. Consequently, it is possible that a pinout that meets the above requirements for a specific bus width might not be supported on a different device in the same package

(even though the package is pinout compatible). MIG can be used to generate a design with the same pinout for multiple devices of a single package. This results in separate UCF generation for each device because for the same pinout, the associated SLICE location constraints are different for different FPGA devices.

If a DQS is placed on either the W3 or W4 pins (the two IOBs share a tile) in the XC3S1500-FG676 device, these +5 tiles can be used for the DQ placement:

W1/W2

U7/V7

V4/V5

V2/V3

U5/U6

These -6 tiles can also be used for the DQ placement:

W5/V6

W6/W7

Y1/Y2

AA1/AA2

Y4/Y5

AA3/AA4

2. MIG designs use two columns of CLBs because the Spartan-3 FPGA architectures have only two FIFOs per CLB, and because each bit of data requires two FIFOs, one for rising edge data and the other for falling edge data. Therefore, each bit of data uses one CLB, and the two pads in an I/O tile use two side-by-side CLBs. Due to restricted Spartan-3 FPGA routing, the top pad must always be assigned to the first column and the bottom pad to the second column of CLBs. With this routing implementation, the DQ lines from both pads have nearly the same route delay. For better convention, one of the CLB columns is dedicated for the odd-numbered dq bits (dq[1], dq[3]) and the other is dedicated to the even numbered dq bits (dq[0], dq[2]), depending on the FPGA family and the side (left or right) on which the data banks reside.

When the data bits are assigned on the left side of a Spartan-3 generation FPGA, the rule for assigning dq bits differs for the Spartan-3E FPGA. However, on the right side, it is the same for all Spartan-3 generation FPGAs.

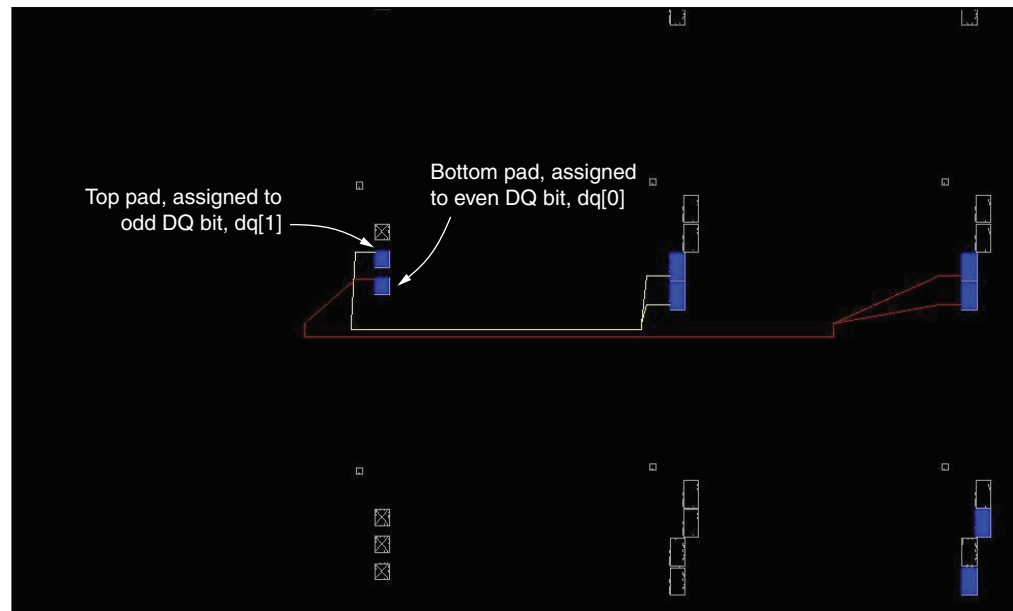
Left side:

- Spartan-3E FPGA: All the even dq signals should be allocated to the bottom pad and odd dq signals to the top pad in an I/O.
- Others: All the even dq signals should be allocated to the top pad and odd dq signals to the bottom pad in an I/O.

Right side:

- All the even dq signals should be allocated to the top pad and odd dq signals to the bottom pad in an I/O.

Figure A-2 shows the DQ bit allocation in an I/O tile of bank 3 (left side) of the XC3S250E-FT256 Spartan-3E FPGA in accordance to the above rule.



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Figure A-2: I/O Pads Connecting to Two Columns of CLBs

3. A byte can be swapped with another byte as long as the pin names of all the necessary signals associated with the byte i.e., DQS, all DQ bits and DM, and the corresponding slice location of all the signals are exchanged.
4. Within a byte, all the even-numbered DQ bits can be swapped only with the other even-numbered bits, and odd-numbered bits only with the other odd bits because two copies of delayed DQS strobes are generated internally for the two columns of CLBs. One of the DQS strobes is used for the even-numbered bits and the other for the odd-numbered bits. Each copy is delayed a specific amount of time relative to the placement of the even (or odd) Read Data FIFOs.
5. The DQ and DQS signals should not be allocated to the IOBs of the same tile.
6. DQS and DQS# should be allocated to a differential pair, such as the pair of IOBs of a single tile, when differential DQS is selected.
7. Memory clock signals ck and ck# should be allocated to a differential pair.
8. DQ, DQS, DM, the memory clocks, and the loopback signals (rst_dqs_div_in and rst_dqs_div_out) should be on the same side of the FPGA.
9. The signals generated in different phases of the clocks should not be allocated in the same I/O tile. The DM and DQ signals are generated on clk90. Thus, these signals cannot be allocated in the same I/O tile where the address, DQS, or control signals that are generated on clk are allocated.
10. For memory interfaces that do not provide a signal to indicate when the read data is valid, a data-valid signal must be provided on the PCB. This loopback is used as a write-enable signal for the Read Data FIFOs. A strobe is used to latch the data. Two pins are needed per design: one to output the signal, and one to input the return signal. The length of the loopback is defined as:

PCB loopback = CLK delay to memory + strobe delay

11. The `rst_dqs_div_in` and `rst_dqs_div_out` signals constitute the loopback pair. To meet the loopback delay requirement, the `rst_dqs_div_in` and `rst_dqs_div_out` signals can be allocated in the same I/O tile.
12. The `rst_dqs_div_in` and `rst_dqs_div_out` signals should be placed at the center of the data bits. If the number of data bytes is even, allocate them at the center of the data bits. If it is odd, allocate them immediately either before or after the centered data byte. If this is not done, the data capture might not be reliable. This is necessary because the MIG design uses the `RST_DQS_DIV` feedback loop to generate a write enable to all the data capture FIFOs.

If the data width is 32, allocate the `rst_dqs_div` pins between the second and the third bytes. However, if the data width is 40, the `rst` pins can be allocated between either the second and third bytes or the third and fourth bytes. Refer to “[Verify Placement and Routing](#),” [page 528](#) for details on these verification steps. For more information on the Spartan-3 FPGA data capture technique, see XAPP768c [\[Ref 24\]](#).

Pin Allocation Rules for Top/Bottom Banks

1. All DQ bits must be placed within five tiles to the right of the associated DQS location.
2. There is no restriction on swapping DQ bits within a DQS group because only one copy of DQS is used to capture the DQ bits. Even DQ bits can be swapped with odd or even DQ bits, and vice versa.
3. Rules 5 to 11 from “[Pin Allocation Rules for Left/Right Banks](#),” [page 546](#) also apply to the top/bottom banks.

Tap Delay Circuit

The Spartan-3/3A/3A DSP FPGA DDR/DDR2 SDRAM and Spartan-3E FPGA DDR SDRAM MIG designs include a tap delay circuit within the physical layer. See XAPP454 [\[Ref 15\]](#) for details.

Proper tap delay implementation requires the circuit logic to be placed in one column. To force the implementation tools to always place the circuit in one column, MIG 2.2 sets the `XIL_PAR_ALIGN_USER_RPMs` environment variable. This is set in the `ise_flow.bat` script file located in the `par` directory of the generated MIG output.

Proper placement of the `tap_dly` circuit in one column can also be implemented with `RLOC_ORIGIN` constraints. This method is recommended if the environment variable causes issues with other parts of the design or if the UCF is being used with an EDK/MPMC design.

Note: MIG 2.3 and later sets the `RLOC_ORIGIN` constraints rather than using the `XIL_PAR_ALIGN_USER_RPMs` environment variable.

An `RLOC_ORIGIN` constraint must be created when the `XIL_PAR_ALIGN_USER_RPMs` environment variable is not used. The value of this constraint is dependent on the `system_clock` bank selection set in the MIG GUI. MIG allows the `system_clocks` to be placed in either top or bottom banks. MIG 2.3 and later generates the required `RLOC_ORIGIN` constraints in the UCF file for placing the `tap_delay` circuits.

Note: The `tap_dly` circuit should be in the same top/bottom location as the BUFG that drives the memory clock.

These are the guidelines to use the `RLOC_ORIGIN` constraints for the UCF generated prior to MIG 2.3:

Top Bank Selection

The MIG output UCF includes an AREA_GROUP constraint on cal_ctl. The first value in the RANGE of this constraint is the value in the added RLOC_ORIGIN constraint. An example AREA_GROUP from a MIG output UCF is:

```
AREA_GROUP "cal_ctl" RANGE = SLICE_X74Y190:SLICE_X85Y203;
```

The first value in the range is X74Y190. This is the new RLOC_ORIGIN value. The syntax for the new constraint to add to the UCF file is:

```
INST "infrastructure_top0/cal_top0/tap_dly0/10" RLOC_ORIGIN = X74Y190;
```

Bottom Bank Selection

The MIG output UCF includes an AREA_GROUP constraint on cal_ctl. To calculate the RLOC_ORIGIN constraint, take the first value in the AREA_GROUP RANGE and add 10 to the X coordinate. An example AREA_GROUP from a MIG output UCF is:

```
AREA_GROUP "cal_ctl" RANGE = SLICE_X74Y4:SLICE_X85Y17;
```

The first value in the range is X74Y4. The new RLOC_ORIGIN value is X84Y4 because 10 is added to the X coordinate. The syntax for the new constraint to be added to the UCF file is:

```
INST"infrastructure_top0/cal_top0/tap_dly0/10" RLOC_ORIGIN=X84Y4;
```

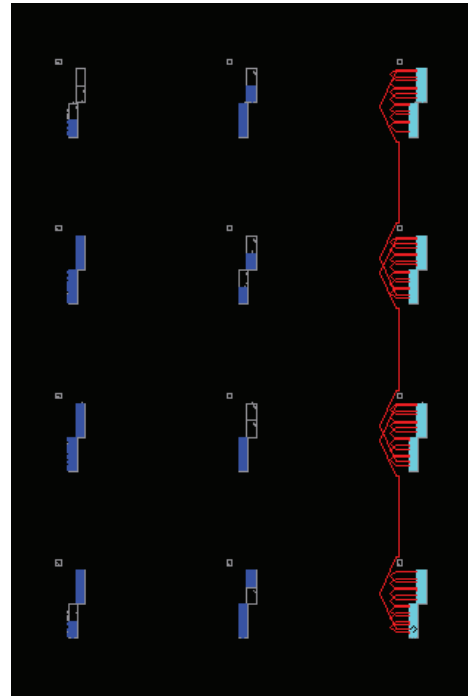
Verification of Tap Delay Circuit Placement

To verify placement of the tap_dly circuit:

1. Open the post-PAR design.ncd and design.pcf files in FPGA Editor.
2. Select **Routed Nets** from the List window located at the top left-hand corner. This shows all the routed net names of the design.
3. Enter ***tap_dly*/tap*** in the Name Filter window to select the tap_dly chain.
4. Select all the nets displayed, and click the **Apply** button on the right-hand side of the Name Filter window.
5. Zoom into the area in the Array window where the selected routes are highlighted.

If properly constrained, the logic is located in a single column in four sequential CLBs. This indicates that the RLOC_ORIGIN is correct.

The screen capture in [Figure A-3](#) shows an example of the correct placement of the tap_dly circuits:



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Figure A-3: Proper Tap Delay Circuit Placement

Note: The hierarchy structure and the naming convention shown in Figure A-3 refer to the MIG generated design. Any change in design hierarchy and naming convention should be taken into account.

Virtex-4 FPGA Direct-Clocking Pins

1. For flexibility of design techniques, it is recommended that all strobe signals be placed on clock-capable inputs (such as DQS, CQ, and QK) with P connected to the P side and N connected to the N side of the pair. If only single-ended strobes are provided, the signal is placed on the P input of the clock-capable I/O pair.
2. Data lines used to read data from a memory are placed in the same bank as their associated strobe. Data is captured with an internal FPGA clock. Data is delayed through the IDELAY element to make it center-aligned with the FPGA clock. The strobe is used to find the data delay with respect to the FPGA clock.
3. Address and control signals are to be placed together in the same bank (see “Memory-Specific Guidelines,” page 554 for exceptions) or placed in banks near each other to minimize the route delays for these signals inside the FPGA.
4. DDRII SRAM ONLY: For memory interfaces that do not provide a data valid signal to indicate when the read data is valid, a data valid signal is to be provided on the PCB. This loopback is used as a write-enable signal for the Read Data FIFOs. A strobe is used to latch the data. Two pins are needed per bank: one to output the signal and one to input the return signal. The length of the loopback is:

$$\text{PCB loopback} = \text{CLK delay to memory} + \text{strobe delay}$$

Virtex-4 FPGA direct-clocking designs that place the strobe on clock-capable I/O should follow the pin-swapping recommendations for the Virtex-4 SerDes and Virtex-5 FPGA designs. If the strobe is not placed on clock-capable I/O, an entire DQS group (containing

data, strobe, and data mask) can be swapped with any other DQS group in same bank. The initial pinout that MIG selects also affects the amount of calibration logic MIG generates. MIG generates one calibration unit for each bank that contains data bits. Therefore, a DQS group cannot be swapped with other byte groups on different banks without appropriate modification to the source code. Within a DQS group, data bits can be swapped with other data bits, and the data signals should be placed on pins near the associated DQS strobe.

Virtex-4 FPGA SerDes Clocking and Virtex-5 FPGA Pins

1. All strobe signals must be placed on clock-capable inputs (such as DQS, CQ, and QK) with P connected to the P side and N connected to the N side of the pair. If only single-ended strobes are provided, the signal is placed on the P input of the clock-capable I/O pair.
2. Data lines used to read data from a memory are placed in the same bank as their associated strobe. Data is captured in the ISERDES block using the strobe signal. The strobe is passed through the BUFIO to delay it with respect to the data input.
3. Address and control signals are to be placed together in the same bank (see [“Memory-Specific Guidelines,” page 554](#) for exceptions) or placed in banks near each other to minimize the route delays for these signals inside the FPGA.
4. DQ signals can transition simultaneously. Concentrating many of them in an I/O bank increases the amount of simultaneous switching noise the I/O bank will experience. Under some conditions it may be desirable to spread the DQ bytes across as many I/O banks as is feasible in the design, back-filling the same banks with address and control signals. Before committing to a PCB layout, check the timing carefully via a place and route run, and check the Simultaneously Switching Output limits.

Virtex-4 SerDes clocking and Virtex-5 FPGA designs must place the strobe on clock-capable I/O with the data for the said strobe placed in the same bank. A byte can be swapped with another byte as long as all the necessary signals associated with that byte (strobe, data, and data mask) are located in the same bank. Within a bank, strobes can be swapped with other strobes while the rest of the pins in a bank can be swapped as needed.

The Virtex-5 FPGA DDR2 design uses a combination of the IOB flop (IDDR) and fabric-based flops for read data capture. This requires the use of pinout-dependent directed-routing and location constraints. If pinouts are changed manually, the UCF must be modified. Refer to [Appendix B, “Pinout-Related UCF Constraints for Virtex-5 FPGA DDR2 SDRAMs”](#) for details.

Termination

These rules apply to termination:

1. IBIS simulation is highly recommended for all high-speed interfaces.
2. Single-ended signals are to be terminated with a pull-up of 50Ω to V_{TT} at the load (see [Figure A-4](#)). A split 100Ω termination to V_{CCO} and 100Ω termination to GND can be used (see [Figure A-5](#)), but takes more power. For bidirectional signals, the termination is needed at both ends of the signal (DCI/ODT or external termination).

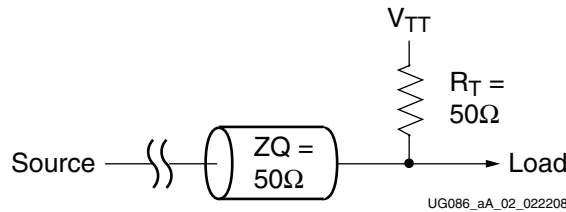


Figure A-4: 50Ω Termination to V_{TT}

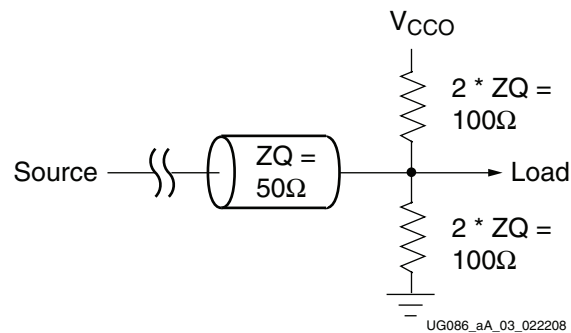


Figure A-5: 100Ω Split Termination to V_{CCO} and GND

- Differential signals are to be terminated with a 100Ω differential termination at the load (see Figure A-6). For bidirectional signals, termination is needed at both ends of the signal (DCI/ODT or external termination).

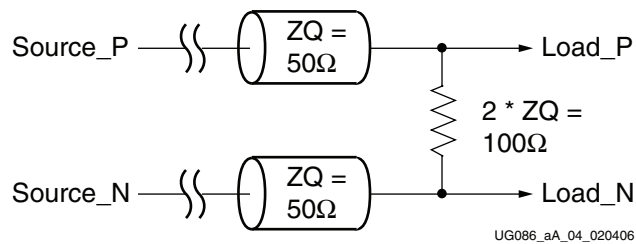


Figure A-6: 100Ω Differential Termination

- All termination must be placed as close to the load as possible. The termination can be placed before or after the load provided that the termination is placed within one inch of the load pin.
- DCI can be used at the FPGA as long as the DCI rules are followed (such as VRN/VRP).

I/O Standards

These rules apply to the I/O standard selection for DDR SDRAMs:

- MIG-generated designs use the SSTL2 CLASS I I/O standard by default for memory address and control signals, and use the SSTL2 CLASS II I/O standard for memory data, data-mask, and data-strobe signals. When DCI is selected in MIG, DCI for SSTL2 CLASS I can be applied only to memory interface signals that are inputs to the FPGA.
- The user can select CLASS II or CLASS I I/O standards from MIG. When SSTL2 CLASS II is selected in MIG, it is applied to all the memory interface signals.
- When DCI is selected in MIG, the DCI I/O standard is applied to all the memory interface signals.

These rules apply to the I/O standard selection for DDR2 SDRAMs:

- MIG-generated designs use the SSTL18 CLASS II I/O standard by default for all memory interface signals. When DCI is selected in MIG, DCI for SSTL18 CLASS II is applied on input, output, and in-out memory interface signals.
- CLASS II is recommended for all SSTL signals in memory interfaces. However, better signal integrity can sometimes be achieved with CLASS I for the address/control group. The user can select between CLASS II or CLASS I I/O standards from the MIG tool. Based on the IBIS simulation results, the CLASS should be selected in the GUI.
 - Selection of the CLASS option is allowed only for the address/control group in Virtex-4 and Virtex-5 FPGA designs. Data group signals always use the SSTL18 CLASS II I/O standard. When SSTL18 CLASS I is selected in the MIG tool, the I/O standard for differential signals (such as memory clocks) remains SSTL18 CLASS II.
 - CLASS can be selected for both data and address/control groups in Spartan-3 FPGA designs. When SSTL18 CLASS I is selected in the MIG tool, the I/O standard for all signals of the selected group is SSTL18 CLASS I.
- When DCI is selected in MIG for SSTL18 CLASS I, the DCI I/O standard is applied only to memory interface signals that are outputs to the FPGA.

Trace Lengths

Trace length matching must also include the package delay information. The PARTGen utility [Ref 33] generates a .pkg file that contains the package trace length in microns for every pin of the device under consideration.

For example, to obtain the package delay information for a Virtex-5 LX50T-FF1136 device used on an ML561 board, issue the following command within a DOS command shell:

```
partgen -v xc5v1x50tff1136
```

This generates an xc5v1x50tff1136.pkg file in the current directory with package trace length information for each pin (unit: micron or μm). Use the typical 6.5 fs per micron (6.5 ps per millimeter) conversion formula to obtain the corresponding electrical propagation delay. While applying specific trace-matching guidelines for each of the memory interfaces as described below, consider this additional package delay term for the overall electrical propagation delay. Note that different die in the same package may have different delays for the same package pin. If this case is expected, average the values appropriately.

Calibration factors out PCB trace mismatches during reads, but the trace matching requirements are needed during writes.

Memory-Specific Guidelines

Each memory interface has three sections:

- Pin assignments
- Termination
- Trace lengths

Trace lengths given are for high-speed operation and can be relaxed depending on the applications target bandwidth requirements. Be sure to include the package delay when determining the effective trace length. These internal delays can be found through the PACE tool.

DDR/DDR2 SDRAM

Pin Assignments

These rules apply to pin assignments for DDR and DDR2 SDRAM:

1. The DQ and DM bits of a byte are to be placed in the same bank as the associated DQS. The DQ bits must be kept close together for better routing.
2. Address and control signals are to be placed in the same bank or placed in banks near each other.
If all control signals cannot fit in one bank, CK, ODT, and CKE should be selected first for placement in another bank.
3. Spartan FPGA designs require a loopback signal. The loopback signal should be placed at the center of the DQ bits.

If a bank is pin-limited and there is a need to free up a few pins, the following actions are to be considered:

1. The loopback signals can be eliminated in Virtex-4 FPGA MIG designs because they are no longer required.
2. The CKE signals can be tied together for multiple devices.
3. For DIMMs, non-critical features need not be implemented, such as PAR_IN/PAR_OUT and the SPD interface (SA, SPD, SCL).

The loading of address (A, BA), command (RAS_N, CAS_N, WE_N), and control (CS_N, ODT) signals depends on various factors, such as speed requirements, termination topology, use of unbuffered DIMMs, and multiple rank DIMMs.

The address and command signals should be implemented with 2T clocking, i.e., asserted for two cycles, so these signals can handle higher loading without impacting the timing budget. Virtex-4 FPGA SerDes designs and Virtex-5 FPGA DDR2 designs are implemented with 2T clocking of address and command signals.

The control signals (CS_N and ODT) have 1T clocking, and so their replication is recommended when the loading is higher. If the application is pin-limited to implement lighter loading on critical clock signals going to memory, it might be necessary to use an external PLL to generate multiple copies of the clock signals.

For descriptions of 1T and 2T clocking, refer to Micron technical note TN-47-01[Ref 36].

Termination

These rules apply to termination for DDR/DDR2 SDRAM:

1. For DIMMs, the CK signals are to be terminated by a 5 pF capacitor between the two legs of the differential signal instead of the 100Ω resistor termination, because these signals are already terminated on each DIMM.

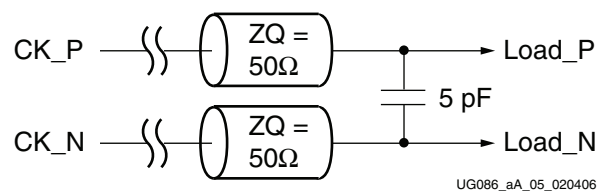


Figure A-7: 5 pF Differential Termination on Clocks

2. The ODT and CKE signals are not terminated. These signals are required to be pulled down during memory initialization with a 4.7 k Ω resistor connected to GND.
3. ODT, which terminates a signal at the memory, applies to the DQ/DQS/DM signals only. If ODT is used, the Mode register must be set appropriately in the RTL design.
4. The Virtex-5 FPGA DDR2 interface requires that if parallel termination is used at the memory end, it must be ODT rather than external termination resistor(s). This is a requirement of the read capture scheme used.

To save board space, DCI at the FPGA and ODT at the memory can be used to minimize the number of external resistors on the board.

Trace Lengths

These rules indicate the maximum electrical delays between DDR/DDR2 SDRAM signals at 333 MHz:

1. ± 25 ps maximum electrical delay between any DQ and its associated DQS/DQS#
2. ± 50 ps maximum electrical delay between any address and control signals and the corresponding CK/CK#
3. ± 100 ps maximum electrical delay between any DQS/DQS# and CK/CK#

QDRII SRAM

Pin Assignments

These rules apply to pin assignments for Virtex-4 FPGA QDRII SRAM:

1. All CQ signals are placed on clock-capable pins, if the Use CC option is selected; otherwise any I/O pin is used. CQ is only connected to the P side of the P-N pair.
2. The Q bits of a byte are placed in the same bank as its associated CQ.
The Q bits must be kept close together for optimal routing.

These rules apply to pin assignments for Virtex-5 FPGA QDRII SRAM:

1. All CQ/CQ# signals are placed on clock-capable pins. CQ and CQ# are connected only to the P side of the CC P-N pair.
2. The Q bits of a byte are placed in the same bank as its associated CQ/CQ#.
The Q bits must be kept close together for optimal routing.

Termination

These rules apply to termination of QDRII SRAM signals:

1. Termination of the qdr_dll_off_n signal should be done based on the recommendation of the memory vendor. If the vendor requires this signal to be driven by the FPGA, this signal should be pulled down with a 4.7 k Ω resistor connected to GND. However, if the vendor requires this signal not to be driven by the FPGA, this signal should be connected to a pull-up resistor with a value recommended by the SRAM vendor.
2. DCI can also be used on CK for QDRII+ support (QVLD signal from memory to FPGA).

To save board space, DCI is to be used at the FPGA to minimize the number of external resistors on the board.

I/O Standards

These rules apply to the I/O Standard selection for QDRII SRAM.

- MIG-generated designs use the HSTL CLASS I I/O standard by default for all memory interface signals.
- When DCI is selected in MIG, the DCI standard for HSTL CLASS I is applied only to memory interface signals that are inputs to FPGA.

Trace Lengths

These rules provide the maximum electrical delays between QDRII SRAM signals:

1. ± 25 ps maximum electrical delay between data and its associated CQ.
2. ± 50 ps maximum electrical delay between address and control signals.
3. ± 100 ps maximum electrical delay between address/control and data.
4. ± 100 ps maximum electrical delay between address/control and K/K# clocks.
5. ± 25 ps maximum electrical delay between data (write port) and K/K# clocks.
6. There is no relation between CQ and the K clocks. K should be matched with D, and CQ should be matched with Q (read data).

DDRII SRAM

Pin Assignments

These rules apply to pin assignments for Virtex-4 FPGA DDRII SRAM:

1. All CQ signals are placed on clock-capable pins, if the Use CC option is selected; otherwise, any I/O pin is used. CQ is only connected to the P side of the P-N pair.
2. The Q bits of a byte are placed in the same bank as its associated CQ. The Q bits must be kept close together for optimal routing.

These rules apply to pin assignments for Virtex-5 FPGA DDRII SRAM:

1. All CQ/CQ# signals are placed on clock-capable pins. CQ and CQ# are connected only to the P side of the CC P-N pair.
2. The Q bits (SIO designs) or DQ bits (CIO designs) of a byte are placed in the same bank as its associated CQ/CQ#. The Q bits or DQ bits must be kept close together for optimal routing.

Termination

These rules apply to termination of DDRII SRAM signals:

1. Termination of the `ddr_dll_off_n` signal should be done based on the recommendation of the memory vendor. If the vendor requires this signal to be driven by the FPGA, this signal should be pulled down with a 4.7 k Ω resistor connected to GND. If the vendor requires this signal not to be driven by the FPGA, this signal should be connected to a pull-up resistor with a value recommended by the SRAM vendor.

To save board space, DCI is to be used at the FPGA to minimize the number of external resistors on the board.

I/O Standards

These rules apply to the I/O Standard selection for DDRII SRAM:

- MIG-generated designs use the HSTL CLASS I I/O standard by default for all memory interface signals except the DQ/Q and CQ/CQ# signals.
- When DCI is selected in the MIG tool, the DCI standard for HSTL CLASS I is applied only to memory interface signals that are inputs to the FPGA, except the CQ/CQ# and DQ/Q signals where the HSTL CLASS II DCI standard is applied.

Trace Lengths

These rules provide the maximum electrical delays between DDRII SRAM signals:

1. ± 25 ps maximum electrical delay between data and its associated CQ.
2. ± 50 ps maximum electrical delay between address and control signals.
3. ± 100 ps maximum electrical delay between address/control and data.
4. ± 100 ps maximum electrical delay between address/control and K/K# clocks.
5. ± 25 ps maximum electrical delay between data (write port) and K/K# clocks.
6. There is no relation between CQ and the K clocks. K should be matched with D, and CQ should be matched with Q (read data).

RLDRAM II

Pin Assignments

These rules apply to pin assignments for RLDRAM II:

1. All QK signals are to be placed on Clock-Capable I/O pairs if the Use CC option is selected in the tool; otherwise normal I/O pins are used. P is connected to the P side and N is connected to the N side of the pair.
2. The DQ bits of a byte are placed in the same bank as the associated QK.
The DQ bits must be kept as close as possible for optimal routing.
3. The loopback signal is not required because RLDRAM II provides a data valid signal for capturing the read data.

If the design is pin constrained, only common I/O (CIO) can use a bidirectional DQ data bus.

Termination

This rule applies to termination of RLDRAM II signals:

1. DCI can be used on DQ/QK at the FPGA provided that DCI rules are followed (such as VRN/VRP).

To save board space, use DCI at the FPGA and ODT at the memory to minimize the number of external resistors on the board.

I/O Standards

These rules apply to the I/O Standard selection for RLDRAM II:

- MIG-generated designs use the HSTL CLASS II I/O standard by default for all memory interface signals. When DCI is selected in MIG, DCI for HSTL CLASS II is applied on input, output, and in-out memory interface signals.
- The user can change the I/O standard to HSTL CLASS I. When DCI is selected in MIG, DCI for HSTL CLASS I is applied only to the memory interface signals that are inputs to the FPGA.
- To have HSTL CLASS I on the required pins, the user must manually edit the UCF constraint file for the corresponding design generated.

Trace Lengths

These rules provide the maximum electrical delays between RLDRAM II signals:

1. ± 25 ps maximum electrical delay between data and its associated QK.
2. ± 50 ps maximum electrical delay between address and control signals.
3. ± 100 ps maximum electrical delay between address/control and data.

Pinout-Related UCF Constraints for Virtex-5 FPGA DDR2 SDRAMs

Introduction

The Virtex®-5 FPGA DDR2 design generated by MIG requires a number of UCF constraints. The values of these UCF constraints might need to be changed if, after using MIG to generate the design, the user changes the data strobe (DQS) pin (and, by extension, the DQ data pin) assignments. In addition, these constraints might need to be changed, or in some cases, added when updating from an older version of the DDR2 design.

Update Design should always be used to update the design and regenerate the updated constraint values. This chapter describes the parameters/UCF constraints that are modified by the Update Design option, and the architectural reasons why the UCF constraints are required. For more information on Update Design, see [“Verify UCF and Update Design and UCF” in Chapter 1](#).

Update Design should be used in these situations:

- The user has a DDR2 design generated using an older version of MIG and needs to upgrade to the latest version of the DDR2 interface
- The user has generated a design using the latest version of MIG and needs to make modifications to the pinout that affect the location of the strobe (DQS) pins. This would occur if the user is swapping DDR2 data byte locations to improve PCB routability.

Historically, additional pinout-related constraints (other than pin number LOC constraints) were not required for MIG 1.73 or earlier DDR2 designs. Because of changes to the read data capture circuitry, these constraints were required starting with MIG 2.0 designs. With MIG 3.0, the required pinout-related constraints have been significantly simplified but not completely eliminated. This section discusses the relevant parameters and constraints for MIG 3.0 and later.

Read Data Capture Block Diagram

The read capture path used for the MIG Virtex-5 FPGA DDR2 interface consists of these subblocks:

- DQ is initially captured using DQS in the IOB using the IDELAY and IDDR elements.
- Data is transferred to the FPGA (CLK0) clock domain using a series of flip-flops located in the fabric. The location of these flip-flops, and the routes between the IDDR and fabric flip-flops, must be carefully defined and matched. In MIG 2.x designs, the flip-flop locations and routing are defined using a combination of RPMs and directed routing constraints. With MIG 3.0, attributes such as XIL_PAR_SKEW and

XIL_PAR_DELAY are embedded in the RTL to allow the ISE® tools to place and route this circuit and meet the required net delay and intra-net skew without the use of the RPM and directed routing constraints.

- For each DQS, a circuit is added to disable the clock enable (CE) pin to each of the corresponding DQ capture IDDRs at the end of a read burst (“DQS Gate”). The placement and routing of this circuit is also critical and is defined by a combination of LOC and MAXDELAY constraints in the UCF.

Figure B-1 shows the read capture path architecture for the MIG Virtex-5 FPGA DDR2 design, as well as the various portions of the capture path that are affected by the additional UCF constraints.

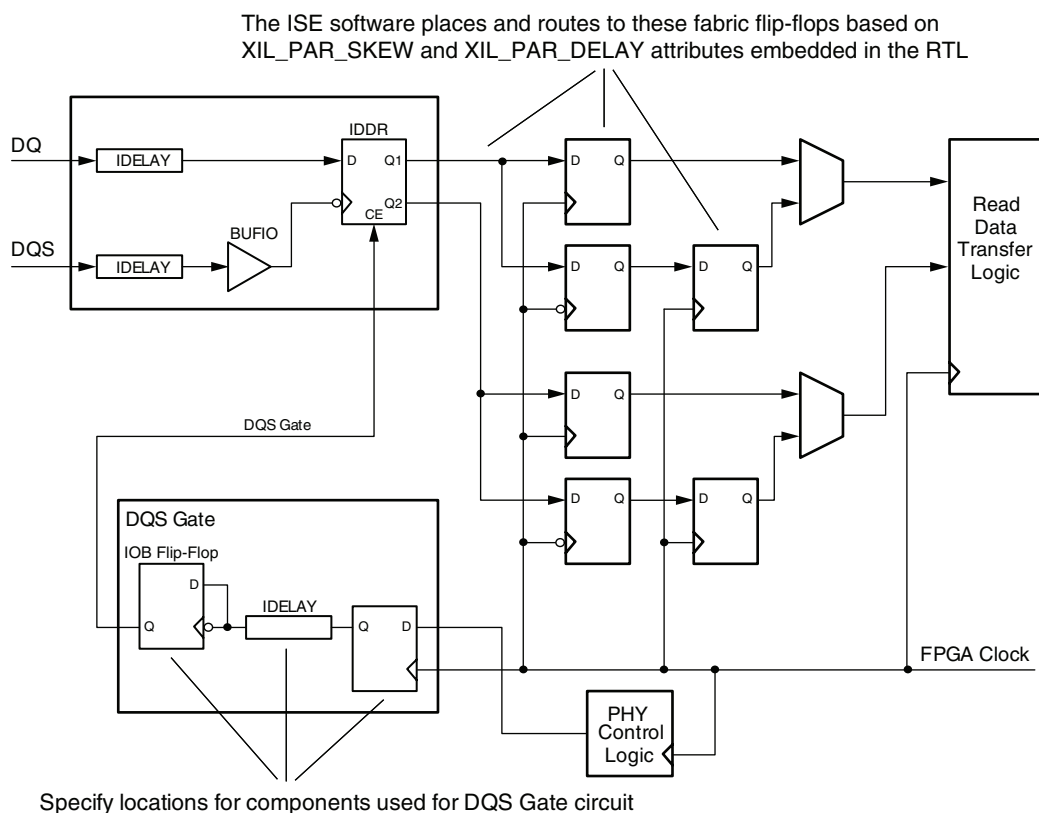


Figure B-1: Virtex-5 FPGA DDR2 Read Capture Path, MIG 3.1 or Later

Pinout-Related UCF Changes Overview

When updating a design whose pinout has been modified, MIG makes specific changes to the UCF file. For each DQS pin:

- A location constraint pair for an IDELAY (input delay element) and IOB flip-flop must be specified. These two elements are used in the DQS Gate circuit, of which there is one per DQS group. The value of the LOC constraint for the IDELAY and IOB flip-flop are determined by the pin location for the corresponding DQS IOB. The rules for determining this value are outlined in “Setting UCF Constraints,” page 563.
- A location constraint for a single fabric flip-flop must be specified. This locks the flip-flop used to drive the DQS Gate signal close to its corresponding IDELAY. This is required to reduce the total net delay on this route, and therefore the delay

fluctuations on this line due to voltage/temperature. The rules for determining this value are outlined in ["Setting UCF Constraints."](#)

Setting UCF Constraints

Beyond the typical constraints found in a UCF file (e.g., the PERIOD timing constraint, pinout LOC, and IOSTANDARD constraints for I/O), the Virtex-5 FPGA DDR2 interface also requires three other classes of constraints to be added to the UCF file. (These constraints are updated upon using the Update Design option.) MIG automatically generates the correct values of these constraints for a new design and updates the values when Update Design is used. These values are based on the pinout and speed grade/operating frequency of the design. The three classes of constraints are:

1. **Location (LOC) constraints for the IDELAY and IOB flip-flop blocks used for every DQS Gate circuit.** There is one DQS Gate circuit per DQS I/O.
2. **MAXDELAY constraints to limit the delay timing-critical paths related to IOB timing.** This is not required to meet any specific cycle-to-cycle timing requirement, but rather to limit any post-calibration voltage/temperature related changes to the net delay. Voltage/temperature variations on a particular net increase as the total net delay increases.

It is critical to reduce the delay on the DQS gate control input. This signal is generated in the CLK0 clock domain and synchronized via an IDELAY to the DQS domain. The synchronization between the CLK0 and DQS domains on this control net is established once during initial calibration. Calibration accounts for the "static" delay component of these nets. However, post-calibration changes in net delay are not accounted for and must be minimized.

3. **FROM-TO constraints:**
 - a. One FROM-TO constraint limits the DQS Gate path from the IOB flip-flop to the DQ CE pins to be approximately one-half clock cycle. This ensures that the DQ clock enables are deasserted before any possible DQS glitch at the end of the read postamble can arrive at the input to the IDDR. This value is clock-frequency dependent:

```

INST "*/gen_dqs*.u_iob_dqs/u_iddr_dq_ce" TNM = "TNM_DQ_CE_IDDR";
INST "*/gen_dq*.u_iob_dq/gen_stg2*.u_iddr_dq" TNM =
    "TNM_DQS_FLOPS";
TIMESPEC "TS_DQ_CE" = FROM "TNM_DQ_CE_IDDR" TO "TNM_DQS_FLOPS"
    1.6 ns;

```
 - b. Additional FROM-TO constraints define multi-cycle paths in the design. These are added to help meet internal (fabric) timing at the higher supported frequencies. At lower frequencies of operation, these multi-cycle path constraints might not be required and can be removed.

Constraint class (1) is discussed in this section. Classes (2) and (3) are not discussed. Their values do not need to change if the pinout is modified.

Determining FPGA Element Site Locations

Setting the correct location constraint for the IDELAY in a DQS Gate circuit requires that the site name for the location where the corresponding DQS_N pin is placed be correctly specified. For example, on an XC5VLX50T-FF1136 device, if DQS_N[0] is located on pin C13, the site name for this location must be known. In this case, it is "IOB_X2Y216" and the LOC constraint is set to:

```
INST "*/gen_dqs[0].u_iob_dqs/u_idelay_dq_ce" LOC = "IDELAY_X2Y216";
```

MIG automatically determines the correct site names when generating a new design or updating an existing design. Site names can also be determined graphically using FPGA Editor, or by using the PARTGen utility to generate a package file for the appropriate device/package combination in text format.

Setting DQS Gate Circuit Location Constraints

Each DQS Gate circuit requires the use of an IDELAY and IOB flip-flop in addition to fabric-based slice resources. The IDELAY and IOB flip-flop for each DQS Gate circuit, as well as the fabric flip-flop driving the IDELAY must be manually located in the UCF file. There are three constraints for every DQS in the design.

The IDELAY and IOB flip-flop must be taken from an IOB site where these resources are available, specifically an IOB site that is used only as an output, or is totally unused. This can be one of the following:

- The DQS_N negative-side I/O site of the DQS differential I/O pair of the corresponding DQS group. A differential I/O pair does not use the input-side resources on the N-side leg of the pair.
- The DM output site for the corresponding DQS group. The DM is an output-only site, and its input-side resources are available for use by the DQS Gate circuit.
- Any IOB site that is either output-only, or unused.

The best site to use is one that is closest in proximity on the FPGA die to the four or eight DQ I/O sites in that DQS group. This reduces the routing delay on the clock enable control from the DQS Gate circuit to its corresponding DQ sites. At higher frequencies, this can often be the critical timing path, because there is only about half a clock cycle for this path. MIG always chooses to place the IDELAY and IOB flip-flop on the DQS_N site for the corresponding DQS group. However, depending on the particular user pinout, a better site might be available. The user might have to relocate the DQS Gate location(s) to other sites in order to meet timing.

The IDELAY and IOB flip-flop for a given DQS Gate circuit must be placed at the same site. They cannot be placed on different sites.

These constraints are used for locating the IDELAY and IOB flip-flop:

```
INST "*/gen_dqs[<x>].u_iob_dqs/u_iddr_dq_ce" LOC = "ILOGIC_<SITE>";
INST "*/gen_dqs[<x>].u_iob_dqs/u_idelay_dq_ce" LOC = "IDELAY_<SITE>";
```

Where <x> denotes the DQS group number, and <SITE> denotes the I/O site name.

For example, on an XC5VLX50T-FF1136 device, if DQS_N[0] is placed on pin K9, and this site is chosen to locate the IDELAY and IOB flip-flop for the DQS Gate circuit for DQS[0], the constraints are:

```
INST "*/gen_dqs[0].u_iob_dqs/u_iddr_dq_ce" LOC = "ILOGIC_X2Y218";
INST "*/gen_dqs[0].u_iob_dqs/u_idelay_dq_ce" LOC = "IDELAY_X2Y218";
```


The fabric flip-flop driving the IDELAY with the DQS Gate control pulse must also be location constrained to be near the corresponding IDELAY/IOB flip-flop. The rules for determining this are:

- Locate the IOB where the corresponding IDELAY and IOB flip-flop are location constrained.
- Use the appropriate package file to find the “nearest CLB.” Location constraint this flip-flop to this location.

For example, on an XC5VLX50T-FF1136 device, if DQS_N[0] is placed on pin N30, the location constraint for the corresponding DQS Gate fabric flip-flop is:

```
INST "*/gen_dqs[0].u_iob_dqs/u_idelay_dq_ce" LOC = "IDELAY_X2Y218";
```

The reason for this requirement is to minimize the net delay from the output of the DQS Gate fabric flip-flop to the synchronizing IDELAY (see the discussion of why MAXDELAY constraints are used in this design in [“Setting UCF Constraints,” page 563](#)). It is possible to *not* constrain this flip-flop to a specific location (or constrain it to a different location) as long as the corresponding MAXDELAY for this net can be met (i.e., by allowing MAP to place this flip-flop).

Verifying UCF/HDL Modifications

The user can verify that the modifications to the UCF and HDL top-level files are correct by verifying that all timing requirements have been met. For more information on verifying timing constraints for the Virtex-5 FPGA DDR2 design, refer to [“Constraints” in Chapter 9](#).

WASSO Limit Implementation Guidelines

Overview

This appendix provides information about WASSO (Weighted Average Simultaneous Switching Output) limit implementation in the bank selection from MIG. It is recommended to use a WASSO calculator before the number of pins selected in a bank. MIG limits the number of outputs/inouts allocated in a bank based on the WASSO limit entered for that bank in bank selection page. WASSO is supported for all FPGA families.

Ground bounce must be controlled to ensure proper operation of high-performance FPGA devices. Particular attention must be applied to minimizing board-level inductance during PCB layout.

When multiple output drivers change state at the same time, power supply disturbances occur. These disturbances can cause undesired transient behavior in output drivers, input receivers, or in internal logic. These disturbances are often referred to as Simultaneous-Switching Output (SSO) noise. The SSO limits govern the number and type of I/O output drivers that can be switched simultaneously while maintaining a safe level of SSO noise.

SSO of an individual bank is calculated by summing the SSO contributions of the individual I/O standards in the bank. The SSO contribution is the percentage of full utilization of any one I/O standard in any one bank. WASSO calculation is done by combining the SSO contributions of all I/Os in a bank into a single figure.

WASSO calculation differs for Virtex®-4 and Virtex-5 devices:

- *Virtex-4 FPGA User Guide* [Ref 7] provides more information on WASSO calculation for Virtex-4 devices.
- *Virtex-5 FPGA User Guide* [Ref 10] provides more information on WASSO calculation for Virtex-5 devices.

A Microsoft Excel-based spreadsheet entitled “WASSO Calculator” is provided to automate these calculations. The WASSO calculator uses PCB geometry, such as board thickness, via diameter, and breakout trace width and length, to determine board inductance. It determines the smallest undershoot and logic-Low threshold voltage among all input devices, calculates the average output capacitance, and determines the SSO allowance by taking into account all of the board-level design parameters mentioned in this document. In addition, the WASSO calculator performs checks to ensure the overall design does not exceed the SSO allowance.

The Virtex-4 FPGA WASSO Calculator [Ref 34] and the Virtex-5 FPGA WASSO Calculator [Ref 35] can be downloaded from the Xilinx® website. A WASSO calculator for Spartan® devices can be downloaded from <http://www.xilinx.com/bvdocs/appnotes/xapp689.zip>.

Pin Allocation Rules with WASSO Limit

MIG allocates the pins starting with exclusive data banks for CIO (Common I/O) designs and exclusive data read banks for SIO (Separate I/O) designs, followed by data (/data read) banks that combine with other groups. After the data(/data read) groups are filled in the banks, MIG allocates the rest of the groups (namely data write, address, and system control).

WASSO can be applied only on output or bidirectional pins. Hence pin allocation rules will change when the WASSO limit is less than the available pins in the bank.

For SIO designs, data read group consists of all input pins and WASSO is not applicable on inputs. In a bank where data read group is combined with other groups (which has output pins), first data read group is allocated. After the data read group is allocated in that bank, if the left over pins are less than the WASSO limit of that bank then all the pins are allocated for the other group. If the left over pins are more than the WASSO limit of that bank, then only the number of pins of other groups equal to the WASSO limit are allocated in that bank.

For CIO designs, a data group consists of bidirectional, input, and output pins. WASSO is applicable on output and bidirectional pins only. In a bank where the data group is combined with other groups (which has output pins), the first data group is allocated. If the WASSO limit is less than the bank pin count, then only the number of pins equal to the WASSO limit are allocated. If the WASSO limit is equal to bank pin count, then all the pins in the bank are allocated for data.

For CIO designs, the number of pins available in a bank or the WASSO limit of the bank should be sufficient to allocated at least one calibration unit. A calibration unit consists of a strobe/read clocks, associated data bits, associated data mask pins, associated data valid signals (if available). If the number of pins available in a bank or the WASSO limit of the bank is less than the number of pins required to allocate at least on calibration unit, then no data group pins are allocated in that bank even if the bank is selected for the data group.

SSO for Spartan FPGA Designs

Overview

Simultaneous switching output guidelines limit the number of outputs that can switch simultaneously for a given I/O standard in a bank while maintaining a safe level of SSO noise. Pin allocation of signals is required to meet these guidelines to reduce ground bounce and increase signal integrity. Refer to the Simultaneously Switching Output Guidelines section of the Spartan-3/3E/3A/3AN/3A DSP data sheets [\[Ref 28\]](#) [\[Ref 29\]](#) [\[Ref 30\]](#) [\[Ref 31\]](#) [\[Ref 32\]](#) for the recommended maximum number of SSOs and other details.

Requirements

SSO is not required to be considered in these conditions:

- The SSO value is greater than the available I/O pin count in a bank
- The simultaneously switching signal count is less than the SSO value of the bank for the given I/O standard

The applicable I/O standards for DDR/DDR2 SDRAM address, control, and data are SSTL2_I, SSTL2_II, SSTL18_I, and SSTL18_II. For the Spartan®-3 and Spartan-3E platforms, the SSO limit for these standards is greater than the available pin count. For Spartan-3A and Spartan-3A DSP devices, although the SSO limit is less than the I/O pin count, the output signals that switch simultaneously are always less than the SSO count value. Thus, for all the Spartan devices described here, the SSO limit does not have to be considered for pin allocation. The DQ, DQS, address, and control signals never switch simultaneously. During write operations, DQS is center aligned with DQ, and therefore, they do not switch together. The address and control signals are asserted before enabling the data.

[Table D-1](#) shows how the number of pins allocated is less than the SSO limit for Bank 3 of the XC3S1400A-FG676 device in a DDR2 SDRAM design.

Table D-1: XC3S1400A-FG676 Device in DDR2 SDRAM Design

Parameter	Value
Device	XC3S1400A-FG676
SSO limit for the SSTL18_II I/O standard for Bank 3	81
Available I/O pin count for Bank 3	103
Memory type	DDR2 SDRAM
Memory part	MT47H256M8HG-3

Table D-1: XC3S1400A-FG676 Device in DDR2 SDRAM Design (Cont'd)

Parameter	Value
Maximum data width for the DDR2 SDRAM	56-bit
Total number of DQ and DM signals that switch together	63
Total number of DQS (differential)	14

Debug Port

Overview

Starting with MIG 2.2, the memory controller interface design HDL for Virtex®-5, Virtex-4, and Spartan®-3 FPGAs adds ports to the top-level design file to allow debugging and monitoring of the physical layer read timing calibration logic and timing. This port consists of signals brought to the top-level HDL from the Read Calibration module (where the read timing calibration logic resides). These signals provide information for debugging hardware issues when calibration does not complete or read timing errors are observed in the system even after calibration completes. For Virtex FPGA designs, these signals also allow the user to adjust the read capture timing by adjusting the various IDELAY elements used for data synchronization. Whereas, for Spartan-3 FPGA designs, these signals allow the user to adjust the read capture timing by adjusting the delays on data_strobe and rst_dqs_div signals.

Specifically, the Debug port allows the user to:

- Observe calibration status signals.
- Observe current tap values for IDELAYs used for read data synchronization for Virtex FPGA designs.
- Observe current tap_delay values for Spartan-3 FPGA designs.
- Dynamically vary these tap values. Possible uses of this functionality include:
 - Debug read data corruption issues
 - Support periodic readjustment of the read data capture timing by adjusting the tap values
 - Use as a tool during product margining to determine actual timing margin available on read data captures

Enabling the Debug Port

For Virtex-5 FPGA memory controller designs, the Debug port is enabled by setting the top-level HDL parameter DEBUG_EN to 1. To disable the Debug port, set DEBUG_EN to 0. This prevents the synthesis of additional logic required to support the Debug port (e.g., logic to allow dynamic adjustment of the IDELAY taps).

For Virtex-4 FPGA memory controller designs, the Debug port is enabled by setting the Debug Signals option in MIG.

If the design is implemented using the batch files (ise_flow.bat/create_ise.bat) provided by MIG, ChipScope™ tool debug EDIF or NGC files (ILA/ICON/VIO) are generated automatically by using the XCO files provided in the par folder. If batch files (ise_flow.bat/create_ise.bat) are not used for implementing the design, the

ChipScope tool debug EDIF or NGC files should be manually generated. Refer to `readme.txt` located in the `par` folder for a set of commands to be executed before starting synthesis and PAR to generate the EDIF or NGC files.

Signal Descriptions

The tables in this section provide the Debug port signal descriptions for the various memory and FPGA combinations. All the signal directions are with respect to the RTL design.

- [Table E-1, “DDR2 SDRAM Signal Descriptions \(Virtex-5 FPGAs\),” page 572](#)
- [Table E-2, “DDR SDRAM Signal Descriptions \(Virtex-5 FPGAs\),” page 575](#)
- [Table E-3, “QDR II SRAM Signal Descriptions \(Virtex-5 FPGAs\),” page 578](#)
- [Table E-4, “DDR2 SDRAM Signal Descriptions \(Virtex-4 FPGAs\),” page 582](#)
- [Table E-5, “DDR SDRAM Signal Descriptions \(Virtex-4 FPGAs\),” page 583](#)
- [Table E-6, “QDR II SRAM Signal Descriptions \(Virtex-4 FPGAs\),” page 584](#)
- [Table E-7, “QDR II SRAM Signal Descriptions \(Virtex-4 FPGAs\),” page 586](#)
- [Table E-8, “RLDRAM II Signal Descriptions \(Virtex-4 FPGAs\),” page 588](#)
- [Table E-9, “DDR/DDR2 SDRAM Signal Descriptions \(Spartan-3 FPGAs\),” page 589](#)

Virtex-5 FPGA: DDR2 SDRAM

All debug ports signals are clocked using the half-frequency clock (`clkdiv`). Increment and decrement control signals (e.g., `dbg_idel_up_all`) must be provided synchronously with `clkdiv`. IDELAY select signals, such as `dbg_sel_all_idel_dqs` and `dbg_sel_idel_dqs` can change asynchronous to `clkdiv`, but must meet setup and hold requirements on `clkdiv` on cycles when the corresponding increment/decrement control signal is asserted.

Table E-1: DDR2 SDRAM Signal Descriptions (Virtex-5 FPGAs)

Bus Name	I/O	Width	Description
<code>dbg_calib_done</code>	O	4	Each bit is driven to a static 1 as each stage of calibration is completed. <code>dbg_calib_done[0]</code> corresponds to Stage 1.
<code>dbg_calib_dq_tap_cnt</code>	O	6*DQ_WIDTH	6-bit tap count for each DQ IDELAY. <code>dbg_calib_dq_tap_cnt[5:0]</code> corresponds to DQ[0].
<code>dbg_calib_dqs_tap_cnt</code>	O	6*DQS_WIDTH	6-bit tap count for each DQS IDELAY. <code>dbg_calib_dqs_tap_cnt[5:0]</code> corresponds to DQS[0].
<code>dbg_calib_gate_tap_cnt</code>	O	6*DQS_WIDTH	6-bit tap count for each DQS Gate IDELAY. <code>dbg_calib_gate_tap_cnt[5:0]</code> corresponds to the DQS Gate for DQS[0].

Table E-1: DDR2 SDRAM Signal Descriptions (Virtex-5 FPGAs) (Cont'd)

Bus Name	I/O	Width	Description
dbg_calib_rd_data_sel	O	DQS_WIDTH	Each bit indicates which polarity of the FPGA clock (clk0) is used to synchronize the captured read data from the DQ IDDR for a DQS group. 1: The rising edge of clk0 synchronizes DDR2 rising edge data. The falling edge of clk0 synchronizes DDR2 falling edge data. 0: The falling edge of clk0 synchronizes DDR2 rising edge data. The rising edge of clk0 synchronizes DDR2 falling edge data. calib_rd_data_sel[0] corresponds to DQS[0].
dbg_calib_rden_dly	O	5*DQS_WIDTH	5-bit value indicating the number of clk0 clock cycles of delay between when a read command is issued by the controller and the synchronization of valid data in the clk0 clock domain. Each DQS group has its own distinct value. dbg_calib_rden_dly[4:0] corresponds to DQS[0].
dbg_calib_gate_dly	O	5*DQS_WIDTH	5-bit value indicating the number of clk0 clock cycles of delay between the end of a read burst and the assertion of DQS Gate. Each DQS group has its own distinct value. dbg_calib_gate_dly[4:0] corresponds to DQS[0].
dbg_calib_err	O	2	Asserted when an error is detected during calibration during stages 3 and/or 4. This appears as a 4-bit bus in the HDL. However, only bits [3:2] are used. dbg_calib_err[2] corresponds to stage 3, and dbg_calib_err[3] corresponds to stage 4. Stages 1 and 2 do not have error signals.
dbg_idel_up_all	I	1	Increments the tap value for all IDELAYs (DQ, DQS, and DQS Gate) used for read data synchronization. Tap values are incremented by one for every clkdiv cycle that this signal is held High.
dbg_idel_down_all	I	1	Decrements the tap value for all IDELAYs (DQ, DQS, and DQS Gate) used for read data synchronization. Tap values are decremented by one for every clkdiv cycle that this signal is held High.

Table E-1: DDR2 SDRAM Signal Descriptions (Virtex-5 FPGAs) (Cont'd)

Bus Name	I/O	Width	Description
dbg_sel_all_idel_dq	I	1	Selects the functionality for dbg_idel_up_dq and dbg_idel_down_dq: 1: All DQ IDELAYs are adjusted. 0: Only the IDELAY for the DQ bit specified by dbg_sel_idel_dq is adjusted. If neither dbg_idel_up_dq nor dbg_idel_down_dq is active in a clkdiv cycle, this signal is a <i>don't care</i> .
dbg_sel_idel_dq	I	$\log_2(\text{DQS_WIDTH} * \text{DQ_PER_DQS})$	When dbg_sel_all_idel_dq = 1, determines the specific DQ IDELAY to vary using dbg_idel_up_dq or dbg_idel_down_dq. If neither dbg_idel_up_dq nor dbg_idel_down_dq is active in a clkdiv cycle, this signal is a <i>don't care</i> .
dbg_idel_up_dq	I	1	Increments the tap value for all DQ IDELAYs. The DQ IDELAY(s) affected are given by dbg_sel_all_idel_dq and dbg_sel_idel_dq. Tap value(s) are incremented by one for every clkdiv cycle that this signal is held High.
dbg_idel_down_dq	I	1	Decrements the tap value for all DQ IDELAYs. The DQ IDELAY(s) affected are given by dbg_sel_all_idel_dq and dbg_sel_idel_dq. Tap value(s) are decremented by one for every clkdiv cycle that this signal is held High.
dbg_sel_all_idel_dqs	I	1	Selects the functionality for dbg_idel_up_dqs and dbg_idel_down_dqs: 1: All DQS IDELAYs are adjusted. 0: Only the IDELAY for the DQS specified by dbg_sel_idel_gate is adjusted. If neither dbg_idel_up_dqs nor dbg_idel_down_dqs is active in a clkdiv cycle, this signal is a <i>don't care</i> .
dbg_sel_idel_dqs	I	$\log_2(\text{DQS_WIDTH})$	When dbg_sel_all_idel_dqs = 1, determines the specific DQS IDELAY to vary using dbg_idel_up_dqs or dbg_idel_down_dqs. If neither dbg_idel_up_dqs nor dbg_idel_down_dqs is active in a clkdiv cycle, this signal is a <i>don't care</i> .
dbg_idel_up_dqs	I	1	Increments the tap value for all DQS IDELAYs. The DQS IDELAY(s) affected are given by dbg_sel_all_idel_dqs and dbg_sel_idel_dqs. Tap value(s) are incremented by one for every clkdiv cycle that this signal is held High.

Table E-1: DDR2 SDRAM Signal Descriptions (Virtex-5 FPGAs) (Cont'd)

Bus Name	I/O	Width	Description
dbg_idel_down_dqs	I	1	Decrements the tap value for all DQS IDELAYs. The DQS IDELAY(s) affected are given by dbg_sel_all_idel_dqs and dbg_sel_idel_dqs. Tap value(s) are decremented by one for every clkdiv cycle that this signal is held High.
dbg_sel_all_idel_gate	I	1	Selects the functionality for dbg_idel_up_gate and dbg_idel_down_gate: 1: All DQS Gate IDELAYs are adjusted. 0: Only the IDELAY for the DQS Gate specified by dbg_sel_idel_gate is adjusted.
dbg_sel_idel_gate	I	$\log_2(\text{DQS_WIDTH})$	When dbg_sel_all_idel_gate = 1, determines the specific DQS Gate IDELAY to vary using dbg_idel_up_gate or dbg_idel_down_gate.
dbg_idel_up_gate	I	1	Increments the tap value for all DQS Gate IDELAYs. The DQS Gate IDELAY(s) affected are given by dbg_sel_all_idel_gate and dbg_sel_idel_gate. Tap value(s) are incremented by one for every clkdiv cycle that this signal is held High. If neither dbg_idel_up_gate nor dbg_idel_down_gate is active in a clkdiv cycle, this signal is a <i>don't care</i> .
dbg_idel_down_gate	I	1	Decrements the tap value for all DQS Gate IDELAYs. The DQS IDELAY(s) affected are given by dbg_sel_all_idel_gate and dbg_sel_idel_gate. Tap value(s) are decremented by one for every clkdiv cycle that this signal is held High. If neither dbg_idel_up_gate nor dbg_idel_down_gate is active in a clkdiv cycle, this signal is a <i>don't care</i> .

Virtex-5 FPGA: DDR SDRAM

All debug port signals are clocked using the design clock frequency (clk90). Increment and decrement control signals (e.g., dbg_idel_up_all) must be provided synchronously with clk90. IDELAY select signals, such as dbg_sel_all_idel_dqs and dbg_sel_idel_dqs, can change asynchronous to clk90, but must meet setup and hold requirements on clk90 on cycles when the corresponding increment/decrement control signal is asserted.

Table E-2: DDR SDRAM Signal Descriptions (Virtex-5 FPGAs)

Bus Name	I/O	Width	Description
dbg_calib_done	O	4	Each bit is driven to a static 1 as each stage of calibration is completed. dbg_calib_done[0] corresponds to Stage 1.
dbg_calib_dq_tap_cnt	O	6*DQ_WIDTH	6-bit tap count for each DQ IDELAY. dbg_calib_dq_tap_cnt[5:0] corresponds to DQ[0].

Table E-2: DDR SDRAM Signal Descriptions (Virtex-5 FPGAs) (Cont'd)

Bus Name	I/O	Width	Description
dbg_calib_dqs_tap_cnt	O	6*DQS_WIDTH	6-bit tap count for each DQS IDELAY. dbg_calib_dqs_tap_cnt[5:0] corresponds to DQS[0].
dbg_calib_gate_tap_cnt	O	6*DQS_WIDTH	6-bit tap count for each DQS Gate IDELAY. dbg_calib_gate_tap_cnt[5:0] corresponds to the DQS Gate for DQS[0].
dbg_calib_rden_dly	O	5*DQS_WIDTH	5-bit value indicating the number of clk90 clock cycles of delay between when a read command is issued by the controller and the synchronization of valid data in the clk90 clock domain. Each DQS group has its own distinct value. dbg_calib_rden_dly[4:0] corresponds to DQS[0].
dbg_calib_gate_dly	O	5*DQS_WIDTH	5-bit value indicating the number of clk90 clock cycles of delay between the end of a read burst and the assertion of DQS Gate. Each DQS group has its own distinct value. dbg_calib_gate_dly[4:0] corresponds to DQS[0].
dbg_calib_err	O	4	Asserted when an error is detected during calibration during stages 3 and/or 4. This appears as a 4-bit bus in the HDL. However, only bits [3:2] are used. dbg_calib_err[2] corresponds to stage 3, and dbg_calib_err[3] corresponds to stage 4. Stages 1 and 2 do not have error signals.
dbg_idel_up_all	I	1	Increments the tap value for all IDELAYs (DQ, DQS, and DQS Gate) used for read data synchronization. Tap values are incremented by one for every clk90 cycle that this signal is held High.
dbg_idel_down_all	I	1	Decrements the tap value for all IDELAYs (DQ, DQS, and DQS Gate) used for read data synchronization. Tap values are decremented by one for every clk90 cycle that this signal is held High.
dbg_sel_all_idel_dq	I	1	Selects the functionality for dbg_idel_up_dq and dbg_idel_down_dq: 1: All DQ IDELAYs are adjusted. 0: Only the IDELAY for the DQ bit specified by dbg_sel_idel_dq is adjusted. If neither dbg_idel_up_dq nor dbg_idel_down_dq is active in a clk90 cycle, this signal is a <i>don't care</i> .
dbg_sel_idel_dq	I	$\log_2(\text{DQS_WIDTH} * \text{DQ_PER_DQS})$	When dbg_sel_add_idel_dq = 1, determines the specific DQ IDELAY to vary using dbg_idel_up_dq or dbg_idel_down_dq. If neither dbg_idel_up_dq nor dbg_idel_down_dq is active in a clk90 cycle, this signal is a <i>don't care</i> .
dbg_idel_down_dq	I	1	Increments the tap value for all DQ IDELAYs. The DQ IDELAY(s) affected are given by dbg_sel_all_idel_dq and dbg_sel_idel_dq. Tap value(s) are incremented by one for every clk90 cycle that this signal is held High.

Table E-2: DDR SDRAM Signal Descriptions (Virtex-5 FPGAs) (Cont'd)

Bus Name	I/O	Width	Description
dbg_sel_all_idel_dqs	I	1	Decrements the tap value for all DQ IDELAYs. The DQ IDELAY(s) affected are given by dbg_sel_all_idel_dq and dbg_sel_idel_dq. Tap value(s) are decremented by one for every clk90 cycle that this signal is held High.
dbg_sel_idel_dqs	I	1	Selects the functionality for dbg_idel_up_dqs and dbg_idel_down_dqs: 1: All DQS IDELAYs are adjusted. 0: Only the IDELAY for the DQS specified by dbg_sel_idel_gate is adjusted. If neither dbg_idel_up_dqs nor dbg_idel_down_dqs is active in a clk90 cycle, this signal is a <i>don't care</i> .
dbg_idel_up_dqs	I	$\log_2(\text{DQS_WIDTH})$	When dbg_sel_add_idel_dqs = 1, determines the specific DQS IDELAY to vary using dbg_idel_up_dqs or dbg_idel_down_dqs. If neither dbg_idel_up_dqs nor dbg_idel_down_dqs is active in a clk90 cycle, this signal is a <i>don't care</i> .
dbg_idel_down_dqs	I	1	Increments the tap value for all DQS IDELAYs. The DQS IDELAY(s) affected are given by dbg_sel_all_idel_dqs and dbg_sel_idel_dqs. Tap value(s) are incremented by one for every clk90 cycle that this signal is held High.
dbg_sel_all_idel_gate	I	1	Decrements the tap value for all DQS IDELAYs. The DQS IDELAY(s) affected are given by dbg_sel_all_idel_dqs and dbg_sel_idel_dqs. Tap value(s) are decremented by one for every clk90 cycle that this signal is held High.
dbg_sel_idel_gate	I	1	Selects the functionality for dbg_idel_up_gate and dbg_idel_down_gate: 1: All DQS Gate IDELAYs are adjusted. 0: Only the IDELAY for the DQS Gate specified by dbg_sel_idel_gate is adjusted.
dbg_idel_up_gate	I	$\log_2(\text{DQS_WIDTH})$	When dbg_sel_add_idel_gate = 1, determines the specific DQS Gate IDELAY to vary using dbg_idel_up_gate or dbg_idel_down_gate.
dbg_idel_down_gate	I	1	Increments the tap value for all DQS Gate IDELAYs. The DQS Gate IDELAY(s) affected are given by dbg_sel_all_idel_gate and dbg_sel_idel_gate. Tap value(s) are incremented by one for every clk90 cycle that this signal is held High. If neither dbg_idel_up_gate nor dbg_idel_down_gate is active in a clk90 cycle, this signal is a <i>don't care</i> .

Virtex-5 FPGA: QDRII SRAM

All the debug input port signals are clocked using the design clock frequency (clk0). Increment and decrement control signals (e.g., dbg_idel_up_all) as well as the IDELAY select signals must be provided synchronously with clk0.

Note:

1. All Data (Q) in a given calibration group has the same IDELAY tap value.
2. For x36 component designs, calibration group has both CQ and CQ# and their corresponding Data (Q) calibrated, hence the debug logic is applied to both CQ and CQ#. For x18 component designs, the calibration group has only CQ and its corresponding Data (Q) calibrated. Thus the designer must ignore the debug logic related to CQ# (e.g., dbg_idel_up_cq_n). The synthesis tool prunes the CQ# related logic anyway.

Table E-3: QDRII SRAM Signal Descriptions (Virtex-5 FPGAs)

Bus Name	I/O	Width	Description
dbg_idel_up_all	I	1	Increments the tap value for all IDELAYs (Q, CQ, CQ#) used for read data synchronization. Tap values are incremented by one for every clk0 cycle that this signal is held High.
dbg_idel_down_all	I	1	Decrements the tap value for all IDELAYs (Q, CQ, CQ#) used for read data synchronization. Tap values are decremented by one for every clk0 cycle that this signal is held High.
dbg_sel_all_idel_cq	I	1	Selects the functionality for dbg_idel_up_cq and dbg_idel_down_cq: 1: All CQ IDELAYs are adjusted. 0: Only the IDELAY for the CQ specified by dbg_sel_idel_cq is adjusted. If neither dbg_idel_up_cq nor dbg_idel_down_cq is active in the clk0 cycle, this signal is a <i>don't care</i> .
dbg_sel_idel_cq	I	CQ_WIDTH	When any dbg_sel_idel_cq bit is set to 1, it determines the specific CQ IDELAY to vary using dbg_idel_up_cq or dbg_idel_down_cq. If neither dbg_idel_up_cq nor dbg_idel_down_cq is active in the clk0 cycle, this signal is a <i>don't care</i> .
dbg_idel_up_cq	I	1	Increments the tap value for all CQ IDELAYs. The CQ IDELAY(s) affected are given by dbg_sel_all_idel_cq and dbg_sel_idel_cq. Tap value(s) are incremented by one for every clk0 cycle that this signal is held High.
dbg_idel_down_cq	I	1	Decrements the tap value for all CQ IDELAYs. The CQ IDELAY(s) affected are given by dbg_sel_all_idel_cq and dbg_sel_idel_cq. Tap value(s) are decremented by one for every clk0 cycle that this signal is held High.

Table E-3: QDRII SRAM Signal Descriptions (Virtex-5 FPGAs) (Cont'd)

Bus Name	I/O	Width	Description
dbg_sel_all_idel_cq_n	I	1	<p>Selects the functionality for dbg_idel_up_cq_n and dbg_idel_down_cq_n:</p> <p>1: All CQ# IDELAYs are adjusted.</p> <p>0: Only the IDELAY for the CQ# specified by dbg_sel_idel_cq_n is adjusted.</p> <p>If neither dbg_idel_up_cq_n nor dbg_idel_down_cq_n is active in the clk0 cycle, this signal is a <i>don't care</i>.</p>
dbg_sel_idel_cq_n	I	CQ_WIDTH	<p>When any dbg_sel_idel_cq_n bit is set to 1, it determines the specific CQ# IDELAY to vary using dbg_idel_up_cq_n or dbg_idel_down_cq_n.</p> <p>If neither dbg_idel_up_cq_n nor dbg_idel_down_cq_n is active in the clk0 cycle, this signal is a <i>don't care</i>.</p>
dbg_idel_up_cq_n	I	1	<p>Increments the tap value for all CQ# IDELAYs. The CQ# IDELAY(s) affected are given by dbg_sel_all_idel_cq_n and dbg_sel_idel_cq_n.</p> <p>Tap value(s) are incremented by one for every clk0 cycle that this signal is held High.</p>
dbg_idel_down_cq_n	I	1	<p>Decrements the tap value for all CQ# IDELAYs. The CQ# IDELAY(s) affected are given by dbg_sel_all_idel_cq_n and dbg_sel_idel_cq_n.</p> <p>Tap value(s) are decremented by one for every clk0 cycle that this signal is held High.</p>
dbg_sel_all_idel_q_cq	I	1	<p>Selects the functionality for dbg_idel_up_q_cq and dbg_idel_down_q_cq:</p> <p>1: All Data (Q) IDELAYs are adjusted.</p> <p>0: Only the IDELAYs for Data (Q) in the calibration group of CQ specified by dbg_sel_idel_q_cq are adjusted.</p> <p>If neither dbg_idel_up_q_cq nor dbg_idel_down_q_cq is active in the clk0 cycle, this signal is a <i>don't care</i>.</p>
dbg_sel_idel_q_cq	I	CQ_WIDTH	<p>When any dbg_sel_idel_q_cq bit is set to 1, it determines all the Data (Q) IDELAYs in the calibration group of CQ to vary using dbg_idel_up_q_cq or dbg_idel_down_q_cq.</p> <p>If neither dbg_idel_up_q_cq nor dbg_idel_down_q_cq is active in the clk0 cycle, this signal is a <i>don't care</i>.</p>
dbg_idel_up_q_cq	I	1	<p>Increments the tap value for all Data (Q) IDELAYs in the calibration group of CQ. The Data (Q) IDELAYs in the calibration group that is affected are given by dbg_sel_all_idel_q_cq and dbg_sel_idel_q_cq.</p> <p>Tap value(s) are incremented by one for every clk0 cycle that this signal is held High.</p>

Table E-3: QDRII SRAM Signal Descriptions (Virtex-5 FPGAs) (Cont'd)

Bus Name	I/O	Width	Description
dbg_idel_down_q_cq	I	1	Decrements the tap value of all Data (Q) IDELAYs in the calibration group of CQ. The Data (Q) IDELAYs in the calibration group of CQ that is affected are given by dbg_sel_all_idel_q_cq and dbg_sel_idel_q_cq. Tap value(s) are decremented by one for every clk0 cycle that this signal is held High.
dbg_sel_all_idel_q_cq_n	I	1	Selects the functionality for dbg_idel_up_q_cq_n and dbg_idel_down_q_cq_n: 1: All Data (Q) IDELAYs are adjusted. 0: Only the IDELAYs of all Data (Q) in the calibration group of CQ# specified by dbg_sel_idel_q_cq_n are adjusted. If neither dbg_idel_up_q_cq_n nor dbg_idel_down_q_cq_n is active in the clk0 cycle, this signal is a <i>don't care</i> .
dbg_sel_idel_q_cq_n	I	CQ_WIDTH	When any dbg_sel_idel_q_cq_n bit is set to 1, it determines all the Data (Q) IDELAYs in the calibration group of CQ# to vary using dbg_idel_up_q_cq_n or dbg_idel_down_q_cq_n. If neither dbg_idel_up_q_cq_n nor dbg_idel_down_q_cq_n is active in the clk0 cycle, this signal is a <i>don't care</i> .
dbg_idel_up_q_cq_n	I	1	Increments the tap value of all Data (Q) IDELAYs in the calibration group of CQ#. The Data (Q) IDELAYs in the calibration group of CQ# that is affected are given by dbg_sel_all_idel_q_cq_n and dbg_sel_idel_q_cq_n. Tap value(s) are incremented by one for every clk0 cycle that this signal is held High.
dbg_idel_down_q_cq_n	I	1	Decrements the tap value of all Data (Q) IDELAYs in the calibration group of CQ#. The Data (Q) IDELAYs in the calibration group of CQ# that is affected are given by dbg_sel_all_idel_q_cq_n and dbg_sel_idel_q_cq_n. Tap value(s) are decremented by one for every clk0 cycle that this signal is held High.
dbg_init_count_done	O	1	When set to 1, indicates the completion of memory initialization.
dbg_q_cq_init_delay_done	O	CQ_WIDTH	When set to 1, indicates the completion of the first stage calibration with respect to CQ.
dbg_q_cq_init_delay_done_tap_count	O	6*CQ_WIDTH	A 6-bit tap count for each group of Data (Q) bits IDELAY associated with CQ. dbg_q_cq_init_delay_done_tap_count[5:0] corresponds to CQ[0].

Table E-3: QDRII SRAM Signal Descriptions (Virtex-5 FPGAs) (Cont'd)

Bus Name	I/O	Width	Description
dbg_q_cq_n_init_delay_done	O	CQ_WIDTH	When set to 1, indicates the completion of the first stage calibration with respect to CQ#.
dbg_q_cq_n_init_delay_done_tap_count	O	6*CQ_WIDTH	A 6-bit tap count for each group of Data (Q) bits IDELAY associated with CQ#. dbg_q_cq_n_init_delay_done_tap_count[5:0] corresponds to CQ#[0].
dbg_cq_cal_done	O	CQ_WIDTH	When set to 1, indicates the completion of the second stage calibration with respect to CQ.
dbg_cq_cal_tap_count	O	6*CQ_WIDTH	A 6-bit tap count for each CQ IDELAY. dbg_cq_cal_tap_count[5:0] corresponds to CQ[0].
dbg_cq_n_cal_done	O	CQ_WIDTH	When set to 1, indicates the completion of the second stage calibration with respect to CQ#.
dbg_cq_n_cal_tap_count	O	6*CQ_WIDTH	A 6-bit tap count for each CQ# IDELAY. dbg_cq_n_cal_tap_count[5:0] corresponds to CQ#[0].
dbg_we_cal_done_cq	O	CQ_WIDTH	When set to 1, indicates the completion of the read enable calibration of the Data (Q) in the calibration group of each CQ.
dbg_we_cal_done_cq_n	O	CQ_WIDTH	When set to 1, indicates the completion of the read enable calibration of the Data (Q) in the calibration group of CQ#.
dbg_cq_q_data_valid	O	CQ_WIDTH	When set to 1, indicates the data valid signal for the Data (Q) in the calibration group of each CQ.
dbg_cq_n_q_data_valid	O	CQ_WIDTH	When set to 1, indicates the data valid signal for the Data (Q) in the calibration group of each CQ#.
dbg_cal_done	O	1	When set to 1, indicates the completion of the Data (Q) calibration process.
dbg_data_valid	O	1	When set to 1, indicates the data valid signal for the Read Data (Q) after calibration.

Virtex-4 FPGA: DDR2 SDRAM Direct Clocking

All the debug input port signals are clocked using the design clock frequency (clk_0). Increment and decrement control signals (e.g., dbg_idel_up_all) as well as the IDELAY select signals must be provided synchronously with clk_0.

Table E-4: DDR2 SDRAM Signal Descriptions (Virtex-4 FPGAs)

Bus Name	I/O	Width	Description
dbg_idel_up_all	I	1	Increments tap value for all IDELAYs (DQ) used for read data synchronization. Tap values are incremented by one for every clk_0 cycle this signal is held High.
dbg_idel_down_all	I	1	Decrements tap value for all IDELAYs (DQ) used for read data synchronization. Tap values are decremented by one for every clk_0 cycle this signal is held High.
dbg_sel_all_idel_dq	I	1	Selects functionality for idel_up_dq and idel_down_dq: 1: All DQ IDELAYs are adjusted 0: Only the IDELAY for the DQ bit specified by sel_idel_dq is adjusted If neither idel_up_dq nor idel_down_dq is active in a clk_0 cycle, this signal is a "don't care".
dbg_sel_idel_dq	I	$\log_2(\text{DATA_STROBE_WIDTH} * \text{DATABITSPERS TROBE})$	When sel_all_idel_dq = 1, determines the specific DQ IDELAY to vary using idel_up_dq or idel_down_dq. If neither idel_up_dq nor idel_down_dq is active in a clk_0 cycle, this signal is a "don't care".
dbg_idel_up_dq	I	1	Increments tap value for all DQ IDELAYs. The DQ IDELAY(s) affected are given by sel_all_idel_dq and sel_idel_dq. Tap value(s) are incremented by one for every clk_0 cycle this signal is held High.
dbg_idel_down_dq	I	1	Decrements tap value for all DQ IDELAYs. The DQ IDELAY(s) affected are given by sel_all_idel_dq and sel_idel_dq. Tap value(s) are decremented by one for every clk_0 cycle this signal is held High.
dbg_calib_dq_tap_cnt	O	6* DATA_WIDTH	6-bit tap count for each DQ IDELAY. calib_dq_tap_cnt [5:0] corresponds to DQ [0].
dbg_data_tap_inc_done	O	DATA_STROBE_WIDTH	Each bit is asserted when per bit calibration is completed for corresponding byte.
dbg_sel_done	O	1	Asserted as per bit calibration (first stage) is completed.
dbg_first_rising	O	DATA_STROBE_WIDTH	Asserted for each byte if rise and fall data arrive staggered with regards to each other.
dbg_cal_first_loop	O	DATA_STROBE_WIDTH	Deasserted ('0') for corresponding byte if pattern calibration is not completed on first pattern read command.
dbg_comp_done	O	DATA_STROBE_WIDTH	Each one asserted as pattern calibration (second stage) is completed for corresponding byte.
dbg_comp_error	O	DATA_STROBE_WIDTH	Each one asserted when a calibration error encountered in pattern stage for corresponding byte.
dbg_init_done	O	1	asserted if both per bit and pattern calibration are completed.

Virtex-4 FPGA: DDR SDRAM

All the debug input port signals are clocked using the design clock frequency (clk_0). Increment and decrement control signals (e.g., dbg_idel_up_all) as well as the IDELAY select signals must be provided synchronously with clk_0.

Table E-5: DDR SDRAM Signal Descriptions (Virtex-4 FPGAs)

Bus Name	I/O	Width	Description
dbg_idel_up_all	I	1	Increments tap value for all IDELAYs (DQ) used for read data synchronization. Tap values are incremented by one for every clk_0 cycle this signal is held High.
dbg_idel_down_all	I	1	Decrements tap value for all IDELAYs (DQ) used for read data synchronization. Tap values are decremented by one for every clk_0 cycle this signal is held High.
dbg_sel_all_idel_dq	I	1	Selects functionality for idel_up_dq and idel_down_dq: 1: All DQ IDELAYs are adjusted 0: Only the IDELAY for the DQ bit specified by sel_idel_dq is adjusted If neither idel_up_dq nor idel_down_dq is active in a clk_0 cycle, this signal is a "don't care".
dbg_sel_idel_dq	I	$\log_2(\text{DATA_STROBE_WIDTH} * \text{DATA_BITS_PER_STROBE})$	When sel_all_idel_dq = 1, determines the specific DQ IDELAY to vary using idel_up_dq or idel_down_dq. If neither idel_up_dq nor idel_down_dq is active in a clk_0 cycle, this signal is a "don't care".
dbg_idel_up_dq	I	1	Increments tap value for all DQ IDELAYs. The DQ IDELAY(s) affected are given by sel_all_idel_dq and sel_idel_dq. Tap value(s) are incremented by one for every clk_0 cycle this signal is held High.
dbg_idel_down_dq	I	1	Decrements tap value for all DQ IDELAYs. The DQ IDELAY(s) affected are given by sel_all_idel_dq and sel_idel_dq. Tap value(s) are decremented by one for every clk_0 cycle this signal is held High.
dbg_calib_dq_tap_cnt	O	6* DATA_WIDTH	6-bit tap count for each DQ IDELAY. calib_dq_tap_cnt [5:0] corresponds to DQ [0].
dbg_data_tap_inc_done	O	DATA_STROBE_WIDTH	Each bit is asserted when per bit calibration is completed for corresponding byte.
dbg_sel_done	O	1	Asserted as per bit calibration (first stage) is completed.
dbg_first_rising	O	DATA_STROBE_WIDTH	Asserted for each byte if rise and fall data arrive staggered with regards to each other.
dbg_cal_first_loop	O	DATA_STROBE_WIDTH	Deasserted ('0') for corresponding byte if pattern calibration is not completed on first pattern read command.
dbg_comp_done	O	DATA_STROBE_WIDTH	Each one asserted as pattern calibration (second stage) is completed for corresponding byte.
dbg_comp_error	O	DATA_STROBE_WIDTH	Each one asserted when a calibration error encountered in pattern stage for corresponding byte.
dbg_init_done	O	1	Asserted if both per bit and pattern calibration are completed.

Virtex-4 FPGA: DDRII SRAM

All the debug input port signals are clocked using the design clock frequency (clk_0). Increment and decrement control signals (e.g., dbg_idel_up_all) as well as the IDELAY select signals must be provided synchronously with clk_0.

Note:

1. All Data (DQ) in a given calibration group has the same IDELAY tap value.
2. A calibration group is determined by the number of Data (DQ) associated with each CQ.

Table E-6: DDRII SRAM Signal Descriptions (Virtex-4 FPGAs)

Bus Name	I/O	Width	Description
dbg_idel_up_all	I	1	Increments the tap value for all Read Data (DQ) IDELAYs used for data synchronization. Tap values are incremented by one for every clk_0 cycle that this signal is held High.
dbg_idel_down_all	I	1	Decrements the tap value for all Read Data (DQ) IDELAYs used for data synchronization. Tap values are decremented by one for every clk_0 cycle that this signal is held High.
dbg_sel_all_idel_data_cq	I	1	Selects the functionality for dbg_idel_up_data_cq and dbg_idel_down_data_cq: 1: All DQ IDELAYs are adjusted. 0: Only the IDELAY for all the DQ IDELAYs in the calibration group specified by dbg_sel_idel_data_cq is adjusted. If neither dbg_idel_up_data_cq nor dbg_idel_down_data_cq is active in the clk_0 cycle, this signal is a <i>don't care</i> .
dbg_sel_idel_data_cq	I	CQ_WIDTH	When any dbg_sel_idel_data_cq bit is set to 1, it determines all the Read Data (DQ) IDELAYs in a calibration group to vary using dbg_idel_up_data_cq or dbg_idel_down_data_cq. If neither dbg_idel_up_data_cq nor dbg_idel_down_data_cq is active in the clk_0 cycle, this signal is a <i>don't care</i> .
dbg_idel_up_data_cq	I	1	Increments the tap value for all Read Data (DQ) IDELAYs in a calibration group. The Read Data (DQ) IDELAYs in a calibration group which are affected are given by dbg_sel_all_idel_data_cq and dbg_sel_idel_data_cq. Tap value(s) are incremented by one for every clk_0 cycle, this signal is held High.

Table E-6: DDRII SRAM Signal Descriptions (Virtex-4 FPGAs) (Cont'd)

Bus Name	I/O	Width	Description
dbg_idel_down_data_cq	I	1	Decrements the tap value for all Read Data (DQ) IDELAYs in a calibration group. The Read Data (DQ) IDELAYs in a calibration group, which are affected, are given by dbg_sel_all_idel_data_cq and dbg_sel_idel_data_cq. Tap value(s) are decremented by one for every clk_0 cycle, this signal is held High.
dbg_cq_first_edge_detect	O	CQ_WIDTH	When set to 1, indicates the detection of the first edge of CQ in each calibration group.
dbg_cq_first_edge_tap_count	O	6*CQ_WIDTH	A 6-bit tap count for CQ IDELAY in each calibration group. This value determines the number of IDELAY taps incremented for first edge detection. dbg_cq_first_edge_tap_count[5:0] corresponds to CQ[0]
dbg_cq_second_edge_detect	O	CQ_WIDTH	When set to 1, indicates the detection of the second edge of CQ in each calibration group.
dbg_cq_second_edge_tap_count	O	6*CQ_WIDTH	A 6-bit tap count for CQ IDELAY in each calibration group. This value determines the number of IDELAY taps incremented for second edge detection. dbg_cq_second_edge_tap_count[5:0] corresponds to CQ[0].
dbg_cq_tap_sel_done	O	CQ_WIDTH	When set to 1, indicates that the calibration process of the center-aligning CQ with respect to clk_0 in each calibration group is completed.
dbg_cq_tap_count	O	6*CQ_WIDTH	A 6-bit tap count for CQ IDELAY in each calibration group. This value determines the number of IDELAY taps incremented. The maximum counter value cannot be more than 64, since the maximum taps that an IDELAY element can be incremented is only 64 taps.
dbg_data_tap_count	O	6*CQ_WIDTH	A 6-bit tap count for all Read Data (DQ) IDELAYs in each calibration group. The counter value indicates the number of tap delays that are to be applied on all Read Data (DQ) IDELAYs in each calibration group.
dbg_data_tap_sel_done	O	CQ_WIDTH	When set to 1, indicates the completion of delaying all the Read Data (DQ) IDELAYs in each calibration group. The number of taps that are to be delayed is determined by dbg_data_tap_count.
dbg_first_rising	O	CQ_WIDTH	1: The first edge detected is rising edge. 0: The first edge detected is falling edge.
dbg_rdcmd2valid_cnt	O	5*CQ_WIDTH	A 5-bit counter to calculate number of clocks from controller read command to data valid for group of Read Data (DQ) associated with specific CQ.
dbg_dly_cal_done	O	1	When set to 1, indicates the completion of the Read Data (DQ) calibration process.

Virtex-4 FPGA: QDRII SRAM

All the debug input port signals are clocked using the design clock frequency (clk_0). Increment and decrement control signals (e.g., dbg_idel_up_all) as well as the IDELAY select signals must be provided synchronously with clk_0.

Note:

1. All Data (Q) in a given calibration group has the same IDELAY tap value.
2. A calibration group is determined by the number of Data (Q) associated with each CQ.

Table E-7: QDRII SRAM Signal Descriptions (Virtex-4 FPGAs)

Bus Name	I/O	Width	Description
dbg_idel_up_all	I	1	Increments the tap value for all Data (Q) IDELAYs used for data synchronization. Tap values are incremented by one for every clk_0 cycle that this signal is held High.
dbg_idel_down_all	I	1	Decrements the tap value for all Data (Q) IDELAYs used for data synchronization. Tap values are decremented by one for every clk_0 cycle that this signal is held High.
dbg_sel_all_idel_data_cq	I	1	Selects the functionality for dbg_idel_up_data_cq and dbg_idel_down_data_cq: 1: All Q IDELAYs are adjusted. 0: Only the IDELAY for all Data (Q) in the calibration specified by dbg_sel_idel_data_cq is adjusted. If neither dbg_idel_up_data_cq nor dbg_idel_down_data_cq is active in the clk_0 cycle, this signal is a <i>don't care</i> .
dbg_sel_idel_data_cq	I	CQ_WIDTH	When any dbg_sel_idel_data_cq bit is set to 1, it determines all the Data (Q) IDELAYs in the calibration group to vary using dbg_idel_up_data_cq or dbg_idel_down_data_cq. If neither dbg_idel_up_data_cq nor dbg_idel_down_data_cq is active in the clk_0 cycle, this signal is a <i>don't care</i> .
dbg_idel_up_data_cq	I	1	Increments the tap value for all Data (Q) IDELAYs in the calibration group. The Data (Q) IDELAYs in the calibration group which are affected are given by dbg_sel_all_idel_data_cq and dbg_sel_idel_data_cq. Tap value(s) are incremented by one for every clk_0 cycle that this signal is held High.
dbg_idel_down_data_cq	I	1	Decrements the tap value for all Data (Q) IDELAYs in the calibration group. The Data (Q) IDELAYs in the calibration group, which are affected, are given by dbg_sel_all_idel_data_cq and dbg_sel_idel_data_cq. Tap value(s) are decremented by one for every clk_0 cycle that this signal is held High.
dbg_cq_first_edge_detect	O	CQ_WIDTH	When set to 1, indicates the detection of the first edge of CQ in each calibration group.

Table E-7: QDRII SRAM Signal Descriptions (Virtex-4 FPGAs) (Cont'd)

Bus Name	I/O	Width	Description
dbg_cq_first_edge_tap_count	O	6*CQ_WIDTH	A 6-bit tap count for CQ IDELAY in each calibration group. This value determines the number of IDELAY taps incremented for first edge detection. dbg_cq_first_edge_tap_count[5:0] corresponds to CQ[0].
dbg_cq_second_edge_detect	O	CQ_WIDTH	When set to 1, indicates the detection of the second edge of CQ in each calibration group.
dbg_cq_second_edge_tap_count	O	6*CQ_WIDTH	A 6-bit tap count for CQ IDELAY in each calibration group. This value determines the number of IDELAY taps incremented for second edge detection. dbg_cq_second_edge_tap_count[5:0] corresponds to CQ[0].
dbg_cq_tap_sel_done	O	CQ_WIDTH	When set to 1, indicates that the calibration process of the center-aligning CQ with respect to clk_0 in each calibration group.
dbg_cq_tap_count	O	6*CQ_WIDTH	A 6-bit tap count for CQ IDELAY in each calibration group. This value determines the number of IDELAY taps incremented. The maximum counter value cannot be more than 64; since the maximum taps that an IDELAY element can be incremented is only 64 taps.
dbg_data_tap_count	O	6*CQ_WIDTH	A 6-bit tap count for all Data (Q) IDELAYs in each calibration group. The counter value indicates the number of tap delays that are to be applied on all Data (Q) IDELAYs in each calibration group.
dbg_data_tap_sel_done	O	CQ_WIDTH	When set to 1, indicates the completion of delaying all the Data (Q) IDELAYs in the calibration group. The number of taps that are to be delayed is determined by dbg_data_tap_count.
dbg_first_rising	O	CQ_WIDTH	1: The first edge detected is rising edge. 0: The first edge detected is falling edge.
dbg_rdcmd2valid_cnt	O	5*CQ_WIDTH	A 5-bit counter to calculate number of clocks from controller read command to data valid for group of Data (Q) associated with specific CQ.
dbg_dly_cal_done	O	1	When set to 1, indicates the completion of the Data (Q) calibration process.

Virtex-4 FPGA: RLDRAM II

All the debug input port signals are clocked using the design clock frequency (clkglob). Increment and decrement control signals (e.g., dbg_idel_up_all) as well as the IDELAY select signals must be provided synchronously with clkglob.

Note:

1. All Read Data (DQ) in a given calibration group has the same IDELAY tap value.
2. A calibration group is determined by the number of Read Data (DQ) associated with each QK.

Table E-8: RLD RAM II Signal Descriptions (Virtex-4 FPGAs)

Bus Name	I/O	Width	Description
dbg_idel_up_all	I	1	Increments the tap value for all Read Data (DQ) IDELAYs used for read data synchronization. Tap values are incremented by one for every clkglob cycle that this signal is held High.
dbg_idel_down_all	I	1	Decrements the tap value for all Read Data (DQ) IDELAYs used for read data synchronization. Tap values are decremented by one for every clkglob cycle that this signal is held High.
dbg_sel_all_idel_data_qk	I	1	Selects the functionality for dbg_idel_up_data_qk and dbg_idel_down_data_qk: 1: All Read Data (DQ) IDELAYs are adjusted. 0: Only the IDELAYs for all the Read Data (DQ) in a calibration group specified by dbg_sel_idel_data_qk is adjusted. If neither dbg_idel_up_data_qk nor dbg_idel_down_data_qk is active in the clkglob cycle, this signal is a <i>don't care</i> .
dbg_sel_idel_data_qk	I	QK_WIDTH	When any dbg_sel_idel_data_qk bit is set to 1, it determines all the Data (DQ) IDELAYs in a calibration group to vary using dbg_idel_up_data_qk or dbg_idel_down_data_qk. If neither dbg_idel_up_data_qk nor dbg_idel_down_data_qk is active in the clkglob cycle, this signal is a <i>don't care</i> .
dbg_idel_up_data_qk	I	1	Increments the tap value for all Data (DQ) IDELAYs in a calibration group. The Data (DQ) IDELAYs in a calibration group, which are affected, are given by dbg_sel_all_idel_data_qk and dbg_sel_idel_data_qk. Tap value(s) are incremented by one for every clkglob cycle that this signal is held High.
dbg_idel_down_data_qk	I	1	Decrements the tap value for all Data (DQ) IDELAYs in a calibration group. The Data (DQ) IDELAYs in a calibration group, which are affected, are given by dbg_sel_all_idel_data_qk and dbg_sel_idel_data_qk. Tap value(s) are decremented by one for every clkglob cycle that this signal is held High.
dbg_qk_first_edge	O	QK_WIDTH	When set to 1, indicates the detection of the first edge of QK in a calibration group.
dbg_qk_first_edge_tap_count	O	6*QK_WIDTH	A 6-bit tap count for QK IDELAY in each calibration group. This value determines the number of IDELAY taps incremented for first edge detection. dbg_qk_first_edge_tap_count[5:0] corresponds to QK[0].
dbg_qk_second_edge	O	QK_WIDTH	When set to 1, indicates the detection of the second edge of QK in a calibration group.

Table E-8: RLDRAM II Signal Descriptions (Virtex-4 FPGAs) (Cont'd)

Bus Name	I/O	Width	Description
dbg_qk_second_edge_tap_count	O	6*QK_WIDTH	A 6-bit tap count for QK IDELAY in each calibration group. This value determines the number of IDELAY taps incremented for second edge detection. dbg_qk_second_edge_tap_count[5:0] corresponds to QK[0].
dbg_qk_tap_count	O	6*QK_WIDTH	A 6-bit counter for QK IDELAY in each calibration group. This value determines the number of IDELAY taps incremented. The maximum counter value cannot be more than 64, since the maximum taps that an IDELAY element can be incremented is only 64 taps.
dbg_first_rising	O	QK_WIDTH	1: Indicates that the first edge detected is rising edge. 0: Indicates that the first edge detected is falling edge.
dbg_qk_tap_sel_done	O	QK_WIDTH	When set to 1, indicates that the calibration process of the center-aligning clkglob with respect to that particular QK is complete.
dbg_data_tap_count	O	6*QK_WIDTH	A 6-bit tap count for all the Read Data (DQ) IDELAYs in a calibration group. The counter value indicates the number of tap delays that are to be applied on group of Read Data (DQ) IDELAYs.
dbg_data_tap_sel_done	O	QK_WIDTH	When set to 1, indicates the completion of delaying the all the Read Data (DQ) IDELAYs in a calibration group. The number of taps that are to be delayed is determined by dbg_data_tap_count.

Spartan-3 FPGA: DDR/DDR2 SDRAMs

Table E-9: DDR/DDR2 SDRAM Signal Descriptions (Spartan-3 FPGAs)

Signal Name	I/O	Width	Description
dbg_delay_sel	O	5	Tap value from the calibration logic used to delay the strobe and rst_dqs_div.
dbg_rst_calib	O	1	Used to stop new tap_values from calibration logic to strobe and rst_dqs_div during memory read operations.
dbg_phase_cnt	O	5	Phase count gives the number of LUTs in the clock phase.
dbg_cnt	O	6	Counter used in the calibration logic.
dbg_trans_onedtct	O	1	Asserted when the first transition is detected.
dbg_trans_twodtct	O	1	Asserted when the second transition is detected.
dbg_enb_trans_two_dtct	O	1	Enable signal for dbg_trans_twodtct.
vio_out_dqs_en	I	1	Enable signal for strobe tap selection.
vio_out_dqs	I	5	Used to change the tap values for strobes.
vio_out_rst_dqs_div_en	I	1	Enable signal for rst_dqs_div tap selection.
vio_out_rst_dqs_div	I	5	Used to change the tap values for rst_dqs_div.

Adjusting the Tap Delays

The Debug port can be used for dynamic adjustment of tap delays. This can be initiated either through a Xilinx® Virtual I/O (VIO) module or through other custom control logic.

Virtex FPGA Designs

This section describes the procedure for adjusting the IDELAY taps for the DDR2 SDRAM Virtex-5 FPGA design. This tap adjusting procedure is applicable for DDR2 SDRAM and DDR SDRAM Virtex-5 FPGA designs only.

1. If all IDELAY taps used in the DDR2 interface (for all DQ, DQS, and DQS Gate) must be adjusted at once:
 - a. Assert either `dbg_sel_idel_up_all` or `dbg_sel_idel_down_all`. For every `clkdiv` cycle where one or the other of these two signals is asserted, the IDELAY taps are incremented or decremented by 1.
 - b. To exactly control the amount of adjustment when using VIO to control these signals, the user should make sure these control signals are set to generate a single pulse one clock cycle wide when selected.
2. If all DQ IDELAYs must be adjusted at once:
 - a. Set `dbg_sel_all_idel_gate` = 1.
 - b. Use `dbg_idel_up_dq` or `dbg_idel_down_dq` to either increment or decrement all DQ IDELAYs at once. As is the case with `dbg_sel_idel_up_all`, these control signals increment or decrement the IDELAY tap count by 1 for every `clkdiv` cycle they are asserted.
3. If only a specific DQ IDELAY must be adjusted:
 - a. Set `dbg_sel_all_idel_dq` = 0.
 - b. Set `dbg_sel_idel_dq` to indicate the specific DQ IDELAY to be adjusted. For example, for a 32-bit DDR2 interface where DQ[10] must be adjusted, the user sets `dbg_sel_idel_dq[4:0]` = 01010.
 - c. Use `dbg_idel_up_dq` or `dbg_idel_down_dq` to either increment or decrement the specified DQ IDELAY.
4. The procedure for adjusting all or individual DQS or DQS Gate IDELAY tap values is the same as outlined in [step 2](#) and [step 3](#), except that separate ports are provided for DQS and DQS Gate IDELAY adjustment.

This next procedure is for the QDRII SRAM Virtex-5 FPGA design:

1. If all IDELAY taps used in the QDRII interface (for all Read Data (Q) and Strobes (CQ, CQ#)) must be adjusted at once:
 - a. Assert either `dbg_sel_idel_up_all` or `dbg_sel_idel_down_all`. For every `clk0` cycle where one or the other of these two signals is asserted, the IDELAY taps are incremented or decremented by 1.
 - b. To exactly control the amount of adjustment when using VIO to control these signals, the user should make sure these control signals are set to generate a single pulse one clock cycle wide when selected.
2. If all CQ or CQ# IDELAYs must be adjusted at once:
 - a. Use `dbg_idel_up_cq` or `dbg_idel_down_cq` to either increment or decrement all CQ IDELAYs at once, when `dbg_sel_all_idel_cq` is set to 1.

- b. Use `dbg_idel_up_cq_n` or `dbg_idel_down_cq_n` to either increment or decrement all CQ# IDELAYs at once, when `dbg_sel_all_idel_cq_n` is set to 1.
As is the case with `dbg_sel_idel_up_all` or `dbg_sel_idel_down_all`, these control signals increment or decrement the IDELAY tap count by 1 for every `clk0` cycle they are asserted.
 3. If only a specific CQ or CQ# IDELAY must be adjusted:
 - a. Set `dbg_sel_all_idel_cq = 0` and set `dbg_sel_idel_cq` to indicate the specific CQ IDELAY to be adjusted. For example, for a x36 QDRII component interface with a 72-bit data width where CQ[1] must be adjusted, the user sets `dbg_sel_idel_cq[1:0] = 10`.
 - b. Set `dbg_sel_all_idel_cq_n = 0` and set `dbg_sel_idel_cq_n` to indicate the specific CQ# IDELAY to be adjusted. For example, for a x36 QDRII component interface with a 72-bit data width where CQ#[1] must be adjusted, the user sets `dbg_sel_idel_cq_n[1:0] = 10`.
 - c. Use `dbg_idel_up_cq` or `dbg_idel_down_cq` to either increment or decrement the specified CQ IDELAY.
 4. The procedure for adjusting all or calibration group Read Data (Q) IDELAY tap values is the same as outlined in [step 2](#) and [step 3](#), except that separate ports are provided for Read Data (Q) IDELAY adjustment.

The above mentioned tap adjustment procedure is applicable for QDRII SRAM Virtex-5 FPGA designs and DDR SDRAM, DDRII SRAM, RLDRAM II, QDRII SRAM Virtex-4 FPGA designs.

Spartan-3 FPGA Designs

The procedure for adjusting the tap delay values is as follows:

1. Adjust the tap delay values for all the strobes (DQS):
 - a. Set `vio_out_dqs_en = 1`.
 - b. Use `vio_out_dqs[4:0]` to change the tap values (see [Table E-10](#)).

Table E-10: Tap Values for Strobes

<code>vio_out_dqs[4:0]</code>	Tap Value
01111 (0x0F)	Tap 1
10111 (0x17)	Tap 2
11011 (0x1B)	Tap 3
11101 (0x1D)	Tap 4
11110 (0x1E)	Tap 5
11111 (0x1F)	Tap 6

2. Adjust the tap delay values for `rst_dqs_div` (loopback signal):
 - a. Set `vio_out_rst_dqs_div_en = 1`.
 - b. Use `vio_out_rst_dqs_div[4:0]` to change the tap values (see [Table E-11](#)).

Table E-11: Tap Values for Loopback Signal

vio_out_rst_dqs_div[4:0]	Tap Value
01111 (0x0F)	Tap 1
10111 (0x17)	Tap 2
11011 (0x1B)	Tap 3
11101 (0x1D)	Tap 4
11110 (0x1E)	Tap 5
11111 (0x1F)	Tap 6

3. Adjust the tap delay values for all the strobes (DQS) and rst_dqs_div:
 - a. Set vio_out_dqs_en = 1.
 - b. Set vio_out_rst_dqs_div_en = 1.
 - c. Set the tap values for rst_dqs_div and all the strobes from [Table E-10](#) and [Table E-11](#) by changing vio_out_dqs[4:0] and vio_out_rst_dqs_div[4:0].

Sample Control/Monitoring of the Debug Port

HDL code for the Spartan-3, Virtex-4, and Virtex-5 FPGA Debug ports can be generated from MIG by selecting the Debug Signals option. Spartan-3 FPGA designs use VIO, ILA, and ICON cores generated using the ChipScope Pro tool to monitor the calibration signals and tap values, as well as allow dynamic adjustment of the tap delay values. Virtex-4 and Virtex-5 FPGA designs use VIO cores generated using the ChipScope Pro tool to monitor both calibration status and IDELAY tap values, as well as allow dynamic adjustment of the IDELAY tap values.

Analyzing MIG Designs in the ChipScope Analyzer with CDC

Upon implementing MIG designs, a BIT file is generated that can be programmed using the ChipScope™ analyzer. Programming of the BIT file depends on the board specifications. At the start of a ChipScope analyzer project, all of the signals in every core have generic names. Changing the signal names based on the RTL is a hectic task. To avoid this, the MIG tool provides the CDC file in the `par` folder for debug enable designs. The CDC file provided by the MIG tool contains the signal names of all ChipScope analyzer cores that are used in the design top RTL (`<top_module>`). The signal names provided in the CDC file are symmetric with respect to the signals mapped to ChipScope analyzer cores.

The CDC file can be imported after the BIT file is loaded into the FPGA. Upon importing the CDC file, the signal names of all ChipScope analyzer cores in the Signal Browser window are renamed to the names specified in the CDC file. If any changes are made to the RTL design files after generating the design, similar changes need to be made to the CDC file, otherwise the CDC file will not be in symmetry with the RTL.

CDC files are provided for all MIG generated debug enable designs and for the Create Design for Xilinx Reference Boards output option. The signal names provided in the CDC file for multicontroller and multiple-interface designs in various families are as follows:

- For Virtex-4 FPGA multicontroller designs, signal names provided in the CDC file are those of the first controller.
- For Virtex-5 FPGA multicontroller and multiple interface designs, the signal names provided in the CDC file are of the controller that is enabled for debug in the GUI.

Low Power Options

IODELAY Performance Mode

In Virtex®-5 family devices, IODELAY elements can be programmed to consume less power. The HIGH_PERFORMANCE_MODE parameter associated with the IODELAY element can be passed with values either TRUE or FALSE.

When the HIGH_PERFORMANCE_MODE parameter is set to TRUE, it reduces the output jitter of the IODELAY element. This reduction results in a slight increase in power dissipation from the IODELAY element.

When the HIGH_PERFORMANCE_MODE parameter is set to FALSE, it reduces the power dissipation at the output of IODELAY, but with an increase in the output jitter of the IODELAY element.

The jitter value associated with the IODELAY output is related to the maximum design frequency. A higher jitter value results in reduction in maximum design frequency value. [Table G-1](#) shows the maximum design frequency that can be attained when the IODELAY HIGH_PERFORMANCE_MODE parameter value is set to FALSE.

Table G-1: Maximum Design Frequencies for HIGH_PERFORMANCE_MODE

Virtex-5 FPGA Memory Controller Designs	Maximum Design Frequency	
	HIGH_PERFORMANCE_MODE = TRUE	HIGH_PERFORMANCE_MODE = FALSE
DDR2 SDRAM	333 MHz	200 MHz
DDR SDRAM	200 MHz	150 MHz
DDRII SRAM	300 MHz	200 MHz
QDRII SRAM	300 MHz	200 MHz

Notes:

1. Maximum design frequencies for HIGH_PERFORMANCE_MODE using a -3 FPGA speed grade.

The IODELAY HIGH_PERFORMANCE_MODE parameter value can be selected from the MIG FPGA options page. A FALSE parameter value can only be selected when the frequency selected in the memory controller options page is less than or equal to the FALSE mode frequency shown in [Table G-1](#). The maximum design frequency for the FALSE mode remains the same for all the selected FPGA speed grades. If the frequency selected is greater than the FALSE mode frequency range, then the FALSE value selection is not allowed. Instead, the value remains TRUE.

The IODELAY HIGH_PERFORMANCE_MODE parameter appears in the design top RTL file. This parameter is mapped to the lower level RTL modules all the way up to IOB modules where the IODELAY primitive is instantiated. In IOB modules, this parameter is mapped to the IODELAY primitive.

The user can change this parameter value manually in the design top RTL file, if required.

For more information on the IODELAY HIGH_PERFORMANCE_MODE, refer to the *Virtex-5 FPGA User Guide* [\[Ref 10\]](#). For more information on the IODELAY output jitter values, refer to the *Virtex-5 FPGA Data Sheet: DC and Switching Characteristics* [\[Ref 11\]](#).

Pin Mapping for x4 RDIMMs

Table H-1 is an example showing the pin mapping for x4 DDR2 registered DIMMs between the memory data sheet and the user constraints file (UCF).

Table H-1: Pin Mapping for x4 DDR2 DIMMs

Memory Data Sheet	MIG UCF
DQ[63:0]	DQ[63:0]
CB3 - CB0	DQ[67:64]
CB7 - CB4	DQ[71:68]
DQS0, $\overline{\text{DQS0}}$	DQS[0], DQS_N[0]
DQS1, $\overline{\text{DQS1}}$	DQS[2], DQS_N[2]
DQS2, $\overline{\text{DQS2}}$	DQS[4], DQS_N[4]
DQS3, $\overline{\text{DQS3}}$	DQS[6], DQS_N[6]
DQS4, $\overline{\text{DQS4}}$	DQS[8], DQS_N[8]
DQS5, $\overline{\text{DQS5}}$	DQS[10], DQS_N[10]
DQS6, $\overline{\text{DQS6}}$	DQS[12], DQS_N[12]
DQS7, $\overline{\text{DQS7}}$	DQS[14], DQS_N[14]
DQS8, $\overline{\text{DQS8}}$	DQS[16], DQS_N[16]
DQS9, $\overline{\text{DQS9}}$	DQS[1], DQS_N[1]
DQS10, $\overline{\text{DQS10}}$	DQS[3], DQS_N[3]
DQS11, $\overline{\text{DQS11}}$	DQS[5], DQS_N[5]
DQS12, $\overline{\text{DQS12}}$	DQS[7], DQS_N[7]
DQS13, $\overline{\text{DQS13}}$	DQS[9], DQS_N[9]
DQS14, $\overline{\text{DQS14}}$	DQS[11], DQS_N[11]
DQS15, $\overline{\text{DQS15}}$	DQS[13], DQS_N[13]
DQS16, $\overline{\text{DQS16}}$	DQS[15], DQS_N[15]
DQS17, $\overline{\text{DQS17}}$	DQS[17], DQS_N[17]

Table H-2 is an example showing the pin mapping for x4 DDR registered DIMMs between the memory data sheet and the UCF.

Table H-2: Pin Mapping for x4 DDR DIMMs

Memory Data Sheet	MIG UCF
DQ[63:0]	DQ[63:0]
CB3 - CB0	DQ[67:64]
CB7 - CB4	DQ[71:68]
DQS0	DQS[0]
DQS1	DQS[2]
DQS2	DQS[4]
DQS3	DQS[6]
DQS4	DQS[8]
DQS5	DQS[10]
DQS6	DQS[12]
DQS7	DQS[14]
DQS8	DQS[16]
DQS9	DQS[1]
DQS10	DQS[3]
DQS11	DQS[5]
DQS12	DQS[7]
DQS13	DQS[9]
DQS14	DQS[11]
DQS15	DQS[13]
DQS16	DQS[15]
DQS17	DQS[17]